RECORDATION FORM COVER SHEET
PATENTS ONLY

Atty Ref/Docket No.: 303.000001 Patent and Trademark Office

To the Director of the U.S. Patent and Trademark Office: Please record the attached original documents or copy thereof.

1. Name of conveying party(ies):

STMicroelectronics S.r.l. (formerly known as SGS-Thomson Microelectronics S.r.l.)

Additional name(s) of conveying party(ies) attached?

[ ]Yes [X]No

3. Nature of conveyance:

[X] Assignment [ ] Merger
[ ] Security Agreement [ ] Change of Name
[ ] Other

Execution Date: February 6, 2008

2. Name and address of receiving party(ies):

Name: Micron Technology, Inc.

Street Address: 8000 So. Federal Way

City: Boise State: ID Zip: 83716-9632
Country: United States of America

Additional name(s) & address(es) attached? [ ]Yes [X]No

4. Application number(s) or patent number(s):

If this document is being filed together with a new application, the execution date of the application is:

A. Patent Application No.(s)

See Appendix A

B. Patent No.(s)

Additional numbers attached? [X]Yes [ ]No

5. Name and address of party to whom correspondence concerning document should be mailed:

Name: Mark V. Muller

Address:
Schwegman, Lundberg & Woessner, P.A.
P.O. Box 2938
Minneapolis, MN 55402--0938

6. Total number of applications and patents involved: 1

7. Total fee (37 CFR 3.41):$ 120.00

[]Enclosed
[X]Authorized to be charged to deposit account 19-0743

8. Please charge any additional fees or credit any over payments to our Deposit Account No.: 19-0743

DO NOT USE THIS SPACE

9. Statement and signature.
To the best of my knowledge and belief, the foregoing information is true and correct and any attached copy is a true copy of the original document.

Mark V. Muller/Reg. No. 37,509 / Mark V. Muller / JULY 19, 2013
Name of Person Signing Signature Date

Total number of pages including cover sheet: 244

Mail documents to be recorded with required cover sheet information to:
Commissioner of Patents and Trademarks
Mail Stop Assignment Recordation Services
P.O. Box 1450
Alexandria, VA 22313-1450

CH $120.00 190743 0837752

Appendix A STMicroelectronics, S.r.l., (formerly known as SGS-Thomson Microelectronics, S.r.l.) to Micron Technology, Inc.			
Appl. Serial No.	**File Date**	**Docket No**	**Status**
08/377,524	1/20/1995	NMXS-0085.00/US	Issued
08/877,066	6/17/1997	NMXS-0340.00/US	Issued
10/060,076	1/29/2002	NMXS-0704.01/US	Issued

ASSIGNMENT

WHEREAS, STMicroelectronics S.r.l., (formerly known as SGS-Thomson Microelectronics S.r.l.), a corporation organized under the laws of Italy, having a place of business at Via C. Olivetti, 2-20041 Agrate Brianza, Milano, Italy (hereinafter referred to as "Assignor") has rights in and to the following:

LISTED IN EXHIBIT A

(said patents, patent applications and invention disclosures listed in Exhibit A being hereinafter referred to as "SAID PATENT RIGHTS"); and

WHEREAS, Assignor is a wholly owned subsidiary of STMicroelectronics NV, a Dutch corporation organized under the laws of The Netherlands, acting through its Swiss branch, having an office at 39 Chemin du Champ-des-Filles, 1228 Plan-les-Ouates, Geneva, Switzerland (hereinafter referred to as "Assignee");

WHEREAS, Assignee requested Assignor to develop certain technology for Assignee;

WHEREAS, Assignee sponsored, paid for and is the equitable and beneficial owner of all resulting intellectual property resulting from such technology development, including SAID PATENT RIGHTS and related rights;

WHEREAS, Assignee and Assignor recognize that Assignee already owns all equitable and beneficial ownership in SAID PATENT RIGHTS and related rights;

WHEREAS, Assignor now desires to transfer the legal title in and to SAID PATENT RIGHTS to Assignee and confirm all ownership in Assignee to SAID PATENT RIGHTS and related rights that may have unintentionally remained in Assignor; and

WHEREAS, Assignee desires to perfect registration in Assignee's name all the above mentioned rights, title and interest in and to SAID PATENT RIGHTS and related rights.

NOW, THEREFORE, for and in consideration of good and valuable consideration the receipt, sufficiency and adequacy of which are hereby acknowledged, Assignor does hereby transfer and assign to Assignee legal title, and any and all rights it may own (beyond said legal title, if any) in and to SAID PATENT RIGHTS, together with any and all continuations, continuations-in-part, continuing prosecution applications, requests for continuing examinations, divisions, reissues, reexaminations, extensions, registrations, and foreign counterparts of any item in any of the foregoing (to the extent not already owned by Assignee), together

with the right to sue for and be entitled to any damages, injunctive relief, and any other remedies of any kind for past, current and future infringement thereof.

IN WITNESS WHEREOF, Assignor has caused this Assignment to be executed by its duly authorized officer on this 6th day of February, 2008.

STMicroelectronics S.r.l.

By: _____

Printed Name: ALDO ROMANO

Title: CEO and MANAGING DIRECTOR

STMicroelectronics Srl

Direttore Generale
(Ing. Pietro Palella)

STMicroelectronics NV

By: _____

Printed Name: Pierre Ellicott

Title: Corporate General Counsel

EXHIBIT A

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
6300195	98-AG-247	US	Granted		98513930
	98-AG-247	IT	Granted	1032035	98830100.6
	98-AG-247	GB	Granted	1032035	98830100.6
6448847	00-AG-004	US	Granted		09786823
	00-AG-004	IT	Granted	1319841	TO00A000148
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	00-AG-005	GB	Granted	1158854	00830105.3
	00-AG-005	DE	Granted	1158854	00830105.3
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	00-AG-009	EP	Publication		00830546.8
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	00-AG-014	JP	Publication		01207874
	00-AG-014	EP	Publication		00890504.7
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	01-AG-346	IT	Publication		MI02A00831
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US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
6,801,466	01-CT-076	US	Granted		10331147
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US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
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6922362	02-CT-161	US	Granted		10386552
	02-CT-161	IT	Filing		MI02A02192
6927991	02-PA-237	US	Granted		10653459
	02-PA-237	IT	Filing		VA02A000045
6885584	02-PA-322	US	Granted		10748447
	02-PA-322	IT	Granted	1435624	02425802.2
	02-PA-322	GB	Granted	1435624	02425802.2
7092277	03-AG-109	US	Granted		10928764
	03-AG-109	EP	Publication		03077667.8
7001800	03-AG-112	US	Granted		10911220
	03-AG-112	EP	Publication		03625632.3
5534448	92-AG-047	US	Granted		08202408
5589701	92-AG-047	US	Granted		08486747
5927403	93-AG-008	US	Granted		08479552
5795621	93-AG-008	US	Granted		08751244
	93-AG-008	IT	Granted	0627763	93830243.7
	93-AG-008	GB	Granted	0627763	93830243.7
	93-AG-008	FR	Granted	0627763	93830243.7
	93-AG-008	DE	Granted	69333722	93830243.7
5549044	93-AG-022	US	Granted		08511941
5536157	93-AG-032	US	Granted		08347653
5612641	93-AG-035	US	Granted		08380309
5659501	93-AG-039	US	Granted		08639931
5818760	93-AG-039	US	Granted		08871226
	93-AG-039	JP	Granted	2718902	28634994
	93-AG-039	GB	Granted	0654791	93830464.9
	93-AG-039	FR	Granted	0654791	93830464.9
5986114	93-AG-045	US	Granted		08349783
5644528	93-AG-046	US	Granted		08635465
5659508	93-AG-047	US	Granted		08381999
5493531	93-AG-048	US	Granted		08350861
5708801	93-AG-048	US	Granted		08802237
5559743	93-AG-050	US	Granted		08412550
5546054	93-AG-051	US	Granted		08377524
	93-AG-051	JP	Granted	2743853	720895
	93-AG-051	IT	Granted	0666486	94830022.3
	93-AG-051	GB	Granted	0666485	94830022.3
	93-AG-051	FR	Granted	0666485	94830022.3
	93-AG-051	DE	Granted	69413793	94830022.3
5515332	93-AG-052	US	Granted		08391160
5663921	93-AG-053	US	Granted		08391159
5717642	93-AG-054	US	Granted		08803915
5687135	93-AG-055	US	Granted		08700126
5594793	93-AG-057	US	Granted		08365510
5768115	93-AG-058	US	Granted		08555922
5499217	93-AG-059	US	Granted		08348461
5927790	93-AG-060	US	Granted		08408589
5717598	93-AG-061	US	Granted		08345530
5600500	93-AG-062	US	Granted		08381530
5600594	93-AG-063	US	Granted		08412326
5687124	93-AG-064	US	Granted		08521304
5585820	93-AG-065	US	Granted		08386211
5748548	93-AG-065	US	Granted		08718132
	93-AG-065	IT	Granted	0661713	93830537.2
	93-AG-065	GB	Granted	0661713	93830537.2
	93-AG-065	FR	Granted	0661713	93830537.2
	93-AG-065	DE	Granted	69326277	93830537.2
6392459	93-AG-066	US	Granted		08347788
5917358	93-AG-067	US	Granted		08395361
5490017	93-AG-068	US	Granted		08386212
5519858	93-AG-071	US	Granted		08386259
5859516	93-AG-072	US	Granted		08388211
5905877	93-AG-072	US	Granted		08831046
5548554	93-AG-073	US	Granted		08386154
5541884	93-AG-075	US	Granted		08391147
	93-AG-075	JP	Granted	2737686	753777
5532972	93-AG-077	US	Granted		08391920
5563826	93-AG-079	US	Granted		08422813
5638327	93-AG-080	US	Granted		08412192
5802788	93-AG-081	US	Granted		08389599
5541880	93-AG-082	US	Granted		08411904
5678990	93-AG-085	US	Granted		08367538
5590075	94-AG-003	US	Granted		08479081
5636716	94-AG-019	US	Granted		08794865
5715204	94-AG-024	US	Granted		08432838
5898028	94-AG-026	US	Granted		08468282
6168587	94-AG-044	US	Granted		08677126
6531714	94-AG-044	US	Granted		08211065
	94-AG-044	IT	Granted	0720223	94830591.7
	94-AG-044	DE	Granted	69452352	94830591.7
5682349	94-AG-067	US	Granted		08454650
	94-AG-067	JP	Granted	3725581	7145034
5719814	94-AG-083	US	Granted		08503303
5920778	94-AG-083	US	Granted		08712373
	94-AG-083	JP	Granted	3024519	7197943
5761222	94-AG-088	US	Granted		08508161
	94-AG-088	JP	Granted	3704104	7254046
5726492	94-AG-096	US	Granted		08639122
5982806	94-AG-096	US	Granted		09013141
6144588	94-AG-101	US	Granted		09150802
	94-AG-101	GB	Granted	0715912	94830554.5
5859360	94-AG-102	US	Granted		08607779
	94-AG-102	US	Unfiled (do not use!)		
5644526	94-AG-103	US	Granted		08638302

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
5710738	94-AG-105	US	Granted		08476547
5639834	94-AG-109	US	Granted		08580324
	94-AG-109	IT	Granted	0713221	94830538.8
5650361	94-AG-112	US	Granted		08628587
	94-AG-112	GB	Granted	0736876	95830153.5
	94-AG-112	FR	Granted	0736876	95830153.5
5742167	94-AG-113	US	Granted		08580090
5657276	94-AG-114	US	Granted		08649468
	94-AG-114	GB	Granted	0743648	95830211.9
	94-AG-114	FR	Granted	0743648	95830211.9
5731716	94-AG-115	US	Granted		08592122
	94-AG-125	IT	Granted	0714133	94830544.8
	94-AG-125	DE	Granted	0714133	94830544.8
5717628	94-AG-132	US	Granted		08642325
5812913	94-AG-134	US	Granted		08539831
	94-AG-134	JP	Filing		7274935
5896461	94-AG-136	US	Granted		08521656
5798676	94-AG-145	US	Granted		08649857
5849713	94-AG-143	US	Granted		08084518
	94-AG-143	GB	Granted	741387	95830184.8
	94-AG-143	FR	Granted	741387	95830184.8
6004847	94-AG-164	US	Granted		08857097
6248639	94-AG-164	US	Granted		09300029
	94-AG-164	GB	Granted	0751559	95830281.2
5856221	94-AG-165	US	Granted		08670179
	94-AG-165	GB	Granted	0751560	95830282.0
6114203	94-AG-166	US	Granted		08644892
	94-AG-166	JP	Granted	30684454	854682
5894065	94-AG-176	US	Granted		08802519
6100558	94-AG-178	US	Granted		08856155
5812017	94-AG-189	US	Granted		08667328
	94-AG-189	IT	Granted	716388	94830563.9
	94-AG-189	DE	Granted	69430906	94830563.9
5914887	94-AG-191	US	Granted		08831574
	94-AG-191	JP	Granted	2963047	861312
	94-AG-191	IT	Granted	0737643	95830153.3
	94-AG-191	GB	Granted	0737643	95830153.3
	94-AG-191	FR	Granted	0737643	95830153.3
	94-AG-191	DE	Granted	69518826	95830153.3
5764670	94-AG-192	US	Granted		08891706
	94-AG-192	JP	Unfiled (do not use!)		
	94-AG-192	GB	Granted	0757357	95830354.7
	94-AG-192	FR	Granted	0757357	95830354.7
5841720	94-AG-194	US	Granted		08724495
	94-AG-194	GB	Granted	768672	95830405.7
	94-AG-194	FR	Granted	768672	95830405.7
5701265	95-AG-003	US	Granted		08593650
5838612	95-AG-009	US	Granted		08699072
	95-AG-004	EP	Publication		95830127.7
5734810	95-AG-012	US	Granted		08690530
	95-AG-012	GB	Granted	0757358	95830357.0
	95-AG-012	FR	Granted	0757358	95830357.0
5878221	95-AG-032	US	Granted	RE38166	09410164
	95-AG-032	JP	Granted	2857849	868710
	95-AG-032	GB	Granted	734024	95830110.3
	95-AG-032	FR	Granted	734024	95830110.3
5894363	95-AG-033	US	Granted		08698975
	95-AG-033	GB	Granted	747903	95830172.3
	95-AG-033	FR	Granted	747903	95830172.3
5737268	95-AG-036	US	Granted		08694431
	95-AG-036	GB	Granted	0756285	95830335.4
	95-AG-036	FR	Granted	0756285	95830335.4
5847584	95-AG-037	US	Granted		08828956
	95-AG-037	GB	Granted	0757352	95830360.4
	95-AG-037	FR	Granted	0757352	95830360.4
5760497	95-AG-038	US	Granted		08684192
	95-AG-038	GB	Granted	0756220	95830335.6
	95-AG-038	FR	Granted	0756220	95830335.6
6,507,067	95-AG-042	US	Granted		08892938
	95-AG-042	IT	Abandon requested	0758129	95830361.3
	95-AG-042	GB	Abandon requested	0758129	95830361.3
	95-AG-042	FR	Abandon requested	0758129	95830361.3
	95-AG-042	EP	Granted	0758129	95830361.3
	95-AG-042	DE	Abandon requested	0758129	95830361.3
5665502	95-AG-056	US	Granted		08685862
5920506	95-AG-056	US	Granted		08881713
	95-AG-056	GB	Granted	750314	95830253.1
	95-AG-056	FR	Granted	750314	95830253.1
5781474	95-AG-057	US	Granted		08722178
	95-AG-057	GB	Granted	760255	95830406.5
	95-AG-057	FR	Granted	760255	95830406.5
5784314	95-AG-058	US	Granted		08579856
	95-AG-058	GB	Granted	753859	95830302.6
	95-AG-058	FR	Granted	753859	95830302.6
5844404	95-AG-059	US	Granted		08720481
	95-AG-059	GB	Granted	0766256	95830407.3
	95-AG-059	FR	Granted	0766256	95830407.3
5948013	95-AG-060	US	Granted		08821618
6137725	95-AG-065	US	Granted		08200837
6320792	95-AG-060	US	Granted		08583334
	95-AG-060	GB	Granted	798735	96830174.7
	95-AG-060	FR	Granted	798735	96830174.7
5822247	95-AG-061	US	Granted		08775111
	95-AG-061	GB	Granted	782149	96830352.9
	95-AG-061	FR	Granted	782149	96830352.9
5864513	95-AG-082	US	Granted		08827409
	95-AG-082	GB	Granted	0798740	96830163.0
6821806	95-AG-083	US	Granted		08787494
	95-AG-083	IT	Abandon requested	0786777	96830026.9
5654496	95-AG-091	US	Granted		08554406
	95-AG-091	FR	Granted	796379	96830327.2

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
5754483	95-AG-092	US	Granted		08618033
	95-AG-092	JP	Publication		975489
	95-AG-092	IT	Abandon requested	798729	96830180.6
	95-AG-092	GB	Granted	798729	96830180.6
	95-AG-092	FR	Granted	798729	96830180.6
6438689	95-AG-094	US	Granted		08813667
	95-AG-094	JP	Publication		969619
	95-AG-094	GB	Granted	797209	96830129.1
5729490	95-AG-096	US	Granted		08690059
	95-AG-095	IT	Granted	757355	95830347.1
	95-AG-095	GB	Granted	757355	95830347.1
	95-AG-095	FR	Granted	757355	95830347.1
	95-AG-095	DE	Granted	757355	95830347.1
6040734	95-AG-097	US	Granted		09139630
	95-AG-097	GB	Granted	782268	96830353.7
	95-AG-097	FR	Granted	782268	96830353.7
5724290	95-AG-098	US	Granted		08774110
	95-AG-098	EP	Publication		96830686.9
6157054	95-AG-086	US	Granted		09092179
	95-AG-099	IT	Granted	0772200	95830461.0
	95-AG-099	GB	Granted	0772200	95830461.0
	95-AG-099	EP	Publication		03012504.1
6195201	95-AG-100	US	Granted		08687145
6468750	95-AG-100	US	Granted		09788744
	95-AG-100	GB	Granted	756288	95830317.4
	95-AG-100	FR	Granted	756288	95830317.4
5754476	95-AG-102	US	Granted		08751289
	95-AG-102	GB	Granted	0772282	95830455.0
	95-AG-102	FR	Granted	0772282	95830455.0
5905387	95-AG-105	US	Granted		08742978
6778012	95-AG-106	US	Granted		08871848
	95-AG-106	GB	Granted	766174	96830408.1
	95-AG-106	FR	Granted	766174	96830408.1
5801988	95-AG-107	US	Granted		08835031
	95-AG-107	IT	Abandon requested	0798743	96830166.9
	95-AG-107	GB	Granted	0798743	96830166.9
	95-AG-107	FR	Granted	0798743	96830166.9
5821786	95-AG-108	US	Granted		08790892
	95-AG-108	GB	Granted	788114	96830045.7
5838619	95-AG-111	US	Granted		08828039
	95-AG-111	GB	Granted	0798842	96830167.1
	95-AG-111	FR	Granted	0798842	96830167.1
6020980	95-AG-117	US	Granted		08807183
	95-AG-117	GB	Granted	0779842	95830520.3
	95-AG-117	FR	Granted	0779842	95830520.3
5977597	95-AG-137	US	Granted		08824668
	95-AG-137	GB	Granted	0798785	96830175.4
6448136	95-AG-155	US	Granted		09548782
6222245	95-AG-158	US	Granted		08799897
	95-AG-158	IT	Granted	0772246	95830459.4
	95-AG-158	GB	Granted	0772246	95830459.4
	95-AG-158	FR	Granted	0772246	95830459.4
5926416	95-AG-165	US	Granted		08807574
	95-AG-166	IT	Publication		96810088.9
	95-AG-166	GB	Publication		96830088.9
5817557	95-AG-168	US	Granted		08792893
	95-AG-168	FR	Granted	0788144	96830039.2
5923975	95-AG-173	US	Granted		08784967
	95-AG-173	IT	Abandon requested	785570	96830021.0
	95-AG-173	GB	Granted	785570	96830021.0
	95-AG-173	FR	Granted	785570	96830021.0
5859795	95-AG-185	US	Granted		08791348
	95-AG-185	JP	Publication		916819
	95-AG-186	IT	Granted	788113	96830044.2
	95-AG-186	FR	Granted	788113	96830044.2
	95-AG-187	WO	Publication		IT9600198
6131121	95-AG-187	US	Granted		08202657
	95-AG-187	JP	Publication		10502636
	96-AG-187	GB	Granted	906522	969937493.3
	95-AG-187	FR	Granted	906522	969937493.3
5936921	95-AG-189	US	Granted		08883822
	95-AG-189	JP	Notice of Allowance		9172303
	96-AG-193	GB	Granted	0817200	96830371.9
	95-AG-193	FR	Granted	0817200	96830371.9
	95-AG-195	WO	Publication		IT9600199
6097628	95-AG-196	US	Granted		08202656
	96-AG-195	JP	Publication		10502637
	95-AG-195	GB	Granted	906523	969937494.1
	95-AG-195	FR	Granted	906523	969937494.1
5854764	95-AG-198	US	Granted		08823804
	95-AG-198	JP	Publication		9861/2
	95-AG-199	GB	Granted	797145	96830144.0
	95-AG-198	FR	Granted	797145	96830144.0
5936450	95-AG-159	US	Granted		08843766
	95-AG-199	GB	Granted	806773	96830267.9
	95-AG-199	FR	Granted	806773	96830267.9
5817753	95-AG-200	US	Granted		08845916
6059187	95-AG-200	US	Granted		09209313
5818783	95-AG-201	US	Granted		08774860
	95-AG-201	GB	Granted	782145	95830554.2
	95-AG-201	FR	Granted	782145	95830554.2
5886949	95-AG-202	US	Granted		08978665
	95-AG-202	GB	Granted	848784	96830598.7
6195290	95-AG-208	US	Granted		08407135
	95-AG-203	US	Limited (do not use!)		
	95-AG-203	GB	Granted	782148	95830245.5
	95-AG-203	FR	Granted	782148	95830245.5
5721707	95-AG-204	US	Granted		08787907
	95-AG-204	IT	Abandon requested	786779	96830025.1
	95-AG-204	GB	Granted	786779	96830025.1
	95-AG-204	FR	Granted	786779	96830025.1
5784319	95-AG-205	US	Granted		08788510
	95-AG-205	IT	Abandon requested	786778	96830024.4
	95-AG-205	IT	Abandon requested	786778	96830024.4

US Pat No	ST Ref	Country	Status	Non-US Pat. number	Filing Number
	95-AG-205	GB	Granted	786778	96830024.4
	95-AG-205	GB	Granted	786778	96830024.4
	95-AG-205	FR	Granted	786778	96830024.4
	95-AG-205	FR	Granted	786778	96830024.4
6005411	95-AG-210	US	Granted		08777296
	95-AG-210	GB	Granted	0782144	96830552.8
	95-AG-210	FR	Granted	0782144	96830552.8
5757719	95-AG-211	US	Granted		08868208
	95-AG-211	GB	Granted	811986	96830318.0
	95-AG-211	FR	Granted	811986	96830318.0
5795275	95-AG-213	US	Granted		08791700
	95-AG-213	IT	Abandon requested	786231	96830043.4
	95-AG-213	GB	Granted	786231	96830043.4
6057591	95-AG-215	US	Granted		09014437
6210994	95-AG-216	US	Granted		09534675
	95-AG-216	JP	Publication		1018490
	95-AG-216	IT	Abandon requested	0856886	97830029.1
	95-AG-216	GB	Granted	0856886	97830029.1
	95-AG-216	FR	Granted	0856886	97830029.1
5917758	95-AG-223	US	Granted		08847385
	96-AG-223	GB	Granted	0805453	96830239.8
5678049	95-AG-224	US	Granted		08840056
	95-AG-224	GB	Granted	0805452	96830238.0
	95-AG-224	FR	Granted	0805452	96830238.0
5777941	95-AG-225	US	Granted		08855732
	95-AG-225	GB	Granted	0813606	96830275.2
	95-AG-225	FR	Granted	0813606	96830275.2
5751654	95-AG-226	US	Granted		08826223
	95-AG-226	GB	Granted	0798742	96830165.3
6148413	95-AG-228	US	Granted		08835030
	95-AG-228	GB	Granted	0798726	96830161.4
5841778	95-AG-230	US	Granted		08791746
5946237	95-AG-231	US	Granted		08826489
6212096	95-AG-231	US	Granted		09351803
	95-AG-231	IT	Abandon requested	0798727	96830162.2
	95-AG-231	GB	Granted	0798727	96830162.2
5831891	95-AG-234	US	Granted		08812595
	95-AG-234	GB	Granted	797208	96830128.3
	95-AG-234	FR	Granted	797208	96830128.3
5859816	95-AG-235	US	Granted		08826009
	95-AG-235	GB	Granted	0798730	96830169.7
	95-AG-235	FR	Granted	0798730	96830169.7
5850992	95-AG-008	US	Granted		08833925
6074816	95-AG-009	US	Granted		09164761
	96-AG-008	GB	Granted	9802588	96830212.5
5891001	96-AG-014	US	Granted		08825098
	96-AG-014	GB	Granted	0798741	96830165.5
	96-AG-014	FR	Granted	0798741	96830165.5
5939935	96-AG-015	US	Granted		08855748
5929674	96-AG-016	US	Granted		08846757
	96-AG-016	IT	Abandon requested	0805556	96830247.1
	96-AG-016	GB	Granted	0805556	96830247.1
5822259	96-AG-017	US	Granted		08848755
	96-AG-017	IT	Abandon requested	0805771	96830248.9
	96-AG-017	GB	Granted	0805771	96830248.9
5850797	96-AG-018	US	Granted		08849753
	96-AG-018	IT	Abandon requested	805456	96830242.2
	96-AG-018	GB	Granted	805456	96830242.2
6018255	96-AG-019	US	Granted		08882563
6064073	96-AG-019	US	Granted		09432842
	96-AG-019	GB	Granted	809254	96830299.2
6128225	96-AG-020	US	Granted		08879017
	96-AG-020	JP	Publication		9161556
	96-AG-020	GB	Granted	814480	96830344.8
	96-AG-020	FR	Granted	814480	96830344.8
5903498	96-AG-021	US	Granted		08877927
	96-AG-021	GB	Publication		96830345.5
	96-AG-021	EP	Publication		96830345.5
5903500	96-AG-022	US	Granted		08877921
	96-AG-022	JP	Publication		9191537
	96-AG-022	GB	Granted	814482	96830346.1
	96-AG-022	FR	Granted	814482	96830346.1
6560247	96-AG-023	US	Granted		09016954
	96-AG-023	US	Filing		08900328
	96-AG-023	IT	Granted	0822601	96830420.4
	96-AG-023	GB	Granted	0822601	96830420.4
6184741	96-AG-024	US	Granted		08900166
	96-AG-024	GB	Granted	822556	96830441.0
	96-AG-024	FR	Granted	822556	96830441.0
6016073	96-AG-025	US	Granted		08995068
6075422	96-AG-026	US	Granted		08946727
6215328	96-AG-027	US	Granted		08899228
	96-AG-027	FR	Granted	821362	96830411.3
6060753	96-AG-028	US	Granted		08889653
6150844	96-AG-029	US	Granted		08888811
	96-AG-029	GB	Granted	821484	96830413.9
	96-AG-029	FR	Granted	821484	96830413.9
5946238	96-AG-032	US	Granted		08877065
	96-AG-032	GB	Granted	814484	96830348.7
5923078	96-AG-033	US	Granted		08811577
6130572	96-AG-034	US	Granted		09012391
	96-AG-034	IT	Abandon requested	856786	97830014.3
	96-AG-034	GB	Granted	856786	97830014.3
5816484	96-AG-035	US	Granted		08811869
	96-AG-035	GB	Granted	794618	96830095.2
	96-AG-035	FR	Granted	794618	96830096.2
6055664	96-AG-036	US	Granted		08816766
	96-AG-036	GB	Granted	0797147	96830136.6
	96-AG-036	FR	Granted	0797147	96830136.6
5959476	96-AG-049	US	Granted		08828791
	96-AG-049	GB	Granted	0798725	96830177.0
5901087	96-AG-050	US	Granted		08828790
6078523	96-AG-050	US	Granted		09040941
	96-AG-050	GB	Granted	0798732	96830164.8

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
	96-AG-050	FR	Granted	0798732	96830164.6
5886945	96-AG-051	US	Granted		08825138
	96-AG-051	GB	Granted	0798744	96830176.2
5889723	96-AG-052	US	Granted		08826008
	96-AG-052	IT	Granted	0800259	96830178.8
	96-AG-052	GB	Granted	0800259	96830178.8
	96-AG-052	FR	Granted	0800259	96830178.8
	96-AG-052	DE	Granted	69616019	96830178.8
5805435	96-AG-053	US	Granted		08824958
	96-AG-053	GB	Granted	0800260	96830179.6
	96-AG-053	FR	Granted	0800260	96830179.6
5754479	96-AG-054	US	Granted		08835294
	96-AG-054	IT	Abandon requested	0800177	96830193.7
	96-AG-054	GB	Granted	0800177	96830193.7
5864500	96-AG-055	US	Granted		08835296
	96-AG-055	IT	Abandon requested	0800178	96830191.1
	96-AG-055	GB	Granted	0800178	96830191.1
	96-AG-055	FR	Granted	0800178	96830191.1
6175821	96-AG-056	US	Granted		08833336
	96-AG-056	IT	Abandon requested	0800176	96830192.9
	96-AG-056	GB	Granted	0800176	96830192.9
5959917	96-AG-057	US	Granted		08819519
	96-AG-057	GB	Granted	0797144	96830143.2
	96-AG-057	FR	Granted	0797144	96830143.2
5838623	96-AG-058	US	Granted		08841904
5936907	96-AG-058	US	Granted		09183469
	96-AG-058	GB	Granted	0802541	96830216.6
	96-AG-058	FR	Granted	0802541	96830216.6
5839710	96-AG-059	US	Granted		08842835
	96-AG-059	IT	Granted	0802483	96830217.4
	96-AG-059	GB	Granted	0802483	96830217.4
5812467	96-AG-060	US	Granted		08841903
	96-AG-060	GB	Granted	0802482	96830215.8
	96-AG-060	FR	Granted	0802482	96830215.8
5864562	96-AG-061	US	Granted		08859859
	96-AG-061	GB	Granted	0811917	96830323.0
5867504	96-AG-062	US	Granted		08889367
	96-AG-062	GB	Granted	0811988	96830326.3
5968183	96-AG-063	US	Granted		08868214
	96-AG-063	IT	Granted	0811918	96830324.8
5831915	96-AG-064	US	Granted		08868213
6081273	96-AG-079	US	Granted		08835347
5998825	96-AG-092	US	Granted		08877922
	96-AG-092	GB	Granted	814483	96830347.9
	96-AG-092	FR	Granted	814483	96830347.9
5999449	96-AG-094	US	Granted		09016874
	96-AG-094	GB	Granted	825611	96830455.0
	96-AG-094	FR	Granted	825611	96830455.0
5946235	96-AG-096	US	Granted		08940279
6238592	96-AG-098	US	Granted		09373813
6152802	96-AG-095	US	Granted		09836397
	96-AG-095	GB	Granted	833257	96830492.3
	96-AG-095	FR	Granted	833257	96830492.3
6046519	96-AG-101	US	Granted		08900424
5965578	96-AG-103	US	Granted		09034499
	96-AG-103	GB	Granted	0831492	96830475.8
	96-AG-103	FR	Granted	0831492	96830475.8
5864762	96-AG-104	US	Granted		08861368
	96-AG-104	GB	Granted	0840327	96830553.2
6239242	96-AG-111	US	Granted		08987454
6472750	96-AG-111	US	Granted		09645711
6054734	96-AG-114	US	Granted		09960956
6147380	96-AG-114	US	Granted		09521887
6399444	96-AG-114	US	Granted		09521876
6710394	96-AG-114	US	Granted		10159706
6841445	96-AG-114	US	Granted		10792308
	96-AG-114	EP	Publication		96830493.1
5994231	96-AG-115	US	Granted		08996920
6156637	96-AG-116	US	Granted		08997403
6537739	96-AG-116	US	Granted		09687217
6803837	96-AG-124	US	Granted		09940119
6073906	96-AG-124	US	Granted		09203798
	96-AG-124	JP	Filing		9263781
	96-AG-124	GB	Granted	833340	96830494.9
	96-AG-124	FR	Granted	833340	96830494.9
5946666	96-AG-125	US	Granted		09032282
6081911	96-AG-131	US	Granted		08866642
5988954	96-AG-132	US	Granted		09960925
5810901	96-AG-147	US	Granted		08868283
	96-AG-147	IT	Abandon requested	1289863	MI97A000009
5903166	96-AG-153	US	Granted		08811548
5890526	96-AG-155	US	Granted		09027343
6071778	96-AG-155	US	Granted		09399955
	96-AG-155	IT	Abandon requested	1289885	MI97A000057
6188121	96-AG-157	US	Granted		09119115
	96-AG-157	EP	Publication		97830384.0
5795699	96-AG-158	US	Granted		08811366
	96-AG-158	IT	Abandon requested	1289864	MI97A000010
6100740	96-AG-159	US	Granted		08957685
6320400	96-AG-159	US	Granted		09911258
6525591	96-AG-159	US	Granted		09558058
5864503	96-AG-165	US	Granted		08886531
6130165	96-AG-168	US	Granted		08997409
6380582	96-AG-168	US	Granted		09328406
	96-AG-168	EP	Publication		98830649.8
5999077	96-AG-169	US	Granted		08998854
6101124	96-AG-169	US	Granted		09327111
6284565	96-AG-169	US	Granted		09387103
5876933	96-AG-203	US	Granted		08807799
6353243	96-AG-203	US	Granted		09356080
	96-AG-203	IT	Granted	08924301	97830359.2
	96-AG-203	GB	Granted	08924301	97830359.2
	96-AG-203	FR	Granted	08924301	97830359.2
6115801	96-AG-204	US	Granted		09049868

US Pat No	ST Ref	Country	Status	Non-US Pat. number	Filing Number
	95-AG-204	IT	Abandon requested	867885	97890151.3
	95-AG-204	GB	Granted	867885	97890151.3
	95-AG-204	FR	Granted	867885	97890151.3
5880993	95-AG-215	US	Granted		08941882
	95-AG-215	JP	Filing		9266534
	95-AG-215	GB	Granted	0833348	96306612.6
	95-AG-215	FR	Granted	0833348	96306612.6
5915185	95-AG-216	US	Granted		09062859
	95-AG-216	JP	Publication		10109568
	95-AG-216	EP	Publication		97830182.8
	95-AG-219	IT	Granted	953984	96830265.9
	95-AG-219	GB	Granted	953984	96830265.9
5888836	96-AG-228	US	Granted		08890926
5959902	96-AG-230	US	Granted		09030804
	96-AG-230	IT	Abandon requested	862183	97830085.3
	96-AG-230	GB	Granted	862183	97830085.3
	96-AG-230	FR	Granted	862183	97830085.3
6063663	96-AG-238	US	Granted		09139909
	96-AG-239	IT	Granted	0902465	97830428.5
	96-AG-239	GB	Granted	0902465	97830428.5
	96-AG-240	IT	Granted	1293810	MI97A01682
6326266	96-AG-242	US	Granted		09141842
	96-AG-242	JP	Publication		10242144
	96-AG-242	EP	Publication		97830427.7
6888225	97-AG-008	US	Granted		10323961
6061288	97-AG-018	US	Granted		09058720
	97-AG-018	IT	Abandon requested	0869506	97830160.4
	97-AG-018	GB	Granted	0869506	97830160.4
6075718	97-AG-019	US	Granted		09059588
	97-AG-019	IT	Abandon requested	1291209	TO97A000227
6212126	97-AG-023	US	Granted		09059382
	97-AG-023	IT	Publication		TO98A000843
6016271	97-AG-024	US	Granted		09141250
	97-AG-024	IT	Abandon requested	899742	97830435.0
	97-AG-024	GB	Granted	899742	97830435.0
	97-AG-024	FR	Granted	899742	97830435.0
6134270	97-AG-027	US	Granted		09130720
6437395	97-AG-027	US	Granted		09776105
	97-AG-027	IT	Granted	1294312	MI97A01902
6187683	97-AG-030	US	Granted		09059740
	97-AG-030	EP	Publication		03077897.8
6195283	97-AG-034	US	Granted		09076013
	97-AG-034	IT	Granted	0877386	97830215.4
	97-AG-034	GB	Granted	0877386	97830215.4
6538190	97-AG-037	US	Granted		09175220
	97-AG-037	GB	Granted	0911747	97830425.8
6378909	97-AG-040	US	Granted		09459754
	97-AG-040	IT	Granted	1304059	MI98A002843
6195288	97-AG-051	US	Granted		09350756
	97-AG-051	IT	Granted	974976	98830438.2
	97-AG-051	GB	Granted	974976	98830438.2
6081448	97-AG-055	US	Granted		09182639
	97-AG-055	IT	Abandon requested	0905712	97830477.2
	97-AG-055	GB	Granted	0905712	97830477.2
6359406	97-AG-072	US	Granted		09311258
	97-AG-072	IT	Granted	1301180	MI98A001123
6330188	97-AG-073	US	Granted		09413383
	97-AG-073	IT	Publication		TO98A000839
6122200	97-AG-074	US	Granted		09200002
	97-AG-074	EP	Publication		97830825.6
	97-AG-075	IT	Granted	1293644	TO97A000687
6362658	97-AG-083	US	Granted		09716747
	97-AG-083	IT	Granted	1313847	MI99A002485
6059822	97-AG-088	US	Granted		09181230
	97-AG-088	EP	Notification 5144		97830550.8
6239048	97-AG-115	US	Granted		09343207
	97-AG-115	IT	Granted	1306911	MI98A001504
6431164	97-AG-130	US	Granted		09159322
	97-AG-130	EP	Publication		97830467.3
5920059	97-AG-131	US	Granted		08927391
5994948	97-AG-132	US	Granted		08921930
6197606	97-AG-133	US	Granted		09108432
	97-AG-133	EP	Publication		97830354.3
6028793	97-AG-142	US	Granted		09224330
6242971	97-AG-143	US	Granted		09321981
	97-AG-143	IT	Granted	0961288	98830332.7
	97-AG-143	GB	Granted	0961288	98830332.7
6172908	97-AG-151	US	Granted		09166236
6279960	97-AG-155	US	Granted		09212856
	97-AG-155	IT	Abandon requested	0926587	97830693.4
	97-AG-155	FR	Granted	0926587	97830693.4
5982677	97-AG-166	US	Granted		09163755
	97-AG-166	IT	Abandon requested	905710	97830484.8
	97-AG-166	FR	Granted	905710	97830484.8
6011715	97-AG-177	US	Granted		09185906
	97-AG-177	GB	Granted	0913832	97830566.2
6075750	97-AG-178	US	Granted		09186497
	97-AG-178	IT	Abandon requested	915477	97830576.1
	97-AG-178	GB	Granted	915477	97830576.1
	97-AG-178	FR	Granted	915477	97830576.1
6169423	97-AG-179	US	Granted		09186496
	97-AG-179	JP	Publication		10315066
	97-AG-179	IT	Abandon requested	915476	97830573.8
	97-AG-179	GB	Granted	915476	97830573.8
	97-AG-179	FR	Granted	915476	97830573.8
6144589	97-AG-180	US	Granted		09186758
	97-AG-180	EP	Publication		97830572.0
6153914	97-AG-182	US	Granted		09170788
	97-AG-182	IT	Abandon requested	911974	97830542.3
	97-AG-182	GB	Granted	911974	97830542.3
6184570	97-AG-183	US	Granted		09186496
	97-AG-183	EP	Publication		97830576.6
6275099	97-AG-193	US	Granted		09239906
	97-AG-193	IT	Granted	1301187	TO98A000077

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
6249172	97-AG-204	US	Granted		09275200
	97-AG-204	IT	Granted	1298817	MI98A00539
6064698	97-AG-205	US	Granted		09275694
	97-AG-205	IT	Granted	1298819	MI98A00641
6266086	97-AG-206	US	Granted		09220127
	97-AG-206	JP	Publication		10367933
	97-AG-206	EP	Publication		97830717.1
6101118	97-AG-207	US	Granted		09196204
6285814	97-AG-207	US	Granted		09602689
	97-AG-207	IT	Granted	1298486	MI97A002594
6204722	97-AG-208	US	Granted		09218796
	97-AG-208	IT	Granted	1298688	MI97A02811
6069887	97-AG-209	US	Granted		09222022
	97-AG-209	IT	Granted	928003	98114051.9
	97-AG-209	FR	Granted	928003	98114051.9
6237104	97-AG-210	US	Granted		09222070
	97-AG-210	IT	Granted	1296908	MI97A02883
6157226	97-AG-211	US	Granted		09234016
	97-AG-211	IT	Granted	1298186	MI98A00115
6151251	97-AG-212	US	Granted		09285667
6304493	97-AG-212	US	Granted		09675985
	97-AG-212	IT	Granted	952615	98830238.6
	97-AG-212	GB	Granted	952615	98830238.6
	97-AG-212	FR	Granted	952615	98830238.6
6031761	97-AG-213	US	Granted		09275255
	97-AG-213	IT	Granted	1298816	MI98A00633
6009041	97-AG-218	US	Granted		09032272
6313480	97-AG-220	US	Granted		09219049
6317396	97-AG-222	US	Granted		09231130
6288594	97-AG-224	US	Granted		09674395
	97-AG-224	IT	Granted	1097454	98926852.8
	97-AG-224	GB	Granted	1097454	98926852.8
	97-AG-224	FR	Granted	1097454	98926852.8
	97-AG-224	DE	Granted	69901259	98926852.8
	97-AG-224	CN	Granted	201459	98803467.4
6087914	97-AG-226	US	Granted		09349702
	97-AG-226	IT	Granted	1301535	MI98A01564
6121127	97-AG-229	US	Granted		09229474
	97-AG-229	EP	Publication		04023387.6
6091642	97-AG-240	US	Granted		09234942
	97-AG-240	IT	Abandon requested	0832181	98830024.0
6088222	97-AG-241	US	Granted		09223691
	97-AG-241	IT	Granted	0932202	97830741.1
	97-AG-241	FR	Granted	0932202	97830741.1
6242793	97-AG-246	US	Granted		09231128
6372597	97-AG-246	US	Granted		09837157
	97-AG-246	JP	Publication		10370047
	97-AG-246	EP	Publication		97830742.9
6147902	97-AG-252	US	Granted		09320315
	97-AG-252	IT	Granted	961287	98830324.4
	97-AG-252	GB	Granted	961287	98830324.4
	97-AG-252	FR	Granted	961287	98830324.4
6216205	97-AG-275	US	Granted		09335059
	97-AG-275	IT	Granted	0971415	98830388.9
	97-AG-275	GB	Granted	0971415	98830388.9
	97-AG-275	FR	Granted	0971415	98830388.9
	97-AG-275	DE	Granted	0971415	98830388.9
6111791	97-AG-283	US	Granted		09322644
	97-AG-283	IT	Granted	1301398	MI98A01193
6298705	97-AG-285	US	Granted		09282500
	97-AG-285	IT	Granted	1298594	MI98A00454
6097833	97-CT-106	US	Granted		09192843
	97-CT-106	IT	Granted	1295910	MI97A02498
6667113	97-CT-174	US	Granted		09191743
	97-CT-174	EP	Publication		97830608.3
6133718	97-CT-205	US	Granted		09248029
	97-CT-205	IT	Granted	1298580	MI98A00219
	97-CT-235	IT	Granted	1298838	MI98A00351
	97-CT-238	IT	Granted	1298839	MI98A00352
6271571	97-CT-238	US	Granted		09276263
	97-CT-238	IT	Granted	1298807	MI98A00628
6466056	97-CT-290	US	Granted		09249834
	97-CT-290	IT	Granted	936627	98830064.6
	97-CT-290	GB	Granted	936627	98830064.6
6130844	97-CT-294	US	Granted		09257682
	97-CT-294	IT	Granted	1302079	TO98A000185
6064594	97-CT-295	US	Granted		09258224
	97-CT-295	IT	Granted	1302080	TO98A000186
6156872	97-CT-296	US	Granted		09257984
	97-CT-296	IT	Granted	1302081	TO98A000187
6111809	98-AG-006	US	Granted		09324087
	98-AG-006	US	Filing		
	98-AG-006	IT	Granted	1300989	TO98A000497
6181502	98-AG-007	US	Granted		09322459
	98-AG-007	JP	Publication		11192232
	98-AG-007	IT	Granted	961285	98830333.5
	98-AG-007	GB	Granted	961285	98830333.5
	98-AG-007	FR	Granted	961285	98830333.5
6157579	98-AG-008	US	Granted		09285253
6097213	98-AG-044	US	Granted		09275691
	98-AG-044	IT	Granted	1298818	MI98A00640
6276198	98-AG-046	US	Granted		09344426
6551892	98-AG-046	US	Granted		09891438
	98-AG-046	IT	Granted	1301642	TO98A000556
	98-AG-047	US	Filing		11933775
	98-AG-047	IT	Granted	1301880	MI98A01759
6084797	98-AG-055	US	Granted		09275214
	98-AG-055	IT	Granted	0945089	98830189.3
	98-AG-055	GB	Granted	0945089	98830189.3
	98-AG-055	FR	Granted	0945089	98830189.3
6515911	98-AG-082	US	Granted		09894975
	98-AG-082	JP	Filing		11289024
	98-AG-082	IT	Granted	991075	98830570.2
	98-AG-082	GB	Granted	991075	98830570.2

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
	98-AG-082	FR	Granted	991075	98830570.2
6251738	98-AG-092	US	Granted		09399923
6420760	98-AG-092	US	Granted		09901404
	98-AG-092	EP	Publication		99120033.0
6300181	98-AG-093	US	Granted		09398075
	98-AG-093	IT	Granted	0979031	98830444.0
	98-AG-093	GB	Granted	0979021	98830444.0
6451922	98-AG-101	US	Granted		09464065
	98-AG-101	EP	Publication		98830757.5
6495455	98-AG-103	US	Granted		09829937
	98-AG-103	IT	Granted	1301840	MI98A001494
6255163	98-AG-109	US	Granted		09330540
	98-AG-109	IT	Granted	1301007	TO98A00516
6284607	98-AG-111	US	Granted		09411134
	98-AG-111	IT	Granted	1302589	MI98A002124
6172913	98-AG-112	US	Granted		09344425
	98-AG-112	IT	Granted	1301043	TO98A00557
6180460	98-AG-116	US	Granted		09337051
	98-AG-116	IT	Granted	1301799	MI98A001449
6444526	98-AG-118	US	Granted		09419403
	98-AG-118	IT	Granted	0994513	98830614.8
	98-AG-118	GB	Granted	0994513	98830614.8
	98-AG-118	FR	Granted	0994513	98830614.8
6009152	98-AG-119	US	Granted		09579332
	98-AG-119	JP	Publication		00139757
	98-AG-119	IT	Granted	1052573	98830286.3
	98-AG-119	GB	Granted	1052572	98830286.3
	98-AG-119	FR	Granted	1052572	98830286.3
6259736	98-AG-121	US	Granted		09473358
	98-AG-121	EP	Publication		98830794.8
6313040	98-AG-123	US	Granted		09466903
	98-AG-123	JP	Publication		11281939
	98-AG-123	EP	Publication		98830694.6
6281077	98-AG-125	US	Granted		09382937
6388101	98-AG-125	US	Granted		09856390
	98-AG-125	EP	Publication		98830645.2
6602774	98-AG-127	US	Granted		09473367
	98-AG-127	IT	Granted	1017088	98830793.0
	98-AG-127	GB	Granted	1017088	98830793.0
6330056	98-AG-129	US	Granted		09513286
	98-AG-129	IT	Granted	1035473	99830099.0
	98-AG-129	GB	Granted	1035473	99830099.0
	98-AG-129	FR	Granted	1035473	99830099.0
	98-AG-129	DE	Granted	69905237	99830099.0
6456527	98-AG-159	US	Granted		09501131
	98-AG-159	JP	Publication		00034209
	98-AG-159	IT	Granted	1028433	99830071.5
	98-AG-159	GB	Granted	1028433	99830071.9
	98-AG-159	FR	Granted	1028433	99830071.9
6301157	98-AG-160	US	Granted		09415024
	98-AG-160	IT	Granted	997913	98830654.4
	98-AG-160	GB	Granted	997913	98830654.4
6323799	98-AG-171	US	Granted		09421916
	98-AG-171	IT	Granted	0997912	98830626.2
	98-AG-171	GB	Granted	0997912	98830626.2
6486481	98-AG-172	US	Granted		09436232
	98-AG-172	IT	Granted	1305181	TO98A00981
6165483	98-AG-173	US	Granted		09447531
	98-AG-173	IT	Granted	1303221	TO98A00990
6128228	98-AG-174	US	Granted		09438823
	98-AG-174	IT	Granted	1305182	TO98A00982
6410387	98-AG-175	US	Granted		09449044
6713347	98-AG-175	US	Granted		10158424
	98-AG-175	JP	Publication		11334205
	98-AG-175	EP	Publication		98830709.6
6169891	98-AG-176	US	Granted		09399387
	98-AG-176	IT	Granted	987715	98830536.3
	98-AG-176	FR	Granted	987715	98830536.3
6350637	98-AG-177	US	Granted		09543400
	98-AG-177	EP	Publication		98830194.9
6195269	98-AG-178	US	Granted		09425446
	98-AG-178	IT	Granted	1305136	TO98A00936
6259635	98-AG-182	US	Granted		09491475
	98-AG-182	IT	Granted	1306984	MI98A000981
6259632	98-AG-183	US	Granted		09491475
	98-AG-183	IT	Granted	1306983	MI98A000980
6452400	98-AG-201	US	Granted		09483656
	98-AG-201	EP	Publication		99830007.3
6387763	98-AG-206	US	Granted		09462834
6737715	98-AG-206	US	Granted		10090978
	98-AG-206	EP	Publication		98830694.0
6232753	98-AG-209	US	Granted		09467726
	98-AG-209	IT	Granted	1304046	MI98A002787
6274411	98-AG-212	US	Granted		09469849
	98-AG-212	EP	Publication		98830771.6
6392931	98-AG-213	US	Granted		09449168
	98-AG-213	IT	Granted	1303204	TO98A01003
6294431	98-AG-215	US	Granted		09547520
	98-AG-215	EP	Publication		99830214.1
6222775	98-AG-227	US	Granted		09599356
	98-AG-227	JP	Publication		00186781
	98-AG-227	IT	Granted	1067557	98830390.3
	98-AG-227	GB	Granted	1067557	98830390.3
	98-AG-227	FR	Granted	1067557	98830390.3
6477625	98-AG-228	US	Granted		09474932
	98-AG-228	EP	Publication		98830801.1
6424575	98-AG-233	US	Granted		09716752
	98-AG-233	IT	Granted	1313858	MI99A002460
6385468	98-AC-234	US	Granted		09507777
	98-AG-234	EP	Publication		99830101.4
6324238	98-AG-248	US	Granted		09464831
6275418	98-AG-257	US	Granted		09472498
6373781	98-AG-258	US	Granted		09499799
6350671	98-AG-262	US	Granted		09579778

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
	98-AG-262	IT	Granted	1058304	98830336.6
	98-AG-262	GB	Granted	1058304	98830336.6
	98-AG-262	FR	Granted	1058304	98830336.6
6535431	98-AG-264	US	Granted		09552933
5803630	98-AG-264	US	Granted		10350745
	98-AG-264	IT	Granted	1047078	98830235.0
	98-AG-264	GB	Granted	1047078	98830235.0
	98-AG-264	FR	Granted	1047078	98830235.0
	98-AG-264	EP	Filing		08012616.6
	98-AG-264	DE	Granted	1047078	98830235.0
6249463	98-AG-265	US	Granted		09457500
	98-AG-282	IT	Granted	1073119	98830491.9
	98-AG-282	GB	Granted	1073119	98830491.9
	98-AG-282	FR	Granted	1073119	98830491.9
6396132	98-AG-283	US	Granted		09802070
	98-AG-283	JP	Publication		00021789
	98-AG-283	IT	Granted	1028464	98830072.7
	98-AG-283	GB	Granted	1028464	98830072.7
	98-AG-283	FR	Granted	1028464	98830072.7
6311149	98-AG-290	US	Granted		09513598
	98-AG-290	JP	Publication		0049429
	98-AG-290	IT	Granted	1031991	98830106.9
	98-AG-290	GB	Granted	1031991	98830106.9
	98-AG-290	FR	Granted	1031991	98830106.9
6249112	98-AG-292	US	Granted		09608445
	98-AG-292	JP	Publication		00199553
	98-AG-292	IT	Granted	1065580	98830418.2
	98-AG-292	GB	Granted	1065580	998304182
	98-AG-292	FR	Granted	1065580	998304182
6294798	98-CT-035	US	Granted		09415992
6511874	98-CT-035	US	Granted		09912698
	98-CT-035	EP	Publication		98830597.5
6240062	98-CT-260	US	Granted		09551271
	98-CT-260	EP	Publication		99201363.1
6310861	98-CT-270	US	Granted		09548783
	98-CT-270	IT	Granted	1307685	TO99A000289
6324098	98-CT-271	US	Granted		09548957
	98-CT-271	IT	Granted	1307686	TO99A000290
6243310	98-CT-272	US	Granted		09548975
	98-CT-272	IT	Granted	1307687	TO99A000291
6410404	98-CT-273	US	Granted		09561272
	98-CT-273	JP	Filing		00130698
	98-CT-273	EP	Publication		99830262.4
6282125	99-AG-012	US	Granted		09553526
	99-AG-012	IT	Granted	1312212	MI99A000859
6363015	99-AG-016	US	Granted		09589723
	99-AG-016	JP	Publication		00182753
	99-AG-016	IT	Granted	1063654	99830382.0
	99-AG-016	GB	Granted	1063654	99830382.0
	99-AG-016	FR	Granted	1063654	99830382.0
	99-AG-016	DE	Granted	1063654	99830382.0
6314043	99-AG-017	US	Granted		09542708
	99-AG-017	IT	Granted	1065668	99830381.2
	99-AG-017	GB	Granted	1065668	99830381.2
	99-AG-017	FR	Granted	1065668	99830381.2
6361413	99-AG-022	US	Granted		09552945
6292398	99-AG-023	US	Granted		09549232
	99-AG-023	IT	Granted	1312471	MI99A001017
6456530	99-AG-025	US	Granted		09602680
	99-AG-035	JP	Publication		00135290
	99-AG-035	IT	Granted	1063653	99830396.0
	99-AG-035	GB	Granted	1063653	99830396.0
	99-AG-035	FR	Granted	1063653	99830396.0
6198660	99-AG-041	US	Granted		09572127
	99-AG-041	IT	Granted	1055259	99830331.7
	99-AG-041	GB	Granted	1055259	99830331.7
6333885	99-AG-046	US	Granted		09603275
	99-AG-046	IT	Granted	1071094	99830403.4
	99-AG-046	GB	Granted	1071094	99830403.4
	99-AG-046	FR	Granted	1071094	99830403.4
6320790	99-AG-047	US	Granted		09586399
	99-AG-047	JP	Publication		00171988
	99-AG-047	EP	Notification 51(4)		99830348.1
6507183	99-AG-051	US	Granted		09608647
	99-AG-051	IT	Granted	1313225	MI99A001474
6392836	99-AG-052	US	Granted		09608239
	99-AG-052	IT	Granted	1313226	MI99A001475
6292400	99-AG-075	US	Granted		09620765
	99-AG-075	IT	Granted	1313198	MI99A001518
6368486	99-AG-081	US	Granted		09631187
	99-AG-081	JP	Publication		00236265
	99-AG-081	JP	Publication		00236265
	99-AG-081	IT	Granted	1074995	99830501.5
	99-AG-081	IT	Granted	1074995	99830501.5
	99-AG-081	GB	Granted	1074995	99830501.5
	99-AG-081	GB	Granted	1074995	99830501.5
	99-AG-081	FR	Granted	1074995	99830501.5
	99-AG-081	FR	Granted	1074995	99830501.5
	99-AG-081	DE	Granted	1074995	99830501.5
	99-AG-081	DE	Granted	1074995	99830501.5
6345058	99-AG-085	US	Granted		09716746
	99-AG-085	EP	Publication		99830722.7
6469934	99-AG-088	US	Granted		09736253
	99-AG-090	IT	Granted	1311314	TO99A001098
6670229	99-AG-098	US	Granted		10077289
	99-AG-098	EP	Publication		99830468.7
	99-AG-102	IT	Granted	1314142	MI99A002650
6320361	99-AG-103	US	Granted		09736884
	99-AG-103	IT	Granted	1314122	MI99A002678
6312598	99-AG-104	US	Granted		09627703
	99-AG-104	EP	Publication		99830495.8
6442068	99-AG-105	US	Granted		09619589
	99-AG-105	JP	Publication		00227222
	99-AG-105	EP	Publication		99830494.3

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
6311177	99-AG-106	US	Granted		09689309
	99-AG-106	IT	Publication		TO99A000842
6501147	99-AG-126	US	Granted		09713144
	99-AG-126	EP	Publication		99830717.7
6327184	99-AG-127	US	Granted		09821019
	99-AG-127	JP	Granted	3655536	00253119
	99-AG-127	IT	Granted	1071096	99830469.5
	99-AG-127	GB	Granted	1071096	99830469.5
	99-AG-127	FR	Granted	1071096	99830469.5
	99-AG-129	IT	Granted	1316285	MI00A000065
6438040	99-AG-130	US	Granted		09698229
6838833	99-AG-132	US	Granted		09804693
6317775	99-AG-137	US	Granted		09658236
	99-AG-137	JP	Granted	3621334	00272586
	99-AG-137	EP	Publication		99830567.6
6574146	99-AG-138	US	Granted		09738889
	99-AG-138	IT	Granted	1313878	MI99A002624
6854040	99-AG-143	US	Granted		09757938
	99-AG-143	EP	Publication		99830723.5
6424121	99-AG-146	US	Granted		09714837
	99-AG-146	IT	Granted	1311440	TO99A000993
6526885	99-AG-147	US	Granted		09698662
	99-AG-147	EP	Publication		99830846.6
6400607	99-AG-148	US	Granted		09699304
	99-AG-148	IT	Granted	1308858	TO99A000843
6473340	99-AG-149	US	Granted		09689043
	99-AG-149	IT	Granted	1308857	TO99A000844
6507534	99-AG-150	US	Granted		09797171
	99-AG-150	IT	Granted	1130601	00830149.1
	99-AG-150	GB	Granted	1130601	00830149.1
6362053	99-AG-151	US	Granted		09699633
	99-AG-151	IT	Granted	1313155	MI99A001769
6385107	99-AG-153	US	Granted		09710067
	99-AG-153	IT	Granted	1313873	MI99A002372
6549485	99-AG-154	US	Granted		09727753
	99-AG-154	IT	Granted	1318978	MI00A002163
6508322	99-AG-155	US	Granted		09718971
6509171	99-AG-155	US	Granted		10225315
	99-AG-155	EP	Publication		99830736.0
6420223	99-AG-159	US	Granted		09730518
	99-AG-159	EP	Publication		99830766.7
6373780	99-AG-161	US	Granted		09827273
	99-AG-161	JP	Publication		00237560
	99-AG-161	IT	Granted	1073060	99830483.6
	99-AG-161	GB	Granted	1073060	99830483.6
	99-AG-161	FR	Granted	1073060	99830483.6
6128219	99-AG-162	US	Granted		09428883
6529961	99-AG-163	US	Granted		09352957
	99-AG-163	EP	Notification 51(4)		00830620.1
6581173	99-AG-193	US	Granted		09686362
	99-AG-193	IT	Granted	1309102	TO99A000884
6437836	99-AG-219	US	Granted		09747312
	99-AG-219	EP	Publication		99830625.8
6418051	99-AG-225	US	Granted		09786079
	99-AG-225	IT	Granted	1126372	00830103.6
	99-AG-225	GB	Granted	1126372	00830103.6
6896745	99-AG-234	US	Granted		09798347
	99-AG-234	IT	Granted	1319937	TO00A000207
6429634	99-AG-258	US	Granted		09778330
	99-AG-258	IT	Granted	1124313	00830088.1
	99-AG-258	GB	Granted	1124313	00830088.1
	99-AG-258	FR	Granted	1124313	00830088.1
6677206	99-AG-260	US	Granted		09740407
	99-AG-260	IT	Granted	1314143	MI99A002651
6351434	99-AG-264	US	Granted		09787762
	99-AG-264	EP	Publication		00830100.4
6804756	99-AG-265	US	Granted		09827389
	99-AG-265	EP	Publication		00830269.7
6501700	99-AG-266	US	Granted		09674737
	99-AG-266	EP	Publication		00830959.7
6414875	99-AG-269	US	Granted		09817363
6683808	99-AG-269	US	Granted		10179553
6954395	99-AG-269	US	Granted		10742181
7072212	99-AG-269	US	Granted		10742429
	99-AG-269	EP	Publication		00830209.3
6451653	99-AG-272	US	Granted		09888335
	99-AG-273	EP	Publication		00201716.6
6981134	99-AG-278	US	Granted		09817804
	99-AG-278	IT	Granted	1139210	00830228.3
	99-AG-278	GB	Granted	1139210	00830228.3
	99-AG-278	FR	Granted	1139210	00830228.3
5465479	99-AG-320	US	Granted		08888744
	99-AG-320	EP	Notification 51(4)		00204538.7
6660173	99-AG-321	US	Granted		09714852
	99-AG-321	IT	Granted	1318441	TO99A000994
6585247	99-AG-358	US	Granted		09798778
	99-AG-358	EP	Publication		00830162.4
6907517	99-AG-368	US	Granted		09871235
	99-AG-368	EP	Publication		00830392.7
6549473	99-AG-369	US	Granted		09871234
	99-AG-369	EP	Publication		00830393.5
6476664	99-AG-370	US	Granted		09823282
	99-AG-370	EP	Publication		00830239.0
6597709	99-AG-372	US	Granted		09821827
	99-AG-372	EP	Publication		00830238.2
6837879	99-AG-376	US	Granted		09900501
6790505	99-AG-376	US	Granted		10337556
	99-AG-376	IT	Granted	1316145	MI00A001567
6580637	99-AG-393	US	Granted		09872769
	99-AG-393	IT	Granted	1318979	MI00A002165
6420926	99-CT-067	US	Granted		09798890
	99-CT-067	IT	Granted	1313877	MI99A002633
5438048	99-CT-195	US	Granted		09670248
	99-CT-195	EP	Publication		99830616.1

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
6282134	99-CT-196	US	Granted		09670471
	99-CT-196	EP	Publication		99830817.9
6442072	99-CT-291	US	Granted		09745286
	99-CT-291	IT	Granted	1313409	VA99A00037
6470431	99-CT-339	US	Granted		09774562
	99-CT-339	EP	Publication		00830291.1
6452864	99-CT-343	US	Granted		09774539
	99-CT-343	IT	Granted	1322978	VA99A00015
6473339	99-CT-345	US	Granted		09773272
	99-CT-345	IT	Granted	1130517	00830168.2
	99-CT-345	GB	Granted	1130517	00830168.2
	99-CT-345	FR	Granted	1130517	00830168.2
	99-CT-345	DE	Granted	1130517	00830168.2
6366934	99-CT-347	US	Granted		09774878
6025706	99-CT-349	US	Granted		09773780
	99-CT-349	EP	Publication		00830313.3
6587913	99-CT-355	US	Granted		09773300
	99-CT-355	JP	Granted	3472698	0122134
	99-CT-355	IT	Granted	1122734	00830068.3
	99-CT-355	GB	Granted	1122734	00830068.3
4888497	DB 393	US	Granted		07187581
4958539	DB 442	US	Granted		07284272
4949307	DB 456	US	Granted		07298487
	DB 456	FR	Granted	329094	891207.50.8
4922402	DB 479	US	Granted		07372492
4958589	DB 482	US	Granted		07373200
4917088	DB 488	US	Granted		07381283
4937782	DB 491	US	Granted		07385159
5014834	DB 528	US	Granted		07446196
4982680	DB 532	US	Granted		07456782
5075246	DB 603	US	Granted		07625764
	DB 603	JP	Granted	3199388	2409854
5486487	DB 632	US	Granted		08139800
5179300	DB 636	US	Granted		07691768
	DB 636	IT	Granted	1240012	20157A90
	DB 636	GB	Granted	455002	91105323.9
	DB 636	FR	Granted	455002	91105323.9
	DB 636	DE	Granted	69128494	91105323.9
5231581	DB 656	US	Granted		07769600
	DB 656	US	Filing		08784048
	DB 656	IT	Granted	0478871	90830428.0
	DB 656	GB	Granted	0478871	90830428.0
5274282	DB 667	US	Granted		07970609
5252169	DB 670	US	Granted		07791973
5275844	DB 671	US	Granted		07791453
	DB 671	TW	Granted	76142	81205692
5270590	DB 679	US	Granted		07805118
5283478	DB 691	US	Granted		07811323
5268959	DB 692	US	Granted		07810480
6350878	DB 745	US	Granted		08411385
5594677	DB 829	US	Granted		08189271
	DB 829	IT	Granted	0808664	93830031.6
	DB 829	DE	Granted	69324789	93830031.6
5724395	DB 830	US	Granted		08188569
5837529	DB 834	US	Granted		08195389
	DB 834	JP	Publication		9515744
5466822	DB 835	US	Granted		08196634
5913120	DB 835	US	Granted		08502829
	DB 835	JP	Granted	3606595	6220549
5487345	DB 836	US	Granted		8196572
5508956	DB 848	US	Granted		08214249
5587948	DB 849	US	Granted		08212807
5633872	DB 849	US	Granted		08458346
	DB 849	JP	Granted	3553121	647209
5419388	DB 850	US	Granted		08219204
	DB 850	JP	Granted	3615551	5878791
	DB 850	IT	Granted	0618587	93830128.0
	DB 850	GB	Granted	0618587	93830128.0
	DB 850	FR	Granted	0618587	93830128.0
	DB 850	DE	Granted	0618587	93830128.0
5634690	DB 855	US	Granted		08454854
5712815	DB 855	US	Granted		08685782
4966845	DB 274	US	Granted		07249991
5486485	93-AG-27	US	Granted		811782
5526535	93-AG-39	US	Granted		8344222
5937226	DB 617	US	Granted		07685043
RE36579	DB 622	US	Granted		08488718
5857484	DB 634	US	Granted		08364505
5267202	DB 644	US	Granted		07729987
RE36292	DB 650	US	Granted		08870130
5327379	DB 712	US	Granted		07878923
5461713	DB 712	US	Granted		08270498
5408148	DB 723	US	Granted		07919906
5321817	DB 730	US	Granted		07996857
5347493	DB 731	US	Granted		07938731
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5663980	DB 752	US	Granted		08594080
5498399	DB 752	US	Granted		08475555
5356333	DB 763	US	Granted		08135842
5407861	DB 755	US	Granted		08068139
5789272	DB 785	US	Granted		08428397
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	DB 785	FR	Granted	0571691	92830285.2
5420525	DB 791	US	Granted		08084727
5440610	DB 794	US	Granted		08089342
5706240	DB 796	US	Granted		08615727
5568418	DB 817	US	Granted		8447772
5798279	DB 817	US	Granted		08469431
5407852	DB 821	US	Granted		08084571
5793995	DB 821	US	Granted		08772301
5813318	DB 822	US	Granted		84654
5799675	DB 822	US	Granted		08629935
	DB 822	US	Filing		08140829
	DB 822	JP	Publication		5272484

US Pat No.	ST Ref	Country	Status	Non-US Pat. number	Filing Number
4372646	DB 825	US	Granted		06153820
	DB 825	JP	Filing		5311209
	DB 825	GB	Granted	0598168	92830625.7
	DB 825	FR	Granted	0598168	92830625.7
4823173	DB 308	US	Granted		54712
4816853	DB 314	US	Granted		64480
4897365	DB 177	US	Granted		07124440
6567296	01-AG-008	US	Granted		09941684
	01-AG-008	IT	Granted	1306852	02078984.8
	01-AG-008	GB	Granted	1306852	02078984.8
	01-AG-008	FR	Granted	1306852	02078984.8
6754167	01-AG-166	US	Granted		10331186
	01-AG-166	EP	Publication		02028615.7
6816404	01-AG-191	US	Granted		10019439
	01-AG-191	EP	Publication		01830805.4
6946673	01-AG-212	US	Granted		10348128
	01-AG-212	US			11020790
	01-AG-212	EP	Notification 51(4)		02425013.6
6891747	01-AG-301	US	Granted		10372761
	01-AG-301	US	Publication		11045170
	01-AG-301	EP	Publication		02425087.0
6972430	01-AG-309	US	Granted		10371154
	01-AG-309	US	Filing		11258340
	01-AG-309	EP	Publication		02425088.8
6930913	01-AG-310	US	Granted		10372639
	01-AG-310	US	Filing		11156880
	01-AG-310	EP	Granted	1339111	02429089.2
7135756	02-AG-077	US	Granted		10680727
	02-AG-077	US	Filing decision		
	02-AG-077	EP	Notification 51(4)		02425605.9
6983560	02-AG-081	US	Granted		10680721
	02-AG-081	US	Filing		11264094
	02-AG-081	EP	Notification 51(4)		02425604.2
6433585	99-AG-082	US	Granted		09585916
	99-AG-082	JP	Granted	3707067	00171859
	99-AG-082	IT	Granted	1058271	99830345.7
	99-AG-082	GB	Granted	1058271	99830345.7
	99-AG-082	FR	Granted	1058271	99830345.7
6366481	99-AG-083	US	Granted		09595054
	99-AG-083	JP	Publication		00187530
	99-AG-083	IT	Granted	1061525	99830378.8
	99-AG-083	GB	Granted	1061525	99830378.8
	99-AG-083	FR	Granted	1061525	99830378.8

EXHIBIT A

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00-AG-081	IT	MI00A00869	1319493	Granted
00-AG-198	IT	MI00A02755	1319590	Granted
00-AG-271	EP	00830855.3		Publication
00-AG-341	US	10/026815		Publication
00-AG-341	EP	02014408.5		Publication
01-AG-165	US	10/309759		Publication
01-AG-193	US	10/735250		Publication
01-AG-193	IT	MI02A002629		Filing
01-AG-255	US	10/330656		Notice of Allowance
01-AG-255	EP	02425152.2		Publication
01-AG-304	IT	MI03A001409		Filing
01-CT-182	US	10/887141		Publication
01-CT-256	US	10/350515		Abandon decision
01-CT-256	IT	VA02A000012		Publication
01-CT-295	US	10/359240		Publication
01-CT-295	EP	02425529.1		Publication
01-CT-337	US	10/789443		Notice of Allowance
01-CT-337	IT	03425126.4	1453062	Granted
01-CT-337	GB	03425126.4	1453062	Granted
01-CT-337	FR	03425126.4	1453062	Granted
02-AG-001	US	10/675221		Publication
02-AG-001	EP	02425591.1		Publication
02-AG-013	US	10/137096		Filing
02-AG-013	US	10/137096		Filing
02-AG-035	US	10/603855		Publication
02-AG-035	US	10/603855		Publication
02-AG-035	EP	02425428.6		Notification 51(4)
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02-AG-046	US	10/631463		Notice of Allowance
02-AG-046	US	10/631463		Notice of Allowance
02-AG-046	EP	02425905.1		Publication
02-AG-046	EP	02425905.1		Publication
02-AG-165	EP	02425618.0		Publication
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02-AG-193	US	11/343593		Filing
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02-AG-211	US	10/741815		Publication
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02-AG-211	EP	03104709.5		Notification 51(4)
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02-AG-219	EP	02425796.6		Publication
02-AG-228	US	10/652862		Publication
02-AG-228	US	10/652862		Publication
02-AG-228	EP	02425536.6		Publication
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02-AG-235	US	10/742731		Notice of Allowance
02-AG-236	EP	02425801.4		Publication
02-AG-242	US	10/781974		Publication
02-AG-242	EP	03425092.6		Publication
02-AG-244	US	10/953651		Publication
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02-AG-256	IT	RM03A00255		Filing
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02-AG-317	US	10749130		Publication
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02-AG-344	IT	MI03A01102		Filing
02-AG-357	US	10893760		Filing
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02-AG-384	US	10777457		Publication
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02-AG-384	IT	TO03A00121		Filing
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02-AG-489	IT	MI03A01591		Filing
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02-AG-491	US	10574888		Filing
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02-AG-509	EP			Filing requested
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02-AG-523	EP	04106858.6		Filing
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02-CT-439	FR	03425134.8	1453059	Granted
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02-Pa-330	EP	02425734.5		Publication
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03-AG-006	EP	03425459.9		Publication
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03-AG-172	US	10913129		Publication
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03-AG-179	US	10971775		Publication
03-AG-179	EP	03102911.8		Publication
03-AG-194	US	11194739		Filing
03-AG-194	EP	04103714.4		Publication
03-AG-224	US	11317679		Publication
03-AG-224	US	11317679		Publication
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03-AG-233	US	11161364		Filing
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03-AG-234	US	11156354		Filing
03-AG-234	EP	04402942.2		Publication
03-AG-251	US	11419679		Filing
03-AG-251	EP	05103557.4		Filing
03-AG-270	US			Filing
03-AG-270	EP	04425486.0		Publication
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03-AG-307	US			Filing
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03-AG-307	EP	05110648.2		Filing
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03-AG-308	US	11317641		Filing
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03-AG-342	US	11319750		Filing
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03-AG-342	EP	05028380.3		Publication
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03-AG-358	US	11134156		Filing
03-AG-358	EP	04102232.8		Publication
03-AG-370	US	11425491		Filing
03-AG-379	EP	05104742.1		Filing
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03-CT-278	IT	VA04A00020		Filing
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03-NP-320	US	11152875		Filing
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03-NP-394	US	11020332		Notice of Allowance
03-NP-394	EP	04425626.1		Notification 5104
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03-PA-111	EP	04103101.4		Publication
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04-AG-038	EP	04104595.5		Publication
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04-AG-112	EP	05022651.3		Publication
04-AG-113	US	11250173		Filing
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04-AG-114	US	11241729		Publication

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04-AG-145	EP	05425092.0		Filing
04-AG-167	US	11434564		Filing
04-AG-167	IT	MI05A000868		Filing
04-AG-185	US	11279381		Filing
04-AG-195	IT	MI05A000610		Filing
04-AG-173	EP			Filing decision
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04-AG-189	EP	06101314.0		Filing
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04-AG-205	EP	06001376.6		Filing
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04-AG-232	EP	05025286.3		Publication
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04-AG-344	EP	05425281.4		Filing
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04-AG-466	EP	05425864.1		Filing
04-AG-469	US	11361426		Filing
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04-CT-179	US	11482524		Filing
04-CT-179	EP	05106180.2		Filing
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04-NP-045	EP	04101301.2		Publication
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04-NP-240	US	11036179		Filing
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05-AG-079	EP	05425712.6		Filing
05-AG-085	EP	05425164.6		Filing
05-AG-085	EP	05425164.6		Filing
05-AG-112	EP	05425371.9		Filing
05-AG-112	EP	05425371.9		Filing
05-AG-118	US			Filing decision
05-AG-118	EP	05425634.2		Filing
05-AG-123	EP	05111234.6		Filing
05-AG-124	EP	05111477.8		Filing
05-AG-126	EP	05113480.5		Filing
05-AG-127	EP	05112926.8		Filing
05-AG-128	EP	05119455.8		Filing
05-AG-159	WO	IT06000170		Filing
05-AG-177	EP	06114228.7		Filing
05-AG-178	EP	06425040.0		Filing
05-AG-178	EP	06425040.0		Filing
05-AG-180	EP	05425843.7		Filing
05-AG-180	EP	05425843.7		Filing
05-AG-188	US	11459831		Filing
05-AG-188	EP	05106973.0		Filing
05-AG-204	EP	06425173.9		Filing
05-AG-205	IT	VA06A000014		Filing
05-AG-206	EP	05425124.2		Filing
05-AG-207	IT	MI06A000748		Filing
05-AG-208	US	11458876		Filing
05-AG-208	EP	05106975.5		Filing
05-AG-231	US	11463260		Filing
05-AG-232	EP	06425141.6		Filing
05-AG-261	EP	05425900.7		Filing
05-AG-317	EP	06113912.5		Filing
05-AG-325	EP	06113809.3		Filing
05-AG-326	EP	06425477.4		Filing
05-AG-342	EP	06426006.8		Filing
05-AG-342	EP	06425606.8		Filing
05-CT-106	US			Filing decision
05-CT-106	EP	06425718.3		Filing
05-CT-191	IT	MI05A002350		Filing
05-CT-299	EP	06425452.7		Filing
05-CT-365	EP	06425214.1		Filing
05-NP-013	US			Filing decision
05-NP-013	EP	05105703.3		Filing
03-NP-047	US	11460777		Filing
05-NP-047	EP	05425559.1		Filing
06-AG-001	US	11460635		Filing
06-AG-001	EP	06118108.4		Filing
05-AG-056	EP	06425831.6		Filing
05-AG-072	US	11457956		Filing
05-AG-072	US	11457956		Filing
06-AG-079	EP	06425281.6		Filing

ST Ref.	Country	Filing Number	Patent number	Status
05-AG-079	EP	06428283.6		Filing
05-AG-085	EP	06119478.1		Filing
05-AG-124	EP	06425632.4		Filing
05-AG-136	EP	06119452.6		Filing
05-AG-140	EP	06116812.7		Filing
05-AG-184	EP	06118440.3		Filing
06-AG-188	EP	06425536.7		Filing
06-AG-255	EP	06120719.7		Filing
06-AG-255	EP	06120719.7		Filing
06-AG-311	IT	VA06A000066		Filing
06-CT-186	EP	06425503.7		Filing
06-KRR-153	EP	06425535.9		Filing
94-AG-125	IT	94830544.6	0714133	Granted
94-AG-125	DE	94830544.6	0714133	Granted
96-AG-240	IT	MI97A001582	1293810	Granted
97-AG-184	IT	97830575.3	0915408	Abandon requested
97-AG-184	GB	97830575.3	0915408	Granted
97-AG-184	FR	97830575.3	0915408	Granted
98-AG-042	IT	98830491.1	0978844	Granted
98-AG-042	FR	98830491.1	0978844	Granted
98-AG-042	DE	98830491.1	0978844	Granted
98-AG-282	IT	98830491.9	1073119	Granted
98-AG-282	GB	98830491.9	1073119	Granted
98-AG-282	FR	98830491.9	1073119	Granted
99-AG-102	IT	MI99A002890	1314142	Granted
99-AG-129	IT	MI00A000085	1318286	Granted
99-AG-168	IT	T099A001112	1311335	Granted
99-AG-193	EP	99830770.6		Publication
99-AG-363	US	09823926		Publication
99-AG-363	IT	MI00A000667	1316870	Granted
DB 063	US			Unfiled (do not use!)
01-AG-215	US	10313091		Notice of Allowance
01-AG-215	JP	02553352		Publication
01-AG-215	EP	01128461.3		Publication
02-AG-264	US	11195358		Publication
03-AG-264	EP	04425601.4		Publication
03-AG-290	US	11312253		Filing
03-AG-290	EP	04425691.5		Publication
04-AG-050	US	11237787		Publication
04-AG-050	EP	05425024.5		Publication
04-AG-270	US	11312231		Publication
04-AG-283	US	11398849		Publication
04-AG-283	EP	06112075.4		Publication
04-AG-316	US	11398858		Filing
04-AG-316	EP	05102811.8		Publication
04-AG-437	WO	EP2006/062812		Filing
04-AG-437	EP	05104877.5		Publication
06-AG-070	EP	06425581.8		Filing
03-AG-232	US	11185905		Filing
03-AG-232	EP	4108488.5		Filing
03-AG-318	US	11149948		Filing
03-AG-318	EP	4425436.5		Publication
03-AG-030	US	11098694		Filing
03-AG-030	EP	4425112.2		Publication
03-AG-034	US	11316053		Filing
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03-AG-321	US	11113616		Filing
03-AG-321	EP	4101718.7		Publication
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04-AG-464	US	11713081		Filing
04-AG-464	IT	MI06A000827		Publication
04-AG-467	US	11677411		Filing
04-AG-467	IT	VA06A000011		Publication
04-AG-470	US	11672857		Filing
04-AG-470	IT	MI06A000220		Publication
05-AG-141	US	11528508		Filing
05-AG-141	EP	5425691.5		Publication
05-AG-155	US	11740941		Filing
05-AG-155	IT	MI06A000680		Publication
05-AG-210	IT	MI07A000777		Publication
05-AG-267	IT	MI07A001012		Publication
05-AG-363	US	11741462		Filing
05-AG-388	IT			Filing requested
06-AG-032	IT	MI06A000585		Publication
06-AG-304	IT	VA07A000042		Publication
06-AG-305	IT	VA07A000023		Publication
07-AG-096	IT	MI07A000787		Publication

Exhibit A

ST Ref - Invention Disclosure
04-AG-081
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04-PA-005
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05-AG-028
05-AG-058
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ST Ref - Invention Disclosure
06-CT-402
06-NP-206
06-PA-416
06-PA-417
06-PA-418
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05-AG-269
06-AG-122
06-AG-203
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07-AG-179
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07-AG-203
07-AG-207
07-AG-227
07-CT-026
07-CT-077
07-CT-080
07-CT-091
07-CT-092
07-CT-093
07-CT-214

CONFIRMATION OF ASSIGNMENT

WHEREAS, STMicroelectronics NV, a Dutch corporation organized under the laws of The Netherlands, acting through its Swiss branch, having an office at 39 Chemin du Champ-des-Filles, 1228 Plan-les-Ouates, Geneva, Switzerland (hereinafter referred to as "Assignor") previously assigned its rights in and to the following:

LISTED IN EXHIBIT A

(said patents, patent applications and invention disclosures listed in Exhibit A being hereinafter referred to as "SAID PATENT RIGHTS"); and

WHEREAS, Numonyx BV is a corporation having a principal place of business at A-ONE Biz Center, Z.A. Vers la Piece, Rte de l'Etraz, 1180 Rolle, Switzerland (hereinafter referred to as "Assignee") previously obtained rights to SAID PATENT RIGHTS;

NOW, THEREFORE, for and in consideration of good and valuable consideration the receipt, sufficiency and adequacy of which are hereby acknowledged, this agreement confirms that Assignor has sold, conveyed, transfered and assigned to Assignee, its successors, assigns and legal representatives, subject to prior encumbrances, all right, title and interest in and to SAID PATENT RIGHTS, together with any and all continuations, continuations-in-part, continuing prosecution applications, requests for continuing examinations, divisions, reissues, reexaminations, extensions, registrations, and foreign counterparts of any item in any of the foregoing, together with the right to sue for and be entitled to any damages, injunctive relief, and any other remedies of any kind for past, current and future infringement thereof.

IN WITNESS WHEREOF, Assignor has caused this Confirmation of Assignment to be executed by its duly authorized officer on this 25 day of April, 2012.

ASSIGNOR
STMicroelectronics, NV
By: _____
Printed Name: Pierre OLLIVIER
Title: Corporate General Counsel

ASIGNEE
Numonyx, BV
By: _____
Printed Name: Thomas L. Lawson
Title: Director

Exhibit A

FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
4964079	US		07342476
	JP	3101697	10714189
5544114	US		08478463
5581511	US		08096684
5638332	US		08486363
	JP	3398722	2035991993
	GB	585150	93401861.5
	FR	585150	93401861.5
5473496	US		08100867
5589793	US		08128871
5592115	US		08467297
	FR	591022	93402229.4
6118315	US		08908583
	JP	3520103	3461071993
4811291	US		07052068
6448842	US		09788623
	IT	1319841	TO00A00146
6404272	US		09785042
	IT	1158654	00830105.3
	GB	1158654	00830105.3
	DE	1158654	00830105.3
6734490	US		09919341
	EP		00830546.8
6519183	US		09908986
	JP		01207874
	EP		00830504.7
6504758	US		09960851
	IT	1320666	TO00A00892
6501673	US		09881661
	IT	1318013	MI00A01315
6462987	US		09930875
	EP		00830582.3
6480436	US		09909467
	EP		00830529.4
6359500	US		09735277
6288603	US		09595680
6563737	US		09953070
	IT	1318892	MI00A02018
6624471	US		09960254
	EP		00830628.4
6404273	US		09785083
7047478	US		10015949
	IT	1321049	TO00A01049
6603681	US		09002599
	IT	1319075	MI00A02367
6532171	US		09919789
	EP		00830553.4
6839818	US		10036088
	EP		00830878.5
6559627	US		09008540
	IT	1316002	RM00A00577
6542404	US		09972726
	IT	1320699	TO00A00936
6646913	US		09976473
	JP		01316940
	EP		00830671.4

Exhibit A

FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
6493260	US		09957628
	JP		01287008
	EP		00830627.6
6567318	US		09991493
	IT	1319130	MI00A02529
6535428	US		09882535
6493268	US		09905163
	IT	1318158	MI00A01585
6674385	US		10060076
	EP		00127649.2
6480421	US		09003474
	IT	1319037	MI00A02337
6788579	US		10119523
	EP		01830247.1
6788517	US		09917613
	IT	1318266	MI00A01729
6700226	US		10035006
6594180	US		10158554
	EP		01830345.3
6788586	US		10161053
	IT		TO01A00530
6829177	US		10161055
	IT		TO01A00531
6687167	US		10225513
	IT	RM20010525	RM01A00525
6687159	US		10036337
	IT	1319614	MI00A02807
6552952	US		10158553
	IT	1325839	MI01A01150
6667903	US		10017502
	IT	1215679	01129768.6
	GB	1215679	01129768.6
	FR	1215679	01129768.6
6643179	US		10047918
	JP		
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6655758	US		10035909
	EP		00830866.0
6963512	US		10328721
	EP		01830832.0
6657895	US		10118660
	EP		01830248.9
6731557	US		10176387
	EP		02013242.9
6605985	US		10162135
	IT		TO01A00537
6618315	US		10057769
	IT	1227499	01830039.2
	GB	1227499	01830039.2
	FR	1227499	01830039.2
6871258	US		10159780
	EP		01830369.3
6700819	US		10176954
	IT	1325884	MI01A01311
6728141	US		10123874
	EP		01830266.1

Exhibit A

FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
6639833	US		10076023
	EP		01830097.0
6724658	US		10133231
	EP		01830276.0
7017099	US		10159782
	IT		TO01A00529
7084032	US		10356351
	US		11476361
	EP		02425044.1
	US		10323615
	EP		02014408.5
6720271	US		10189152
6816001	US		10290030
	JP		02302131
	EP		01830695.1
6496439	US		09895491
6292405	US		09636363
6701419	US		09977561
	EP		00830675.5
6489807	US		09925842
	IT	VA20000027	VA00A00027
6650153	US		10033711
	IT	1220448	01130836.8
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	FR	1220448	01130836.8
	DE	60102212	01130836.8
6650569	US		10076134
	IT		TO01A00143
6560145	US		10068560
	EP		01830070.7
6674666	US		10077687
	IT		TO01A00148
6917994	US		10115888
	IT		TO01A00333
6549486	US		09998903
6720822	US		09998902
6549048	US		09925979
	FR	2812984	0010554
6807103	US		10438733
	GB	1342244	01996861.9
	FR	1342244	01996861.9
6774663	US		10060105
	GB	1227329	02290165.6
	FR	1227329	02290165.6
6928530	US		10081740
	JP		200246868
	EP		02290278.7
6568510	US		09997214
6714453	US		10352581
	FR	2816750	0014742
5557124	US		08212176
6654287	US		10171078
	IT	1325862	MI01A01232
6567296	US		09041684
	IT	1306852	02078984.8
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Exhibit A

FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
	FR	1306852	02078984.8
6865114	US		10372626
	IT	1339069	02425084.7
	GB	1339069	02425084.7
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7035769	US		10330485
	US		11294044
6829168	US		10334126
	EP		02029093.8
6696990	US		10325707
	IT	1328967	MI01A02795
6809961	US		10331116
	EP		02029092.0
6816407	US		10259252
6965523	US		10964160
	JP		02287067
	EP		01830614.2
6882001	US		10372044
	EP		02425085.4
6958949	US		10331177
	IT	1327316	MI01A02817
6822906	US		10331158
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	EP		02019284.5
6958510	US		10294999
	EP		01830700.9
6754107	US		10331185
	EP		02028616.7
6825523	US		10267033
	US		10964049
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6891755	US		10340207
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6981107	US		10281078
	EP		01830671.2
6944072	US		10440043
	JP		03142641
	EP		02425319.7
6920066	US		10438175
	EP		03010684.3
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	EP		02425416.1
7088614	US		10331161
	EP		01830827.0
6882231	US		10406628
	IT		TO02A00288
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Exhibit A

FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
	IT		MI02A00931
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6822919	US		10190917
6731550	US		10161501
	EP		03253297.0
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	IT		VA01A00035
6990596	US		10325486
	EP		01830782.7
7050322	US		10360840
	IT		TO02A00118
6996697	US		10371221
	IT		VA02A00016
6490197	US		09922043
	JP		2002224398
	EP		02255360.6
6552935	US		09922044
6563732	US		09922068
6594177	US		09922176
	EP		02255361.4
6621737	US		10096531
	EP		02366003.8
	FR	2831315	0113635
	EP		02358013.7
	EP		02358012.9
	FR	2832566	0114969
7031189	US		10434395
	IT		MI02A00984
6826083	US		10426924
	IT	1359591	02425273.6
	GB	1359591	02425273.6
6822905	US		10331106
	EP		02019433.8
6909264	US		10608998
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7135756	US		10680727
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6989580	US		10680721
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6901011	US		10417416
	EP		02425231.4
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6930927	US		10616414
	EP		02425453.4
6949803	US		10675245
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6972454	US		10715887
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Exhibit A

FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
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	IT		TO02A00787
7031193	US		10729875
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	EP		03104383.9
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	IT		MI02A02387
	EP		03104130.4
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7110300	US		10782725
	EP		03425096.9
6967876	US		10651019
6956787	US		10700322
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6940756	US		10739928
	IT		MI02A02668
	EP		03104713.7
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	IT		VA02A00067
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	IT		MI02A02570
	EP		03104384.7
6953609	US		10686556
	EP		02425615.8

Exhibit A

FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
6897710	US		10748697
	EP		02425809.7
7075844	US		10762195
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7023047	US		10745295
	IT		TO02A01119
	EP		03104939.8
7091570	US		10745297
	US		
	IT		TO02A01118
	EP		03104938.0
7054197	US		10820458
	EP		03425224.7
6785174	US		10447293
	EP		02425361.9
6975559	US		10452762
	IT		MI02A01185
6922362	US		10686552
	IT		MI02A02192
6927991	US		10653459
	IT		VA02A00045
6885584	US		10748447
	IT	1435624	02425802.2
	GB	1435624	02425802.2
	EP		03358005.1
	FR	2843660	0210350
7031212	US		10816204
	FR	304077	0304077
6891756	US		10789449
	FR	2851843	0302398
7046577	US		10760631
	EP		04000808.8
6965526	US		10775032
	FR	2851074	0301558
7012837	US		10903927
	FR		0309456
7079448	US		10867381
	EP		04012393.7
7001800	US		10911220
	EP		03425532.3
7064534	US		10695294
7012417	US		10690332
7050335	US		10867378
	EP		04013056.9
7068538	US		10921365
	EP		04291653.6
6975696	US		11076785
4802124	US		07081032
4787066	US		07081037
6373737	US		08478429
5005158	US		07464219
5279887	US		07843818
RE37769	US		08316035
5121346	US		07454408
5502655	US		08221986
5206817	US		07600201

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FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
5031152	US		07414775
	KR	223623	9013107
5072137	US		07569009
5053996	US		07661555
5265100	US		07552567
5311473	US		08071448
5161159	US		07568968
	JP	3616564	2000317923
5408435	US		07984233
5706232	US		08424722
5119340	US		07588601
5128897	US		07588577
5072138	US		07570203
5099148	US		07601288
	GB	482869	91309721.8
	FR	482869	91309721.8
5121358	US		07588609
5526318	US		08376127
5124951	US		07588600
5124584	US		07601287
	JP	3375143	3272191
	GB	482868	91309720.0
	FR	482868	91309720.0
5265054	US		07827403
5297090	US		07627050
5258952	US		07627236
	JP	3609837	3330242
	GB	490679	91311570.5
	FR	490679	91311570.5
5355340	US		08101347
5311477	US		07731803
5319768	US		07694451
	GB	0514050	92303960.6
	FR	0514050	92303960.6
5428632	US		07693670
5339322	US		07677313
	GB	0506474	92302736.1
	FR	0506474	92302736.1
5297094	US		07731487
5287322	US		07731802
5321314	US		08109697
5377153	US		07982988
5623438	US		08697482
5734602	US		08651233
5285419	US		07809393
5748556	US		08777836
5377143	US		08040916
5483489	US		08307332
5487048	US		08041321
5295104	US		07809735
5471426	US		07830315
	JP	3598119	514481
5257229	US		07830314
5311467	US		07864481
5357235	US		07876959
	JP	3509894	5104270

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FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
5319347	US		07876851
	JP	3515591	5104305
5386377	US		08122804
	GB	564137	93302156.0
	FR	564137	93302156.0
5357236	US		07890919
5355113	US		07901667
5381126	US		07923855
5508679	US		08303172
5257226	US		07809733
5534448	US		08282408
5589701	US		08486747
5831457	US		08477283
5355344	US		07975628
5526317	US		08263048
6262617	US		08367681
	GB	586207	93306835.5
	FR	586207	93306835.5
	DE	69309196	93306835.5
5422591	US		08176960
5485430	US		08306527
5455802	US		07995581
5389577	US		08180692
5400007	US		08020045
	JP	3517442	622814
5424988	US		07954276
5644542	US		08460409
5300828	US		07938399
5365129	US		08055080
5339277	US		08056078
	GB	622803	94303082.5
	FR	622803	94303082.5
5341336	US		08056376
5349246	US		07995666
5331228	US		07923135
5404331	US		08099606
	GB	637036	94305553.3
	FR	637036	94305553.3
5644216	US		08454926
5627403	US		08473552
5795821	US		08751244
	IT	0627763	93830243.7
	GB	0627763	93830243.7
	FR	0627763	93830243.7
	DE	69333722	93830243.7
5546044	US		08311941
5535157	US		08347653
5612641	US		08380309
5659501	US		08639931
5818760	US		08871226
	JP	2718902	28634994
	GB	0654791	93830464.9
	FR	0654791	93830464.9
5566114	US		08349783
5644529	US		08635455
5659509	US		08391999

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FMG with US Granted:

US Pat No.	Country	Non-US Pat. number	Filing Number
5493531	US		08350961
5708601	US		08602237
5559743	US		08412550
5546054	US		08377524
	JP	2743853	720895
	IT	0665485	94830022.3
	GB	0665485	94830022.3
	FR	0665485	94830022.3
	DE	69413793	94830022.3
5515332	US		08391160
5663921	US		08391159
5717642	US		08803915
5687135	US		08700126
5594703	US		08365510
5768115	US		08855922
5499217	US		08348461
5627790	US		08408589
5717698	US		08345530
5600600	US		08381530
5600594	US		08412326
5687124	US		08521304
5583820	US		08366211
5748548	US		08711132
	IT	0661713	93830537.2
	GB	0661713	93830537.2
	FR	0661713	93830537.2
	DE	69325277	93830537.2
6392469	US		08347788
5617356	US		08395361
5586077	US		08366212
5519656	US		08366259
5659516	US		08368211
5905677	US		08831046
5548554	US		08365154
5541884	US		08391147
	JP	2737686	753777
5532972	US		08391920
5563826	US		08422813
5638327	US		08412162
5602786	US		08389599
5541880	US		08411904
5576990	US		08367538
5486486	US		831792
5528536	US		8344232
5781043	US		08932930
	US		09616821
5471431	US		08051184
RE36319	US		08966042
5349243	US		08085760
5428311	US		08085580
5546537	US		08410383
5627793	US		08413789
5469116	US		08188153
5377150	US		08099947
5473567	US		08298766
5402379	US		08114749

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US Pat No.	Country	Non-US Pat. number	Filing Number
5579326	US		08189589
5841789	US		08647222
5572456	US		08114747
6014050	US		08801452
6252447	US		09139225
5440516	US		08188158
5835427	US		08172854
6101618	US		08172848
5568061	US		08492219
5708789	US		08717139
5396108	US		08129257
	JP	3526921	6236207
5418756	US		08129763
5568073	US		08172853
5440178	US		08160608
5491444	US		08174139
5577051	US		08173197
5424985	US		08170612
5493537	US		08202830
	JP	2720013	3140291994
5430319	US		08246070
5661324	US		08399900
	IT	651394	94460037.8
	GB	651394	94460037.8
	FR	651394	94460037.8
	DE	651394	94460037.8
5555216	US		08361313
5537349	US		08361996
	JP	2886472	33625894
5886386	US		08379337
6265277	US		09220635
5900756	US		08767521
5579265	US		08393464
	IT	0669576	95400420.6
	GB	0669576	95400420.6
	FR	0669576	95400420.6
	DE	0669576	95400420.6
5610860	US		08402519
5729162	US		08811358
	JP	2919299	9956195
5606523	US		08380737
5592417	US		08380738
5677870	US		08752814
5721706	US		08754432
5561621	US		08381529
5612611	US		08423398
	FR	678868	95470013.4
5619451	US		08421671
5796653	US		08394314
	JP	2833646	5972695
5644530	US		08418636
5651128	US		08484873
5594693	US		08408016
5590075	US		08479081
5696716	US		08794965
5715204	US		08432838

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US Pat No.	Country	Non-US Pat. number	Filing Number
5598028	US		08468282
6153537	US		08577125
6531714	US		09211065
	IT	0720223	94830591.7
	DE	69432352	94830591.7
5682349	US		08454650
	JP	3725581	7145034
5712814	US		08503303
5920776	US		08712373
	JP	3024519	7197943
5761222	US		08538161
	JP	3704184	7254046
5729492	US		08639192
5982666	US		09013141
6144588	US		09150802
	GB	0715312	94830554.5
5850360	US		08607779
	US		
5644526	US		08538302
5710739	US		08476547
5633834	US		08560324
	IT	0713221	94830538.8
5850361	US		08628587
	GB	0736876	95830133.5
	FR	0736876	95830133.5
5742187	US		08560090
5657276	US		08649468
	GB	0743648	95830211.9
	FR	0743648	95830211.9
5731716	US		08592122
	IT	0714133	94830544.6
	DE	0714133	94830544.6
5717636	US		08642325
5612913	US		08533631
	JP		7274935
5696461	US		08521666
5793676	US		08649857
5949713	US		09094916
	GB	741387	95830184.8
	FR	741387	95830184.8
6004847	US		08667097
6248630	US		09300029
	GB	0751559	95830281.2
5856221	US		08670179
	GB	0751560	95830282.0
6114203	US		08644892
	JP	3068454	854682
5894065	US		08802619
6104058	US		08898155
5812017	US		08567328
	IT	716368	94830563.6
	DE	69430806	94830563.6
5914867	US		08631574
	JP	2963047	891312
	IT	0737643	95830153.3
	GB	0737643	95830153.3

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US Pat No.	Country	Non-US Pat. number	Filing Number
	FR	0737643	95830153.3
	DE	69518826	95830153.3
5764570	US		08691796
	JP		
	GB	0757357	95830354.7
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5841728	US		08724495
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	FR	768672	95830405.7
5905683	US		08940045
5517455	US		08220976
5471157	US		08220834
	JP	3673372	774338
	GB	675597	94309218.9
	FR	675597	94309218.9
5530674	US		08235161
5583816	US		08267667
5455799	US		08267666
5521880	US		08251718
5493532	US		08251337
5589783	US		08282177
5982188	US		08282047
5566112	US		08288334
5570316	US		08438276
5495446	US		08316087
5502678	US		08315337
5517148	US		08331892
5610866	US		08331699
5574688	US		08438903
5579263	US		08362187
5568084	US		08357664
5654663	US		08631063
5596297	US		08360228
5548241	US		08360229
	JP	3679178	7330189
5594373	US		08359397
5581209	US		08359927
	JP	3596637	33198395
5598122	US		08359926
5589794	US		08360227
5917353	US		08848342
5572470	US		08438349
6052806	US		08519192
	JP	2898230	21890495
6052806	US		08519192
	JP	2898230	21890495
5734608	US		08580549
5675539	US		08575953
5742546	US		08526500
5699295	US		08649282
5652720	US		08573897
5841314	US		08663524
	FR	750244	96470009.0
5717323	US		08576881
5774390	US		08652710
5701265	US		08593650

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US Pat No.	Country	Non-US Pat. number	Filing Number
5838612	US		08869072
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	GB	0757358	95830357.0
	FR	0757358	95830357.0
5673221	US	RE38166	09410164
	JP	2857649	866710
	GB	734024	95830110.3
	FR	734024	95830110.3
5694363	US		08638976
	GB	747903	95830172.3
	FR	747903	95830172.3
5737268	US		08684431
	GB	0756285	95830336.4
	FR	0756285	95830336.4
5847584	US		08688956
	GB	0757352	95830360.4
	FR	0757352	95830360.4
5760497	US		08684192
	GB	0756220	95830335.6
	FR	0756220	95830335.6
5659502	US		08665862
5920505	US		08881713
	GB	750314	95830253.1
	FR	750314	95830253.1
5781474	US		08722378
	GB	766255	95830406.5
	FR	766255	95830406.5
5784314	US		08679656
	GB	753859	95830302.6
	FR	753859	95830302.6
5844404	US		08720491
	GB	0766256	95830407.3
	FR	0766256	95830407.3
5848013	US		08824616
6137725	US		09203937
6320792	US		09633334
	GB	798735	96830174.7
	FR	798735	96830174.7
5822247	US		08775111
	GB	782149	96830352.9
	FR	782149	96830352.9
5864513	US		08827409
	GB	0798740	96830163.0
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5659498	US		08684406
	FR	756379	95830337.2
5754483	US		08835033
	JP		975469
	IT	798729	96830160.6
	GB	798729	96830160.6
	FR	798729	96830160.6
6438669	US		08813687
	JP		959519
	GB	797209	96830129.1

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US Pat No.	Country	Non-US Pat. number	Filing Number
5729490	US		08690059
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	FR	757355	95830347.1
	DE	757355	95830347.1
6040734	US		09109630
	GB	782268	96830353.7
	FR	782268	96830353.7
5724290	US		08774110
	EP		95830555.9
6157054	US		09032179
	IT	0772200	95830461.0
	GB	0772200	95830461.0
	EP		03012504.1
6195291	US		08687145
6483750	US		09768744
	GB	756286	95830317.4
	FR	756286	95830317.4
5754476	US		08751299
	GB	0772282	95830456.0
	FR	0772282	95830456.0
5905387	US		08742978
5778012	US		08671848
	GB	766174	95830408.1
	FR	766174	95830408.1
5801988	US		08835031
	IT	0798743	96830168.9
	GB	0798743	96830168.9
	FR	0798743	96830168.9
5821786	US		08790832
	GB	788114	96830046.7
5838619	US		08828039
	GB	0798642	96830167.1
	FR	0798642	96830167.1
6000980	US		08807113
	GB	0779642	95830520.3
	FR	0779642	95830520.3
5977591	US		08824888
	GB	0798785	96830175.4
6448138	US		09548782
6222245	US		08739997
	IT	0772246	95830459.4
	GB	0772246	95830459.4
	FR	0772246	95830459.4
5926416	US		08807574
	IT		96830088.9
	GB		96830088.9
5817557	US		08792893
	FR	0788144	96830039.2
5923975	US		08784967
	IT	785570	96830021.0
	GB	785570	96830021.0
	FR	785570	96830021.0
5859795	US		08791348
	JP		918819
	IT	788113	96830044.2

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US Pat No.	Country	Non-US Pat. number	Filing Number
	FR	788113	96830044.2
	WO		IT9600198
6101121	US		09202657
	JP		10502636
	GB	906622	96937493.3
	FR	906622	96937493.3
5986921	US		08883822
	JP		9172303
	GB	0817200	96830371.9
	FR	0817200	96830371.9
	WO		IT9600199
6097628	US		09202656
	JP		10502637
	GB	906623	96937494.1
	FR	906623	96937494.1
5854764	US		08821804
	JP		966172
	GB	797145	96830144.0
	FR	797145	96830144.0
5999450	US		08853756
	GB	806773	96830267.9
	FR	806773	96830267.9
5917753	US		08845916
6055187	US		09209319
5818763	US		08774860
	GB	782145	95830554.2
	FR	782145	95830554.2
5886949	US		08978665
	GB	845784	96830598.7
6195290	US		09407135
	US		
	GB	782148	96830245.5
	FR	782148	96830245.5
5721707	US		08787907
	IT	786779	96830025.1
	GB	786779	96830025.1
	FR	786779	96830025.1
5784319	US		08788530
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	IT	786778	96830024.4
	GB	786778	96830024.4
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	GB	0782144	95830552.6
	FR	0782144	95830552.6
5757719	US		08869208
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	FR	811986	96830318.0
5796275	US		08791700
	IT	788231	96830043.4
	GB	788231	96830043.4
6057591	US		09014437
6210994	US		09534675
	JP		1018490

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US Pat No.	Country	Non-US Pat. number	Filing Number
	IT	0856886	97830029.1
	GB	0856886	97830029.1
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5917768	US		08847385
	GB	0805453	96830239.8
5878049	US		08840056
	GB	0805452	96830238.0
	FR	0805452	96830238.0
5777941	US		08853732
	GB	0810606	96830275.2
	FR	0810606	96830275.2
5751654	US		08826223
	GB	0798742	96830166.3
6148413	US		08835030
	GB	0798726	96830161.4
5854770	US		08791746
5946237	US		08826489
6212096	US		09351603
	IT	0798727	96830162.2
	GB	0798727	96830162.2
5831891	US		08812595
	GB	797208	96830128.3
	FR	797208	96830128.3
5859810	US		08826009
	GB	0798730	96830169.7
	FR	0798730	96830169.7
5625603	US		08477244
5793247	US		08667481
5640122	US		08464551
	GB	747800	96303214.9
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5576656	US		08414103
RE37876	US		09568201
5768206	US		08484491
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5745420	US		08833582
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5608678	US		08509351
5648933	US		08509211
5629896	US		08521800
5612918	US		08582424
6144594	US		08587709
6297996	US		09457558
5701275	US		08588730
5798980	US		08878612
5801563	US		08588988
5790462	US		08580827
5657292	US		08588662
5845059	US		08588762
5745432	US		08589141
5808960	US		08858295
	JP		96024

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US Pat No.	Country	Non-US Pat. number	Filing Number
5825691	US		08858788
	JP		96236
5802004	US		08587726
5828622	US		08944649
5848018	US		08926833
5864696	US		08587711
6006339	US		09020430
	JP		96721
5619466	US		08589024
5883838	US		08929987
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	FR	760518	96305856.5
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	JP		8219954
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	JP	2727527	10419096
5760638	US		08664083
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5801577	US		08762677
5737266	US		08738231
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	GB	0798741	96830165.5
	FR	0798741	96830165.5
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5929674	US		08846757
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5822259	US		08846755
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5805500	US		08877921
	JP		9161557
	GB	814482	96830346.1
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6215329	US		08899228
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5754473	US		08835294
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	GB	0811988	96830326.3
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5886925	US		08877922
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6841445	US		10792308
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5994231	US		08996920
6156637	US		08997403
6630739	US		09687217
5883837	US		08940115
5973966	US		09203798
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6380582	US		09528406
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5880993	US		08941882
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	FR	2758022	9616355
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5969961	US		09059088
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	FR	2770947	9714018
5966034	US		09087478
	FR	2764135	9706703
6127898	US		09005722
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6888225	US		10323961
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	IT	0869506	97830160.4
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6195286	US		09353756
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	IT	0905712	97830477.2
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6369406	US		09311258
	IT	1301100	MI98A01123
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	IT	1293644	TO97A00667
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5926059	US		08927391
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6028793	US		09224330
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6144589	US		09186758
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6153914	US		09170788
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6275099	US		09239908
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6101118	US		09196204
6285614	US		09602669
	IT	1296486	MI97A02594
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6097633	US		09182843
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6133718	US		09246029
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	IT	1298938	MI98A00351
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6181602	US		09322460
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6551892	US		09891438
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6251728	US		09359923
6420769	US		09861404
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6456527	US		09501131
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	JP		0049429
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6084390	US		09217323
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6081466	US		09183451
6041000	US		09183840
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6511874	US		09912638
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6240002	US		09561271
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	FR	2782421	9810308
6212112	US		09452446
	FR	2787233	9815786
6249456	US		09448632
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6333885	US		09603275
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	JP		00227222
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6420223	US		09730518
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6418051	US		09785079
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6954395	US		10742181
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	EP		00830209.3
6451653	US		09858335
	EP		00201716.8
6581134	US		09817804
	IT	1139210	00830228.3
	GB	1139210	00830228.3
	FR	1139210	00830228.3
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6650173	US		09714852
	IT	1311441	TO99A00994
6686241	US		09798778
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6476664	US		09823262
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6559709	US		09821827
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	JP		2001508458
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	JP		2000281033
	GB	1085520	00402549.0
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	DE	1085520	00402549.0
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6385096	US		09952904
	EP		00402443.6
	GB	1085518	00402548.2
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	EP		00125553.8
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4816883	US		64480
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4968639	US		07284272
4949307	US		07298487
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RE36579	US		08488718
5486487	US		08139800
5657484	US		08364505
5179300	US		07691768
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5696399	US		08475555
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5407861	US		08068139
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5793086	US		08772301
5515318	US		84654
5793675	US		08829935
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5372956	US		08153620
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5637520	US		08195369
	JP		616744
5466622	US		08196634
5913120	US		08502329
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5497345	US		8196572
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6816404	US		10319439
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	US		110201790
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	US		11045170
	EP		02425087.0
6972430	US		10371154
	US		11258340
	EP		02425088.8
6930913	US		10372639
	US		11156989
	EP	1339111	02425089.6
7092277	US		10926784
	EP		03077667.8
RE35,385	US		08336560
	DE		88403141.0
	FR		8717900
	GB		88403141.0
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	JP	2931864	3247668
	KR		1718688
	US		07283305
	US		07912867
RE35,578	US		08198208
	US		7283214
	DE		88403140.2
	EP	321327	88403140.2
	FR		8717386
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	IT	1368784	02706857.6
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	FR		9711787
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6140869	US		09234194
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6842191	US		09705145
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6856547	US		10664606
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Country	Filing Number	Patent number
IT	MI00A02593	1319493
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IT	MI02A02629	
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IT	MI03A01403	
US	10387141	
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IT	VA02A00012	
US	10639240	
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US	10789443	
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US	10690368	
JP	2004307123	
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IT	MI04A02373	
EP	05027285.5	
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IT	MI05A000610	
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Exhibit A

FMG Pending

Country	Filing Number	Patent number
US	10816271	
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US	10698747	
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US	11348513	
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EP	05425052.7	
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US	11323937	
EP	05425001.4	
US	11437405	
EP	05425347.1	
US	11437268	
EP	05425348.9	
US	11300145	
IT	MI04A002374	
EP	05027286.3	
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EP	05425814.0	
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US	11411982	
EP	05425261.4	
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US	11334205	
IT	VA05A000001	
US	11340414	
JP	06015176	
EP	05100551.0	
CN	0610059263.5	
US	11444892	
EP	05104656.3	
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IT	MI05A000780	
US	11304488	
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US	11368363	
EP	05101659.0	
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EP	04425724.4	

Exhibit A

FMG Pending

Country	Filing Number	Patent number
US	11482524	
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IT	VA05A00002	
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EP	05100308.5	
US	11337085	
EP	05100310.1	
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IT	VA05A000024	
US	11455896	
EP	05425440.4	
US	11093012	
EP	04101301.2	
US	11035013	
US	11036179	
US	11261131	
IT	MI04A02072	
US	11495874	
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US	11458916	
EP	05106782.5	
IT	MI06A 001037	
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IT	MI05A001679	
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Exhibit A

FMG Pending

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EP	06120719.7	
IT	VA06A000065	
EP	06425503.7	
EP	06425537.5	
EP	06425535.9	
IT	94830544.6	0714133
DE	94830544.6	0714133
IT	MI97A01682	1293610
IT	97830575.3	0915408
GB	97830575.3	0915408
FR	97830575.3	0915408
IT	98830491.1	0978844
FR	98830491.1	0978844
DE	98830491.1	0978844
IT	99830491.9	1073119
GB	99830491.9	1073119
FR	99830491.9	1073119
IT	MI99A02650	1314142
IT	MI00A00065	1316286
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US	09823926	
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Exhibit A

FMG Pending

Country	Filing Number	Patent number
FR	9911858	2798769
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US	10313991	
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EP	06112075.4	
US	11398858	
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WO	EP06062812	
EP	05104877.5	
EP	06425531.8	
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EP	4425112.2	
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US	11113818	
EP	4101718.7	
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US	11672857	
IT	MI06A000220	
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IT	VA07A000042	
IT	VA07A000026	
IT	MI07A000787	

Exhibit A

FMG Invention Disclosures

Invention Disclosure
TECNICA DI SCRITTURA DI UNA MEMORIA A CAMBIAMENTO DI FASE CON SELETTORE BIPOLARE A RIDUZIONE DI TENSIONE
PROCESSO PER LA REALIZZAZIONE DI UNA MEMORIA NON VOLATILE AD ALTA DENSITA' INTEGRABILE CON CIRCUITERIA AD ALTRE PRESTAZIONI MEDIANTE
CIRCUITERIA PER DISPOSITIVI DI MEMORIA NON VOLATILE REALIZZATI INTERAMENTE CON OSSIDI LOW VOLTAGE
SHAPES OF FLOATING GATE WITH A BROKEN PROFILE IN A PROCESS FLOW WITHOUT SELF ALIGNED FLOATING GATE
PROCESSO PER INTEGRARE MEMORIE FLASH CON LOGICHE AVANZATE
ARCHITETTURA CIRCUITALE E PROTOCOLLO DI COMUNICAZIONE PER L'INDIRIZZAMENTO DELLO SPAZIO DEI REGISTRI DI PROTEZIONE DEI SOTTO-
TECNICA DI RIDONDANZA HARD SOFT
ELEVATOR A RISPARMIO ENERGETICO
SANDWICH MULTI-LAYER HARDMASK
METODO PER LA DEFINIZIONE DEI CONTATTI IN UNA MEMORIA MEDIANTE DOPPIA ESPOSIZIONE LITOGRAFICA
CONSTANT ACCESS TIME WITH TEMPERATURE VARIATION
PIPILINE ROW DECODER
CONTINUOS GATE RAMP REFERENCE SETTING
METODOLOGIA DI PRECARICA CONTROLLATA PER APPLICAZIONI LOW VOLTAGE E HIGH PERFORMANCE
MODALITA' ALTERNATIVA DI TESTING DI DISPOSITIVO A SEMICONDUTTORE CHE ESCLUDA L'UTILIZZO DI MACCHINE DI ESTING E IMPIEGHI SCATOLE PER AUTOTEST
DISPOSITIVO A SEMICONDUTTORE PREDISPSOTO ALLA CONTATTATURA DAL RETRO MEDIANTE VIE PASSANTI ATTRAVERSO IL SUBSTRATO
NUOVA PROGRAMMAZIONE PER MEMORIE FLASH NOR
METODO DI FABBRICAZIONE DI UNA CELLA FOTOVOLTATICA FLESSIBILE A STATO SOLIDO
METODO PER RIDURRE IL DISTURBO DI WORD LINE DURANTE LA FASE DI CANCELLAZIONE DI MEMORIE FLASH LA CUI ORGANIZZAZIONE PREVEDA LA
STRUCTURE AND METHOD TO OBTAIN A FAST PROGRAM NAND DEVICE
PARTITION SUPPLY INDEPENDENCE
METODO LITOGRAFICO PER LA DEFINIZIONE DELLE GEOMETRIE DI UN DISPOSITIVO MEDIANTE UTILIZZO DELLA POLARIZZAZIONE DELLA LUCE DI ESPOSIZIONE E
PROCESS FOR HAVING LITHOGRAPHIC PITCH TO DEFINE MEMORY ARRAYS
SCHEMA DI INTEGRAZIONE MEDIANTE TECNICA DPCC DI LOGICA AD ALTE PRESTAZIONI IN UN PROCESSO PER MEMORIE NON VOLATILI A FLOATING GATE DI
HIGH IMPEDANCE DRAIN VOLTAGE REFERENCE DISTRIBUTION ARCHITECTURE
MEMORY CELL FOR SUB-50NM FLASH NON VOLATILE MEMORIES
DEFINIZIONE DI CONTATTI TRAMITE ESPOSIZIONE DI MASCHERE LINEE-SPAZI E ATTACCHI DRY ALTAMENTE SELETTIVI
REALIZZAZIONE INNOVATIVA DEL LIVELLO DI CONTATTATURA IN MEMORIE NON VOLATILI IN PRESENZA DI ALTA DENSITA' DELLE STRUTTURE, CON
REFERENCE CELL WITH ENHANCED RTN IMMUNITY
A NEW ARCHITECTURE FOR A SINGLE POLYSILICON LEVEL FLAH EEPROM CELL IN ARRAY
VIRTUAL GROUND FLASH NAND MEMORY
CONTATTI CON STRATO DI ADESIONE E SILICIURIZZAZIONE MEDIANTE FILM DI COBALTO PER LOGICHE E MEMORIE
REGOLATORE DI TENSIONE "ON CHIP" PER MEMORIE FLASH NOR UTILIZZANTE SOLO TRANSISTORI HV
BUFFER DI USCITA CON SPEED UP AUTO-ADATTATIVO DEI SEGNALI DI CONTROLLO DEI DRIVERS FINALI

Exhibit A

FMG Invention Disclosures

Invention Disclosure
PORTABLE UNIVERSAL FLASH MEMORY FUNCTIONAL DIAGNOSTIC PLATFORM
GAP FILL MODULATION BY USING RAMPED INPUT PARAMETERS PROCESS (RIPP) IN HIGH DENSITY PLASMA REACTORS
REALIZZAZIONE DI UNA NUOVA TECNICA LITOGRAFICA CHE PERMETTA L'ESPOSIZIONE DIFFERENZIATA DI PATTERN PRESENTI SULLA STESSA MASCHERA
SISTEMI DI RIFERIMENTI PER IL TRACCIAMENTO DELLO SPOSTAMENTO DELLE SOGLIE DOPO CICLATURA, IN MEMORIE FLASH
PROCESS TO INTEGRATE IN A SINGLE CHIP FLASH MEMORY AND ADVANCED CMOS: AN IMPROVEMENT WITH RESPECT TO PATENT 99-AG-328
NUOVO ALGORITMO DI PROGRAMMAZIONE - CANCELLAZIONE PER MIGLIORARE PRESTAZIONI E AFFIDABILITA' DI UN DISPOSITIVO DI MEMORIA NON VOLATILE
TECNICA DI SCRITTURA DI UNA MEMORIA A CAMBIAMENTO DI FASE MULTILIVELLO
PROCESSO INNOVATIVO PER LA RIMOZIONE SLETTIVA DEI METALLI NON REAGITI DURANTE LA DORMAZIONE DI SILICIURI AUTOALLINEATI MEDIANTE L'USO DI
NUOVA STRUTTURA DELLA STRINGA DI UNA MEMORIA FLASH NAND
FLUSSO SASTI+POLY1-1 CON POLYCMP OTTIMIZZATO PER OTTENERE UN MIGLIOR ACCOPPIAMENTO CAPACITIVO
FLUSSO DSASTI
ARCHITETTURA CON CELLE DI RIFERIMENTO MULTIPLE PER UN SINGOLO LIVELLO D'INFORMAZIONE IN UNA MEMORIA NOR FLASH
ERROR CORRECTION CODE METHOD WITH DYNAMIC ENABLING/DISABLING
OTTIMIZZAZIONE DELLA LARGHEZZA DELLA DISTRUBUZIONE DU SOFT PROGRAM IN UNA MEMORIA FLASH NOR
REFRESH DELLE CELLE PROGRAMMATE DURANTE L'OPERAZIONE MDI CANCELLAZIONE
ARCHITECTURE OPTIMIZATION FOR TRISTATE NORFLASH MEMORY
METODO DI PROGRAMMAZIONE E BIT-MANIPULATION PER MEMORIE FLASH TRISTATO CON RECUPERO DAL POWER LOSS COMPATIBILE CON FLASH 2 BIT PER
COMPENSAZIONE DEI TEMPI DI SET UP NELLA GENERAZIONE DEGLI STATI DI WAIT
METODO PER UNA GESTIONE MISTA VOLATILE/NON VOLATILE DELLO STATO DI PROTEZIONE DEI SETTORI DI UNA MEMORIA FLASH
PARITY CHECK SOLUTION FOR POWER ON INFORMATION
PATTERN BINARIO PER CELLE TRI-STATO IDONEO ALLA BIT MANIPULATION IN DI RECOVERY DOPO POWER LOSS
SEPARAZIONE REFERENCE DI READ E PROGRAM SU PIU' WORD LINE PER MINIMIZZARE L'EFFETTO DEL READ DISTURB DURANTE L'UTILIZZO DELLE REFENCE
IC SEMICONDUCTOR DEVICE INFORMATION WITH THROUGH SILICON VIAS TECHNOLOGY FOR STACKED DICE
A MEMORY HAVING AN EMBEDDED ECC WITH WORDS MANAGEMENT CAPABILITIES
A MEMORY WITH SIMULTANEOUS SLC AND MLC READ MODES CAPABILITIES
FLASH MEMORY ARCHITECTURE WITH ROW ADDRESS SCRAMBLING
REFERENCE CELLS NUMBER REDUCTION IN GATE RAMP READING SYSTEM BY MEANS OF DIODES
PRPOSTA DI BREVETTO PER LA SCRITTURA MULTILIVELLO DI CELLE DI MEMORIA CON TRIMMING DEL RESET
UTILIZZO DI UNA MATRICE DI MEMORIA FLASH PER APPLICAZIONE DI DOSIMETRIA
DISPOSITIVO BARRIERA ALLA CRESCITA DI WHISKER PER PACKAGES A INSERZIONE MONTATI SU BOARD
A MEMORY WIH SIMULTANEUS SLC AND HLC PROGRAM MODES CAPABILITIES
A METHODOLOGY FOR REDUCING CONTAMINATION COMING FROM THE SUBSTRATE DURING HIGH THEMPERATURE OXIDATION
RAPID ACCESS WORDLINE

Exhibit A

FMG Invention Disclosures

Invention Disclosure
ARCHITETTURA DELLE LINEE DI ALIMENTAZIONE PER MEMORIE CON FUNZIONAMENTO DUAL WORK AD ALTE PERFORMANCE
ARCHITETTURA PER UNA MEMORIA FLASH AD ELEVATA SICUREZZA CONTROLLABILE DAL CLIENTE
ARCHITETTURA DI LETTURA PER MEMORIE INSENSIBILI A DEGRADO DELLE CELLE
RAM FOR FIRMWARE PATCH E DEBUGGING
PROPOSTA DI ARCHITETTURA DI POMPA DI CARICA NEGATIVA AD ELEVATA EFFICIENZA
ARCHITETTURA E METODOLOGIA PER UN PRECISO E VELOCE SETTING DELLE CELLE DI RIFERIMENTO IN MEMORIE FLASH
METODOLOGIA DI PROGRAMMAZIONE DI UNA CELLA FLASH SINGLE BIT ADATTATIVA ALL'INVECCHIAMENTO E SENZA VERIFICA
4GB 60mm NAND FLASH
CIRCUITO DI LETTURA DELLE CELLE DI RIFERIMENTO PER FLASH MEMORY MULTILIVELLO
CIRCUITO DI RIDUZIONE DEL RUMORE DALL'ALIMENTAZIONE IN UN SENSE AMPLIFIER PER FLASH MEMORY MULTILIVELLO
CIRCUITO DI LETTURA DI UNA FLASH MEMORY MULTILIVELLO CON RIFERIMENTO "VIRTUALE"
CIRCUITO DI LETTURA PER FLASH MEMORY 2b/c VS 1b/c
INVALIDATION D'UN PLAN MEMOIRE
GESTION DES RAFRAICHISSEMENTS SUR UNE MEMOIRE FLASH EFFACABLE PAR PAGE ET SOUS-SECTEURS
GENERATEUR DE RAMPE HAUTE TENSION POUR MEMOIRE RF
DETECTEUR D'HORLOGE
GENERATEUR DE RAMPE HAUTE TENSION POUR MEMOIRE RF AVEC DIFFERENTIEL HAUTE TENSION
NEW WRITE METHOD FOR PHASE CHANGE MEMORIES
NEGATIVE POLARITY FOR READING PHASE CHANGE CELLS WITH VERY SHORT DELAY AFTER PROGRAMMING
HEATER ENGINEERING FOR PHASE CHANGE MULTI BIT STORAGE DEVICES
PHASE CHANGE MEDIA FINE PATTERING WITH ELECTRODEPOSITON OF A CONDUCTIVE MATERIAL
PRECARIA E SENSE PER UN DISPOSITIVO PCM CON SELETTORE A BIPOLARE
NITRIDE PROTECTIVE LAYER FOR TISIN CVD HEATER ELEMENT FOR PCM
SCRITTURA MULTILIVELLO DI CELLE DI MEMORIA PCM CON RISCALDAMENTO E RAFFREDDAMENTO GRADUALE
TECNICA DI LETTURA PER MEMORIE PCM-MLC
PROPOSTA DI BREVETTO PER IL CRIPTAGGIO DI DATI INUNA MEMORIA MULTILIVELLO PCM
A NEW VIRTUAL BLOCKS ARCHITECTURE FOR FLASH MEMORIES
A NOVEL MECHANISM OF INHERITING HASH TABLE FOR WEAR LEVELING
A DEFERRED MINIMIZE STRUCTURE MECHANISM IN FTL
A CYCLE BASED WEAR LEVELLING ARCHITECTURE
CONFIGURABLE MEMORY ARCHITECTURE SIMULATION
METHOD FOR THE REDUCTION OF THE SWITCHING NOISE AFFECTING VOLTAGFE REFERENCE LINES
ARCHITECTURE TO OPTIMIZE PROGRAMMING IN MEMORIES
STRUCTURE AND METHOD TO OBTAIN AN ENHANCED MULTILEVEL NAND FLASH MEMORY
WRITE WITH FLUSH COMMAND FOR A LOW POWER DOUBLE RATE NON VOLATILE MEMORY
METODO DI LETTURA AD ALTA PRECISONE PER LE CELLE DI UNA MEMORIA FLASH

Exhibit A

FMG Invention Disclosures

Invention Disclosure
METODO DI LETTURA A TEMPO VARIABILE PER UNA MEMORIA FLASH
FAST PROGRAM VERIFY
ARCHITETTURA CIRCUITO DI LETTURA PER MEMORIE A DUE BLOCCHI
METODO DI COMPENSAZIONE NEI DISTURBI DI PROGRAMMAZIONE IN UNA MEMORIA NON VOLATILE
METODO DI LETTURA AD ALTA PRECISIONE MMEDIANTE CAMPIONAMENTO DEL VALORE ANALOGICO DELLA TENSIONE DI BIT LINE PER CELLE DI MEMORIA NAND
RIDUZIONE DELLA PROBABILITA' DI FALLIMENTO PER SILC TRAMITE POLARIZZAZIONE DINAMICA DI RIPOSO PER ARRAY DI MEMORIE FLASH
READING METHOD FOR NAND MEMORIES
NUOVO ALGORITMO DI PROGRAMMAZIONE PER MIGLIORARE PRESTAZIONI E AFFIDABILITA' DI UN DISPOSITIVO DI MEMORIA NON VOLATILE
PROGRAMMING METHODOLOGY TO INCREASE CYCLING PERFORMANCE
METODO DI PROGRAMMAZIONE PER UNA MEMORIA NAND
ALGORITMO DI CODIFICA LOGICA DEI DATI IN MEMORIE DIGITALI PER IL MIGLIROAMENTO DELLE PRESTAZIONI AFFIDABILISTICHE
BULK ERASE TIME REDUCTION IN NON VOLATILE MEMORY DEVICES
METODO DI CAMPIONAMENTO DI CELLE DI RIFERIMENTO PER MEMORIE CON ARCHITETTURA SINCRONA E DUAL WORK
MEMORIE MULTILIVELLO SINGLE BIT
MEMORIE MULTILIVELLO A CODIFICA MULTIBIT RIDONDATA
ALGORITMO PER LA PROTEZIONE DATI IN MEMORIE MULTILIVELLO A CODIFICA RIDONDATA
ALGORITMO DEDICATO A OTTIMIZZARE LE PRESTAZIONI DI SCRITTURA IN MEMORIE MULTILEVEL SINGLE BIT
EFFICACE SISTEMAPER IL RECUPERO DELLO STATO DELLA MEMORIA FLASH DOPO POWER LOSS
TWO-DIMENSION HASH TABLE MECHANISM FOR BLOCK MANAGER

Exhibit A

Hynix: Co-Owned

Priority	COUNTRY	APP.NUM	REG.NUM
20040078954	KR	20040078954	0624960
	US	11/010664	
20040097161	KR	20040097161	0582421
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20030034695	KR	20030034695	0526576
	US	10/736719	6903595
20030036500	KR	20030036500	0554830
	US	10/727470	6869848
20030038233	KR	20030038233	0532780
	US	10/739649	6908805
20030042420	KR	20030042420	0511679
	US	10/720457	
20030040155	KR	20030040155	0497474
	US	10/722814	7179707
20030062485	KR	20030062485	0542394
	US	10/744495	6803277
20030060792	KR	20030060792	0538075
	US	10/883279	7041555
20030043614	KR	20030043614	0535651
	US	11/379455	7262995
	US	10/740100	7072216
	US	11/379456	7280402
20030059419	KR	20030059419	0481890
	US	10/880691	7169670
20030043792	KR	20030043792	0554836
	US	10/736720	7067425
20030062073	KR	20030062073	0537278
	US	10/881461	6835620
20030067157	KR	20030067157	0613078
	US	10/886867	7061803
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	US	10/743934	6998873
20030096240	KR	20030096240	0543310
	US	10/878093	7110296
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	US	10/879434	7015743
20030043798	KR	20030043798	0568425
	US	10/734389	6964921
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	US	10/882451	6987046
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	US	10/727478	6927151
20030100158	KR	20030100158	0562985
	US	10/879785	
20030081957	KR	20030081957	0538886
	US	10/878273	7034360
20030079422	KR	20030079422	0538379
	US	10/878811	6958289
20030043624	KR	20030043624	0543655
	US	10/739746	7199028
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	US	10/730688	6858543

Exhibit A

Hynix: Co-Owned

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20040021780	KR	20040021780	0538884
	US	11/018701	7166510
20030043400	KR	20030043400	0490288
	US	10/734533	6884682
20030088265	KR	20030088265	0582335
	US	10/876065	6930001
	US	11/137895	
20030077490	KR	20030077490	0562675
	US	10/880035	7078332
20030043621	KR	20030043621	
	US	10/740089	6974747
20030043619	KR	20030043619	0578656
	US	10/720408	6964913
20030049469	KR	20030049469	0542388
	US	10/731480	7037822
20030093726	KR	20030093726	0705937
	US	10/879840	7271439
20030043688	KR	20030043688	0538882
	US	10/743578	7179735
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	US	10/887964	6979618
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	US	10/745008	7211484
20030043410	KR	20030043410	
	US	10/740352	7022624
20030043686	KR	20030043686	
	US	10/727825	6927168
20030070557	KR	20030070557	0714034
	US	10/876144	7030684
20040001648	KR	20040001648	0562134
	US	11/007182	7099213
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	US	10/879848	7053689
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	US	10/879540	7031210
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	US	10/876121	7102942
20030077246	KR	20030077246	0562674
	US	10/872725	7259067
20030100169	KR	20030100169	0568790
	US	10/887944	7109109
20030091653	KR	20030091653	
	US	10/878916	
20030100172	KR	20030100172	0567530
	US	10/880282	7030036
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	US	10/881423	
20040001656	KR	20040001656	0533772
	US	10/887258	7067389
20030100171	KR	20030100171	0567529
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	US	10/883414	6943075

Exhibit A

Hynix: Co-Owned

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20040012705	KR	20040012705	0520682
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	US	11/006082	7027330
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	US	10/879857	6963509
20040027109	KR	20040027109	0539158
	US	10/879680	6984562
20040011753	KR	20040011753	0541157
	US	10/883402	7148109
20030098846	KR	20030098846	0612557
	US	10/878173	
20040033207	KR	20040033207	0604561
	US	11/010987	7196373
20040022677	KR	20040022677	0559716
	US	10/876319	7035143
20040012714	KR	20040012714	0559715
	US	11/007183	7095656
20040011754	KR	20040011754	0537554
	US	11/007181	
20040001749	KR	20040001749	0609942
	US	10/880202	7157332
20040019745	KR	20040019745	0630535
	US	11/008486	7187584
20040034443	KR	20040034443	0635203
	US	11/014581	7072221
20040033199	KR	20040033199	0624287
	US	11/010515	7236397
20040026766	KR	20040026766	0559714
	US	10/888067	7212439
20040033214	KR	20040033214	0613079
	US	11/010165	7126434
20040027108	KR	20040027108	0602322
	US	10/879671	7084031
20040034518	KR	20040034518	0582422
	US	11/016286	7075824
20040038468	KR	20040038468	0567912
	US	11/009749	7046554
20040001746	KR	20040001746	0665396
	US	11/007311	7132328
20040019479	KR	20040019479	0559040
	US	11/009712	7192883
20040024186	KR	20040024186	0554828
	US	10/880278	7205242
20040043618	KR	20040043618	0624290
	US	10/887260	7015097
20040070228	KR	20040070228	0705221
	US	11/011725	7161842
20040070229	KR	20040070229	0580117
	US	11/016437	7259078
20040054061	KR	20040054061	0539449
	US	11/014570	7138314

Exhibit A

Hynix: Co-Owned

Prioirity	COUNTRY	APP.NUM	REG.NUM
20040049763	KR	20040049763	
	US	11/016413	7268064
20040054510	KR	20040054510	0519170
	US	11/018698	7229912
20040087145	KR	20040087145	0650835
	US	11/020330	7183173
20040055273	KR	20040055273	0609568
	US	11/014507	7061813
20040085423	KR	20040085423	0650839
	US	11/011962	
20040073679	KR	20040073679	0616193
	US	11/010986	7259063
20040079505	KR	20040079505	0650846
	US	11/016436	7279394
20040085429	KR	20040085429	0607330
	US	11/010755	7235458
20040057185	KR	20040057185	0694982
	US	11/119646	
20040085430	KR	20040085430	
	US	11/015451	7122443
20040079903	KR	20040079903	0616187
	US	11/022460	
20040084179	KR	20040084179	0671583
	US	11/027153	
20040078957	KR	20040078957	0609576
	US	11/010156	7206228
20040093176	KR	20040093176	0635205
	US	11/103383	
	US	11/007918	7189618
	US	11/138560	7223655

PATENT ASSIGNMENT AGREEMENT

WHEREAS, Numonyx B.V., a company organized under the laws of Netherlands, having a place of business at A-ONE Biz Center, Z.A. Vers la Piece, Rte. De l'Etraz, 1180 Rolle, Switzerland (hereinafter referred to as "Assignor") has rights in and to the following:

1. U.S. Letters Patents Listed on Exhibit A,
2. U.S. Patent Applications listed on Exhibit B,
3. Foreign patents and patent applications listed on Exhibit C.

(said patents and patent applications listed in Exhibits A, B, and C being hereinafter referred to as "SAID PATENT RIGHTS"); and

WHEREAS, Micron Technology, Inc. is a corporation having a principal place of business at 8000 S. Federal Way, Boise, Idaho 83707, United States (hereinafter referred to as "Assignee") is desirous of obtaining rights to SAID PATENT RIGHTS;

NOW, THERFORE, for and in consideration of good and valuable consideration the receipt, sufficiency and adequacy of which are hereby acknowledged, Assignor does hereby sell, convey, transfer and assign to Assignee, its successors, assigns and legal representatives, subject to prior encumbrances, all right, title and interest in and to SAID PATENT RIGHTS, together with any and all continuations, continuation-in-part, continuing prosecution applications, requests for continuing examinations, divisions, reissues, reexaminations, extensions, registrations, and foreign counterparts of any item in any of the foregoing, together with the right to sue for and be entitled to any damages, injunctive relief, and any other remedies of any kind for past, current and future infringement thereof.

IN WTINESS WHEREOF, Assignor has caused this Assignment to be executed by its duly authorized officer effective as of the 23 day of May, 2012

Numonyx B.V.
By: Thomas L. Lewis
Printed Name: Thomas L. Lewis Sr.
Title: Director

Micron Technology, Inc.
By: Roderic W. Lewis
Printed Name: Roderic W. Lewis
Title: V.P. of Legal Affairs

f.s.

STMicroelectronics originated

Exhibit A - US Issued Patents

MTI-DocNo	MatterTyp	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0001.00/RE	Utility - REIS	Expired	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINED THEREBY	12/12/1988	08/198,208	3/20/1990	RE35,578	US
NMXS-0001.00/US	Utility - ORG	Expired	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/12/1988	07/283,214	3/20/1990	4,908,937	US
NMXS-0002.00/US	Utility - ORG	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/12/1988	07/283,305	7/17/1990	4,941,257	US
NMXS-0002.01/RE	Utility - REIS	Expired	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	11/9/1994	08/336,560	7/17/1990	RE35,385	US
NMXS-0003.00/US	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/24/1989	07/342,475	10/16/1990	4,964,079	US
NMXS-0004.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/23/1993	08/096,684	12/3/1996	5,581,511	US
NMXS-0004.01/US	Utility - CON	Issued	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	6/7/1995	08/486,363	6/10/1997	5,638,332	US
NMXS-0004.02/US	Utility - DIV	Issued	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	6/7/1995	08/478,463	8/6/1996	5,544,114	US
NMXS-0005.00/US	Utility - ORG	Issued	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	8/2/1993	08/100,867	12/5/1995	5,473,496	US
NMXS-0006.00/US	Utility - ORG	Issued	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH BOOTSTRAPPED OSCILLATOR	9/29/1993	08/128,871	12/31/1996	5,589,793	US
NMXS-0006.01/US	Utility - DIV	Issued	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	6/6/1995	08/467,297	1/7/1997	5,592,115	US
NMXS-0007.01/US	Utility - CON	Issued	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY INTERRUPTIONS	8/8/1997	08/908,583	9/12/2000	6,118,315	US
NMXS-0008.00/US	Utility - ORG	Expired	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/21/1987	07/052,068	3/7/1989	4,811,291	US
NMXS-0009.00/US	Utility - ORG	Expired	NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	8/3/1987	07/081,032	1/31/1989	4,802,124	US
NMXS-0010.00/US	Utility - ORG	Expired	NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	8/3/1987	07/081,037	11/22/1988	4,787,066	US
NMXS-0011.03/US	Utility - CON	Issued	CONTENT ADDRESSABLE MEMORY	6/7/1995	08/478,429	4/16/2002	6,373,737	US
NMXS-0012.00/US	Utility - ORG	Expired	REDUNDANCY FOR SERIAL MEMORY	1/12/1990	07/464,219	4/2/1991	5,005,158	US
NMXS-0013.00/RE	Utility - REIS	Expired	METHODS FOR FABRICATING MEMORY CELLS AND LOAD ELEMENTS	9/29/1994	08/316,035	9/29/1992	RE37,769	US
NMXS-0013.00/US	Utility - ORG	Abandoned	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	4/30/1990	07/516,272	9/29/1992	5,151,387	US
NMXS-0013.01/US	Utility - DIV	Expired	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	2/28/1992	07/843,818	1/18/1994	5,279,887	US
NMXS-0014.00/US	Utility - CIP	Expired	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/21/1989	07/454,408	6/9/1992	5,121,346	US
NMXS-0014.03/US	Utility - CON	Issued	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	4/1/1994	08/221,986	3/26/1996	5,502,655	US
NMXS-0015.00/US	Utility - ORG	Expired	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/18/1990	07/600,201	4/27/1993	5,206,817	US
NMXS-0016.00/US	Utility - ORG	Expired	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	9/29/1989	07/414,775	7/9/1991	5,031,152	US
NMXS-0017.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/17/1990	07/569,009	12/10/1991	5,072,137	US
NMXS-0018.00/US	Utility - ORG	Expired	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	2/26/1991	07/661,555	10/1/1991	5,053,996	US
NMXS-0019.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	7/13/1990	07/552,567	11/23/1993	5,265,100	US
NMXS-0019.01/US	Utility - DIV	Expired	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	6/2/1993	08/071,448	5/10/1994	5,311,473	US
NMXS-0020.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/17/1990	07/568,968	11/3/1992	5,161,159	US

Exhibit A - US Issued Patents

MTI Docket No	Matter Type	Matter Status	Title	FileDate	Serial No.	Issue Date	Patent No.	Country
NMXS-0021.01/US	Utility - CON	Issued	SEMICONDUCTOR MEMORY WITH INHIBITED TEST MODE ENTRY DURING POWER-UP	11/20/1992	07/984,233	4/18/1995	5,408,435	US
NMXS-0021.02/US	Utility - CON	Issued	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	4/18/1995	08/424,722	1/6/1998	5,706,232	US
NMXS-0022.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/26/1990	07/588,601	6/2/1992	5,119,340	US
NMXS-0023.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/26/1990	07/588,577	7/7/1992	5,128,897	US
NMXS-0024.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/17/1990	07/570,203	12/10/1991	5,072,138	US
NMXS-0025.00/US	Utility - ORG	Expired	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/22/1990	07/601,288	3/24/1992	5,099,148	US
NMXS-0026.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/26/1990	07/588,609	6/9/1992	5,121,358	US
NMXS-0026.02/US	Utility - CON	Issued	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	1/19/1995	08/376,127	6/11/1996	5,526,318	US
NMXS-0027.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/26/1990	07/588,600	6/23/1992	5,124,951	US
NMXS-0028.00/US	Utility - ORG	Expired	ADDRESS BUFFER CIRCUIT WITH TRANSITION-BASED LATCHING	10/22/1990	07/601,287	6/23/1992	5,124,584	US
NMXS-0029.00/US	Utility - ORG	Expired	VEHICLE SEAT ASSEMBLY WITH INTEGRATED CHILD SEAT	12/14/1990	07/827,403	11/23/1993	5,265,054	US
NMXS-0030.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH COLUMN DECODED BIT LINE EQUILIBRATE	12/13/1990	07/627,050	3/22/1994	5,297,090	US
NMXS-0031.00/US	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/14/1990	07/627,236	11/2/1993	5,258,952	US
NMXS-0032.01/US	Utility - CON	Expired	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	8/2/1993	08/101,347	10/11/1994	5,355,340	US
NMXS-0033.00/US	Utility - ORG	Expired	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	7/17/1991	07/731,803	5/10/1994	5,311,477	US
NMXS-0034.00/US	Utility - ORG	Expired	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	5/1/1991	07/694,451	6/7/1994	5,319,768	US
NMXS-0035.00/US	Utility - ORG	Expired	CONTROL CIRCUIT FOR DUAL PORT MEMORY	4/30/1991	07/693,670	6/27/1995	5,428,632	US
NMXS-0036.00/US	Utility - ORG	Expired	CACHE TAG PARITY DETECT CIRCUIT	3/29/1991	07/677,313	8/16/1994	5,339,322	US
NMXS-0037.00/US	Utility - ORG	Expired	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	7/17/1991	07/731,487	3/22/1994	5,297,094	US
NMXS-0038.00/US	Utility - ORG	Expired	INTEGRATED CIRCUIT DUAL-PART MEMORY DEVICE HAVING REDUCED CAPACITANCE	7/17/1991	07/731,802	2/15/1994	5,287,322	US
NMXS-0039.01/US	Utility - CON	Expired	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	8/20/1993	08/109,697	6/14/1994	5,321,314	US
NMXS-0040.00/US	Utility - ORG	Issued	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	11/30/1992	07/982,988	12/27/1994	5,377,153	US
NMXS-0040.02/US	Utility - DIV	Issued	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	5/22/1996	08/651,233	3/31/1998	5,734,602	US
NMXS-0040.03/US	Utility - CON	Issued	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	8/26/1996	08/697,482	4/22/1997	5,623,438	US
NMXS-0041.00/US	Utility - ORG	Expired	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	12/17/1991	07/809,393	2/8/1994	5,285,419	US
NMXS-0042.01/US	Utility - CON	Issued	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/31/1996	08/777,836	5/5/1998	5,748,556	US
NMXS-0043.00/US	Utility - ORG	Issued	MULTIPLEXING SENSE AMPLIFIER HAVING LEVEL SHIFTER CIRCUITS	3/31/1993	08/040,916	12/27/1994	5,377,143	US
NMXS-0043.01/US	Utility - DIV	Issued	MULTIPLEXING SENSE AMPLIFIER	9/16/1994	08/307,332	1/9/1996	5,483,489	US
NMXS-0044.00/US	Utility - ORG	Issued	MULTIPLEXING SENSE AMPLIFIER	3/31/1993	08/041,321	1/23/1996	5,487,048	US
NMXS-0045.00/US	Utility - ORG	Expired	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	12/17/1991	07/809,735	3/15/1994	5,295,104	US
NMXS-0046.00/US	Utility - ORG	Issued	REDUNDANCY DECODER	1/31/1992	07/830,315	11/28/1995	5,471,426	US
NMXS-0047.00/US	Utility - ORG	Expired	COLUMN REDUNDANCY ARCHITECTURE FOR A READ/WRITE MEMORY	1/31/1992	07/830,314	10/26/1993	5,257,229	US
NMXS-0048.00/US	Utility - ORG	Issued	SELECTIVE BULK WRITE OPERATION	4/7/1992	07/864,481	5/10/1994	5,311,467	US
NMXS-0049.00/US	Utility - ORG	Issued	PARALLELIZED MAGNITUDE COMPARATOR	4/30/1992	07/876,959	10/18/1994	5,357,235	US
NMXS-0050.00/US	Utility - ORG	Issued	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE	4/30/1992	07/876,851	6/7/1994	5,319,347	US
NMXS-0051.01/US	Utility - CON	Issued	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	9/16/1993	08/122,804	1/31/1995	5,386,377	US
NMXS-0052.00/US	Utility - ORG	Issued	PARALLELIZED DIFFERENCE FLAG LOGIC	5/29/1992	07/890,919	10/18/1994	5,357,236	US

PATENT
REEL: 030872 FRAME: 0084

Exhibit A - US Issued Patents

MtrlDocketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0053.00/US	Utility - ORG	Issued	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/22/1992	07/901,667	10/11/1994	5,355,113	US
NMXS-0054.00/US	Utility - ORG	Issued	PROGRAMMABLE DIFFERENCE FLAG LOGIC	7/31/1992	07/923,855	1/10/1995	5,381,126	US
NMXS-0054.01/US	Utility - CON	Issued	FIFO WITH ADAPTABLE FLAGS FOR CHANGING SYSTEM SPEED REQUIREMENTS	9/8/1994	08/303,172	4/16/1996	5,508,679	US
NMXS-0055.00/US	Utility - ORG	Expired	INTEGRATED CIRCUIT WITH SELF-BIASED DIFFERENTIAL DATA LINES	12/17/1991	07/809,733	10/26/1993	5,257,226	US
NMXS-0056.00/US	Utility - ORG	Issued	PROCESS FOR REALIZING P-CHANNEL MOS TRANSISTORS HAVING A LOW THRESHOLD VOLTAGE IN SEMICONDUCTOR INTEGRATED CIRCUITS FOR ANALOG APPLICATIONS	7/28/1994	08/282,408	7/9/1996	5,534,448	US
NMXS-0056.01/US	Utility - DIV	Issued	PROCESS FOR REALIZING P-CHANNEL MOS TRANSISTORS HAVING A LOW THRESHOLD VOLTAGE IN SEMICONDUCTOR INTEGRATED CIRCUITS FOR ANALOG APPLICATIONS	6/7/1995	08/486,747	12/31/1996	5,589,701	US
NMXS-0057.02/US	Utility - CON	Issued	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	6/7/1995	08/477,283	11/3/1998	5,831,457	US
NMXS-0058.00/US	Utility - ORG	Issued	STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE	11/13/1992	07/975,628	10/11/1994	5,355,344	US
NMXS-0058.01/US	Utility - CON	Issued	STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE	6/21/1994	08/263,048	6/11/1996	5,526,317	US
NMXS-0059.01/US	Utility - CON	Issued	INTEGRATED CIRCUIT OUTPUT DRIVER	12/30/1994	08/367,681	7/17/2001	6,262,617	US
NMXS-0060.00/US	Utility - ORG	Issued	OUTPUT DRIVER CIRCUIT WITH BODY BIAS CONTROL FOR MULTIPLE POWER SUPPLY OPERATION	1/3/1994	08/176,960	6/6/1995	5,422,591	US
NMXS-0061.01/US	Utility - CON	Issued	MULTIPLE CLOCKED DYNAMIC SENSE AMPLIFIER	9/15/1994	08/306,527	1/16/1996	5,485,430	US
NMXS-0062.00/US	Utility - ORG	Issued	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/22/1992	07/995,581	10/3/1995	5,455,802	US
NMXS-0063.01/US	Utility - CON	Issued	LEADFRAME FOR INTEGRATED CIRCUITS	1/13/1994	08/180,692	2/14/1995	5,389,577	US
NMXS-0064.00/US	Utility - CIP	Issued	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/19/1993	08/020,045	5/21/1995	5,400,007	US
NMXS-0065.00/US	Utility - ORG	Issued	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/30/1992	07/954,276	6/13/1995	5,424,988	US
NMXS-0065.01/US	Utility - CON	Issued	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	6/2/1995	08/460,409	7/1/1997	5,644,542	US
NMXS-0066.00/US	Utility - ORG	Issued	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/31/1992	07/938,399	4/5/1994	5,300,828	US
NMXS-0067.00/US	Utility - ORG	Issued	TEMPERATURE-COMPENSATED VOLTAGE LEVEL SENSE CIRCUIT	4/29/1993	08/055,080	11/15/1994	5,365,129	US
NMXS-0068.00/US	Utility - ORG	Issued	ADDRESS BUFFER	4/30/1993	08/056,078	8/16/1994	5,339,277	US
NMXS-0069.00/US	Utility - ORG	Issued	METHOD FOR STRESS TESTING DECODERS AND PERIPHERY CIRCUITS	4/30/1993	08/056,376	8/23/1994	5,341,336	US
NMXS-0070.00/US	Utility - ORG	Issued	INPUT BUFFER WITH HYSTERESIS CHARACTERISTICS	12/21/1992	07/995,666	9/20/1994	5,349,246	US
NMXS-0071.00/US	Utility - ORG	Issued	OUTPUT DRIVER CIRCUIT	7/31/1992	07/923,135	7/19/1994	5,331,228	US
NMXS-0072.00/US	Utility - ORG	Issued	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	7/30/1993	08/099,606	4/4/1995	5,404,331	US
NMXS-0073.00/US	Utility - ORG	Issued	TEMPERATURE-STABLE CURRENT SOURCE	5/31/1995	08/454,926	7/1/1997	5,644,216	US
NMXS-0074.01/US	Utility - DIV	Issued	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	6/6/1995	08/473,552	5/6/1997	5,627,403	US
NMXS-0074.02/US	Utility - CON	Issued	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	11/18/1996	08/751,244	8/18/1998	5,795,821	US
NMXS-0075.00/US	Utility - ORG	Issued	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/26/1994	08/311,941	8/13/1996	5,546,044	US
NMXS-0076.00/US	Utility - ORG	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	9/7/1994	08/301,792	1/23/1996	5,486,486	US
NMXS-0076.01/US	Utility - DIV	Issued	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	6/7/1995	08/477,302	2/4/1997	5,600,590	US
NMXS-0077.00/US	Utility - ORG	Issued	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/30/1994	08/347,653	7/9/1996	5,535,157	US
NMXS-0078.00/US	Utility - ORG	Issued	CIRCUIT FOR COVERING INITIAL CONDITIONS WHEN STARTING-UP AN INTEGRATED CIRCUIT DEVICE	1/30/1995	08/380,309	3/18/1997	5,612,641	US
NMXS-0079.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/23/1994	08/344,232	6/18/1996	5,528,536	US
NMXS-0079.01/US	Utility - DIV	Issued	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	4/26/1996	08/639,931	8/19/1997	5,659,501	US

PATENT
REEL: 030872 FRAME: 0085

Exhibit A - US Issued Patents

MTI DocNo	MatterTyp	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0079.02/US	Utility - CON	Issued	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	6/9/1997	08/871,226	10/6/1998	5,818,760	US
NMXS-0080.00/US	Utility - ORG	Issued	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/6/1994	08/349,783	10/15/1996	5,566,114	US
NMXS-0081.01/US	Utility - CON	Issued	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	4/18/1996	08/635,455	7/1/1997	5,644,529	US
NMXS-0082.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/16/1995	08/391,999	8/19/1997	5,659,509	US
NMXS-0083.00/US	Utility - ORG	Issued	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/7/1994	08/350,961	2/20/1996	5,493,531	US
NMXS-0083.01/US	Utility - CIP	Issued	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	2/16/1996	08/602,237	1/13/1998	5,708,601	US
NMXS-0084.00/US	Utility - ORG	Issued	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/29/1995	08/412,550	9/24/1996	5,559,743	US
NMXS-0085.00/US	Utility - ORG	Issued	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/20/1995	08/377,524	8/13/1996	5,546,054	US
NMXS-0086.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE-MEMORY OUTPUT DATA	2/21/1995	08/391,160	5/7/1996	5,515,332	US
NMXS-0087.00/US	Utility - ORG	Issued	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/21/1995	08/391,159	9/2/1997	5,663,921	US
NMXS-0088.01/US	Utility - CON	Issued	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/25/1997	08/803,915	2/10/1998	5,717,642	US
NMXS-0089.01/US	Utility - CON	Issued	COUNT UNIT FOR NONVOLATILE MEMORIES	8/20/1996	08/700,126	11/11/1997	5,687,135	US
NMXS-0090.00/US	Utility - ORG	Issued	END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES	12/28/1994	08/365,510	1/14/1997	5,594,703	US
NMXS-0091.01/US	Utility - CON	Issued	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	5/14/1997	08/855,922	6/16/1998	5,768,115	US
NMXS-0092.00/US	Utility - ORG	Issued	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1994	08/348,461	3/12/1996	5,499,217	US
NMXS-0093.00/US	Utility - ORG	Issued	READING CIRCUIT FORAN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1995	08/408,589	5/6/1997	5,627,790	US
NMXS-0094.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/28/1994	08/345,530	2/10/1998	5,717,698	US
NMXS-0095.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/31/1995	08/381,530	2/4/1997	5,600,600	US
NMXS-0096.00/US	Utility - ORG	Issued	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/31/1995	08/412,326	2/4/1997	5,600,594	US
NMXS-0097.00/US	Utility - ORG	Issued	CIRCUIT FOR IDENTIFYING A MEMORY CELL HAVING ERRONEOUS DATA STORED THEREIN	8/30/1995	08/521,304	11/11/1997	5,687,124	US
NMXS-0098.00/US	Utility - ORG	Issued	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	12/29/1994	08/366,211	12/10/1996	5,583,820	US
NMXS-0098.01/US	Utility - DIV	Issued	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	9/9/1996	08/711,132	5/5/1998	5,748,548	US
NMXS-0099.00/US	Utility - ORG	Issued	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1994	08/347,788	5/21/2002	6,392,469	US
NMXS-0100.00/US	Utility - ORG	Issued	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1995	08/395,361	4/1/1997	5,617,356	US
NMXS-0101.00/US	Utility - ORG	Issued	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/29/1994	08/366,212	12/17/1996	5,586,077	US
NMXS-0102.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	12/29/1994	08/366,259	5/21/1996	5,519,656	US
NMXS-0103.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	1/3/1995	08/368,211	8/19/1997	5,659,516	US
NMXS-0103.01/US	Utility - DIV	Issued	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	4/1/1997	08/831,046	5/18/1999	5,905,677	US
NMXS-0104.00/US	Utility - ORG	Issued	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/28/1994	08/365,154	8/20/1996	5,548,554	US
NMXS-0105.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/21/1995	08/391,147	7/30/1996	5,541,884	US
NMXS-0106.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/21/1995	08/391,920	7/2/1996	5,532,972	US

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MII-Docno	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0107.00/US	Utility - ORG	Issued	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH	4/17/1995	08/422,813	10/8/1996	5,563,826	US
NMXS-0108.00/US	Utility - ORG	Issued	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME	3/28/1995	08/412,162	6/10/1997	5,638,327	US
NMXS-0109.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY	2/16/1995	08/389,599	2/11/1997	5,602,786	US
NMXS-0110.00/US	Utility - ORG	Issued	REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS	3/28/1995	08/411,904	7/30/1996	5,541,880	US
NMXS-0111.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	1/8/1995	08/367,538	11/19/1996	5,576,990	US
NMXS-0112.00/RE	Utility - REIS	Issued	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	7/12/2000	09/616,821	7/14/1998	RE39,918	US
NMXS-0112.02/US	Utility - CON	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	9/18/1997	08/932,930	7/14/1998	5,781,043	US
NMXS-0113.00/US	Utility - ORG	Issued	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/22/1993	08/051,184	11/28/1995	5,471,431	US
NMXS-0114.00/RE	Utility - REIS	Issued	STRUCTURE FOR DESELECTIVE BROKEN SELECT LINES IN MEMORY ARRAYS	11/7/1997	08/966,042	11/7/1995	RE36,319	US
NMXS-0114.00/US	Utility - ORG	Abandoned	STRUCTURE FOR DESELECTIVE BROKEN SELECT LINES IN MEMORY ARRAYS	5/28/1993	08/069,025	11/7/1995	5,465,233	US
NMXS-0115.00/US	Utility - ORG	Issued	LATCH CONTROLLED OUTPUT DRIVER	6/30/1993	08/085,760	9/20/1994	5,349,243	US
NMXS-0116.00/US	Utility - ORG	Issued	FUSE CURCUITRY TO CONTROL THE PROPAGATION DELAY OF AN IC	6/30/1993	08/085,580	6/27/1995	5,428,311	US
NMXS-0117.01/US	Utility - CON	Issued	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	3/27/1995	08/410,383	8/13/1996	5,546,537	US
NMXS-0118.01/US	Utility - CON	Issued	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	3/30/1995	08/413,789	5/6/1997	5,627,793	US
NMXS-0119.00/US	Utility - ORG	Issued	CLOCK GENERATOR CIRCUIT WITH LOW CURRENT FREQUENCY DIVIDER	1/27/1994	08/188,153	11/21/1995	5,469,116	US
NMXS-0120.00/US	Utility - CIP	Issued	DISABLING SENSE AMPLIFIER	7/30/1993	08/099,947	12/27/1994	5,377,150	US
NMXS-0120.01/US	Utility - DIV	Issued	DISABLING SENSE AMPLIFIER	8/31/1994	08/298,766	12/5/1995	5,473,567	US
NMXS-0121.00/US	Utility - ORG	Issued	PRECHARGE DEVICE FOR AN INTEGRATED CIRCUIT INTERNAL BUS	8/31/1993	08/114,749	3/28/1995	5,402,379	US
NMXS-0122.00/US	Utility - ORG	Issued	APPARATUS FOR TESTING SIGNAL TIMING AND PROGRAMMING DELAY	1/31/1994	08/189,589	11/26/1996	5,579,326	US
NMXS-0122.01/US	Utility - DIV	Lapsed	APPARATUS FOR TESTING SIGNAL TIMING AND PROGRAMMING DELAY	5/9/1996	08/647,222	11/24/1998	5,841,789	US
NMXS-0123.00/US	Utility - ORG	Issued	DISTRIBUTED NOR TAG MATCH APPARATUS	8/31/1993	08/114,747	11/5/1996	5,572,456	US
NMXS-0124.02/US	Utility - CON	Issued	VARIABLE IMPEDANCE DELAY ELEMENTS	2/18/1997	08/801,452	1/11/2000	6,014,050	US
NMXS-0124.03/US	Utility - DIV	Issued	VARIABLE IMPEDANCE DELAY ELEMENTS	8/25/1998	09/139,225	6/28/2001	6,252,447	US
NMXS-0125.00/US	Utility - ORG	Issued	TESTING CIRCUITRY OF INTERNAL PERIPHERAL BLOCKS IN A SEMICONDUCTOR MEMORY DEVICE AND METHOD OF TESTING THE SAME	1/27/1994	08/188,158	8/8/1995	5,440,516	US
NMXS-0126.00/US	Utility - ORG	Issued	STRESS TEST MODE	12/22/1993	08/172,854	11/10/1998	5,835,427	US
NMXS-0127.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR ACQUIRING REDUNDANCY INFORMATION FROM A PACKAGED MEMORY CHIP	12/22/1993	08/172,848	8/8/2000	6,101,618	US
NMXS-0128.01/US	Utility - CON	Issued	REDUNDANT LINE DECODER MASTER ENABLE	6/19/1995	08/492,219	10/22/1996	5,568,061	US
NMXS-0129.01/US	Utility - CON	Issued	STRUCTURE TO UTILIZE A PARTIALLY FUNCTIONAL CACHE MEMORY BY INVALIDATION OF FAULTY CACHE MEMORY LOCATIONS	9/20/1996	08/717,139	1/13/1998	5,708,789	US
NMXS-0130.00/US	Utility - ORG	Issued	LATCH CONTROLLED OUTPUT DRIVER	9/30/1993	08/129,257	3/7/1995	5,396,108	US
NMXS-0131.00/US	Utility - ORG	Issued	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/30/1993	08/129,763	5/23/1995	5,418,756	US
NMXS-0132.00/US	Utility - ORG	Issued	DATA COMPARING SENSE AMPLIFIER	12/22/1993	08/172,853	10/22/1996	5,568,073	US
NMXS-0133.00/US	Utility - ORG	Issued	STATIC TEST MODE NOISE FILTER	11/30/1993	08/160,608	8/8/1995	5,440,178	US
NMXS-0134.00/US	Utility - ORG	Issued	FUSE CIRCUIT WITH FEEDBACK DISCONNECT	12/28/1993	08/174,139	2/13/1996	5,491,444	US
NMXS-0135.00/US	Utility - ORG	Issued	STATIC MEMORY LONG WRITE TEST	12/22/1993	08/173,197	11/19/1996	5,577,051	US
NMXS-0136.00/US	Utility - CIP	Issued	COMPENSATING DELAY ELEMENT FOR CLOCK GENERATION IN A MEMORY DEVICE	12/20/1993	08/170,612	6/13/1995	5,424,985	US
NMXS-0137.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY WITH EDGE TRANSITION DETECTION PULSE DISABLE	2/28/1994	08/202,830	2/20/1996	5,493,537	US
NMXS-0138.00/US	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/17/1994	08/340,940	4/21/1998	5,742,548	US

PATENT
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MFI DcktNo	MatterTyp	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0139.00/US	Utility - ORG	Issued	RESISTOR-CAPACITOR-TRANSISTOR TYPE INTEGRATED CIRCUIT, METHOD FOR THE MANUFACTURE OF SUCH A CIRCUIT AND APPLICATION TO AN OSCILLATOR	5/19/1994	08/246,070	7/4/1995	5,430,319	US
NMXS-0139.01/US	Utility - CON	Issued	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	3/8/1995	08/399,900	8/26/1997	5,661,324	US
NMXS-0140.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/27/1994	08/329,975	1/14/1997	5,594,793	US
NMXS-0141.00/US	Utility - ORG	Issued	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/21/1994	08/361,313	9/10/1996	5,555,216	US
NMXS-0142.00/US	Utility - ORG	Issued	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/21/1994	08/361,996	7/16/1996	5,537,349	US
NMXS-0143.00/US	Utility - ORG	Issued	METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES	1/27/1995	08/379,337	3/23/1999	5,886,386	US
NMXS-0143.01/US	Utility - DIV	Issued	METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES	12/24/1998	09/220,635	7/24/2001	6,265,277	US
NMXS-0144.02/US	Utility - CON	Issued	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	12/16/1996	08/767,521	5/4/1999	5,900,756	US
NMXS-0145.00/US	Utility - ORG	Issued	MEMORY REDUNDANCY CIRCUIT	2/27/1995	08/393,464	11/26/1996	5,579,265	US
NMXS-0146.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/10/1995	08/402,519	3/11/1997	5,610,860	US
NMXS-0146.01/US	Utility - DIV	Issued	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/4/1997	08/811,358	3/17/1998	5,729,162	US
NMXS-0147.00/US	Utility - ORG	Issued	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/30/1995	08/380,737	2/25/1997	5,606,523	US
NMXS-0148.00/US	Utility - ORG	Issued	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/30/1995	08/380,738	1/7/1997	5,592,417	US
NMXS-0148.01/US	Utility - DIV	Issued	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	11/21/1996	08/752,814	10/14/1997	5,677,870	US
NMXS-0148.02/US	Utility - DIV	Issued	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	11/21/1996	08/754,432	2/24/1998	5,721,706	US
NMXS-0149.00/US	Utility - ORG	Issued	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/31/1995	08/381,529	10/1/1996	5,561,621	US
NMXS-0150.00/US	Utility - ORG	Issued	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/19/1995	08/423,398	3/18/1997	5,612,611	US
NMXS-0151.00/US	Utility - ORG	Issued	VOLTAGE BOOSTER CIRCUIT	4/19/1995	08/423,396	6/3/1997	5,636,115	US
NMXS-0152.00/US	Utility - ORG	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/12/1995	08/421,671	4/8/1997	5,619,451	US
NMXS-0153.00/US	Utility - ORG	Issued	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/22/1995	08/394,314	8/18/1998	5,796,658	US
NMXS-0154.00/US	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/7/1995	08/418,636	7/1/1997	5,644,530	US
NMXS-0155.00/US	Utility - ORG	Issued	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	6/7/1995	08/484,873	7/22/1997	5,651,128	US
NMXS-0156.00/US	Utility - ORG	Issued	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/21/1995	08/408,016	1/14/1997	5,594,693	US
NMXS-0157.00/US	Utility - ORG	Issued	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/7/1995	08/479,081	12/31/1996	5,590,075	US
NMXS-0158.01/US	Utility - CON	Issued	PROGRAMMABLE MEMORY ELEMENT	2/4/1997	08/794,965	12/9/1997	5,696,716	US
NMXS-0159.00/US	Utility - ORG	Issued	SENSE AMPLIFIER WITH HYSTERESIS	5/2/1995	08/432,838	2/3/1998	5,715,204	US
NMXS-0160.01/US	Utility - DIV	Issued	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	6/6/1995	08/468,282	1/28/1997	5,598,028	US
NMXS-0161.00/US	Utility - ORG	Issued	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/22/1995	08/577,125	11/28/2000	6,153,537	US
NMXS-0161.01/US	Utility - DIV	Issued	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/14/1998	09/213,065	3/11/2003	6,531,714	US
NMXS-0162.00/US	Utility - ORG	Issued	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	5/31/1995	08/454,650	10/28/1997	5,682,349	US

Exhibit A - US Issued Patents

Mfr. Docket #	Matter Type	Matter Status	Title	File Date	Serial No.	Issue Date	Patent No.	Country
NMXS-0163.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY CELL AND A METHOD FOR FORMING THE SAME	7/18/1995	08/503,303	1/27/1998	5,712,814	US
NMXS-0163.01/US	Utility - DIV	Issued	METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL	9/11/1996	08/712,373	7/6/1999	5,920,776	US
NMXS-0164.00/US	Utility - ORG	Issued	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	10/2/1995	08/538,161	6/2/1998	5,761,222	US
NMXS-0165.00/US	Utility - ORG	Issued	SENSE AMPLIFIER HAVING CAPACITIVELY COUPLED INPUT FOR OFFSET COMPENSATION	4/26/1996	08/639,192	3/17/1998	5,729,492	US
NMXS-0165.01/US	Utility - CON	Issued	SENSE AMPLIFIER CIRCUIT FOR SEMICONDUCTOR MEMORY DEVICES	1/26/1998	09/013,141	11/9/1999	5,982,666	US
NMXS-0166.01/US	Utility - CON	Issued	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	9/10/1998	09/150,802	11/7/2000	6,144,588	US
NMXS-0167.00/US	Utility - ORG	Issued	HIGH-VOLTAGE N-CHANNEL MOS TRANSISTOR AND ASSOCIATED MANUFACTURING PROCESS	2/27/1996	08/607,779	12/15/1998	5,850,360	US
NMXS-0168.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS	10/2/1995	08/538,302	7/1/1997	5,644,526	US
NMXS-0169.00/US	Utility - ORG	Issued	READING CIRCUIT FOR MEMORY CELLS	6/6/1995	08/476,547	1/20/1998	5,710,739	US
NMXS-0170.00/US	Utility - ORG	Issued	SYNCHRONIZATION DEVICE FOR OUTPUT STAGES, PARTICULARLY FOR ELECTRONIC MEMORIES	11/17/1995	08/560,324	5/27/1997	5,633,834	US
NMXS-0171.00/US	Utility - ORG	Issued	PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING	4/4/1996	08/628,587	12/15/1998	5,850,361	US
NMXS-0172.00/US	Utility - ORG	Issued	DECODER WITH REDUCED ARCHITECTURE	11/17/1995	08/560,090	4/21/1998	5,742,187	US
NMXS-0173.00/US	Utility - ORG	Issued	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	5/17/1996	08/649,468	8/12/1997	5,657,276	US
NMXS-0174.00/US	Utility - ORG	Issued	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	1/26/1996	08/592,122	3/24/1998	5,731,716	US
NMXS-0176.00/US	Utility - ORG	Issued	EEPROM MEMORY WITH CONTACTLESS MEMORY CELLS	5/3/1996	08/642,825	2/10/1998	5,717,636	US
NMXS-0177.00/US	Utility - ORG	Issued	BYTE ERASABLE EEPROM FULLY COMPATIBLE WITH A SINGLE POWER SUPPLY FLASH-EPROM PROCESS	9/25/1995	08/533,631	3/18/1997	5,612,913	US
NMXS-0178.00/US	Utility - ORG	Issued	POWER-ON RESET CIRCUIT	8/31/1995	08/521,666	12/9/1997	5,696,461	US
NMXS-0179.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	5/3/1996	08/649,857	8/11/1998	5,793,676	US
NMXS-0179.01/US	Utility - CON	Issued	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	6/15/1998	09/094,916	9/7/1999	5,949,713	US
NMXS-0180.00/US	Utility - ORG	Issued	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	6/20/1996	08/667,097	12/21/1999	6,004,847	US
NMXS-0180.01/US	Utility - CON	Issued	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	4/27/1999	09/300,029	6/19/2001	6,248,630	US
NMXS-0181.00/US	Utility - ORG	Issued	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC	6/20/1996	08/670,179	1/5/1999	5,856,221	US
NMXS-0182.00/US	Utility - ORG	Issued	METHOD OF MANUFACTURING A MOS INTEGRATED CIRCUIT HAVING COMPONENTS WITH DIFFERENT DIELECTRICS	5/10/1996	08/644,892	9/5/2000	6,114,203	US
NMXS-0183.00/US	Utility - ORG	Issued	METHOD FOR IMPROVING THE PROFILE OF THE INTERMEDIATE DIELECTRIC, PARTICULARLY FOR NON VOLATILE MEMORIES	2/19/1997	08/802,619	4/13/1999	5,894,065	US
NMXS-0183.01/US	Utility - DIV	Issued	METHOD FOR IMPROVING THE INTERMEDIATE DIELECTRIC PROFILE, PARTICULARLY FOR NON-VOLATILE MEMORIES	7/22/1997	08/898,155	8/15/2000	6,104,058	US
NMXS-0184.00/US	Utility - ORG	Issued	CHARGE PUMP VOLTAGE MULTIPLIER CIRCUIT	12/5/1995	08/567,328	9/22/1998	5,812,017	US
NMXS-0185.00/US	Utility - ORG	Issued	VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS	4/12/1996	08/631,574	6/22/1999	5,914,867	US
NMXS-0186.00/US	Utility - ORG	Issued	CURRENT DETECTING CIRCUIT	8/2/1996	08/691,796	6/9/1998	5,764,570	US
NMXS-0187.00/US	Utility - ORG	Issued	HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES	9/30/1996	08/724,495	11/24/1998	5,841,728	US

PATENT
REEL: 030872 FRAME: 0089

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MTI Docket	Master Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0188.04/US	Utility - CON	Issued	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	5/16/1997	08/940,045	5/18/1999	5,905,683	US
NMXS-0189.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	3/31/1994	08/220,976	5/14/1996	5,517,455	US
NMXS-0190.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	3/31/1994	08/220,834	11/28/1995	5,471,157	US
NMXS-0191.00/US	Utility - ORG	Issued	STRUCTURE CAPABLE OF SIMULTANEOUSLY TESTING REDUNDANT AND NON-REDUNDANT MEMORY ELEMENTS DURING STRESS TESTING OF AN INTEGRATED CIRCUIT MEMORY DEVICE	4/29/1994	08/235,161	6/25/1996	5,530,674	US
NMXS-0192.00/US	Utility - ORG	Issued	LONG WRITE TEST	6/29/1994	08/267,667	12/10/1996	5,583,816	US
NMXS-0193.00/US	Utility - ORG	Issued	CIRCUIT WHICH PROVIDES POWER ON RESET DISABLE DURING A TEST MODE	6/29/1994	08/267,666	10/3/1995	5,455,799	US
NMXS-0194.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	5/31/1994	08/251,718	5/28/1996	5,521,880	US
NMXS-0195.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT MEMORY WITH DISABLED EDGE TRANSITION PULSE GENERATION DURING SPECIAL TEST MODE	5/31/1994	08/251,337	7/20/1996	5,493,537	US
NMXS-0196.00/US	Utility - ORG	Issued	VARIABLE INPUT THRESHOLD ADJUSTMENT	7/29/1994	08/282,177	12/31/1996	5,589,783	US
NMXS-0197.00/US	Utility - ORG	Issued	TEST MODE CONTROL CIRCUIT OF AN INTEGRATED CIRCUIT DEVICE	7/29/1994	08/282,047	11/9/1999	5,982,188	US
NMXS-0198.00/US	Utility - ORG	Issued	APPARATUS AND METHOD FOR ENABLING A BUS DRIVER WHEN A DATA SIGNAL IS VALID	8/10/1994	08/288,334	10/15/1996	5,566,112	US
NMXS-0198.01/US	Utility - DIV	Issued	APPARATUS AND METHOD FOR ENABLING A BUS DRIVER WHEN A DATA SIGNAL IS VALID	5/10/1995	08/438,276	10/29/1996	5,570,316	US
NMXS-0199.00/US	Utility - ORG	Issued	PRE-CHARGED EXCLUSIONARY WIRED-CONNECTED PROGRAMMED REDUNDANT SELECT	9/30/1994	08/316,087	2/27/1996	5,495,446	US
NMXS-0200.00/US	Utility - ORG	Issued	FUEL MEMORY CHIP LONG WRITE TEST MODE	9/30/1994	08/315,337	3/26/1996	5,502,678	US
NMXS-0201.00/US	Utility - ORG	Issued	LOW CURRENT DIFFERENTIAL LEVEL SHIFTER	10/31/1994	08/331,892	5/14/1996	5,517,148	US
NMXS-0202.00/US	Utility - ORG	Issued	CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES	10/31/1994	08/331,699	3/11/1997	5,610,866	US
NMXS-0203.00/US	Utility - ORG	Issued	APPARATUS AND METHOD FOR MAPPING A REDUNDANT MEMORY COLUMN TO A DEFECTIVE MEMORY COLUMN	5/10/1995	08/438,903	11/12/1996	5,574,688	US
NMXS-0204.00/US	Utility - ORG	Issued	POST-FABRICATION SELECTABLE REGISTERED AND NON-REGISTERED MEMORY	12/22/1994	08/362,187	11/26/1996	5,579,263	US
NMXS-0205.00/US	Utility - ORG	Issued	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	12/16/1994	08/357,664	10/22/1996	5,568,084	US
NMXS-0205.01/US	Utility - CON	Issued	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	4/12/1996	08/631,063	8/5/1997	5,654,663	US
NMXS-0206.00/US	Utility - ORG	Issued	OUTPUT DRIVER CIRCUITRY WITH LIMITED OUTPUT HIGH VOLTAGE	12/20/1994	08/360,228	1/21/1997	5,596,297	US
NMXS-0207.00/US	Utility - ORG	Issued	VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE	12/20/1994	08/360,229	8/20/1996	5,548,241	US
NMXS-0208.00/US	Utility - ORG	Issued	OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE	12/20/1994	08/359,397	1/14/1997	5,594,373	US
NMXS-0209.00/US	Utility - ORG	Issued	ADJUSTABLE CURRENT SOURCE	12/20/1994	08/359,927	12/3/1996	5,581,209	US
NMXS-0210.00/US	Utility - ORG	Issued	VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT	12/20/1994	08/359,926	1/28/1997	5,598,122	US
NMXS-0211.00/US	Utility - ORG	Issued	DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT	12/20/1994	08/360,227	12/31/1996	5,589,794	US
NMXS-0212.01/US	Utility - CON	Issued	CLOCK PULSE EXTENDER MODE FOR CLOCKED MEMORY DEVICES HAVING PRECHARGED DATA PATHS	4/30/1997	08/848,342	6/29/1999	5,917,353	US
NMXS-0213.00/US	Utility - ORG	Issued	APPARATUS AND METHOD FOR MAPPING A REDUNDANT MEMORY COLUMN TO A DEFECTIVE MEMORY COLUMN	5/10/1995	08/438,349	11/5/1996	5,572,470	US
NMXS-0214.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR TESTING AN INTEGRATED CIRCUIT DEVICE	8/25/1995	08/519,192	4/18/2000	6,052,806	US
NMXS-0215.00/US	Utility - ORG	Issued	RESIDUAL CHARGE ELIMINATION FOR A MEMORY DEVICE	12/29/1995	08/580,549	3/31/1998	5,734,608	US
NMXS-0216.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/21/1995	08/575,953	10/7/1997	5,675,539	US
NMXS-0217.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/11/1995	08/526,500	4/21/1998	5,742,546	US
NMXS-0218.00/US	Utility - ORG	Issued	CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM	5/17/1996	08/649,282	12/16/1997	5,699,295	US

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MFLDocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0219.00/US	Utility - ORG	Issued	AN ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/18/1995	08/573,897	7/29/1997	5,652,720	US
NMXS-0220.00/US	Utility - ORG	Issued	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/13/1996	08/663,524	11/24/1998	5,841,314	US
NMXS-0221.00/US	Utility - ORG	Issued	RESISTANCE REFERENCE CIRCUIT	12/21/1995	08/576,881	2/10/1998	5,717,323	US
NMXS-0222.00/US	Utility - ORG	Issued	DIGITAL RAMP GENERATOR	5/30/1996	08/652,710	6/30/1998	5,774,390	US
NMXS-0223.00/US	Utility - ORG	Issued	SERIAL DICHOTOMIC METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT IMPLEMENTING SUCH METHOD	1/29/1996	08/593,650	12/23/1997	5,701,265	US
NMXS-0224.01/US	Utility - CON	Issued	READING CIRCUIT FOR MULTILEVEL NON VOLATILE MEMORY CELL DEVICES	6/4/1997	08/869,072	11/17/1998	5,838,612	US
NMXS-0225.00/US	Utility - ORG	Issued	CIRCUIT FOR READING NON-VOLATILE MEMORIES	7/31/1996	08/690,530	3/31/1998	5,734,610	US
NMXS-0226.00/RE	Utility - REIS	Issued	CIRCUIT AND METHOD FOR READING A MEMORY CELL THAT CAN STORE MULTIPLE BITS OF DATA	9/30/1999	09/410,164	9/30/1997	RE38,166	US
NMXS-0226.00/US	Utility - ORG	Abandoned	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT	1/29/1996	08/592,939	9/30/1997	5,673,221	US
NMXS-0227.00/US	Utility - ORG	Issued	READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE	4/25/1996	08/638,976	12/2/1997	5,694,363	US
NMXS-0228.00/US	Utility - ORG	Issued	MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS	7/19/1996	08/684,431	4/7/1998	5,737,268	US
NMXS-0229.00/US	Utility - ORG	Issued	THRESHOLD DETECTING DEVICE	7/31/1996	08/688,956	12/8/1998	5,847,584	US
NMXS-0230.00/US	Utility - ORG	Issued	CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES	7/19/1996	08/684,192	6/2/1998	5,760,497	US
NMXS-0231.00/US	Utility - ORG	Issued	FLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE	7/31/1996	08/692,936	1/14/2003	6,507,067	US
NMXS-0232.00/US	Utility - ORG	Issued	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/19/1996	08/665,862	8/19/1997	5,659,502	US
NMXS-0232.01/US	Utility - CON	Issued	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/23/1997	08/881,713	7/6/1999	5,920,505	US
NMXS-0233.00/US	Utility - ORG	Issued	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	9/30/1996	08/722,378	7/14/1998	5,781,474	US
NMXS-0234.00/US	Utility - ORG	Issued	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	7/12/1996	08/679,656	7/21/1998	5,784,314	US
NMXS-0235.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE	9/30/1996	08/720,491	12/1/1998	5,844,404	US
NMXS-0236.00/US	Utility - ORG	Issued	ROW DECODING CIRCUIT FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	3/27/1997	08/824,616	12/8/1998	5,848,013	US
NMXS-0236.01/US	Utility - DIV	Issued	ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	12/2/1998	09/203,937	10/24/2000	6,137,725	US
NMXS-0236.02/US	Utility - DIV	Issued	ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	8/7/2000	09/633,334	11/20/2001	6,320,792	US
NMXS-0237.00/US	Utility - ORG	Issued	DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY	12/30/1996	08/775,111	10/13/1998	5,822,247	US
NMXS-0238.00/US	Utility - ORG	Issued	SYSTEM FOR DETERMINING THE PROGRAMMED/NON PROGRAMMED STATUS OF A MEMORY CELL	3/27/1997	08/827,409	1/26/1999	5,864,513	US
NMXS-0239.00/US	Utility - ORG	Issued	BOOST REGULATOR	1/21/1997	08/787,494	10/13/1998	5,821,806	US
NMXS-0240.00/US	Utility - ORG	Issued	UNBALANCED LATCH AND FUSE CIRCUIT INCLUDING THE SAME	7/19/1996	08/684,406	8/19/1997	5,659,498	US
NMXS-0241.00/US	Utility - ORG	Issued	REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS	3/27/1997	08/835,033	5/19/1998	5,754,483	US
NMXS-0242.00/US	Utility - ORG	Issued	TIMESHARING INTERNAL BUS, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/7/1997	08/813,687	8/20/2002	6,438,069	US
NMXS-0243.00/US	Utility - ORG	Issued	PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE-LEVEL NON VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD	7/31/1996	08/690,059	3/17/1998	5,729,490	US

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MTI Ref No	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0244.01/US	Utility - CON	Issued	SUPPLY VOLTAGES SWITCHES CIRCUIT	7/2/1998	09/109,630	3/21/2000	6,040,734	US
NMXS-0245.00/US	Utility - ORG	Abandoned	METHOD AND PROGRAMMING DEVICE FOR DETECTING AN ERROR IN A MEMORY	12/24/1996	08/774,110	3/3/1998	5,724,290	US
NMXS-0246.00/US	Utility - ORG	Issued	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS	10/23/1996	08/735,709	8/11/1998	5,793,679	US
NMXS-0246.01/US	Utility - DIV	Issued	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS	2/27/1998	09/032,179	12/5/2000	6,157,054	US
NMXS-0247.00/US	Utility - ORG	Issued	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	7/24/1996	08/687,145	2/27/2001	6,195,291	US
NMXS-0247.01/US	Utility - DIV	Issued	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	1/23/2001	09/768,744	11/19/2002	6,483,750	US
NMXS-0248.00/US	Utility - ORG	Issued	NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	10/31/1996	08/751,299	5/19/1998	5,754,476	US
NMXS-0249.00/US	Utility - ORG	Issued	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	11/1/1996	08/742,978	5/18/1999	5,905,387	US
NMXS-0250.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH IMPROVED YIELD AND RELIABILITY	6/28/1996	08/671,848	7/7/1998	5,778,012	US
NMXS-0251.00/US	Utility - ORG	Issued	CIRCUIT FOR THE GENERATION OF A VOLTAGE AS A FUNCTION OF THE CONDUCTIVITY OF AN ELEMENTARY CELL OF A NON-VOLATILE MEMORY	3/27/1997	08/835,031	9/1/1998	5,801,988	US
NMXS-0252.00/US	Utility - ORG	Issued	ZERO CONSUMPTION POWER-ON-RESET	1/30/1997	08/790,832	10/13/1998	5,821,788	US
NMXS-0253.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES	3/27/1997	08/828,039	11/17/1998	5,838,619	US
NMXS-0254.00/US	Utility - ORG	Issued	PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL	12/13/1996	08/807,113	12/14/1999	6,000,980	US
NMXS-0255.00/US	Utility - ORG	Issued	HIGH-VOLTAGE-RESISTANT MOS TRANSISTOR, AND CORRESPONDING MANUFACTURING PROCESS	3/18/1997	08/824,888	11/2/1999	5,977,591	US
NMXS-0256.01/US	Utility - CON	Issued	NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION	4/13/2000	09/548,782	9/10/2002	6,448,138	US
NMXS-0257.00/US	Utility - ORG	Issued	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURING PROCESS	10/30/1996	08/739,997	4/24/2001	6,222,245	US
NMXS-0258.00/US	Utility - ORG	Issued	ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS DEVICE FOR A REDUCED NUMBER OF PROGRAMMING CYCLES	2/27/1997	08/807,574	7/20/1999	5,926,416	US
NMXS-0259.00/US	Utility - ORG	Issued	PROCESS OF FABRICATING TUNNEL-OXIDE NONVOLATILE MEMORY DEVICES	1/31/1997	08/792,893	10/6/1998	5,817,557	US
NMXS-0260.00/US	Utility - ORG	Issued	FABRICATION OF NATURAL TRANSISTORS IN A NONVOLATILE MEMORY PROCESS	1/16/1997	08/784,967	7/13/1999	5,923,975	US
NMXS-0261.00/US	Utility - ORG	Issued	MULTI-LEVEL MEMORY CIRCUITS AND CORRESPONDING READING AND WRITING METHODS	1/30/1997	08/791,348	1/12/1999	5,859,795	US
NMXS-0262.00/US	Utility - NSPCT	Issued	MULTI-LEVEL MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	09/202,557	8/8/2000	6,101,121	US
NMXS-0263.00/US	Utility - ORG	Issued	CLOCK CIRCUIT FOR READING A MUTILEVEL NON VOLATILE MEMORY CELLS DEVICE	6/27/1997	08/883,822	11/16/1999	5,986,921	US
NMXS-0264.00/US	Utility - NSPCT	Issued	MULTI-LEVEL MEMORY CIRCUIT WITH REGULATED WRITING VOLTAGE	10/30/1996	09/202,656	8/1/2000	6,097,628	US
NMXS-0265.00/US	Utility - ORG	Issued	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	3/21/1997	08/821,804	12/29/1998	5,854,764	US
NMXS-0266.00/US	Utility - ORG	Issued	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	5/8/1997	08/853,756	12/7/1999	5,999,450	US
NMXS-0267.00/US	Utility - ORG	Issued	SENSING CIRCUITRY FOR READING AND VERIFYING THE CONTENTS OF ELECTRICALLY PROGRAMMABLE/ERASABLE NON-VOLATILE MEMORY CELLS	4/29/1997	08/845,916	6/29/1999	5,917,753	US
NMXS-0267.01/US	Utility - CON	Issued	SENSING CIRCUITRY FOR READING AND VERIFYING THE CONTENTS OF ELECTRICALLY PROGRAMMABLE/ERASABLE NON-VOLATILE MEMORY CELLS	12/9/1998	09/209,319	4/25/2000	6,055,187	US
NMXS-0268.00/US	Utility - ORG	Issued	ERASING METHOD FOR A NON-VOLATILE MEMORY	12/24/1996	08/774,860	10/6/1998	5,818,763	US
NMXS-0269.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR GENERATING A SYNCHRONIZING ATD SIGNAL	11/26/1997	08/978,665	3/23/1999	5,886,949	US
NMXS-0270.01/US	Utility - DIV	Issued	METHOD OF AVOIDING DISTURBANCE DURING THE STEP OF PROGRAMMING AND ERASING AN ELECTRICALLY PROGRAMMABLE, SEMICONDUCTOR NON-VOLATILE STORAGE DEVICE	9/27/1999	09/407,135	2/27/2001	6,195,290	US

Exhibit A - US Issued Patents

MtrJacketNo	MatterType	MatterStatus	Title	FileDate	Ser.No.	IssueDate	PatentNo.	Country
NMXS-0271.00/US	Utility - ORG	Issued	ERASE VOLTAGE CONTROL CIRCUIT FOR AN ELECTRICALLY ERASABLE NON-VOLATILE MEMORY CELL	1/23/1997	08/787,907	2/24/1998	5,721,707	US
NMXS-0272.00/US	Utility - ORG	Issued	METHOD FOR ERASING AN ELECTRICALLY PROGRAMMABLE AND ERASABLE NON-VOLATILE MEMORY CELL	1/24/1997	08/788,530	7/21/1998	5,784,319	US
NMXS-0273.00/US	Utility - ORG	Issued	MONOLITHICALLY INTEGRATED PROGRAMMABLE DEVICE HAVING ELEMENTARY MODULES CONNECTED ELECTRICALLY BY MEANS OF MEMORY CELLS OF THE FLASH TYPE	12/27/1996	08/777,296	12/21/1999	6,005,411	US
NMXS-0274.00/US	Utility - ORG	Issued	PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS	6/5/1997	08/869,208	5/26/1998	5,757,719	US
NMXS-0275.00/US	Utility - ORG	Issued	HIGH VOLTAGES DETECTOR CIRCUIT AND INTEGRATED CIRCUIT USING SAME	1/30/1997	08/791,700	8/18/1998	5,796,275	US
NMXS-0276.00/US	Utility - ORG	Issued	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE	1/27/1998	09/014,437	5/2/2000	6,057,591	US
NMXS-0276.01/US	Utility - DIV	Issued	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES	3/24/2000	09/534,675	4/3/2001	6,210,994	US
NMXS-0277.00/US	Utility - ORG	Issued	MEMORY ARCHITECTURE FOR FLEXIBLE READING MANAGEMENT, PARTICULARLY FOR NON-VOLATILE MEMORIES, HAVING NOISE-IMMUNITY FEATURES, MATCHING DEVICE PERFORMANCE, AND HAVING OPTIMIZED THROUGHOUT	4/24/1997	08/847,385	6/29/1999	5,917,768	US
NMXS-0278.00/US	Utility - ORG	Issued	CIRCUITS AND METHODS FOR READ-ENABLING MEMORY DEVICES SYNCHRONOUSLY WITHTHE REACHING OF THE MINIMUM FUNCTIONALITY CONDITIONS OF THE MEMORY CELLS AND READING CIRCUITS, PARTICULARLY FOR NON-VOLATILE MEMORIES	4/24/1997	08/840,056	3/2/1999	5,878,049	US
NMXS-0279.00/US	Utility - ORG	Issued	COLUMN MULTIPLEXER	5/9/1997	08/853,732	7/7/1998	5,777,941	US
NMXS-0280.00/US	Utility - ORG	Issued	DRIVER DEVICE FOR SELECTION LINES FOR A MULTIPLEXER, TO BE USED IN A WIDE RANGE OF SUPPLY VOLTAGES, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/27/1997	08/826,223	5/12/1998	5,751,654	US
NMXS-0281.00/US	Utility - ORG	Issued	A MEMORY UNDER TEST PROGRAMMING AND READING DEVICE	3/28/1997	08/835,030	11/14/2000	6,148,413	US
NMXS-0282.00/US	Utility - ORG	Issued	DECODING HIERARCHICAL ARCHITECTURE FOR HIGH INTEGRATION MEMORIES	1/30/1997	08/791,746	12/29/1998	5,854,770	US
NMXS-0283.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY DEVICE CAPABLE OF READING DATA WITH AN APPROPRIATE SELF-TIMING AND A REDUCED NUMBER OF REFERENCE LINES	3/27/1997	08/826,489	8/31/1999	5,946,237	US
NMXS-0283.01/US	Utility - DIV	Issued	DATA READING PATH MANAGEMENT ARCHITECTURE FOR A MEMORY DEVICE, PARTICULARLY FOR NON-VOLATILE MEMORIES	7/12/1999	09/351,603	4/3/2001	6,212,096	US
NMXS-0284.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE HAVING OPTIMIZED MANAGEMENT OF DATA TRANSMISSION LINES	3/7/1997	08/812,595	11/3/1998	5,831,891	US
NMXS-0285.00/US	Utility - ORG	Issued	PULSE GENERATION CIRCUIT AND METHOD FOR SYNCHRONIZED DATA LOADING IN AN OUTPUT PRE-BUFFER	3/27/1997	08/826,009	1/12/1999	5,859,810	US
NMXS-0286.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT WITH UNEQUALLY-SIZED, PAIRED MEMORY COUPLED TO ODD NUMBER OF INPUT/OUTPUT PADS	6/7/1995	08/477,244	4/29/1997	5,625,603	US
NMXS-0287.01/US	Utility - CON	Issued	CONSTANT CURRENT SOURCE WITH REDUCED SENSITIVITY TO SUPPLY VOLTAGE AND PROCESS VARIATION	6/24/1996	08/667,481	8/11/1998	5,793,247	US
NMXS-0288.00/US	Utility - ORG	Issued	CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS	6/5/1995	08/464,551	6/17/1997	5,640,122	US
NMXS-0289.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE	3/31/1995	08/414,103	11/19/1996	5,576,656	US
NMXS-0290.00/RE	Utility - REIS	Issued	POWER SUPPLY SWITCH REFERENCE CIRCUITRY	5/5/2000	09/568,201	5/5/1998	RE37,876	US
NMXS-0290.00/US	Utility - ORG	Abandoned	POWER SUPPLY SWITCH REFERENCE CIRCUITRY	6/5/1995	08/464,082	5/5/1998	5,747,890	US
NMXS-0291.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR BIASING BIT LINES	6/7/1995	08/484,491	6/16/1998	5,768,205	US
NMXS-0292.00/US	Utility - ORG	Issued	REDUCED PIN COUNT STRESS TEST CIRCUIT FOR INTEGRATED MEMORY DEVICES AND METHOD THEREFOR	6/7/1995	08/476,658	1/7/1997	5,592,422	US
NMXS-0293.00/US	Utility - ORG	Issued	FAULT DETECTION FOR ENTIRE WAFER STRESS TEST	7/31/1995	08/509,158	4/8/1997	5,619,462	US

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MTI Docket No	Matter Type	Matter Status	Title	File Date	Serial No	Issue Date	Patent No	Country
NMXS-0294.01/US	Utility - CON	Issued	INTEGRATED MEMORY CIRCUIT WITH SEQUENCED BITLINES FOR STRESS TEST	4/7/1997	08/833,582	4/28/1998	5,745,420	US
NMXS-0295.01/US	Utility - CON	Issued	METHOD AND APPARATUS FOR TEST MODE ENTRY DURING POWER UP	9/12/1996	08/712,960	12/30/1997	5,703,512	US
NMXS-0296.00/US	Utility - ORG	Issued	COLUMN REDUNDANCY OF A MULTIPLE BLOCK MEMORY ARCHITECTURE	7/31/1995	08/509,351	3/4/1997	5,608,678	US
NMXS-0297.00/US	Utility - CIP	Issued	STRUCTURE FOR DESELECTING BROKEN SELECT LINES IN MEMORY ARRAYS	7/31/1995	08/509,211	7/15/1997	5,648,933	US
NMXS-0298.00/US	Utility - ORG	Issued	WRITE CONTROLLED ADDRESS BUFFER	8/31/1995	08/521,800	5/13/1997	5,629,896	US
NMXS-0299.00/US	Utility - ORG	Issued	REDUNDANCY ARCHITECTURE	12/29/1995	08/582,424	3/18/1997	5,612,918	US
NMXS-0300.00/US	Utility - ORG	Issued	TEST MODE ACTIVATION AND DATA OVERRIDE	1/19/1996	08/587,709	11/7/2000	6,144,594	US
NMXS-0300.02/US	Utility - CON	Issued	TEST MODE ACTIVATION AND DATA OVERRIDE	12/9/1999	09/457,558	10/2/2001	6,297,996	US
NMXS-0301.00/US	Utility - ORG	Issued	PIPELINED CHIP ENABLE CONTROL CIRCUITRY AND METHODOLOGY	1/19/1996	08/588,730	12/23/1997	5,701,275	US
NMXS-0301.01/US	Utility - DIV	Issued	PIPELINED CHIP ENABLE CONTROL CIRCUITRY AND METHODOLOGY	6/19/1997	08/878,612	8/25/1998	5,798,980	US
NMXS-0302.00/US	Utility - ORG	Issued	OUTPUT DRIVER CIRCUITRY HAVING A SINGLE SLEW RATE RESISTOR	1/19/1996	08/588,988	9/1/1998	5,801,563	US
NMXS-0303.00/US	Utility - ORG	Issued	REDUNDANCY CONTROL	12/29/1995	08/580,827	8/4/1998	5,790,462	US
NMXS-0304.00/US	Utility - ORG	Issued	WRITE PASS THROUGH CIRCUIT	1/19/1996	08/588,662	8/12/1997	5,657,292	US
NMXS-0305.00/US	Utility - ORG	Issued	DATA-INPUT DEVICE FOR GENERATING TEST SIGNALS ON BIT AND BIT-COMPLEMENT LINES	1/19/1996	08/588,762	12/1/1998	5,845,059	US
NMXS-0306.00/US	Utility - ORG	Issued	WRITE DRIVER HAVING A TEST FUNCTION	1/19/1996	08/589,141	1/28/1998	5,715,432	US
NMXS-0307.01/US	Utility - CON	Issued	CIRCUIT AND METHOD FOR TRACKING THE START OF A WRITE TO A MEMORY CELL	5/19/1997	08/858,295	9/15/1998	5,808,960	US
NMXS-0308.01/US	Utility - CON	Issued	CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL	5/19/1997	08/858,788	10/20/1998	5,825,691	US
NMXS-0309.00/US	Utility - ORG	Issued	CLOCKED SENSE AMPLIFIER WITH WORDLINE TRACKING	1/19/1996	08/587,728	9/1/1998	5,802,004	US
NMXS-0309.01/US	Utility - DIV	Issued	CLOCKED SENSE AMPLIFIER WITH WORDLINE TRACKING	10/6/1997	08/944,649	10/27/1998	5,828,622	US
NMXS-0310.01/US	Utility - CON	Lapsed	MEMORY-ROW SELECTOR HAVING A TEST FUNCTION	9/10/1997	08/926,833	12/8/1998	5,848,018	US
NMXS-0311.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR SETTING THE TIME DURATION OF A WRITE TO A MEMORY CELL	1/19/1996	08/587,711	1/26/1999	5,864,696	US
NMXS-0311.01/US	Utility - DIV	Issued	CIRCUIT AND METHOD FOR SETTING THE TIME DURATION OF A WRITE TO A MEMORY CELL	2/9/1998	09/020,430	12/21/1999	6,006,339	US
NMXS-0312.00/US	Utility - ORG	Issued	LOW-POWER READ CIRCUIT AND METHOD FOR CONTROLLING A SENSE AMPLIFIER	1/19/1996	08/589,024	4/8/1997	5,619,466	US
NMXS-0313.01/US	Utility - DIV	Issued	DEVICE AND METHOD FOR DRIVING A CONDUCTIVE PATH WITH A SIGNAL	9/15/1997	08/929,987	3/16/1999	5,883,838	US
NMXS-0313.02/US	Utility - CON	Issued	DEVICE AND METHOD FOR DRIVING A CONDUCTIVE PATH WITH A SIGNAL	11/19/1997	08/974,747	4/20/1999	5,896,336	US
NMXS-0314.00/US	Utility - ORG	Issued	CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES	8/24/1995	08/519,075	5/27/1997	5,633,828	US
NMXS-0315.00/US	Utility - ORG	Issued	ENTIRE WAFER STRESS TEST METHOD FOR INTEGRATED MEMORY DEVICES AND CIRCUIT THEREFOR	8/21/1995	08/484,609	9/17/1996	5,557,573	US
NMXS-0316.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/28/1996	08/623,044	9/22/1998	5,812,446	US
NMXS-0317.00/US	Utility - ORG	Issued	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OF NEGATIVE SUPPLY CIRCUIT	6/13/1996	08/664,083	6/2/1998	5,760,638	US
NMXS-0318.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	8/27/1996	08/708,811	3/16/1999	5,883,833	US
NMXS-0318.01/US	Utility - DIV	Issued	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	11/24/1998	09/198,431	3/7/2000	6,034,895	US
NMXS-0319.00/US	Utility - ORG	Issued	HIGH VOLTAGE GENERATOR	12/11/1996	08/762,677	9/1/1998	5,801,577	US
NMXS-0320.00/US	Utility - ORG	Issued	METHODS AND APPARATUS FOR PROGRAMING CONTENT-ADDRESSABLE MEMORIES USING FLOATING-GATE MEMORY CELLS	10/25/1996	08/738,231	4/7/1998	5,737,266	US
NMXS-0321.00/US	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/12/1997	08/797,948	9/7/1999	5,950,224	US
NMXS-0322.00/US	Utility - ORG	Issued	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1/24/1997	08/792,962	3/23/1999	5,886,549	US

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MatDocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0322.01/US	Utility - CON	Issued	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	11/17/1998	09/193,735	9/26/2000	6,125,022	US
NMXS-0323.00/US	Utility - ORG	Issued	FLASH-EPROM WITH EMBEDDED EEPROM	4/10/1997	08/833,925	12/15/1998	5,850,092	US
NMXS-0323.01/US	Utility - DIV	Issued	FLASH-EPROM WITH EMBEDDED EEPROM	10/1/1998	09/164,761	6/13/2000	6,074,916	US
NMXS-0324.00/US	Utility - ORG	Issued	DATA SENSING TIMING MODULATING CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/27/1997	08/825,098	3/9/1999	5,881,001	US
NMXS-0325.00/US	Utility - ORG	Issued	SYNCHRONIZATION SIGNAL GENERATION CIRCUIT AND METHOD	5/30/1997	08/865,748	9/28/1999	5,959,935	US
NMXS-0326.00/US	Utility - ORG	Issued	POWER ON RESET CIRCUIT WITH AUTO TURN OFF	4/30/1997	08/846,757	7/27/1999	5,929,674	US
NMXS-0327.00/US	Utility - ORG	Issued	UPROM CELL FOR LOW VOLTAGE SUPPLY	4/30/1997	08/846,755	10/13/1998	5,822,259	US
NMXS-0328.00/US	Utility - ORG	Issued	BIASING CIRCUIT FOR UPROM CELLS WITH LOW VOLTAGE SUPPLY	4/30/1997	08/846,753	1/12/1999	5,859,797	US
NMXS-0329.00/US	Utility - ORG	Issued	LINE DECODER FOR MEMORY DEVICES	5/23/1997	08/862,563	1/25/2000	6,018,255	US
NMXS-0329.01/US	Utility - DIV	Issued	LINE DECODER FOR MEMORY DEVICES	11/2/1999	09/432,642	7/25/2000	6,094,073	US
NMXS-0330.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR READING LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS	6/18/1997	08/879,017	10/3/2000	6,128,225	US
NMXS-0331.00/US	Utility - ORG	Issued	LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY DEVICE WITH VOLTAGE BOOSTING	6/18/1997	08/877,927	5/11/1999	5,903,498	US
NMXS-0332.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS	6/18/1997	08/877,921	9/8/1998	5,805,500	US
NMXS-0333.01/US	Utility - CON	Issued	MOS CAPACITOR WITH WIDE VOLTAGE AND FREQUENCY OPERATING RANGES	7/27/2001	09/916,954	7/8/2003	6,590,247	US
NMXS-0334.00/US	Utility - ORG	Issued	BIDIRECTIONAL CHARGE PUMP GENERATING EITHER A POSITIVE OR NEGATIVE VOLTAGE	7/28/1997	08/900,165	2/6/2001	6,184,741	US
NMXS-0335.00/US	Utility - ORG	Issued	BICMOS NEGATIVE CHARGE PUMP	11/5/1997	08/965,068	1/18/2000	6,016,073	US
NMXS-0336.00/US	Utility - ORG	Issued	POSITIVE CHARGE PUMP	10/8/1997	08/946,727	6/13/2000	6,075,402	US
NMXS-0337.00/US	Utility - ORG	Issued	OUTPUT STAGE FOR A MEMORY DEVICE AND FOR LOW VOLTAGE APPLICATIONS	7/23/1997	08/899,228	4/10/2001	6,215,329	US
NMXS-0338.00/US	Utility - ORG	Issued	LOW NOISE OUTPUT BUFFER FOR SEMICONDUCTOR ELECTRONIC CIRCUITS	7/8/1997	08/889,653	5/9/2000	6,060,753	US
NMXS-0339.00/US	Utility - ORG	Issued	HIGH VOLTAGE TOLERANCE OUTPUT STAGE	7/23/1997	08/898,811	11/21/2000	6,150,844	US
NMXS-0340.00/US	Utility - CON	Issued	SINGLE-CELL REFERENCE SIGNAL GENERATING CIRCUIT FOR READING NONVOLATILE MEMORY	6/17/1997	08/877,066	8/31/1999	5,946,238	US
NMXS-0341.00/US	Utility - ORG	Issued	INTEGRATED DEVICE WITH PADS	3/5/1997	08/811,577	7/13/1999	5,923,076	US
NMXS-0342.00/US	Utility - ORG	Issued	NMOS NEGATIVE CHARGE PUMP	1/23/1998	09/012,331	10/10/2000	6,130,572	US
NMXS-0343.00/US	Utility - ORG	Issued	ADDRESS TRANSITION DETECTION CIRCUIT	3/5/1997	08/811,869	9/29/1998	5,815,464	US
NMXS-0344.00/US	Utility - ORG	Issued	METHOD FOR RECOVERING FAILED MEMORY DEVICES	3/18/1997	08/816,766	4/25/2000	6,055,665	US
NMXS-0345.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR GENERATING A POWER-ON RESET SIGNAL	3/27/1997	08/828,791	9/28/1999	5,959,476	US
NMXS-0346.00/US	Utility - ORG	Issued	GAIN MODULATED SENSE AMPLIFIER	3/27/1997	08/828,790	5/4/1999	5,901,087	US
NMXS-0346.01/US	Utility - DIV	Issued	GAIN MODULATED SENSE AMPLIFIER, PARTICULARLY FOR MEMORY DEVICES	3/26/1998	09/048,941	6/20/2000	6,078,523	US
NMXS-0347.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD TO ADJUST MEMORY TIMING	3/28/1997	08/825,138	3/23/1999	5,886,945	US
NMXS-0348.00/US	Utility - ORG	Issued	STANDBY VOLTAGE BOOSTING STAGE AND METHOD FOR A MEMORY DEVICE	3/27/1997	08/826,008	3/30/1999	5,889,723	US
NMXS-0349.00/US	Utility - ORG	Issued	VOLTAGE BOOSTER FOR MEMORY DEVICES	3/27/1997	08/824,958	9/8/1998	5,805,435	US
NMXS-0350.00/US	Utility - ORG	Issued	CIRCUIT FOR THE SWITCHING OF SUPPLY VOLTAGES IN ELECTRICALLY PROGRAMMABLE AND CANCELABLE NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	4/7/1997	08/835,294	5/19/1998	5,754,473	US
NMXS-0351.00/US	Utility - ORG	Issued	AUTO-SAVING CIRCUIT FOR PROGRAMMING CONFIGURATION ELEMENTS IN NON-VOLATILE MEMORY DEVICES	4/7/1997	08/835,296	1/26/1999	5,864,500	US
NMXS-0352.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR PROGRAMMING ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS IN A CELL MATRIX	4/4/1997	08/833,336	1/16/2001	6,175,521	US
NMXS-0353.00/US	Utility - ORG	Issued	CIRCUIT FOR DETECTING THE COINCIDENCE BETWEEN A BINARY INFORMATION UNIT STORED THEREIN AND AN EXTERNAL DATUM	3/17/1997	08/819,519	9/28/1999	5,959,917	US
NMXS-0354.00/US	Utility - ORG	Issued	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	4/17/1997	08/841,904	11/17/1998	5,838,623	US

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NMXS-0354.01/US	Utility - CON	Issued	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	10/30/1998	09/183,469	8/10/1999	5,936,907	US
NMXS-0355.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY DEVICE WITH ROW REDUNDANCY	4/17/1997	08/842,835	3/30/1999	5,889,710	US
NMXS-0356.00/US	Utility - ORG	Issued	REDUNDANCY MEMORY REGISTER	4/17/1997	08/841,903	9/22/1998	5,812,467	US
NMXS-0357.00/US	Utility - ORG	Issued	CIRCUIT FOR TRANSFERRING REDUNDANCY DATA OF A REDUNDANCY CIRCUIT INSIDE A MEMORY DEVICE BY MEANS OF A TIME-SHARED APPROACH	6/5/1997	08/869,859	1/26/1999	5,864,562	US
NMXS-0358.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY DEVICE WITH ROW AND COLUMN REDUNDANCY CIRCUITS AND A TIME-SHARED REDUNDANCY CIRCUIT TEST ARCHITECTURE	6/5/1997	08/869,367	2/2/1999	5,867,504	US
NMXS-0359.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH	6/3/1997	08/868,214	10/19/1999	5,968,183	US
NMXS-0360.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY	6/3/1997	08/868,213	11/3/1998	5,831,915	US
NMXS-0361.00/US	Utility - ORG	Issued	PRE-CHARGE STEP DETERMINING CIRCUIT OF A GENERIC BIT LINE PARTICULARLY FOR NON-VOLATILE MEMORIES	4/7/1997	08/835,347	5/9/2000	6,061,273	US
NMXS-0362.00/US	Utility - ORG	Issued	READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE	6/18/1997	08/877,922	3/23/1999	5,886,925	US
NMXS-0363.00/US	Utility - ORG	Issued	MULTILEVEL NON VOLATILE MEMORY DEVICE	8/22/1997	08/916,874	12/7/1999	5,999,445	US
NMXS-0364.00/US	Utility - ORG	Issued	FLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT	9/30/1997	08/940,278	8/31/1999	5,946,235	US
NMXS-0364.01/US	Utility - CON	Issued	FLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT	8/13/1999	09/373,813	5/22/2001	6,236,592	US
NMXS-0364.02/US	Utility - CON	Issued	FLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT	8/9/2000	09/636,397	6/26/2001	6,252,802	US
NMXS-0365.00/US	Utility - ORG	Issued	ASYMMETRICAL PULSIVE DELAY NETWORK	7/25/1997	08/900,424	4/4/2000	6,046,619	US
NMXS-0366.00/US	Utility - ORG	Issued	CONTROL CIRCUIT OF AN OUTPUT BUFFER	9/19/1997	08/934,499	5/18/1999	5,905,678	US
NMXS-0367.00/US	Utility - ORG	Issued	PROTECTION CIRCUIT FOR REDUNDANCY REGISTER SET-UP CELLS OF ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICES	10/30/1997	08/961,368	12/29/1998	5,854,762	US
NMXS-0368.00/US	Utility - ORG	Issued	PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES	12/9/1997	08/987,454	5/29/2001	6,239,042	US
NMXS-0368.01/US	Utility - DIV	Issued	PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES	8/24/2000	09/645,711	10/29/2002	6,472,750	US
NMXS-0369.00/US	Utility - ORG	Issued	FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE AND MANUFACTURING METHOD	9/29/1997	08/940,856	4/25/2000	6,054,731	US
NMXS-0369.01/US	Utility - DIV	Issued	Floating gate non-volatile memory cell with low erasing voltage and having different potential barriers	3/8/2000	09/521,867	11/14/2000	6,147,380	US
NMXS-0369.02/US	Utility - DIV	Issued	METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE	3/8/2000	09/521,876	6/4/2002	6,399,444	US
NMXS-0369.03/US	Utility - DIV	Issued	METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC	5/30/2002	10/158,706	3/23/2004	6,710,394	US
NMXS-0369.04/US	Utility - DIV	Issued	METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC	3/3/2004	10/792,308	1/11/2005	6,841,445	US
NMXS-0370.00/US	Utility - ORG	Issued	PROCESS FOR DEPOSITING A STRATIFIED DIELECTRIC STRUCTURE FOR ENHANCING THE PLANARITY OF SEMICONDUCTOR ELECTRONIC DEVICES	12/23/1997	08/996,920	11/30/1999	5,994,231	US
NMXS-0371.00/US	Utility - ORG	Abandoned	METHOD OF PLANARIZING A SEMICONDUCTOR DEVICE BY DEPOSITING A DIELECTRIC PLY STRUCTURE	12/23/1997	08/997,403	12/5/2000	6,156,637	US
NMXS-0371.01/US	Utility - DIV	Abandoned	PLANARIZATION STRUCTURE AND METHOD FOR DIELECTRIC LAYERS	10/13/2000	09/687,217	10/7/2003	6,630,739	US
NMXS-0372.00/US	Utility - ORG	Issued	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	9/29/1997	08/940,115	3/16/1999	5,883,837	US
NMXS-0372.01/US	Utility - DIV	Issued	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	12/1/1998	09/203,798	10/26/1999	5,973,966	US
NMXS-0373.00/US	Utility - ORG	Issued	STAIRCASE ADAPTIVE VOLTAGE GENERATOR CIRCUIT	2/26/1998	09/032,282	9/7/1999	5,949,666	US
NMXS-0374.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT ARCHITECTURE FOR TESTING A NON-VOLATILE MEMORY DEVICE	5/30/1997	08/865,642	6/27/2000	6,081,911	US

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MtrDocNbr	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0375.00/US	Utility - ORG	Issued	SELF-REGULATED EQUALIZER, PARTICULARLY FOR SENSE AMPLIFIERS	10/30/1997	08/960,926	11/16/1999	5,986,954	US
NMXS-0376.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT FOR GENERATING INITIALIZATION SIGNALS FOR MEMORY CELL SENSING CIRCUITS	5/30/1997	08/866,283	6/22/1999	5,914,901	US
NMXS-0377.00/US	Utility - ORG	Issued	CIRCUIT FOR IMMUNIZING AN INTEGRATED CIRCUIT FROM NOISE AFFECTING ENABLE SIGNALS OF THE INTEGRATED CIRCUIT	3/4/1997	08/811,548	5/11/1999	5,903,166	US
NMXS-0378.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH A MEMORY CELL ARRAY IN TRIPLE WELL, AND RELATED MANUFACTURING PROCESS	2/20/1998	09/027,343	11/23/1999	5,990,526	US
NMXS-0378.01/US	Utility - DIV	Issued	MEMORY DEVICE WITH A MEMORY CELL ARRAY IN TRIPLE WELL, AND RELATED MANUFACTURING PROCESS	9/3/1999	09/389,955	6/6/2000	6,071,778	US
NMXS-0379.00/US	Utility - ORG	Issued	HIGH VOLTAGE CAPACITOR	7/20/1998	09/119,115	2/13/2001	6,188,121	US
NMXS-0380.00/US	Utility - ORG	Issued	CIRCUIT FOR THE GENERATION AND RESET OF TIMING SIGNAL USED FOR READING A MEMORY DEVICE	3/4/1997	08/813,386	8/11/1998	5,793,689	US
NMXS-0381.00/US	Utility - ORG	Issued	CIRCUIT FOR SELECTIVELY ENABLING ONE AMONG A PLURALITY OF CIRCUIT ALTERNATIVES OF AN INTEGRATED CIRCUIT	10/24/1997	08/957,685	8/8/2000	6,100,740	US
NMXS-0381.01/US	Utility - CON	Issued	CIRCUIT FOR SELECTIVELY ENABLING ONE AMONG A PLURALITY OF CIRCUIT ALTERNATIVES OF AN INTEGRATED CIRCUIT	4/25/2000	09/558,956	2/25/2003	6,525,591	US
NMXS-0381.02/US	Utility - DIV	Issued	METHOD FOR SELECTIVELY ENABLING ALTERNATIVE CIRCUITS	7/6/2000	09/611,258	11/20/2001	6,320,440	US
NMXS-0382.00/US	Utility - ORG	Issued	METHOD FOR VERIFYING ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE AFTER PROGRAMMING	5/30/1997	08/866,531	1/25/1999	5,864,503	US
NMXS-0383.00/US	Utility - ORG	Issued	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	12/23/1997	08/997,499	10/10/2000	6,130,165	US
NMXS-0383.01/US	Utility - DIV	Issued	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	3/17/2000	09/528,406	4/30/2002	6,380,582	US
NMXS-0384.00/US	Utility - ORG	Issued	ELECTRONIC MEMORY DEVICE HAVING BIT LINES WITH BLOCK SELECTOR SWITCHES	12/29/1997	08/998,854	10/19/1999	5,969,977	US
NMXS-0384.01/US	Utility - CON	Issued	MEMORY BLOCK FOR REALIZING SEMICONDUCTOR MEMORY DEVICES AND CORRESPONDING MANUFACTURING PROCESS	6/7/1999	09/327,111	8/8/2000	6,101,124	US
NMXS-0384.02/US	Utility - DIV	Issued	ELECTRONIC MEMORY DEVICE HAVING BIT LINES WITH BLOCK SELECTOR SWITCHES	8/13/1999	09/387,103	9/4/2001	6,284,585	US
NMXS-0385.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS	7/21/1997	08/897,799	11/2/1999	5,976,933	US
NMXS-0385.01/US	Utility - DIV	Issued	PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS	7/16/1999	09/356,080	3/5/2002	6,353,243	US
NMXS-0386.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR INCREASING THE INTERNAL ADDRESS OF A MEMORY DEVICE USING MULTIFUNCTIONAL TERMINALS	3/27/1998	09/049,858	9/5/2000	6,115,801	US
NMXS-0387.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	9/30/1997	08/941,882	3/9/1999	5,880,993	US
NMXS-0388.00/US	Utility - ORG	Abandoned	METHOD OF PRODUCING MOSFET TRANSISTORS BY MEANS OF TILTED IMPLANTS	4/20/1998	09/062,859	6/22/1999	5,915,185	US
NMXS-0389.00/US	Utility - ORG	Issued	METHOD FOR SAVING DATA IN THE EVENT OF UNWANTED INTERRUPTIONS IN THE PROGRAMMING CYCLE OF A NONVOLATILE MEMORY, AND A NONVOLATILE MEMORY	4/29/1999	09/302,231	9/5/2000	6,115,313	US
NMXS-0390.00/US	Utility - ORG	Issued	PROCESS FOR THE REPAIR OF FLOATING-GATE NON-VOLATILE MEMORIES DAMAGED BY PLASMA TREATMENT	12/15/1997	08/990,328	3/30/1999	5,888,836	US
NMXS-0391.00/US	Utility - ORG	Issued	VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARY FOR A NONVOLATILE MEMORY	2/25/1998	09/030,604	9/28/1999	5,959,902	US
NMXS-0392.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING A NATIVE MOS P-CHANNEL TRANSISTOR WITH A PROCESS FOR MANUFACTURING NON-VOLATILE MEMORIES	8/26/1998	09/139,909	5/16/2000	6,063,663	US

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MTI Docket	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0394.00/US	Utility - ORG	Issued	METHOD OF MANUFACTURING AN EPROM MEMORY DEVICE HAVING MEMORY CELLS ORGANIZED IN A TABLECLOTH MATRIX	8/27/1998	09/141,849	12/4/2001	6,326,266	US
NMXS-0395.00/US	Utility - ORG	Issued	SWITCHING MASTER SLAVE CIRCUIT	1/19/1996	08/588,648	7/21/1998	5,783,958	US
NMXS-0396.00/US	Utility - ORG	Issued	MULTIPLE ACCESS MEMORY DEVICE	12/31/1996	08/775,664	7/21/1998	5,784,331	US
NMXS-0397.00/US	Utility - CIP	Issued	LOW CURRENT CRYSTAL OSCILLATOR WITH FAST START-UP TIME	5/3/1996	08/642,271	9/8/1998	5,805,027	US
NMXS-0398.00/US	Utility - ORG	Issued	EXTERNAL WRITE PULSE CONTROL METHOD AND STRUCTURE	12/21/1996	08/771,642	6/9/1998	5,764,592	US
NMXS-0399.00/US	Utility - ORG	Issued	BURN-IN STRESS TEST MODE	12/21/1996	08/771,645	3/14/2000	6,037,792	US
NMXS-0399.01/US	Utility - DIV	Issued	INTEGRATED CIRCUIT DEVICE HAVING A BURN-IN MODE FOR WHICH ENTRY INTO AND EXIT FROM CAN BE CONTROLLED	1/27/2000	09/491,664	10/30/2001	6,310,485	US
NMXS-0399.02/US	Utility - DIV	Issued	INTEGRATED CIRCUIT DEVICE HAVING A BURN-IN MODE FOR WHICH ENTRY INTO AND EXIT FROM CAN BE CONTROLLED	8/17/2001	09/931,820	2/11/2003	6,518,746	US
NMXS-0400.00/US	Utility - ORG	Issued	INPUT DELAY CONTROL	12/23/1996	08/780,053	2/17/1998	5,719,445	US
NMXS-0401.00/US	Utility - ORG	Issued	SENSE AMPLIFIER CONTROL OF A MEMORY DEVICE	4/25/1997	08/844,696	9/28/1999	5,959,910	US
NMXS-0402.00/US	Utility - CIP	Issued	CIRCUIT AND METHOD FOR SELECTING A SIGNAL	11/27/1996	08/758,587	3/14/2000	6,037,799	US
NMXS-0403.00/RE	Utility - REIS	Issued	EDGE TRANSITION DETECTION CIRCUITRY FOR USE WITH TEST MODE OPERATION OF AN INTEGRATED CIRCUIT MEMORY DEVICE	5/9/2002	10/145,606	5/9/2000	RE40,282	US
NMXS-0403.00/US	Utility - ORG	Issued	EDGE TRANSITION DETECTION CIRCUITRY FOR USE WITH TEST MODE OPERATION OF AN INTEGRATED CIRCUIT MEMORY DEVICE	12/21/1996	08/771,643	5/9/2000	6,059,450	US
NMXS-0404.00/US	Utility - CIP	Issued	INTEGRATED CIRCUIT THAT SUPPORTS AND METHOD FOR WAFER-LEVEL TESTING	9/17/1996	08/710,357	9/15/1998	5,808,947	US
NMXS-0405.00/US	Utility - ORG	Issued	DEVICE FOR READING CELLS OF A MEMORY	6/12/1997	08/873,502	7/13/1999	5,923,590	US
NMXS-0406.00/US	Utility - ORG	Issued	PARALLEL-ACCESS MEMORY AND METHOD	5/9/1997	08/853,526	7/4/2000	6,085,280	US
NMXS-0407.00/US	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY COMPRISING INTERNAL REFRESH MEANS	10/24/1997	08/957,715	4/11/2000	6,049,497	US
NMXS-0408.00/US	Utility - ORG	Issued	READ CIRCUIT FOR NON-VOLATILE MEMORY WORKING WITH A LOW SUPPLY VOLTAGE	9/22/1997	08/934,696	1/12/1999	5,859,798	US
NMXS-0409.00/US	Utility - ORG	Issued	DEVICE FOR THE PROTECTION OF STORED DATA	8/21/1997	08/916,054	7/28/1998	5,787,040	US
NMXS-0410.00/US	Utility - ORG	Issued	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	1/30/1997	08/791,383	5/11/1999	5,903,141	US
NMXS-0411.00/US	Utility - ORG	Issued	DEVICE FOR THE PROTECTION OF STORED DATA USING A TIME DELAY CIRCUIT	8/21/1997	08/915,855	9/12/2000	6,119,210	US
NMXS-0412.00/US	Utility - ORG	Issued	MEMORY WITH IMPROVED READING TIME	10/24/1997	08/957,666	2/9/1999	5,870,336	US
NMXS-0413.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR POWER-ON/POWER-OFF CHECKING OF AN INTEGRATED CIRCUIT	12/18/1997	08/993,071	8/28/2001	6,281,723	US
NMXS-0414.00/US	Utility - ORG	Issued	OSCILLATOR AND SWITCH-OVER CONTROL CIRCUIT FOR A HIGH-VOLTAGE GENERATOR	12/22/1997	08/995,667	11/14/2000	6,147,566	US
NMXS-0414.01/US	Utility - DIV	Issued	OSCILLATOR AND SWITCH-OVER CONTROL CIRCUIT FOR A HIGH-VOLTAGE GENERATOR.	5/25/2000	09/578,778	4/16/2002	6,373,311	US
NMXS-0415.00/US	Utility - ORG	Issued	ELECTRICALLY ERASABLE FLOATING-GATE MEMORY ORGANIZED IN WORDS	3/24/1999	09/275,327	8/1/2000	6,097,631	US
NMXS-0416.00/US	Utility - ORG	Abandoned	METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	12/16/1997	08/991,693	10/24/2000	6,138,220	US
NMXS-0417.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY	12/16/1997	08/991,428	1/23/2001	6,178,490	US
NMXS-0418.00/US	Utility - ORG	Issued	MEMORY WITH READ PROTECTED ZONES	12/19/1997	08/994,889	12/14/1999	6,002,619	US
NMXS-0419.00/US	Utility - ORG	Issued	A READ CIRCUIT FOR MEMORY ADAPTED TO THE MEASUREMENT OF LEAKAGE CURRENTS	2/27/1998	09/031,748	3/30/1999	5,889,702	US
NMXS-0420.00/US	Utility - ORG	Issued	LOAD PUMP TYPE OF VOLTAGE GENERATOR CIRCUIT	4/13/1998	09/059,088	10/19/1999	5,969,961	US
NMXS-0421.00/US	Utility - ORG	Issued	DIFFERENTIAL AMPLIFIER IN A MOS TRANSISTORS STRUCTURE	11/6/1998	09/188,071	10/31/2000	6,140,876	US
NMXS-0422.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR THE FILTERING OF A PULSE SIGNAL	5/29/1998	09/087,478	10/12/1999	5,966,034	US
NMXS-0423.00/US	Utility - ORG	Issued	RING OSCILLATOR USING CMOS TECHNOLOGY	1/12/1998	09/005,722	10/3/2000	6,127,898	US
NMXS-0424.00/US	Utility - ORG	Issued	PAGE-WRITE INDICATOR FOR NON-VOLATILE MEMORY	1/20/1998	09/009,088	9/28/1999	5,959,886	US
NMXS-0425.00/US	Utility - ORG	Issued	WORD ADDRESSABLE FLOATING-GATE MEMORY COMPRISING A REFERENCE VOLTAGE GENERATOR CIRCUIT FOR THE VERIFICATION OF THE CONTENTS OF A WORD	3/6/1998	09/035,654	9/14/1999	5,953,253	US

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MTI Docket	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0426.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR THE ERASURE OF A NON-VOLATILE AND ELECTRICALLY ERASABLE MEMORY	11/26/1997	08/980,195	1/4/2000	6,011,724	US
NMXS-0427.00/US	Utility - ORG	Issued	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	11/14/1997	08/970,445	1/19/1999	5,862,075	US
NMXS-0428.00/US	Utility - ORG	Issued	CIRCUIT FOR THE DETECTION OF CHANGES OF ADDRESS	1/27/1998	09/013,956	8/15/2000	6,104,644	US
NMXS-0429.00/US	Utility - ORG	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	4/8/1998	09/056,921	3/20/2001	6,205,512	US
NMXS-0429.01/US	Utility - DIV	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	12/21/2000	09/746,473	8/13/2002	6,434,056	US
NMXS-0429.02/US	Utility - DIV	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	12/21/2000	09/746,472	8/21/2001	6,279,068	US
NMXS-0430.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR THE PROGRAMMING OF A MEMORY	1/22/1998	09/012,938	11/23/1999	5,991,199	US
NMXS-0430.02/US	Utility - NSPCT	Issued	METHOD FOR PROGRAMMING AN EPROM-FLASH TYPE MEMORY	1/22/1998	09/355,064	10/31/2000	6,141,254	US
NMXS-0431.00/US	Utility - ORG	Issued	VARIABLE FREQUENCY CHARGE PUMP	7/17/1998	09/118,953	5/9/2000	6,060,932	US
NMXS-0432.02/US	Utility - CON	Issued	PROCESS OF FINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE	12/18/2002	10/323,961	5/3/2005	6,888,225	US
NMXS-0433.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH REDUCED POWER DISSIPATION	4/1/1998	09/053,720	5/9/2000	6,061,286	US
NMXS-0434.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR READING A NON-ERASABLE MEMORY CELL	3/16/1998	09/039,588	6/13/2000	6,075,718	US
NMXS-0435.00/US	Utility - ORG	Issued	SEMICONDUCTOR INTEGRATED CIRCUIT	10/6/1999	09/093,382	4/3/2001	6,212,128	US
NMXS-0436.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLATILE MEMORY DEVICES	8/27/1998	09/141,250	1/18/2000	6,016,271	US
NMXS-0437.00/US	Utility - ORG	Issued	PROCESS FOR THE MANUFACTURING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE	8/6/1998	09/130,720	2/27/2001	6,194,270	US
NMXS-0437.01/US	Utility - DIV	Issued	PROCESS FOR THE MANUFACTURING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE	2/1/2001	09/776,105	8/20/2002	6,437,395	US
NMXS-0438.00/US	Utility - ORG	Issued	METHOD FOR FINAL PASSIVATION OF INTEGRATED CIRCUIT	4/14/1998	09/059,740	2/13/2001	6,187,683	US
NMXS-0439.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR ANALOG PROGRAMMING OF NON-VOLATILE MEMORY CELLS	5/11/1998	09/076,013	2/27/2001	6,195,283	US
NMXS-0440.00/US	Utility - ORG	Issued	MEMORY DEVICE GENERATOR FOR GENERATING MEMORY DEVICES WITH REDUNDANCY	10/19/1998	09/175,220	7/22/2003	6,598,190	US
NMXS-0441.00/US	Utility - ORG	Issued	METHOD FOR FORMING NON VOLATILE MEMORY STRUCTURES ON A SEMICONDUCTOR SUBSTRATE	12/10/1999	09/459,754	4/23/2002	6,376,306	US
NMXS-0442.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR READING A NON-VOLATILE MEMORY	7/14/1999	09/353,756	2/27/2001	6,195,286	US
NMXS-0443.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR ANALOG PROGRAMMING OF FLASH EEPROM MEMORY CELLS WITH AUTOVERIFY	9/28/1998	09/162,639	6/27/2000	6,081,448	US
NMXS-0444.00/US	Utility - ORG	Abandoned	METHOD FOR LOCALIZING POINT DEFECTS CAUSING LEAKAGE CURRENTS IN A NON-VOLATILE MEMORY DEVICE	5/13/1999	09/311,258	4/9/2002	6,369,406	US
NMXS-0445.00/US	Utility - ORG	Issued	DATA READ CIRCUIT FOR NON VOLATILE MEMORY CELLS	10/6/1999	09/413,383	12/11/2001	6,330,188	US
NMXS-0446.00/US	Utility - ORG	Issued	ROW DECODER FOR A FLASH-EEPROM MEMORY DEVICE WITH THE POSSIBILITY OF SELECTIVE ERASING OF A SUB-GROUP OF ROWS OF A SECTOR	11/25/1998	09/200,002	9/19/2000	6,122,200	US
NMXS-0447.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD OF READING CELLS OF AN ANALOG MEMORY ARRAY, IN PARTICULAR OF THE FLASH TYPE	7/22/1998	09/121,024	10/26/1999	5,973,959	US
NMXS-0448.00/US	Utility - ORG	Issued	DECODER FOR MEMORIES HAVING OPTIMIZED CONFIGURATION	11/20/2000	09/716,747	3/26/2002	6,362,658	US
NMXS-0449.00/US	Utility - ORG	Issued	METHOD FOR PARALLEL PROGRAMMING OF NONVOLATILE MEMORY DEVICES, IN PARTICULAR FLASH MEMORIES AND EEPROMS	10/27/1998	09/181,230	5/30/2000	6,069,822	US
NMXS-0450.00/US	Utility - ORG	Issued	METHOD OF MEASURING THE THICKNESS OF A LAYER OF SILICON DAMAGED BY PLASMA ETCHING	6/29/1999	09/343,207	5/15/2001	6,233,046	US
NMXS-0451.00/US	Utility - ORG	Issued	SECTORED SEMICONDUCTOR MEMORY DEVICE WITH CONFIGURABLE MEMORY SECTOR ADDRESSES	9/23/1998	09/159,322	6/4/2002	6,401,164	US
NMXS-0452.00/US	Utility - ORG	Issued	STACKED CHARGE PUMP CIRCUIT	8/27/1997	08/927,391	7/20/1999	5,926,059	US
NMXS-0453.00/US	Utility - ORG	Issued	CMOS TWIN-TUB NEGATIVE VOLTAGE SWITCHING ARCHITECTURE	8/27/1997	08/921,930	11/30/1999	5,994,948	US
NMXS-0454.00/US	Utility - ORG	Abandoned	DETERMINATION OF THE THICKNESS OF A DENUDED ZONE IN A SILICON WAFER	7/1/1998	09/108,439	3/6/2001	6,197,606	US

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MR Docket No.	Matter Type	Matter Status	Title	File Date	Serial No.	Issue Date	Patent No.	Country
NMXS-0455.00/US	Utility - ORG	Issued	HIGH VOLTAGE DRIVER CIRCUIT FOR A DECODING CIRCUIT IN MULTILEVEL NON-VOLATILE MEMORY DEVICES	12/31/1998	09/224,330	2/22/2000	6,028,793	US
NMXS-0456.00/US	Utility - ORG	Issued	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELL DEVICES	5/28/1999	09/321,961	6/5/2001	6,242,971	US
NMXS-0457.00/US	Utility - ORG	Issued	CONTROLLED HOT-ELECTRON WRITING METHOD FOR NON-VOLATILE MEMORY CELLS	10/8/1998	09/169,239	1/9/2001	6,172,908	US
NMXS-0458.00/US	Utility - ORG	Issued	SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF	12/16/1998	09/212,896	8/14/2001	6,275,960	US
NMXS-0459.00/US	Utility - ORG	Issued	COMPENSATED VOLTAGE REGULATOR	9/30/1998	09/163,755	11/9/1999	5,982,677	US
NMXS-0460.00/US	Utility - ORG	Issued	METHOD FOR MULTILEVEL PROGRAMMING OF A NONVOLATILE MEMORY, AND A MULTILEVEL NONVOLATILE MEMORY	11/3/1998	09/185,906	1/4/2000	6,011,715	US
NMXS-0461.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR GENERATING AN ATD SIGNAL TO REGULATE THE ACCESS TO A NON-VOLATILE MEMORY	11/4/1998	09/186,497	6/13/2000	6,075,750	US
NMXS-0462.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR REGULATING THE LENGTH OF AN ATD PULSE SIGNAL	11/4/1998	09/186,496	1/2/2001	6,169,423	US
NMXS-0463.00/US	Utility - ORG	Issued	BOOSTING CIRCUIT PARTICULARY FOR A MEMORY DEVICE	11/5/1998	09/186,758	11/7/2000	6,144,589	US
NMXS-0464.00/US	Utility - ORG	Issued	IMPROVED OUTPUT CIRCUIT FOR INTEGRATED CIRCUITS	10/13/1998	09/170,788	11/28/2000	6,153,914	US
NMXS-0465.00/US	Utility - ORG	Issued	MEMORY CELL VOLTAGE REGULATOR WITH TEMPERATURE CORRELATED VOLTAGE GENERATOR CIRCUIT	11/4/1998	09/186,498	2/6/2001	6,184,670	US
NMXS-0467.00/US	Utility - ORG	Issued	HIGH-VOLTAGE PUMP ARCHITECTURE FOR INTEGRATED ELECTRONIC DEVICES	1/29/1999	09/239,908	8/14/2001	6,275,099	US
NMXS-0468.00/US	Utility - ORG	Issued	CIRCUIT FOR DISCHARGING A NEGATIVE POTENTIAL NODE TO GROUND, INCLUDING CONTROL OF THE DISCHARGE CURRENT	3/24/1999	09/275,200	6/19/2001	6,249,172	US
NMXS-0469.00/US	Utility - ORG	Issued	SWITCHING CIRCUIT	3/24/1999	09/275,694	5/16/2000	6,064,598	US
NMXS-0470.00/US	Utility - ORG	Issued	DATA PROTECTION METHOD FOR A SEMICONDUCTOR MEMORY AND CORRESPONDING PROTECTED MEMORY DEVICE	12/23/1998	09/220,127	9/4/2001	6,286,086	US
NMXS-0471.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR SINGLE FEED VOLTAGE MEMORY CIRCUITS, AND FLASH TYPE MEMORY IN PARTICULAR	11/20/1998	09/196,204	8/8/2000	6,101,118	US
NMXS-0471.01/US	Utility - DIV	Issued	VOLTAGE REGULATOR FOR SINGLE FEED VOLTAGE MEMORY CIRCUITS, AND FLASH TYPE MEMORIES IN PARTICULAR	6/26/2000	09/602,669	9/4/2001	6,285,614	US
NMXS-0472.00/US	Utility - ORG	Issued	ELECTRONIC CIRCUIT FOR GENERATING A STABLE VOLTAGE SIGNAL FOR POLARIZING DURING A READING STEP UPROM MEMORY CELLS OPERATING AT LOW FEED VOLTAGE	12/21/1998	09/218,796	3/20/2001	6,204,722	US
NMXS-0473.00/US	Utility - ORG	Issued	ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS	12/29/1998	09/222,022	5/30/2000	6,069,837	US
NMXS-0474.00/US	Utility - ORG	Issued	METHOD AND A RELATED CIRCUIT FOR ADJUSTING THE DURATION OF A SYNCHRONIZATION SIGNAL ATD FOR TIMING THE ACCESS TO A NON-VOLATILE MEMORY	12/29/1998	09/222,070	5/22/2001	6,237,104	US
NMXS-0475.00/US	Utility - ORG	Issued	DRIVING CIRCUIT WITH THREE OUTPUT LEVELS, ONE OUTPUT LEVEL BEING A BOOSTED LEVEL	1/19/1999	09/234,016	12/5/2000	6,157,225	US
NMXS-0476.00/US	Utility - ORG	Abandoned	MEMORY CELL INTEGRATED STRUCTURE AND CORRESPONDING BIASING DEVICE	4/21/1999	09/295,667	11/21/2000	6,151,251	US
NMXS-0476.01/US	Utility - DIV	Abandoned	MEMORY CELL INTEGRATED STRUCTURE WITH CORRESPONDING BIASING DEVICE	9/29/2000	09/675,985	10/16/2001	6,304,490	US
NMXS-0477.00/US	Utility - ORG	Issued	SWITCHING CIRCUIT HAVING AN OUTPUT VOLTAGE VARYING BETWEEN A REFERENCE VOLTAGE AND A NEGATIVE VOLTAGE	3/24/1999	09/275,255	2/29/2000	6,031,761	US
NMXS-0478.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TRIMMING THE INTERNAL TIMING CONDITIONS OF A SEMICONDUCTOR MEMORY DEVICE	2/26/1998	09/032,272	12/28/1999	6,009,041	US
NMXS-0479.00/US	Utility - ORG	Issued	STRUCTURE AND METHOD FOR EVALUATING AN INTEGRATED ELECTRONIC DEVICE	12/9/1998	09/209,049	11/6/2001	6,313,480	US
NMXS-0480.00/US	Utility - ORG	Issued	LOW CONSUMPTION TTL-CMOS INPUT BUFFER STAGE	12/30/1999	09/231,130	10/23/2001	6,307,396	US

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Mil-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0481.00/US	Utility - NSPCT	Issued	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	09/674,395	9/11/2001	6,288,594	US
NMXS-0482.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY CAPABLE OF AUTONOMOUSLY EXECUTING A PROGRAM	7/8/1999	09/349,702	7/1/2003	6,587,934	US
NMXS-0483.00/US	Utility - ORG	Issued	OPERATING VOLTAGE SELECTION CIRCUIT FOR NON-VOLATILE SEMICONDUCTOR MEMORIES	1/13/1999	09/229,474	8/8/2000	6,101,127	US
NMXS-0484.00/US	Utility - ORG	Issued	METHOD FOR CONTROLLED ERASING MEMORY DEVICES, IN PARTICULAR ANALOG AND MULTI-LEVEL FLASH-EEPROM DEVICES	1/21/1999	09/234,942	7/18/2000	6,091,642	US
NMXS-0485.00/US	Utility - ORG	Issued	ESD PROTECTION NETWORK FOR CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	12/30/1998	09/223,621	7/24/2001	6,266,222	US
NMXS-0486.00/US	Utility - ORG	Issued	METHOD AND A CIRCUIT FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	12/30/1998	09/231,129	6/5/2001	6,242,793	US
NMXS-0486.01/US	Utility - DIV	Issued	METHOD FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR SUBSTRATE	4/17/2001	09/837,137	4/16/2002	6,372,597	US
NMXS-0487.00/US	Utility - ORG	Issued	HIGH STORAGE CAPACITY NON-VOLATILE MEMORY	5/26/1999	09/320,315	11/14/2000	6,147,902	US
NMXS-0488.00/US	Utility - ORG	Issued	PROCESS FOR FABRICATING A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	6/18/1999	09/336,089	4/17/2001	6,218,265	US
NMXS-0489.00/US	Utility - ORG	Issued	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR PROGRAMMING A NONVOLATILE MEMORY CELL HAVING A SINGLE VOLTAGE SUPPLY	5/28/1999	09/322,644	8/29/2000	6,111,791	US
NMXS-0490.00/US	Utility - ORG	Issued	ELECTRONIC COUNTER FOR A NON-VOLATILE MEMORY DEVICE INTEGRATED ON A SEMICONDUCTOR	3/4/1999	09/262,500	3/27/2001	6,208,705	US
NMXS-0491.00/US	Utility - ORG	Issued	EDGE TRANSITION DETECTION CONTROL OF A MEMORY DEVICE	12/30/1997	08/000,547	11/30/1999	5,995,444	US
NMXS-0492.01/US	Utility - CON	Abandoned	VSS SWITCHING SCHEME FOR BATTERY BACKED-UP SEMICONDUCTOR DEVICES	10/29/1999	09/429,904	8/22/2000	6,107,865	US
NMXS-0493.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR READING A MEMORY CELL	5/29/1998	09/087,399	11/30/1999	5,995,421	US
NMXS-0494.00/US	Utility - ORG	Issued	READ CIRCUIT FOR NON VOLATILE MEMORIES	10/29/1998	09/182,843	8/1/2000	6,097,633	US
NMXS-0495.00/US	Utility - ORG	Issued	IN-SITU DEPOSITION AND DOPING PROCESS FOR POLYCRYSTALLINE SILICON LAYERS AND THE RESULTING DEVICE	11/13/1998	09/191,743	3/15/2005	6,867,113	US
NMXS-0496.00/US	Utility - ORG	Issued	TEMPERATURE-STABLE CURRENT GENERATION	2/5/1999	09/246,029	10/17/2000	6,133,718	US
NMXS-0497.00/US	Utility - ORG	Issued	BITLINE BIAS CIRCUIT FOR NON-VOLATILE MEMORY DEVICES	2/23/1999	09/256,648	4/11/2000	6,049,491	US
NMXS-0498.00/US	Utility - ORG	Issued	SENSE AMPLIFIER FOR NON-VOLATILE MEMORY DEVICES	2/23/1999	09/256,603	7/25/2000	6,094,394	US
NMXS-0499.00/US	Utility - ORG	Issued	UPROM MEMORY CELLS FOR NON-VOLATILE MEMORY DEVICES INTEGRATED ON SEMICONDUCTORS	3/25/1999	09/276,263	8/7/2001	6,271,571	US
NMXS-0500.00/US	Utility - ORG	Issued	SENSE AMPLIFER FOR LOW VOLTAGE MEMORIES	2/12/1999	09/249,834	10/15/2002	6,466,059	US
NMXS-0501.00/US	Utility - ORG	Issued	LOW CONSUMPTION BOOSTED VOLTAGE DRIVING CIRCUIT	2/26/1999	09/257,682	10/10/2000	6,130,844	US
NMXS-0502.00/US	Utility - ORG	Issued	VOLTAGE BOOSTING CIRCUIT FOR GENERATING BOOSTED VOLTAGE PHASES	2/26/1999	09/258,224	5/16/2000	6,064,594	US
NMXS-0503.00/US	Utility - ORG	Issued	VOLTAGE PHASE GENERATOR WITH INCREASED DRIVING CAPACITY	2/26/1999	09/257,684	3/6/2001	6,198,672	US
NMXS-0504.00/US	Utility - ORG	Issued	PIPELINED NON-BLOCKING LEVEL TWO CACHE SYSTEM WITH INHERENT TRANSACTION COLLISION-AVOIDANCE	12/4/1998	09/205,598	2/11/2003	6,519,682	US
NMXS-0505.00/US	Utility - ORG	Issued	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON VOLATILE MEMORY HAVING A PROTECTABLE ZONE AND AN ELECTRONIC SYSTEM INCLUDING THE MEMORY	10/23/1998	09/177,899	3/7/2000	6,034,889	US
NMXS-0506.00/US	Utility - ORG	Issued	METHOD FOR WRITING IN AN ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY	10/27/1998	09/179,521	3/21/2000	6,040,994	US
NMXS-0507.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY	9/18/1998	09/156,945	11/30/1999	5,995,416	US
NMXS-0508.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORIES PROGRAMMABLE BY ""HOT CARRIER"" TUNNEL EFFECT AND ERASABLE BY TUNNEL EFFECT	10/15/1998	09/173,136	10/3/2000	6,128,222	US
NMXS-0509.00/US	Utility - ORG	Issued	NON-VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY	11/25/1998	09/199,671	12/7/1999	5,999,447	US
NMXS-0510.00/US	Utility - ORG	Issued	DETECTOR OF RADIO FREQUENCY SIGNALS FOR CONTACTLESS CHIP CARDS	9/18/1998	09/157,060	11/28/2000	6,152,373	US

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MD Docket No	Matter Type	Matter Status	Title	FileDate	SerialNo	Issue Date	PatentNo	Country
NMXS-0511.00/US	Utility - ORG	Issued	CIRCUIT FOR THE GENERATION OF VOLTAGE FOR THE PROGRAMMING OR ERASURE OF A MEMORY THAT USES FLOATING-GATE TRANSISTORS	10/27/1998	09/179,635	11/7/1999	5,978,268	US
NMXS-0512.00/US	Utility - ORG	Issued	DEVICE FOR DEMODULATING A BINARY PHASE-SHIFT KEYED SIGNAL	1/20/1999	09/234,194	10/31/2000	6,140,869	US
NMXS-0513.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE AND METHOD FOR THE PROGRAMMING OF THE SAME	11/18/1998	09/195,276	7/18/2000	6,091,641	US
NMXS-0514.00/US	Utility - ORG	Abandoned	DEVICE AND METHOD FOR THE READING OF EEPROM CELLS	4/27/1999	09/300,527	4/17/2001	6,219,277	US
NMXS-0515.00/US	Utility - ORG	Issued	LINE DECODER FOR A LOW SUPPLY VOLTAGE MEMORY DEVICE	6/1/1999	09/324,087	8/29/2000	6,111,809	US
NMXS-0516.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR READING NONVOLATILE MEMORY CELLS	5/28/1999	09/322,460	1/30/2001	6,181,602	US
NMXS-0517.00/US	Utility - ORG	Issued	CIRCUIT FOR PROVIDING A READING PHASE AFTER POWER-ON-RESET	4/20/1999	09/295,203	12/5/2000	6,157,579	US
NMXS-0519.00/US	Utility - ORG	Issued	SWITCHING CIRCUIT WITH AN OUTPUT VOLTAGE CHANGING AMONG FOUR POSSIBLE VALUES	3/24/1999	09/275,691	8/1/2000	6,097,243	US
NMXS-0520.00/US	Utility - ORG	Issued	PROCESS FOR THE MANUFACTURE OF INTEGRATED DEVICES WITH GATE OXIDE PROTECTION FROM MANUFACTURING PROCESS DAMAGE, AND PROTECTION STRUCTURE THEREFOR	6/25/1999	09/344,426	8/21/2001	6,278,159	US
NMXS-0520.01/US	Utility - DIV	Issued	PROCESS FOR THE MANUFACTURE OF INTEGRATED DEVICES WITH GATE OXIDE PROTECTION FROM MANUFACTURING PROCESS DAMAGE, AND PROTECTION STRUCTURE THEREFOR	6/25/2001	09/891,438	4/22/2003	6,551,897	US
NMXS-0521.00/US	Utility - ORG	Issued	ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD	7/30/1999	09/364,766	4/10/2001	6,215,688	US
NMXS-0521.01/US	Utility - DIV	Issued	ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD	2/9/2001	09/779,956	2/8/2005	6,852,596	US
NMXS-0521.02/US	Utility - DIV	Issued	ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD	1/12/2005	11/033,776	10/13/2009	7,601,590	US
NMXS-0522.00/US	Utility - ORG	Issued	METHOD FOR READING A MULTIPLE-LEVEL MEMORY CELL	3/25/1999	09/276,214	7/4/2000	6,084,797	US
NMXS-0523.01/US	Utility - CON	Issued	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	6/27/2001	09/894,975	2/4/2003	6,515,911	US
NMXS-0524.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	7/22/1999	09/359,923	6/26/2001	6,251,728	US
NMXS-0524.01/US	Utility - DIV	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	5/18/2001	09/861,404	7/16/2002	6,420,769	US
NMXS-0525.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING AN ELECTRONIC DEVICE INCLUDING MOS TRANSISTORS WITH SALICIDED JUNCTIONS AND NON-SALICIDED RESISTORS	7/21/1999	09/358,075	10/9/2001	6,300,182	US
NMXS-0526.00/US	Utility - ORG	Issued	METHOD FOR THE INTEGRATION OF RESISTORS AND ESD SELF-PROTECTED TRANSISTORS IN AN INTEGRATED DEVICE WITH A MEMORY MATRIX MANUFACTURED BY MEANS OF A PROCESS FEATURING SELF-ALIGNED SOURCE (SAS) FORMATION AND JUNCTION SALICIDATION	12/15/1999	09/464,066	10/8/2002	6,461,922	US
NMXS-0527.01/US	Utility - DIV	Issued	METHOD FOR ENHANCING SELECTIVITY BETWEEN A FILM OF A LIGHT-SENSITIVE MATERIAL AND A LAYER TO BE ETCHED IN ELECTRONIC SEMICONDUCTOR DEVICE FABRICATION PROCESSES	4/17/2001	09/836,937	12/17/2002	6,495,455	US
NMXS-0528.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING SELECTION TRANSISTORS FOR NONVOLATILE SERIAL-FLASH, EPROM, EEPROM AND FLASH-EEPROM MEMORIES IN STANDARD OR AMG CONFIGURATION	6/11/1999	09/330,540	7/3/2001	6,255,163	US
NMXS-0529.00/US	Utility - ORG	Issued	METHOD OF MAKING HIGH-VOLTAGE HV TRANSISTORS WITH DRAIN EXTENSION IN A CMOS PROCESS OF THE DUAL GATE TYPE WITH SILICIDE	10/1/1999	09/411,134	9/4/2001	6,284,607	US
NMXS-0530.00/US	Utility - ORG	Issued	METHOD FOR FAST PROGRAMMING FLOATING GATE MEMORIES BY TUNNEL EFFECT	6/25/1999	09/344,425	1/9/2001	6,172,913	US
NMXS-0531.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING OF A NON VOLATILE MEMORY WITH REDUCED RESISTANCE OF THE COMMON SOURCE LINES	6/21/1999	09/337,051	1/30/2001	6,180,460	US
NMXS-0532.00/US	Utility - ORG	Issued	SIMPLIFIED PROCESS FOR DEFINING THE TUNNEL AREA IN NON-ALIGNED, NON-VOLATILE SEMICONDUCTOR MEMORY CELLS	10/14/1999	09/419,403	9/3/2002	6,444,526	US
NMXS-0533.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH ROW REDUNDANCY	5/12/2000	09/570,332	10/9/2001	6,301,152	US
NMXS-0534.00/US	Utility - ORG	Issued	METHOD FOR FORMING CONTACTLESS MOS TRANSISTORS AND RESULTING DEVICES, ESPECIALLY FOR USE IN NON-VOLATILE MEMORY ARRAYS	12/28/1999	09/473,368	6/26/2001	6,251,736	US

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MII-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0535.00/US	Utility - ORG	Abandoned	PROCESS FOR THE DEFINITION OF OPENINGS IN A DIELECTRIC LAYER	9/28/1999	09/406,903	11/6/2001	6,313,040	US
NMXS-0536.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	9/9/1999	09/392,937	8/28/2001	6,281,077	US
NMXS-0536.01/US	Utility - DIV	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	4/16/2001	09/836,590	5/28/2002	6,396,101	US
NMXS-0537.00/US	Utility - ORG	Issued	SELECTIVE SALICIDATION PROCESS FOR ELECTRONIC DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/28/1999	09/473,367	8/5/2003	6,602,774	US
NMXS-0538.00/US	Utility - ORG	Issued	METHOD FOR CORRECTION OF ERRORS IN A BINARY WORD STORED IN MULTILEVEL MEMORY CELLS, NOT REQUIRING ADDITIONAL CELLS	2/24/2000	09/513,286	3/4/2003	6,530,058	US
NMXS-0539.00/US	Utility - ORG	Issued	NONVOLATILE MULTILEVEL MEMORY AND READING METHOD THEREFORE	2/9/2000	09/501,131	9/24/2002	6,456,527	US
NMXS-0540.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TESTING MEMORY CELLS IN A MULTILEVEL MEMORY DEVICE	10/7/1999	09/415,024	10/9/2001	6,301,157	US
NMXS-0541.00/US	Utility - ORG	Issued	DEVICE FOR READING NON-VOLATILE MEMORY CELLS, IN PARTICULAR ANALOG FLASH MEMORY CELLS	10/19/1999	09/421,616	11/27/2001	6,323,799	US
NMXS-0542.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH AUTOMATIC GENERATION OF PROGRAMMING VOLTAGE	11/12/1999	09/438,232	10/15/2002	6,466,481	US
NMXS-0543.00/US	Utility - ORG	Issued	CIRCUIT FOR PARALLEL PROGRAMMING NONVOLATILE MEMORY CELLS, WITH ADJUSTABLE PROGRAMMING SPEED	11/23/1999	09/447,531	12/19/2000	6,163,483	US
NMXS-0544.00/US	Utility - ORG	Issued	CIRCUIT FOR HIGH-PRECISION ANALOG READING OF NONVOLATILE MEMORY CELLS, IN PARTICULAR ANALOG OR MULTILEVEL FLASH OR EEPROM MEMORY CELLS	11/12/1999	09/438,823	10/3/2000	6,128,228	US
NMXS-0545.00/US	Utility - ORG	Issued	PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH-PERFORMANCE LOGIC CIRCUITRY	11/24/1999	09/449,044	6/25/2002	6,410,387	US
NMXS-0545.01/US	Utility - DIV	Issued	PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH-PERFORMANCE LOGIC CIRCUITRY	5/29/2002	10/158,424	3/30/2004	6,713,347	US
NMXS-0546.00/US	Utility - ORG	Issued	METHOD FOR MAINTAINING THE MEMORY CONTENT OF NON-VOLATILE MEMORY CELLS	9/15/1999	09/397,387	1/2/2001	6,169,691	US
NMXS-0547.00/US	Utility - ORG	Issued	METHOD OF FABRICATION OF A NO-FIELD MOS TRANSISTOR	4/5/2000	09/543,400	2/26/2002	6,350,637	US
NMXS-0548.00/US	Utility - CIP	Issued	DEVICE FOR READING ANALOG NONVOLATILE MEMORY CELLS, IN PARTICULAR FLASH CELLS	10/22/1999	09/425,445	2/27/2001	6,195,289	US
NMXS-0549.00/US	Utility - ORG	Issued	CAPACITIVE BOOSTING CIRCUIT FOR THE REGULATION OF THE WORD LINE READING VOLTAGE IN NON-VOLATILE MEMORIES	1/19/2000	09/491,476	7/10/2001	6,259,635	US
NMXS-0550.00/US	Utility - ORG	Issued	CAPACITIVE COMPENSATION CIRCUIT FOR THE REGULATION OF THE WORD LINE READING VOLTAGE IN NON-VOLATILE MEMORIES	1/19/2000	09/491,475	7/10/2001	6,259,632	US
NMXS-0551.00/US	Utility - ORG	Issued	CHIP OUTLINE BAND (COB) STRUCTURE FOR INTEGRATED CIRCUITS	1/14/2000	09/483,656	10/8/2002	6,462,400	US
NMXS-0552.00/US	Utility - ORG	Issued	IMPROVED FIELD-EFFECT TRANSISTOR AND CORRESPONDING MANUFACTURING METHOD	11/18/1999	09/442,834	5/14/2002	6,387,763	US
NMXS-0552.01/US	Utility - DIV	Issued	FIELD-EFFECT TRANSISTOR AND CORRESPONDING MANUFACTURING METHOD	3/4/2002	10/090,978	5/18/2004	6,737,715	US
NMXS-0553.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR DRIVING PLURAL LOADS BASED ON THE NUMBER OF LOADS BEING DRIVEN	12/20/1999	09/467,726	5/15/2001	6,232,753	US
NMXS-0554.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES, COMPRISING NON-SALICIDED NON-VOLATILE MEMORY CELLS, NON-SALICIDED HV TRANSISTORS, AND LV TRANSISTORS WITH SALICIDED JUNCTIONS WITH FEW MASKS	12/21/1999	09/469,849	8/14/2001	6,274,411	US
NMXS-0555.00/US	Utility - ORG	Issued	METHOD FOR HIGH PRECISION PROGRAMMING NONVOLATILE MEMORY CELLS, WITH OPTIMIZED PROGRAMMING SPEED	11/24/1999	09/449,168	5/21/2002	6,392,931	US
NMXS-0556.00/US	Utility - ORG	Issued	PROCESS OF MANUFACTURE OF A NON VOLATILE MEMORY WITH ELECTRIC CONTINUITY OF THE COMMON SOURCE LINES	4/12/2000	09/547,520	9/25/2001	6,294,431	US
NMXS-0557.00/US	Utility - ORG	Issued	FLASH COMPATIBLE EEPROM	6/21/2000	09/599,356	4/24/2001	6,222,775	US

PATENT
REEL: 030872 FRAME: 0103

Exhibit A - US Issued Patents

MTI DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0558.00/US	Utility - ORG	Issued	METHOD FOR READING A MEMORY, PARTICULARLY A NON-VOLATILE MEMORY	12/29/1999	09/474,932	11/5/2002	6,477,675	US
NMXS-0559.00/US	Utility - ORG	Issued	SYNCHRONOUS OUTPUT BUFFER, PARTICULARLY FOR NON-VOLATILE MEMORIES	11/20/2000	09/716,759	7/23/2002	6,424,575	US
NMXS-0560.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	2/18/2000	09/507,777	4/2/2002	6,365,456	US
NMXS-0561.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	2/25/2000	09/512,900	10/9/2001	6,300,195	US
NMXS-0562.00/US	Utility - ORG	Abandoned	BIT COUNTER STAGE, PARTICULARLY FOR MEMORIES	12/15/1999	09/464,631	11/27/2001	6,324,238	US
NMXS-0563.00/US	Utility - ORG	Issued	PULSE GENERATOR CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES	12/27/1999	09/472,496	8/14/2001	6,275,416	US
NMXS-0564.00/US	Utility - ORG	Issued	PRIORITY DETERMINING CIRCUIT FOR NON-VOLATILE MEMORY	2/8/2000	09/499,799	4/16/2002	6,373,781	US
NMXS-0565.00/US	Utility - ORG	Issued	METHOD FOR AUTOALIGNING OVERLAPPED LINES OF A CONDUCTIVE MATERIAL PROVIDED IN INTEGRATED ELECTRONIC CIRCUITS	5/26/2000	09/579,778	2/26/2002	6,350,671	US
NMXS-0566.00/US	Utility - ORG	Issued	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/20/2000	09/552,933	3/18/2003	6,535,431	US
NMXS-0566.01/US	Utility - DIV	Issued	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	1/24/2003	10/350,745	10/12/2004	6,803,630	US
NMXS-0567.00/US	Utility - ORG	Issued	ADDRESS LATCH ENABLE SIGNAL CONTROL CIRCUIT FOR ELECTRONIC MEMORIES	12/8/1999	09/457,500	6/19/2001	6,249,468	US
NMXS-0569.00/US	Utility - ORG	Issued	SEMICONDUCTOR DEVICE WITH IMPROVED INTERCONNECTIONS BETWEEN THE CHIP AND THE TERMINALS, AND PROCESS FOR ITS MANUFACTURE	2/10/2000	09/502,070	5/28/2002	6,396,132	US
NMXS-0570.00/US	Utility - ORG	Issued	Method for reading a multilevel nonvolatile memory and multilevel nonvolatile memory	2/25/2000	09/513,598	10/9/2001	6,301,149	US
NMXS-0571.00/US	Utility - ORG	Issued	VOLTAGE REGULATING CIRCUIT FOR A CAPACITIVE LOAD	6/29/2000	09/608,445	6/19/2001	6,249,112	US
NMXS-0572.00/US	Utility - ORG	Issued	APPARATUS AND METHOD FOR SWITCHING BETWEEN TWO POWER SUPPLIES OF AN INTEGRATED CIRCUIT	12/21/1998	09/217,321	9/12/2000	6,118,188	US
NMXS-0573.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR INCREASING COMPARATOR GAIN WITHOUT AFFECTING STANDBY CURRENT	12/21/1998	09/217,323	7/4/2000	6,084,390	US
NMXS-0574.00/US	Utility - ORG	Issued	METHOD AND STRUCTURE FOR ENHANCING THE ACCESS TIME OF INTEGRATED CIRCUIT MEMORY DEVICES	10/30/1998	09/183,231	8/31/1999	5,946,264	US
NMXS-0575.00/US	Utility - ORG	Issued	CONTROL CIRCUIT FOR TERMINATING A MEMORY ACCESS CYCLE IN A MEMORY BLOCK OF AN ELECTRONIC STORAGE DEVICE	10/30/1998	09/183,589	3/7/2000	6,034,917	US
NMXS-0576.00/US	Utility - ORG	Issued	STRESS TEST MODE ENTRY AT POWER UP FOR LOW/ZERO POWER MEMORIES	10/30/1998	09/183,451	6/27/2000	6,081,466	US
NMXS-0577.00/US	Utility - ORG	Issued	INITIALIZATION FOR FUSE CONTROL	10/30/1998	09/183,840	3/21/2000	6,041,000	US
NMXS-0578.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT STRUCTURE COMPRISING CAPACITOR ELEMENT AND CORRESPONDING MANUFACTURING PROCESS	10/12/1999	09/415,992	9/25/2001	6,294,798	US
NMXS-0578.01/US	Utility - DIV	Issued	INTEGRATED CIRCUIT STRUCTURE COMPRISING CAPACITOR ELEMENT AND CORRESPONDING MANUFACTURING PROCESS	7/24/2001	09/912,638	1/28/2003	6,511,874	US
NMXS-0579.00/US	Utility - ORG	Issued	CONTENT ADDRESSABLE MEMORY PROTECTION CIRCUIT AND METHOD	4/28/2000	09/561,271	5/29/2001	6,240,002	US
NMXS-0580.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR FAST ADDRESSING REDUNDANt COLUMNS IN A NON VOLATILE MEMORY	4/13/2000	09/548,783	10/30/2001	6,310,801	US
NMXS-0581.00/US	Utility - ORG	Issued	READING CIRCUIT FOR NONVOLATILE MEMORY CELLS WITHOUT LIMITATIONOF THE SUPPLY VOLTAGE	4/11/2000	09/546,957	11/27/2001	6,324,098	US
NMXS-0582.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR AUTOMATICALLY REGULATING THE EQUALIZATION DURATION WHEN READING A NONVOLATILE MEMORY	4/11/2000	09/546,975	6/5/2001	6,243,310	US
NMXS-0583.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING SOI INTEGRATED CIRCUITS AND CIRCUITS MADE THEREBY	4/28/2000	09/561,272	6/25/2002	6,410,404	US
NMXS-0584.00/US	Utility - ORG	Issued	COMMUNICATIONS SYSTEM AND METHOD FOR REDUCING THE EFFECTS OF TRANSMITTER NON-LINEAR DISTORTION ON A RECEIVED SIGNAL	6/17/1999	09/335,024	8/13/2002	6,434,189	US
NMXS-0585.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES	5/18/1999	09/313,926	7/23/2002	6,425,066	US

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MTI Docket No	Matter Type	Matter Status	Title	File Date	Serial No	Issue Date	Patent No	Country
NMXS-0586.00/US	Utility - ORG	Issued	MULTIPLE LEVEL FLOATING-GATE MEMORY	12/2/1999	09/453,753	6/11/2002	6,404,679	US
NMXS-0587.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR GENERATING A HIGH VOLTAGE	8/10/1999	09/371,549	12/5/2000	6,157,243	US
NMXS-0588.00/US	Utility - ORG	Abandoned	METHOD FOR VERIFYING THE MEMORY CIRCUIT INTEGRITY	12/2/1999	09/452,446	4/3/2001	6,212,112	US
NMXS-0589.00/US	Utility - ORG	Issued	SECURED EEPROM MEMORY COMPRISING MEANS FOR THE DETECTION OF ERASURE BY ULTRAVIOLET RADIATION	11/24/1999	09/448,632	6/19/2001	6,249,456	US
NMXS-0590.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR THE PROGRAMMING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY FOR IMPROVING RELIABILITY	4/21/2000	09/556,476	9/18/2001	6,292,396	US
NMXS-0591.00/US	Utility - ORG	Issued	METHOD FOR ERASING AND REWRITING NON VOLATILE MEMORY CELLS AND PARTICULARLY FLASH CELLS	4/20/2000	09/553,526	8/28/2001	6,282,125	US
NMXS-0592.00/US	Utility - ORG	Issued	READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATIO VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	6/8/2000	09/589,723	3/26/2002	6,363,015	US
NMXS-0593.00/US	Utility - ORG	Issued	ERASING AND PARALLEL REWRITING CIRCUIT FOR MEMORY CELL BLOCKS, PARTICULARLY FOR ANALOG FLASH CELLS, AND RELATED OPERATING METHOD	6/13/2000	09/592,796	11/6/2001	6,314,043	US
NMXS-0594.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY DEVICE, IN PARTICULAR A FLASH-EEPROM	4/20/2000	09/552,945	2/26/2002	6,351,413	US
NMXS-0595.00/US	Utility - ORG	Issued	METHOD FOR THE IN-WRITING VERIFICATION OF THE THRESHOLD VALUE IN NON-VOLATILE MEMORIES	5/11/2000	09/569,232	9/18/2001	6,292,398	US
NMXS-0596.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY DEVICE WITH HIERARCHICAL SECTOR DECODING	6/26/2000	09/602,680	9/24/2002	6,456,530	US
NMXS-0597.00/US	Utility - ORG	Issued	SYNCHRONOUS MULTILEVEL NON-VOLATILE MEMORY AND RELATED READING METHOD	5/17/2000	09/572,127	3/6/2001	6,198,660	US
NMXS-0598.00/US	Utility - ORG	Issued	CIRCUIT FOR READING A SEMICONDUCTOR MEMORY	6/26/2000	09/603,275	12/25/2001	6,333,885	US
NMXS-0599.00/US	Utility - ORG	Issued	BIASING STAGE FOR BIASING THE DRAIN TERMINAL OF A NONVOLATILE MEMORY CELL DURING THE READ PHASE	6/2/2000	09/586,399	11/20/2001	6,320,790	US
NMXS-0600.00/US	Utility - ORG	Issued	METHOD AND A DEVICE FOR MEASURING AN ANALOG VOLTAGE IN A NON-VOLATILE MEMORY	6/29/2000	09/608,847	1/14/2003	6,507,183	US
NMXS-0601.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR GENERATING FROM A SINGLE SUPPLY LINE VOLTAGES INTERNAL TO A FLASH MEMORY WITH REDUCED SETTLING TIMES	6/30/2000	09/608,239	5/21/2002	6,392,936	US
NMXS-0602.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH LOW POWER CONSUMPTION AND AND RELATIVE WRITING, READING AND ERASING METHODS	7/21/2000	09/620,765	9/18/2001	6,292,400	US
NMXS-0603.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING MULTI-LEVEL NON-VOLATILE MEMORIES BY CONTROLLING THE GATE VOLTAGE	8/2/2000	09/631,187	4/2/2002	6,366,496	US
NMXS-0604.00/US	Utility - ORG	Issued	CMOS SWITCH CIRCUIT FOR TRANSFERRING HIGH VOLTAGES, IN PARTICULAR FOR LINE	6/2/2000	09/585,916	8/13/2002	6,433,583	US
NMXS-0605.00/US	Utility - ORG	Abandoned	ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE	6/16/2000	09/595,054	3/12/2002	6,356,481	US
NMXS-0606.00/US	Utility - ORG	Issued	METHOD FOR READING DATA FROM A NON-VOLATILE MEMORY DEVICE WITH AUTODETECT BURST MODE READING AND CORRESPONDING READING CIRCUIT	11/20/2000	09/716,746	2/19/2002	6,349,059	US
NMXS-0607.00/US	Utility - ORG	Issued	SOFT PROGRAMMING METHOD FOR NON-VOLATILE MEMORY CELLS	12/14/2000	09/738,253	10/22/2002	6,469,934	US
NMXS-0608.01/US	Utility - DIV	Issued	BIPOLAR TRANSISTOR PRODUCED USING PROCESSES COMPATIBLE WITH THOSE EMPLOYED IN THE MANUFACTURE OF MOS DEVICES	2/15/2002	10/077,288	12/30/2003	6,670,229	US
NMXS-0610.00/US	Utility - ORG	Issued	BUFFER DEVICE WITH DUAL SUPPLY VOLTAGE FOR LOW SUPPLY VOLTAGE APPLICATIONS	12/13/2000	09/736,984	11/20/2001	6,320,361	US
NMXS-0611.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY WITH FUNCTIONAL CAPABILITY OF SIMULTANEOUS MODIFICATION OF THE CONTENT AND BURST MODE READ OR PAGE MODE READ	7/28/2000	09/627,703	6/28/2005	6,912,598	US
NMXS-0612.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY WITH FUNCTIONAL CAPABILITY OF BURST MODE READ AND PAGE MODE READ DURING SUSPENSION OF AN OPERATION OF ELECTRICAL ALTERATION	7/19/2000	09/619,589	8/27/2002	6,442,068	US

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Exhibit A - US Issued Patents

MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0613.00/US	Utility - ORG	Issued	METHOD FOR CONTROLLED SOFT PROGRAMMING OF NON-VOLATILE MEMORY CELLS, IN PARTICULAR OF THE FLASH EEPROM AND EPROM TYPE	10/27/2000	09/699,309	4/30/2002	6,381,177	US
NMXS-0614.00/US	Utility - ORG	Issued	MANUFACTURE OF AN HV-MOS TRANSISTOR WITH LOW MULTIPLICATION FACTOR IN A DUAL-GATE CMOS PROCESS	11/14/2000	09/713,144	12/31/2002	6,501,147	US
NMXS-0615.00/US	Utility - ORG	Issued	READ CIRCUIT FOR A NONVOLATILE MEMORY	7/21/2000	09/621,019	12/4/2001	6,327,184	US
NMXS-0617.00/US	Utility - ORG	Issued	ENABLING CIRCUIT FOR OUTPUT DEVICES IN ELECTRONIC MEMORIES	7/31/2000	09/629,229	8/20/2002	6,438,040	US
NMXS-0618.00/US	Utility - ORG	Issued	PROCESS FOR THE FABRICATION OF INTEGRATED DEVICES WITH REDUCTION OF DAMAGE FROM PLASMA	3/9/2001	09/804,693	10/28/2003	6,638,833	US
NMXS-0619.00/US	Utility - ORG	Issued	NON VOLATILE MEMORY WITH DETECTION OF SHORT CIRCUITS BETWEEN WORD LINES	9/8/2000	09/658,236	10/23/2001	6,307,778	US
NMXS-0620.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR TIMING MULTI-LEVEL NON-VOLATILE MEMORIES	12/15/2000	09/738,889	6/3/2003	6,574,146	US
NMXS-0621.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH BURST MODE READING AND CORRESPONDING READING METHOD	11/21/2000	09/717,938	2/8/2005	6,854,040	US
NMXS-0622.00/US	Utility - ORG	Issued	VOLTAGE GENERATOR SWITCHING BETWEEN ALTERNATING, FIRST AND SECOND VOLTAGE VALUES, IN PARTICULAR FOR PROGRAMMING MULTILEVEL CELLS	11/15/2000	09/714,837	7/23/2002	6,424,121	US
NMXS-0623.00/US	Utility - ORG	Lapsed	ANTI-DECIPHERING CONTACTS	10/1/2001	09/968,682	3/4/2003	6,528,885	US
NMXS-0624.00/US	Utility - ORG	Issued	READING CIRCUIT FOR A NON-VOLATILE MEMORY	10/27/2000	09/699,304	6/4/2002	6,400,607	US
NMXS-0625.00/US	Utility - ORG	Issued	READING METHOD AND CIRCUIT FOR A NON-VOLATILE MEMORY	10/27/2000	09/699,043	10/29/2002	6,473,340	US
NMXS-0626.00/US	Utility - ORG	Issued	COLUMN DECODER CIRCUIT FOR PAGE READING OF A SEMICONDUCTOR MEMORY	2/27/2001	09/797,171	1/14/2003	6,507,534	US
NMXS-0627.00/US	Utility - ORG	Issued	FLOW PROCESS FOR PRODUCING NON-VOLATILE MEMORIES WITH DIFFERENTIATED REMOVAL OF SACRIFICAL OXIDE	8/2/2000	09/630,933	3/26/2002	6,362,053	US
NMXS-0628.00/US	Utility - ORG	Issued	ARCHITECTURE FOR HANDLING INTERNAL VOLTAGES IN A NON-VOLATILE MEMORY, PARTICULARLY IN A SINGLE-VOLTAGE SUPPLY TYPE OF DUAL-WORK FLASH MEMORY	11/9/2000	09/710,067	5/7/2002	6,385,107	US
NMXS-0629.00/US	Utility - ORG	Issued	CONTROL AND TIMING STRUCTURE FOR A MEMORY	10/5/2001	09/972,753	4/15/2003	6,549,485	US
NMXS-0630.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NONVOLATILE MEMORY CELLS OF REDUCED DIMENSIONS	11/22/2000	09/718,971	1/21/2003	6,509,222	US
NMXS-0630.01/US	Utility - DIV	Issued	PROCESS FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NONVOLATILE MEMORY CELLS OF REDUCED DIMENSIONS	8/20/2002	10/225,315	8/5/2003	6,603,171	US
NMXS-0631.00/US	Utility - ORG	Issued	MANUFACTURING PROCESS FOR NON-VOLATILE FLOATING GATE MEMORY CELLS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND COMPRISED IN A CELL MATRIX WITH AN ASSOCIATED CONTROL CIRCUITRY	12/5/2000	09/730,518	7/16/2002	6,420,223	US
NMXS-0632.00/US	Utility - ORG	Issued	SINGLE SUPPLY VOLTAGE NONVOLATILE MEMORY DEVICE WITH ROW DECODING	7/28/2000	09/627,273	4/16/2002	6,373,780	US
NMXS-0633.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY TEST STRUCTURE AND NONVOLATILE MEMORY RELIABILITY TEST METHOD	10/27/1999	09/428,683	10/3/2000	6,128,219	US
NMXS-0635.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY	9/12/2001	09/952,957	2/25/2003	6,525,961	US
NMXS-0637.00/US	Utility - ORG	Issued	SERIAL-FLASH, EPROM, EEPROM AND FLASH EEPROM NONVOLATILE MEMORY IN AMG CONFIGURATION	10/10/2000	09/686,362	4/30/2002	6,381,173	US
NMXS-0638.00/US	Utility - ORG	Issued	LOW CONSUMPTION VOLTAGE BOOST DEVICE	12/22/2000	09/747,312	8/20/2002	6,437,636	US
NMXS-0639.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH CONFIGURABLE ROW REDUNDANCY	2/14/2001	09/785,079	7/9/2002	6,418,051	US
NMXS-0640.00/US	Utility - ORG	Abandoned	INTEGRATED DEVICE WITH OPERATIVITY TESTING	3/2/2001	09/798,347	5/24/2005	6,898,745	US
NMXS-0641.00/US	Utility - ORG	Issued	VOLTAGE BOOSTING DEVICE, IN PARTICULAR FOR SPEEDING POWER-UP OF MULTILEVEL NONVOLATILE MEMORIES	2/6/2001	09/778,330	8/6/2002	6,429,634	US
NMXS-0642.00/US	Utility - ORG	Issued	NON-VOLATILE HIGH-PERFORMANCE MEMORY DEVICE AND RELATIVE MANUFACTURING PROCESS	12/19/2000	09/740,407	1/13/2004	6,677,206	US
NMXS-0643.00/US	Utility - ORG	Issued	SYNCHRONOUS COUNTER FOR ELECTRONIC MEMORIES	1/28/2001	09/767,762	2/26/2002	6,351,434	US

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MN FileNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0644.00/US	Utility - ORG	Issued	SYNCHRONIZATION CIRCUIT FOR READ PATHS OF AN ELETRONIC MEMORY	4/5/2001	09/827,369	10/12/2004	6,804,756	US
NMXS-0645.00/US	Utility - ORG	Issued	INTERNAL ADDRESSING STRUCTURE OF A SEMICONDUCTOR MEMORY	10/9/2001	09/974,737	12/31/2002	6,501,700	US
NMXS-0646.00/US	Utility - ORG	Issued	STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE	3/20/2001	09/817,363	7/2/2002	6,414,875	US
NMXS-0646.01/US	Utility - DIV	Issued	STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE	6/24/2002	10/179,553	1/27/2004	6,683,808	US
NMXS-0646.02/US	Utility - DIV	Issued	STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE	12/19/2003	10/742,429	7/4/2006	7,072,212	US
NMXS-0646.03/US	Utility - DIV	Issued	STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE	12/19/2003	10/742,181	10/11/2005	6,954,395	US
NMXS-0647.00/US	Utility - ORG	Issued	MANUFACTURING PROCESS FOR THE INTEGRATION IN A SEMICONDUCTOR CHIP OF AN INTEGRATED CIRCUIT INCLUDING A HIGH-DENSITY INTEGRATED CIRCUIT COMPONENTS PORTION AND A HIGH-PERFORMANCE LOGIC INTEGRATED CIRCUIT COMPONENTS PORTION	5/15/2001	09/858,335	9/17/2002	6,451,653	US
NMXS-0648.00/US	Utility - ORG	Issued	LOGIC PARTITIONING OF A NONVOLATILE MEMORY ARRAY	3/26/2001	09/817,804	6/17/2003	6,581,134	US
NMXS-0649.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY MATRIX ARCHITECTURE WITH VERTICAL INSULATION STRIPS BETWEEN ADJACENT MEMORY BLOCKS	7/3/2001	09/898,744	10/15/2002	6,466,479	US
NMXS-0650.00/US	Utility - ORG	Issued	PROGRAMMABLE VOLTAGE GENERATOR	11/15/2000	09/714,852	11/18/2003	6,650,173	US
NMXS-0651.00/US	Utility - ORG	Issued	METHOD OF FORMING LOW-RESISTIVITY CONNECTIONS IN NON-VOLATILE MEMORIES	3/2/2001	09/798,778	2/3/2004	6,686,241	US
NMXS-0652.00/US	Utility - ORG	Issued	METHOD AND A DEVICE FOR TESTING ELECTRONIC MEMORY DEVICES	3/30/2001	09/823,926	1/23/2007	7,168,016	US
NMXS-0653.00/US	Utility - ORG	Issued	CIRCUITAL STRUCTURE FOR PROGRAMMING DATA IN A NON-VOLATILE MEMORY DEVICE	5/30/2001	09/871,235	1/14/2003	6,507,517	US
NMXS-0654.00/US	Utility - ORG	Issued	CIRCUITAL STRUCTURE FOR READING DATA IN A NON-VOLATILE MEMORY DEVICE	5/30/2001	09/871,234	4/15/2003	6,549,473	US
NMXS-0655.00/US	Utility - ORG	Abandoned	INTEGRATED DEVICE WITH VOLTAGE SELECTOR	3/29/2001	09/823,262	11/5/2002	6,476,664	US
NMXS-0656.00/US	Utility - ORG	Abandoned	LOW-CONSUMPTION CHARGE PUMP FOR A NONVOLATILE MEMORY	3/28/2001	09/821,827	5/6/2003	6,559,709	US
NMXS-0657.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY CELL WITH A FLOATING GATE REGION AUTOALIGNED TO THE ISOLATION AND WITH A HIGH COUPLING COEFFICIENT	7/6/2001	09/900,501	3/25/2003	6,537,879	US
NMXS-0657.01/US	Utility - DIV	Issued	NON-VOLATILE MEMORY CELL WITH A FLOATING GATE REGION AUTOALIGNED TO THE ISOLATION AND WITH A HIGH COUPLING COEFFICIENT	1/7/2003	10/337,556	6/15/2004	6,750,505	US
NMXS-0658.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY ARCHITECTURE	10/5/2001	09/972,769	6/17/2003	6,580,637	US
NMXS-0659.00/US	Utility - ORG	Issued	REFERENCE VOLTAGE ADJUSTMENT	12/31/1999	09/476,036	8/28/2001	6,281,734	US
NMXS-0659.01/US	Utility - DIV	Issued	REFERENCE VOLTAGE ADJUSTMENT	7/10/2002	09/902,205	11/5/2002	6,476,669	US
NMXS-0660.00/US	Utility - ORG	Issued	INTEGRATED VOLATILE AND NON-VOLATILE MEMORY	8/31/2000	09/653,495	7/15/2003	6,594,192	US
NMXS-0660.01/US	Utility - DIV	Issued	INTEGRATED VOLATILE AND NON-VOLATILE MEMORY	5/20/2003	10/442,844	8/24/2004	6,781,916	US
NMXS-0661.00/US	Utility - ORG	Issued	CMOS TECHNOLOGY VOLTAGE BOOSTER	12/15/2000	09/738,890	7/16/2002	6,420,926	US
NMXS-0662.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY AND HIGH SPEED MEMORY TEST METHOD	9/26/2000	09/670,248	8/20/2002	6,438,048	US
NMXS-0663.00/US	Utility - ORG	Issued	Memory test method and nonvolatile memory with low error masking probability	9/26/2000	09/670,471	8/28/2001	6,282,134	US
NMXS-0664.00/US	Utility - ORG	Issued	ROW SELECTION CIRCUIT FOR FAST MEMORY DEVICES	12/21/2000	09/745,286	8/27/2002	6,442,072	US
NMXS-0665.00/US	Utility - ORG	Issued	INTERLEAVED DATA PATH AND OUTPUT MANAGEMENT ARCHITECTURE FOR AN INTERLEAVED MEMORY AND LOAD PULSER CIRCUIT FOR OUTPUTTING THE READ DATA	1/31/2001	09/774,542	10/22/2002	6,470,431	US
NMXS-0666.00/US	Utility - ORG	Issued	INTERLEAVED MEMORY DEVICE FOR SEQUENTIAL ACCESS SYNCHRONOUS READING WITH SIMPLIFIED ADDRESS COUNTERS	1/31/2001	09/774,539	9/17/2002	6,452,864	US
NMXS-0667.00/US	Utility - ORG	Issued	REDUNDANCY ARCHITECTURE FOR AN INTERLEAVED MEMORY	1/31/2001	09/773,272	10/29/2002	6,473,339	US
NMXS-0668.00/US	Utility - ORG	Issued	ACCELERATED CARRY GENERATION	1/31/2001	09/774,878	4/2/2002	6,366,634	US
NMXS-0669.00/US	Utility - ORG	Issued	ATD GENERATION IN A SYNCHRONOUS MEMORY	1/31/2001	09/773,760	9/23/2003	6,625,706	US
NMXS-0670.00/US	Utility - ORG	Issued	INTERLEAVED MEMORY DEVICE FOR BURST TYPE ACCESS IN SYNCHRONOUS READ MODE WITH THE TWO SEMI-ARRAYS INDEPENDENTLY READABLE IN RANDOM ACCESS ASYNCHRONOUS MODE	1/31/2001	09/773,300	7/1/2003	6,587,913	US
NMXS-0671.00/US	Utility - ORG	Issued	COLOR IMAGE RESTORATION WITH ANTI-ALIAS	11/2/2000	09/705,145	1/11/2005	6,842,191	US

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Mtl DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0672.00/US	Utility - NSPCT	Issued	VOLTAGE PRODUCTION CIRCUIT	6/26/2000	10/019,771	9/16/2003	6,621,720	US
NMXS-0673.00/US	Utility - ORG	Issued	METHOD FOR PAGE MODE WRITING IN AN ELECTRICALLY ERASABLE/PROGRAMMABLE NON-VOLATILE MEMORY AND CORRESPONDING ARCHITECTURE	9/12/2000	09/660,303	1/7/2003	6,504,791	US
NMXS-0674.00/US	Utility - ORG	Issued	MEMORY INCORPORATING COLUMN REGISTER AND METHOD OF WRITING IN SAID MEMORY	9/29/2000	09/675,366	10/23/2001	6,307,792	US
NMXS-0674.01/US	Utility - DIV	Issued	MEMORY INCORPORATING COLUMN REGISTER AND METHOD OF WRITING IN SAID MEMORY	9/13/2001	09/952,904	5/7/2002	6,385,096	US
NMXS-0675.00/US	Utility - ORG	Issued	ARCHITECTURE OF A NON-VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY	9/7/2000	09/657,319	8/14/2001	6,275,413	US
NMXS-0677.00/US	Utility - ORG	Issued	PAGE BY PAGE PROGRAMMABLE FLASH MEMORY	12/14/2000	09/737,170	1/4/2005	6,839,285	US
NMXS-0678.00/US	Utility - ORG	Issued	METHOD FOR THE CORRECTION OF A BIT IN A STRING OF BITS	12/15/2000	09/737,827	5/11/2004	6,735,733	US
NMXS-0679.00/US	Utility - ORG	Issued	HIGH-EFFICIENCY BIDIRECTIONAL VOLTAGE BOOSTING DEVICE	2/13/2001	09/788,623	9/10/2002	6,448,842	US
NMXS-0680.00/US	Utility - ORG	Issued	CHARGE PUMP BOOSTER DEVICE WITH TRANSFER AND RECOVERY OF THE CHARGE	2/13/2001	09/785,042	6/11/2002	6,404,272	US
NMXS-0681.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY CELL WITH HIGH PROGRAMMING EFFICIENCY	7/30/2001	09/919,341	5/11/2004	6,734,490	US
NMXS-0682.00/US	Utility - ORG	Issued	METHOD AND A CIRCUIT STRUCTURE FOR MODIFYING THE THRESHOLD VOLTAGES OF NON-VOLATILE MEMORY CELLS	7/18/2001	09/908,986	2/11/2003	6,519,183	US
NMXS-0683.00/US	Utility - ORG	Issued	CONTROL CIRCUIT FOR A VARIABLE-VOLTAGE REGULATOR OF A NONVOLATILE MEMORY WITH HIERARCHICAL ROW DECODING	9/21/2001	09/960,851	1/7/2003	6,504,758	US
NMXS-0684.00/US	Utility - ORG	Issued	CIRCUIT ARRANGEMENT FOR THE LOWERING OF THE THRESHOLD VOLTAGE OF A DIODE CONFIGURED TRANSISTOR	6/13/2001	09/881,661	12/31/2002	6,501,673	US
NMXS-0685.00/US	Utility - ORG	Issued	DIRECT COMPARISON READING CIRCUIT FOR A NONVOLATILE MEMORY ARRAY	8/15/2001	09/930,875	10/8/2002	6,462,987	US
NMXS-0686.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY WITH A CHARGE PUMP WITH REGULATED VOLTAGE	7/19/2001	09/909,467	11/12/2002	6,480,436	US
NMXS-0687.00/US	Utility - ORG	Issued	CHARGE PUMP WITH EFFICIENT SWITCHING TECHNIQUES	12/11/2000	09/735,277	3/19/2002	6,359,500	US
NMXS-0688.00/US	Utility - ORG	Issued	High-voltage bidirectional switch made using high-voltage MOS transistors	6/16/2000	09/595,680	9/11/2001	6,288,603	US
NMXS-0689.00/US	Utility - ORG	Issued	READING CIRCUIT FOR SEMICONDUCTOR NON-VOLATILE MEMORIES	9/13/2001	09/953,070	5/13/2003	6,563,737	US
NMXS-0691.00/US	Utility - ORG	Issued	LATERAL DMOS TRANSISTOR WITH FIRST AND SECOND DRAIN ELECTRODES IN RESPECTIVE CONTACT WITH HIGH-AND LOW-CONCENTRATION PORTIONS OF A DRAIN REGION	9/20/2001	09/960,254	9/23/2003	6,624,471	US
NMXS-0692.00/US	Utility - ORG	Issued	VOLTAGE BOOSTER WITH A LOW OUTPUT RESISTANCE	2/13/2001	09/785,083	6/11/2002	6,404,273	US
NMXS-0693.00/US	Utility - ORG	Issued	MULTIPURPOSE METHOD FOR CONSTRUCTING AN ERROR-CONTROL CODE FOR MULTILEVEL MEMORY CELLS OPERATING WITH A VARIABLE NUMBER OF STORAGE LEVELS, AND MULTIPURPOSE ERROR-CONTROL METHOD USING SAID ERROR-CONTROL CODE	11/2/2001	10/015,949	5/16/2006	7,047,478	US
NMXS-0694.00/US	Utility - ORG	Issued	FOLDING TOP FOR A MOTOR VEHICLE	10/31/2001	09/002,599	8/5/2003	6,603,681	US
NMXS-0695.00/US	Utility - ORG	Issued	NONVOLATILE SEMICONDUCTOR MEMORY CAPABLE OF SELECTIVELY ERASING A PLURALITY OF ELEMENTAL MEMORY UNITS	7/31/2001	09/919,789	3/11/2003	6,532,171	US
NMXS-0696.00/US	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE, NON-VOLATILE, SEMICONDUCTOR MEMORY WHICH CAN KEEP A DATUM STORED UNTIL AN OPERATION TO MODIFY THE DATUM IS COMPLETED	12/28/2001	10/036,088	1/4/2005	6,839,818	US
NMXS-0697.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR FOR LOW-CONSUMPTION CIRCUITS	11/7/2001	09/008,540	5/6/2003	6,559,627	US
NMXS-0698.00/US	Utility - ORG	Issued	SMALL SIZE, LOW CONSUMPTION, MULTILEVEL NONVOLATILE MEMORY	10/4/2001	09/972,726	4/1/2003	6,542,404	US
NMXS-0699.00/US	Utility - ORG	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY	10/11/2001	09/976,473	11/11/2003	6,646,913	US
NMXS-0700.00/US	Utility - ORG	Abandoned	NONVOLATILE MEMORY DEVICE, HAVING PARTS WITH DIFFERENT ACCESS TIME, RELIABILITY, AND CAPACITY	9/19/2001	09/957,628	12/10/2002	6,498,260	US
NMXS-0701.00/US	Utility - ORG	Issued	CONTROL CIRCUIT FOR AN OUTPUT DRIVING STAGE OF AN INTEGRATED CIRCUIT	11/21/2001	09/991,493	5/20/2003	6,567,318	US

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NMXS-0702.00/US	Utility - ORG	Issued	BIASING CIRCUIT FOR MULTI-LEVEL MEMORY CELLS	6/14/2001	09/882,535	3/18/2003	6,535,428	US
NMXS-0703.00/US	Utility - ORG	Issued	CIRCUIT DEVICE FOR PERFORMING HIERARCHIC ROW DECODING IN NON-VOLATILE MEMORY DEVICES	7/12/2001	09/905,163	12/10/2002	6,493,268	US
NMXS-0704.01/US	Utility - CON	Issued	ANALOG-TO-DIGITAL CONVERSION METHOD AND DEVICE, IN HIGH-DENSITY MULTILEVEL NON-VOLATILE MEMORY DEVICES	1/29/2002	10/060,076	1/6/2004	6,674,385	US
NMXS-0705.00/US	Utility - ORG	Issued	POWER-ON RESET CIRCUIT FOR DUAL SUPPLY VOLTAGES	10/25/2001	09/003,474	11/12/2002	6,480,421	US
NMXS-0706.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH PROGRAM AND VERIFY ALGORITHM USING A STAIRCASE VOLTAGE WITH VARYING STEP AMPLITUDE	4/9/2002	10/119,523	9/7/2004	6,788,579	US
NMXS-0707.00/US	Utility - ORG	Issued	CONDUCTION LINE DECOUPLING CIRCUIT	7/26/2001	09/917,613	9/7/2004	6,788,517	US
NMXS-0708.00/US	Utility - ORG	Issued	MULTI-EMITTER BIPOLAR TRANSISTOR FOR BANDGAP REFERENCE CIRCUITS	12/27/2001	10/035,006	3/2/2004	6,700,226	US
NMXS-0710.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY SYSTEM	5/30/2002	10/158,554	7/15/2003	6,594,180	US
NMXS-0711.00/US	Utility - ORG	Issued	OUTPUT BUFFER FOR A NONVOLATILE MEMORY WITH OUTPUT SIGNAL SWITCHING NOISE REDUCTION, AND NONVOLATILE MEMORY COMPRISING THE SAME	5/30/2002	10/161,055	9/7/2004	6,788,586	US
NMXS-0712.00/US	Utility - ORG	Issued	OUTPUT BUFFER FOR A NONVOLATILE MEMORY WITH OPTIMIZED SLEW-RATE CONTROL	5/30/2002	10/161,055	12/7/2004	6,829,177	US
NMXS-0713.00/US	Utility - ORG	Issued	EEPROM FLASH MEMORY ERASABLE LINE BY LINE	8/20/2002	10/225,513	2/3/2004	6,687,167	US
NMXS-0714.00/US	Utility - ORG	Issued	METHOD OF PROGRAMMING A PLURALITY OF MEMORY CELLS CONNECTED IN PARALLEL, AND A PROGRAMMING CIRCUIT THEREFOR	12/19/2001	10/036,337	2/3/2004	6,687,159	US
NMXS-0715.00/US	Utility - ORG	Issued	COLUMN MULTIPLEXER FOR SEMICONDUCTOR MEMORIES	5/30/2002	10/158,553	4/22/2003	6,552,952	US
NMXS-0716.00/US	Utility - ORG	Issued	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/14/2001	10/017,502	12/23/2003	6,667,903	US
NMXS-0717.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL NONVOLATILE MEMORY CELL	1/14/2002	10/047,918	11/4/2003	6,643,179	US
NMXS-0718.00/US	Utility - ORG	Issued	METHOD FOR STORING DATA IN A NONVOLATILE MEMORY	12/19/2001	10/035,909	12/2/2003	6,655,758	US
NMXS-0720.00/US	Utility - ORG	Issued	AUTOTESTING METHOD OF A MEMORY CELL MATRIX, PARTICULARLY OF THE NON-VOLATILE TYPE	12/23/2002	10/328,721	11/8/2005	6,963,512	US
NMXS-0721.00/US	Utility - ORG	Issued	READING CIRCUIT AND METHOD FOR A MULTILEVEL NON-VOLATILE MEMORY	4/8/2002	10/118,660	12/2/2003	6,657,895	US
NMXS-0722.00/US	Utility - ORG	Abandoned	METHOD OF REFRESHING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	6/20/2002	10/176,387	5/4/2004	6,731,557	US
NMXS-0723.00/US	Utility - ORG	Issued	HIGH-EFFICIENCY POWER CHARGE PUMP SUPPLYING HIGH DC OUTPUT CURRENTS	6/3/2002	10/162,135	8/12/2003	6,605,985	US
NMXS-0724.00/US	Utility - ORG	Issued	NON-VOLATILE, ELECTRICALLY ALTERABLE SEMICONDUCTOR MEMORY	1/24/2002	10/057,769	9/9/2003	6,618,315	US
NMXS-0725.00/US	Utility - ORG	Issued	METHOD FOR ERASING AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, IN PARTICULAR AN EEPROM-FLASH MEMORY DEVICE, AND AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, IN PARTICULAR AN EEPROM-FLASH MEMORY DEVICE	5/30/2002	10/159,780	3/22/2005	6,871,258	US
NMXS-0726.00/US	Utility - ORG	Issued	METHOD FOR REFRESHING STORED DATA IN AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	1/24/2002	10/057,768	12/23/2003	6,668,308	US
NMXS-0727.00/US	Utility - ORG	Issued	MEMORY WITH IMPROVED DIFFERENTIAL READING SYSTEM	6/20/2002	10/176,554	3/2/2004	6,700,819	US
NMXS-0728.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR TIMING DYNAMIC READING OF A MEMORY CELL WITH CONTROL OF THE INTEGRATION TIME	4/16/2002	10/123,874	4/27/2004	6,728,141	US
NMXS-0729.00/US	Utility - CIP	Issued	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL AT LOW SUPPLY VOLTAGE AND WITH LOW OUTPUT DYNAMICS	2/13/2002	10/076,023	10/28/2003	6,639,833	US
NMXS-0730.00/US	Utility - CIP	Issued	METHOD AND CIRCUIT FOR GENERATING REFERENCE VOLTAGES FOR READING A MULTILEVEL MEMORY CELL	4/26/2002	10/133,231	4/20/2004	6,724,658	US
NMXS-0731.00/US	Utility - ORG	Issued	METHOD FOR ERROR CONTROL IN MULTILEVEL CELLS WITH CONFIGURABLE NUMBER OF STORED BITS	5/30/2002	10/159,782	3/21/2006	7,017,099	US
NMXS-0732.00/US	Utility - ORG	Issued	MANUFACTURING PROCESS OF AN INTERPOLY DIELECTRIC STRUCTURE FOR NON-VOLATILE SEMICONDUCTOR INTEGRATED MEMORIES	1/30/2003	10/356,351	8/1/2006	7,084,032	US

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NMXS-0733.00/US	Utility - ORG	Issued	MANUFACTURING PROCESS OF A SEMICONDUCTOR NON-VOLATILE MEMORY CELL	12/18/2002	10/323,615	8/28/2007	7,262,098	US
NMXS-0734.00/US	Utility - ORG	Issued	PROCESS FOR REMOVING POLYMERS DURING THE FABRICATION OF SEMICONDUCTOR DEVICES	7/2/2002	10/189,152	4/13/2004	6,720,271	US
NMXS-0735.00/US	Utility - ORG	Issued	LOW POWER CHARGE PUMP CIRCUIT	11/7/2002	10/290,030	11/9/2004	6,816,001	US
NMXS-0736.00/US	Utility - ORG	Issued	CONTENT ADDRESSABLE MEMORY (CAM) WITH BATTERY BACK-UP	6/29/2001	09/895,491	12/17/2002	6,496,439	US
NMXS-0737.00/US	Utility - ORG	Issued	Data output buffer with precharge	8/11/2000	09/636,363	9/18/2001	6,292,405	US
NMXS-0738.00/US	Utility - ORG	Issued	INTERLACED MEMORY DEVICE WITH RANDOM OR SEQUENTIAL ACCESS	10/15/2001	09/977,561	3/2/2004	6,701,419	US
NMXS-0739.00/US	Utility - ORG	Issued	OUTPUT BUFFER AND METHOD OF DRIVING	8/8/2001	09/925,842	12/3/2002	6,489,807	US
NMXS-0740.00/US	Utility - ORG	Issued	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/28/2001	10/033,711	11/18/2003	6,650,153	US
NMXS-0741.00/US	Utility - ORG	Issued	BOOST DEVICE FOR NONVOLATILE MEMORIES WITH AN INTEGRATED STAND-BY CHARGE PUMP	2/13/2002	10/076,134	11/18/2003	6,650,569	US
NMXS-0742.00/US	Utility - ORG	Abandoned	CHARGE PUMP FOR A NONVOLATILE MEMORY WITH READ VOLTAGE REGULATION IN THE PRESENCE OF ADDRESS SKEW, AND NONVOLATILE MEMORY COMPRISING SUCH A CHARGE PUMP	2/5/2002	10/068,560	5/6/2003	6,560,145	US
NMXS-0743.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR TIMING THE READING OF A NONVOLATILE MEMORY WITH REDUCED SWITCHING NOISE	2/15/2002	10/077,687	1/6/2004	6,674,666	US
NMXS-0744.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR AUTOMATICALLY GENERATING AN APPROPRIATE NUMBER OF WAIT CYCLES WHILE READING A NONVOLATILE MEMORY	4/3/2002	10/115,888	7/12/2005	6,917,994	US
NMXS-0745.00/US	Utility - ORG	Issued	CIRCUIT FOR GENERATING A PULSE SIGNAL INDEPENDENT OF VOLTAGE AND TEMPERATURE VARIATIONS	10/31/2001	09/998,903	4/15/2003	6,549,486	US
NMXS-0746.00/US	Utility - ORG	Issued	NEGATIVE CHARGE PUMP ARCHITECTURE WITH SELF-GENERATED BOOSTED PHASES	10/31/2001	09/998,902	4/13/2004	6,720,822	US
NMXS-0748.00/US	Utility - ORG	Issued	THRESHOLD AMPLIFIER	8/9/2001	09/925,979	4/15/2003	6,549,048	US
NMXS-0749.00/US	Utility - NSPCT	Issued	PAGE-ERASABLE FLASH MEMORY	11/14/2001	10/438,733	10/19/2004	6,807,103	US
NMXS-0750.00/US	Utility - ORG	Issued	CIRCUIT FOR THE DETECTION OF A DEFECTIVE POWER SUPPLY CONNECTION	1/29/2002	10/060,105	8/10/2004	6,774,663	US
NMXS-0751.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR SEQUENTIAL READOUT OF A MEMORY WITH ADDRESS JUMP	2/22/2002	10/081,740	8/9/2005	6,928,530	US
NMXS-0752.00/US	Utility - ORG	Issued	FLASH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL THRESHOLD VOLTAGES	11/15/2001	09/997,214	5/27/2003	6,568,510	US
NMXS-0752.01/US	Utility - DIV	Issued	FLASH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL THRESHOLD VOLTAGES	1/28/2003	10/352,581	3/30/2004	6,714,453	US
NMXS-0753.00/US	Utility - NSPCT	Issued	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	2/14/2002	10/471,883	1/16/2007	7,163,154	US
NMXS-0754.00/US	Utility - ORG	Issued	FLASH EEPROM AND EPROM ARRAYS WITH SELECT TRANSISTORS WITHIN THE BIT LINE PITCH	3/11/1994	08/212,176	9/17/1996	5,557,124	US
NMXS-0755.00/US	Utility - ORG	Issued	METHOD OF RE-PROGRAMMING AN ARRAY OF NON-VOLATILE MEMORY CELLS, IN PARTICULAR OF THE NOR ARCHITECTURE FLASH TYPE, AFTER AN ERASE OPERATION, AND A CORRESPONDING MEMORY DEVICE	6/12/2002	10/171,078	11/25/2003	6,654,287	US
NMXS-0756.00/US	Utility - ORG	Issued	MEMORY DEVICE	10/24/2001	10/041,684	5/20/2003	6,567,296	US
NMXS-0757.00/US	Utility - ORG	Issued	WORD LINE SELECTOR FOR A SEMICONDUCTOR MEMORY	2/20/2003	10/372,626	3/8/2005	6,865,114	US
NMXS-0758.00/US	Utility - ORG	Issued	DESIGN FAILURE MODE EFFECT ANALYSIS (DFMEA)	12/26/2002	10/330,485	4/25/2006	7,035,769	US
NMXS-0759.00/US	Utility - ORG	Issued	POWER SUPPLY CIRCUIT STRUCTURE FOR A ROW DECODER OF A MULTILEVEL NON-VOLATILE MEMORY DEVICE	12/30/2002	10/334,126	12/7/2004	6,829,168	US
NMXS-0760.00/US	Utility - ORG	Issued	BINARY ENCODING CIRCUIT	12/20/2002	10/325,707	2/24/2004	6,696,990	US
NMXS-0761.00/US	Utility - ORG	Issued	REGULATION METHOD FOR THE DRAIN, BODY AND SOURCE TERMINALS VOLTAGES IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	12/27/2002	10/331,116	10/26/2004	6,809,961	US

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NMXS-0762.00/US	Utility ORG	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY, AND ARCHITECTURE THEREFOR	9/26/2002	10/259,252	11/9/2004	6,816,407	US
NMXS-0762.01/US	Utility - DIV	Issued	MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS	10/12/2004	10/964,160	11/15/2005	6,965,523	US
NMXS-0763.00/US	Utility - ORG	Issued	ELECTRICALLY-PROGRAMMABLE NON-VOLATILE MEMORY CELL	2/20/2003	10/372,044	4/19/2005	6,882,001	US
NMXS-0764.00/US	Utility - ORG	Issued	DECODING STRUCTURE FOR A MEMORY DEVICE WITH A CONTROL CODE	12/27/2002	10/331,177	10/25/2005	6,958,949	US
NMXS-0765.00/US	Utility - ORG	Issued	SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON-VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD	12/26/2002	10/331,158	11/23/2004	6,822,906	US
NMXS-0766.00/US	Utility - ORG	Issued	PROCESS FOR FABRICATING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	11/14/2002	10/294,999	10/25/2005	6,958,510	US
NMXS-0767.00/US	Utility - ORG	Issued	FINITE STATE MACHINE INTERFACE HAS ARBITRATION STRUCTURE TO STORE COMMAND GENERATED BY INTERNAL CIRCUITS DURING EVALUATION PHASE OF STATE MACHINE FOR FLASH EEPROM DEVICE	12/4/2002	10/309,759	10/16/2007	7,284,144	US
NMXS-0768.00/US	Utility - ORG	Issued	SINGLE SUPPLY VOLTAGE, NONVOLATILE PHASE CHANGE MEMORY DEVICE WITH CASCODED COLUMN SELECTION AND SIMULTANEOUS WORD READ/WRITE OPERATIONS	12/27/2002	10/331,185	6/22/2004	6,754,107	US
NMXS-0769.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	10/7/2002	10/267,033	11/30/2004	6,825,523	US
NMXS-0769.01/US	Utility - DIV	Issued	PROCESS FOR MANUFACTURING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	10/12/2004	10/964,049	10/3/2006	7,115,472	US
NMXS-0770.00/US	Utility - ORG	Issued	ARCHITECTURE FOR A FLASH-EEPROM SIMULTANEOUSLY READABLE IN OTHER SECTORS WHILE ERASING AND/OR PROGRAMMING ONE OR MORE SECTORS	1/10/2003	10/340,207	5/10/2005	6,891,755	US
NMXS-0771.00/US	Utility - ORG	Issued	FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE	10/24/2002	10/281,078	12/27/2005	6,981,107	US
NMXS-0772.00/US	Utility - ORG	Issued	ARCHITECTURE OF A PHASE-CHANGE NONVOLATILE MEMORY ARRAY	12/12/2002	10/319,439	11/9/2004	6,816,404	US
NMXS-0773.00/US	Utility - ORG	Issued	MEMORY SYSTEM COMPRISING A SEMICONDUCTOR MEMORY	12/12/2003	10/735,250	5/22/2007	7,221,602	US
NMXS-0774.00/US	Utility - ORG	Issued	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES WITH ERASING/PROGRAMMING FAILURE, AND RELATIVE NONVOLATILE MEMORY DEVICE	5/15/2003	10/440,043	9/13/2005	6,944,072	US
NMXS-0775.00/US	Utility - ORG	Issued	INTEGRATED RESISTOR, PHASE-CHANGE MEMORY ELEMENT INCLUDING THIS RESISTOR, AND PROCESS FOR THE FABRICATION THEREOF	1/14/2003	10/345,129	9/20/2005	6,946,673	US
NMXS-0776.00/US	Utility - ORG	Issued	METHOD FOR AVOIDING THE EFFECTS OF LACK OF UNIFORMITY IN TRENCH ISOLATED INTEGRATED CIRCUITS	11/29/2001	09/997,227	7/1/2003	6,586,313	US
NMXS-0777.00/US	Utility - ORG	Issued	SMALL AREA CONTACT REGION, HIGH EFFICIENCY PHASE CHANGE MEMORY CELL AND FABRICATION METHOD THEREOF	12/5/2002	10/313,991	6/5/2007	7,227,171	US
NMXS-0778.00/US	Utility - ORG	Issued	PROGRAMMING METHOD OF THE MEMORY CELLS IN A MULTILEVEL NON-VOLATILE MEMORY DEVICE	5/13/2003	10/438,175	7/19/2005	6,920,066	US
NMXS-0779.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE	3/14/2003	10/390,556	12/12/2006	7,149,844	US
NMXS-0780.00/US	Utility - CIP	Issued	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	2/20/2003	10/372,761	5/10/2005	6,891,747	US
NMXS-0780.01/US	Utility - DIV	Issued	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	1/27/2005	11/045,170	8/9/2011	7,993,957	US
NMXS-0782.00/US	Utility - CIP	Issued	SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	2/20/2003	10/371,154	12/6/2005	6,972,430	US
NMXS-0782.01/US	Utility - DIV	Issued	SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	10/24/2005	11/258,340	5/13/2008	7,372,166	US
NMXS-0783.00/US	Utility - CIP	Issued	CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS	2/20/2003	10/372,639	8/16/2005	6,930,913	US

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MTI Docno	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0783.01/US	Utility - DIV	Issued	MANUFACTURING METHOD OF A CONTACT STRUCTURE AND PHASE CHANGE MEMORY CELL WITH ELIMINATION OF DOUBLE CONTACTS	6/20/2006	11/156,989	7/22/2008	7,402,455	US
NMXS-0784.00/US	Utility - ORG	Issued	BASIC STAGE FOR A CHARGE PUMP CIRCUIT	3/28/2003	10/402,852	2/21/2006	7,002,399	US
NMXS-0785.00/US	Utility - ORG	Issued	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY CELL	6/25/2003	10/606,164	4/5/2005	6,876,033	US
NMXS-0786.00/US	Utility - ORG	Issued	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/26/2002	10/331,161	8/8/2006	7,088,614	US
NMXS-0787.00/US	Utility - ORG	Issued	ADJUSTABLE FREQUENCY OSCILLATOR WITH PROGRAMMABLE CALIBRATING CIRCUIT AND RELATED SYSTEM AND METHOD	4/2/2003	10/406,628	4/19/2005	6,882,231	US
NMXS-0788.00/US	Utility - ORG	Issued	TEST STRUCTURE FOR THE MEASUREMENT OF CONTACT TO GATE DISTANCE IN NON-VOLATILE MEMORY DEVICES AND CORRESPONDING TEST METHOD	5/30/2003	10/449,761	6/7/2005	6,903,995	US
NMXS-0789.00/US	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING ELECTRONIC CIRCUITS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	5/1/2003	10/428,338	2/14/2006	6,998,348	US
NMXS 0790.00/US	Utility - ORG	Issued	SINGLE ENDED OUTPUT SENSE AMPLIFIER CIRCUIT WITH REDUCED POWER CONSUMPTION AND NOISE	7/8/2002	10/190,917	11/23/2004	6,822,919	US
NMXS-0791.00/US	Utility - ORG	Issued	REDUNDANCY CIRCUIT AND METHOD FOR SEMICONDUCTOR MEMORY DEVICES	5/31/2002	10/161,501	5/4/2004	6,731,550	US
NMXS-0792.00/US	Utility - ORG	Issued	CIRCUIT FOR CONTROLLING A REFERENCE NODE IN A SENSE AMPLIFIER	12/27/2002	10/331,147	10/5/2004	6,801,466	US
NMXS-0793.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY DEVICE WITH DOUBLE SERIAL/PARALLEL COMMUNICATION INTERFACE	10/15/2002	10/271,352	5/10/2005	6,892,269	US
NMXS-0794.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY WITH SELF-REFRESH CAPABILITY	3/11/2003	10/387,141	5/8/2007	7,216,212	US
NMXS-0796.00/US	Utility - ORG	Issued	MEMORY DEVICE OUTPUTTING READ DATA IN A TIME STARTING FROM A RISING EDGE OF AN EXTERNAL CLOCK THAT IS SHORTER THAN THAT OF KNOWN DEVICES	12/19/2002	10/325,486	1/24/2006	6,990,596	US
NMXS-0797.00/US	Utility - ORG	Issued	DEVICE INTEGRATING A NONVOLATILE MEMORY ARRAY AND A VOLATILE MEMORY ARRAY	2/7/2003	10/360,840	5/23/2006	7,050,322	US
NMXS-0798.00/US	Utility - ORG	Issued	METHOD OF WRITING A GROUP OF DATA BYTES IN A MEMORY AND MEMORY DEVICE	2/21/2003	10/371,221	2/7/2006	6,996,697	US
NMXS-0799.00/US	Utility - ORG	Issued	NONVOLATILE STORAGE DEVICE AND SELF-REDUNDANCY METHOD FOR THE SAME	8/11/2003	10/639,240	4/8/2008	7,355,908	US
NMXS-0800.00/US	Utility - ORG	Issued	BUILT-IN TESTING METHODOLOGY IN FLASH MEMORY	2/27/2004	10/789,443	5/23/2006	7,050,343	US
NMXS-0801.00/US	Utility - ORG	Issued	SECTOR PROTECTION CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	8/2/2001	09/922,043	12/3/2002	6,490,197	US
NMXS-0802.00/US	Utility - ORG	Issued	DUAL BANK FLASH MEMORY DEVICE AND METHOD	8/2/2001	09/922,044	4/22/2003	6,552,935	US
NMXS-0803.00/US	Utility - ORG	Issued	REDUNDANCY CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	8/2/2001	09/922,068	5/13/2003	6,563,732	US
NMXS-0804.00/US	Utility - ORG	Issued	REDUNDANCY CIRCUIT AND METHOD FOR REPLACING DEFECTIVE MEMORY CELLS IN A FLASH MEMORY DEVICE	8/2/2001	09/922,176	7/15/2003	6,594,177	US
NMXS-0805.00/US	Utility - ORG	Issued	CIRCUIT AND ASSOCIATED METHOD FOR THE ERASURE OR PROGRAMMING OF A MEMORY CELL	3/11/2002	10/096,531	9/16/2003	6,621,737	US
NMXS-0806.00/US	Utility - ORG	Issued	EEPROM MEMORY COMPRISING MEANS FOR SIMULTANEOUS READING OF SPECIAL BITS OF A FIRST AND SECOND TYPE	10/21/2002	10/277,183	5/18/2004	6,738,286	US
NMXS-0807.00/US	Utility - ORG	Issued	EEPROM MEMORY PROTECTED AGAINST THE EFFECTS FROM A BREAKDOWN OF AN ACCESS TRANSISTOR	6/24/2002	10/178,796	8/23/2005	6,934,192	US
NMXS-0808.00/US	Utility - ORG	Issued	READ AMPLIFIER WITH A LOW CURRENT CONSUMPTION DIFFERENTIAL OUTPUT STAGE	11/19/2002	10/299,965	7/6/2004	6,760,265	US
NMXS-0809.00/US	Utility - ORG	Issued	METHOD FOR ERASING NON-VOLATILE MEMORY CELLS AND CORRESPONDING MEMORY DEVICE	9/30/2003	10/675,221	2/27/2007	7,184,319	US
NMXS-0810.00/US	Utility - ORG	Issued	NON-VOLATILE LATCH CIRCUIT	5/7/2003	10/434,395	4/18/2006	7,031,189	US
NMXS-0811.00/US	Utility - ORG	Issued	METHOD FOR REDUCING SPURIOUS ERASING DURING PROGRAMMING OF A NONVOLATILE NROM	4/29/2003	10/426,924	11/30/2004	6,826,083	US
NMXS-0812.00/US	Utility - CIP	Issued	METHOD FOR POST ETCH CLEANS	5/1/2002	10/137,096	6/24/2008	7,390,755	US

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NMXS-0813.00/US	Utility - ORG	Issued	REGULATION METHOD FOR THE SOURCE TERMINAL VOLTAGE IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	12/27/2002	10/331,106	11/23/2004	6,822,905	US
NMXS-0815.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURES	7/30/2003	10/631,463	1/16/2007	7,163,898	US
NMXS-0816.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR WITH VERY QUICK RESPONSE	6/26/2003	10/608,998	6/21/2005	6,909,264	US
NMXS-0817.00/US	Utility - ORG	Issued	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	10/7/2003	10/680,727	11/14/2006	7,135,756	US
NMXS-0817.01/US	Utility - DIV	Issued	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	10/19/2006	11/551,170	11/4/2008	7,446,011	US
NMXS-0818.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	10/7/2003	10/680,721	1/24/2006	6,989,580	US
NMXS-0818.01/US	Utility - DIV	Issued	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	11/1/2005	11/264,084	7/21/2009	7,563,684	US
NMXS-0819.00/US	Utility - ORG	Issued	SELF-REPAIR METHOD VIA ECC FOR NONVOLATILE MEMORY DEVICES, AND RELATIVE NONVOLATILE MEMORY DEVICE	4/15/2003	10/417,416	5/31/2005	6,901,011	US
NMXS-0820.00/US	Utility - ORG	Issued	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE, AND NONVOLATILE MEMORY DEVICE	4/24/2003	10/423,845	7/26/2005	6,922,366	US
NMXS-0821.00/US	Utility - ORG	Issued	LINE SELECTOR FOR A MATRIX OF MEMORY ELEMENTS	7/8/2003	10/616,414	8/16/2005	6,930,927	US
NMXS-0822.00/US	Utility - ORG	Issued	MANUFACTURING PROCESS FOR A HIGH VOLTAGE TRANSISTOR INTEGRATED ON A SEMICONDUCTOR SUBSTRATE WITH NON-VOLATILE MEMORY CELLS AND CORRESPONDING TRANSISTOR	9/29/2003	10/675,245	9/27/2005	6,949,803	US
NMXS-0823.00/US	Utility - ORG	Issued	PROCESS FOR MANUFACTURING A BYTE SELECTION TRANSISTOR FOR A MATRIX OF NON VOLATILE MEMORY CELLS AND CORRESPONDING STRUCTURE	11/18/2003	10/715,887	12/6/2005	6,972,454	US
NMXS-0823.01/US	Utility - DIV	Issued	PROCESS FOR MANUFACTURING A BYTE SELECTION TRANSISTOR FOR A MATRIX OF NON VOLATILE MEMORY CELLS AND CORRESPONDING STRUCTURE	10/25/2005	11/258,675	11/25/2008	7,456,467	US
NMXS-0824.00/US	Utility - ORG	Issued	ION-IMPLANTATION MACHINE, CONTROL METHOD THEREOF, AND PROCESS FOR MANUFACTURING INTEGRATED DEVICES	9/8/2003	10/657,801	6/13/2006	7,060,995	US
NMXS-0826.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	12/5/2003	10/729,875	4/18/2006	7,031,193	US
NMXS-0827.00/US	Utility - ORG	Issued	CIRCUIT FOR PROGRAMMING A NON-VOLATILE MEMORY DEVICE WITH ADAPTIVE PROGRAM LOAD CONTROL	11/12/2003	10/706,306	10/18/2005	6,956,773	US
NMXS-0828.00/US	Utility - ORG	Issued	SINGLE CELL ERASING METHOD FOR RECOVERING MEMORY CELLS UNDER PROGRAMMING DISTURBS IN NON VOLATILE SEMICONDUCTOR MEMORY DEVICES	11/26/2003	10/724,022	9/13/2005	6,944,061	US
NMXS-0829.00/US	Utility - ORG	Issued	CIRCUIT FOR BIASING AN INPUT NODE OF A SENSE AMPLIFIER WITH A PRE-CHARGE STAGE	9/16/2003	10/664,606	2/15/2005	6,856,547	US
NMXS-0830.00/US	Utility - ORG	Issued	INTEGRATED RESISTIVE ELEMENTS WITH SILICIDATION PROTECTION	9/26/2003	10/672,293	2/13/2007	7,176,553	US
NMXS-0830.01/US	Utility - DIV	Issued	PROCESS FOR MANUFACTURING INTEGRATED RESISTIVE ELEMENTS WITH SILICIDATION PROTECTION	1/30/2006	11/343,593	7/28/2009	7,566,610	US
NMXS-0831.00/US	Utility - ORG	Issued	SELF-ALIGNED INTEGRATED ELECTRONIC DEVICES	11/24/2003	10/719,538	12/23/2008	7,468,535	US
NMXS-0831.01/US	Utility - DIV	Issued	PROCESS FOR SELF-ALIGNED MANUFACTURE OF INTEGRATED ELECTRONIC DEVICES	1/4/2008	12/006,706	8/10/2010	7,772,084	US
NMXS-0832.00/US	Utility - ORG	Issued	VOLTAGE BOOST DEVICE AND MEMORY SYSTEM	7/7/2003	10/614,693	12/28/2004	6,836,442	US
NMXS-0833.00/US	Utility - ORG	Issued	METHOD OF PROGRAMMING A MULTI-LEVEL, ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	2/19/2004	10/782,725	9/19/2006	7,110,300	US
NMXS-0834.00/US	Utility - ORG	Issued	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	12/18/2003	10/741,815	1/13/2009	7,478,292	US

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NMXS-0834.01/US	Utility DIV	Issued	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	10/14/2008	12/251,289	6/1/2010	7,730,383	US
NMXS-0835.00/US	Utility - ORG	Issued	METHOD FOR CONTROLLING PROGRAMMING VOLTAGE LEVELS OF NON-VOLATILE MEMORY CELLS, THE METHOD TRACKING THE CELL FEATURES, AND CORRESPONDING VOLTAGE REGULATOR	8/28/2003	10/651,019	11/22/2005	6,967,876	US
NMXS-0836.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY SYSTEM INCLUDING SELECTION TRANSISTORS	12/24/2003	10/746,555	4/4/2006	7,023,728	US
NMXS-0837.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR TIMING RANDOM READING OF A MEMORY DEVICE	11/3/2003	10/700,322	10/18/2005	6,956,787	US
NMXS-0838.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH IMPROVED SEQUENTIAL PROGRAMMING SPEED	12/18/2003	10/739,928	9/6/2005	6,940,756	US
NMXS-0839.00/US	Utility - ORG	Issued	MEMORY DEVICE COMPOSED OF A PLURALITY OF MEMORY CHIPS IN A SINGLE PACKAGE	12/3/2003	10/727,150	9/27/2005	6,950,324	US
NMXS-0840.00/US	Utility - ORG	Issued	NONVOLATILE MEMORY DEVICE WITH SIMULTANEOUS READ/WRITE	11/21/2003	10/719,650	9/27/2005	6,950,337	US
NMXS-0842.00/US	Utility - ORG	Issued	NON VOLATILE MEMORY DEVICE INCLUDING A PREDETERMINED NUMBER OF SECTORS	12/30/2003	10/748,696	4/25/2006	7,035,142	US
NMXS-0843.00/US	Utility - ORG	Issued	PROGRAMMING METHOD FOR NON VOLATILE MULTILEVEL MEMORY CELLS AND CORRESPONDING PROGRAMMING CIRCUIT	11/26/2003	10/724,023	8/23/2005	6,934,185	US
NMXS-0844.00/US	Utility - ORG	Issued	STABILIZATION METHOD FOR DRAIN VOLTAGE IN NON-VOLATILE MULTI-LEVEL MEMORY CELLS AND RELATED MEMORY DEVICE	12/30/2003	10/748,701	4/18/2006	7,031,191	US
NMXS-0845.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY WITH ACCESS PROTECTION SCHEME	2/18/2004	10/781,974	7/24/2007	7,249,231	US
NMXS-0849.00/US	Utility ORG	Issued	ANALYSIS OF THE QUALITY OF CONTACTS AND VIAS IN MULTI-METAL FABRICATION PROCESSES OF SEMICONDUCTOR DEVICES, METHOD AND TEST CHIP ARCHITECTURE	5/21/2004	10/850,834	12/4/2007	7,304,485	US
NMXS-0850.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTIVE SUBSTRATE	12/29/2003	10/749,020	10/24/2006	7,125,808	US
NMXS-0851.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTOR SUBSTRATE	12/23/2003	10/746,878	10/24/2006	7,125,807	US
NMXS-0853.00/US	Utility - ORG	Issued	METHOD FOR DETECTING A RESISTIVE PATH OR A PREDETERMINED POTENTIAL IN NON-VOLATILE MEMORY ELECTRONIC DEVICES	9/30/2003	10/675,805	9/20/2005	6,947,329	US
NMXS-0854.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY CELL SENSING CIRCUIT, PARTICULARLY FOR LOW POWER SUPPLY VOLTAGES AND HIGH CAPACITIVE LOAD VALUES	12/4/2003	10/728,372	5/17/2005	6,894,934	US
NMXS-0855.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY WITH EMBEDDED DRAM	11/20/2003	10/720,013	4/11/2006	7,027,317	US
NMXS-0857.00/US	Utility - ORG	Issued	REDUNDANCY SCHEME FOR A MEMORY INTEGRATED CIRCUIT	7/16/2004	10/893,760	12/26/2006	7,154,803	US
NMXS-0858.00/US	Utility - ORG	Issued	FULL-SWING WORDLINE DRIVING CIRCUIT	4/29/2004	10/835,538	4/4/2006	7,023,738	US
NMXS-0859.00/US	Utility - ORG	Issued	METHOD FOR GENERATING A REFERENCE CURRENT FOR SENSE AMPLIFIERS AND CORRESPONDING GENERATOR	6/4/2004	10/861,340	2/28/2006	7,006,025	US
NMXS-0860.00/US	Utility - ORG	Issued	METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	12/5/2003	10/729,829	6/27/2006	7,068,540	US
NMXS-0861.00/US	Utility - ORG	Issued	HIGH-DENSITY PLASMA PROCESS FOR DEPOSITING A LAYER OF SILICON NITRIDE	10/14/2003	10/686,556	10/11/2005	6,953,609	US
NMXS-0862.00/US	Utility - ORG	Issued	SENSE AMPLIFIER FOR LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS	2/12/2004	10/777,457	3/24/2009	7,508,716	US
NMXS-0862.01/US	Utility - CON	Issued	SENSE AMPLIFIER FOR LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS	2/9/2009	12/368,271	2/8/2011	7,885,116	US
NMXS-0863.00/US	Utility - ORG	Issued	VOLTAGE SUPPLY DISTRIBUTION ARCHITECTURE FOR A PLURALITY OF MEMORY MODULES	12/30/2003	10/748,697	5/24/2005	6,897,710	US
NMXS-0864.00/US	Utility - ORG	Issued	NONLITHOGRAPHIC METHOD OF DEFINING GEOMETRIES FOR PLASMA AND/OR ION IMPLANTATION TREATMENTS ON A SEMICONDUCTOR WAFER	3/25/2005	11/089,942	10/30/2007	7,288,008	US
NMXS-0865.00/US	Utility - ORG	Issued	PARALLEL SENSE AMPLIFIER WITH MIRRORING OF THE CURRENT TO BE MEASURED INTO EACH REFERENCE BRANCH	1/20/2004	10/762,195	7/11/2006	7,075,844	US
NMXS-0866.00/US	Utility - ORG	Issued	METHOD FOR THE FABRICATION OF ISOLATION STRUCTURES	8/2/2004	10/909,749	5/8/2007	7,214,596	US
NMXS-0869.00/US	Utility - ORG	Issued	MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL-POLYSILICON LAYER TECHNOLOGY	12/23/2003	10/745,295	4/4/2006	7,023,047	US

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NMXS-0870.00/US	Utility - ORG	Issued	MOS DEVICE AND A PROCESS FOR MANUFACTURING MOS DEVICES USING A DUAL-POLYSILICON LAYER TECHNOLOGY WITH SIDE CONTACT	12/23/2003	10/745,297	8/15/2006	7,091,570	US
NMXS-0871.00/US	Utility - ORG	Issued	FAST READING, LOW CONSUMPTION MEMORY DEVICE AND READING METHOD THEREOF	12/20/2004	11/018,550	4/10/2007	7,203,087	US
NMXS-0872.00/US	Utility - ORG	Issued	METHOD FOR READING A NONVOLATILE MEMORY DEVICE AND NONVOLATILE MEMORY DEVICE IMPLEMENTING THE READING METHOD	4/8/2004	10/820,458	5/30/2006	7,054,197	US
NMXS-0873.00/US	Utility - ORG	Issued	TESTING METHOD AND DEVICE FOR NON-VOLATILE MEMORIES HAVING A LPC (LOW PIN COUNT) COMMUNICATION SERIAL INTERFACE	5/28/2003	10/447,293	8/31/2004	6,785,174	US
NMXS-0874.00/US	Utility - ORG	Issued	DEVICE AND METHOD FOR READING NON-VOLATILE MEMORIES HAVING AT LEAST ONE PSEUDO-PARALLEL COMMUNICATION INTERFACE	5/30/2003	10/452,762	12/13/2005	6,975,559	US
NMXS-0875.00/US	Utility - ORG	Issued	AUTOMATIC DECODING METHOD FOR MAPPING AND SELECTING A NON-VOLATILE MEMORY DEVICE HAVING A LPC SERIAL COMMUNICATION INTERFACE IN THE AVAILABLE ADDRESSING AREA ON MOTHERBOARDS	7/18/2003	10/623,474	6/12/2007	7,231,487	US
NMXS-0876.00/US	Utility - ORG	Issued	STRUCTURE FOR UPDATING A BLOCK OF MEMORY CELLS IN A FLASH MEMORY DEVICE WITH ERASE AND PROGRAM OPERATION REDUCTION	10/15/2003	10/686,552	7/26/2005	6,922,362	US
NMXS-0877.00/US	Utility - ORG	Issued	VOLTAGE REGULATION SYSTEM FOR A MULTIWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY	2/26/2004	10/789,351	11/21/2006	7,139,197	US
NMXS-0878.00/US	Utility - ORG	Issued	GATE VOLTAGE REGULATION SYSTEM FOR A NON VOLATILE MEMORY CELLS PROGRAMMING AND/OR SOFT PROGRAMMING PHASE	2/26/2004	10/788,525	8/1/2006	7,085,163	US
NMXS-0879.00/US	Utility - ORG	Issued	METHOD FOR SOFT-PROGRAMMING AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, AND AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE IMPLEMENTING THE SOFT-PROGRAMMING METHOD	2/17/2004	10/779,856	10/10/2006	7,120,062	US
NMXS-0880.00/US	Utility - ORG	Issued	MEMORY DEVICE ACCESSIBLE WITH DIFFERENT COMMUNICATION PROTOCOLS	9/2/2003	10/653,459	8/9/2005	6,927,991	US
NMXS-0881.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE ARCHITECTURE, FOR INSTANCE A FLASH KIND, HAVING A SERIAL COMMUNICATION INTERFACE	11/26/2003	10/727,341	12/19/2006	7,151,705	US
NMXS-0882.00/US	Utility - ORG	Issued	FAST PAGE PROGRAMMING ARCHITECTURE AND METHOD IN A NON-VOLATILE MEMORY DEVICE WITH AN SPI INTERFACE	12/30/2003	10/748,447	4/26/2005	6,885,584	US
NMXS-0883.00/US	Utility - ORG	Issued	ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING AN INTERNAL SUPPLY VOLTAGE MANAGEMENT DEVICE	4/22/2003	10/420,588	12/7/2004	6,829,169	US
NMXS-0884.00/US	Utility - ORG	Issued	PROGRAMMABLE POR CIRCUIT WITH TWO SWITCHING THRESHOLDS	8/14/2003	10/641,337	5/24/2005	6,897,689	US
NMXS-0885.00/US	Utility - NSPCT	Issued	EEPROM MEMORY COMPRISING A NON-VOLATILE REGISTER INTEGRATED INTO THE MEMORY ARRAY THEREOF	8/21/2003	11/067,345	11/21/2006	7,139,195	US
NMXS-0886.00/US	Utility - ORG	Issued	DOUBLE READ STAGE SENSE AMPLIFIER	4/1/2004	10/816,204	4/18/2006	7,031,212	US
NMXS-0887.00/US	Utility - ORG	Issued	MANUFACTURING PROCESS FOR A FLASH MEMORY AND FLASH MEMORY THUS PRODUCED	1/22/2004	10/763,044	2/27/2007	7,183,160	US
NMXS-0888.00/US	Utility - ORG	Issued	FLASH MEMORY COMPRISING AN ERASE VERIFY ALGORITHM INTEGRATED INTO A PROGRAMMING ALGORITHM	2/26/2004	10/789,449	5/10/2005	6,891,756	US
NMXS-0889.00/US	Utility - ORG	Issued	NEGATIVE VOLTAGE WORD LINE DECODER HAVING COMPACT TERMINATING ELEMENTS	1/20/2004	10/760,631	5/16/2006	7,046,577	US
NMXS-0890.00/US	Utility - ORG	Issued	SECTORED FLASH MEMORY COMPRISING MEANS FOR CONTROLLING AND FOR REFRESHING MEMORY CELLS	2/9/2004	10/775,032	11/15/2005	6,965,526	US
NMXS-0891.00/US	Utility - ORG	Issued	METHOD FOR ERASING/PROGRAMMING A NON-VOLATILE ELECTRICALLY ERASABLE MEMORY	7/31/2004	10/903,927	3/14/2006	7,012,837	US
NMXS-0892.00/US	Utility - ORG	Issued	WORD-PROGRAMMABLE FLASH MEMORY	6/14/2004	10/867,381	7/18/2006	7,079,448	US
NMXS-0893.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING DIFFERENTIAL ISOLATION STRUCTURES IN A SEMICONDUCTOR ELECTRONIC DEVICE AND CORRESPONDING STRUCTURE	7/12/2004	10/890,529	10/26/2010	7,820,504	US
NMXS-0894.00/US	Utility - ORG	Issued	CHARGE PUMP CIRCUIT WITH A BRIEF SETTLING TIME AND HIGH OUTPUT VOLTAGE REGULATION PRECISION	11/5/2004	10/982,528	2/13/2007	7,176,748	US

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MII-DckNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0895.00/US	Utility - ORG	Issued	METHOD FOR REDUCING NON-UNIFORMITY OR TOPOGRAPHY VARIATION BETWEEN AN ARRAY AND CIRCUITRY IN A PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED NON-VOLATILE MEMORY DEVICES	2/16/2005	11/059,294	3/20/2007	7,192,820	US
NMXS-0896.00/US	Utility - ORG	Issued	EXPLOITING A STATISTICAL DISTRIBUTION OF THE VALUES OF AN ELECTRICAL CHARACTERISTIC IN A POPULATION OF AUXILIARY MEMORY CELLS FOR OBTAINING REFERENCE CELLS	12/23/2005	11/318,053	12/8/2009	7,630,263	US
NMXS-0897.00/US	Utility - ORG	Issued	SENSE AMPLIFIER WITH EQUALIZER	8/6/2004	10/913,788	11/14/2006	7,136,305	US
NMXS-0898.00/US	Utility - ORG	Issued	METHOD FOR REDUCING DEFECTS AFTER A METAL ETCHING IN SEMICONDUCTOR DEVICES	12/10/2004	11/009,687	10/30/2007	7,288,427	US
NMXS-0899.00/US	Utility - ORG	Issued	METHOD FOR PERFORMING ERROR CORRECTIONS OF DIGITAL INFORMATION CODIFIED AS A SYMBOL SEQUENCE	3/19/2004	10/805,168	2/5/2008	7,328,397	US
NMXS-0900.00/US	Utility - ORG	Issued	INTEGRATED MEMORY SYSTEM	3/19/2004	10/805,182	6/1/2010	7,730,357	US
NMXS-0901.00/US	Utility - ORG	Issued	PHASE CHANGE MEMORY DEVICE WITH BIASING OF DESELECTED BIT LINES	8/25/2004	10/926,784	8/15/2006	7,092,277	US
NMXS-0902.00/US	Utility - ORG	Issued	MANUFACTURING METHOD FOR NON-ACTIVE ELECTRICALLY STRUCTURES IN ORDER TO OPTIMIZE THE DEFINITION OF ACTIVE ELECTRICALLY STRUCTURES IN AN ELECTRONIC CIRCUIT INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT	8/3/2004	10/911,220	2/21/2006	7,001,800	US
NMXS-0902.01/US	Utility - DIV	Issued	MANUFACTURING METHOD FOR NON-ACTIVE ELECTRICALLY STRUCTURES IN ORDER TO OPTIMIZE THE DEFINITION OF ACTIVE ELECTRICALLY STRUCTURES IN AN ELECTRONIC CIRCUIT INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT	1/19/2006	11/334,988	1/22/2008	7,320,904	US
NMXS-0903.00/US	Utility - ORG	Issued	SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	10/22/2004	10/971,774	7/18/2006	7,078,294	US
NMXS-0904.00/US	Utility - ORG	Issued	SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY	8/6/2004	10/913,128	9/18/2007	7,272,059	US
NMXS-0905.00/US	Utility - ORG	Issued	BIT LINE DISCHARGE CONTROL METHOD AND CIRCUIT FOR A SEMICONDUCTOR MEMORY	10/22/2004	10/971,776	8/14/2007	7,257,039	US
NMXS-0906.00/US	Utility - ORG	Issued	SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY	8/1/2005	11/194,739	2/27/2007	7,184,348	US
NMXS-0908.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/27/2005	11/319,798	9/2/2008	7,419,876	US
NMXS-0910.00/US	Utility - ORG	Issued	DISTRIBUTION OF AN ELECTRIC QUANTITY THROUGH A CIRCUIT	7/20/2005	11/185,905	4/21/2009	7,521,989	US
NMXS-0912.00/US	Utility - ORG	Issued	PAGE BUFFER CIRCUIT AND METHOD FOR A PROGRAMMABLE MEMORY DEVICE	6/24/2005	11/166,354	7/28/2009	7,567,456	US
NMXS-0913.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY DEVICE WITH INFORMATION LOSS SELF-DETECT CAPABILITY	5/1/2006	11/415,879	8/19/2008	7,414,902	US
NMXS-0914.00/US	Utility - ORG	Issued	NONVOLATILE PHASE CHANGE MEMORY DEVICE AND BIASING METHOD THEREFOR	8/2/2005	11/195,359	9/11/2007	7,269,080	US
NMXS-0916.00/US	Utility - ORG	Issued	PHASE CHANGE MEMORY CELL WITH JUNCTION SELECTOR AND MANUFACTURING METHOD THEREOF	12/19/2005	11/312,253	10/14/2008	7,436,692	US
NMXS-0917.00/US	Utility - ORG	Issued	READ/VERIFY CIRCUIT FOR MULTILEVEL MEMORY CELLS WITH RAMP READ VOLTAGE, AND READ/VERIFY METHOD THEREOF	7/8/2005	11/178,240	7/8/2008	7,397,702	US
NMXS-0919.00/US	Utility - ORG	Issued	METHOD OF MAKING A FLOATING GATE NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE WITH IMPROVED CAPACITIVE COUPLING AND DEVICE THUS OBTAINED	12/22/2005	11/317,641	8/30/2011	8,008,701	US
NMXS-0920.00/US	Utility - ORG	Issued	PROGRAMMABLE NAND MEMORY	7/14/2005	11/183,229	6/8/2010	7,733,697	US
NMXS-0921.00/US	Utility - ORG	Issued	DATA CONTROL UNIT CAPABLE OF CORRECTING BOOT ERRORS, AND CORRESPONDING SELF-CORRECTION METHOD	6/9/2005	11/149,948	10/28/2008	7,444,543	US
NMXS-0923.00/US	Utility - ORG	Issued	TRIMMING FUNCTIONAL PARAMETERS IN INTEGRATED CIRCUITS	4/25/2005	11/113,818	5/22/2007	7,221,212	US
NMXS-0924.00/US	Utility - ORG	Issued	METHOD FOR MANUFACTURING ELECTRONIC NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/27/2005	11/319,750	2/5/2008	7,326,615	US

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NMXS-0926.00/US	Utility - ORG	Issued	FLASH MEMORY DEVICE WITH NAND ARCHITECTURE WITH REDUCED CAPACITIVE COUPLING EFFECT	5/31/2006	11/445,491	7/1/2008	7,394,694	US
NMXS-0928.00/US	Utility - ORG	Issued	INTEGRATED ELECTRONIC DEVICE HAVING A LOW VOLTAGE ELECTRIC SUPPLY	4/11/2006	11/401,523	11/10/2009	7,616,515	US
NMXS-0929.00/US	Utility - ORG	Issued	REGULATOR CIRCUITRY AND METHOD	10/27/2003	10/695,294	6/20/2006	7,064,534	US
NMXS-0930.00/US	Utility - ORG	Issued	MAGNITUDE CONTENT ADDRESSABLE MEMORY	10/21/2003	10/690,368	6/12/2007	7,230,839	US
NMXS-0931.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR WITH STRESS MODE	10/21/2003	10/690,332	3/14/2006	7,012,417	US
NMXS-0932.00/US	Utility - ORG	Issued	USER RAM FLASH CLEAR	2/27/2004	10/788,581	2/6/2007	7,173,845	US
NMXS-0933.00/US	Utility - ORG	Issued	RESET INITIALIZATION	11/30/2004	10/999,751	4/24/2007	7,208,987	US
NMXS-0934.00/US	Utility - ORG	Issued	TAMPER MEMORY CELL	2/20/2004	10/783,935	5/29/2007	7,224,600	US
NMXS-0935.00/US	Utility - ORG	Issued	RESET RAMP CONTROL	12/15/2004	11/012,693	8/12/2008	7,411,433	US
NMXS-0936.00/US	Utility - ORG	Issued	ESD BONDING PAD	12/15/2004	11/013,123	2/19/2008	7,333,310	US
NMXS-0937.00/US	Utility - ORG	Issued	VOLTAGE TRANSLATING CONTROL STRUCTURE	12/15/2004	11/012,533	5/6/2008	7,368,947	US
NMXS-0938.00/US	Utility - ORG	Issued	RESET CIRCUIT	12/15/2004	11/012,712	10/2/2007	7,276,948	US
NMXS-0939.00/US	Utility - ORG	Abandoned	SENSE AMPLIFIER FOR READING A CELL OF A NON-VOLATILE MEMORY DEVICE	5/4/2005	11/121,616	1/23/2007	7,167,394	US
NMXS-0940.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR VERIFYING AND EVENTUALLY SUBSTITUTING DEFECTIVE REFERENCE CELLS OF A MEMORY	5/4/2005	11/121,615	2/13/2007	7,177,217	US
NMXS-0941.00/US	Utility - ORG	Issued	CIRCUIT FOR SELECTING/DESELECTING A BITLINE OF A NON-VOLATILE MEMORY	5/3/2005	11/120,766	8/7/2007	7,254,062	US
NMXS-0943.01/US	Utility - CON	Issued	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	2/19/2008	12/033,855	10/13/2009	7,603,593	US
NMXS-0944.00/US	Utility - ORG	Issued	ROW DECODER FOR NAND MEMORIES	8/11/2005	11/202,632	2/20/2007	7,180,786	US
NMXS-0945.00/US	Utility - ORG	Issued	METHOD OF GENERATING AN ENABLE SIGNAL OF A STANDARD MEMORY CORE AND RELATIVE MEMORY DEVICE	7/7/2004	10/886,003	4/14/2009	7,519,751	US
NMXS-0946.00/US	Utility - ORG	Issued	INTEGRATED MEMORY DEVICE WITH MULTI-SECTOR SELECTION COMMANDS	11/8/2004	10/984,372	11/25/2008	7,457,908	US
NMXS-0947.00/US	Utility - ORG	Issued	SYNCHRONOUS MEMORY DEVICE WITH REDUCED POWER CONSUMPTION	5/25/2005	11/138,884	4/29/2008	7,366,012	US
NMXS-0948.00/US	Utility - ORG	Issued	FLASH MEMORY COMPRISING MEANS FOR CHECKING AND REFRESHING MEMORY CELLS IN THE ERASED STATE	6/14/2004	10/867,378	5/23/2006	7,050,335	US
NMXS-0949.00/US	Utility - ORG	Issued	MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD	8/18/2004	10/921,365	6/27/2006	7,068,538	US
NMXS-0950.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	12/9/2004	11/008,586	2/12/2008	7,330,381	US
NMXS-0952.00/US	Utility - ORG	Issued	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION	12/9/2004	11/008,588	10/30/2007	7,290,078	US
NMXS-0952.01/US	Utility - DIV	Issued	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION	9/10/2007	11/852,937	9/7/2010	7,793,033	US
NMXS-0953.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH UNIPOLAR AND BIPOLAR SELECTORS	9/22/2005	11/233,464	1/27/2009	7,483,296	US
NMXS-0954.00/US	Utility - ORG	Issued	ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING A CNAND STRUCTURE AND BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2006	11/401,521	3/9/2010	7,675,788	US
NMXS-0957.00/US	Utility - ORG	Issued	MEMORY DEVICE	10/13/2005	11/249,763	3/27/2007	7,196,943	US
NMXS-0958.00/US	Utility - ORG	Issued	CHARGE-PUMP DEVICE WITH INCREASED CURRENT OUTPUT	11/9/2005	11/270,308	5/12/2009	7,532,060	US
NMXS-0959.00/US	Utility - ORG	Issued	INTEGRATED ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING NAND STRUCTURE	4/11/2006	11/279,384	11/13/2007	7,295,472	US
NMXS-0961.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2006	11/279,378	9/25/2007	7,274,594	US
NMXS-0963.00/US	Utility - ORG	Issued	PROGRAMMING METHOD OF MULTILEVEL MEMORIES AND CORRESPONDING CIRCUIT	10/27/2005	11/261,903	1/8/2008	7,317,637	US
NMXS-0964.00/US	Utility - ORG	Issued	MEMORY DEVICE	10/13/2005	11/250,176	4/1/2008	7,352,645	US
NMXS-0965.00/US	Utility - ORG	Issued	MEMORY DEVICE AND METHOD FOR OPERATING THE SAME WITH HIGH REJECTION OF THE NOISE ON THE HIGH-VOLTAGE SUPPLY LINE	9/30/2005	11/241,729	1/29/2008	7,324,379	US

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NMXS-0966.00/US	Utility - ORG	Issued	ELECTRONIC MEMORY DEVICE HAVING HIGH DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE INTERFERENCE CELL-TO-CELL	12/14/2005	11/300,053	1/15/2008	7,319,604	US
NMXS-0968.00/US	Utility - ORG	Issued	ROW DECODER CIRCUIT AND RELATED SYSTEM AND METHOD	5/15/2006	11/434,564	4/28/2009	7,525,851	US
NMXS-0969.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2006	11/279,381	7/8/2008	7,397,700	US
NMXS-0971.00/US	Utility - ORG	Issued	FLASH MEMORY DEVICE WITH REDUCED DRAIN STRESSES	2/6/2007	11/703,535	5/19/2009	7,535,770	US
NMXS-0972.00/US	Utility - ORG	Issued	REMOVABLE DATA STORAGE DEVICE AND RELATED ASSEMBLING METHOD	1/31/2006	11/344,519	2/2/2010	7,656,676	US
NMXS-0974.00/US	Utility - ORG	Issued	METHOD FOR CONFIGURING A VOLTAGE REGULATOR	11/16/2005	11/280,803	6/17/2008	7,388,793	US
NMXS-0974.01/US	Utility - DIV	Issued	VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	12/26/2007	11/964,250	4/27/2010	7,706,193	US
NMXS-0975.00/US	Utility - ORG	Issued	PROCESS FOR DIGGING A DEEP TRENCH IN A SEMICONDUCTOR BODY AND SEMICONDUCTOR BODY SO OBTAINED	12/28/2006	11/648,838	6/9/2009	7,544,620	US
NMXS-0976.00/US	Utility - ORG	Issued	METHOD AND SYSTEM FOR CONTROLLING MRAM WRITE CURRENT TO REDUCE POWER CONSUMPTION	3/31/2004	10/816,271	9/19/2006	7,110,289	US
NMXS-0977.00/US	Utility - ORG	Issued	MAGNETIC MEMORY CELL WITH PLURAL READ TRANSISTORS	10/31/2003	10/698,747	3/14/2006	7,012,832	US
NMXS-0978.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE THE LATERAL COUPLING EFFECTS BETWEEN MEMORY CELLS	2/6/2006	11/348,513	12/30/2008	7,471,571	US
NMXS-0979.00/US	Utility - ORG	Issued	DUAL RESISTANCE HEATER FOR PHASE CHANGE DEVICES AND MANUFACTURING METHOD THEREOF	12/19/2005	11/312,231	2/1/2011	7,880,123	US
NMXS-0983.00/US	Utility - ORG	Issued	HIGH-VOLTAGE SWITCH WITH LOW OUTPUT RIPPLE FOR NON-VOLATILE FLOATING-GATE MEMORIES	5/19/2006	11/437,405	4/21/2009	7,521,983	US
NMXS-0984.00/US	Utility - ORG	Issued	CHARGE-PUMP TYPE, VOLTAGE-BOOSTING DEVICE WITH REDUCED RIPPLE, IN PARTICULAR FOR NON-VOLATILE FLASH MEMORIES	5/19/2006	11/437,268	5/12/2009	7,532,061	US
NMXS-0985.00/US	Utility - ORG	Issued	PHASE CHANGE MEMORY CELL WITH TUBULAR HEATER AND MANUFACTURING METHOD THEREOF	4/6/2006	11/398,858	10/21/2008	7,439,536	US
NMXS-0986.00/US	Utility - ORG	Issued	ELECTRONIC MEMORY DEVICE HAVING HIGH INTEGRATION DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE COUPLING	12/14/2005	11/300,145	9/22/2009	7,593,247	US
NMXS-0987.00/US	Utility - ORG	Issued	METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND NON-VOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONCTOR	11/20/2006	11/561,799	5/5/2009	7,529,881	US
NMXS-0987.01/US	Utility - DIV	Issued	METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND NON-VOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONCTOR	3/24/2009	12/409,740	1/19/2010	7,649,778	US
NMXS-0988.00/US	Utility - ORG	Issued	VERTICAL MOSFET TRANSISTOR, IN PARTICULAR OPERATING AS A SELECTOR IN NONVOLATILE MEMORY DEVICES	4/26/2006	11/411,982	12/7/2010	7,847,329	US
NMXS-0989.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY IMPLEMENTED WITH LOW-VOLTAGES TRANSISTORS AND RELATED SYSTEM AND METHOD	11/27/2006	11/605,209	8/3/2009	7,499,345	US
NMXS-0990.00/US	Utility - ORG	Issued	CONTROL OF VOLTAGES DURING ERASE AND RE-PROGRAM OPERATIONS OF MEMORY CELLS	1/18/2006	11/334,205	10/30/2007	7,289,368	US
NMXS-0991.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH A RAMP-LIKE VOLTAGE BIASING STRUCTURE BASED ON A CURRENT GENERATOR	1/26/2006	11/340,414	4/15/2008	7,359,246	US
NMXS-0992.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR RETRIEVING DATA STORED IN SEMICONDUCTOR MEMORY CELLS	5/31/2006	11/444,892	1/6/2009	7,474,577	US
NMXS-0992.01/US	Utility - DIV	Issued	CIRCUIT AND METHOD FOR RETRIEVING DATA STORED IN SEMICONDUCTOR MEMORY CELLS	10/9/2008	12/248,843	2/1/2011	7,889,586	US
NMXS-0993.00/US	Utility - ORG	Issued	DATA STORING METHOD FOR A NON-VOLATILE MEMORY CELL ARRAY HAVING AN ERROR CORRECTION CODE	4/25/2006	11/411,010	1/26/2010	7,653,863	US
NMXS-0995.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH A RAMP-LIKE VOLTAGE BIASING STRUCTURE AND REDUCED NUMBER OF REFERENCE CELLS	8/3/2006	11/368,363	6/30/2009	7,554,861	US
NMXS-0996.00/US	Utility - ORG	Issued	METHOD OF MANAGING FAILS IN A NON-VOLATILE MEMORY DEVICE AND RELATIVE MEMORY DEVICE	11/8/2006	11/557,786	8/4/2009	7,571,362	US

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Exhibit A - US Issued Patents

MTI Docket	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0997.00/US	Utility NSPCT	Issued	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/1/2006	11/949,598	12/29/2009	7,639,526	US
NMXS-0998.00/US	Utility - ORG	Issued	FLASH MEMORY DEVICE WITH IMPROVED MANAGEMENT OF PROTECTION INFORMATION	5/10/2006	11/432,301	7/20/2010	7,761,675	US
NMXS-0999.00/US	Utility - ORG	Issued	NAND FLASH MEMORY WITH ERASE VERIFY BASED ON SHORTER EVALUATION TIME	7/28/2006	11/495,886	4/22/2008	7,362,616	US
NMXS-1000.00/US	Utility - ORG	Issued	TRANSISTOR STRUCTURE WITH HIGH INPUT IMPEDANCE AND HIGH CURRENT CAPABILITY	11/27/2006	11/605,190	7/14/2009	7,560,782	US
NMXS-1001.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH TIME-SHIFTING BASED EMULATION OF REFERENCE CELLS	3/2/2006	11/367,707	3/18/2008	7,345,905	US
NMXS-1002.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE FLOATING GATE COUPLING AND MEMORY DEVICE	4/2/2007	11/732,486	3/30/2010	7,688,633	US
NMXS-1003.00/US	Utility - ORG	Issued	NON VOLATILE MEMORY DEVICE ARCHITECTURE AND CORRESPONDING PROGRAMMING METHOD	2/28/2007	11/713,081	1/19/2010	7,649,791	US
NMXS-1004.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH MULTIPLE REFERENCES AND CORRESPONDING CONTROL METHOD	7/27/2006	11/460,531	1/12/2010	7,646,644	US
NMXS-1006.00/US	Utility - ORG	Issued	RAMP GENERATOR AND RELATIVE ROW DECODER FOR FLASH MEMORY DEVICE	5/3/2006	11/381,426	1/22/2008	7,321,512	US
NMXS-1007.00/US	Utility - ORG	Issued	ROW SELECTOR WITH REDUCED AREA OCCUPATION FOR SEMICONDUCTOR MEMORY DEVICES	2/8/2007	11/672,857	6/1/2011	7,965,561	US
NMXS-1008.00/US	Utility - ORG	Issued	BUILT-IN SELF TEST FOR A COUNTER SYSTEM	3/10/2005	11/076,785	12/13/2005	6,975,696	US
NMXS-1009.00/US	Utility - ORG	Issued	READING CIRCUIT AND METHOD FOR A NONVOLATILE MEMORY DEVICE	9/28/2005	11/238,137	7/10/2007	7,242,619	US
NMXS-1009.01/US	Utility - CON	Issued	READING CIRCUIT AND METHOD FOR A NONVOLATILE MEMORY DEVICE	6/8/2007	11/811,394	11/11/2008	7,450,428	US
NMXS-1010.00/US	Utility - ORG	Issued	SELF-ADAPTIVE OUTPUT BUFFER BASED ON CHARGE SHARING	7/7/2006	11/482,524	9/8/2009	7,586,331	US
NMXS-1011.00/US	Utility - ORG	Issued	CIRCUIT FOR GENERATING AN INTERNAL ENABLING SIGNAL FOR AN OUTPUT BUFFER OF A MEMORY	1/20/2006	11/337,030	5/19/2009	7,535,774	US
NMXS-1014.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR SIMULTANEOUSLY PROGRAMMING MEMORY CELLS	4/13/2006	11/279,663	12/4/2007	7,304,896	US
NMXS-1016.00/US	Utility - ORG	Issued	SEQUENTIAL PROGRAM-VERIFY METHOD WITH RESULT BUFFERING	3/29/2005	11/093,012	2/27/2007	7,184,310	US
NMXS-1017.00/US	Utility - ORG	Issued	OPTIMIZING WRITE/ERASE OPERATIONS IN MEMORY DEVICES	1/13/2005	11/035,013	4/22/2008	7,363,421	US
NMXS-1018.00/US	Utility - ORG	Issued	CONTROLLING OPERATION OF FLASH MEMORIES	1/14/2005	11/036,179	11/25/2008	7,457,909	US
NMXS-1026.00/US	Utility - ORG	Issued	MEMORY ARCHITECTURE	9/1/2006	11/469,754	7/28/2009	7,567,475	US
NMXS-1033.00/US	Utility - ORG	Issued	MEMORY ARCHITECURE WITH SERIAL PERIPHERAL INTERFACE	9/8/2006	11/530,199	9/7/2010	7,793,031	US
NMXS-1038.00/US	Utility - ORG	Issued	VOLTAGE REGULATOR OR NON-VOLATILE MEMORIES IMPLEMENTED WITH LOW-VOLTAGE TRANSISTORS	8/24/2007	11/844,470	8/17/2010	7,777,466	US
NMXS-1040.00/US	Utility - ORG	Issued	READING CIRCUIT FOR SEMICONDUCTOR MEMORY	4/27/2007	11/740,941	3/24/2009	7,508,717	US
NMXS-1043.00/US	Utility - ORG	Issued	SENSING CIRCUIT FOR SEMICONDUCTOR MEMORIES	4/24/2007	11/739,167	4/7/2009	7,515,493	US
NMXS-1044.00/US	Utility - ORG	Issued	ELECTRONIC DEVICE CONTAINING SEMICONDUCTOR POLYMERS AND CORRESPONDING MANUFACTURING PROCESS	1/30/2007	11/700,541	10/18/2011	8,039,831	US
NMXS-1046.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY DEVICE WITH A PAGE BUFFER HAVING AN IMPROVED LAYOUT ARRANGEMENT	7/25/2006	11/459,881	8/5/2008	7,408,819	US
NMXS-1047.00/US	Utility - ORG	Issued	REDUCTION OF THE TIME FOR EXECUTING AN EXTERNALLY COMMANDED TRANSFER OF DATA IN AN INTEGRATED DEVICE	3/16/2007	11/687,353	7/28/2009	7,567,107	US
NMXS-1048.00/US	Utility - ORG	Issued	SYNCHONIZATION OF OPERATIONS IN DISTINCT MEMORY PARTITIONS	3/14/2007	11/686,133	4/7/2009	7,515,464	US
NMXS-1050.00/US	Utility - ORG	Issued	OPTIMIZED FLASH MEMORY ACCESS METHOD AND DEVICE	4/13/2007	11/787,101	9/6/2011	8,015,345	US
NMXS-1052.00/US	Utility - ORG	Issued	METHOD AND CIRCUIT FOR PROGRAMMING A MEMORY CELL, IN PARTICULAR OF THE NOR FLASH TYPE	4/16/2008	12/104,118	2/2/2010	7,656,712	US
NMXS-1053.00/US	Utility - ORG	Issued	HIGH VOLTAGE GENERATOR OF THE DAC-CONTROLLED TYPE	8/8/2006	11/463,260	4/27/2010	7,706,160	US

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Exhibit A - US Issued Patents

MTI Docket No.	Matter Type	Matter Status	Title	FileDate	Serial No.	IssueDate	Patent No.	Country
NMXS-1054.00/US	Utility - ORG	Issued	READING METHOD OF A MEMORY DEVICE WITH EMBEDDED ERROR CORRECTING CODE AND MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE	3/1/2007	11/713,376	3/15/2011	7,908,543	US
NMXS-1055.00/US	Utility - ORG	Issued	FAST PROGRAMMING MEMORY DEVICE	5/19/2008	12/123,359	9/13/2011	8,018,771	US
NMXS-1056.00/US	Utility - ORG	Issued	OUTPUT BUFFER	12/13/2006	11/638,321	12/9/2008	7,463,051	US
NMXS-1056.01/US	Utility - DIV	Issued	OUTPUT BUFFER	10/30/2008	12/261,101	9/28/2010	7,804,322	US
NMXS-1062.00/US	Utility - ORG	Issued	REFERENCE CELL LAYOUT WITH ENHANCED RTN IMMUNITY	4/27/2007	11/741,462	6/23/2009	7,551,465	US
NMXS-1066.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE	10/12/2006	11/549,057	1/27/2009	7,483,300	US
NMXS-1067.00/US	Utility - ORG	Issued	METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE	12/8/2006	11/636,382	10/20/2009	7,606,078	US
NMXS-1067.01/US	Utility - DIV	Issued	METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE	9/20/2009	12/556,970	5/17/2011	7,944,751	US
NMXS-1068.00/US	Utility - ORG	Issued	AUTOMATIC REGULATION METHOD FOR THE REFERENCE SOURCES IN A NON-VOLATILE MEMORY DEVICE AND CORRESPONDING MEMORY DEVICE	6/29/2007	11/771,677	7/28/2009	7,567,470	US
NMXS-1070.00/US	Utility - ORG	Issued	METHOD FOR ACCESSING A MULTILEVEL NONVOLATILE MEMORY DEVICE OF THE FLASH NAND TYPE	7/20/2005	11/458,904	6/3/2008	7,382,660	US
NMXS-1071.00/US	Utility - ORG	Issued	CONFIGURATION OF A MULTILEVEL FLASH MEMORY DEVICE	7/28/2006	11/460,777	5/3/2011	7,937,576	US
NMXS-1075.00/US	Utility - ORG	Issued	ELECTRONIC DEVICE COMPRISING NON VOLATILE MEMORY CELLS WITH OPTIMIZED PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD	2/28/2007	11/713,074	3/31/2009	7,512,032	US
NMXS-1079.00/US	Utility - CIP	Issued	SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	7/17/2006	11/457,966	8/12/2008	7,410,872	US
NMXS-1084.00/US	Utility - ORG	Issued	METHOD FOR COMPACTING THE ERASED THRESHOLD VOLTAGE DISTRIBUTION OF FLASH MEMORY DEVICES DURING WRITING OPERATIONS	8/24/2007	11/844,480	5/5/2009	7,529,136	US
NMXS-1085.00/US	Utility - ORG	Issued	CIRCUIT AND METHOD FOR ELECTRICALLY PROGRAMMING A NON-VOLATILE	6/21/2007	11/766,493	3/3/2009	7,499,332	US
NMXS-1089.00/US	Utility - ORG	Issued	METHOD OF MANAGING A MULTILEVEL MEMORY DEVICE AND RELATED DEVICE	4/25/2008	12/109,525	5/4/2010	7,710,772	US
NMXS-1090.00/US	Utility - ORG	Issued	METHOD OF MANAGING A MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS	2/28/2008	12/039,268	8/24/2010	7,782,665	US
NMXS-1091.00/US	Utility - ORG	Issued	MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS AND RELATED METHODS OF MANAGING	11/2/2007	11/934,144	9/29/2009	7,596,023	US
NMXS-1093.00/US	Utility - ORG	Issued	MEMORY DEVICE WITH FAIL SEARCH AND REDUNDANCY	7/20/2007	11/780,581	1/12/2010	7,646,655	US
NMXS-1094.00/US	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE AND METHOD OF HANDLING A DATUM READ FROM A MEMORY CELL	8/3/2007	11/833,400	5/12/2009	7,532,512	US
NMXS-1095.00/US	Utility - ORG	Issued	ADDRESS COUNTER FOR NONVOLATILE MEMORY DEVICE	7/27/2007	11/829,527	7/7/2009	7,558,152	US
NMXS-1104.01/US	Utility - CON	Expired	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	11/23/1987	07/124,440	1/30/1990	4,897,365	US
NMXS-1105.01/US	Utility - DIV	Expired	A METHOD FOR MANUFACTURING MOS/CMOS MONALITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	12/15/1988	07/289,391	11/6/1990	4,968,645	US
NMXS-1106.00/US	Utility - ORG	Expired	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/27/1987	07/054,712	4/18/1989	4,823,175	US
NMXS-1107.00/US	Utility - ORG	Expired	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/22/1987	07/064,480	3/28/1989	4,816,883	US
NMXS-1108.00/US	Utility - ORG	Expired	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	4/28/1988	07/187,581	12/19/1989	4,888,497	US
NMXS-1109.00/US	Utility - ORG	Expired	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/14/1988	07/284,272	11/6/1990	4,968,639	US
NMXS-1110.00/US	Utility - ORG	Expired	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	07/298,487	8/14/1990	4,949,307	US
NMXS-1111.00/US	Utility - ORG	Expired	CMOS VOLTAGE MULTIPLIER	6/28/1989	07/372,493	5/1/1990	4,922,402	US
NMXS-1112.00/US	Utility - ORG	Expired	CMOS LOGIC CIRCUIT FOR HIGH VOLTAGE OPERATION	6/30/1989	07/373,203	9/11/1990	4,956,569	US
NMXS-1113.00/US	Utility - ORG	Expired	FABRICATION OF CMOS DEVICES WITH REDUCED GATE LENGTH	7/18/1989	07/381,283	1/22/1991	4,987,088	US
NMXS-1114.00/US	Utility - ORG	Expired	FABRICATION OF CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTH AND LIGHTLY DOPED DRAIN	7/28/1989	07/386,189	3/5/1991	4,997,782	US

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MTI Docket No.	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1115.00/US	Utility - ORG	Expired	GRIPPER FOR THE ADVANTAGEOUSLY ROBOTIZED HANDLING OF ONE OR MORE SILICON WAFERS AND/OR OF A SUPPORT FOR SUCH WAFERS	12/5/1989	07/446,196	10/8/1991	5,054,834	US
NMXS-1116.00/US	Utility - ORG	Expired	PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	12/27/1989	07/456,782	2/12/1991	4,992,680	US
NMXS-1117.00/US	Utility - ORG	Expired	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/13/1990	07/625,764	12/24/1991	5,075,246	US
NMXS-1118.00/US	Utility - ORG	Expired	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	2/14/1991	07/655,049	3/17/1992	5,097,226	US
NMXS-1119.00/RE	Utility - REIS	Expired	SENSE CIRCUIT FOR READING DATA STORED IN NONVOLATILE MEMORY CELLS	6/8/1995	08/488,718	6/8/1993	RE36,579	US
NMXS-1119.00/US	Utility - ORG	Abandoned	READING CIRCUIT FOR NONVOLATILEMEMORY CELL.	2/19/1991	07/657,083	6/8/1993	5,218,570	US
NMXS-1120.01/US	Utility - CIP	Issued	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	10/19/1993	08/139,800	1/23/1996	5,486,487	US
NMXS-1121.02/US	Utility - CON	Issued	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	12/27/1994	08/364,505	8/12/1997	5,657,484	US
NMXS-1122.00/US	Utility - ORG	Expired	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	4/26/1991	07/691,768	1/12/1993	5,179,300	US
NMXS-1123.00/US	Utility - ORG	Expired	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	7/5/1991	07/725,987	11/30/1993	5,267,202	US
NMXS-1124.00/US	Utility - ORG	Expired	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	10/1/1991	07/769,600	7/27/1993	5,231,051	US
NMXS-1125.01/US	Utility - CON	Expired	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	10/30/1992	07/970,609	12/28/1993	5,274,282	US
NMXS-1126.00/US	Utility - ORG	Abandoned	TWO PHASES SCAN PATH WITH SINGLECLOCK.	10/22/1991	07/781,360	7/6/1993	5,225,724	US
NMXS-1126.01/RE	Utility - REIS	Expired	OPERATIONAL ANALYSIS DEVICE OF THE SCAN PATH TYPE HAVING A SINGLE SCANNING CLOCK AND A SINGLE OUTPUT PHASE FOR AN INTEGRATED CIRCUIT	6/23/1997	08/876,130	7/6/1993	RE36,292	US
NMXS-1127.00/US	Utility - ORG	Expired	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	11/13/1991	07/791,973	1/25/1994	5,282,169	US
NMXS-1128.00/US	Utility - ORG	Expired	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/13/1991	07/791,453	1/4/1994	5,276,644	US
NMXS-1129.00/US	Utility - ORG	Expired	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/12/1991	07/805,118	12/14/1993	5,270,590	US
NMXS-1130.00/US	Utility - ORG	Expired	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/20/1991	07/811,323	2/1/1994	5,283,478	US
NMXS-1131.00/US	Utility - ORG	Expired	MEMORY CELL READING CIRCUIT	12/19/1991	07/810,480	11/2/1993	5,258,959	US
NMXS-1132.00/US	Utility - ORG	Issued	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	5/4/1992	07/878,823	7/5/1994	5,327,379	US
NMXS-1132.01/US	Utility - CIP	Issued	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	7/5/1994	08/270,498	10/24/1995	5,461,713	US
NMXS-1133.00/US	Utility - ORG	Issued	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	7/24/1992	07/919,606	4/18/1995	5,408,148	US
NMXS-1134.00/US	Utility - ORG	Issued	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	8/27/1992	07/936,857	6/14/1994	5,321,317	US
NMXS-1135.00/US	Utility - ORG	Issued	ROW DECODER FOR NAND-TYPE ROM	8/31/1992	07/938,731	9/13/1994	5,347,493	US
NMXS-1136.01/US	Utility - CON	Issued	METHOD OF FORMING HIGH-STABILITY METALLIC CONTACTS IN AN INTEGRATED CIRCUIT WITH ONE OR MORE METALLIZED LAYERS	3/28/1995	08/411,385	2/26/2002	6,350,676	US
NMXS-1137.01/US	Utility - DIV	Issued	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	6/7/1995	08/475,555	12/9/1997	5,696,399	US
NMXS-1137.02/US	Utility - CON	Issued	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	9/6/1995	08/524,080	9/2/1997	5,663,080	US
NMXS-1138.01/US	Utility - CON	Issued	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	10/12/1993	08/135,842	10/11/1994	5,355,333	US
NMXS-1139.00/US	Utility - ORG	Issued	METALLIZATION OVER TUNGSTEN PLUGS	5/26/1993	08/068,139	4/18/1995	5,407,861	US
NMXS-1139.01/US	Utility - CON	Issued	METALLIZATION OVER TUNGSTEN PLUGS	4/18/1995	08/423,397	7/28/1998	5,786,272	US

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MEI Docket No.	Matter Type	Matter Status	Title	File Date	Serial No.	Issue Date	Patent No.	Country
NMXS-1140.00/US	Utility - ORG	Issued	LOW SWITCHING NOISE OUTPUT BUFFER	6/28/1993	08/084,727	5/30/1995	5,420,525	US
NMXS-1141.00/US	Utility - ORG	Issued	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	6/30/1993	08/086,342	8/8/1995	5,440,510	US
NMXS-1142.02/US	Utility - CON	Issued	VOLTAGE REGULATOR FOR MEMORY DEVICE	3/13/1996	08/615,727	1/6/1998	5,706,240	US
NMXS-1143.01/US	Utility - DIV	Issued	A NON-VOLATILE MEMORY IN AN INTEGRATED CIRCUIT	5/23/1995	08/447,772	10/22/1996	5,568,418	US
NMXS-1143.02/US	Utility - CON	Issued	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	8/8/1995	08/469,431	8/25/1998	5,798,279	US
NMXS-1144.00/US	Utility - ORG	Issued	METHOD OF MAKING NOR-TYPE ROM WITH LDD CELLS	6/28/1993	08/084,971	4/18/1995	5,407,852	US
NMXS-1144.02/US	Utility - CON	Issued	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	12/23/1996	08/772,301	8/11/1998	5,793,086	US
NMXS-1145.01/US	Utility - DIV	Issued	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	6/2/1995	08/460,540	5/7/1996	5,515,318	US
NMXS-1145.02/US	Utility - CON	Issued	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	4/1/1997	08/829,935	8/11/1998	5,793,675	US
NMXS-1146.00/US	Utility - ORG	Issued	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	11/17/1993	08/153,690	12/13/1994	5,372,956	US
NMXS-1147.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	1/28/1994	08/189,271	1/14/1997	5,594,677	US
NMXS-1148.00/US	Utility - ORG	Issued	METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS	1/28/1994	08/188,569	3/3/1998	5,724,395	US
NMXS-1149.00/US	Utility - ORG	Issued	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS	2/10/1994	08/195,369	6/10/1997	5,637,520	US
NMXS-1150.00/US	Utility - ORG	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	2/15/1994	08/196,634	11/14/1995	5,466,622	US
NMXS-1150.01/US	Utility - CON	Issued	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	7/13/1995	08/502,329	6/15/1999	5,913,120	US
NMXS-1151.00/US	Utility - ORG	Issued	NONVOLATILE EPROM, EEPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	2/15/1994	08/196,572	3/5/1996	5,497,345	US
NMXS-1152.00/US	Utility - ORG	Issued	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	3/15/1994	08/214,049	4/16/1996	5,508,956	US
NMXS-1153.00/US	Utility - ORG	Issued	METHOD OF READING, ERASING AND PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	3/15/1994	08/212,907	12/24/1996	5,587,946	US
NMXS-1153.01/US	Utility - DIV	Issued	METHOD OF PROGRAMMINING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	6/2/1995	08/458,346	5/27/1997	5,633,823	US
NMXS-1154.00/US	Utility - ORG	Issued	SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS	3/29/1994	08/219,204	11/21/1995	5,469,389	US
NMXS-1155.01/US	Utility - DIV	Issued	METHOD OF EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	5/31/1995	08/454,854	2/18/1997	5,604,699	US
NMXS-1155.02/US	Utility - CON	Issued	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	7/24/1996	08/685,782	1/27/1998	5,712,816	US
NMXS-1157.00/US	Utility - NSPCT	Issued	METHOD AND APPARTUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/9/1992	08/075,543	1/9/1996	5,483,492	US
NMXS-1158.00/US	Utility - ORG	Issued	SUPPLY VOLTAGE DISTRIBUTION SYSTEM WITH REDUCED RESISTANCE FOR SEMICONDUCTOR DEVICES	7/27/2007	11/881,505	9/27/2011	8,027,217	US

PATENT
REEL: 030872 FRAME: 0122

Exhibit B - US Applications

MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-0002.00/RE	Utility - REIS	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	7/13/1992	07/912,867	US
NMXS-0007.00/US	Utility - ORG	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/14/1993	08/166,970	US
NMXS-0011.00/US	Utility - ORG	Abandoned	CONTENT ADDRESSABLE MEMORY	5/31/1990	07/531,011	US
NMXS-0011.01/US	Utility - CON	Abandoned	CONTENT ADDRESSABLE MEMORY	3/15/1994	08/213,474	US
NMXS-0011.02/US	Utility - CON	Abandoned	CONTENT ADDRESSABLE MEMORY	12/6/1994	08/350,516	US
NMXS-0014.01/US	Utility - CON	Abandoned	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	4/20/1992	07/870,878	US
NMXS-0014.02/US	Utility - CON	Abandoned	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	8/2/1993	08/101,281	US
NMXS-0020.01/US	Utility - CON	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	10/20/1992	07/964,103	US
NMXS-0021.00/US	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH INHIBITED TEST MODE ENTRY DURING POWER-UP	8/17/1990	07/570,148	US
NMXS-0026.01/US	Utility - DIV	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	2/12/1992	07/834,632	US
NMXS-0032.00/US	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/14/1990	07/627,823	US
NMXS-0039.00/US	Utility - ORG	Abandoned	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	1/21/1992	07/823,680	US
NMXS-0040.01/US	Utility - DIV	Abandoned	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	9/16/1994	08/307,519	US
NMXS-0042.00/US	Utility - ORG	Abandoned	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/17/1991	07/809,392	US
NMXS-0051.00/US	Utility - ORG	Abandoned	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	3/31/1992	07/860,981	US
NMXS-0057.00/US	Utility - ORG	Abandoned	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	11/2/1992	07/970,266	US
NMXS-0057.01/US	Utility - CON	Abandoned	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	5/9/1994	08/240,091	US
NMXS-0059.00/US	Utility - ORG	Abandoned	INTEGRATED CIRCUIT OUTPUT DRIVER	8/31/1992	07/938,401	US
NMXS-0061.00/US	Utility - ORG	Abandoned	MULTIPLE CLOCKED DYNAMIC SENSE AMPLIFIER	12/22/1992	07/995,580	US
NMXS-0063.00/US	Utility - ORG	Abandoned	LEADFRAME FOR INTEGRATED CIRCUITS	8/31/1992	07/938,396	US
NMXS-0063.02/US	Utility - DIV	Abandoned	LEADFRAME FOR INTEGRATED CIRCUITS	10/7/1994	08/319,799	US
NMXS-0074.00/US	Utility - ORG	Abandoned	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	4/28/1994	08/235,173	US
NMXS-0081.00/US	Utility - ORG	Abandoned	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	11/30/1994	08/347,267	US
NMXS-0088.00/US	Utility - ORG	Abandoned	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/21/1995	08/391,146	US
NMXS-0089.00/US	Utility - ORG	Abandoned	COUNT UNIT FOR NONVOLATILE MEMORIES	12/28/1994	08/365,155	US
NMXS-0091.00/US	Utility - ORG	Abandoned	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	12/28/1994	08/365,284	US
NMXS-0112.00/US	Utility - ORG	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	4/30/1993	08/056,301	US
NMXS-0112.01/US	Utility - CON	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	2/23/1996	08/606,233	US
NMXS-0112.03/US	Utility - CON	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	2/9/1998	09/020,980	US

Exhibit B - US Applications

MTI-DktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-0117.00/US	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	6/30/1993	08/085,980	US
NMXS-0118.00/US	Utility - ORG	Abandoned	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	6/30/1993	08/085,751	US
NMXS-0124.00/US	Utility - ORG	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	7/30/1993	08/100,624	US
NMXS-0124.01/US	Utility - CON	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	7/25/1995	08/507,023	US
NMXS-0128.00/US	Utility - ORG	Abandoned	REDUNDANT LINE DECODER MASTER ENABLE	9/30/1993	08/129,766	US
NMXS-0129.00/US	Utility - ORG	Abandoned	STRUCTURE TO UTILIZE A PARTIALLY FUNCTIONAL CACHE MEMORY BY INVALIDATION OF FAULTY CACHE MEMORY LOCATIONS	11/1/1993	08/146,228	US
NMXS-0144.00/US	Utility - ORG	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/27/1995	08/393,463	US
NMXS-0144.01/US	Utility - CON	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	7/1/1996	08/674,283	US
NMXS-0158.00/US	Utility - ORG	Abandoned	PROGRAMMABLE MEMORY ELEMENT	3/31/1995	08/413,969	US
NMXS-0160.00/US	Utility - ORG	Abandoned	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	4/11/1995	08/419,826	US
NMXS-0161.02/US	Utility - DIV	Abandoned	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	9/27/2000	09/670,723	US
NMXS-0166.00/US	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	11/29/1995	08/563,758	US
NMXS-0175.00/US	Utility - ORG	Abandoned	TWIN-WELL MANUFACTURING PROCESS FOR AN EEPROM INTEGRATED DEVICE WITH REDUCED BODY EFFECT	11/22/1995	08/561,840	US
NMXS-0180.02/US	Utility - DIV	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	7/6/1999	09/347,905	US
NMXS-0181.01/US	Utility - DIV	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC	7/28/1998	09/123,295	US
NMXS-0188.00/US	Utility - ORG	Abandoned	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	2/28/1994	08/202,827	US
NMXS-0188.01/US	Utility - DIV	Abandoned	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	5/25/1995	08/450,087	US
NMXS-0188.02/US	Utility - CON	Abandoned	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	8/24/1995	08/518,959	US
NMXS-0188.03/US	Utility - CON	Abandoned	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	3/26/1997	08/826,269	US
NMXS-0212.00/US	Utility - ORG	Abandoned	CLOCK PULSE EXTENDER MODE FOR CLOCKED MEMORY DEVICES HAVING PRECHARGED DATA PATHS	2/15/1995	08/388,755	US
NMXS-0224.00/US	Utility - ORG	Abandoned	READING CIRCUIT FOR MULTILEVEL NON VOLATILE MEMORY CELL DEVICES	4/1/1996	08/625,895	US
NMXS-0244.00/US	Utility - ORG	Abandoned	SUPPLY VOLTAGES SWITCHES CIRCUIT	12/30/1996	08/775,109	US
NMXS-0249.01/US	Utility - CON	Abandoned	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	12/11/1998	09/210,179	US
NMXS-0256.00/US	Utility - ORG	Abandoned	NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION	1/31/1997	08/792,621	US
NMXS-0256.02/US	Utility - DIV	Abandoned	NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION	6/6/2002	10/165,010	US

PATENT
REEL: 030872 FRAME: 0124

Exhibit B - US Applications

MTI-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-0257.01/US	Utility - DIV	Abandoned	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURINGPROCESS	7/12/2000	09/614,955	US
NMXS-0270.00/US	Utility - ORG	Abandoned	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	12/30/1996	08/775,110	US
NMXS-0287.00/US	Utility - CIP	Abandoned	CONSTANT CURRENT SOURCE WITH REDUCED SENSITIVITY TO SUPPLY VOLTAGE AND PROCESS VARIATION	3/8/1995	08/399,079	US
NMXS-0294.00/US	Utility - ORG	Abandoned	INTEGRATED MEMORY CIRCUIT WITH SEQUENCED BITLINES FOR STRESS TEST	7/31/1995	08/509,196	US
NMXS-0295.00/US	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR TEST MODE ENTRY DURING POWER UP	6/6/1995	08/466,107	US
NMXS-0300.01/US	Utility - DIV	Abandoned	TEST MODE ACTIVATION AND DATA OVERRIDE	12/3/1999	09/454,800	US
NMXS-0307.00/US	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR TRACKING THE START OF A WRITE TO A MEMORY CELL	1/19/1996	08/589,139	US
NMXS-0308.00/US	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL	1/19/1996	08/588,737	US
NMXS-0310.00/US	Utility - ORG	Abandoned	MEMORY ROW SELECTOR HAVING A TEST FUNCTION	1/19/1996	08/589,140	US
NMXS-0313.00/US	Utility - ORG	Abandoned	DEVICE AND METHOD FOR DRIVING A CONDUCTIVE PATH WITH A SIGNAL	1/19/1996	08/587,708	US
NMXS-0321.00/RE	Utility - REIS	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	9/7/2001	09/949,290	US
NMXS-0321.01/US	Utility - CON	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/19/2002	10/078,169	US
NMXS-0321.02/US	Utility - CON	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	8/16/2002	10/222,940	US
NMXS-0321.03/US	Utility - CON	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	3/10/2003	10/385,189	US
NMXS-0321.04/US	Utility - CON	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	8/21/2003	10/645,344	US
NMXS-0321.05/US	Utility - CON	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	3/8/2004	10/796,635	US
NMXS-0321.06/US	Utility - CON	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	9/13/2004	10/939,960	US
NMXS-0321.07/US	Utility - CON	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	3/17/2005	11/083,367	US
NMXS-0333.00/US	Utility - ORG	Abandoned	MOS CAPACITOR WITH WIDE VOLTAGE AND FREQUENCY OPERATING RANGES	7/25/1997	08/900,328	US
NMXS-0393.00/US	Utility - ORG	Abandoned	DEPOSITION METHOD OF A DIELECTRIC STRUCTURE FOR PLANARIZING MEMORY DEVICES	6/30/1998	09/107,535	US

PATENT
REEL: 030872 FRAME: 0125

Exhibit B - US Applications

M.I. DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-0430.01/US	Utility - CON	Abandoned	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	10/22/1998	09/177,324	US
NMXS-0432.00/US	Utility - ORG	Abandoned	PROCESS OF FINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE	4/14/1998	09/060,192	US
NMXS-0432.01/US	Utility - DIV	Abandoned	PROCESS OF FINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE	7/30/1999	09/365,355	US
NMXS-0466.00/US	Utility - ORG	Abandoned	HIGH VOLTAGE REGULATOR AND CORRESPONDING VOLTAGE REGULATION METHOD	11/4/1998	09/186,504	US
NMXS-0479.01/US	Utility - DIV	Abandoned	METHOD FOR EVALUATING AN INTEGRATED ELECTRONIC DEVICE	4/19/2001	09/838,946	US
NMXS-0479.02/US	Utility - CON	Abandoned	METHOD FOR EVALUATING AN INTEGRATED ELECTRONIC DEVICE	5/21/2001	09/862,665	US
NMXS-0492.00/US	Utility - ORG	Abandoned	VSS SWITCHING SCHEME FOR BATTERY BACKED-UP SEMICONDUCTOR DEVICES	10/31/1997	08/962,977	US
NMXS-0523.00/US	Utility - ORG	Abandoned	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	9/29/1999	09/408,157	US
NMXS-0527.00/US	Utility - ORG	Abandoned	METHOD FOR ENHANCING SELECTIVITY BETWEEN A FILM OF A LIGHT-SENSITIVE MATERIAL AND A LAYER TO BE ETCHED IN ELECTRONIC SEMICONDUCTOR DEVICE FABRICATION PROCESSES	6/29/1999	09/342,318	US
NMXS-0568.00/US	Utility - ORG	Abandoned	ESD PROTECTION DEVICE FOR SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURE	7/28/2000	09/627,876	US
NMXS-0608.00/US	Utility - ORG	Abandoned	BIPOLAR TRANSISTOR PRODUCED USING PROCESSES COMPATIBLE WITH THOSE EMPLOYED IN THE MANUFACTURE OF MOS DEVICES	7/20/2000	09/619,720	US
NMXS-0609.00/US	Utility - ORG	Abandoned	NON-VOLATILE MEMORY DEVICE AND MANUFACTURING PROCESS THEREOF	12/6/2000	09/731,065	US
NMXS-0616.00/US	Utility - ORG	Abandoned	LOW RATE REMOVAL ETCH PROCESS IN THE MANUFACTURE OF SEMICONDUCTOR INTEGRATED DEVICES USING A DIELECTRIC FILM DEPOSITION CHAMBER	1/11/2001	09/759,125	US
NMXS-0634.00/US	Utility - ORG	Abandoned	INTEGRATED MOS TRANSISTOR WITH A HIGH THRESHOLD VOLTAGE AND LOW MULTIPLICATION COEFFICIENT	12/14/2000	09/737,842	US
NMXS-0704.00/US	Utility - ORG	Abandoned	PROCESS FOR PRODUCING OPTICALLY ACTIVE TITANIUM ALKOXIDE COMPLEXES	10/31/2001	09/001,918	US
NMXS-0719.00/US	Utility - ORG	Abandoned	METHOD AND DEVICE FOR REDUCING AVERAGE ACCESS TIME OF A NON-VOLATILE MEMORY DURING READING	12/28/2001	10/033,358	US
NMXS-0732.01/US	Utility - DIV	Abandoned	MANUFACTURING PROCESS OF AN INTERPOLY DIELECTRIC STRUCTURE FOR NON-VOLATILE SEMICONDUCTOR INTEGRATED MEMORIES	6/27/2006	11/476,361	US
NMXS-0753.01/US	Utility - CON	Abandoned	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	11/30/2006	11/564,864	US
NMXS-0758.01/US	Utility - DIV	Abandoned	Design failure mode effect analysis (DFMEA)	12/5/2005	11/294,044	US
NMXS-0775.01/US	Utility - DIV	Abandoned	PROCESS FOR MANUFACTUING INTEGRATED RESISTOR AND PHASE-CHANGE MEMORY ELEMENT INCLUDING THIS RESISTOR	8/11/2005	11/201,790	US
NMXS-0780.02/US	Utility - CON	Pending	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	6/10/2011	13/158,291	US
NMXS-0789.01/US	Utility - CON	Abandoned	METHOD FOR MANUFACTURING ELECTRONIC CIRCUITS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	12/6/2005	11/294,763	US
NMXS-0795.00/US	Utility - ORG	Abandoned	MEMORY DEVICE AND METHOD FOR READING SEQUENTIALLY GROUPS OF BITS FROM A MEMORY DEVICE	2/7/2003	10/360,515	US

PATENT
REEL: 030872 FRAME: 0126

Exhibit B - US Applications

MII-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-0814.00/US	Utility - ORG	Abandoned	PROCESS FOR FORMING TRENCHES WITH OBLIQUE PROFILE AND ROUNDED TOP CORNERS	6/27/2003	10/608,855	US
NMXS-0824.01/US	Utility - DIV	Abandoned	ION-IMPLANTATION MACHINE, CONTROL METHOD THEREOF, AND PROCESS FOR MANUFACTURING INTEGRATED DEVICES	6/7/2006	11/449,129	US
NMXS-0841.00/US	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR DETECTING A LEAK OF EXTERNAL AIR INTO A PLASMA REACTOR	8/29/2003	10/652,862	US
NMXS-0846.00/US	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A MEMORY DEVICE HAVING SELECTOR TRANSISTORS FOR STORAGE ELEMENTS AND MEMORY DEVICE FABRICATED THEREBY	4/30/2004	10/836,651	US
NMXS-0848.00/US	Utility - ORG	Abandoned	PROCESS FOR THE FORMATION OF DIELECTRIC ISOLATION STRUCTURES IN SEMICONDUCTOR DEVICES	5/25/2004	10/853,565	US
NMXS-0848.01/US	Utility - DIV	Abandoned	PROCESS FOR THE FORMATION OF DIELECTRIC ISOLATION STRUCTURES IN SEMICONDUCTOR DEVICES	1/16/2008	12/014,883	US
NMXS-0852.00/US	Utility - ORG	Abandoned	NON-VOLATILE MEMORY CELL COMPRISING DIELECTRICLAYERS HAVING A LOW DIELECTRIC CONSTANT AND CORRESPONDING MANUFACTURING PROCESS	12/30/2003	10/749,130	US
NMXS-0867.00/US	Utility - NSPCT	Abandoned	ELEKTONENSPEKTROSKOP MIT EMISSION, DIE DURCH EINEN MONOCHROMATISCHEN ELEKTRONENSTRAHL INDUZIERT WIRD	10/6/2004	10/574,868	US
NMXS-0870.01/US	Utility - DIV	Abandoned	MOS DEVICE AND A PROCESS FOR MANUFACTURING MOS DEVICES USING A DUAL-POLYSILICON LAYER TECHNOLOGY WITH SIDE CONTACT	6/29/2006	11/479,369	US
NMXS-0898.01/US	Utility - DIV	Pending	METHOD FOR REDUCING DEFECTS AFTER A METAL ETCHING IN SEMICONDUCTOR DEVICES	9/14/2007	11/855,229	US
NMXS-0899.01/US	Utility - DIV	Pending	METHOD FOR PERFORMING ERROR CORRECTIONS OF DIGITAL INFORMATION CODIFIED AS A SYMBOL SEQUENCE	12/10/2007	12/001,294	US
NMXS-0903.01/US	Utility - CIP	Abandoned	SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	7/17/2006	11/457,948	US
NMXS-0907.00/US	Utility - ORG	Pending	METHOD OF MAKING A FLOATING-GATE NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE WITH IMPROVED CAPACITIVE COUPLING	12/22/2005	11/317,679	US
NMXS-0909.00/US	Utility - ORG	Abandoned	PROCESS FOR DEFINING INTEGRATED CIRCUITS IN SEMICONDUCTOR ELECTRONIC DEVICES	11/16/2005	11/280,186	US
NMXS-0915.00/US	Utility - ORG	Abandoned	METHOD AND SYSTEM FOR CORRECTING LOW LATENCY ERRORS IN READ AND WRITE NON VOLATILE MEMORIES, PARTICULARLY OF THE FLASH TYPE	6/30/2005	11/173,896	US
NMXS-0918.00/US	Utility - ORG	Abandoned	NONVOLATILE MEMORY HAVING CONDUCTIVE FILM BETWEEN ADJACENT MEMORY CELLS	11/2/2006	11/592,020	US
NMXS-0918.01/US	Utility - DIV	Abandoned	PROCESS FOR MANUFACTURING A NONVOLATILE MEMORY HAVING CONDUCTIVE FILM BETWEEN ADJACENT MEMORY CELLS	5/21/2010	12/785,346	US
NMXS-0919.01/US	Utility - CON	Pending	METHOD OF MAKING A FLOATING GATE NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE WITH IMPROVED CAPACITIVE COUPLING AND DEVICE THUS OBTAINED	8/26/2011	13/219,491	US
NMXS-0922.00/US	Utility - ORG	Abandoned	METHOD AND SYSTEM FOR CORRECTING ERRORS IN ELECTRONIC MEMORY DEVICES	6/29/2005	11/169,497	US

Exhibit B - US Applications

VTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-0927.00/US	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY ELECTRONIC DEVICE INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING DEVICE	12/29/2006	11/618,370	US
NMXS-0927.01/US	Utility - DIV	Pending	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY ELECTRONIC DEVICE INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING DEVICE	5/13/2010	12/779,150	US
NMXS-0933.00/PR	Prov - ORG	Abandoned	RESET INITIALIZATION	12/18/2003	60/530,726	US
NMXS-0934.00/PR	Prov - ORG	Abandoned	TAMPER MEMORY CELL	1/8/2004	60/535,064	US
NMXS-0935.00/PR	Prov - ORG	Completed	RESET RAMP CONTROL	12/18/2003	60/530,727	US
NMXS-0936.00/PR	Prov - ORG	Abandoned	ESD BONDING PAD	12/18/2003	60/530,736	US
NMXS-0937.00/PR	Prov - ORG	Abandoned	VOLTAGE TRANSLATING CONTROL STRUCTURE	12/18/2003	60/530,576	US
NMXS-0938.00/PR	Prov - ORG	Abandoned	RESET CIRCUIT	12/18/2003	60/530,848	US
NMXS-0939.00/RE	Utility - REIS	Abandoned	SENSE AMPLIFIER FOR READING A CELL OF A NON-VOLATILE MEMORY DEVICE	1/23/2009	12/359,221	US
NMXS-0942.00/US	Utility - ORG	Abandoned	MASS MEMORY DEVICE BASED ON A FLASH MEMORY WITH MULTIPLE BUFFERS	6/4/2004	10/861,341	US
NMXS-0943.00/US	Utility - ORG	Abandoned	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	6/14/2005	11/152,675	US
NMXS-0955.00/US	Utility - ORG	Abandoned	PHASE CHANGE MEMORY DEVICE AND MANUFACTURING PROCESS THEREOF	1/23/2006	11/337,787	US
NMXS-0960.00/US	Utility - ORG	Abandoned	EMBEDDED STORAGE DEVICE WITH INTEGRATED DATA-MANAGEMENT FUNCTIONS AND STORAGE SYSTEM INCORPORATING IT	8/16/2005	11/205,766	US
NMXS-0962.00/US	Utility - ORG	Pending	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2006	11/279,385	US
NMXS-0962.01/US	Utility - CON	Pending	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	8/5/2011	13/198,978	US
NMXS-0970.00/US	Utility - ORG	Abandoned	NON-VOLATILE MEMORY ELECTRONIC DEVICE	12/28/2006	11/617,472	US
NMXS-0973.00/US	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A MEMORY WITH LOCAL ELECTRICAL CONTACT BETWEEN THE SOURCE LINE AND THE WELL	1/12/2006	11/331,826	US
NMXS-0979.01/US	Utility - DIV	Pending	DUAL RESISTANCE HEATER FOR PHASE CHANGE DEVICES AND MANUFACTURING METHOD THEREOF	12/28/2010	12/980,141	US
NMXS-0981.00/US	Utility - ORG	Abandoned	PROCESS FOR PHYSICAL VAPOR DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER AND CHAMBER FOR PHYSICAL VAPOR DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER OF A PHASE CHANGE MEMORY DEVICE	4/5/2006	11/398,849	US
NMXS-0982.00/US	Utility - ORG	Abandoned	LOW-RIPPLE BOOSTED VOLTAGE GENERATOR	12/30/2005	11/323,937	US
NMXS-0988.01/US	Utility - CON	Pending	VERTICAL MOSFET TRANSISTOR, IN PARTICULAR OPERATING AS A SELECTOR IN NONVOLATILE MEMORY DEVICES	8/24/2010	12/862,624	US
NMXS-0994.00/US	Utility - ORG	Abandoned	NON VOLATILE MEMORY DEVICE SUPPORTING HIGH-PARALLELISM TEST AT WAFER LEVEL	12/15/2005	11/304,488	US
NMXS-0996.00/RE	Utility - REIS	Pending	METHOD OF MANAGING FAILS IN A NON-VOLATILE MEMORY DEVICE AND RELATIVE MEMORY DEVICE	8/4/2011	13/198,665	US
NMXS-1005.00/US	Utility - ORG	Abandoned	MEMORY DEVICE AND RELATIVE CONTROL METHOD	2/21/2007	11/677,411	US

PATENT
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MTI-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-1012.00/US	Utility - ORG	Abandoned	METHOD AND ARCHITECTURE FOR RESTRICTING ACCESS TO A MEMORY DEVICE	1/19/2006	11/336,411	US
NMXS-1013.00/US	Utility - ORG	Pending	ENHANCED SECURITY MEMORY ACCESS METHOD AND ARCHITECTURE	1/19/2006	11/337,085	US
NMXS-1015.00/US	Utility - ORG	Abandoned	BASIC SEMICONDUCTOR ELECTRONIC CIRCUIT WITH REDUCED SENSITIVITY TO PROCESS VARIATIONS	6/19/2006	11/455,896	US
NMXS-1020.00/US	Utility - ORG	Pending	FLASH MEMORY DEVICE WITH A LOW PIN COUNT (LPC) COMMUNICATION INTERFACE	10/28/2005	11/261,131	US
NMXS-1025.00/US	Utility - ORG	Abandoned	READING METHOD OF A NON-VOLATILE ELECTRONIC DEVICE AND CORRESPONDING DEVICE	5/24/2007	11/753,368	US
NMXS-1031.00/US	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING/ERASING A NON VOLATILE MEMORY CELL DEVICE, IN PARTICULAR FOR FLASH TYPE MEMORIES	3/9/2007	11/684,052	US
NMXS-1032.00/US	Utility - ORG	Abandoned	NON-ACTIVE ELECTRICALLY STRUCTURES OF INTEGRATED ELECTRONIC CIRCUIT	5/29/2007	11/754,494	US
NMXS-1034.00/US	Utility - ORG	Abandoned	CHARGE PUMP SYSTEMS AND METHODS	11/27/2006	11/605,193	US
NMXS-1035.00/US	Utility - ORG	Abandoned	VOLTAGE SWITCHING CIRCUITS AND METHODS	3/21/2007	11/726,707	US
NMXS-1036.00/US	Utility - ORG	Abandoned	ROW SELECTOR FOR A SEMICONDUCTOR MEMORY DEVICE	3/21/2007	11/726,726	US
NMXS-1037.00/US	Utility - ORG	Abandoned	COLUMN DECODING SYSTEM FOR SEMICONDUCTOR MEMORY DEVICES IMPLEMENTED WITH LOW VOLTAGE TRANSISTORS	4/12/2007	11/787,220	US
NMXS-1039.00/US	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY DEVICE	9/27/2006	11/528,500	US
NMXS-1041.00/US	Utility - NSPCT	Pending	SEMICONDUCTOR FIELD-EFFECT TRANSISTOR, MEMORY CELL AND MEMORY DEVICE	12/23/2009	12/293,534	US
NMXS-1042.00/US	Utility - ORG	Abandoned	TEST CARTRIDGE WITH INTERNAL GENERATION OF THE TEST SIGNALS	12/20/2007	11/961,266	US
NMXS-1045.00/US	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING NON VOLATILE MEMORY CELLS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	12/27/2006	11/647,504	US
NMXS-1049.00/US	Utility - ORG	Abandoned	METHOD FOR LOCALLY SUPPRESSING A DISTURBANCE OF A REFERENCE LINE	2/27/2007	11/712,239	US
NMXS-1050.01/US	Utility - CON	Pending	OPTIMIZED FLASH MEMORY ACCESS METHOD AND DEVICE	8/3/2011	13/197,056	US
NMXS-1054.01/US	Utility - CON	Pending	READING METHOD OF A MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE AND MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE	3/14/2011	13/047,678	US
NMXS-1055.01/US	Utility - DIV	Pending	FAST PROGRAMMING MEMORY DEVICE	6/7/2011	13/155,347	US
NMXS-1058.00/US	Utility - ORG	Abandoned	Process for manufacturing an electronic device integrated on semiconductor substrate comprising non volatile floating gate memories and an associated circuitry and corresponding electronic device	2/14/2008	12/070,175	US
NMXS-1060.00/US	Utility - ORG	Abandoned	SEMICONDUCTOR-INTEGRATED ELECTRONIC DEVICE HAVING A PLURALITY OF LEADS	7/6/2007	11/774,416	US
NMXS-1061.00/US	Utility - ORG	Abandoned	MANUFACTURING METHOD OF AN INTEGRATED CIRCUIT FORMED ON A SEMICONDUCTOR SUBSTRATE	9/4/2007	11/899,275	US
NMXS-1065.00/US	Utility - ORG	Abandoned	Process for manufacturing integrated circuits formed on a semiconductor substrate and comprising tungsten layers	3/5/2008	12/074,776	US

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MTI-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS-1069.00/US	Utility - ORG	Allowed	METHOD AND DEVICE FOR DETECTING POSSIBLE CORRUPTION OF SECTOR PROTECTION INFORMATION OF A NON-VOLATILE MEMORY STORED IN AN ON BOARD VOLATILE MEMORY ARRAY AT POWER-ON	3/29/2007	11/693,360	US
NMXS-1071.01/US	Utility - CON	Pending	CONFIGURATION OF A MULTILEVEL FLASH MEMORY DEVICE	3/15/2011	13/048,760	US
NMXS-1072.00/US	Utility - ORG	Abandoned	VOLTAGE REGULATOR MADE OF HIGH VOLTAGE TRANSISTORS	12/3/2007	11/949,517	US
NMXS-1074.00/US	Utility - ORG	Abandoned	METHOD OF PROGRAMMING A FOUR-LEVEL FLASH MEMORY DEVICE AND A RELATED PAGE BUFFER	7/28/2006	11/460,835	US
NMXS-1074.01/US	Utility - DIV	Pending	METHOD OF PROGRAMMING A MULTI-LEVEL MEMORY DEVICE	8/31/2009	12/551,383	US
NMXS-1075.01/US	Utility - CON	Pending	ELECTRONIC DEVICE COMPRISING NON VOLATILE MEMORY CELLS WITH OPTIMIZED PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD	2/19/2009	12/388,656	US
NMXS-1075.02/US	Utility - CON	Pending	ELECTRONIC DEVICE COMPRISING NON VOLATILE MEMORY CELLS WITH OPTIMIZED PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD	3/22/2011	13/053,723	US
NMXS-1076.00/US	Utility - ORG	Abandoned	METHOD OF FIXING READ EVALUATION TIME IN A NON VOLATILE NAND TYPE MEMORY DEVICE	9/13/2007	11/854,713	US
NMXS-1077.00/US	Utility - ORG	Abandoned	PLASMA DEPOSITION PROCESS WITH VARIABLE PROCESS PARAMETERS	11/26/2007	11/944,791	US
NMXS-1078.00/US	Utility - NSPCT	Pending	PHASE CHANGE MEMORY DEVICE	2/22/2010	12/442,392	US
NMXS-1080.00/US	Utility - ORG	Abandoned	MANUFACTURING PROCESS OF AN ORGANIC MASK FOR MICROELECTRONIC INDUSTRY	4/13/2007	11/734,818	US
NMXS-1086.00/US	Utility - ORG	Abandoned	MEMORY DEVICE	8/24/2007	11/895,609	US
NMXS-1097.00/US	Utility - ORG	Pending	NON-VOLATILE MEMORY CIRCUIT, SYSTEM AND METHOD	4/17/2008	12/148,521	US
NMXS-1104.00/US	Utility - ORG	Abandoned	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	10/4/1985	06/784,324	US
NMXS-1105.00/US	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	12/11/1986	06/940,501	US
NMXS-1120.00/US	Utility - ORG	Abandoned	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	3/29/1991	07/678,557	US
NMXS-1121.00/US	Utility - ORG	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	4/24/1991	07/690,495	US
NMXS-1121.01/US	Utility - CON	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	2/9/1993	08/015,307	US
NMXS-1124.00/RE	Utility - REIS	Abandoned	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	7/26/1995	08/507,545	US
NMXS-1124.01/US	Utility - CON	Abandoned	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	1/16/1997	08/784,040	US
NMXS-1125.00/US	Utility - ORG	Abandoned	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	9/27/1991	07/767,141	US
NMXS-1126.00/RE	Utility - REIS	Abandoned	OPERATIONAL ANALYSIS DEVICE OF THE SCAN PATH TYPE HAVING A SINGLE SCANNING CLOCK AND A SINGLE OUTPUT PHASE FOR AN INTEGRATED CIRCUIT	7/6/1995	08/498,856	US
NMXS-1135.01/US	Utility - DIV	Abandoned	ROW DECODER FOR NAND-TYPE ROM	10/26/1995		US
NMXS-1136.00/US	Utility - ORG	Abandoned	PLANARIZED CONTACT WITH A SANDWICH OF TUNGSTEN AND ALUMINIUM.	11/23/1992	07/980,550	US
NMXS-1137.00/US	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	11/23/1992	07/980,453	US
NMXS-1138.00/US	Utility - ORG	Abandoned	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	9/22/1992	07/949,678	US

Exhibit B - US Applications

MTI-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	Country
NMXS 1142.00/US	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	6/28/1993	08/083,377	US
NMXS-1142.01/US	Utility - CON	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	5/23/1995	08/447,736	US
NMXS-1143.00/US	Utility - ORG	Abandoned	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	9/30/1993	08/129,776	US
NMXS-1144.01/US	Utility - DIV	Abandoned	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	1/3/1995	08/367,830	US
NMXS-1145.00/US	Utility - ORG	Abandoned	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH EEPROM MEMORIES	10/21/1993	08/140,629	US
NMXS-1153.02/US	Utility - DIV	Abandoned	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	6/2/1995	08/460,227	US
NMXS-1155.00/US	Utility - ORG	Abandoned	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH EEPROM MEMORIES	10/21/1993	08/140,628	US
NMXS-1158.01/US	Utility - CON	Pending	SUPPLY VOLTAGE DISTRIBUTION SYSTEM WITH REDUCED RESISTANCE FOR SEMICONDUCTOR DEVICES	9/26/2011	13/245,392	US

Exhibit C - Foreign Applications and Patents

MII DktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS 0481.00/CN	Utility - NSPCT	Issued	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	99805467.4	4/19/2006	ZL99805467.4	CN
NMXS-0991.00/CN	Utility - ORG	Issued	A MEMORY DEVICE WITH A RAMP-LIKE VOLTAGE BIASING STRUCTURE BASED ON A CURRENT GENERATOR	1/27/2006	200610059263.5	4/27/2011	ZL200610059263.5	CN
NMXS-0997.00/CN	Utility - NSPCT	Issued	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/1/2006	200680028619.7	3/28/2012	ZL200680028619.7	CN
NMXS-1021.00/CN	Utility - ORG	Pending	METHOD AND DEVICE FOR IRREVERSIBLY PROGRAMMING AND READING NONVOLATILE MEMORY CELLS	9/27/2008	200810148814.4			CN
NMXS-1034.00/CN	Utility - ORG	Issued	ELECTRONIC DEVICE WITH LOW-VOLTAGE TRANSISTOR REALIZING	11/27/2006	200610131005.3	6/15/2011	ZL200610131005.3	CN
NMXS-1041.00/CN	Utility - NSPCT	Issued	SEMICONDUCTOR FIELD-EFFECT TRANSISTOR, MEMORY CELL AND MEMORY DEVICE	3/20/2006	200680005428.7	1/19/2011	ZL200680054287	CN
NMXS-1047.00/CN	Utility - ORG	Abandoned	REDUCTION OF THE TIME FOR EXECUTING AN EXTERNALLY COMMANDED TRANSFER OF DATA IN AN INTEGRATED DEVICE	3/16/2007	200710088583			CN
NMXS-1060.00/CN	Utility - ORG	Pending	SEMICONDUCTOR- INTEGRATED ELECTRONIC DEVICE HAVING A PLURALITY OF LEADS	7/9/2007	200710146438			CN
NMXS-1076.00/CN	Utility - ORG	Abandoned	METHOD OF FIXING READ EVALUATION TIME IN A NON VOLATILE NAND TYPE MEMORY DEVICE	9/13/2007	200710182163			CN
NMXS-1078.00/CN	Utility - NSPCT	Issued	PHASE CHANGE MEMORY DEVICE	7/26/2007	200780017151.6	8/17/2011	ZL200780017151.6	CN
NMXS-1082.00/CN	Utility - ORG	Pending	PHASE CHANGE MEMORY DEVICE FOR MULTIBIT STORAGE	9/8/2008	200810212331.6			CN
NMXS-1085.00/CN	Utility - ORG	Issued	METHOD AND CIRCUIT FOR ELECTRICALLY PROGRAMMING SEMICONDUCTOR MEMORY CELLS	6/21/2007	200710149427.8	11/30/2011	ZL200710149427.8	CN
NMXS-1091.00/CN	Utility - ORG	Pending	MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS AND RELATED METHODS OF MANAGING	11/2/2007	200710169601.5			CN
NMXS-1094.00/CN	Utility - ORG	Pending	NON-VOLATILE MEMORY DEVICE AND METHOD OF HANDLING A DATUM READ FROM A MEMORY CELL	7/27/2007	200710138330.7			CN
NMXS-1158.00/CN	Utility - ORG	Pending	SUPPLY VOLTAGE DISTRIBUTION SYSTEM WITH REDUCED RESISTANCE FOR SEMICONDUCTOR DEVICES	7/27/2007	200710138333.0			CN
NMXS-0001.00/DE	Utility - EPPAT	Abandoned	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/9/1988	88403140.2	4/10/1996	3855197	DE
NMXS-0002.00/DE	Utility - EPPAT	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/9/1988	88403141.0	1/13/1993	3877550	DE
NMXS-0003.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/26/1989	89401183.2	5/10/1993	68910374	DE
NMXS-0004.00/DE	Utility - EPPAT	Lapsed	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/19/1993	93401861.5	2/15/1995	0585150	DE
NMXS-0005.00/DE	Utility - EPPAT	Abandoned	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	7/15/1993	93401836.7	12/28/1994	0581639	DE
NMXS-0006.00/DE	Utility - EPPAT	Lapsed	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	9/14/1993	93402229.4	1/18/1995	0591022	DE
NMXS-0007.00/DE	Utility - EPPAT	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/14/1993	93405029.7	4/3/1996	0604270	DE
NMXS-0008.00/DE	Utility - EPPAT	Abandoned	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/19/1987	87401120.8	3/14/1990	3761932	DE
NMXS-0009.00/DE	Utility - EPPAT	Lapsed	NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401991.0	10/27/1993	3885191	DE
NMXS-0010.00/DE	Utility - EPPAT	Lapsed	NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401990.2	5/26/1993	3881296	DE
NMXS-0011.00/DE	Utility - EPPAT	Lapsed	CONTENT ADDRESSABLE MEMORY	5/23/1991	91304677.7	8/16/2000	69132367	DE
NMXS-0012.00/DE	Utility - EPPAT	Lapsed	REDUNDANCY FOR SERIAL MEMORY	12/21/1990	90314116.6	4/23/1997	69030567	DE
NMXS-0013.00/DE	Utility - EPPAT	Lapsed	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	3/25/1991	91302575.5	12/16/1998	69130622	DE

PATENT
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Exhibit C - Foreign Applications and Patents

MTI DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0014.00/DE	Utility - EPPAT	Lapsed	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/19/1990	90313891.5	4/1/1998	69037198	DE
NMXS-0015.00/DE	Utility - EPPAT	Lapsed	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/16/1991	91309521.2	7/29/1998	69129889	DE
NMXS-0016.00/DE	Utility - EPPAT	Lapsed	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	6/29/1990	90307156.1	1/8/1997	69029634	DE
NMXS-0017.00/DE	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/12/1991	91307425.8	3/19/1997	69125226	DE
NMXS-0018.00/DE	Utility - EPPAT	Lapsed	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	5/31/1991	91304952.4	12/18/1996	69123719	DE
NMXS-0019.00/DE	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	5/31/1991	91304951.6	7/30/1997	69127036	DE
NMXS-0020.00/DE	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307423.3	3/19/1997	69125225	DE
NMXS-0021.00/DE	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307419.1	6/26/1996	69120483	DE
NMXS-0022.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308632.8	6/18/1997	69126589	DE
NMXS-0023.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308633.6	4/8/1998	69129215	DE
NMXS-0024.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	96117267.3	2/18/2004	69133365	DE
NMXS-0024.01/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	91307426.6	5/14/1997	69125073	DE
NMXS-0025.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/21/1991	91309721.8	1/7/1998	69128603	DE
NMXS-0026.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/23/1991	91308634.4	11/27/1996	69123324	DE
NMXS-0027.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/23/1991	91308636.9	5/28/1997	69126268	DE
NMXS-0028.00/DE	Utility - EPPAT	Abandoned	ADDRESS BUFFER CIRCUIT HAVING LATCHING BASED ON TRANSITION	10/21/1991	91309720.0	1/7/1998	69128602	DE
NMXS-0029.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH PRECHARGED REDUNDANCY MULTIPLEXING	12/12/1991	91311569.7	9/11/1996	69122056	DE
NMXS-0031.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/12/1991	91311570.5	9/24/1997	69127748	DE
NMXS-0032.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/12/1991	91311571.3	10/2/1996	69122481	DE
NMXS-0033.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	7/16/1992	92306526.2	3/4/1998	69224565	DE
NMXS-0034.00/DE	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	4/30/1992	92303960.6	10/20/1999	69230159	DE
NMXS-0035.00/DE	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR DUAL PORT MEMORY	4/30/1992	92303958.0	7/22/1998	69226309	DE
NMXS-0036.00/DE	Utility - EPPAT	Abandoned	CACHE TAG PARITY DETECT CIRCUIT	3/27/1992	92302736.1	10/8/1997	69222554	DE
NMXS-0037.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	7/16/1992	92306527.0	3/4/1998	69224566	DE
NMXS-0038.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT DUAL-PORT MEMORY DEVICE HAVING REDUCED CAPACITANCE	7/16/1992	92306528.8	5/20/1998	69225537	DE
NMXS-0039.00/DE	Utility - EPPAT	Abandoned	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	1/20/1993	93300397.2	7/8/1998	69318454	DE
NMXS-0040.00/DE	Utility - EPPAT	Abandoned	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	11/29/1993	93309486.3	6/13/2001	69330335	DE
NMXS-0041.00/DE	Utility - EPPAT	Abandoned	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	12/16/1992	92311510.9	3/3/1999	69228522	DE
NMXS-0042.00/DE	Utility - EPPAT	Abandoned	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/16/1992	92311511.7	4/14/1999	69228919	DE
NMXS-0045.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	12/16/1992	92311514.1	10/28/1998	69227436	DE
NMXS-0046.00/DE	Utility - EPPAT	Abandoned	REDUNDANCY DECODER	1/27/1993	93300560.5	7/22/1998	69319754	DE
NMXS-0049.00/DE	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR	4/29/1993	93303369.8	12/29/1999	69327421	DE

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MII-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0050.00/DE	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE	4/29/1993	93303870.6	10/20/1999	69326793	DE
NMXS-0051.00/DE	Utility - EPPAT	Abandoned	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	3/22/1993	93302156.0	6/20/2001	69330363	DE
NMXS-0052.00/DE	Utility - EPPAT	Abandoned	PARALLELIZED DIFFERENCE FLAG LOGIC	5/19/1993	93303874.7	2/23/2000	69327886	DE
NMXS-0053.00/DE	Utility - EPPAT	Abandoned	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/10/1993	93304489.3	12/20/2000	69329761	DE
NMXS-0059.00/DE	Utility - EPPAT	Issued	INTEGRATED CIRCUIT OUTPUT DRIVER	8/27/1993	93306835.5	3/26/1997	69309196	DE
NMXS-0062.00/DE	Utility - EPPAT	Abandoned	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/21/1993	93310384.8	3/3/1999	69323708	DE
NMXS-0064.00/DE	Utility - EPPAT	Abandoned	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/18/1994	94300188.2	5/10/2000	69424327	DE
NMXS-0065.00/DE	Utility - EPPAT	Abandoned	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/30/1993	93307775.0	3/3/1999	69323681	DE
NMXS-0066.00/DE	Utility - EPPAT	Abandoned	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/27/1993	93306836.3	10/29/1997	69314893	DE
NMXS-0067.00/DE	Utility - EPPAT	Abandoned	TEMPERATURE-COMPENSATED VOLTAGE LEVEL SENSE CIRCUIT	4/26/1994	94303005.6	4/3/2002	69430278	DE
NMXS-0068.00/DE	Utility - EPPAT	Abandoned	ADDRESS BUFFER	4/28/1994	94303082.5	9/22/1999	69420771	DE
NMXS-0071.00/DE	Utility - EPPAT	Abandoned	OUTPUT DRIVER CIRCUIT	7/28/1993	93305947.9	2/24/1999	69323579	DE
NMXS-0072.00/DE	Utility - EPPAT	Abandoned	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	7/27/1994	94305553.3	11/10/1999	69421572	DE
NMXS-0073.00/DE	Utility - EPPAT	Abandoned	TEMPERATURE-STABLE CURRENT SOURCE	6/12/1995	95401363.7	4/8/1998	0687967	DE
NMXS-0074.00/DE	Utility - EPPAT	Lapsed	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	5/31/1993	93830243.7	12/15/2004	69333722	DE
NMXS-0075.00/DE	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/30/1993	93830403.7	12/1/1999	69327164	DE
NMXS-0076.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	9/10/1993	93830365.8	12/2/1998	0643418	DE
NMXS-0077.00/DE	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/30/1993	93830481.3	2/10/1999	69323494	DE
NMXS-0079.00/DE	Utility - EPPAT	Lapsed	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/24/1993	93830464.9	7/28/1999	0654791	DE
NMXS-0080.00/DE	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/7/1993	93830491.2	3/17/1999	0657814	DE
NMXS-0081.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	11/30/1993	93830474.8	8/25/1999	0655743	DE
NMXS-0082.00/DE	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830062.9	7/8/1998	0668563	DE
NMXS-0083.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/9/1993	93830493.8	9/2/1998	0657811	DE
NMXS-0084.00/DE	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/29/1994	94830146.0	8/5/1998	0675440	DE
NMXS-0085.00/DE	Utility - EPPAT	Issued	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/21/1994	94830022.3	10/7/1998	69413793	DE
NMXS-0086.00/DE	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE-MEMORY OUTPUT DATA	2/18/1994	94830069.4	7/7/1999	69419403	DE
NMXS-0087.00/DE	Utility - EPPAT	Abandoned	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/18/1994	94830070.2	5/17/2000	69424523	DE
NMXS-0088.00/DE	Utility - EPPAT	Abandoned	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/18/1994	94830071.0	6/7/2000	69424860	DE
NMXS-0089.00/DE	Utility - EPPAT	Abandoned	COUNT UNIT FOR NONVOLATILE MEMORIES	12/28/1993	93830527.3	7/7/1999	69325587	DE
NMXS-0090.00/DE	Utility - EPPAT	Abandoned	END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES	12/28/1993	93830526.5	3/31/1999	69324258	DE
NMXS-0091.00/DE	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	12/28/1993	93830525.7	7/16/1997	69312305	DE
NMXS-0092.00/DE	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1993	93830489.6	5/27/1998	69318842	DE
NMXS-0093.00/DE	Utility - EPPAT	Abandoned	READING CIRCUIT FOR AN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1994	94830124.7	5/31/2000	69424771	DE
NMXS-0094.00/DE	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/30/1993	93830478.9	9/1/1999	69326248	DE
NMXS-0095.00/DE	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/31/1994	94830032.2	5/23/2001	69427277	DE
NMXS-0096.00/DE	Utility - EPPAT	Abandoned	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/31/1994	94830156.9	7/11/2001	0675504	DE

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Mtr Pckg No	Matter Type	Matter Status	Title	File Date	Serial No	Issue Date	Patent No	Country
NMXS-0098.00/DE	Utility - EPPAT	Issued	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	12/31/1993	93830537.2	6/9/1999	69325277.4	DE
NMXS-0099.00/DE	Utility - EPPAT	Abandoned	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1993	93830482.1	5/10/2000	69328628	DE
NMXS-0100.00/DE	Utility - EPPAT	Abandoned	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1994	94830077.7	9/26/2001	0668593	DE
NMXS-0101.00/DE	Utility - EPPAT	Abandoned	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830540.6	6/23/1999	69325458	DE
NMXS-0102.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	12/31/1993	93830545.5	3/29/2000	69328253	DE
NMXS-0103.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830542.2	6/9/1999	69325278	DE
NMXS-0104.00/DE	Utility - EPPAT	Abandoned	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/29/1993	93830528.1	9/23/1998	0661686	DE
NMXS-0105.00/DE	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/18/1994	94830073.6	7/28/1999	69419723	DE
NMXS-0106.00/DE	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/18/1994	94830074.4	10/20/1999	69421266	DE
NMXS-0107.00/DE	Utility - EPPAT	Abandoned	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH	4/19/1994	94830182.5	7/26/2000	69425367	DE
NMXS-0108.00/DE	Utility - EPPAT	Abandoned	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME	3/28/1994	94830144.5	10/4/2001	69428516	DE
NMXS-0109.00/DE	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830061.1	8/5/1998	0668562	DE
NMXS-0110.00/DE	Utility - EPPAT	Abandoned	REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS	3/28/1994	94830143.7	12/27/2000	69426487	DE
NMXS-0111.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	12/31/1993	93830543.0	7/21/1999	69325714	DE
NMXS-0112.00/DE	Utility - EPPAT	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	4/28/1994	94303084.1	4/7/1999	69417622	DE
NMXS-0113.00/DE	Utility - EPPAT	Abandoned	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/20/1994	94302808.4	11/11/1998	69414450	DE
NMXS-0115.00/DE	Utility - EPPAT	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	6/27/1994	94304643.3	9/8/1999	69420476	DE
NMXS-0117.00/DE	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	6/27/1994	94304644.1	3/14/2001	69426845	DE
NMXS-0118.00/DE	Utility - EPPAT	Abandoned	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	6/27/1994	94304645.8	9/19/2001	69428306	DE
NMXS-0124.00/DE	Utility - EPPAT	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	7/27/1994	94305954.1	9/23/1998	69413478	DE
NMXS-0130.00/DE	Utility - EPPAT	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	9/28/1994	94307070.6	3/20/2002	69430165	DE
NMXS-0131.00/DE	Utility - EPPAT	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	99300541.2	3/6/2002	69430080	DE
NMXS-0131.01/DE	Utility - EPPAT	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	94307068.0	5/31/2000	69424735	DE
NMXS-0138.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/21/1994	94460043.6	5/29/1996	69400219	DE
NMXS-0139.00/DE	Utility - EPPAT	Abandoned	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	5/25/1994	94401162.6	10/4/2001	0626728	DE
NMXS-0140.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/26/1994	94460037.8	12/16/1998	0651394	DE
NMXS-0141.00/DE	Utility - EPPAT	Abandoned	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/21/1994	94470041.8	4/14/1999	0660331	DE
NMXS-0142.00/DE	Utility - EPPAT	Abandoned	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/16/1994	94402912.3	8/21/1996	0660333	DE
NMXS-0144.00/DE	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/23/1995	95470006.8	10/16/1996	0669622	DE
NMXS-0145.00/DE	Utility - EPPAT	Issued	MEMORY REDUNDANCY CIRCUIT	2/27/1995	95400420.6	6/19/1996	0669576	DE
NMXS-0146.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/20/1995	95400608.6	10/6/1999	0675503	DE
NMXS-0147.00/DE	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400190.5	10/16/1996	0666572	DE

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NMXS-0148.00/DE	Utility EPPAT	Abandoned	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400189.7	6/26/1996	0666573	DE
NMXS-0149.00/DE	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400188.9	6/26/1996	0666559	DE
NMXS-0150.00/DE	Utility - EPPAT	Abandoned	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/14/1995	95470014.2	9/18/1996	0678801	DE
NMXS-0151.00/DE	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER CIRCUIT	4/14/1995	95470013.4	6/18/1997	0678868	DE
NMXS-0152.00/DE	Utility - EPPAT	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/6/1995	95400772.0	9/29/1999	0678875	DE
NMXS-0153.00/DE	Utility - EPPAT	Abandoned	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/17/1995	95460007.8	1/22/1997	69500143	DE
NMXS-0154.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/3/1995	95460015.1	8/21/1996	69500023	DE
NMXS-0155.00/DE	Utility - EPPAT	Abandoned	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	7/18/1995	95401709.1	12/18/1996	69500112	DE
NMXS-0156.00/DE	Utility - EPPAT	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/20/1995	95400607.8	6/2/1999	0675441	DE
NMXS-0157.00/DE	Utility - EPPAT	Abandoned	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/7/1994	94830276.5	3/7/2001	0686978	DE
NMXS-0158.00/DE	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY ELEMENT	3/31/1994	94830154.4	6/13/2001	69427461	DE
NMXS-0159.00/DE	Utility - EPPAT	Abandoned	SENSE AMPLIFIER WITH HYSTERESIS	5/3/1994	94830209.6	3/28/2001	69426977	DE
NMXS-0160.00/DE	Utility - EPPAT	Abandoned	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	4/12/1994	94830167.6	3/17/1999	0677869	DE
NMXS-0161.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/30/1994	94830591.7	3/26/2003	69432352.7	DE
NMXS-0162.00/DE	Utility - EPPAT	Abandoned	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	6/10/1994	94830283.1	3/7/2001	69426818	DE
NMXS-0163.00/DE	Utility - EPPAT	Abandoned	METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL	7/18/1994	94830363.1	10/14/1998	69413960	DE
NMXS-0164.00/DE	Utility - EPPAT	Abandoned	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	9/30/1994	94830471.2	12/1/1999	69421925	DE
NMXS-0165.00/DE	Utility - EPPAT	Abandoned	SENSE AMPLIFIER CIRCUIT FOR SEMICONDUCTOR MEMORY DEVICES	4/28/1995	95830166.5	12/12/2001	0740307	DE
NMXS-0168.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS	9/30/1994	94830468.8	12/15/1999	69422174	DE
NMXS-0171.00/DE	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING	4/4/1995	95830133.5	6/27/2001	69521493	DE
NMXS-0173.00/DE	Utility - EPPAT	Abandoned	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	5/19/1995	95830211.9	3/29/2000	69515991	DE
NMXS-0174.00/DE	Utility - EPPAT	Abandoned	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	1/26/1995	95830020.4	4/11/2001	69520659	DE
NMXS-0175.00/DE	Utility - EPPAT	Abandoned	TWIN-WELL MANUFACTURING PROCESS FOR AN EEPROM INTEGRATED DEVICE WITH REDUCED BODY EFFECT	11/24/1994	94830544.6	2/6/2002	0714133	DE
NMXS-0177.00/DE	Utility - EPPAT	Abandoned	BYTE ERASABLE EEPROM FULLY COMPATIBLE WITH A SINGLE POWER SUPPLY FLASH-EPROM PROCESS	9/27/1994	94830459.7	11/28/2001	69429284	DE
NMXS-0179.00/DE	Utility - EPPAT	Abandoned	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	5/5/1995	95830184.8	1/12/2000	69514502	DE
NMXS-0184.00/DE	Utility - EPPAT	Abandoned	CHARGE PUMP VOLTAGE MULTIPLIER CIRCUIT	12/5/1994	94830563.6	6/12/2002	69430806.4	DE
NMXS-0185.00/DE	Utility - EPPAT	Issued	VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS	4/14/1995	95830153.3	9/13/2000	69518826	DE
NMXS-0186.00/DE	Utility - EPPAT	Abandoned	CURRENT DETECTING CIRCUIT	8/3/1995	95830384.7	1/26/2000	69514793	DE
NMXS-0187.00/DE	Utility - EPPAT	Abandoned	HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES	9/29/1995	95830405.7	4/4/2001	69520580	DE
NMXS-0189.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	12/2/1994	94308981.3	9/1/1999	69420389	DE

Exhibit C - Foreign Applications and Patents

MD DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0190.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	12/9/1994	94309218.9	3/24/1999	69417393	DE
NMXS-0194.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	5/24/1995	95303484.0	12/1/1999	69513568	DE
NMXS-0202.00/DE	Utility - EPPAT	Abandoned	CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES	10/27/1995	95307657.7	10/4/2001	69523009	DE
NMXS-0205.00/DE	Utility - EPPAT	Abandoned	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	11/21/1995	95308348.2	2/2/2003	69529557	DE
NMXS-0207.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE	11/28/1995	95308560.2	6/27/2001	69521484	DE
NMXS-0208.00/DE	Utility - EPPAT	Abandoned	OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE	11/28/1995	95308561.0	2/20/2002	69525517	DE
NMXS-0209.00/DE	Utility - EPPAT	Abandoned	ADJUSTABLE CURRENT SOURCE	11/28/1995	95308562.8	10/31/2001	69523547	DE
NMXS-0210.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT	11/28/1995	95308543.8	3/15/2000	69515621	DE
NMXS-0211.00/DE	Utility - EPPAT	Abandoned	DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT	11/28/1995	95308563.6	8/30/2000	69518616	DE
NMXS-0214.00/DE	Utility - EPPAT	Abandoned	INTERNAL BUS CONTROL(FLASH MEMORY DEVICE TEST MODE TO DRIVE AN INTERNAL CONTROLBUS EXTERNALLY)	8/21/1995	95305818.7	11/10/1999	69513250	DE
NMXS-0216.00/DE	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/14/1995	95402815.5	2/25/1998	69501662	DE
NMXS-0217.00/DE	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/11/1995	95402054.1	4/22/1998	0703584	DE
NMXS-0219.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/14/1995	95402820.5	4/22/1998	0718849	DE
NMXS-0220.00/DE	Utility - EPPAT	Abandoned	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/17/1996	96470009.0	4/29/1998	0750244	DE
NMXS-0221.00/DE	Utility - EPPAT	Abandoned	RESISTANCE REFERENCE CIRCUIT	12/21/1995	95402912.0	5/19/1999	0718887	DE
NMXS-0222.00/DE	Utility - EPPAT	Abandoned	DIGITAL RAMP GENERATOR	5/29/1996	96401155.5	4/7/1999	0745996	DE
NMXS-0223.00/DE	Utility - EPPAT	Abandoned	SERIAL DICHOTOMIC METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT IMPLEMENTING SUCH METHOD	1/27/1995	95830023.8	12/12/2001	0724266	DE
NMXS-0225.00/DE	Utility - EPPAT	Abandoned	CIRCUIT FOR READING NON-VOLATILE MEMORIES	8/4/1995	95830357.0	3/28/2001	69520495	DE
NMXS-0226.00/DE	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT	3/23/1995	95830110.3	1/26/2000	0734024	DE
NMXS-0228.00/DE	Utility - EPPAT	Abandoned	MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS	7/28/1995	95830336.4	7/5/2000	0756285	DE
NMXS-0229.00/DE	Utility - EPPAT	Abandoned	THRESHOLD DETECTING DEVICE	8/4/1995	95830360.4	3/28/2001	69520494	DE
NMXS-0230.00/DE	Utility - EPPAT	Abandoned	CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES	7/28/1995	95830335.6	10/11/2000	0756220	DE
NMXS-0231.00/DE	Utility - EPPAT	Abandoned	FLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE	8/2/1995	95830351.3	5/23/2001	0758129	DE
NMXS-0232.00/DE	Utility - EPPAT	Abandoned	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/19/1995	95830253.1	1/26/2000	0750314	DE
NMXS-0233.00/DE	Utility - EPPAT	Abandoned	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	9/29/1995	95830406.5	1/26/2000	69514802	DE
NMXS-0234.00/DE	Utility - EPPAT	Abandoned	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	7/14/1995	95830302.6	1/26/2000	0753859	DE
NMXS-0235.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE	9/29/1995	95830407.3	12/1/1999	69513658	DE
NMXS-0240.00/DE	Utility - EPPAT	Abandoned	UNBALANCED LATCH AND FUSE CIRCUIT INCLUDING THE SAME	7/28/1995	95830337.2	9/24/2003	0756379	DE
NMXS-0243.00/DE	Utility - EPPAT	Issued	PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD	7/31/1995	95830347.1	4/19/2000	0757355	DE
NMXS-0244.00/DE	Utility - EPPAT	Abandoned	SUPPLY VOLTAGES SWITCHES CIRCUIT	6/20/1996	96830358.7	4/24/2002	69620855	DE
NMXS-0247.00/DE	Utility - EPPAT	Abandoned	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	7/24/1995	95830317.4	1/26/2000	0756286	DE

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MII-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS 0248.00/DE	Utility - EPPAT	Abandoned	NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	10/31/1995	95830456.0	3/15/2000	0772282	DE
NMXS-0249.00/DE	Utility - EPPAT	Abandoned	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	11/3/1995	95830466.9			DE
NMXS-0250.00/DE	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH IMPROVED YIELD AND RELIABILITY	9/29/1995	95830408.1	5/22/2002	69526789	DE
NMXS-0253.00/DE	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES	3/29/1996	96830167.1	11/7/2001	69616747	DE
NMXS-0254.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL	12/14/1995	95830520.3	9/13/2000	69518849	DE
NMXS-0259.00/DE	Utility - EPPAT	Abandoned	PROCESS OF FABRICATING TUNNEL-OXIDE NONVOLATILE MEMORY DEVICES	1/31/1996	96830039.2	11/26/2003	0788144	DE
NMXS-0262.00/DE	Utility - EPPAT	Lapsed	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	96937493.3	1/10/2001	69611550	DE
NMXS-0263.00/DE	Utility - EPPAT	Abandoned	CLOCK CIRCUIT FOR READING A MULTILEVEL NON VOLATILE MEMORY CELLS DEVICE	6/28/1996	96830371.9	3/19/2003	69626804	DE
NMXS-0264.00/DE	Utility - EPPAT	Abandoned	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	96937494.1	1/3/2001	69611483	DE
NMXS-0265.00/DE	Utility - EPPAT	Abandoned	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	3/22/1996	96830144.0	6/12/2002	0797145	DE
NMXS-0266.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	5/9/1996	96830267.9	3/19/2003	0806773	DE
NMXS-0268.00/DE	Utility - EPPAT	Abandoned	ERASING METHOD FOR A NON-VOLATILE MEMORY	12/29/1995	95830554.2	5/10/2000	69516883	DE
NMXS-0270.00/DE	Utility - EPPAT	Abandoned	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	4/30/1996	96830245.5	2/26/2003	69626376	DE
NMXS-0273.00/DE	Utility - EPPAT	Abandoned	PROGRAMMABILE DEVICE WITH BASIC MODULES ELECTRICALLY CONNECTED BY FLASH MEMORY CELLS	12/29/1995	95830552.6	5/23/2001	69521051	DE
NMXS-0274.00/DE	Utility - EPPAT	Abandoned	PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS	6/5/1996	96830318.0	3/12/2003	0811986	DE
NMXS-0276.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE	1/31/1997	97830029.1	6/25/2003	69723044	DE
NMXS-0279.00/DE	Utility - EPPAT	Abandoned	COLUMN MULTIPLEXER	5/13/1996	96830275.2	11/12/2008	69630678	DE
NMXS-0284.00/DE	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE HAVING OPTIMIZED MANAGEMENT OF DATA TRANSMISSION LINES	3/20/1996	96830128.3	1/2/2003	69625582	DE
NMXS-0288.00/DE	Utility - EPPAT	Abandoned	CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS	5/8/1996	96830214.9	12/22/1999	69606717	DE
NMXS-0289.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE	12/20/1995	95309306.9	5/14/2003	69530748	DE
NMXS-0291.00/DE	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR BIASING BIT LINES	5/15/1996	96308448.3	2/5/2003	69626067	DE
NMXS-0314.00/DE	Utility - EPPAT	Issued	CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES	8/9/1996	96305856.5	11/28/2001	69617336	DE
NMXS-0316.00/DE	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/6/1996	96470004.1	6/23/1999	0735489	DE
NMXS-0317.00/DE	Utility - EPPAT	Abandoned	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OR NEGATIVE SUPPLY CIRCUIT	6/17/1996	96470011.6	5/20/1998	0757427	DE
NMXS-0318.00/DE	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	9/2/1996	96460031.6	11/11/1998	0762428	DE
NMXS-0319.00/DE	Utility - EPPAT	Abandoned	HIGH VOLTAGE GENERATOR	12/24/1996	96402887.2	3/8/2000	0782243	DE
NMXS-0321.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/17/1997	97460008.0	6/9/1999	0791933	DE
NMXS-0322.00/DE	Utility - EPPAT	Issued	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1/24/1997	97460008.2	12/2/1998	0788233	DE
NMXS-0332.00/DE	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS	6/18/1996	96830346.1	8/27/2003	69629668	DE
NMXS-0334.00/DE	Utility - EPPAT	Abandoned	BIDIRECTIONAL CHARGE PUMP	8/2/1996	96830441.0	4/2/2003	0822556	DE

PATENT
REEL: 030872 FRAME: 0138

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MatterNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0335.00/DE	Utility - EPPAT	Abandoned	BICMOS NEGATIVE CHARGE PUMP	11/14/1996	96830581.3	2/27/2002	0843402	DE
NMXS-0339.00/DE	Utility - EPPAT	Abandoned	HIGH VOLTAGE TOLERANCE OUTPUT STAGE	7/24/1996	96830413.9	10/9/2002	0821484	DE
NMXS-0343.00/DE	Utility - EPPAT	Abandoned	ADDRESS TRANSITION DETECTION CIRCUIT	3/6/1996	96830096.2	9/12/2001	69615149	DE
NMXS-0344.00/DE	Utility - EPPAT	Abandoned	METHOD FOR RECOVERING FAILED MEMORY	3/21/1996	96830136.6	7/3/2002	69622149	DE
NMXS-0346.00/DE	Utility - EPPAT	Abandoned	GAIN MODULATED SENSE AMPLIFIER, PARTICULARLY FOR MEMORY DEVICES	3/29/1996	96830164.8	2/5/2003	69626099	DE
NMXS-0348.00/DE	Utility - EPPAT	Issued	STANDBY VOLTAGE BOOSTING STAGE AND METHOD FOR A MEMORY DEVICE	3/29/1996	96830178.8	10/17/2001	69616019.6	DE
NMXS-0349.00/DE	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER FOR MEMORY DEVICES	3/29/1996	96830179.6	10/17/2001	69616021	DE
NMXS-0354.00/DE	Utility - EPPAT	Abandoned	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	4/18/1996	96830216.6	3/12/2003	0802541	DE
NMXS-0357.00/DE	Utility - EPPAT	Abandoned	CIRCUIT FOR TRANSFERRING REDUNDANCY DATA OF A REDUNDANCY CIRCUIT INSIDE A MEMORY DEVICE BY MEANS OF A TIME-SHARED APPROACH	6/6/1996	96830323.0	1/2/2002	0811917	DE
NMXS-0359.00/DE	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH	6/6/1996	96830324.8	1/30/2002	0811918	DE
NMXS-0360.00/DE	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY	6/6/1996	96830325.5	12/12/2001	0811919	DE
NMXS-0362.00/DE	Utility - EPPAT	Abandoned	READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE	6/18/1996	96830347.9	8/27/2003	69629669	DE
NMXS-0363.00/DE	Utility - EPPAT	Abandoned	MULTILEVEL NON VOLATILE MEMORY DEVICE	8/22/1996	96830455.0	4/9/2003	69627318	DE
NMXS-0366.00/DE	Utility - EPPAT	Abandoned	CONTROL CIRCUIT OF AN OUTPUT BUFFER	9/19/1996	96830475.8	3/19/2003	69626815	DE
NMXS-0372.00/DE	Utility - EPPAT	Abandoned	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	9/30/1996	96830494.9	4/2/2003	69627152	DE
NMXS-0387.00/DE	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	12/5/1996	96830612.6	7/9/2003	69629029	DE
NMXS-0391.00/DE	Utility - EPPAT	Abandoned	VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARY FOR A NONVOLATILE MEMORY	2/28/1997	97830083.3	5/7/2003	69721724	DE
NMXS-0394.00/DE	Utility - EPPAT	Issued	PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED ELECTRONIC MEMORY DEVICES HAVING A VIRTUAL GROUND CELLS MATRIX	8/27/1997	97830427.7	10/15/2008	69739045.4	DE
NMXS-0407.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY WITH INTERNAL REFRESH MEANS	10/21/1997	97460043.9	8/4/1999	0838826	DE
NMXS-0410.00/DE	Utility - EPPAT	Abandoned	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	1/29/1997	97400209.9	10/7/1998	0788047	DE
NMXS-0412.00/DE	Utility - EPPAT	Abandoned	MEMORY WITH IMPROVED READING TIME	10/15/1997	97402429.1	12/11/2002	0838824	DE
NMXS-0416.00/DE	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	11/21/1997	97402807.8	10/20/1999	0849740	DE
NMXS-0417.00/DE	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY	11/21/1997	97402805.0	10/20/1999	0849739	DE
NMXS-0418.00/DE	Utility - EPPAT	Abandoned	MEMORY WITH READ PROTECTED ZONES	11/28/1997	97402869.8	6/9/1999	0851359	DE
NMXS-0427.00/DE	Utility - EPPAT	Abandoned	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	11/5/1997	97470027.0	8/4/1999	0845787	DE
NMXS-0430.00/DE	Utility - EPPAT	Issued	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1998	98903102.6	5/15/2001	0954865	DE
NMXS-0431.00/DE	Utility - EPPAT	Issued	VARIABLE FREQUENCY LOAD PUMP	7/17/1998	98401807.7	1/23/2002	0898356	DE
NMXS-0436.00/DE	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLAITLE MEMORY DEVICES	8/29/1997	97830435.0	11/12/2003	69726136	DE
NMXS-0446.00/DE	Utility - EPPAT	Issued	DECODER FOR ERASING A SINGLE ROW IN A FLASH MEMORY	11/26/1997	97830625.6	6/30/2010	69739922.2	DE
NMXS-0451.00/DE	Utility - EPPAT	Issued	SECTORED SEMICONDUCTOR MEMORY DEVICE WITH CONFIGURABLE MEMORY SECTOR ADDRESS	9/24/1997	97830467.3	3/31/2010	69739825.0	DE
NMXS-0458.00/DE	Utility - EPPAT	Abandoned	SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF	12/22/1997	97830698.4	3/2/2005	0926687	DE
NMXS-0465.00/DE	Utility - EPPAT	Issued	TEMPERATURE CORRELATED VOLTAGE GENERATOR CIRCUIT AND CORRESPONDING VOLTAGE REGULATOR FOR A SINGLE POWER MEMORY CELL, PARTICULARLY OF THE FLASH TYPE	11/5/1997	97830574.6	3/4/2009	69739284.8	DE
NMXS-0466.00/DE	Utility - EPPAT	Abandoned	HIGH VOLTAGE REGULATOR AND CORRESPONDING VOLTAGE REGULATION METHOD	11/5/1997	97830575.3	2/19/2008	69719188	DE
NMXS-0481.00/DE	Utility - EPPAT	Issued	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	99926682.8	4/10/2002	69901259.7	DE

PATENT
REEL: 030872 FRAME: 0139

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MII-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS 0483.00/DE	Utility EPPAT	Issued	METHOD AND CIRCUIT TO SELECT THE STANDARD OR LOW VOLTAGE WORKING RANGE OF A SEMICONDUCTOR NON VOLATILE MEMORY	2/26/1998	04023387.6	12/17/2008	69840370.3	DE
NMXS-0486.00/DE	Utility - EPPAT	Abandoned	METHOD AND A CIRCUIT FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	12/31/1997	69739267.8	2/18/2009	0932203	DE
NMXS-0488.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR THE FABRICATION OF A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	6/30/1998	98830388.9	11/14/2001	0971415	DE
NMXS-0495.00/DE	Utility - EPPAT	Issued	IN-SITU DEPOSITION AND DOPING PROCESS FOR POLYCRYSTALLINE SILICON LAYERS AND THE RESULTING DEVICE	11/14/1997	97830603.3	1/7/2009	69739202.3	DE
NMXS-0505.00/DE	Utility - EPPAT	Abandoned	NON VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING A READ AND/OR WRITE PROTECTABLE AREA AND ELECTRONIC SYSTEM INCLUDINT IT	10/21/1998	98402620.3	6/4/2003	0918336	DE
NMXS-0507.00/DE	Utility - EPPAT	Issued	METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY	9/10/1998	98460036.1	11/15/2000	0903750	DE
NMXS-0510.00/DE	Utility - EPPAT	Issued	RADIO FREQUENCE SIGNAL DETECTOR FOR CONTACT-LESS SMARTCARD	9/17/1998	98402308.6	5/24/2006	0903888	DE
NMXS-0512.00/DE	Utility - EPPAT	Abandoned	SPSK DEMODULATION DEVICE	1/20/1999	99400126.1	6/13/2001	0932283	DE
NMXS-0518.00/DE	Utility - EPPAT	Abandoned	SENSING ARRANGEMENT FOR A MULTILEVEL SEMICONDUCTOR MEMORY DEVICE	8/7/1998	98830491.1	11/2/2005	0978844	DE
NMXS-0524.00/DE	Utility - EPPAT	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/22/1998	98120033.0	2/11/2009	0975020	DE
NMXS-0536.00/DE	Utility - EPPAT	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/23/1998	98830645.2	5/19/2010	69841670.8	DE
NMXS-0538.00/DE	Utility - EPPAT	Abandoned	METHOD FOR CORRECTING ERRORS IN A MULTILEVEL MEMORY WITHOUT ADDITIONAL CELLS	2/25/1999	99830089.0	2/5/2003	69905237.8	DE
NMXS-0551.00/DE	Utility - EPPAT	Issued	CHIP OUTLINE BAND (COB) STRUCTURE FOR INTEGRATED CIRCUITS	1/15/1999	99830007.3	12/1/2010	1020907	DE
NMXS-0554.00/DE	Utility - EPPAT	Issued	PROCESS FOR MANUFACTURING SALICIZED ELECTRONIC DEVICES WITH FEWER MASKS	12/22/1998	98830771.6	8/5/2009	69841040.8	DE
NMXS-0566.00/DE	Utility - EPPAT	Issued	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/21/1999	06012616.6	12/16/2009	69941829.1	DE
NMXS-0566.01/DE	Utility - EPPAT	Issued	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/21/1999	99830235.0	8/9/2006	1047078	DE
NMXS-0583.00/DE	Utility - EPPAT	Issued	MANUFACTURING PROCESS OF INTEGRATED SOI CIRCUIT STRUCUTRES	4/30/1999	99830262.4	2/18/2009	69940422.3	DE
NMXS-0585.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES	5/26/1999	99470014.4	11/22/2000	0962938	DE
NMXS-0592.00/DE	Utility - EPPAT	Abandoned	READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATION VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	6/21/1999	99830382.0	3/5/2003	69905699.3	DE
NMXS-0603.00/DE	Utility - EPPAT	Issued	METHOD FOR PROGRAMMING MULTILEVEL NON-VOLATILE MEMORIES BY APPLYING SEQUENCES OF PULSES WITHOUT VERIFY	8/3/1999	99830501.5	10/26/2005	1074995	DE
NMXS-0606.00/DE	Utility - EPPAT	Issued	METHOD FOR READING DATA FROM A NON-VOLATILE MEMORY DEVICE WITH AUTODETECT BURST MODE READING AND CORRESPONDING READING CIRCUIT	11/25/1999	69940473.8-08	2/25/2009	1103977	DE
NMXS-0608.00/DE	Utility - EPPAT	Issued	VERTICAL BIPOLAR TRANSISTOR WITH HIGH GAIN OBTAINED BY MEANS OF A...	7/21/1999	99830468.7	4/21/2010	69942273.6	DE
NMXS-0614.00/DE	Utility - EPPAT	Issued	MANUFACTURE OF AN HV-MOS TRANSISTOR WITH LOW MULTIPLICATION FACTOR IN A DUAL-GATE CMOS PROCESS	11/19/1999	99830717.7	5/26/2010	69942418.6	DE
NMXS-0619.00/DE	Utility - EPPAT	Issued	EMBEDDED STAGE FOR DETECTING SHORTCIRCUITS BETWEEN WORDLINES OF NON VOLATILE MEMORIES	9/10/1999	99830567.6	11/14/2007	1083575	DE
NMXS-0621.00/DE	Utility - EPPAT	Issued	NON-VOLATILE MEMORY DEVICE WITH BURST MODE READING AND CORRESPONDING READING METHOD	11/25/1999	69940369.3	1/28/2009	1103978	DE

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Mtl-Docl No	MatterType	Matterstatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0631.00/DE	Utility - EPPAT	Issued	MANUFACTURING PROCESS FOR NON-VOLATILE FLOATING GATE MEMORY CELLS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND COMPRISED IN A CELL MATRIX WITH AN ASSOCIATED CONTROL CIRCUITRY	12/6/1999	99830755.7	10/13/2010	1107309	DE
NMXS-0635.00/DE	Utility - EPPAT	Issued	METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY	9/18/2000	00830620.1	3/7/2007	60033818.5	DE
NMXS-0643.00/DE	Utility - EPPAT	Issued	SYNCHRONOUS COUNTER FOR ELECTRONIC MEMORIES	2/14/2000	00830100.4	4/8/2009	1126467	DE
NMXS-0645.00/DE	Utility - EPPAT	Issued	INTERNAL ADDRESSING STRUCTURE OF A SEMICONDUCTOR MEMORY	10/6/2000	60042272.0-08	5/27/2009	1195770	DE
NMXS-0646.00/DE	Utility - EPPAT	Issued	STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE	3/21/2000	0830209.3	12/10/2008	60041037.4	DE
NMXS-0653.00/DE	Utility - EPPAT	Issued	CIRCUITAL STRUCTURE FOR PROGRAMMING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830392.7	7/23/2008	60039587.1	DE
NMXS-0654.00/DE	Utility - EPPAT	Issued	CIRCUITAL STRUCTURE FOR READING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830393.5	12/19/2007	1160795	DE
NMXS-0655.00/DE	Utility - EPPAT	Issued	INTEGRATED DEVICE WITH VOLTAGE SELECTOR	3/29/2000	00830239.0	5/28/2008	60039027.6	DE
NMXS-0663.00/DE	Utility - EPPAT	Abandoned	TEST METHOD AND MEMORY USING AN ADDRESS-DEPENDENT POLINOMINAL FOR GENERATING A SIGNATURE CODE	9/30/1999	99830617.9	12/10/2008	69940061.9	DE
NMXS-0665.00/DE	Utility - EPPAT	Issued	INTERLEAVED DATA PATH AND OUTPUT MANAGEMENT ARCHITECTURE FOR AN INTERLEAVED MEMORY AND LOAD PULSER CIRCUIT FOR OUTPUTTING THE READ DATA	4/17/2000	00830291.1	9/1/2010	60044895.9	DE
NMXS-0667.00/DE	Utility - EPPAT	Issued	REDUNDANCY ARCHITECTURE FOR AN INTERLEAVED MEMORY	3/2/2000	00830158.2	5/26/2004	1130517	DE
NMXS-0669.00/DE	Utility - EPPAT	Issued	ATD GENERATION IN A SYNCHRONOUS MEMORY	4/27/2000	00830313.3	10/28/2009	60043212.2	DE
NMXS-0673.00/DE	Utility - EPPAT	Issued	NEW ARCHITECTURE FOR PAGE MODE IN A NON VOLATILE MEMORY	9/15/2000	00402549.0	7/23/2003	1085520	DE
NMXS-0674.00/DE	Utility - EPPAT	Issued	MEMORY WITH COLUMN REGISTER AND WRITING METHOD	9/5/2000	00402443.6	12/23/2009	60043565.2	DE
NMXS-0677.00/DE	Utility - EPPAT	Issued	PAGE PROGRAMMABLE FLASH MEMORY	11/22/2000	00125553.8	12/21/2011	111162181	DE
NMXS-0678.00/DE	Utility - EPPAT	Issued	METHOD FOR THE CORRECTION OF A BIT IN A STRING OF BITS	11/22/2000	00125557.9	7/29/2009	60042634.3	DE
NMXS-0680.00/DE	Utility - EPPAT	Abandoned	CHARGE PUMP BOOSTER DEVICE WITH TRANSFER AND RECOVERY OF THE CHARGE	2/15/2000	00830105.3	5/3/2006	60027706.2	DE
NMXS-0682.00/DE	Utility - EPPAT	Issued	METHOD AND A CIRCUIT STRUCTURE FOR MODIFYING THE THRESHOLD VOLTAGES OF NON-VOLATILE MEMORY CELLS	7/18/2000	60041050.1-08	12/10/2008	1178492	DE
NMXS-0685.00/DE	Utility - EPPAT	Issued	DIRECT-COMPARISON READING CIRCUIT FOR A NONVOLATILE MEMORY ARRAY	8/16/2000	00830582.3	12/10/2008	60041056.0	DE
NMXS-0691.00/DE	Utility - EPPAT	Issued	A LATERAL DMOS TRANSISTOR	9/21/2000	00830628.4	11/28/2007	1191601	DE
NMXS-0696.00/DE	Utility - EPPAT	Issued	ELECTRICALLY MODIFIABLE, NON-VOLATILE, SEMICONDUCTOR MEMORY WHICH CAN KEEP A DATUM STORED UNTIL AN OPERATION TO MODIFY THE DATUM IS COMPLETED	12/29/2000	60041823.5-08	3/18/2009	1220229	DE
NMXS-0699.00/DE	Utility - EPPAT	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY	10/18/2000	00830671.4	10/6/2010	1198725	DE
NMXS-0706.00/DE	Utility - EPPAT	Issued	METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH PROGRAM AND VERIFY ALGORITHM USING A STAIRCASE VOLTAGE WITH VARYING STEP AMPLITUDE	4/10/2001	01830247.1	8/26/2009	60139670.7	DE
NMXS-0710.00/DE	Utility - EPPAT	Issued	SEMICONDUCTOR MEMORY SYSTEM	5/30/2001	60141200.1	1/27/2010	EP1262995	DE
NMXS-0717.00/DE	Utility - EPPAT	Issued	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL NONVOLATILE MEMORY CELL	1/15/2001	01830017.8	8/8/2007	1225595	DE
NMXS-0718.00/DE	Utility - EPPAT	Abandoned	METHOD FOR STORING DATA IN A NONVOLATILE MEMORY	12/29/2000	60041199	12/24/2008	1220228	DE
NMXS-0721.00/DE	Utility - EPPAT	Issued	READING CIRCUIT AND METHOD FOR A MULTILEVEL NON-VOLATILE MEMORY	4/10/2001	01830248.9	10/29/2008	60136330.2	DE
NMXS-0730.00/DE	Utility - EPPAT	Issued	METHOD AND CIRCUIT FOR GENERATING REFERENCE VOLTAGES FOR READING A MULTILEVEL MEMORY CELL	4/27/2001	01830276.0	11/5/2008	60136440.6	DE
NMXS-0733.00/DE	Utility - EPPAT	Issued	MANUFACTURING PROCESS OF A SEMICONDUCTOR NON-VOLATILE MEMORY CELL	6/28/2002	02014408.5	4/9/2008	1324393	DE
NMXS-0735.00/DE	Utility - EPPAT	Issued	LOW POWER CHARGE PUMP CIRCUIT	11/9/2001	01830695.1	6/18/2008	60134477.4	DE
NMXS-0738.00/DE	Utility - EPPAT	Issued	INTERLACED MEMORY DEVICE WITH RANDOM OR SEQUENTIAL ACCESS	10/18/2000	00830675.5	12/31/2008	60041263.6	DE

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Mtr-DCktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0740.00/DE	Utility - EPPAT	Issued	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/27/2001	01130830.8	3/3/2004	601.02212.2	DE
NMXS-0742.00/DE	Utility - EPPAT	Issued	CHARGE PUMP FOR A NONVOLATILE MEMORY WITH READ VOLTAGE REGULATION IN THE PRESENCE OF ADDRESS SKEW, AND NONVOLATILE MEMORY COMPRISING SUCH A CHARGE PUMP	2/6/2001	01830070.7	5/21/2008	60134115.5	DE
NMXS-0753.00/DE	Utility - EPPAT	Issued	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	2/14/2002	02706857.6	5/11/2005	1368784	DE
NMXS-0754.00/DE	Utility - EPPAT	Abandoned	FLASH EEPROM AND EPROM ARRAYS WITH SELECT TRANSISTORS WITHIN THE BIT LINE PITCH	3/10/1995	95301607.8	8/14/2002	69527734	DE
NMXS-0768.00/DE	Utility - EPPAT	Issued	ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELL	2/20/2002	02425085.4	5/14/2008	60226571.1	DE
NMXS-0771.00/DE	Utility - EPPAT	Issued	FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE	10/25/2001	01830671.2	10/3/2007	1308964	DE
NMXS-0772.00/DE	Utility - EPPAT	Issued	ARCHITECTURE OF A PHASE-CHANGE NONVOLATILE MEMORY ARRAY	12/27/2001	01830806.4	2/25/2009	1326254	DE
NMXS-0774.00/DE	Utility - EPPAT	Issued	SELF-REPAIR METHOD FOR NON VOLATILE MEMORY DEVICE WITH ERASING/PROGRAMMING FAILURE DETECTION, AND NON VOLATILE MEMORY DEVICE THEREFOR	5/21/2002	02425319.7	12/31/2008	60230592.6	DE
NMXS-0777.00/DE	Utility - EPPAT	Issued	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	2/20/2002	02425087.0	5/28/2008	60226839.7	DE
NMXS-0779.00/DE	Utility - EPPAT	Issued	A NON-VOLATILE MEMORY DEVICE	3/14/2002	02425152.2	5/11/2011	1345236	DE
NMXS-0782.00/DE	Utility - EPPAT	Issued	SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	2/20/2002	02425088.8	9/12/2007	60222373.3	DE
NMXS-0783.00/DE	Utility - EPPAT	Issued	CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS	2/20/2002	02425089.6	5/9/2007	60220015.6	DE
NMXS-0786.00/DE	Utility - EPPAT	Issued	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/28/2001	60134870.2	7/16/2008	1324342	DE
NMXS-0791.00/DE	Utility - EPPAT	Issued	REDUNDANCY CIRCUIT AND METHOD FOR SEMICONDUCTOR MEMORY DEVICES	5/27/2003	03253297.0	4/6/2011	60336614.7	DE
NMXS-0799.00/DE	Utility - EPPAT	Issued	NONVOLATILE STORAGE DEVICE AND SELF-REDUNDANCY METHOD FOR THE SAME	8/13/2002	02425529.1	10/10/2007	60222891.3	DE
NMXS-0804.00/DE	Utility - EPPAT	Issued	REDUNDANCY CIRCUIT AND METHOD FOR REPLACING DEFECTIVE MEMORY CELLS IN A FLASH MEMORY DEVICE	7/31/2002	02255361.4	9/10/2008	1282137	DE
NMXS-0805.00/DE	Utility - EPPAT	Issued	CIRCUIT AND ASSOCIATED METHOD FOR THE ERASURE OR PROGRAMMING OF A MEMORY CELL	3/5/2002	02366003.8	5/28/2008	60226800.1	DE
NMXS-0807.01/DE	Utility - EPPAT	Issued	EEFPROM MEMORY PROTECTED AGAINST THE EFFECTS OF ACCESS TRANSISTOR BREAKDOWN	6/25/2002	02358013.7	10/6/2010	60237864.8	DE
NMXS-0809.00/DE	Utility - EPPAT	Issued	METHOD FOR REPLACING FAILED NON-VOLATILE MEMORY CELLS AND CORRESPONDING MEMORY DEVICE	9/30/2002	02425591.1	11/3/2010	1403879	DE
NMXS-0817.00/DE	Utility - EPPAT	Issued	ARRAY OF CELLS INCLUDING A SELECTION DIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	10/8/2002	02425605.9	12/27/2006	60217120.2	DE
NMXS-0818.00/DE	Utility - EPPAT	Issued	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	10/8/2002	02425604.2	5/7/2007	60218685.4	DE
NMXS-0820.00/DE	Utility - EPPAT	Issued	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE, AND NONVOLATILE MEMORY DEVICE	4/26/2002	02425265.2	6/14/2006	60212332.1	DE
NMXS-0821.00/DE	Utility - EPPAT	Issued	LINE SELECTOR FOR A MATRIX OF MEMORY ELEMENTS	7/10/2002	02425453.4	12/3/2008	60230129.7	DE
NMXS-0833.00/DE	Utility - EPPAT	Issued	METHOD OF PROGRAMMING A MULTI-LEVEL, ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	2/20/2003	03425096.9	7/15/2009	60328354.3	DE
NMXS-0844.00/DE	Utility - EPPAT	Issued	STABILIZATION METHOD FOR DRAIN VOLTAGE IN NON-VOLATILE MULTI-LEVEL MEMORY CELLS AND RELATED MEMORY DEVICE	12/30/2002	60226987.3	6/4/2008	EP1435623	DE

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NMXS-0846.00/DE	Utility - EPPAT	Issued	PROCESS FOR MANUFACTURING A MEMORY DEVICE HAVING SELECTOR TRANSISTORS FOR STORAGE ELEMENTS AND MEMORY DEVICE FABRICATED THEREBY	5/7/2003	03425292.4	7/19/2006	60306893.6	DE
NMXS-0857.00/DE	Utility - EPPAT	Issued	A REDUNDANCY SCHEME FOR AN INTEGRATED MEMORY CIRCUIT	7/16/2003	03077228.9	12/31/2008	60325576.0	DE
NMXS-0858.00/DE	Utility - EPPAT	Issued	A FULL-SWING WORLDLINE DRIVING CIRCUIT FOR A NONVOLATILE MEMORY	4/30/2003	03425264.3	11/4/2009	1473738	DE
NMXS-0863.00/DE	Utility - EPPAT	Issued	VOLTAGE SUPPLY DISTRIBUTION ARCHITECTURE FOR A PLURALITY OF MEMORY MODULES	12/30/2002	02425809.7	7/11/2007	60221140.9	DE
NMXS-0864.00/DE	Utility - EPPAT	Abandoned	NONLITHOGRAPHIC METHOD OF DEFINING GEOMETRIES FOR PLASMA AND/OR ION IMPLANTATION TREATMENTS ON A SEMICONDUCTOR WAFER	4/1/2004	602004017958.2	11/26/2008	1582922	DE
NMXS-0867.00/DE	Utility - NSPCT	Abandoned	ELEKTONENSPEKTROSKOP MIT EMISSION, DIE DURCH EINEN MONOCHROMATISCHEN ELEKTRONENSTRAHL INDUZIERT WIRD	10/6/2004	200411001895			DE
NMXS-0869.00/DE	Utility - EPPAT	Issued	MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL-POLYSILICON LAYER TECHNOLOGY	12/23/2003	03104939.8	9/15/2010	60334188.8	DE
NMXS-0870.00/DE	Utility - EPPAT	Issued	MOS DEVICE AND A PROCESS FOR MANUFACTURING MOS DEVICES USING A DUAL-POLYSILICON LAYER TECHNOLOGY WITH SIDE CONTACT	12/23/2003	03104938.0	7/20/2011	60337723.8	DE
NMXS-0872.00/DE	Utility - EPPAT	Issued	METHOD FOR READING A NONVOLATILE MEMORY DEVICE AND NONVOLATILE MEMORY DEVICE IMPLEMENTING THE READING METHOD	4/10/2003	03425224.7	11/28/2007	1467377	DE
NMXS-0877.00/DE	Utility - EPPAT	Issued	VOLTAGE REGULATION SYSTEM FOR A MULTIWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY	2/28/2003	03425133.0	12/24/2008	60325453.5	DE
NMXS-0881.00/DE	Utility - EPPAT	Issued	NON-VOLATILE MEMORY DEVICE ARCHITECTURE, FOR INSTANCE A FLASH KIND, HAVING A SERIAL COMMUNICATION INTERFACE	11/28/2002	02425780.5	10/29/2008	60229649.8	DE
NMXS-0892.00/DE	Utility - EPPAT	Issued	WORD-PROGRAMMABLE FLASH MEMORY	5/26/2004	04012393.7	4/9/2008	1486986	DE
NMXS-0893.00/DE	Utility - EPPAT	Issued	METHOD FOR MANUFACTURING DIFFERENTIAL ISOLATION STRUCTURES IN A SEMICONDUCTOR ELECTRONIC DEVICE AND CORRESPONDING STRUCTURE	7/11/2003	03425459.9	1/2/2008	60318419	DE
NMXS-0895.00/DE	Utility - EPPAT	Issued	METHOD FOR REDUCING NON-UNIFORMITY OR TOPOGRAPHY VARIATION BETWEEN AN ARRAY AND CIRCUITRY IN A PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED NON-VOLATILE MEMORY DEVICES	2/24/2004	602004025197.6	1/20/2010	1569274	DE
NMXS-0903.00/DE	Utility - EPPAT	Issued	SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	10/22/2003	03425687.5	2/25/2009	1526568	DE
NMXS-0912.00/DE	Utility - EPPAT	Issued	AN IMPROVED PAGE BUFFER FOR A PROGRAMMABLE MEMORY DEVICE	6/24/2004	04102942.2	12/19/2007	602004010795.5	DE
NMXS-0919.00/DE	Utility - EPPAT	Issued	METHOD OF MAKING A NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE	12/22/2004	04425936.4	12/9/2009	1675180	DE
NMXS-0920.00/DE	Utility - EPPAT	Issued	REDUNDANCY BASED NAND FLASH MEMORY	7/14/2004	04103354.9	10/25/2006	602004002947.5	DE
NMXS-0922.00/DE	Utility - EPPAT	Abandoned	METHOD AND SYSTEM FOR CORRECTING ERRORS IN ELECTRONIC MEMORY DEVICES	6/30/2004	04425485.2	4/21/2010	602004026707.4	DE
NMXS-0924.00/DE	Utility - EPPAT	Pending	METHOD FOR MANUFACTURING ELECTRONIC NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/23/2005	05028380.3			DE
NMXS-0943.00/DE	Utility - EPPAT	Issued	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	6/14/2004	04425435.7	8/15/2007	602004008240.6	DE
NMXS-0948.00/DE	Utility - EPPAT	Issued	FLASH MEMORY COMPRISING MEANS FOR CHECKING AND REFRESHING MEMORY CELLS IN THE ERASED STATE	6/3/2004	04013056.9	5/13/2009	1486987	DE
NMXS-0949.00/DE	Utility - EPPAT	Issued	MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD	6/30/2004	04291653.6	8/15/2007	1508901	DE
NMXS-0950.00/DE	Utility - EPPAT	Issued	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	12/8/2004	04029018.1	4/11/2007	1542130	DE
NMXS-0953.00/DE	Utility - EPPAT	Issued	A MEMORY DEVICE WITH UNIPOLAR AND BIPOLAR SELECTORS	9/22/2004	EP04104595.6	4/7/2010	602004026447.4	DE
NMXS-0955.00/DE	Utility - EPPAT	Issued	PHASE-CHANGE MEMORY DEVICE AND MANUFACTURING PROCESS THEREOF	1/21/2005	05425024.6	9/17/2008	602005009793.7	DE
NMXS-0957.00/DE	Utility - EPPAT	Issued	MEMORY DEVICE	10/15/2004	04105094.9	9/19/2007	1647991	DE

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MII Docket#	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0961.00/DE	Utility - EPPAT	Issued	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2005	05425209.3	12/12/2007	1713084	DE
NMXS-0965.00/DE	Utility - EPPAT	Issued	MEMORY DEVICE AND METHOD OF OPERATING THE SAME WITH HIGH REJECTION OF THE NOISE ON THE HIGH-VOLTAGE SUPPLY LINE	10/8/2004	04425754.1	3/5/2008	1646051	DE
NMXS-0966.00/DE	Utility - EPPAT	Issued	ELECTRONIC MEMORY DEVICE HAVING HIGH DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE INTERFERENCE CELL-TO-CELL	12/14/2005	05027285.5	11/4/2009	602005017461.3	DE
NMXS-0970.01/DE	Utility - EPPAT	Pending	NON-VOLATILE MEMORY ELECTRONIC DEVICE	12/22/2006	06026787.9			DE
NMXS-0971.00/DE	Utility - EPPAT	Issued	FLASH MEMORY DEVICE WITH REDUCED DRAIN STRESSES	2/6/2006	06101314.0	6/3/2009	602006007095.0	DE
NMXS-0974.00/DE	Utility - EPPAT	Issued	VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	11/18/2005	05025286.5	10/3/2007	1670002	DE
NMXS-0975.00/DE	Utility - EPPAT	Issued	PROCESS FOR DIGGING A DEEP TRENCH IN A SEMICONDUCTOR BODY AND SEMICONDUCTOR BODY SO OBTAINED	12/28/2005	05425930.4	12/14/2011	602005031636.1	DE
NMXS-0981.00/DE	Utility - EPPAT	Issued	PVD PROCESS AND CHAMBER FOR THE PULSED DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER OF A PHASE CHANGE MEMORY DEVICE	3/31/2006	6112075.4	12/3/2008	1710324	DE
NMXS-0983.00/DE	Utility - EPPAT	Issued	HIGH-VOLTAGE SWITCH WITH LOW OUTPUT RIPPLE FOR NON-VOLATILE FLOATING-GATE MEMORIES	5/20/2005	05425347.1	7/8/2008	602005008396.0	DE
NMXS-0986.00/DE	Utility - EPPAT	Issued	ELECTRONIC MEMORY DEVICE HAVING HIGH INTEGRATION DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE COUPLING	12/14/2005	05027286.3	10/14/2009	602005017113.4	DE
NMXS-0987.00/DE	Utility - EPPAT	Issued	METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND NON-VOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONCTOR	11/18/2005	05425814.0	1/20/2010	602005019069.4	DE
NMXS-0988.00/DE	Utility - EPPAT	Issued	VERTICAL MOSFET TRANSISTOR, IN PARTICULAR OPERATING AS A SELECTOR IN NONVOLATILE MEORY DEVICES	4/27/2005	05425261.4	8/25/2010	602005023125.0	DE
NMXS-0991.00/DE	Utility - EPPAT	Issued	MEMORY DEVICE WITH A RAMP-LIKE VOLTAGE BIASING STRUCTURE BASED ON A CURRENT GENERATOR	1/28/2005	05100551	1/9/2008	602005004253.9	DE
NMXS-0997.00/DE	Utility - EPPAT	Issued	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/3/2005	05104877.5	12/15/2010	1729303	DE
NMXS-0999.00/DE	Utility - EPPAT	Issued	NAND FLASH MEMORY WITH ERASE VERIFY BASED ON SHORTER DELAY BEFORE SENSING	7/28/2005	05106976.3	4/23/2008	602005006274.2	DE
NMXS-1000.00/DE	Utility - EPPAT	Issued	TRANSISTOR STRUCTURE WITH HIGH INPUT IMPEDANCE AND HIGH CURRENT CAPABILITY AND MANUFACTURING PROCESS THEREOF	11/25/2005	05425835.5	2/3/2010	1791181	DE
NMXS-1001.00/DE	Utility - EPPAT	Issued	A MEMORY DEVICE WITH TIME-SHIFTING BASED EMULATION OF REFERENCE CELLS	3/3/2005	05101660.8	1/6/2010	1699055	DE
NMXS-1002.00/DE	Utility - EPPAT	Issued	METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE FLOATING GATE COUPLING AND MEMORY DEVICE	3/31/2006	06425223.2	4/28/2010	602006013935.7	DE
NMXS-1004.00/DE	Utility - EPPAT	Issued	NON-VOLATILE MEMORY DEVICE WITH MULTIPLE REFERENCES AND CORRESPONDING CONTROL METHOD	7/29/2005	05425564.1	7/6/2011	1750281	DE
NMXS-1009.00/DE	Utility - EPPAT	Issued	READING CIRCUIT AND METHOD FOR A NONVOLATILE MEMORY DEVICE	9/28/2004	04425724.4	6/17/2009	602004021599.6	DE
NMXS-1010.00/DE	Utility - EPPAT	Issued	SELF-ADAPTIVE OUTPUT BUFFER BASED ON CHARGE SHARING	7/7/2005	05106180.2	2/9/2009	1742361	DE
NMXS-1013.00/DE	Utility - EPPAT	Issued	ENHANCED SECURITY MEMORY ACCESS METHOD AND ARCHITECTURE	1/19/2005	05100310.1	3/18/2009	602005013344.5	DE
NMXS-1016.00/DE	Utility - EPPAT	Issued	SEQUENTIAL PROGRAM-VERIFY METHOD WITH RESULT BUFFERING	3/30/2004	04101301.2	8/1/2007	1583102	DE
NMXS-1021.00/DE	Utility - ORG	Pending	METHOD AND DEVICE FOR IRREVERSIBLY PROGRAMMING AND READING NONVOLATILE MEMORY CELLS	9/10/2008	102008041947.8			DE
NMXS-1031.00/DE	Utility - EPPAT	Issued	METHOD FOR PROGRAMMING/ERASING A NON VOLATILE MEMORY CELL DEVICE, IN PARTICULAR FOR FLASH TYPE MEMORIES	3/10/2006	06425164.8	8/11/2010	602006016065.8	DE
NMXS-1035.00/DE	Utility - EPPAT	Pending	IMPROVEMENTS TO THE DESIGN OF VOLTAGE SWITCHES	3/21/2006	06111477.3			DE
NMXS-1036.00/DE	Utility - EPPAT	Issued	ROW SELECTOR FOR A SEMICONDUCTOR MEMORY DEVICE BUILT FROM LOW VOLTAGE TRANSISTORS	5/4/2006	06113480.5	1/27/2010	602006008738	DE
NMXS-1037.00/DE	Utility - EPPAT	Lapsed	A COLUMN DECODING SYSTEM FOR SEMICONDUCTOR MEMORY DEVICES IMPLEMENTED WITH LOW VOLTAGE TRANSISTORS	4/12/2006	061125266	4/1/2009	1845532	DE
NMXS-1039.00/DE	Utility - EPPAT	Pending	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY DEVICE	9/30/2005	05425681.3			DE

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NMXS-1046.00/DE	Utility - EPPAT	Issued	A SEMICONDUCTOR MEMORY DEVICE WITH A PAGE BUFFER HAVING AN IMPROVED LAYOUT ARRANGEMENT	7/28/2005	05106973.0	5/14/2008	2005006791.4	DE
NMXS-1049.00/DE	Utility - EPPAT	Issued	METHOD FOR LOCALLY SUPPRESSING A DISTURBANCE OF A REFERENCE LINE	2/28/2006	06425124.2	9/30/2009	602006009476.0	DE
NMXS-1054.00/DE	Utility - EPPAT	Issued	READING METHOD OF A MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE AND MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE	3/2/2006	06425141.6	5/13/2009	602006006788.7	DE
NMXS-1066.00/DE	Utility - EPPAT	Issued	NON-VOLATILE MEMORY DEVICE	10/13/2005	05425718.3	12/2/2009	602005018067.2	DE
NMXS-1068.00/DE	Utility - EPPAT	Issued	AUTOMATIC REGULATION METHOD FOR THE REFERENCE SOURCES IN A NON VOLATILE MEMORY DEVICE AND CORRESPONDING MEMORY DEVICE	6/30/2006	06425452.7	2/17/2010	602006012299.3	DE
NMXS-1069.00/DE	Utility - EPPAT	Issued	METHOD AND DEVICE FOR DETECTING POSSIBLE CORRUPTION OF SECTOR PROTECTION INFORMATION OF A NON-VOLATILE MEMORY STORED IN AN ON BOARD VOLATILE MEMORY ARRAY AT POWER-ON	3/29/2006	06425214.1	8/5/2009	602006008270.3	DE
NMXS-1070.00/DE	Utility - EPPAT	Issued	METHOD FOR ACCESSING A MULTILEVEL NONVOLATILE MEMORY DEVICE OF THE FLASH NAND TYPE	7/22/2005	05106783.3	2/4/2009	602005012625.2	DE
NMXS-1071.00/DE	Utility - EPPAT	Issued	CONFIGURATION OF A MULTILEVEL FLASH MEMORY DEVICE	7/28/2005	05425559.1	5/19/2010	602005021344.9	DE
NMXS-1074.00/DE	Utility - EPPAT	Issued	METHOD OF PROGRAMMING A FOUR-LEVEL FLASH MEMORY DEVICE AND A RELATED PAGE BUFFER	6/7/2006	06115106.4	11/11/2009	602006010280.1	DE
NMXS-1076.00/DE	Utility - EPPAT	Issued	METHOD OF FIXING READ EVALUATION TIME IN A NON VOLATILE NAND TYPE MEMORY DEVICE	9/13/2006	06425631.6	4/28/2010	1901309	DE
NMXS-1078.00/DE	Utility - EPPAT	Issued	PHASE CHANGE MEMORY DEVICE	7/27/2006	06425531.8	3/10/2010	1883113	DE
NMXS-1078.01/DE	Utility - NSPCT	Abandoned	PHASE CHANGE MEMORY DEVICE	7/26/2007	112007001750.3			DE
NMXS-1082.00/DE	Utility - EPPAT	Issued	PHASE CHANGE MEMORY DEVICE FOR MULTIBIT STORAGE	9/7/2007	07425555.5	11/17/2010	602007010624.9	DE
NMXS-1082.01/DE	Utility - ORG	Abandoned	PHASE CHANGE MEMORY DEVICE FOR MULTIBIT STORAGE	9/4/2008	102008041810.2			DE
NMXS-1084.00/DE	Utility - EPPAT	Issued	METHOD FOR COMPACTING THE ERASED THRESHOLD VOLTAGE DISTRIBUTION OF FLASH MEMORY DEVICES DURING WRITING OPERATIONS	8/24/2006	06119452.8	10/7/2009	602006009662.3	DE
NMXS-1085.00/DE	Utility - EPPAT	Issued	METHOD AND CIRCUIT FOR ELECTRICALLY PROGRAMMING SEMICONDUCTOR MEMORY CELLS	6/23/2006	06115812.7	12/30/2009	1870905	DE
NMXS-1086.00/DE	Utility - EPPAT	Issued	A MEMORY DEVICE WITH ROW SELECTOR COMPRISING SERIES CONNECTED MEDIUM VOLTAGE TRANSISTORS	8/24/2006	06119440.3	12/9/2009	602006011005.7	DE
NMXS-1091.00/DE	Utility - ORG	Pending	MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS AND RELATED METHODS OF MANAGING	10/25/2007	102007051192.4			DE
NMXS-1094.00/DE	Utility - EPPAT	Issued	NON-VOLATILE MEMORY DEVICE AND METHOD OF HANDLING A DATUM READ FROM A MEMORY CELL	7/28/2005	05425537.5	12/3/2008	602006004038.5	DE
NMXS-1104.00/DE	Utility - ORG	Abandoned	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	10/17/1985	3537047.5	6/1/1995	3537047	DE
NMXS-1105.00/DE	Utility - EPPAT	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	10/9/1986	86830298.6	8/29/1990	3673777	DE
NMXS-1106.00/DE	Utility - EPPAT	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/20/1987	87830204.1	2/27/1991	3768176	DE
NMXS-1107.00/DE	Utility - EPPAT	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/22/1987	87830234	4/21/1993	3785509	DE
NMXS-1108.00/DE	Utility - EPPAT	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	5/4/1988	88107152.6	9/9/1992	3874436	DE
NMXS-1109.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/15/1988	88120977.9	5/12/1993	3881004	DE
NMXS-1110.00/DE	Utility - EPPAT	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	89100780.9	10/20/1993	68909959	DE
NMXS-1111.00/DE	Utility - EPPAT	Abandoned	CMOS VOLTAGE MULTIPLIER	6/16/1989	89830269.0	2/9/1994	68912979	DE
NMXS-1116.00/DE	Utility - EPPAT	Abandoned	PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	12/22/1989	89830569.3	7/19/1995	68923541	DE

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NMXS-1117.00/DE	Utility - EPPAT	Abandoned	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/14/1990	90313667.9	11/8/1995	0435534	DE
NMXS-1118.00/DE	Utility - EPPAT	Abandoned	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	2/7/1991	91830037.7	5/10/1995	69109521	DE
NMXS-1119.00/DE	Utility - EPPAT	Abandoned	READING CIRCUIT FOR NONVOLATILEMEMORY CELL.	2/7/1991	91830036.9	1/3/1996	69115952	DE
NMXS-1120.00/DE	Utility - EPPAT	Abandoned	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	3/19/1991	91104217.4	9/13/1995	69112882	DE
NMXS-1121.00/DE	Utility - EPPAT	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	4/24/1991	91830167.2	11/25/1998	69130513	DE
NMXS-1122.00/DE	Utility - EPPAT	Expired	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	4/4/1991	91105323.9	12/29/1997	69128494	DE
NMXS-1123.00/DE	Utility - EPPAT	Abandoned	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	6/27/1991	91201641.7	5/28/1997	0464928	DE
NMXS-1125.00/DE	Utility - EPPAT	Abandoned	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	9/30/1991	91116659.3	8/13/1997	691272483	DE
NMXS-1126.00/DE	Utility - EPPAT	Abandoned	TWO PHASES SCAN PATH WITH SINGLECLOCK.	10/15/1991	91202668.9	7/8/1998	0482697	DE
NMXS-1127.00/DE	Utility - EPPAT	Abandoned	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	11/19/1990	90830529.5	2/19/1997	69029968	DE
NMXS-1128.00/DE	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/19/1990	90830530.3	5/8/1996	69026946	DE
NMXS-1129.00/DE	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/13/1990	90830583.2	5/1/1996	69026828	DE
NMXS-1130.00/DE	Utility - EPPAT	Abandoned	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/20/1991	91121952.5	4/2/1997	69125465	DE
NMXS-1131.00/DE	Utility - EPPAT	Abandoned	MEMORY CELL READING CIRCUIT	12/18/1991	91121675.2	3/12/1997	69125119	DE
NMXS-1132.00/DE	Utility - EPPAT	Abandoned	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	5/5/1992	92830205.8	7/29/1998	69226400	DE
NMXS-1133.00/DE	Utility - EPPAT	Abandoned	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	7/21/1992	92830400.5	10/15/1997	69222712	DE
NMXS-1134.00/DE	Utility - EPPAT	Abandoned	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	8/27/1992	92830458.3	7/2/1997	0530159	DE
NMXS-1135.00/DE	Utility - EPPAT	Abandoned	ROW DECODER FOR NAND-TYPE ROM	8/27/1992	92830457.5	3/4/1998	69224576	DE
NMXS-1136.00/DE	Utility - EPPAT	Abandoned	PLANARIZED CONTACT WITH A SANDWICH OF TUNGSTEN AND ALUMINIUM.	11/10/1992	92119191.2	9/22/1999	69230025	DE
NMXS-1137.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	11/2/1992	92118785.2	9/27/2000	69231484	DE
NMXS-1138.00/DE	Utility - EPPAT	Abandoned	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	9/24/1992	92830523.4	1/21/1998	69224125	DE
NMXS-1139.00/DE	Utility - EPPAT	Abandoned	METALLIZATION OVER TUNGSTEN PLUGS	5/27/1992	92830265.2	9/18/1996	69213928	DE
NMXS-1140.00/DE	Utility - EPPAT	Abandoned	LOW SWITCHING NOISE OUTPUT BUFFER	6/26/1992	92830335.3	10/31/2001	69232170	DE
NMXS-1141.00/DE	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	6/30/1992	92830339.5	9/13/1995	0576773	DE
NMXS-1142.00/DE	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	6/30/1992	92830340.3	9/15/1999	69229995	DE
NMXS-1143.00/DE	Utility - EPPAT	Abandoned	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	9/30/1992	92830541.6	12/2/1998	69227772	DE
NMXS-1144.00/DE	Utility - EPPAT	Abandoned	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	10/1/1992	92830552.3	5/27/1998	69225700	DE
NMXS-1145.00/DE	Utility - EPPAT	Abandoned	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	10/29/1992	92830589.5	7/28/1999	69229673	DE
NMXS-1146.00/DE	Utility - EPPAT	Abandoned	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	11/18/1992	92830625.7	5/28/1997	69220067	DE
NMXS-1147.00/DE	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	1/29/1993	93830031.6	5/6/1999	69324789.4	DE
NMXS-1148.00/DE	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS	1/29/1993	93830032.4	1/7/1998	69316186	DE
NMXS-1149.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS	2/11/1993	93830050.6	9/10/1997	69313816	DE

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NMXS-1150.00/DE	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830057.1	7/30/1997	69312676	DE
NMXS-1151.00/DE	Utility - EPPAT	Abandoned	NONVOLATILE EPROM, EEPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830058.9	10/13/1999	69326749	DE
NMXS-1152.00/DE	Utility - EPPAT	Abandoned	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	3/18/1993	93830109.0	6/23/1999	69325442	DE
NMXS-1153.00/DE	Utility - EPPAT	Abandoned	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	3/18/1993	93830110.8	6/23/1999	69325443	DE
NMXS-1154.00/DE	Utility - EPPAT	Issued	SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS	3/31/1993	93830128.0	7/22/1998	0618587	DE
NMXS-1155.00/DE	Utility - EPPAT	Abandoned	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	4/1/1993	93830134.8	7/28/1999	69325767	DE
NMXS-1157.00/DE	Utility - NSPCT	Abandoned	METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/9/1992	92402777.4	3/4/1998	0537082	DE
NMXS-1158.00/DE	Utility - EPPAT	Issued	SUPPLY VOLTAGE DISTRIBUTION SYSTEM WITH REDUCED RESISTANCE FOR SEMICONDUCTOR DEVICES	7/27/2006	06117949.5	2/4/2009	1884954	DE
NMXS-0001.00/EP	Utility - ORG	Abandoned	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/9/1988	88403140.2	4/10/1996	0321327	EP
NMXS-0002.00/EP	Utility - ORG	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/9/1988	88403141.0	1/13/1993	0323295	EP
NMXS-0003.00/EP	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/26/1989	89401183.2	5/10/1993	0340107	EP
NMXS-0004.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/19/1993	93401861.5	2/15/1995	0585150	EP
NMXS-0005.00/EP	Utility - ORG	Abandoned	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	7/15/1993	93401836.7	12/28/1994	0581639	EP
NMXS-0006.00/EP	Utility - ORG	Lapsed	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	9/14/1993	93402229.4	1/18/1995	0591022	EP
NMXS-0007.00/EP	Utility - ORG	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/14/1993	93403029.7	4/3/1996	0604270	EP
NMXS-0008.00/EP	Utility - ORG	Abandoned	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/19/1987	87401120.8	3/14/1990	0246965	EP
NMXS-0009.00/EP	Utility - ORG	Abandoned	NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401991.0	10/27/1993	0302780	EP
NMXS-0010.00/EP	Utility - ORG	Abandoned	NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401990.2	5/26/1993	0302779	EP
NMXS-0011.00/EP	Utility - ORG	Abandoned	CONTENT ADDRESSABLE MEMORY	5/23/1991	91304677.7	8/16/2000	0459703	EP
NMXS-0012.00/EP	Utility - ORG	Abandoned	REDUNDANCY FOR SERIAL MEMORY	12/21/1990	90314116.6	4/23/1997	0437081	EP
NMXS-0013.00/EP	Utility - ORG	Abandoned	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	5/25/1991	91302575.5	12/16/1998	0459839	EP
NMXS-0014.00/EP	Utility - ORG	Abandoned	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/19/1990	90313891.5	4/1/1998	0434381	EP
NMXS-0015.00/EP	Utility - ORG	Abandoned	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/16/1991	91309521.2	7/29/1998	0481751	EP
NMXS-0016.00/EP	Utility - ORG	Abandoned	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	6/29/1990	90307156.1	1/8/1997	0420388	EP
NMXS-0017.00/EP	Utility - DIV	Abandoned	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/12/1991	96113905.2			EP
NMXS-0017.01/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/12/1991	91307425.8	3/19/1997	0471543	EP
NMXS-0018.00/EP	Utility - ORG	Abandoned	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	5/31/1991	91304952.4	12/18/1996	0501057	EP

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NMXS-0019.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	5/31/1991	91304951.6	7/30/1997	0472266	EP
NMXS-0020.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307423.3	3/19/1997	0471541	EP
NMXS-0021.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307419.1	6/26/1996	0475588	EP
NMXS-0022.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308632.8	6/18/1997	0478251	EP
NMXS-0023.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308633.6	4/8/1998	0478252	EP
NMXS-0024.00/EP	Utility - DIV	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	98117267.3	2/18/2004	0768676	EP
NMXS-0024.01/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	91307426.6	5/14/1997	0471544	EP
NMXS-0025.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/21/1991	91309721.8	1/7/1998	0482869	EP
NMXS-0026.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/23/1991	91308634.4	11/27/1996	0478253	EP
NMXS-0027.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/23/1991	91308636.9	5/28/1997	0478254	EP
NMXS-0028.00/EP	Utility - ORG	Abandoned	ADDRESS BUFFER CIRCUIT HAVING LATCHING BASED ON TRANSITION	10/21/1991	91309720.0	1/7/1998	0482868	EP
NMXS-0029.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH PRECHARGED REDUNDANCY MULTIPLEXING	12/12/1991	91311569.7	9/11/1996	0491523	EP
NMXS-0030.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH COLUMN DECODED BIT LINE EQUILIBRATE	12/11/1991	91311506.9	10/4/2000	0490650	EP
NMXS-0031.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/12/1991	91311570.5	9/24/1997	0490679	EP
NMXS-0032.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/12/1991	91311571.3	10/2/1996	0490680	EP
NMXS-0033.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	7/16/1992	92306526.2	3/4/1998	0523995	EP
NMXS-0034.00/EP	Utility - ORG	Abandoned	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	4/30/1992	92303960.6	10/20/1999	0514050	EP
NMXS-0035.00/EP	Utility - ORG	Abandoned	CONTROL CIRCUIT FOR DUAL PORT MEMORY	4/30/1992	92303958.0	7/22/1998	0514049	EP
NMXS-0036.00/EP	Utility - ORG	Abandoned	CACHE TAG PARITY DETECT CIRCUIT	3/27/1992	92302736.1	10/8/1997	0506474	EP
NMXS-0037.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	7/16/1992	92306527.0	3/4/1998	0523996	EP
NMXS-0038.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT DUAL-PORT MEMORY DEVICE HAVING REDUCED CAPACITANCE	7/16/1992	92306528.8	5/20/1998	0523997	EP
NMXS-0039.00/EP	Utility - ORG	Abandoned	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	1/20/1993	93300397.2	7/8/1998	0552941	EP
NMXS-0040.00/EP	Utility - ORG	Abandoned	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	11/29/1993	93309496.3	6/13/2001	0600692	EP
NMXS-0041.00/EP	Utility - ORG	Abandoned	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	12/16/1992	92311510.9	3/3/1999	0547888	EP
NMXS-0042.00/EP	Utility - ORG	Abandoned	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/16/1992	92311511.7	4/14/1999	0547889	EP
NMXS-0043.00/EP	Utility - ORG	Abandoned	MULTIPLEXING SENSE AMPLIFIER	3/31/1994	94302349.9			EP
NMXS-0045.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	12/16/1992	92311514.1	10/28/1998	0547892	EP
NMXS-0046.00/EP	Utility - ORG	Abandoned	REDUNDANCY DECODER	1/27/1993	93300560.5	7/22/1998	0554052	EP
NMXS-0047.00/EP	Utility - ORG	Abandoned	COLUMN REDUNDANCY ARCHITECTURE FOR A READ/WRITE MEMORY	1/27/1993	93300562.1			EP
NMXS-0048.00/EP	Utility - ORG	Abandoned	SELECTIVE BULK WRITE OPERATION	3/26/1993	93302376.4			EP
NMXS-0049.00/EP	Utility - ORG	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR	4/29/1993	93303369.8	12/29/1999	0568373	EP
NMXS-0050.00/EP	Utility - ORG	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE	4/29/1993	93303370.6	10/20/1999	0568374	EP
NMXS-0051.00/EP	Utility - ORG	Abandoned	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	3/22/1993	93302156.0	6/20/2001	0564137	EP
NMXS-0052.00/EP	Utility - ORG	Abandoned	PARALLELIZED DIFFERENCE FLAG LOGIC	5/19/1993	93303874.7	2/23/2000	0574144	EP
NMXS-0053.00/EP	Utility - ORG	Abandoned	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/10/1993	93304489.3	12/20/2000	0579375	EP
NMXS-0054.00/EP	Utility - ORG	Abandoned	FIFO WITH ADAPTABLE FLAGS FOR CHANGING SYSTEM SPEED REQUIREMENTS	7/30/1993	93306052.7			EP

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MTI DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0056.00/EP	Utility - ORG	Abandoned	PROCESS FOR REALIZING P CHANNEL MOS TRANSISTORS HAVING A LOW THRESHOLD VOLTAGE IN SEMICONDUCTOR INTEGRATED CIRCUITS FOR ANALOG APPLICATIONS	7/29/1993	93830336.9			EP
NMXS-0057.00/EP	Utility - ORG	Abandoned	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	10/26/1993	93308503.7			EP
NMXS-0058.00/EP	Utility - ORG	Abandoned	STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE	11/12/1993	93309092.0			EP
NMXS-0059.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT OUTPUT DRIVER	8/27/1993	93306835.5	3/26/1997	0586207	EP
NMXS-0062.00/EP	Utility - ORG	Abandoned	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/21/1993	93310384.8	3/3/1999	0604195	EP
NMXS-0064.00/EP	Utility - ORG	Abandoned	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/18/1994	94301188.2	5/10/2000	0612008	EP
NMXS-0065.00/EP	Utility - ORG	Abandoned	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/30/1993	93307776.0	3/3/1999	0590882	EP
NMXS-0066.00/EP	Utility - ORG	Abandoned	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/27/1993	93306836.3	10/29/1997	0586208	EP
NMXS-0067.00/EP	Utility - ORG	Abandoned	TEMPERATURE-COMPENSATED VOLTAGE LEVEL SENSE CIRCUIT	4/26/1994	94303005.6	4/3/2002	0626582	EP
NMXS-0068.00/EP	Utility - ORG	Abandoned	ADDRESS BUFFER	4/28/1994	94303082.5	9/22/1999	0622803	EP
NMXS-0069.00/EP	Utility - ORG	Abandoned	METHOD FOR STRESS TESTING DECODERS AND PERIPHERY CIRCUITS	4/28/1994	94303083.3	7/28/1999	0622809	EP
NMXS-0071.00/EP	Utility - ORG	Abandoned	OUTPUT DRIVER CIRCUIT	7/28/1993	93305947.9	2/24/1999	0581579	EP
NMXS-0072.00/EP	Utility - ORG	Abandoned	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	7/27/1994	94305553.3	11/10/1999	0637036	EP
NMXS-0073.00/EP	Utility - ORG	Abandoned	TEMPERATURE-STABLE CURRENT SOURCE	6/12/1995	95401363.7	4/8/1998	0687967	EP
NMXS-0074.00/EP	Utility - ORG	Lapsed	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	5/31/1993	93830243.7	12/15/2004	0627763	EP
NMXS-0075.00/EP	Utility - ORG	Abandoned	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/30/1993	93830403.7	12/1/1999	0646924	EP
NMXS-0076.00/EP	Utility - ORG	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	9/10/1993	93830365.8	12/2/1998	0643418	EP
NMXS-0077.00/EP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/30/1993	93830481.3	2/10/1999	0655742	EP
NMXS-0078.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR COVERING INITIAL CONDITIONS WHEN STARTING-UP AN INTEGRATED CIRCUIT DEVICE	1/31/1994	94830031.4			EP
NMXS-0079.00/EP	Utility - ORG	Lapsed	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/24/1993	93830464.9	7/28/1999	0654791	EP
NMXS-0080.00/EP	Utility - ORG	Abandoned	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/7/1993	93830491.2	3/17/1999	0657814	EP
NMXS-0081.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	11/30/1993	93830474.8	8/25/1999	0655743	EP
NMXS-0082.00/EP	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830062.9	7/8/1998	0668563	EP
NMXS-0083.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/9/1993	93830493.8	9/2/1998	0657811	EP
NMXS-0084.00/EP	Utility - ORG	Abandoned	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/29/1994	94830146.0	8/5/1998	0675440	EP
NMXS-0085.00/EP	Utility - ORG	Abandoned	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/21/1994	94830022.3	10/7/1998	0665485	EP
NMXS-0086.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE-MEMORY OUTPUT DATA	2/18/1994	94830059.4	7/7/1999	0678869	EP
NMXS-0087.00/EP	Utility - ORG	Abandoned	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/18/1994	94830070.1	5/17/2000	0668592	EP
NMXS-0088.00/EP	Utility - ORG	Abandoned	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/18/1994	94830071.0	6/7/2000	0678873	EP
NMXS-0089.00/EP	Utility - ORG	Abandoned	COUNT UNIT FOR NONVOLATILE MEMORIES	12/28/1993	93830527.3	7/7/1999	0662692	EP
NMXS-0090.00/EP	Utility - ORG	Abandoned	END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES	12/28/1993	93830526.5	3/31/1999	0661814	EP
NMXS-0091.00/EP	Utility - ORG	Abandoned	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	12/28/1993	93830525.7	7/16/1997	0661795	EP
NMXS-0092.00/EP	Utility - ORG	Abandoned	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1993	93830489.6	5/27/1998	0662690	EP
NMXS-0093.00/EP	Utility - ORG	Abandoned	READING CIRCUIT FOR AN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1994	94830124.7	5/31/2000	0678871	EP

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MEI Docket No	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0094.00/EP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/30/1993	93830478.9	9/1/1999	0655683	EP
NMXS-0095.00/EP	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/31/1994	94850082.2	5/23/2001	0665558	EP
NMXS-0096.00/EP	Utility - ORG	Abandoned	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/31/1994	94830156.9	7/11/2001	0675504	EP
NMXS-0097.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR IDENTIFYING A MEMORY CELL HAVING ERRONEOUS DATA STORED THEREIN	8/31/1994	94850412.6			EP
NMXS-0098.00/EP	Utility - ORG	Issued	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	12/31/1993	93830537.2	6/9/1999	0661713	EP
NMXS-0099.00/EP	Utility - ORG	Abandoned	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1993	93830482.1	5/10/2000	0655669	EP
NMXS-0100.00/EP	Utility - ORG	Abandoned	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1994	94830077.7	9/26/2001	0668593	EP
NMXS-0101.00/EP	Utility - ORG	Abandoned	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830540.6	6/23/1999	0661714	EP
NMXS-0102.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	12/31/1993	93830545.5	3/29/2000	0661717	EP
NMXS-0103.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830542.2	6/9/1999	0661715	EP
NMXS-0104.00/EP	Utility - ORG	Abandoned	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/29/1993	93830528.1	9/23/1998	0661636	EP
NMXS-0105.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/18/1994	94830073.6	7/28/1999	0678870	EP
NMXS-0106.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/18/1994	94830074.4	10/20/1999	0668591	EP
NMXS-0107.00/EP	Utility - ORG	Abandoned	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH	4/19/1994	94830182.5	7/26/2000	0678874	EP
NMXS-0108.00/EP	Utility - ORG	Abandoned	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME	3/28/1994	94830144.5	10/4/2001	0676816	EP
NMXS-0109.00/EP	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830061.1	8/5/1998	0668562	EP
NMXS-0110.00/EP	Utility - ORG	Abandoned	REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS	3/28/1994	94830143.7	12/27/2000	0676768	EP
NMXS-0111.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	12/31/1993	93830543.0	7/21/1999	0661716	EP
NMXS-0112.00/EP	Utility - ORG	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	4/28/1994	94303084.1	4/7/1999	0627817	EP
NMXS-0113.00/EP	Utility - DIV	Abandoned	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/20/1994	98200771.8			EP
NMXS-0113.01/EP	Utility - ORG	Abandoned	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/20/1994	94302808.4	11/11/1998	0621537	EP
NMXS-0114.00/EP	Utility - ORG	Abandoned	STRUCTURE FOR DESELECTIVE BROKEN SELECT LINES IN MEMORY ARRAYS	5/19/1994	94303589.9			EP
NMXS-0115.00/EP	Utility - ORG	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	6/27/1994	94304643.8	9/8/1999	0632594	EP
NMXS-0117.00/EP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	6/27/1994	94304644.1	3/14/2001	0634751	EP
NMXS-0118.00/EP	Utility - ORG	Abandoned	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	6/27/1994	94304645.8	9/19/2001	0632460	EP
NMXS-0124.00/EP	Utility - ORG	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	7/27/1994	94305554.1	9/23/1998	0637134	EP
NMXS-0128.00/EP	Utility - ORG	Abandoned	REDUNDANT LINE DECODER MASTER ENABLE	9/28/1994	94307069.8			EP
NMXS-0130.00/EP	Utility - ORG	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	9/28/1994	94307070.6	3/20/2002	0647028	EP
NMXS-0131.00/EP	Utility - DIV	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	99300541.2	3/6/2002	0952549	EP
NMXS-0131.01/EP	Utility - ORG	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	94307068.0	5/31/2000	0646926	EP
NMXS-0138.00/EP	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/21/1994	94460043.6	5/29/1996	0654792	EP
NMXS-0139.00/EP	Utility - ORG	Abandoned	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	5/25/1994	94401162.6	10/4/2001	0626728	EP

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MFI DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0140.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/26/1994	94460037.8	12/16/1998	0651394	EP
NMXS-0141.00/EP	Utility - ORG	Abandoned	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/21/1994	94470041.8	4/14/1999	0660331	EP
NMXS-0142.00/EP	Utility - ORG	Abandoned	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/16/1994	94402912.3	8/21/1996	0660333	EP
NMXS-0143.00/EP	Utility - ORG	Abandoned	METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES	1/23/1995	95470003.5			EP
NMXS-0144.00/EP	Utility - ORG	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/23/1995	95470006.8	10/16/1996	0669622	EP
NMXS-0145.00/EP	Utility - ORG	Abandoned	MEMORY REDUNDANCY CIRCUIT	2/27/1995	95400420.6	6/19/1996	0669576	EP
NMXS-0146.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/20/1995	95400608.6	10/6/1999	0675503	EP
NMXS-0147.00/EP	Utility - ORG	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400190.5	10/16/1996	0666572	EP
NMXS-0148.00/EP	Utility - ORG	Abandoned	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400189.7	6/26/1996	0666573	EP
NMXS-0149.00/EP	Utility - ORG	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400188.9	6/26/1996	0666559	EP
NMXS-0150.00/EP	Utility - ORG	Abandoned	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/14/1995	95470014.2	9/18/1996	0678801	EP
NMXS-0151.00/EP	Utility - ORG	Abandoned	VOLTAGE BOOSTER CIRCUIT	4/14/1995	95470013.4	6/18/1997	0678868	EP
NMXS-0152.00/EP	Utility - ORG	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/6/1995	95400772.0	9/29/1999	0678875	EP
NMXS-0153.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/17/1995	95460007.8	1/22/1997	0674264	EP
NMXS-0154.00/EP	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/3/1995	95460015.1	8/21/1996	0676769	EP
NMXS-0155.00/EP	Utility - ORG	Abandoned	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	7/18/1995	95401709.1	12/18/1996	0696031	EP
NMXS-0156.00/EP	Utility - ORG	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/20/1995	95400607.8	6/2/1999	0675441	EP
NMXS-0157.00/EP	Utility - ORG	Abandoned	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/7/1994	94830276.5	3/7/2001	0686978	EP
NMXS-0158.00/EP	Utility - ORG	Abandoned	PROGRAMMABLE MEMORY ELEMENT	3/31/1994	94830154.4	6/13/2001	0675501	EP
NMXS-0159.00/EP	Utility - ORG	Abandoned	SENSE AMPLIFIER WITH HYSTERESIS	5/3/1994	94830209.6	3/28/2001	0681293	EP
NMXS-0160.00/EP	Utility - ORG	Abandoned	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	4/12/1994	94830167.6	3/17/1999	0677869	EP
NMXS-0161.00/EP	Utility - ORG	Abandoned	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/30/1994	94830591.7	3/26/2003	0720223	EP
NMXS-0162.00/EP	Utility - ORG	Abandoned	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	6/10/1994	94830283.1	3/7/2001	0686979	EP
NMXS-0163.00/EP	Utility - ORG	Abandoned	METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL	7/18/1994	94830363.1	10/14/1998	0696050	EP
NMXS-0164.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	9/30/1994	94830471.2	12/1/1999	0704854	EP
NMXS-0165.00/EP	Utility - ORG	Abandoned	SENSE AMPLIFIER CIRCUIT FOR SEMICONDUCTOR MEMORY DEVICES	4/28/1995	95830166.5	12/12/2001	0740307	EP
NMXS-0166.00/EP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	11/30/1994	94830554.5	10/23/2002	0715312	EP
NMXS-0167.00/EP	Utility - ORG	Abandoned	HIGH-VOLTAGE N-CHANNEL MOS TRANSISTOR AND ASSOCIATED MANUFACTURING PROCESS	2/28/1995	95830065.9			EP
NMXS-0168.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS	9/30/1994	94830468.8	12/15/1999	0704901	EP
NMXS-0169.00/EP	Utility - ORG	Abandoned	READING CIRCUIT FOR MEMORY CELLS	8/31/1994	94830415.9			EP
NMXS-0170.00/EP	Utility - ORG	Abandoned	SYNCHRONIZATION DEVICE FOR OUTPUT STAGES, PARTICULARLY FOR ELECTRONIC MEMORIES	11/18/1994	94830538.8	1/9/2002	0713221	EP

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MtrDcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0171.00/EP	Utility - ORG	Abandoned	PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING	4/4/1995	95830133.5	6/27/2001	0736876	EP
NMXS-0172.00/EP	Utility - ORG	Abandoned	DECODER WITH REDUCED ARCHITECTURE	11/18/1994	94830539.6			EP
NMXS-0173.00/EP	Utility - ORG	Abandoned	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	5/19/1995	95830211.9	3/29/2000	0743648	EP
NMXS-0174.00/EP	Utility - ORG	Abandoned	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	1/26/1995	95830020.4	4/11/2001	0724267	EP
NMXS-0175.00/EP	Utility - ORG	Abandoned	TWIN-WELL MANUFACTURING PROCESS FOR AN EEPROM INTEGRATED DEVICE WITH REDUCED BODY EFFECT	11/24/1994	94830544.6	2/6/2002	0714133	EP
NMXS-0176.00/EP	Utility - ORG	Abandoned	EEPROM MEMORY WITH CONTACTLESS MEMORY CELLS	5/5/1995	95830182.2			EP
NMXS-0177.00/EP	Utility - ORG	Abandoned	BYTE ERASABLE EEPROM FULLY COMPATIBLE WITH A SINGLE POWER SUPPLY FLASH-EPROM PROCESS	9/27/1994	94830459.7	11/28/2001	0704851	EP
NMXS-0178.00/EP	Utility - ORG	Abandoned	POWER-ON RESET CIRCUIT	8/31/1994	94830417.5			EP
NMXS-0179.00/EP	Utility - ORG	Abandoned	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	5/5/1995	95830184.8	1/12/2000	0741387	EP
NMXS-0180.00/EP	Utility - ORG	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	6/30/1995	95830281.2	11/27/2002	0751559	EP
NMXS-0181.00/EP	Utility - ORG	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC	6/30/1995	95830282.0	11/27/2002	0751560	EP
NMXS-0182.00/EP	Utility - DIV	Abandoned	A PROCESS FOR MANUFACTURING A MOS INTEGRATED CIRCUIT HAVINGCOMPONENTS WITH DIFFERENT DIELECTRICS	5/10/1995	01200376.0			EP
NMXS-0182.01/EP	Utility - ORG	Abandoned	A PROCESS FOR MANUFACTURING A MOS INTEGRATED CIRCUIT HAVINGCOMPONENTS WITH DIFFERENT DIELECTRICS	5/10/1995	95830189.7			EP
NMXS-0183.00/EP	Utility - ORG	Abandoned	METHOD FOR IMPROVING THE PROFILE OF THE INTERMEDIATE DIELECTRIC, PARTICULARLY FOR NON VOLATILE MEMORIES	2/28/1996	96830086.3	12/10/2008	0793273	EP
NMXS-0184.00/EP	Utility - ORG	Abandoned	CHARGE PUMP VOLTAGE MULTIPLIER CIRCUIT	12/5/1994	94830563.6	6/12/2002	0716368	EP
NMXS-0185.00/EP	Utility - ORG	Abandoned	VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS	4/14/1995	95830153.3	9/13/2000	0737643	EP
NMXS-0186.00/EP	Utility - ORG	Abandoned	CURRENT DETECTING CIRCUIT	8/3/1995	95830354.7	1/26/2000	0757357	EP
NMXS-0187.00/EP	Utility - ORG	Abandoned	HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES	9/29/1995	95830405.7	4/4/2001	0768672	EP
NMXS-0188.00/EP	Utility - ORG	Abandoned	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	11/30/1994	94308869.0			EP
NMXS-0189.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	12/2/1994	94308981.3	9/1/1999	0675439	EP
NMXS-0190.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	12/9/1994	94309218.9	3/24/1999	0675597	EP
NMXS-0194.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	5/24/1995	95303484.0	12/1/1999	0685853	EP
NMXS-0202.00/EP	Utility - ORG	Abandoned	CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES	10/27/1995	95307657.7	10/4/2001	0709853	EP
NMXS-0205.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	11/21/1995	95308348.2	2/2/2003	0717334	EP
NMXS-0206.00/EP	Utility - ORG	Abandoned	OUTPUT DRIVER CIRCUITRY WITH LIMITED OUTPUT HIGH VOLTAGE	11/28/1995	95308559.4			EP
NMXS-0207.00/EP	Utility - ORG	Abandoned	VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE	11/28/1995	95308560.2	6/27/2001	0718739	EP
NMXS-0208.00/EP	Utility - ORG	Abandoned	OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE	11/28/1995	95308561.0	2/20/2002	0718977	EP
NMXS-0209.00/EP	Utility - ORG	Abandoned	ADJUSTABLE CURRENT SOURCE	11/28/1995	95308562.8	10/31/2001	0718744	EP
NMXS-0210.00/EP	Utility - ORG	Abandoned	VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT	11/28/1995	95308543.8	3/15/2000	0718743	EP
NMXS-0211.00/EP	Utility - ORG	Abandoned	DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT	11/28/1995	95308563.6	8/30/2000	0718740	EP
NMXS-0214.00/EP	Utility - ORG	Abandoned	INTERNAL BUS CONTROL(FLASH MEMORY DEVICE TEST MODE TO DRIVE AN INTERNAL CONTROLBUS EXTERNALLY)	8/21/1995	95305818.7	11/10/1999	0698848	EP
NMXS-0215.00/EP	Utility - ORG	Abandoned	RESIDUAL CHARGE ELIMINATION FOR A MEMORY DEVICE	12/27/1995	95309478.5	5/5/2002	0721188	EP

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NMXS-0216.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/14/1995	95402815.5	2/25/1998	0718850	EP
NMXS-0217.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/11/1995	95402054.1	4/22/1998	0703584	EP
NMXS-0218.00/EP	Utility - ORG	Abandoned	CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM	5/15/1996	96401080.5	7/25/2001	0743650	EP
NMXS-0219.00/EP	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/14/1995	95402820.5	4/22/1998	0718849	EP
NMXS-0220.00/EP	Utility - ORG	Abandoned	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/17/1996	96470009.0	4/29/1998	0750244	EP
NMXS-0221.00/EP	Utility - ORG	Abandoned	RESISTANCE REFERENCE CIRCUIT	12/21/1995	95402912.0	5/19/1999	0718887	EP
NMXS-0222.00/EP	Utility - ORG	Abandoned	DIGITAL RAMP GENERATOR	5/29/1996	96401155.5	4/7/1999	0745996	EP
NMXS-0223.00/EP	Utility - ORG	Abandoned	SERIAL DICHOTOMIC METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT IMPLEMENTING SUCH METHOD	1/27/1995	95830023.8	12/12/2001	0724266	EP
NMXS-0224.00/EP	Utility - ORG	Abandoned	READING CIRCUIT FOR MULTILEVEL NON VOLATILE MEMORY CELL DEVICES	8/31/1995	95830127.7			EP
NMXS-0225.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR READING NON-VOLATILE MEMORIES	8/4/1995	95830357.0	3/28/2001	0757358	EP
NMXS-0226.00/EP	Utility - ORG	Abandoned	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT	8/23/1995	95830110.3	1/26/2000	0734024	EP
NMXS-0227.00/EP	Utility - ORG	Abandoned	READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE	4/28/1995	95830172.3	4/10/2002	0747903	EP
NMXS-0228.00/EP	Utility - ORG	Abandoned	MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS	7/28/1995	95830336.4	7/5/2000	0756285	EP
NMXS-0229.00/EP	Utility - ORG	Abandoned	THRESHOLD DETECTING DEVICE	8/4/1995	95830360.4	3/28/2001	0757852	EP
NMXS-0230.00/EP	Utility - ORG	Abandoned	CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES	7/28/1995	95830335.6	10/11/2000	0756220	EP
NMXS-0231.00/EP	Utility - ORG	Abandoned	FLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE	8/2/1995	95830351.3	5/23/2001	0758129	EP
NMXS-0232.00/EP	Utility - ORG	Abandoned	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/19/1995	95830253.1	1/26/2000	0750314	EP
NMXS-0233.00/EP	Utility - ORG	Abandoned	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	9/29/1995	95830406.5	1/26/2000	0766255	EP
NMXS-0234.00/EP	Utility - ORG	Abandoned	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	7/14/1995	95830302.6	1/26/2000	0753859	EP
NMXS-0235.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE	9/29/1995	95830407.3	11/1/1999	0766256	EP
NMXS-0236.00/EP	Utility - ORG	Abandoned	ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	3/29/1996	96830174.7	7/28/2004	0798735	EP
NMXS-0237.00/EP	Utility - ORG	Abandoned	DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY	6/20/1996	95830553.4			EP
NMXS-0237.01/EP	Utility - ORG	Abandoned	DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY	6/20/1996	96830352.9	5/28/2003	0782149	EP
NMXS-0238.00/EP	Utility - ORG	Abandoned	SYSTEM FOR DETERMINING THE PROGRAMMED/NON PROGRAMMED STATUS OF A MEMORY CELL	3/29/1996	96830163.0	11/12/2003	0798740	EP
NMXS-0239.00/EP	Utility - ORG	Abandoned	BOOST REGULATOR	1/24/1996	96830026.9	3/31/2004	0786777	EP
NMXS-0240.00/EP	Utility - ORG	Abandoned	UNBALANCED LATCH AND FUSE CIRCUIT INCLUDING THE SAME	7/28/1995	95830337.2	9/24/2003	0756379	EP
NMXS-0241.00/EP	Utility - ORG	Abandoned	REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS	3/29/1996	96830160.6	11/3/2004	0798729	EP
NMXS-0242.00/EP	Utility - ORG	Abandoned	TIME SHARING INTERNATIONAL BUS, PARTICULARLY FOR NON VOLATILE MEMORIES	3/20/1996	96830129.1	12/11/2002	0797209	EP

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NMXS-0243.00/EP	Utility - ORG	Abandoned	PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE LEVEL NON VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD	7/31/1995	95830347.1	4/19/2000	0757355	EP
NMXS-0244.00/EP	Utility - ORG	Abandoned	SUPPLY VOLTAGES SWITCHES CIRCUIT	6/20/1996	96830353.7	4/24/2002	0782268	EP
NMXS-0245.00/EP	Utility - ORG	Abandoned	METHOD AND PROGRAMMING DEVICE FOR DETECTING AN ERROR IN A MEMORY	12/29/1995	95830595.9			EP
NMXS-0246.00/EP	Utility - DIV	Abandoned	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS	10/31/1995	03012504.1			EP
NMXS-0245.01/EP	Utility - ORG	Abandoned	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS	10/31/1995	95830461.0	7/23/2003	0772200	EP
NMXS-0247.00/EP	Utility - ORG	Abandoned	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	7/24/1995	95830317.4	1/26/2000	0756286	EP
NMXS-0248.00/EP	Utility - ORG	Abandoned	NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	10/31/1995	95830456.0	3/15/2000	0772282	EP
NMXS-0249.00/EP	Utility - ORG	Abandoned	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	11/3/1995	95830466.9			EP
NMXS-0250.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE WITH IMPROVED YIELD AND RELIABILITY	9/29/1995	95830408.1	5/22/2002	0766174	EP
NMXS-0251.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR THE GENERATION OF A VOLTAGE AS A FUNCTION OF THE CONDUCTIVITY OF AN ELEMENTARY CELL OF A NON-VOLATILE MEMORY	3/29/1996	96830168.9	11/24/2004	0798743	EP
NMXS-0252.00/EP	Utility - ORG	Abandoned	ZERO CONSUMPTION POWER-ON-RESET	2/2/1996	96830046.7	11/13/2002	0788114	EP
NMXS-0253.00/EP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES	3/29/1996	96830167.1	11/7/2001	0798642	EP
NMXS-0254.00/EP	Utility - ORG	Abandoned	PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL	12/14/1995	95830520.3	9/13/2000	0779642	EP
NMXS-0255.00/EP	Utility - ORG	Abandoned	HIGH-VOLTAGE-RESISTANT MOS TRANSISTOR, AND CORRESPONDING MANUFACTURING PROCESS	3/29/1996	96830175.4	12/3/2003	0798785	EP
NMXS-0256.00/EP	Utility - ORG	Abandoned	NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION	1/31/1996	96830040.0			EP
NMXS-0257.00/EP	Utility - ORG	Abandoned	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURINGPROCESS	10/31/1995	95830459.4	10/12/2005	0772246	EP
NMXS-0258.00/EP	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS DEVICE FOR A REDUCED NUMBER OF PROGRAMMING CYCLES	2/29/1996	96830088.9			EP
NMXS-0259.00/EP	Utility - ORG	Abandoned	PROCESS OF FABRICATING TUNNEL-OXIDE NONVOLATILE MEMORY DEVICES	1/31/1996	96830039.2	11/26/2003	0788144	EP
NMXS-0260.00/EP	Utility - ORG	Abandoned	FABRICATION OF NATURAL TRANSISTORS IN A NONVOLATILE MEMORY PROCESS	1/22/1996	96830021.0	12/4/2002	0785570	EP
NMXS-0261.00/EP	Utility - ORG	Abandoned	MULTI-LEVEL MEMORY CIRCUITS AND CORRESPONDING READING AND WRITING METHODS	1/31/1996	96830044.2	8/24/2005	0788113	EP
NMXS-0262.00/EP	Utility - ORG	Abandoned	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	6/20/1996	96830355.2			EP
NMXS-0262.01/EP	Utility - NSPCT	Issued	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	96937493.3	1/10/2001	0906622	EP
NMXS-0263.00/EP	Utility - ORG	Abandoned	CLOCK CIRCUIT FOR READING A MULTILEVEL NON VOLATILE MEMORY CELLS DEVICE	6/28/1996	96830371.9	3/19/2003	0817200	EP
NMXS-0264.00/EP	Utility - ORG	Abandoned	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	96830354.5			EP
NMXS-0264.01/EP	Utility - NSPCT	Abandoned	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	96937494.1	1/3/2001	0906623	EP
NMXS-0265.00/EP	Utility - ORG	Abandoned	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	3/22/1996	96830144.0	6/12/2002	0797145	EP
NMXS-0266.00/EP	Utility - ORG	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	5/9/1996	96830267.9	3/19/2003	0806773	EP
NMXS-0267.00/EP	Utility - ORG	Abandoned	SENSING CIRCUIT FOR READING AND VERIFYING THE CONTENT OF A MEMORY CELL	4/30/1996	96830246.3			EP
NMXS-0268.00/EP	Utility - ORG	Abandoned	ERASING METHOD FOR A NON-VOLATILE MEMORY	12/29/1995	95830554.2	5/10/2000	0782145	EP
NMXS-0269.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR GENERATING A SYNCHRONIZING ATD SIGNAL	11/27/1996	96830598.7	4/9/2003	0845784	EP

PATENT
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MTI Docket	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS 0270.00/EP	Utility - DIV	Abandoned	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	4/30/1996	02015769.9			EP
NMXS-0270.01/EP	Utility - ORG	Abandoned	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	4/30/1996	96830245.5	2/26/2003	0782148	EP
NMXS-0271.00/EP	Utility - ORG	Abandoned	ERASE VOLTAGE CONTROL CIRCUIT FOR AN ELECTRICALLY ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830025.1	7/28/2004	0786779	EP
NMXS-0272.00/EP	Utility - ORG	Abandoned	METHOD FOR ERASING AN ELECTRICALLY PROGRAMMABLE AND ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830024.4	11/12/2003	0786778	EP
NMXS-0273.00/EP	Utility - ORG	Abandoned	PROGRAMMABLE DEVICE WITH BASIC MODULES ELECTRICALLY CONNECTED BY FLASH MEMORY CELLS	12/29/1995	95830552.6	5/23/2001	0782144	EP
NMXS-0274.00/EP	Utility - ORG	Abandoned	PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS	6/5/1996	96830318.0	3/12/2003	0811986	EP
NMXS-0275.00/EP	Utility - ORG	Abandoned	HIGH VOLTAGES DETECTOR CIRCUIT AND INTEGRATED CIRCUIT USING SAME	1/31/1996	96830043.4	3/31/2004	0788731	EP
NMXS-0276.00/EP	Utility - ORG	Abandoned	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE	1/31/1997	97830029.1	6/25/2003	0856886	EP
NMXS-0277.00/EP	Utility - ORG	Abandoned	MEMORY ARCHITECTURE FOR FLEXIBLE READING MANAGEMENT, PARTICULARLY FOR NON-VOLATILE MEMORIES, HAVING NOISE-IMMUNITY FEATURES, MATCHING DEVICE PERFORMANCE, AND HAVING OPTIMIZED THROUGHOUT	4/29/1996	96830239.8	1/2/2004	0805453	EP
NMXS-0278.00/EP	Utility - ORG	Abandoned	CIRCUITS AND METHODS FOR READ-ENABLING MEMORY DEVICES SYNCHRONOUSLY WITH THE REACHING OF THE MINIMUM FUNCTIONALITY CONDITIONS OF THE MEMORY CELLS AND READING CIRCUITS, PARTICULARLY FOR NON-VOLATILE MEMORIES	4/29/1996	96830238.0	9/24/2003	0805452	EP
NMXS-0279.00/EP	Utility - ORG	Abandoned	COLUMN MULTIPLEXER	5/13/1996	96830275.2	11/12/2003	0810606	EP
NMXS-0280.00/EP	Utility - ORG	Abandoned	DRIVER DEVICE FOR SELECTION LINES FOR A MULTIPLEXER, TO BE USED IN A WIDE RANGE OF SUPPLY VOLTAGES, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/29/1996	96830166.3	11/12/2003	0798742	EP
NMXS-0281.00/EP	Utility - ORG	Abandoned	PROGRAMMING AND READING MANAGEMENT ARCHITECTURE FOR MEMORY DEVICES, PARTICULARLY FOR TEST PURPOSES	3/29/1996	96830161.4	1/7/2004	0798726	EP
NMXS-0283.00/EP	Utility - ORG	Abandoned	DATA READING PATH MANAGEMENT ARCHITECTURE FOR A MEMORY DEVICE, PARTICULARLY FOR NON VOLATILE MEMORIES	3/29/1996	96830162.2	5/26/2004	0798727	EP
NMXS-0284.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY DEVICE HAVING OPTIMIZED MANAGEMENT OF DATA TRANSMISSION LINES	3/20/1996	96830128.3	1/2/2003	0797208	EP
NMXS-0285.00/EP	Utility - ORG	Abandoned	PULSE GENERATION CIRCUIT AND METHOD FOR SYNCHRONIZED DATA LOADING IN AN OUTPUT PRE-BUFFER	3/29/1996	96830169.7	11/12/2003	0798730	EP
NMXS-0287.00/EP	Utility - ORG	Abandoned	CONSTANT CURRENT SOURCE WITH REDUCED SENSITIVITY TO SUPPLY VOLTAGE AND PROCESS VARIATION	2/26/1996	96301270.3			EP
NMXS-0288.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS	5/8/1996	96303214.9	12/22/1999	0747800	EP
NMXS-0289.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE	12/20/1995	95309306.9	5/14/2003	0718741	EP
NMXS-0291.00/EP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR BIASING BIT LINES	5/15/1996	96303448.3	2/5/2003	0747824	EP
NMXS-0314.00/EP	Utility - ORG	Abandoned	CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES	8/9/1996	96305856.5	11/28/2001	0760518	EP
NMXS-0316.00/EP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/6/1996	96470004.1	6/23/1999	0735489	EP
NMXS-0317.00/EP	Utility - ORG	Abandoned	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OR NEGATIVE SUPPLY CIRCUIT	6/17/1996	96470011.6	5/20/1998	0757427	EP
NMXS-0318.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	9/2/1996	96460031.6	11/11/1998	0762428	EP
NMXS-0319.00/EP	Utility - ORG	Abandoned	HIGH VOLTAGE GENERATOR	12/24/1996	96402887.2	3/8/2000	0782243	EP

PATENT
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NMI-Docket No	Matter Type	Matter Status	Title	FileDate	SerialNo	GrantDate	PatentNo	Country
NMXS-0321.00/EP	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/17/1997	97460009.0	6/9/1999	0791933	EP
NMXS-0322.00/EP	Utility - ORG	Abandoned	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1/24/1997	97460008.2	12/2/1998	0788233	EP
NMXS-0323.00/EP	Utility - ORG	Abandoned	FLASH-EPROM WITH EMBEDDED EEPROM	4/15/1996	96830212.5	9/24/2003	0802569	EP
NMXS-0324.00/EP	Utility - ORG	Abandoned	DATA SENSING TIMING MODULATING CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/29/1996	96830165.5	11/12/2003	0798741	EP
NMXS-0326.00/EP	Utility - ORG	Abandoned	POWER ON RESET CIRCUIT WITH AUTO TURN OFF	4/30/1996	96830247.1	3/23/2005	0805556	EP
NMXS-0327.00/EP	Utility - ORG	Abandoned	UPROM CELL FOR LOW VOLTAGE SUPPLY	4/30/1996	96830243.0	2/18/2004	0806771	EP
NMXS-0328.00/EP	Utility - ORG	Abandoned	BIASING CIRCUIT FOR UPROM CELLS WITH LOW VOLTAGE SUPPLY	4/30/1996	96830242.2	2/11/2004	0805456	EP
NMXS-0329.00/EP	Utility - ORG	Abandoned	ROW DECODER FOR LOW POWER SUPPLY	5/24/1996	96830299.2	10/15/2003	0809254	EP
NMXS-0330.00/EP	Utility - ORG	Abandoned	I/V CONVERTER FOR LOW SUPPLY NON VOLATILE MEMORY CELLS	6/18/1996	96830344.6	12/17/2003	0814480	EP
NMXS-0331.00/EP	Utility - ORG	Abandoned	LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY DEVICE WITH VOLTAGE BOOSTING	6/18/1996	96830345.3	3/20/2002	0814481	EP
NMXS-0332.00/EP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS	6/18/1996	96830346.1	8/27/2003	0814482	EP
NMXS-0333.00/EP	Utility - ORG	Abandoned	MOS CAPACITOR WITH WIDE VOLTAGE AND FREQUENCY OPERATING RANGES	7/30/1996	96830420.4	5/24/2006	0822601	EP
NMXS-0334.00/EP	Utility - ORG	Abandoned	BIDIRECTIONAL CHARGE PUMP	8/2/1996	96830441.0	4/2/2003	0822556	EP
NMXS-0335.00/EP	Utility - ORG	Abandoned	BICMOS NEGATIVE CHARGE PUMP	11/14/1996	96830581.3	2/27/2002	0843402	EP
NMXS-0336.00/EP	Utility - ORG	Abandoned	IMPROVED POSITIVE CHARGE PUMP	10/11/1996	96830521.9	2/6/2002	0836268	EP
NMXS-0337.00/EP	Utility - ORG	Abandoned	OUTPUT STAGE FOR A MEMORY DEVICE AND FOR LOW VOLTAGE APPLICATIONS	7/24/1996	96830411.3	5/26/2004	0821362	EP
NMXS-0338.00/EP	Utility - ORG	Abandoned	LOW NOISE OUTPUT BUFFER FOR SEMICONDUCTOR ELECTRONIC CIRCUITS	7/31/1996	96830430.3			EP
NMXS-0339.00/EP	Utility - ORG	Abandoned	HIGH VOLTAGE TOLERANCE OUTPUT STAGE	7/24/1996	96830413.9	10/9/2002	0821484	EP
NMXS-0340.00/EP	Utility - ORG	Abandoned	SINGLE-CELL REFERENCE SIGNAL GENERATING CIRCUIT FOR READING NONVOLATILE MEMORY	6/18/1996	96830348.7	9/17/2003	0814484	EP
NMXS-0341.00/EP	Utility - ORG	Abandoned	INTEGRATED DEVICE WITH PADS	3/6/1996	96830095.4			EP
NMXS-0342.00/EP	Utility - ORG	Abandoned	NMOS NEGATIVE CHARGE PUMP	1/23/1997	97830014.3	6/22/2005	0855788	EP
NMXS-0343.00/EP	Utility - ORG	Abandoned	ADDRESS TRANSITION DETECTION CIRCUIT	3/6/1996	96830096.2	9/12/2001	0794618	EP
NMXS-0344.00/EP	Utility - ORG	Abandoned	METHOD FOR RECOVERING FAILED MEMORY	3/21/1996	96830136.6	7/3/2002	0797147	EP
NMXS-0345.00/EP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR GENERATING A POWER-ON RESET SIGNAL	3/29/1996	96830177.0	6/18/2003	0798728	EP
NMXS-0346.00/EP	Utility - ORG	Abandoned	GAIN MODULATED SENSE AMPLIFIER, PARTICULARLY FOR MEMORY DEVICES	3/29/1996	96830184.8	2/5/2003	0798732	EP
NMXS-0347.00/EP	Utility - ORG	Abandoned	CIRCUIT AND METHOD TO ADJUST MEMORY TIMING	3/29/1996	96830176.2	12/3/2003	0798744	EP
NMXS-0348.00/EP	Utility - ORG	Abandoned	STANDBY VOLTAGE BOOSTING STAGE AND METHOD FOR A MEMORY DEVICE	3/29/1996	96830178.8	10/17/2001	0800259	EP
NMXS-0349.00/EP	Utility - ORG	Abandoned	VOLTAGE BOOSTER FOR MEMORY DEVICES	3/29/1996	96830179.6	10/17/2001	0800260	EP
NMXS-0350.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR THE SWITCHING OF SUPPLY VOLTAGES IN ELECTRICALLY PROGRAMMABLE AND CANCELABLE NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	4/5/1996	96830193.7	3/3/2004	0800177	EP
NMXS-0351.00/EP	Utility - ORG	Abandoned	AUTO-SAVING CIRCUIT FOR PROGRAMMING CONFIGURATION ELEMENTS IN NON-VOLATILE MEMORY DEVICES	4/5/1996	96830191.1	2/2/2005	0800178	EP
NMXS-0352.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE MEMORY CELLS	4/5/1996	96830192.9	7/2/2003	0800176	EP
NMXS-0353.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR DETECTING THE COINCIDENCE BETWEEN A BINARY INFORMATION UNIT STORED THEREIN AND AN EXTERNAL DATUM	3/22/1996	96830148.2	8/14/2002	0797144	EP
NMXS-0354.00/EP	Utility - ORG	Abandoned	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	4/18/1996	96830216.6	3/12/2003	0802541	EP
NMXS-0355.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH ROW REDUNDANCY	4/18/1996	96830217.4	1/30/2002	0802483	EP
NMXS-0356.00/EP	Utility - ORG	Abandoned	REDUNDANCY MEMORY REGISTER	4/18/1996	96830215.8	2/20/2002	0802482	EP
NMXS-0357.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR TRANSFERRING REDUNDANCY DATA OF A REDUNDANCY CIRCUIT INSIDE A MEMORY DEVICE BY MEANS OF A TIME-SHARED APPROACH	6/6/1996	96830323.0	1/2/2002	0811917	EP

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MTI Docket No	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0358.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH ROW AND COLUMN REDUNDANCY CIRCUITS AND A TIME-SHARED REDUNDANCY CIRCUIT TEST ARCHITECTURE.	6/6/1996	96830326.3	10/1/2003	0811988	EP
NMXS-0359.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH	6/6/1996	96830324.8	1/30/2002	0811918	EP
NMXS-0360.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY	6/6/1996	96830325.5	12/12/2001	0811919	EP
NMXS-0361.00/EP	Utility - ORG	Abandoned	PRE-CHARGE STEP DETERMINING CIRCUIT OF A GENERIC BIT LINE, PARTICULARLY FOR NON-VOLATILE MEMORIES	4/9/1996	96830197.8	3/10/2004	0801393	EP
NMXS-0362.00/EP	Utility - ORG	Abandoned	READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE	6/18/1996	96830347.9	8/27/2003	0814483	EP
NMXS-0363.00/EP	Utility - ORG	Abandoned	MULTILEVEL NON VOLATILE MEMORY DEVICE	8/22/1996	96830455.0	4/9/2003	0825611	EP
NMXS-0364.00/EP	Utility - ORG	Abandoned	CHARGE INJECTION CIRCUIT FOR AN INSULATED GATE MOS TRANSISTOR AND COMPUTING DEVICES USING THE SAME	9/30/1996	96830492.3	2/25/2004	0833267	EP
NMXS-0366.00/EP	Utility - ORG	Abandoned	CONTROL CIRCUIT OF AN OUTPUT BUFFER	9/19/1996	96830475.8	3/19/2003	0831492	EP
NMXS-0367.00/EP	Utility - ORG	Abandoned	PROTECTION CIRCUIT FOR REDUNDANCY REGISTER SET-UP CELLS OF ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICES	10/30/1996	96830553.2	3/19/2003	0840327	EP
NMXS-0368.00/EP	Utility - ORG	Abandoned	PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES	12/24/1996	96830646.4			EP
NMXS-0369.00/EP	Utility - ORG	Allowed	METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC	9/30/1996	96830493.1			EP
NMXS-0370.00/EP	Utility - ORG	Abandoned	PROCESS FOR DEPOSING A STRATIFIED DIELECTRIC STRUCTURE FOR ENHANCING THE PLANARITY OF SEMICONDUCTOR ELECTRONIC DEVICES	12/24/1996	96830645.6			EP
NMXS-0371.00/EP	Utility - ORG	Abandoned	PROCESS FOR DEPOSING A MULTIPLE DIELECTRIC STRUCTURE FOR ENHANCING THE PLANARITY OF SEMICONDUCTOR ELECTRONIC DEVICES	12/24/1996	96830644.9			EP
NMXS-0372.00/EP	Utility - ORG	Abandoned	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	9/30/1996	96830494.9	4/2/2003	0833340	EP
NMXS-0373.00/EP	Utility - ORG	Abandoned	STAIRCASE ADAPTIVE VOLTAGE GENERATOR CIRCUIT	2/28/1997	97830084.6			EP
NMXS-0379.00/EP	Utility - ORG	Abandoned	HIGH VOLTAGE CAPACITOR	7/23/1997	97830384.0			EP
NMXS-0383.00/EP	Utility - ORG	Abandoned	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	12/24/1996	96830649.8	5/23/2007	0851485	EP
NMXS-0384.00/EP	Utility - ORG	Abandoned	MEMORY BLOCK FOR REALIZING SEMICONDUCTOR MEMORY DEVICES AND CORRESPONDING MANUFACTURING PROCESS	5/23/1997	96830657.1			EP
NMXS-0384.01/EP	Utility - ORG	Abandoned	MEMORY BLOCK FOR REALIZING SEMICONDUCTOR MEMORY DEVICES AND CORRESPONDING MANUFACTURING PROCESS	5/23/1997	97830238.8			EP
NMXS-0385.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS	7/16/1997	97830359.2	3/23/2005	0892430	EP
NMXS-0386.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE WITH MULTIFUNCTIONAL TERMINALS	3/28/1997	97830151.3	7/28/2004	0867885	EP
NMXS-0387.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	12/5/1996	96830612.6	7/9/2003	0833348	EP
NMXS-0388.00/EP	Utility - ORG	Abandoned	METHOD OF PRODUCING MOSFET TRANSISTORS BY MEANS OF TILTED IMPLANTS	4/21/1997	97830182.8	8/1/2007	0874389	EP
NMXS-0389.00/EP	Utility - ORG	Abandoned	METHOD FOR DATA SAVING IN CASE OF UNWANTED PROGRAMMING CYCLE INTERRUPTIONS OF A NON VOLATILE MEMORY AND NON VOLATILE MEMORY	4/30/1998	98830265.9	7/2/2003	0953984	EP
NMXS-0390.00/EP	Utility - ORG	Abandoned	PROCESS FOR THE REPAIR OF FLOATING-GATE NON-VOLATILE MEMORIES DAMAGED BY PLASMA TREATMENT	12/16/1996	96830624.1	3/27/2002	0848422	EP
NMXS-0391.00/EP	Utility - ORG	Abandoned	VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARY FOR A NONVOLATILE MEMORY	2/28/1997	97830085.3	5/7/2003	0862183	EP
NMXS-0392.00/EP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING A NATIVE MOS P-CHANNEL TRANSISTOR WITH A PROCESS FOR MANUFACTURING NON-VOLATILE MEMORIES	8/27/1997	97830428.5	1/19/2005	0902466	EP
NMXS-0393.00/EP	Utility - ORG	Abandoned	DEPOSITION METHOD OF A DIELECTRIC STRUCTURE FOR PLANARIZING MEMORY DEVICES	6/30/1997	97830328.7			EP

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MII-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0394.00/EP	Utility - ORG	Issued	PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED ELECTRONIC MEMORY DEVICES HAVING A VIRTUAL GROUND CELLS MATRIX	8/27/1997	97830427.7	10/15/2008	0902465	EP
NMXS-0401.00/EP	Utility - ORG	Abandoned	SENSE AMPLIFIER CONTROL OF A MEMORY DEVICE	4/22/1998	98303111.3			EP
NMXS-0407.00/EP	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY WITH INTERNAL REFRESH MEANS	10/21/1997	97460043.9	8/4/1999	0838826	EP
NMXS-0410.00/EP	Utility - ORG	Abandoned	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	1/29/1997	97400209.9	10/7/1998	0788047	EP
NMXS-0412.00/EP	Utility - ORG	Abandoned	MEMORY WITH IMPROVED READING TIME	10/15/1997	97402429.1	12/11/2002	0838824	EP
NMXS-0416.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	11/21/1997	97402807.8	10/20/1999	0849740	EP
NMXS-0417.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY	11/21/1997	97402806.0	10/20/1999	0849739	EP
NMXS-0418.00/EP	Utility - ORG	Abandoned	MEMORY WITH READ PROTECTED ZONES	11/28/1997	97402869.8	6/9/1999	0851359	EP
NMXS-0421.00/EP	Utility - ORG	Abandoned	DIFFERENTIAL AMPLIFIER IN A MOS TRANSISTORS STRUCTURE	11/5/1998	98402753.2			EP
NMXS-0422.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR THE FILTERING OF A PULSE SIGNAL	5/28/1998	98401287.2			EP
NMXS-0427.00/EP	Utility - ORG	Abandoned	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	11/5/1997	97470027.0	8/4/1999	0845787	EP
NMXS-0429.00/EP	Utility - ORG	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	3/20/1998	98400661.9	6/18/2003	0875899	EP
NMXS-0430.00/EP	Utility - NSPCT	Issued	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1998	98903102.6	5/16/2001	0954865	EP
NMXS-0431.00/EP	Utility - ORG	Abandoned	VARIABLE FREQUENCY LOAD PUMP	7/17/1998	98401807.7	1/23/2002	0898356	EP
NMXS-0432.00/EP	Utility - ORG	Abandoned	PROCESS OF FINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE	4/15/1997	97830174.5			EP
NMXS-0433.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE WITH REDUCED POWER DISSIPATION	4/3/1997	97830160.4	7/2/2003	0869506	EP
NMXS-0436.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLAITLE MEMORY DEVICES	8/29/1997	97830435.0	11/12/2003	0899742	EP
NMXS-0438.00/EP	Utility - DIV	Abandoned	PROCESS OF FINAL PASSIVATION OF INTEGRATED CIRCUIT DEVICES	4/15/1997	03077997.9			EP
NMXS-0438.01/EP	Utility - ORG	Abandoned	PROCESS OF FINAL PASSIVATION OF INTEGRATED CIRCUIT DEVICES	4/15/1997	97830173.7			EP
NMXS-0439.00/EP	Utility - ORG	Abandoned	PARALLEL ANALOG PROGRAMMING OF FLASH DEVICES	5/9/1997	97830216.4	7/30/2003	0877386	EP
NMXS-0440.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE GENERATOR FOR GENERATING MEMORY DEVICES WITH REDUNDANCY	10/20/1997	97830525.8	1/2/2004	0911747	EP
NMXS-0442.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR READING A NON-VOLATILE MEMORY	7/20/1998	98830438.2	12/3/2003	0974976	EP
NMXS-0443.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR ANALOG PROGRAMMING OF FLASH EEPROM WITH AUTOVERIFY	9/29/1997	97830477.2	4/23/2003	0905712	EP
NMXS-0446.00/EP	Utility - ORG	Issued	DECODER FOR ERASING A SINGLE ROW IN A FLASH MEMORY	11/26/1997	97830625.6	6/30/2010	0920023	EP
NMXS-0449.00/EP	Utility - ORG	Abandoned	INTERLEAVED ARCHITECTURE FOR PARALLEL PROGRAMMING OF FLASH DEVICES	10/28/1997	97830550.6	3/21/2007	0913835	EP
NMXS-0451.00/EP	Utility - ORG	Issued	SECTORED SEMICONDUCTOR MEMORY DEVICE WITH CONFIGURABLE MEMORY SECTOR ADDRESS	9/24/1997	97830467.3	3/31/2010	EP0905704	EP
NMXS-0454.00/EP	Utility - ORG	Abandoned	DETERMINATION OF THICKNESS OF A DENUDED ZONE IN A SILICON WAFER	7/15/1997	97830354.3	9/12/2007	0898298	EP
NMXS-0455.00/EP	Utility - ORG	Abandoned	HIGH-VOLTAGE DRIVER CIRCUIT FOR THE DECODING PHASE IN MULTILEVEL NON-VOLATILE MEMORY DEVICES	12/31/1997	97830738.7			EP
NMXS-0456.00/EP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	5/29/1998	98830332.7	5/19/2004	0961288	EP
NMXS-0457.00/EP	Utility - ORG	Abandoned	CONTROLLED HOT-ELECTRON PROGRAMMING OF NON VOLATILE MEMORY CELLS	10/9/1997	97830504.3			EP
NMXS-0458.00/EP	Utility - ORG	Abandoned	SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF	12/22/1997	97830693.4	3/2/2005	0926687	EP
NMXS-0459.00/EP	Utility - ORG	Abandoned	COMPENSATED VOLTAGE REGULATOR	9/30/1997	97830484.8	7/23/2003	0905710	EP
NMXS-0460.00/EP	Utility - ORG	Abandoned	METHOD OF MULTI-LEVEL PROGRAMMING A NON VOLATILE MEMORY AND MULTI-LEVEL NONVOLATILE MEMORY	11/3/1997	97830566.2	7/23/2003	0913832	EP
NMXS-0461.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR GENERATING AN ATD SIGNAL TO REGULATE THE ACCESS TO A NON-VOLATILE MEMORY	11/5/1997	97830576.1	3/17/2004	0915477	EP
NMXS-0462.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR REGULATING THE LENGTH OF AN ATD PULSE SIGNAL	11/5/1997	97830573.8	3/3/2004	0915476	EP

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MII DcktNo	MasterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0463.00/EP	Utility - ORG	Abandoned	IMPROVED BOOSTING CIRCUIT, PARTICULARLY FOR A MEMORY DEVICE	11/5/1997	97830572.0	4/28/2010	915478	EP
NMXS-0464.00/EP	Utility - ORG	Abandoned	IMPROVED OUTUPUT CIRCUIT FOR INTEGRATED CIRCUITS	10/24/1997	97830542.3	4/9/2003	0911974	EP
NMXS-0465.00/EP	Utility - ORG	Issued	TEMPERATURE CORRELATED VOLTAGE GENERATOR CIRCUIT AND CORRESPONDING VOLTAGE REGULATOR FOR A SINGLE POWER MEMORY CELL, PARTICULARLY OF THE FLASH TYPE	11/5/1997	97830574.6	3/4/2009	0915407	EP
NMXS-0466.00/EP	Utility - ORG	Abandoned	HIGH VOLTAGE REGULATOR AND CORRESPONDING VOLTAGE REGULATION METHOD	11/5/1997	97830575.3	2/19/2003	0915408	EP
NMXS-0470.00/EP	Utility - ORG	Pending	DATA PROTECTION METHOD FOR A SEMICONDUCTOR MEMORY AND CORRESPONDING PROTECTED MEMORY DEVICE	12/24/1997	97830717.1			EP
NMXS-0473.00/EP	Utility - ORG	Abandoned	ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS	7/28/1998	98114061.9	9/21/2005	0928003	EP
NMXS-0473.01/EP	Utility - ORG	Abandoned	ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS	7/28/1998	97830739.5			EP
NMXS-0476.00/EP	Utility - ORG	Abandoned	MEMORY CELL INTEGRATED STRUCTURE AND CORRESPONDING BIASING DEVICE	4/22/1998	98830238.6	9/28/2005	0952615	EP
NMXS-0480.00/EP	Utility - ORG	Abandoned	LOW CONSUPTION TTL-CMOS INPUT BUFFER STAGE	12/31/1997	97830743.7			EP
NMXS-0481.00/EP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1998	98830391.3			EP
NMXS-0481.01/EP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	99925682.8	4/10/2002	1097454	EP
NMXS-0482.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY CAPABLE OF AUTONOMOUSLY EXECUTING A PROGRAM	7/2/1999	99202169.1			EP
NMXS-0483.00/EP	Utility - DIV	Issued	METHOD AND CIRCUIT TO SELECT THE STANDARD OR LOW VOLTAGE WORKING RANGE OF A SEMICONDUCTOR NON VOLATILE MEMORY	2/26/1998	04023387.6	12/17/2008	1498905	EP
NMXS-0483.01/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT TO SELECT THE STANDARD OR LOW VOLTAGE WORKING RANGE OF A SEMICONDUCTOR NON VOLATILE MEMORY	2/26/1998	98830104.0			EP
NMXS-0484.00/EP	Utility - ORG	Abandoned	CONTROLLED ERASING FOR ANALOG & MULTILEVEL STORAGE IN FLASH EEPROM DEVICE	1/22/1998	98830024.0	6/9/2004	0932161	EP
NMXS-0485.00/EP	Utility - ORG	Abandoned	ESD PROTECTION NETWORK ON SEMICONDUCTOR CIRCUIT STRUCTURES	12/31/1997	97830741.1	9/20/2006	0932202	EP
NMXS-0486.00/EP	Utility - ORG	Abandoned	METHOD AND A CIRCUIT FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	12/31/1997	97830747.9	2/18/2009	0932203	EP
NMXS-0487.00/EP	Utility - ORG	Abandoned	HIGH STORAGE CAPACITY NON-VOLATILE MEMORY	5/27/1998	98830324.4	11/26/2003	0961287	EP
NMXS-0488.00/EP	Utility - ORG	Abandoned	PROCESS FOR THE FABRICATION OF A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	6/30/1998	98830388.9	11/14/2001	0971415	EP
NMXS-0495.00/EP	Utility - ORG	Issued	IN-SITU DEPOSITION AND DOPING PROCESS FOR POLYCRYSTALLINE SILICON LAYERS AND THE RESULTING DEVICE	11/14/1997	97830603.3	1/7/2009	EP0917185	EP
NMXS-0500.00/EP	Utility - ORG	Abandoned	LOW VOLTAGE NON VOLATILE MEMORY SENSE AMPLIFIER	2/13/1998	98830064.6	10/20/2004	0936627	EP
NMXS-0504.00/EP	Utility - ORG	Abandoned	PIPELINED NON-BLOCKING LEVEL TWO CACHE SYSTEM WITH INHERENT TRANSACTION COLLISION-AVOIDANCE	12/1/1999	99309641.1	3/14/2007	1006448	EP
NMXS-0505.00/EP	Utility - ORG	Abandoned	NON VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING A READ AND/OR WRITE PROTECTABLE AREA AND ELECTRONIC SYSTEM INCLUDINT IT	10/21/1998	98402620.3	6/4/2003	0918335	EP
NMXS-0507.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY	9/10/1998	98460036.1	11/15/2000	0903750	EP
NMXS-0510.00/EP	Utility - ORG	Abandoned	RADIO FREQUENCE SIGNAL DETECTOR FOR CONTACT-LESS SMARTCARD	9/17/1998	98402303.6	5/24/2006	0903688	EP
NMXS-0511.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR THE GENERATION OF VOLTAGE FOR THE PROGRAMMING OR ERASURE OF A MEMORY THAT USES FLOATING-GATE TRANSISTORS	10/12/1998	98470024.5	7/18/2001	0913836	EP
NMXS-0512.00/EP	Utility - ORG	Abandoned	SPSK DEMODULATION DEVICE	1/20/1999	99400126.1	6/13/2001	0932283	EP
NMXS-0516.00/EP	Utility - ORG	Abandoned	DIFFERENCIAL READING OF NONVOLATILE MEMORY CELLS WITHOUT USING A REFERENCE	5/29/1998	98830333.5	12/17/2003	0961285	EP

PATENT
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MTI Docket No	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0518.00/EP	Utility - ORG	Abandoned	SENSING ARRANGEMENT FOR A MULTILEVEL SEMICONDUCTOR MEMORY DEVICE	8/7/1998	98830491.1	11/2/2005	0978844	EP
NMXS-0522.00/EP	Utility - ORG	Abandoned	METHOD FOR READING A MULTI-LEVEL MEMORY CELL	3/27/1998	98830188.3	11/17/2004	0945869	EP
NMXS-0523.00/EP	Utility - ORG	Abandoned	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	9/30/1998	98830570.2	5/6/2004	0991075	EP
NMXS-0524.00/EP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/22/1998	98830443.2			EP
NMXS-0524.01/EP	Utility - ORG	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/22/1998	98120033.0	2/11/2009	0975020	EP
NMXS-0524.02/EP	Utility - DIV	Pending	METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/22/1998	08021768.0			EP
NMXS-0525.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING MOS TRANSISTORS WITH SALICIZED JUNCTIONS AND NON-SALICIZED RESISTORS	7/22/1998	98830444.0	11/2/2005	0975021	EP
NMXS-0526.00/EP	Utility - ORG	Pending	METHOD FOR INTEGRATING RESISTORS AND ESD SELF-PROTECTED TRANSISTORS WITH MEMORY MATRIX	12/16/1998	98830757.5			EP
NMXS-0532.00/EP	Utility - ORG	Abandoned	A SIMPLIFIED PROCESS FOR DEFINING THE TUNNEL AREA IN SEMICONDUCTOR NON-VOLATILE NON-ALIGNED MEMORY CELLS	10/15/1998	98830614.8	2/25/2004	0994513	EP
NMXS-0533.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY DEVICE WITH ROW REDUNDANCY	5/12/1999	99830286.3	7/30/2003	1052572	EP
NMXS-0534.00/EP	Utility - ORG	Abandoned	IMPROVED PROCESS TO MANUFACTURING AN INTEGRATE MOS TRANSISTOR ON A SEMICONDUCTOR SUBSTRATE	12/29/1998	98830794.8			EP
NMXS-0535.00/CP	Utility - ORG	Abandoned	PROCESS FOR DEFINITION OF OPENINGS IN A DIELECTRIC LAYER	9/28/1998	98830564.5			CP
NMXS-0536.00/EP	Utility - ORG	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/23/1998	98830645.2	5/19/2010	0986100	EP
NMXS-0536.01/EP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/23/1998	98830532.2			EP
NMXS-0537.00/EP	Utility - ORG	Abandoned	IMPROVED SELECTIVE SALICIZATION PROCESS FOR SEMICONDUCTOR SUBSTRATE INTEGRATED ELECTRONIC DEVICES	12/29/1998	98830793.0	10/26/2005	1017088	EP
NMXS-0538.00/EP	Utility - ORG	Abandoned	METHOD FOR CORRECTING ERRORS IN A MULTILEVEL MEMORY WITHOUT ADDITIONAL CELLS	2/25/1999	99830099.0	2/5/2003	1035473	EP
NMXS-0539.00/EP	Utility - ORG	Abandoned	MULTILEVEL NON VOLATILE MEMORY AND READING METHOD THEREFOR	2/10/1999	99830071.9	4/28/2004	1028433	EP
NMXS-0540.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT TO TEST THE VIRGIN CELLS IN A MULTILEVEL MEMORY	10/29/1998	98830654.4	8/10/2005	0997913	EP
NMXS-0541.00/EP	Utility - ORG	Abandoned	N-STAGE CONVERTER FOR READING/WRITING ANALOG FLASH CELLS	10/20/1998	98830626.2	1/11/2006	0997912	EP
NMXS-0545.00/EP	Utility - ORG	Pending	PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH-PERFORMANCE LOGIC CIRCUITRY	11/26/1998	98830709.6			EP
NMXS-0546.00/EP	Utility - ORG	Abandoned	LEVELS RESTORE IN ANALOG FLASH EEPROM	9/15/1998	98830536.3	2/9/2005	0987715	EP
NMXS-0547.00/EP	Utility - ORG	Abandoned	METHOD OF FABRICATION OF A NO-FIELD MOS TRANSISTOR	4/6/1999	99830194.9			EP
NMXS-0551.00/EP	Utility - ORG	Issued	CHIP OUTLINE BAND (COB) STRUCTURE FOR INTEGRATED CIRCUITS	1/15/1999	99830007.3	12/1/2010	1020907	EP
NMXS-0552.00/EP	Utility - ORG	Abandoned	FIELD-EFFECT TRANSISTOR AND CORRESPONDING MANUFACTURING METHOD	11/19/1998	98830694.0			EP
NMXS-0554.00/EP	Utility - ORG	Issued	PROCESS FOR MANUFACTURING SALICIZED ELECTRONIC DEVICES WITH POWER MASKS	12/22/1998	98830771.6	8/5/2009	1014441	EP
NMXS-0555.00/EP	Utility - ORG	Abandoned	PROCESS OF MANUFACTURE OF A NON VOLATILE MEMORY WITH ELECTRIC CONTINUITY OF THE COMMON SOURCE LINES	4/14/1999	99830211.1			EP
NMXS-0557.00/EP	Utility - ORG	Abandoned	FLASH COMPATIBLE EEPROM	6/22/1999	99830390.3	2/2/2005	1067557	EP
NMXS-0558.00/EP	Utility - ORG	Abandoned	METHOD FOR READING A MEMORY, PARTICULARLY A NON-VOLATILE MEMORY	12/30/1998	98830801.1	7/18/2007	1017059	EP
NMXS-0560.00/EP	Utility - ORG	Pending	IMPROVED PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	2/26/1999	99830101.4			EP
NMXS-0561.00/EP	Utility - ORG	Abandoned	IMPROVED PROCESS FOR MANUFACTURING ELECTRONIC MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	2/26/1999	99830100.6	10/13/2004	1032035	EP

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MIT-DocketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0565.00/EP	Utility - ORG	Abandoned	METHOD FOR AUTOALIGNING OVERLAPPED LINES OF CONDUCTOR MATERIAL PROVIDED IN INTEGRATED ELECTRONIC CIRCUITS	5/31/1999	99830336.6	8/17/2005	1058304	EP
NMXS-0566.00/EP	Utility - DIV	Issued	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/21/1999	06012616.6	12/16/2009	EP1715491	EP
NMXS-0566.01/EP	Utility - ORG	Abandoned	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/21/1999	99830235.0	8/9/2006	1047078	EP
NMXS-0568.00/EP	Utility - ORG	Abandoned	ESD PROTECTION DEVICE FOR SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURE	7/30/1999	99830491.9	5/26/2004	1073119	EP
NMXS-0569.00/EP	Utility - ORG	Abandoned	A SEMICONDUCTOR DEVICE WITH IMPROVED CHIP-LEADS INTERCONNECTIONS AND A PROCESS FOR MANUFACTURING THEREOF	2/11/1999	99830072.7	7/26/2006	1028464	EP
NMXS-0570.00/EP	Utility - ORG	Abandoned	READING METHOD FOR MULTILEVEL MEMORIES WITH SELECTIVE AMPLIFICATION OF CURRENT	2/26/1999	99830108.9	4/28/2004	1031991	EP
NMXS-0571.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATING FOR A CAPACITIVE LOAD	5/30/1999	99830418.2	11/12/2003	1065580	EP
NMXS-0578.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT STRUCTURE COMPRISING CAPACITOR ELEMENT AND CORRESPONDING MANUFACTURING PROCESS	10/12/1998	98830597.5			EP
NMXS-0579.00/EP	Utility - ORG	Abandoned	CONTENT ADDRESSABLE MEMORY PROTECTION CIRCUIT AND METHOD	5/1/1999	99201363.1			EP
NMXS-0583.00/EP	Utility - ORG	Issued	MANUFACTURING PROCESS OF INTEGRATED SOI CIRCUIT STRUCUTRES	4/30/1999	99830262.4	2/18/2009	1049156	EP
NMXS-0584.00/EP	Utility - ORG	Abandoned	COMMUNICATIONS SYSTEM AND METHOD FOR REDUCING THE EFFECTS OF TRANSMITTER NON-LINEAR DISTORTION ON A RECEIVED SIGNAL	6/14/2000	00305020.0	1/31/2007	1061689	EP
NMXS-0585.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES	5/26/1999	99470014.4	11/22/2000	0962938	EP
NMXS-0589.00/CP	Utility - ORG	Abandoned	SECURED EEPROM WITH UV ERASING DETECTION MEANS	11/26/1999	99460065.8	1/21/2004	1006592	EP
NMXS-0592.00/EP	Utility - ORG	Abandoned	READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATION VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	6/21/1999	99830382.0	3/5/2003	1063654	EP
NMXS-0593.00/EP	Utility - ORG	Abandoned	ERASING AND PARALLEL REWRITING CIRCUIT FOR MEMORY CELL BLOCKS, PARTICULARLY FOR ANALOG FLASH CELLS, AND RELATED OPERATING METHOD	6/21/1999	99830381.2	8/9/2006	1065868	EP
NMXS-0594.00/EP	Utility - ORG	Abandoned	MEMORY ARRAY WITH ROW AND COLUMN SECTOR ORGANIZATION	4/21/1999	99830236.8			EP
NMXS-0596.00/EP	Utility - ORG	Abandoned	GERARCHIC SECTOR BIASING FOR FLASH MEMORIES	6/24/1999	99830396.0	11/17/2004	1063653	EP
NMXS-0597.00/EP	Utility - ORG	Abandoned	SYNCHRONOUS MULTILEVEL NON VOLATILE MEMORY AND RELATED READING METHOD	5/31/1999	99830331.7	3/29/2006	1058269	EP
NMXS-0598.00/EP	Utility - ORG	Abandoned	A READING CIRCUIT FOR A SEMICONDUCTOR MEMORY	6/25/1999	99830403.4	11/23/2005	1071094	EP
NMXS-0599.00/EP	Utility - ORG	Abandoned	BIASING THE DRAIN OF A MEMORY CELL DURING READING	6/4/1999	99830348.1	3/21/2007	1058270	EP
NMXS-0603.00/EP	Utility - ORG	Issued	METHOD FOR PROGRAMMING MULTILEVEL NON-VOLATILE MEMORIES BY APPLYING SEQUENCES OF PULSES WITHOUT VERIFY	8/3/1999	99830501.5	10/26/2005	1074995	EP
NMXS-0604.00/EP	Utility - ORG	Abandoned	ROW DECODER WITH REDUCED POWER CONSUMPTION DURING SWITCHING	6/4/1999	99830345.7	12/15/2004	1058271	EP
NMXS-0605.00/EP	Utility - ORG	Abandoned	ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE	6/17/1999	99830378.8	3/8/2006	1061525	EP
NMXS-0605.00/EP	Utility - ORG	Issued	METHOD FOR READING DATA FROM A NON-VOLATILE MEMORY DEVICE WITH AUTODETECT BURST MODE READING AND CORRESPONDING READING CIRCUIT	11/25/1999	99830722.7	2/25/2009	1103977	EP
NMXS-0608.00/EP	Utility - ORG	Issued	VERTICAL BIPOLAR TRANSISTOR WITH HIGH GAIN OBTAINED BY MEANS OF A...	7/21/1999	99830468.7	4/21/2010	1071133	EP
NMXS-0611.00/EP	Utility - ORG	Pending	NON-VOLATILE MEMORY WITH FUNCTIONAL CAPABILITY OF SIMULTANEOUS MODIFICATION OF THE CONTENT AND BURST MODE READ OR PAGE MODE READ	7/30/1999	99830495.0			EP
NMXS-0612.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY WITH BURST AND PAGE READ CAPABILITY DURING ELECTRICAL ALTERATION SUSPEND	7/30/1999	99830494.3			EP
NMXS-0614.00/EP	Utility - ORG	Issued	MANUFACTURE OF AN HV-MOS TRANSISTOR WITH LOW MULTIPLICATION FACTOR IN A DUAL-GATE CMOS PROCESS	11/19/1999	99830717.7	5/26/2010	1102319	EP

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NMXS-0615.00/EP	Utility - ORG	Abandoned	I/V CONVERTER WITH DECOUPLING MEANS FOR THE ARRAY INPUT/OUTPUT NODES	7/22/1999	99830469.5	9/24/2008	1071096	EP
NMXS-0619.00/EP	Utility - ORG	Abandoned	EMBEDDED STAGE FOR DETECTING SHORTCIRCUITS BETWEEN WORDLINES OF NON VOLATILE MEMORIES	9/10/1999	99830567.6	11/14/2007	1083575	EP
NMXS-0621.00/EP	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH BURST MODE READING AND CORRESPONDING READING METHOD	11/25/1999	99830723.5	1/28/2009	1103978	EP
NMXS-0623.00/EP	Utility - ORG	Abandoned	ANTI-DECIPHERING CONTACTS	10/2/2000	00830646.6			EP
NMXS-0626.00/EP	Utility - ORG	Abandoned	COLUMN DECODER CIRCUIT FOR PAGE READING OF A SEMICONDUCTOR MEMORY	2/29/2000	00830149.1	1/26/2005	1130601	EP
NMXS-0630.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NONVOLATILE MEMORY CELLS OF REDUCED DIMENSIONS	11/26/1999	99830735.9			EP
NMXS-0631.00/EP	Utility - ORG	Issued	MANUFACTURING PROCESS FOR NON-VOLATILE FLOATING GATE MEMORY CELLS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND COMPRISED IN A CELL MATRIX WITH AN ASSOCIATED CONTROL CIRCUITRY	12/6/1999	99830755.7	10/13/2010	1107309	EP
NMXS-0632.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY WITH SINGLE SUPPLY AND HIERARCHICAL ROW DECODING	7/28/1999	99830483.6	9/21/2005	1073060	EP
NMXS-0635.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY	9/18/2000	00830620.1	3/7/2007	1197968	EP
NMXS-0636.00/EP	Utility - ORG	Abandoned	METHOD OF MANUFACTURING LOW AND HIGH VOLTAGE CMOS TRANSISTORS WITH EPROM CELLS	12/13/1999	99830770.6			EP
NMXS-0638.00/EP	Utility - ORG	Abandoned	LOW CONSUMPTION VOLTAGE BOOST DEVICE	12/30/1999	99830825.8	4/25/2007	1113450	EP
NMXS-0639.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY DEVICE WITH CONFIGURABLE ROW REDUNDANCY	2/14/2000	00830103.8	5/18/2005	1126372	EP
NMXS-0641.00/EP	Utility - ORG	Abandoned	VOLTAGE BOOSTING DEVICE, IN PARTICULAR FOR SPEEDING POWER-UP OF MULTILEVEL NONVOLATILE MEMORIES	2/8/2000	00830088.1	1/25/2006	1124313	EP
NMXS-0643.00/EP	Utility - ORG	Issued	SYNCHRONOUS COUNTER FOR ELECTRONIC MEMORIES	2/14/2000	00830100.4	4/8/2009	1126467	EP
NMXS-0644.00/EP	Utility - ORG	Abandoned	SYNCHRONIZATION CIRCUIT FOR READ PATHS OF AN ELETRONIC MEMORY	4/10/2000	00830269.7			EP
NMXS-0645.00/EP	Utility - ORG	Issued	INTERNAL ADDRESSING STRUCTURE OF A SEMICONDUCTOR MEMORY	10/6/2000	00830655.7	5/27/2009	1195770	EP
NMXS-0646.00/EP	Utility - ORG	Issued	STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE	3/21/2000	00830209.3	12/10/2008	1137011	EP
NMXS-0647.00/EP	Utility - ORG	Pending	MANUFACTURING PROCESS FOR THE INTEGRATION IN A SEMICONDUCTOR CHIP OF AN INTEGRATED CIRCUIT INCLUDING A HIGH-DENSITY INTEGRATED CIRCUIT COMPONENTS PORTION AND A HIGH-PERFORMANCE LOGIC INTEGRATED CIRCUIT COMPONENTS PORTION	5/15/2000	00201716.8			EP
NMXS-0648.00/EP	Utility - ORG	Abandoned	LOGIC PARTITIONING OF A NONVOLATILE MEMORY ARRAY	3/28/2000	00830228.3	3/17/2004	1139210	EP
NMXS-0649.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY MATRIX ARCHITECTURE	7/4/2000	00830494.1			EP
NMXS-0649.01/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY MATRIX ARCHITECTURE	7/4/2000	00830468.5			EP
NMXS-0649.02/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY MATRIX ARCHITECTURE	12/14/2000	00204838.7	9/6/2006	1170798	EP
NMXS-0651.00/EP	Utility - ORG	Abandoned	METHOD OF FORMING LOW-RESISTIVITY CONNECTIONS IN NON-VOLATILE MEMORIES	3/3/2000	00830162.4			EP
NMXS-0653.00/EP	Utility - ORG	Issued	CIRCUITAL STRUCTURE FOR PROGRAMMING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830392.7	7/23/2008	1160794	EP
NMXS-0654.00/EP	Utility - ORG	Issued	CIRCUITAL STRUCTURE FOR READING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830393.5	12/19/2007	1160795	EP
NMXS-0655.00/EP	Utility - ORG	Issued	INTEGRATED DEVICE WITH VOLTAGE SELECTOR	3/29/2000	00830239.0	5/28/2008	1143454	EP
NMXS-0656.00/EP	Utility - ORG	Abandoned	LOW-CONSUMPTION CHARGE PUMP FOR A NONVOLATILE MEMORY	3/29/2000	00830238.2			EP
NMXS-0657.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY CELL WITH A FLOATING GATE REGION AUTOALIGNED TO THE ISOLATION AND WITH A HIGH COUPLING COEFFICIENT	6/20/2001	01114948.1			EP
NMXS-0662.00/EP	Utility - ORG	Abandoned	NONVOLATILE MEMORY WITH INTERNAL TEST CLOCK AND HIGH SPEED TEST METHOD	9/30/1999	99830616.1			EP

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MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS 0663.00/EP	Utility ORG	Abandoned	TEST METHOD AND MEMORY USING AN ADDRESS-DEPENDENT POLINOMINAL FOR GENERATING A SIGNATURE CODE	9/30/1999	99830617.9	12/10/2008	1089293	EP
NMXS-0665.00/EP	Utility - ORG	Issued	INTERLEAVED DATA PATH AND OUTPUT MANAGEMENT ARCHITECTURE FOR AN INTERLEAVED MEMORY AND LOAD PULSER CIRCUIT FOR OUTPUTTING THE READ DATA	4/17/2000	00830291.1	9/1/2010	1122735	EP
NMXS-0667.00/EP	Utility - ORG	Abandoned	REDUNDANCY ARCHITECTURE FOR AN INTERLEAVED MEMORY	3/2/2000	00830158.2	5/26/2004	1130517	EP
NMXS-0668.00/EP	Utility - ORG	Abandoned	ACCELERATED CARRY GENERATION	4/27/2000	00830312.5			EP
NMXS-0669.00/EP	Utility - ORG	Issued	ATD GENERATION IN A SYNCHRONOUS MEMORY	4/27/2000	00830313.3	10/28/2009	1122736	EP
NMXS-0670.00/EP	Utility - ORG	Abandoned	INTERLEAVED MEMORY DEVICE FOR BURST TYPE ACCESS IN SYNCHRONOUS READ MODE WITH THE TWO SEMI-ARRAYS INDEPENDENTLY READABLE IN RANDOM ACCESS ASYNCHRONOUS MODE	1/31/2000	00830068.3	3/30/2005	1122734	EP
NMXS-0671.00/EP	Utility - ORG	Abandoned	COLOR IMAGE RESTORATION WITH ANTI-ALIAS	10/11/2000	00308954.7			EP
NMXS-0672.00/EP	Utility - NSPCT	Abandoned	CIRCUIT FOR THE PRODUCTION OF HIGHT VOLTAGE FOR THE PROGRAMMING OF A MEMORY	6/26/2000	00946012.2	3/16/2005	1196926	EP
NMXS-0673.00/EP	Utility - ORG	Issued	NEW ARCHITECTURE FOR PAGE MODE IN A NON VOLATILE MEMORY	9/15/2000	00402549.0	7/23/2008	1085520	EP
NMXS-0674.00/EP	Utility - ORG	Issued	MEMORY WITH COLUMN REGISTER AND WRITING METHOD	9/5/2000	00402443.6	12/23/2009	1089290	EP
NMXS-0675.00/EP	Utility - ORG	Abandoned	NEW ARCHITECTURE OF A NON VOLATILE MEMORY, WITH A COMMON DIFFUSED SOURCE FOR EACH WORD	9/15/2000	00402548.7	4/10/2002	1085518	EP
NMXS-0677.00/EP	Utility - ORG	Issued	PAGE PROGRAMMABLE FLASH MEMORY	11/22/2000	00125553.8	12/21/2011	111162181	EP
NMXS-0678.00/EP	Utility - ORG	Issued	METHOD FOR THE CORRECTION OF A BIT IN A STRING OF BITS	11/22/2000	00125557.9	7/29/2009	EP1109321	EP
NMXS-0680.00/EP	Utility - ORG	Abandoned	CHARGE PUMP BOOSTER DEVICE WITH TRANSFER AND RECOVERY OF THE CHARGE	2/15/2000	00830105.3	5/3/2006	1158654	EP
NMXS-0681.00/EP	Utility - ORG	Pending	NONVOLATILE MEMORY CELL WITH HIGH PROGRAMMING EFFICIENCY	7/31/2000	00830546.8			EP
NMXS-0682.00/EP	Utility - ORG	Issued	METHOD AND A CIRCUIT STRUCTURE FOR MODIFYING THE THRESHOLD VOLTAGES OF NON-VOLATILE MEMORY CELLS	7/18/2000	00830504.7	12/10/2008	1178492	EP
NMXS-0685.00/EP	Utility - ORG	Issued	DIRECT-COMPARISON READING CIRCUIT FOR A NONVOLATILE MEMORY ARRAY	8/16/2000	00830582.3	12/10/2008	1184873	EP
NMXS-0686.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY WITH A CHARGE PUMP WITH REGULATED VOLTAGE	7/26/2000	00830529.4			EP
NMXS-0691.00/EP	Utility - ORG	Abandoned	A LATERAL DMOS TRANSISTOR	9/21/2000	00830628.4	11/28/2007	1191601	EP
NMXS-0692.00/EP	Utility - ORG	Abandoned	VOLTAGE BOOSTER WITH A LOW OUTPUT RESISTANCE	10/26/2000	00830706.8			EP
NMXS-0695.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY	8/2/2000	00830553.4			EP
NMXS-0696.00/EP	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE, NON-VOLATILE, SEMICONDUCTOR MEMORY WHICH CAN KEEP A DATUM STORED UNTIL AN OPERATION TO MODIFY THE DATUM IS COMPLETED	12/29/2000	00830878.5	9/16/2009	1220229	EP
NMXS-0699.00/EP	Utility - ORG	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY	10/13/2000	00830671.4	10/6/2010	1199725	EP
NMXS-0700.00/EP	Utility - ORG	Abandoned	NONVOLATILE MEMORY DEVICE, HAVING PARTS WITH DIFFERENT ACCESS TIME, RELIABILITY, AND CAPACITY	9/20/2000	00830627.6			EP
NMXS-0704.00/EP	Utility - ORG	Abandoned	ANALOG-TO-DIGITAL CONVERSION METHOD AND DEVICE, IN HIGH-DENSITY MULTILEVEL NON-VOLATILE MEMORY DEVICES	10/31/2000	00830722.5			EP
NMXS-0704.01/EP	Utility - ORG	Abandoned	ANALOG-TO-DIGITAL CONVERSION METHOD AND DEVICE, IN HIGH-DENSITY MULTILEVEL NON-VOLATILE MEMORY DEVICES	11/23/2000	00127649.2	11/15/2006	1211812	EP
NMXS-0705.00/EP	Utility - ORG	Issued	METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH PROGRAM AND VERIFY ALGORITHM USING A STAIRCASE VOLTAGE WITH VARYING STEP AMPLITUDE	4/10/2001	01830247.1	8/26/2009	1249842	EP
NMXS-0708.00/EP	Utility - ORG	Abandoned	MULTI-EMITTER BIPOLAR TRANSISTOR FOR BANDGAP REFERENCE CIRCUITS	12/28/2000	00830851.2			EP
NMXS-0710.00/EP	Utility - ORG	Issued	SEMICONDUCTOR MEMORY SYSTEM	5/30/2001	01830345.3	1/27/2010	EP1262995	EP
NMXS-0716.00/EP	Utility - ORG	Abandoned	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/15/2000	00830827.2			EP
NMXS-0716.01/EP	Utility - ORG	Abandoned	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/13/2001	01125768.6	3/3/2004	1215679	EP

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MT-Docket No	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0717.00/EP	Utility - ORG	Issued	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL NONVOLATILE MEMORY CELL	1/15/2001	01830017.8	8/8/2007	1225595	EP
NMXS-0718.00/EP	Utility - ORG	Abandoned	METHOD FOR STORING DATA IN A NONVOLATILE MEMORY	12/29/2000	00830866.0	12/24/2008	1220228	EP
NMXS-0719.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR REDUCING AVERAGE ACCESS TIME OF A NON-VOLATILE MEMORY DURING READING	12/28/2000	00830855.3			EP
NMXS-0720.00/EP	Utility - ORG	Abandoned	AUTOTESTING METHOD OF A MEMORY CELL MATRIX, PARTICULARLY OF THE NON-VOLATILE TYPE	12/28/2001	01830832.0			EP
NMXS-0721.00/EP	Utility - ORG	Issued	READING CIRCUIT AND METHOD FOR A MULTILEVEL NON-VOLATILE MEMORY	4/10/2001	01830248.9	10/29/2008	1249841	EP
NMXS-0722.00/EP	Utility - ORG	Abandoned	A METHOD OF REFRESHING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	6/17/2002	02013242.9			EP
NMXS-0722.01/EP	Utility - ORG	Abandoned	A METHOD OF REFRESHING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	6/17/2002	01830418.8			EP
NMXS-0724.00/EP	Utility - ORG	Abandoned	NON-VOLATILE ELECTRICALLY ALTERABLE SEMICONDUCTOR MEMORY	1/24/2001	01830039.2	5/10/2006	1227499	EP
NMXS-0725.00/EP	Utility - ORG	Abandoned	METHOD FOR ERASING AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, IN PARTICULAR AN EEPROM-FLASH MEMORY DEVICE, AND AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, IN PARTICULAR AN EEPROM-FLASH MEMORY DEVICE	6/5/2001	01830369.3			EP
NMXS-0726.00/EP	Utility - ORG	Abandoned	METHOD FOR REFRESHING STORED DATA IN AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	2/19/2001	01830110.1	7/11/2007	1233421	EP
NMXS-0728.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TIMING DYNAMIC READING OF A MEMORY CELL WITH CONTROL OF THE INTEGRATION TIME	4/19/2001	01830266.1	8/15/2007	1251523	EP
NMXS-0729.00/EP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL AT LOW SUPPLY VOLTAGE AND WITH LOW OUTPUT DYNAMICS	2/14/2001	01830097.0	8/8/2007	1233420	EP
NMXS-0730.00/EP	Utility - ORG	Issued	METHOD AND CIRCUIT FOR GENERATING REFERENCE VOLTAGES FOR READING A MULTILEVEL MEMORY CELL	4/27/2001	01830276.0	11/5/2008	1253597	EP
NMXS-0732.00/EP	Utility - ORG	Abandoned	MANUFACTURING PROCESS OF AN INTERPOLY DIELECTRIC STRUCTURE FOR NON-VOLATILE SEMICONDUCTOR INTEGRATED MEMORIES	1/31/2002	02425044.1			EP
NMXS-0733.00/EP	Utility - ORG	Issued	MANUFACTURING PROCESS OF A SEMICONDUCTOR NON-VOLATILE MEMORY CELL	6/28/2002	02014408.5	4/9/2008	1324393	EP
NMXS-0733.01/EP	Utility - ORG	Abandoned	MANUFACTURING PROCESS OF A SEMICONDUCTOR NON-VOLATILE MEMORY CELL	6/28/2002	01830831.2			EP
NMXS-0735.00/EP	Utility - ORG	Issued	LOW POWER CHARGE PUMP CIRCUIT	11/9/2001	01830695.1	6/18/2008	1310959	EP
NMXS-0738.00/EP	Utility - ORG	Issued	INTERLACED MEMORY DEVICE WITH RANDOM OR SEQUENTIAL ACCESS	10/18/2000	00830675.5	12/31/2008	1199723	EP
NMXS-0740.00/EP	Utility - ORG	Abandoned	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/29/2000	00830869.4			EP
NMXS-0740.01/EP	Utility - ORG	Abandoned	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/27/2001	01130836.8	3/3/2004	1220448	EP
NMXS-0742.00/EP	Utility - ORG	Issued	CHARGE PUMP FOR A NONVOLATILE MEMORY WITH READ VOLTAGE REGULATION IN THE PRESENCE OF ADDRESS SKEW, AND NONVOLATILE MEMORY COMPRISING SUCH A CHARGE PUMP	2/6/2001	01830070.7	5/21/2008	1229548	EP
NMXS-0749.00/EP	Utility - NSPCT	Abandoned	PAGE-ERASABLE FLASH MEMORY	11/14/2001	01996861.9	4/6/2005	1342244	EP
NMXS-0750.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR THE DETECTION OF A DEFECTIVE POWER SUPPLY CONNECTION	1/23/2002	02290165.6	4/14/2004	1227529	EP
NMXS-0751.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR SEQUENTIAL READOUT OF A MEMORY WITH ADDRESS JUMP	2/5/2002	02290278.7			EP
NMXS-0753.00/EP	Utility - NSPCT	Issued	CONTROL SIGNAL-ADAPTIVE CONTACTLESS CHIP CARD	2/14/2002	02706857.6	5/11/2005	1368784	EP
NMXS-0754.00/EP	Utility - ORG	Abandoned	FLASH EEPROM AND EPROM ARRAYS WITH SELECT TRANSISTORS WITHIN THE BIT LINE PITCH	3/10/1995	95301607.8	8/14/2002	0673071	EP
NMXS-0756.00/EP	Utility - ORG	Abandoned	A MEMORY DEVICE	9/27/2002	02078984.8	9/6/2006	1306852	EP
NMXS-0757.00/EP	Utility - ORG	Abandoned	WORD LINE SELECTOR FOR A SEMICONDUCTOR MEMORY	2/20/2002	02425084.7	7/7/2004	1339069	EP

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MII DckNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0759.00/EP	Utility - ORG	Pending	POWER SUPPLY CIRCUIT STRUCTURE FOR A ROW DECODER OF A MULTILEVEL NON-VOLATILE MEMORY DEVICE	12/30/2002	02029093.8			EP
NMXS-0759.01/EP	Utility - ORG	Abandoned	POWER SUPPLY CIRCUIT STRUCTURE FOR A ROW DECODER OF A MULTILEVEL NON-VOLATILE MEMORY DEVICE	12/30/2002	01830829.6			EP
NMXS-0761.00/EP	Utility - ORG	Abandoned	REGULATION METHOD FOR THE DRAIN, BODY AND SOURCE TERMINALS VOLTAGES IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	12/30/2002	01830830.8			EP
NMXS-0761.01/EP	Utility - ORG	Abandoned	REGULATION METHOD FOR THE DRAIN, BODY AND SOURCE TERMINALS VOLTAGES IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	12/30/2002	02029092.0			EP
NMXS-0762.00/EP	Utility - ORG	Abandoned	MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS	9/28/2001	01830614.2	3/7/2007	1298670	EP
NMXS-0763.00/EP	Utility - ORG	Issued	ELECTRICALLY-PROGRAMMABLE NON-VOLATILE MEMORY CELL	2/20/2002	02425085.4	5/14/2008	1339068	EP
NMXS-0765.00/EP	Utility - ORG	Abandoned	SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON-VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD	8/5/2002	02019284.5	4/4/2007	1324344	EP
NMXS-0765.01/EP	Utility - ORG	Abandoned	SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON-VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD	8/5/2002	01830828.8			EP
NMXS-0766.00/EP	Utility - ORG	Abandoned	PROCESS FOR FABRICATING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	11/14/2001	01830700.9			EP
NMXS-0767.00/EP	Utility - ORG	Abandoned	FINITE STATE MACHINE INTERFACE HAS ARBITRATION STRUCTURE TO STORE COMMAND GENERATED BY INTERNAL CIRCUITS DURING EVALUATION PHASE OF STATE MACHINE FOR FLASH EEPROM DEVICE	12/4/2001	01830744.7	8/17/2005	1318440	EP
NMXS-0768.00/EP	Utility - ORG	Abandoned	SINGLE SUPPLY VOLTAGE, NONVOLATILE MEMORY DEVICE WITH CASCODED COLUMN DECODING	12/27/2001	01830808.0			EP
NMXS-0768.01/EP	Utility - ORG	Pending	SINGLE SUPPLY VOLTAGE, NONVOLATILE PHASE CHANGE MEMORY DEVICE WITH CASCODED COLUMN SELECTION AND SIMULTANEOUS WORD READ/WRITE OPERATIONS	12/20/2002	02028616.7			EP
NMXS-0769.00/EP	Utility - ORG	Pending	PROCESS FOR MANUFACTURING A DUAL CHARGE STORAGE LOCATION MEMORY CELL	10/8/2001	01830634.0			EP
NMXS-0770.00/EP	Utility - ORG	Abandoned	ARCHITECTURE FOR A FLASH-EEPROM SIMULTANEOUSLY READABLE IN OTHER SECTORS WHILE ERASING AND/OR PROGRAMMING ONE OR MORE SECTORS	1/11/2002	02425009.4	3/30/2005	1327992	EP
NMXS-0771.00/EP	Utility - ORG	Issued	FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE	10/25/2001	01830671.2	10/3/2007	1308964	EP
NMXS-0772.00/EP	Utility - ORG	Issued	ARCHITECTURE OF A PHASE-CHANGE NONVOLATILE MEMORY ARRAY	12/27/2001	01830806.4	2/25/2009	1326254	EP
NMXS-0774.00/EP	Utility - ORG	Issued	SELF-REPAIR METHOD FOR NON VOLATILE MEMORY DEVICE WITH ERASING/PROGRAMMING FAILURE DETECTION, AND NON VOLATILE MEMORY DEVICE THEREFOR	5/21/2002	02425319.7	12/31/2008	1365419	EP
NMXS-0775.00/EP	Utility - ORG	Abandoned	INTEGRATED RESISTIVE ELEMENT, PHASE-CHANGE MEMORY ELEMENT INCLUDING SAID RESISTIVE ELEMENT, AND METHOD OF MANUFACTURE THEREOF	1/17/2002	02425013.6	5/23/2007	1331675	EP
NMXS-0777.00/EP	Utility - ORG	Pending	SMALL AREA CONTACT REGION, HIGH EFFICIENCY PHASE CHANGE MEMORY CELL AND FABRICATION METHOD THEREOF	12/5/2001	01128461.9			EP
NMXS-0777.01/EP	Utility - DIV	Issued	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	2/20/2002	02425087.0	5/28/2008	1339110	EP
NMXS-0778.00/EP	Utility - ORG	Abandoned	PROGRAMMING METHOD OF THE MEMORY CELLS IN A MULTILEVEL NON-VOLATILE MEMORY DEVICE	5/13/2002	02425293.4			EP
NMXS-0778.01/EP	Utility - ORG	Pending	PROGRAMMING METHOD OF THE MEMORY CELLS IN A MULTILEVEL NON-VOLATILE MEMORY DEVICE	5/13/2003	03010684.3			EP
NMXS-0779.00/EP	Utility - ORG	Issued	A NON-VOLATILE MEMORY DEVICE	3/14/2002	02425152.2	5/11/2011	EP1345236	EP

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MII DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0780.00/EP	Utility - ORG	Issued	PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES	2/20/2002	02425087.0	5/28/2008	1339110	EP
NMXS-0782.00/EP	Utility - ORG	Abandoned	SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	2/20/2002	02425088.8	9/12/2007	1339108	EP
NMXS-0783.00/EP	Utility - ORG	Abandoned	CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS	2/20/2002	02425089.6	5/9/2007	1339111	EP
NMXS-0784.00/EP	Utility - ORG	Abandoned	BASIC STAGE FOR A CHARGE PUMP CIRCUIT	3/29/2002	02425199.3	11/9/2005	1349284	EP
NMXS-0785.00/EP	Utility - ORG	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY CELL	6/25/2002	02425416.1			EP
NMXS-0786.00/EP	Utility - ORG	Issued	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/28/2001	01830827.0	7/16/2008	1324342	EP
NMXS-0788.00/EP	Utility - ORG	Abandoned	TEST STRUCTURE FOR THE MEASUREMENT OF CONTACT TO GATE DISTANCE IN NON-VOLATILE MEMORY DEVICES AND CORRESPONDING TEST METHOD	5/31/2002	02425360.1	8/3/2005	1367597	EP
NMXS-0789.00/EP	Utility - ORG	Pending	METHOD FOR MANUFACTURING ELECTRONIC CIRCUITS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	4/29/2003	03009600.2			EP
NMXS-0791.00/EP	Utility - ORG	Issued	REDUNDANCY CIRCUIT AND METHOD FOR SEMICONDUCTOR MEMORY DEVICES	5/27/2003	03253297.0	4/6/2011	1367599	EP
NMXS-0792.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR CONTROLLING A REFERENCE NODE IN A SENSE AMPLIFIER	12/28/2001	01830817.1	10/27/2004	1324347	EP
NMXS-0794.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SELF-REFRESH CAPABILITY	3/11/2002	02425138.1			EP
NMXS-0796.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE OUTPUTTING READ DATA IN A TIME STARTING FROM A RISING EDGE OF AN EXTERNAL CLOCK THAT IS SHORTER THAN THAT OF KNOWN DEVICES	12/20/2001	01830782.7	4/27/2008	1324346	EP
NMXS-0799.00/EP	Utility - ORG	Issued	NONVOLATILE STORAGE DEVICE AND SELF-REDUNDANCY METHOD FOR THE SAME	8/13/2002	02425529.1	10/10/2007	1394810	EP
NMXS-0800.00/EP	Utility - ORG	Abandoned	BUILT-IN TESTING METHODOLOGY IN FLASH MEMORY	2/27/2003	03425126.4	6/28/2006	1453062	EP
NMXS-0801.00/EP	Utility - ORG	Abandoned	SECTOR PROTECTION CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	7/31/2002	02255360.5	12/6/2006	1282135	EP
NMXS-0802.00/EP	Utility - ORG	Abandoned	DUAL BANK FLASH MEMORY DEVICE AND METHOD	7/31/2002	02255372.1			EP
NMXS-0803.00/EP	Utility - ORG	Abandoned	REDUNDANCY CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	7/31/2002	02255371.3			EP
NMXS-0804.00/EP	Utility - ORG	Issued	REDUNDANCY CIRCUIT AND METHOD FOR REPLACING DEFECTIVE MEMORY CELLS IN A FLASH MEMORY DEVICE	7/31/2002	02255361.4	9/10/2008	1282137	EP
NMXS-0805.00/EP	Utility - ORG	Issued	CIRCUIT AND ASSOCIATED METHOD FOR THE ERASURE OR PROGRAMMING OF A MEMORY CELL	3/5/2002	02366008.8	5/28/2008	1246197	EP
NMXS-0807.00/EP	Utility - DIV	Pending	EEPROM WITH CONTROLLED PROGRAMMING CURRENT	6/25/2002	02358012.9			EP
NMXS-0807.01/EP	Utility - ORG	Issued	EEPROM MEMORY PROTECTED AGAINST THE EFFECTS OF ACCESS TRANSISTOR BREAKDOWN	6/25/2002	02358013.7	10/6/2010	1278199	EP
NMXS-0809.00/EP	Utility - ORG	Issued	METHOD FOR REPLACING FAILED NON-VOLATILE MEMORY CELLS AND CORRESPONDING MEMORY DEVICE	9/30/2002	02425591.1	11/3/2010	1403879	EP
NMXS-0811.00/EP	Utility - ORG	Abandoned	METHOD FOR REDUCING SPURIOUS ERASING DURING PROGRAMMING OF A NONVOLATILE NROM	4/30/2002	02425273.6	7/5/2006	1359591	EP
NMXS-0813.00/EP	Utility - ORG	Abandoned	REGULATION METHOD FOR THE SOURCE TERMINAL VOLTAGE IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	8/30/2002	02019433.8	3/14/2007	1331644	EP
NMXS-0814.00/EP	Utility - ORG	Abandoned	PROCESS FOR FORMING TRENCHES WITH OBLIQUE PROFILE AND ROUNDED TOP CORNERS	6/28/2002	02425428.6	3/7/2007	1376683	EP
NMXS-0815.00/EP	Utility - ORG	Pending	METHOD FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURES	7/31/2002	02425505.1			EP
NMXS-0817.00/EP	Utility - ORG	Abandoned	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	10/8/2002	02425605.9	12/27/2006	1408550	EP
NMXS-0818.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	10/8/2002	02425604.2	3/7/2007	1408549	EP

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MR Docket No	Matter Type	Matter Status	Title	Filing Date	Serial No	Issue Date	Patent No	Country
NMXS-0819.00/EP	Utility - ORG	Pending	USE OF AN ERROR CORRECTION CIRCUIT IN PROGRAM AND ERASE VERIFY PROCEDURES	4/15/2002	02425231.4			EP
NMXS-0820.00/EP	Utility - ORG	Issued	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE, AND NONVOLATILE MEMORY DEVICE	4/26/2002	02425265.2	6/14/2006	1357559	EP
NMXS-0821.00/EP	Utility - ORG	Issued	LINE SELECTOR FOR A MATRIX OF MEMORY ELEMENTS	7/10/2002	02425453.4	12/3/2008	1381057	EP
NMXS-0822.00/EP	Utility - ORG	Pending	MANUFACTURING PROCESS FOR A HIGH VOLTAGE TRANSISTOR INTEGRATED ON A SEMICONDUCTOR SUBSTRATE WITH NON-VOLATILE MEMORY CELLS AND CORRESPONDING TRANSISTOR	9/30/2002	02425592.9			EP
NMXS-0825.00/EP	Utility - ORG	Pending	A CHARGE PUMP WITH CURRENT PEAK NOISE REDUCTION	10/11/2002	02425616.6			EP
NMXS-0826.00/EP	Utility - ORG	Pending	METHOD OF PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	11/26/2003	03104383.9			EP
NMXS-0827.00/EP	Utility - ORG	Pending	A CIRCUIT FOR PROGRAMMING A NON-VOLATILE MEMORY DEVICE WITH ADAPTIVE PROGRAM LOAD CONTROL	11/10/2003	03104130.4			EP
NMXS-0828.00/EP	Utility - ORG	Abandoned	SINGLE CELL ERASING METHOD FOR RECOVERING MEMORY CELLS UNDER PROGRAMMING DISTURBS IN NON VOLATILE SEMICONDUCTOR MEMORY DEVICES	11/28/2002	02425727.1	8/3/2005	1424700	EP
NMXS-0829.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR BIASING AN INPUT NODE OF A SENSE AMPLIFIER WITH A PRE-CHARGE STAGE	9/17/2002	02425552.2			EP
NMXS-0830.00/EP	Utility - ORG	Abandoned	INTEGRATED RESISTIVE ELEMENTS WITH SILICIDATION PROTECTION	9/30/2002	02425586.1			EP
NMXS-0831.00/EP	Utility - ORG	Pending	PROCESS FOR SELF-ALIGNED MANUFACTURE OF INTEGRATED ELECTRONIC DEVICES	11/13/2003	03104191.6			EP
NMXS-0832.00/EP	Utility - ORG	Abandoned	VOLTAGE BOOST DEVICE AND MEMORY SYSTEM	7/4/2003	03425442.5	5/10/2006	1378913	EP
NMXS-0833.00/EP	Utility - ORG	Issued	METHOD OF PROGRAMMING A MULTI-LEVEL, ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	2/20/2003	03425096.9	7/15/2009	EP1450375	EP
NMXS-0834.00/EP	Utility - ORG	Abandoned	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	12/16/2003	03104709.5	2/28/2007	1435574	EP
NMXS-0836.00/EP	Utility - ORG	Pending	SEMICONDUCTOR MEMORY SYSTEM INCLUDING SELECTION TRANSISTORS	12/24/2002	02425796.6			EP
NMXS-0837.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR TIMING RANDOM READING OF A MEMORY DEVICE	11/6/2002	02425676.0			EP
NMXS-0838.00/EP	Utility - ORG	Pending	NON-VOLATILE MEMORY DEVICE WITH IMPROVED SEQUENTIAL PROGRAMMING SPEED	12/16/2003	03104713.7			EP
NMXS-0840.00/EP	Utility - ORG	Pending	NONVOLATILE MEMORY DEVICE WITH SIMULTANEOUS READ/WRITE	11/24/2003	03104345.8			EP
NMXS-0841.00/EP	Utility - ORG	Abandoned	A METHOD AND APPARATUS FOR DETECTING A LEAK OF EXTERNAL AIR INTO A PLASMA REACTOR	8/29/2002	02425536.6			EP
NMXS-0842.00/EP	Utility - ORG	Abandoned	NON VOLATILE MEMORY DEVICE INCLUDING A PREDETERMINED NUMBER OF SECTORS	12/30/2002	02425808.9			EP
NMXS-0844.00/EP	Utility - ORG	Issued	STABILIZATION METHOD FOR DRAIN VOLTAGE IN NON-VOLATILE MULTI-LEVEL MEMORY CELLS AND RELATED MEMORY DEVICE	12/30/2002	02425801.4	6/4/2008	1435623	EP
NMXS-0845.00/EP	Utility - ORG	Pending	SEMICONDUCTOR MEMORY WITH ACCESS PROTECTION SCHEME	2/18/2003	03425093.6			EP
NMXS-0846.00/EP	Utility - ORG	Issued	PROCESS FOR MANUFACTURING A MEMORY DEVICE HAVING SELECTOR TRANSISTORS FOR STORAGE ELEMENTS AND MEMORY DEVICE FABRICATED THEREBY	5/7/2003	03425292.4	7/19/2006	1475840	EP
NMXS-0849.00/EP	Utility - ORG	Abandoned	ANALYSIS OF THE QUALITY OF CONTACTS AND VIAS IN MULTI-METAL FABRICATION PROCESSES OF SEMICONDUCTOR DEVICES, METHOD AND TEST CHIP ARCHITECTURE	5/23/2003	03425336.9			EP
NMXS-0852.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY CELL COMPRISING DIELECTRIC LAYERS HAVING A LOW DIELECTRIC CONSTANT AND CORRESPONDING MANUFACTURING PROCESS	12/30/2002	02425805.5			EP
NMXS-0853.00/EP	Utility - ORG	Abandoned	METHOD FOR DETECTING A RESISTIVE PATH OR A PREDETERMINED POTENTIAL IN NON-VOLATILE MEMORY ELECTRONIC DEVICES	9/30/2002	02425593.7	5/23/2007	1403880	EP

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MTL Docket No	Matter Type	Matter Status	Title	Filing Date	Serial No	Issue Date	Patent No	Country
NMXS-0854.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY CELL SENSING CIRCUIT, PARTICULARLY FOR LOW POWER SUPPLY VOLTAGES AND HIGH CAPACITIVE LOAD VALUES	12/4/2002	02425747.9			EP
NMXS-0855.00/EP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH EMBEDDED DRAM	10/23/2003	03103920.9	4/8/2009	1422719	EP
NMXS-0857.00/EP	Utility - ORG	Issued	A REDUNDANCY SCHEME FOR AN INTEGRATED MEMORY CIRCUIT	7/16/2003	03077228.9	12/31/2008	1498906	EP
NMXS-0858.00/EP	Utility - ORG	Issued	A FULL-SWING WORDLINE DRIVING CIRCUIT FOR A NONVOLATILE MEMORY	4/30/2003	03425264.3	11/4/2009	1473738	EP
NMXS-0859.00/EP	Utility - ORG	Abandoned	METHOD FOR GENERATING A REFERENCE CURRENT FOR SENSE AMPLIFIERS AND CORRESPONDING GENERATOR	6/4/2003	03425353.4	8/16/2006	1484764	EP
NMXS-0860.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	11/26/2003	03104884.7			EP
NMXS-0861.00/EP	Utility - ORG	Abandoned	A HIGH-DENSITY PLASMA PROCESS FOR DEPOSITING A LAYER OF SILICON NITRIDE	10/11/2002	02425615.8			EP
NMXS-0863.00/EP	Utility - ORG	Abandoned	VOLTAGE SUPPLY DISTRIBUTION ARCHITECTURE FOR A PLURALITY OF MEMORY MODULES	12/30/2002	02425809.7	7/11/2007	1435621	EP
NMXS-0864.00/EP	Utility - ORG	Abandoned	NONLITHOGRAPHIC METHOD OF DEFINING GEOMETRIES FOR PLASMA AND/OR ION IMPLANTATION TREATMENTS ON A SEMICONDUCTOR WAFER	4/1/2004	04425243.5	11/26/2008	1582922	EP
NMXS-0869.00/EP	Utility - ORG	Issued	MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL-POLYSILICON LAYER TECHNOLOGY	12/23/2003	03104939.8	9/15/2010	1434257	EP
NMXS-0870.00/EP	Utility - ORG	Issued	MOS DEVICE AND A PROCESS FOR MANUFACTURING MOS DEVICES USING A DUAL-POLYSILICON LAYER TECHNOLOGY WITH SIDE CONTACT	12/23/2003	03104938.0	7/20/2011	1434258	EP
NMXS-0871.00/EP	Utility - ORG	Abandoned	FAST READING, LOW CONSUMPTION MEMORY DEVICE AND READING METHOD THEREOF	12/23/2003	03425820.2			EP
NMXS-0871.01/EP	Utility - ORG	Abandoned	FAST READING, LOW POWER CONSUMPTION MEMORY DEVICE AND READING METHOD THEREOF	12/22/2004	04106858.6	10/22/2008	1548745	EP
NMXS-0872.00/EP	Utility - ORG	Issued	METHOD FOR READING A NONVOLATILE MEMORY DEVICE AND NONVOLATILE MEMORY DEVICE IMPLEMENTING THE READING METHOD	4/10/2003	03425224.7	11/28/2007	1467377	EP
NMXS-0873.00/EP	Utility - ORG	Abandoned	TESTING METHOD AND DEVICE FOR NON-VOLATILE MEMORIES HAVING A LPC (LOW PIN COUNT) COMMUNICATION SERIAL INTERFACE	5/31/2002	02425361.9			EP
NMXS-0877.00/EP	Utility - ORG	Issued	VOLTAGE REGULATION SYSTEM FOR A MULTIWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY	2/28/2003	03425133.0	12/24/2008	1453057	EP
NMXS-0878.00/EP	Utility - ORG	Abandoned	GATE VOLTAGE REGULATION SYSTEM FOR A NON-VOLATILE MEMORY CELLS PROGRAMMING AND/OR SOFT PROGRAMMING PHASE	2/28/2003	03425134.8	10/12/2005	1453059	EP
NMXS-0881.00/EP	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE ARCHITECTURE, FOR INSTANCE A FLASH KIND, HAVING A SERIAL COMMUNICATION INTERFACE	11/28/2002	02425730.5	10/29/2008	1424635	EP
NMXS-0882.00/EP	Utility - ORG	Abandoned	FAST PAGE PROGRAMMING ARCHITECTURE AND METHOD IN A NON-VOLATILE MEMORY DEVICE WITH AN SPI INTERFACE	12/30/2002	02425802.2	9/20/2006	1435624	EP
NMXS-0883.00/EP	Utility - ORG	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING AN INTERNAL SUPPLY VOLTAGE MANAGEMENT DEVICE	4/17/2003	03358005.1	1/31/2007	1365418	EP
NMXS-0889.00/EP	Utility - ORG	Pending	NEGATIVE VOLTAGE WORD LINE DECODER, HAVING COMPACT TERMINATING ELEMENTS	1/16/2004	04000808.8			EP
NMXS-0892.00/EP	Utility - ORG	Issued	WORD-PROGRAMMABLE FLASH MEMORY	5/26/2004	04012398.7	4/9/2008	1496536	EP
NMXS-0893.00/EP	Utility - ORG	Issued	METHOD FOR MANUFACTURING DIFFERENTIAL ISOLATION STRUCTURES IN A SEMICONDUCTOR ELECTRONIC DEVICE AND CORRESPONDING STRUCTURE	7/11/2003	03425459.9	1/2/2008	1496548	EP
NMXS-0895.00/EP	Utility - ORG	Issued	METHOD FOR REDUCING NON-UNIFORMITY OR TOPOGRAPHY VARIATION BETWEEN AN ARRAY AND CIRCUITRY IN A PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED NON-VOLATILE MEMORY DEVICES	2/24/2004	04425112.2	1/20/2010	1569274	EP
NMXS-0899.00/EP	Utility - ORG	Pending	METHOD FOR PERFORMING ERROR CORRECTIONS OF DIGITAL INFORMATION CODIFIED AS A SYMBOL SEQUENCE	3/19/2003	03425172.8			EP
NMXS-0900.00/EP	Utility - ORG	Pending	INTEGRATED MEMORY SYSTEM	3/19/2003	03425171.0			EP
NMXS-0901.00/EP	Utility - ORG	Pending	PHASE-CHANGE MEMORY DEVICE WITH BIASING OF DESELECTED BIT LINES	8/27/2003	03077667.8			EP

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NMXS-0902.00/EP	Utility - ORG	Abandoned	MANUFACTURING METHOD FOR NON-ACTIVE ELECTRICALLY STRUCTURES IN ORDER TO OPTIMIZE THE DEFINITION OF ACTIVE ELECTRICALLY STRUCTURES IN AN ELECTRONIC CIRCUIT INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT	8/4/2003	03425532.3			EP
NMXS-0903.00/EP	Utility - ORG	Issued	SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE	10/22/2003	03425687.5	2/25/2009	1526568	EP
NMXS-0904.00/EP	Utility - ORG	Abandoned	SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY	8/6/2003	03017939.4			EP
NMXS-0905.00/EP	Utility - ORG	Abandoned	IMPROVED BIT LINE DISCHARGE METHOD AND CIRCUIT FOR A SEMICONDUCTOR MEMORY	10/22/2003	03103911.8			EP
NMXS-0906.00/EP	Utility - ORG	Abandoned	SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY	8/2/2004	04103714.4			EP
NMXS-0907.00/EP	Utility - ORG	Abandoned	METHODE OF MAKING A NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE	12/22/2004	04425937.2			EP
NMXS-0910.00/EP	Utility - ORG	Abandoned	DISTRIBUTION OF AN ELECTRIC QUANTITY THROUGH A CIRCUIT	7/21/2004	04103488.5			EP
NMXS-0912.00/EP	Utility - ORG	Abandoned	AN IMPROVED PAGE BUFFER FOR A PROGRAMMABLE MEMORY DEVICE	6/24/2004	04102942.2	12/19/2007	1610343	EP
NMXS-0913.00/EP	Utility - ORG	Pending	A SEMICONDUCTOR MEMORY DEVICE WITH INFORMATION LOSS SELF-DETECT CAPABILITY	4/29/2005	05103557.4			EP
NMXS-0914.00/EP	Utility - ORG	Abandoned	NONVOLATILE PHASE CHANGE MEMORY DEVICE AND BIASING METHOD THEREFOR	8/3/2004	04425601.4			EP
NMXS-0915.00/EP	Utility - ORG	Pending	METHOD AND SYSTEM FOR CORRECTING LOW LATENCY ERRORS IN READ AND WRITE NON VOLATILE MEMORIES, PARTICULARLY OF THE FLASH TYPE	6/30/2004	04425486.0			EP
NMXS-0916.00/EP	Utility - ORG	Abandoned	PHASE CHANGE MEMORY CELL WITH DIODE JUNCTION SELECTION AND MANUFACTURING METHOD THEREOF	12/21/2004	04425931.5			EP
NMXS-0918.00/EP	Utility - NSPCT	Abandoned	FLOATING GATE NON-VOLATILE MEMORY CELL AND PROCESS FOR MANUFACTURING	11/11/2005	05110648.2			EP
NMXS-0919.00/EP	Utility - ORG	Abandoned	METHOD OF MAKING A NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE	12/22/2004	04425936.4	12/9/2009	1675180	EP
NMXS-0920.00/EP	Utility - ORG	Abandoned	REDUNDANCY BASED NAND FLASH MEMORY	7/14/2004	04103354.9	10/25/2006	1617438	EP
NMXS-0921.00/EP	Utility - ORG	Pending	DATA CONTROL UNIT CAPABLE OF CORRECTING BOOT ERRORS, AND CORRESPONDING SELF-CORRECTION METHOD	6/14/2004	04425436.5			EP
NMXS-0922.00/EP	Utility - ORG	Abandoned	METHOD AND SYSTEM FOR CORRECTING ERRORS IN ELECTRONIC MEMORY DEVICES	6/30/2004	04425485.2			EP
NMXS-0923.00/EP	Utility - ORG	Pending	TRIMMING FUNCTIONAL PARAMETERS IN INTEGRATED CIRCUITS	4/26/2004	04101718.7			EP
NMXS-0924.00/EP	Utility - ORG	Allowed	METHOD FOR MANUFACTURING ELECTRONIC NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/23/2005	05028380.8			EP
NMXS-0926.00/EP	Utility - ORG	Abandoned	FLASH MEMORY DEVICE WITH NAND ARCHITECTURE WITH REDUCED CAPACITIVE COUPLING EFFECT	6/1/2005	05104742.1			EP
NMXS-0927.00/EP	Utility - ORG	Pending	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY ELECTRONIC DEVICE INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING DEVICE	12/30/2005	05425942.9			EP
NMXS-0930.00/EP	Utility - ORG	Issued	MAGNITUDE CONTENT ADDRESSABLE MEMORY	10/20/2004	04256444.3	5/9/2012		EP
NMXS-0943.00/EP	Utility - ORG	Issued	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	6/14/2004	04425435.7	8/15/2007	1607984	EP
NMXS-0944.00/EP	Utility - ORG	Abandoned	ROW DECODER FOR NAND MEMORIES	8/11/2004	04425626.1	2/21/2007	1626413	EP
NMXS-0945.00/EP	Utility - ORG	Abandoned	METHOD OF GENERATING AN ENABLE SIGNAL OF A STANDARD MEMORY CORE AND RELATIVE MEMORY DEVICE	7/1/2004	04103101.4			EP
NMXS-0948.00/EP	Utility - ORG	Issued	FLASH MEMORY COMPRISING MEANS FOR CHECKING AND REFRESHING MEMORY CELLS IN THE ERASED STATE	6/3/2004	04013056.9	5/13/2009	1486987	EP
NMXS-0949.00/EP	Utility - ORG	Abandoned	MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD	6/30/2004	04291653.6	8/15/2007	1508901	EP

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NMXS-0950.00/EP	Utility - ORG	Issued	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	12/8/2004	04029018.1	4/11/2007	1542130	EP
NMXS-0951.00/EP	Utility - NSPCT	Pending	METHOD FOR THE IMPLEMENTATION OF AN EXTENDED MEMORY ARRAY BY THE MEANS OF A PLURALITY OF SERIAL MEMORIES	12/8/2004	04029017.3			EP
NMXS-0952.00/EP	Utility - ORG	Abandoned	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION	12/8/2004	04029016.5	5/30/2007	1542233	EP
NMXS-0953.00/EP	Utility - ORG	Issued	A MEMORY DEVICE WITH UNIPOLAR AND BIPOLAR SELECTORS	9/22/2004	04104595.6	4/7/2010	1640994	EP
NMXS-0954.00/EP	Utility - ORG	Abandoned	ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING A CNAND STRUCTURE AND BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/10/2006	06007497.8			EP
NMXS-0955.00/EP	Utility - ORG	Issued	PHASE-CHANGE MEMORY DEVICE AND MANUFACTURING PROCESS THEREOF	1/21/2005	05425024.6	9/17/2008	1684352	EP
NMXS-0957.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE	10/15/2004	04105094.9	9/19/2007	1647991	EP
NMXS-0960.00/EP	Utility - ORG	Abandoned	EMBEDDED STORAGE DEVICE WITH INTEGRATED DATA-MANAGEMENT FUNCTIONS AND STORAGE SYSTEM INCORPORATING IT	8/30/2004	04425643.6			EP
NMXS-0961.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2005	05425209.3	12/12/2007	1713084	EP
NMXS-0962.00/EP	Utility - ORG	Pending	NON VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2005	05425207.7			EP
NMXS-0963.00/EP	Utility - ORG	Abandoned	PROGRAMMING METHOD OF MULTILEVEL MEMORIES AND CORRESPONDING CIRCUIT	10/18/2005	05022651.3			EP
NMXS-0965.00/EP	Utility - ORG	Issued	MEMORY DEVICE AND METHOD OF OPERATING THE SAME WITH HIGH REJECTION OF THE NOISE ON THE HIGH-VOLTAGE SUPPLY LINE	10/8/2004	04425754.1	3/5/2008	1646051	EP
NMXS-0966.00/EP	Utility - ORG	Issued	ELECTRONIC MEMORY DEVICE HAVING HIGH DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE INTERFERENCE CELL-TO-CELL	12/14/2005	05027285.5	11/4/2009	1672645	EP
NMXS-0967.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING ON A SEMICONDUCTOR SUBSTRATE AN ELECTRONIC MEMORY DEVICE COMPRISING A MATRIX OF NON-VOLATILE MEMORY CELLS AND ASSOCIATED CIRCUITRY	2/3/2006	06425059.0			EP
NMXS-0970.00/EP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY ELECTRONIC DEVICE	12/30/2005	05425940.3			EP
NMXS-0970.01/EP	Utility - ORG	Allowed	NON-VOLATILE MEMORY ELECTRONIC DEVICE	12/22/2006	06026787.9			EP
NMXS-0971.00/EP	Utility - ORG	Issued	FLASH MEMORY DEVICE WITH REDUCED DRAIN STRESSES	2/6/2006	06101314.0	6/3/2009	1816652	EP
NMXS-0972.00/EP	Utility - ORG	Abandoned	REMOVABLE DATA STORAGE DEVICE AND RELATED ASSEMBLING METHOD	1/24/2006	06001378.6			EP
NMXS-0973.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A MEMORY WITH LOCAL ELECTRICAL CONTACT BETWEEN THE SOURCE LINE AND THE WELL	1/28/2005	05425034.5			EP
NMXS-0974.00/EP	Utility - ORG	Issued	VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	11/18/2005	05025286.5	10/3/2007	1670002	EP
NMXS-0975.00/EP	Utility - ORG	Issued	PROCESS FOR DIGGING A DEEP TRENCH IN A SEMICONDUCTOR BODY AND SEMICONDUCTOR BODY SO OBTAINED	12/28/2005	05425930.4	12/14/2011	1804281	EP
NMXS-0978.00/EP	Utility - ORG	Pending	METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE THE LATERAL COUPLING EFFECTS BETWEEN MEMORY CELLS	2/4/2005	05425052.7			EP
NMXS-0979.00/EP	Utility - ORG	Abandoned	DUAL RESISTANCE HEATER FOR PHASE CHANGE DEVICES AND MANUFACTURING METHOD THEREOF	12/30/2004	04107070.7			EP
NMXS-0981.00/EP	Utility - ORG	Abandoned	PROCESS FOR PHYSICAL VAPOR DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER AND CHAMBER FOR PHYSICAL VAPOR DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER AND CHAMBER FOR PHYSICAL VAPOR DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER OF A PHASE CHANGE MEMORY DEVICE	4/8/2005	05102812.4			EP
NMXS-0981.01/EP	Utility - ORG	Issued	PVD PROCESS AND CHAMBER FOR THE PULSED DEPOSITION OF A CHALCOGENIDE MATERIAL LAYER OF A PHASE CHANGE MEMORY DEVICE	3/31/2006	06112075.4	12/3/2008	1710824	EP
NMXS-0982.00/EP	Utility - ORG	Abandoned	LOW-RIPPLE BOOSTED VOLTAGE GENERATOR	1/3/2005	05425001.4			EP
NMXS-0983.00/EP	Utility - ORG	Issued	HIGH-VOLTAGE SWITCH WITH LOW OUTPUT RIPPLE FOR NON-VOLATILE FLOATING-GATE MEMORIES	5/20/2005	05425847.1	7/8/2008	1724784	EP

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NMXS-0984.00/EP	Utility ORG	Abandoned	CHARGE-PUMP TYPE, VOLTAGE-BOOSTING DEVICE WITH REDUCED RIPPLE, IN PARTICULAR FOR NON-VOLATILE FLASH MEMORIES	5/20/2005	05425348.9			EP
NMXS-0985.00/EP	Utility - ORG	Abandoned	PHASE CHANGE MEMORY CELL WITH TUBULAR HEATER AND MANUFACTURING METHOD THEREOF	4/8/2005	05102811.6	11/26/2008	1710807	EP
NMXS-0986.00/EP	Utility - ORG	Issued	ELECTRONIC MEMORY DEVICE HAVING HIGH INTEGRATION DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE COUPLING	12/14/2005	05027286.3	10/14/2009	1672646	EP
NMXS-0987.00/EP	Utility - ORG	Issued	METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND NON-VOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONCTOR	11/18/2005	05425814.0	1/20/2010	1788575	EP
NMXS-0988.00/EP	Utility - ORG	Issued	VERTICAL MOSFET TRANSISTOR, IN PARTICULAR OPERATING AS A SELECTOR IN NONVOLATILE MEORY DEVICES	4/27/2005	05425261.4	8/25/2010	1717861	EP
NMXS-0991.00/EP	Utility - ORG	Abandoned	DEVICE FOR AUTOMATICALLY OPENING AND CLOSING CASH CONTAINER	1/28/2005	05100551.0	1/9/2008	1686591	EP
NMXS-0992.00/EP	Utility - ORG	Pending	A CIRCUIT FOR RETRIEVING DATA STORED IN SEMICONDUCTOR MEMORY CELLS	5/31/2005	05104656.3			EP
NMXS-0994.00/EP	Utility - NSPCT	Abandoned	A NON-VOLATILE MEMORY DEVICE SUPPORTING HIGH-PARALLELISM TEST AT WAFER LEVEL	12/15/2004	04106909.3			EP
NMXS-0995.00/EP	Utility - ORG	Abandoned	A MEMORY DEVICE WITH A RAMP-LIKE VOLTAGE BIASING STRUCTURE AND REDUCED NUMBER OF REFERENCE CELLS	3/3/2005	05101659.0			EP
NMXS-0997.00/EP	Utility - ORG	Issued	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/3/2005	05104877.5	12/15/2010	1729303	EP
NMXS-0997.01/EP	Utility - DIV	Pending	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/3/2005	10171507.6			EP
NMXS-0997.02/EP	Utility - DIV	Pending	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/3/2005	10173621.3			EP
NMXS-0999.00/EP	Utility - ORG	Issued	NAND FLASH MEMORY WITH ERASE VERIFY BASED ON SHORTER DELAY BEFORE SENSING	7/28/2005	05106976.3	4/23/2008	1752989	EP
NMXS-1000.00/EP	Utility - ORG	Issued	TRANSISTOR STRUCTURE WITH HIGH INPUT IMPEDANCE AND HIGH CURRENT CAPABILITY AND MANUFACTURING PROCESS THEREOF	11/25/2005	05425835.5	2/3/2010	1791181	EP
NMXS-1001.00/EP	Utility - ORG	Issued	A MEMORY DEVICE WITH TIME-SHIFTING BASED EMULATION OF REFERENCE CELLS	3/3/2005	05101660.8	1/6/2010	1699055	EP
NMXS-1002.00/EP	Utility - ORG	Issued	METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE FLOATING GATE COUPLING AND MEMORY DEVICE	3/31/2006	06425223.2	4/28/2010	1840901	EP
NMXS-1004.00/EP	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH MULTIPLE REFERENCES AND CORRESPONDING CONTROL METHOD	7/29/2005	05425564.1	7/6/2011	1750281	EP
NMXS-1009.00/EP	Utility - NSPCT	Issued	READING CIRCUIT AND METHOD FOR A NONVOLATILE MEMORY DEVICE	9/28/2004	04425724.4	6/17/2009	1640995	EP
NMXS-1010.00/EP	Utility - ORG	Issued	SELF-ADAPTIVE OUPUT BUFFER BASED ON CHARGE SHARING	7/7/2005	05106180.2	9/9/2009	1742361	EP
NMXS-1012.00/EP	Utility - ORG	Abandoned	METHOD AND ARCHITECTURE FOR RESTRICTING ACCESS TO A MEMORY DEVICE	1/19/2005	05100308.5			EP
NMXS-1013.00/EP	Utility - ORG	Issued	ENHANCED SECURITY MEMORY ACCESS METHOD AND ARCHITECTURE	1/19/2005	05100310.1	3/18/2009	1684182	EP
NMXS-1015.00/EP	Utility - ORG	Abandoned	BASIC SEMICONDUCTOR ELECTRONIC CIRCUIT WITH REDUCED SENSITIVITY TO PROCESS VARIATIONS	6/20/2005	05425440.4			EP
NMXS-1016.00/EP	Utility - ORG	Issued	SEQUENTIAL PROGRAM-VERIFY METHOD WITH RESULT BUFFERING	3/30/2004	04101301.2	8/1/2007	1583102	EP
NMXS-1021.00/EP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR IRREVERSIBLY PROGRAMMING AND READING NONVOLATILE MEMORY CELLS	10/3/2007	07425616.5			EP
NMXS-1031.00/EP	Utility - ORG	Issued	METHOD FOR PROGRAMMING/ERASING A NON VOLATILE MEMORY CELL DEVICE, IN PARTICULAR FOR FLASH TYPE MEMORIES	3/10/2006	06425164.8	8/11/2010	1833058	EP
NMXS-1032.00/EP	Utility - ORG	Pending	NON-ACTIVE ELECTRICALLY STRUCTURES OF INTEGRATED ELECTRONIC CIRCUIT	5/31/2006	06425371.9			EP
NMXS-1033.00/EP	Utility - ORG	Abandoned	MEMORY ARCHITECURE WITH SERIAL PERIPHERAL INTERFACE	9/9/2005	05425634.2			EP
NMXS-1034.00/EP	Utility - ORG	Abandoned	CHARGE PUMP CIRCUIT	11/25/2005	05111284.5			EP

PATENT
REEL: 030872 FRAME: 0171

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MII-OcketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1035.00/EP	Utility - ORG	Issued	IMPROVEMENTS TO THE DESIGN OF VOLTAGE SWITCHES	3/21/2006	06111477.3	1/27/2010	1837993	EP
NMXS-1036.00/EP	Utility - ORG	Issued	ROW SELECTOR FOR A SEMICONDUCTOR MEMORY DEVICE BUILT FROM LOW VOLTAGE TRANSISTORS	5/4/2006	06113480.5	8/26/2009	1837880	EP
NMXS-1037.00/EP	Utility - ORG	Lapsed	A COLUMN DECODING SYSTEM FOR SEMICONDUCTOR MEMORY DEVICES IMPLEMENTED WITH LOW VOLTAGE TRANSISTORS	4/12/2006	06112526.6	4/1/2009	1845532	EP
NMXS-1038.00/EP	Utility - ORG	Pending	VOLTAGE REGULATOR FOR NON-VOLATILE MEMORIES IMPLEMENTED WITH LOW-VOLTAGE TRANSISTORS	8/24/2006	06119456.9			EP
NMXS-1039.00/EP	Utility - NSPCT	Allowed	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY DEVICE	9/30/2005	05425681.3			EP
NMXS-1041.00/EP	Utility - NSPCT	Pending	SEMICONDUCTOR FIELD-EFFECT TRANSISTOR, MEMORY CELL AND MEMORY DEVICE	3/20/2006	06745237.5			EP
NMXS-1043.00/EP	Utility - ORG	Abandoned	A SENSING CIRCUIT FOR SEMICONDUCTOR MEMORIES	5/19/2005	06114228.7			EP
NMXS-1044.00/EP	Utility - ORG	Pending	ELECTRONIC DEVICE CONTAINING SEMICONDUCTOR POLYMERS AND CORRESPONDING MANUFACTURING PROCESS	1/30/2006	06425040.0			EP
NMXS-1045.00/EP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING NON VOLATILE MEMORY CELLS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	12/30/2005	05425943.7			EP
NMXS-1046.00/EP	Utility - ORG	Issued	A SEMICONDUCTOR MEMORY DEVICE WITH A PAGE BUFFER HAVING AN IMPROVED LAYOUT ARRANGEMENT	7/28/2005	05106973.0	5/14/2008	1748443	EP
NMXS-1047.00/EP	Utility - ORG	Abandoned	REDUCTION OF THE TIME FOR EXECUTING AN EXTERNALLY COMMANDED TRANSFER OF DATA IN AN INTEGRATED DEVICE	3/16/2006	06425173.9			EP
NMXS-1049.00/EP	Utility - ORG	Issued	METHOD FOR LOCALLY SUPPRESSING A DISTURBANCE OF A REFERENCE LINE	2/28/2006	06425124.2	9/30/2009	1826766	EP
NMXS-1054.00/EP	Utility - NSPCT	Issued	READING METHOD OF A MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE AND MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE	3/2/2006	06425141.6	5/13/2009	1830269	EP
NMXS-1056.00/EP	Utility - ORG	Pending	OUTPUT BUFFER	12/21/2005	05425900.7			EP
NMXS-1060.00/EP	Utility - ORG	Pending	SEMICONDUCTOR-INTEGRATED ELECTRONIC DEVICE HAVING A PLURALITY OF LEADS	7/7/2006	06425477.4			EP
NMXS-1061.00/EP	Utility - ORG	Abandoned	MANUFACTURING METHOD OF AN INTEGRATED CIRCUIT FORMED ON A SEMICONDUCTOR SUBSTRATE	9/1/2006	06425606.8			EP
NMXS-1066.00/EP	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE	10/13/2005	05425718.3	12/2/2009	1775731	EP
NMXS-1068.00/EP	Utility - ORG	Issued	AUTOMATIC REGULATION METHOD FOR THE REFERENCE SOURCES IN A NON VOLATILE MEMORY DEVICE AND CORRESPONDING MEMORY DEVICE	6/30/2006	06425452.7	7/17/2010	1873787	EP
NMXS-1069.00/EP	Utility - ORG	Issued	METHOD AND DEVICE FOR DETECTING POSSIBLE CORRUPTION OF SECTOR PROTECTION INFORMATION OF A NON-VOLATILE MEMORY STORED IN AN ON BOARD VOLATILE MEMORY ARRAY AT POWER-ON	8/29/2006	06425214.1	8/5/2009	1840902	EP
NMXS-1070.00/EP	Utility - ORG	Issued	METHOD FOR ACCESSING A MULTILEVEL NONVOLATILE MEMORY DEVICE OF THE FLASH NAND TYPE	7/22/2005	05106783.3	2/4/2009	1746604	EP
NMXS-1071.00/EP	Utility - NSPCT	Issued	CONFIGURATION OF A MULTILEVEL FLASH MEMORY DEVICE	7/28/2005	05425559.1	5/19/2010	1750277	EP
NMXS-1074.00/EP	Utility - ORG	Issued	METHOD OF PROGRAMMING A FOUR-LEVEL FLASH MEMORY DEVICE AND A RELATED PAGE BUFFER	6/7/2006	06115106.4	11/11/2009	1750278	EP
NMXS-1076.00/EP	Utility - ORG	Issued	METHOD OF FIXING READ EVALUATION TIME IN A NON VOLATILE NAND TYPE MEMORY DEVICE	9/13/2006	06425651.6	4/28/2010	1901309	EP
NMXS-1078.00/EP	Utility - ORG	Issued	PHASE CHANGE MEMORY DEVICE	7/27/2006	06425531.8	3/10/2010	1883113	EP
NMXS-1080.00/EP	Utility - ORG	Pending	MANUFACTURING PROCESS OF AN ORGANIC MASK FOR MICROELECTRONIC INDUSTRY	4/28/2006	06425283.6			EP
NMXS-1082.00/EP	Utility - ORG	Issued	PHASE CHANGE MEMORY DEVICE FOR MULTIBIT STORAGE	9/7/2007	07425555.5	11/17/2010	2034536	EP
NMXS-1084.00/EP	Utility - ORG	Issued	METHOD FOR COMPACTING THE ERASED THRESHOLD VOLTAGE DISTRIBUTION OF FLASH MEMORY DEVICES DURING WRITING OPERATIONS	8/24/2006	06119452.8	10/7/2009	1909290	EP
NMXS-1085.00/EP	Utility - ORG	Issued	METHOD AND CIRCUIT FOR ELECTRICALLY PROGRAMMING SEMICONDUCTOR MEMORY CELLS	6/21/2006	06115812.7	12/30/2009	1870905	EP

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MILDocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1086.00/EP	Utility - ORG	Issued	A MEMORY DEVICE WITH ROW SELECTOR COMPRISING SERIES CONNECTED MEDIUM VOLTAGE TRANSISTORS	8/24/2006	06119440.3	12/9/2009	1892724	EP
NMXS-1093.00/EP	Utility - ORG	Abandoned	MEMORY DEVICE WITH A MANAGING MICROPROCESSOR SYSTEM AND AN ARCHITECTURE OF FAIL SEARCH AND AUTOMATIC REDUNDANCY	7/20/2006	06425503.7			EP
NMXS-1094.00/EP	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE AND METHOD OF HANDLING A DATUM READ FROM A MEMORY CELL	7/28/2006	06425537.5	12/3/2008	1883073	EP
NMXS-1095.00/EP	Utility - ORG	Abandoned	ADDRESS COUNTER FOR NONVOLATILE MEMORY DEVICE	7/28/2006	06425535.9			EP
NMXS-1105.00/EP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	10/9/1986	86830293.6	8/29/1990	0226549	EP
NMXS-1106.00/EP	Utility - ORG	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/29/1987	87830204.1	2/27/1991	0256993	EP
NMXS-1107.00/EP	Utility - ORG	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/22/1987	87830234.8	4/21/1993	0255489	EP
NMXS-1108.00/EP	Utility - ORG	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	5/4/1988	88107152.6	9/9/1992	0298215	EP
NMXS-1109.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/15/1988	88120977.9	5/12/1993	0322665	EP
NMXS-1110.00/EP	Utility - ORG	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	89100780.9	10/20/1993	0326004	EP
NMXS-1111.00/EP	Utility - ORG	Abandoned	CMOS VOLTAGE MULTIPLIER	6/16/1989	89830269.0	2/9/1994	0349495	EP
NMXS-1112.00/EP	Utility - ORG	Abandoned	CMOS LOGIC CIRCUIT FOR HIGH VOLTAGE OPERATION	6/23/1989	89830290.6			EP
NMXS-1113.00/EP	Utility - ORG	Abandoned	FABRICATION OF CMOS DEVICES WITH REDUCED GATE LENGTH	7/17/1989	89830330.0			EP
NMXS-1114.00/EP	Utility - ORG	Abandoned	FABRICATION OF CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTH AND LIGHTLY DOPED DRAIN	7/24/1989	89830341.7			EP
NMXS-1116.00/EP	Utility - ORG	Abandoned	PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	12/22/1989	89830569.3	7/19/1995	0376905	EP
NMXS-1117.00/EP	Utility - ORG	Abandoned	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/14/1990	90313667.9	11/8/1995	0435534	EP
NMXS-1118.00/EP	Utility - ORG	Abandoned	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	2/7/1991	91830037.7	5/10/1995	0445083	EP
NMXS-1119.00/EP	Utility - ORG	Abandoned	READING CIRCUIT FOR NONVOLATILEMEMORY CELL.	2/7/1991	91830036.9	1/3/1996	0443989	EP
NMXS-1120.00/EP	Utility - ORG	Abandoned	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	3/19/1991	91104217.4	9/13/1995	0450389	EP
NMXS-1121.00/EP	Utility - ORG	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	4/24/1991	91830167.2	11/25/1998	0454636	EP
NMXS-1122.00/EP	Utility - ORG	Abandoned	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	4/4/1991	91105323.9	12/29/1997	0455002	EP
NMXS-1123.00/EP	Utility - ORG	Abandoned	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	6/27/1991	91201641.7	5/28/1997	0464928	EP
NMXS-1124.00/EP	Utility - ORG	Abandoned	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	10/1/1990	90830428.0	4/28/2004	0478871	EP
NMXS-1125.00/EP	Utility - ORG	Abandoned	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	9/30/1991	91116659.3	8/13/1997	0479191	EP
NMXS-1126.00/EP	Utility - ORG	Abandoned	TWO PHASES SCAN PATH WITH SINGLECLOCK.	10/15/1991	91202668.9	7/8/1998	0482697	EP
NMXS-1127.00/EP	Utility - ORG	Abandoned	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	11/19/1990	90830529.5	2/19/1997	0487808	EP
NMXS-1128.00/EP	Utility - ORG	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/19/1990	90830530.3	5/8/1996	0486743	EP
NMXS-1129.00/EP	Utility - ORG	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/13/1990	90830583.2	5/1/1996	0491105	EP
NMXS-1130.00/EP	Utility - ORG	Abandoned	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/20/1991	91121952.5	4/2/1997	0492506	EP

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MTI-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1131.00/EP	Utility - ORG	Abandoned	MEMORY CELL READING CIRCUIT	12/18/1991	91121675.2	3/12/1997	0492382	EP
NMXS-1132.00/EP	Utility - ORG	Abandoned	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	5/5/1992	92830205.8	7/29/1998	0514350	EP
NMXS-1133.00/EP	Utility - ORG	Abandoned	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	7/21/1992	92830400.5	10/15/1997	0526427	EP
NMXS-1134.00/EP	Utility - ORG	Abandoned	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	8/27/1992	92830458.3	7/2/1997	6922063	EP
NMXS-1135.00/EP	Utility - ORG	Abandoned	ROW DECODER FOR NAND-TYPE ROM	8/27/1992	92830457.5	3/4/1998	0534910	EP
NMXS-1136.00/EP	Utility - ORG	Abandoned	PLANARIZED CONTACT WITH A SANDWICH OF TUNGSTEN AND ALUMINIUM.	11/10/1992	92119191.2	9/22/1999	0543254	EP
NMXS-1137.00/EP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	11/2/1992	92118785.2	9/27/2000	0545082	EP
NMXS-1138.00/EP	Utility - ORG	Abandoned	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	9/24/1992	92830523.4	1/21/1998	0536095	EP
NMXS-1139.00/EP	Utility - ORG	Abandoned	METALLIZATION OVER TUNGSTEN PLUGS	5/27/1992	92830265.2	9/18/1996	0571691	EP
NMXS-1140.00/EP	Utility - ORG	Abandoned	LOW SWITCHING NOISE OUTPUT BUFFER	6/26/1992	92830335.3	10/31/2001	0585505	EP
NMXS-1141.00/EP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	6/30/1992	92830339.5	9/13/1995	0576773	EP
NMXS-1142.00/EP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	6/30/1992	92830340.3	9/15/1999	0576774	EP
NMXS-1143.00/EP	Utility - ORG	Abandoned	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	9/30/1992	92830541.6	12/2/1998	0591598	EP
NMXS-1144.00/EP	Utility - ORG	Abandoned	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	10/1/1992	92830552.3	5/27/1998	0575688	EP
NMXS-1145.00/EP	Utility - ORG	Abandoned	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	10/29/1992	92830589.5	7/28/1999	0594920	EP
NMXS-1146.00/EP	Utility - ORG	Abandoned	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	11/18/1992	92830625.7	5/28/1997	0598168	EP
NMXS-1147.00/EP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	1/29/1993	93830031.6	5/6/1999	0608664	EP
NMXS-1148.00/EP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS	1/29/1993	93830032.4	1/7/1998	0608665	EP
NMXS-1149.00/EP	Utility - ORG	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS	2/11/1993	93830050.6	9/10/1997	0610643	EP
NMXS-1150.00/EP	Utility - ORG	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830057.1	7/30/1997	0613176	EP
NMXS-1151.00/EP	Utility - ORG	Abandoned	NONVOLATILE EPROM, EEPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830058.9	10/13/1999	0614223	EP
NMXS-1152.00/EP	Utility - ORG	Abandoned	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	3/18/1993	93830109.0	6/23/1999	0616332	EP
NMXS-1153.00/EP	Utility - ORG	Abandoned	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	3/18/1993	93830110.8	6/23/1999	0616333	EP
NMXS-1154.00/EP	Utility - ORG	Issued	SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS	3/31/1993	93830128.0	7/22/1998	0618587	EP
NMXS-1155.00/EP	Utility - ORG	Abandoned	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	4/1/1993	93830134.8	7/28/1999	0595775	EP
NMXS-1156.00/EP	Utility - ORG	Abandoned	METHOD FOR RECOVERING FLOATING-GATE MEMORY CELLS WITH LOW THRESHOLD VOLTAGE IN FLASH-EEPROM MEMORY DEVICES.	4/23/1993	93830173.6			EP
NMXS-1157.00/EP	Utility - NSPCT	Abandoned	METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/9/1992	92402777.4	3/4/1998	0537082	EP
NMXS-1158.00/EP	Utility - ORG	Issued	SUPPLY VOLTAGE DISTRIBUTION SYSTEM WITH REDUCED RESISTANCE FOR SEMICONDUCTOR DEVICES	7/27/2006	06117949.5	2/4/2009	1884954	EP
NMXS-0001.00/FR	Utility - ORG	Abandoned	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/14/1987	8717386	9/6/1991	2624651	FR
NMXS-0002.00/FR	Utility - ORG	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/22/1987	8717900	5/19/1995	2625067	FR
NMXS-0003.00/FR	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/26/1988	8805511	7/13/1990	2630573	FR

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MTL DocketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0004.00/FR	Utility - ORG	Lapsed	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/24/1992	9209199			FR
NMXS-0004.01/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/19/1993	93401861.5	2/15/1995	0585150	FR
NMXS-0005.00/FR	Utility - ORG	Abandoned	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	7/31/1992	9209566	10/7/1994	2694448	FR
NMXS-0005.01/FR	Utility - EPPAT	Abandoned	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	7/15/1993	93401836.7	12/28/1994	0581639	FR
NMXS-0006.00/FR	Utility - ORG	Lapsed	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	10/1/1992	9211751			FR
NMXS-0006.01/FR	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	9/14/1993	93402229.4	1/18/1995	0591022	FR
NMXS-0007.00/FR	Utility - ORG	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/22/1992	9215522	3/10/1995	2699755	FR
NMXS-0007.01/FR	Utility - EPPAT	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/14/1993	93403029.7	4/3/1996	0604270	FR
NMXS-0008.00/FR	Utility - ORG	Abandoned	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/23/1986	8607386			FR
NMXS-0008.01/FR	Utility - EPPAT	Abandoned	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/19/1987	87401120.8	3/14/1990	0246965	FR
NMXS-0009.00/FR	Utility - EPPAT	Lapsed	NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401991.0	10/27/1993	0302780	FR
NMXS-0010.00/FR	Utility - EPPAT	Abandoned	NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401990.2	5/26/1993	0302779	FR
NMXS-0011.00/FR	Utility - EPPAT	Lapsed	CONTENT ADDRESSABLE MEMORY	5/23/1991	91304677.7	8/16/2000	0459703	FR
NMXS-0012.00/FR	Utility - EPPAT	Lapsed	REDUNDANCY FOR SERIAL MEMORY	12/21/1990	90314116.6	4/23/1997	0437081	FR
NMXS-0013.00/FR	Utility - EPPAT	Lapsed	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	3/25/1991	91302575.5	12/16/1998	0455339	FR
NMXS-0014.00/FR	Utility - EPPAT	Lapsed	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/19/1990	90313891.5	4/1/1998	0434381	FR
NMXS-0015.00/FR	Utility - EPPAT	Lapsed	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/16/1991	91309521.2	7/29/1998	0481751	FR
NMXS-0016.00/FR	Utility - EPPAT	Lapsed	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	6/29/1990	90307156.1	1/8/1997	0420388	FR
NMXS-0017.00/FR	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/12/1991	91307425.8	3/19/1997	0471543	FR
NMXS-0018.00/FR	Utility - EPPAT	Lapsed	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	5/31/1991	91304952.4	12/18/1996	0501057	FR
NMXS-0019.00/FR	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	5/31/1991	91304951.6	7/30/1997	0472266	FR
NMXS-0020.00/FR	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307423.3	3/19/1997	0471541	FR
NMXS-0021.00/FR	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307419.1	6/26/1996	0475588	FR
NMXS-0022.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308632.8	6/18/1997	0478251	FR
NMXS-0023.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308633.6	4/8/1998	0478252	FR
NMXS-0024.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	96117267.3	2/18/2004	0768676	FR
NMXS-0024.01/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	91307426.6	5/14/1997	0471544	FR
NMXS-0025.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/21/1991	91309721.8	1/17/1998	0482869	FR

PATENT
REEL: 030872 FRAME: 0175

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MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0026.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/23/1991	91308634.4	11/27/1996	0478253	FR
NMXS-0027.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/23/1991	91308636.9	5/28/1997	0478254	FR
NMXS-0028.00/FR	Utility - EPPAT	Abandoned	ADDRESS BUFFER CIRCUIT HAVING LATCHING BASED ON TRANSITION	10/21/1991	91309720.0	1/7/1998	0482868	FR
NMXS-0029.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH PRECHARGED REDUNDANCY MULTIPLEXING	12/12/1991	91311569.7	9/11/1996	0491523	FR
NMXS-0031.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/12/1991	91311570.5	9/24/1997	0490679	FR
NMXS-0032.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/12/1991	91311571.3	10/2/1996	0490680	FR
NMXS-0033.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	7/16/1992	92306526.2	3/4/1998	0523995	FR
NMXS-0034.00/FR	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	4/30/1992	92303960.6	10/20/1999	0514050	FR
NMXS-0035.00/FR	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR DUAL PORT MEMORY	4/30/1992	92303958.0	7/22/1998	0514049	FR
NMXS-0036.00/FR	Utility - EPPAT	Abandoned	CACHE TAG PARITY DETECT CIRCUIT	3/27/1992	92302736.1	10/8/1997	0506474	FR
NMXS-0037.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	7/16/1992	92306527.0	3/4/1998	0523996	FR
NMXS-0038.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT DUAL-PORT MEMORY DEVICE HAVING REDUCED CAPACITANCE	7/16/1992	92306528.8	5/20/1998	0523997	FR
NMXS-0039.00/FR	Utility - EPPAT	Abandoned	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	1/20/1993	93300397.2	7/8/1998	0552941	FR
NMXS-0040.00/FR	Utility - EPPAT	Abandoned	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	11/29/1993	93309496.3	6/13/2001	0600692	FR
NMXS-0041.00/FR	Utility - EPPAT	Abandoned	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	12/16/1992	92311510.9	3/3/1999	0547888	FR
NMXS-0042.00/FR	Utility - EPPAT	Abandoned	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/16/1992	92311511.7	4/14/1999	0547889	FR
NMXS-0045.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	12/16/1992	92311514.1	10/28/1998	0547892	FR
NMXS-0046.00/FR	Utility - EPPAT	Abandoned	REDUNDANCY DECODER	1/27/1993	93300560.5	7/22/1998	0554052	FR
NMXS-0049.00/FR	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR	4/29/1993	93303369.8	12/29/1999	0568373	FR
NMXS-0050.00/FR	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE	4/29/1993	93303370.6	10/20/1999	0568374	FR
NMXS-0051.00/FR	Utility - EPPAT	Abandoned	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	3/22/1993	93302155.0	6/20/2001	0564137	FR
NMXS-0052.00/FR	Utility - EPPAT	Abandoned	PARALLELIZED DIFFERENCE FLAG LOGIC	5/19/1993	93303874.7	2/23/2000	0574144	FR
NMXS-0053.00/FR	Utility - EPPAT	Abandoned	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/10/1993	93304489.3	12/20/2000	0579375	FR
NMXS-0059.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT OUTPUT DRIVER	8/27/1993	93306835.5	3/26/1997	0586207	FR
NMXS-0062.00/FR	Utility - EPPAT	Abandoned	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/21/1993	93310384.8	3/3/1999	0604195	FR
NMXS-0064.00/FR	Utility - EPPAT	Abandoned	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/18/1994	94300188.2	5/10/2000	0612008	FR
NMXS-0065.00/FR	Utility - EPPAT	Abandoned	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/30/1993	93307776.0	3/3/1999	0590882	FR
NMXS-0066.00/FR	Utility - EPPAT	Abandoned	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/27/1993	93306836.3	10/29/1997	0586208	FR
NMXS-0067.00/FR	Utility - EPPAT	Abandoned	TEMPERATURE-COMPENSATED VOLTAGE LEVEL SENSE CIRCUIT	4/26/1994	94303005.6	4/3/2002	0626582	FR
NMXS-0068.00/FR	Utility - EPPAT	Abandoned	ADDRESS BUFFER	4/28/1994	94303082.5	9/22/1999	0622803	FR
NMXS-0069.00/FR	Utility - EPPAT	Abandoned	METHOD FOR STRESS TESTING DECODERS AND PERIPHERY CIRCUITS	4/28/1994	94303083.3	7/28/1999	0622809	FR
NMXS-0071.00/FR	Utility - EPPAT	Abandoned	OUTPUT DRIVER CIRCUIT	7/28/1993	93305947.9	2/24/1999	0581579	FR
NMXS-0072.00/FR	Utility - EPPAT	Lapsed	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	7/27/1994	94305553.3	11/10/1999	0637036	FR
NMXS-0073.00/FR	Utility - ORG	Abandoned	TEMPERATURE-STABLE CURRENT SOURCE	6/13/1994	9407407	7/19/1996	2721119	FR
NMXS-0073.01/FR	Utility - EPPAT	Abandoned	TEMPERATURE-STABLE CURRENT SOURCE	6/12/1995	95401363.7	4/8/1998	0687967	FR
NMXS-0074.00/FR	Utility - EPPAT	Lapsed	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	5/31/1993	93830243.7	12/15/2004	0627763	FR
NMXS-0075.00/FR	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/30/1993	93830408.7	12/1/1999	0648824	FR
NMXS-0076.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	9/10/1993	93830365.8	12/2/1998	0643418	FR
NMXS-0077.00/FR	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/30/1993	93830481.3	2/10/1999	0655742	FR

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Vin Dckt No	Matter Type	Matter Status	Title	File Date	Serial No	Issue Date	Patent No	Country
NMXS-0079.00/FR	Utility - EPPAT	Lapsed	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/24/1993	93830464.9	7/28/1999	0654791	FR
NMXS-0080.00/FR	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/7/1993	93830491.2	3/17/1999	0657814	FR
NMXS-0081.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	11/30/1993	93830474.8	8/25/1999	0655743	FR
NMXS-0082.00/FR	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830062.9	7/8/1998	0668563	FR
NMXS-0083.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/9/1993	93830493.8	9/2/1998	0657811	FR
NMXS-0084.00/FR	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/29/1994	94830146.0	8/5/1998	0675440	FR
NMXS-0085.00/FR	Utility - EPPAT	Abandoned	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/21/1994	94830022.3	10/7/1998	0665485	FR
NMXS-0086.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE-MEMORY OUTPUT DATA	2/18/1994	94830069.4	7/7/1999	0678869	FR
NMXS-0087.00/FR	Utility - EPPAT	Abandoned	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/18/1994	94830070.2	5/17/2000	0668592	FR
NMXS-0088.00/FR	Utility - EPPAT	Abandoned	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/18/1994	94830071.0	6/7/2000	0678873	FR
NMXS-0089.00/FR	Utility - EPPAT	Abandoned	COUNT UNIT FOR NONVOLATILE MEMORIES	12/28/1993	93830527.3	7/7/1999	0662691	FR
NMXS-0090.00/FR	Utility - EPPAT	Abandoned	END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES	12/28/1993	93830526.5	3/31/1999	0661814	FR
NMXS-0091.00/FR	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	12/28/1993	93830525.7	7/16/1997	0661795	FR
NMXS-0092.00/FR	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1993	93830489.6	5/27/1998	0662690	FR
NMXS-0093.00/FR	Utility - EPPAT	Abandoned	READING CIRCUIT FOR AN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1994	94830124.7	5/31/2000	0678871	FR
NMXS-0094.00/FR	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/30/1993	93830478.9	9/1/1999	0655683	FR
NMXS-0095.00/FR	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/31/1994	94830032.2	5/23/2001	0665558	FR
NMXS-0096.00/FR	Utility - EPPAT	Abandoned	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/31/1994	94830156.9	7/11/2001	0675504	FR
NMXS-0098.00/FR	Utility - EPPAT	Lapsed	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	12/31/1993	93830537.2	6/9/1999	0661713	FR
NMXS-0099.00/FR	Utility - EPPAT	Abandoned	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1993	93830482.1	5/10/2000	0655669	FR
NMXS-0100.00/FR	Utility - EPPAT	Abandoned	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1994	94830077.7	9/26/2001	0668593	FR
NMXS-0101.00/FR	Utility - EPPAT	Abandoned	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830540.6	6/23/1999	0661714	FR
NMXS-0102.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	12/31/1993	93830545.5	3/29/2000	0661717	FR
NMXS-0103.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830542.2	6/9/1999	0661715	FR
NMXS-0104.00/FR	Utility - EPPAT	Abandoned	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/29/1993	93830528.1	9/23/1998	0661636	FR
NMXS-0105.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/18/1994	94830073.6	7/28/1999	0678870	FR
NMXS-0106.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/18/1994	94830074.4	10/20/1999	0668591	FR
NMXS-0107.00/FR	Utility - EPPAT	Abandoned	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH	4/19/1994	94830182.5	7/26/2000	0678874	FR
NMXS-0108.00/FR	Utility - EPPAT	Abandoned	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME	3/28/1994	94830144.5	10/4/2001	0676816	FR
NMXS-0109.00/FR	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830061.1	8/5/1998	0668562	FR
NMXS-0110.00/FR	Utility - EPPAT	Abandoned	REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS	3/28/1994	94830143.7	12/27/2000	0676768	FR

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MII-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0111.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	12/31/1993	93830543.0	7/21/1999	0661716	FR
NMXS-0112.00/FR	Utility - EPPAT	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	4/28/1994	94303084.1	4/7/1999	0627817	FR
NMXS-0113.00/FR	Utility - EPPAT	Abandoned	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/20/1994	94302808.4	11/11/1998	0621537	FR
NMXS-0115.00/FR	Utility - EPPAT	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	6/27/1994	94304643.3	9/8/1999	0632594	FR
NMXS-0117.00/FR	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	6/27/1994	94304644.1	3/14/2001	0634751	FR
NMXS-0118.00/FR	Utility - EPPAT	Abandoned	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	6/27/1994	94304645.8	9/19/2001	0632460	FR
NMXS-0124.00/FR	Utility - EPPAT	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	7/27/1994	94305554.1	9/23/1998	0637134	FR
NMXS-0130.00/FR	Utility - EPPAT	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	9/28/1994	94307070.6	3/20/2002	0647028	FR
NMXS-0131.00/FR	Utility - EPPAT	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	99300541.2	3/6/2002	0952549	FR
NMXS-0131.01/FR	Utility - EPPAT	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	94307068.0	5/31/2000	0646926	FR
NMXS-0138.00/FR	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/23/1993	9314711	12/27/1995	2713008	FR
NMXS-0138.01/FR	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/21/1994	94460043.6	5/29/1996	0654792	FR
NMXS-0139.00/FR	Utility - ORG	Abandoned	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	5/28/1993	9306481	6/30/1995	2705833	FR
NMXS-0139.01/FR	Utility - EPPAT	Abandoned	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	5/25/1994	94401162.6	10/4/2001	0626728	FR
NMXS-0140.00/FR	Utility - ORG	Abandoned	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/28/1993	9313091	12/1/1995	2711833	FR
NMXS-0140.01/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/26/1994	94460037.8	12/16/1998	0651394	FR
NMXS-0141.00/FR	Utility - ORG	Abandoned	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/22/1993	9315498	3/1/1996	2714201	FR
NMXS-0141.01/FR	Utility - EPPAT	Abandoned	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/21/1994	94470041.8	4/14/1999	0660331	FR
NMXS-0142.00/FR	Utility - ORG	Abandoned	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/22/1993	9315499	1/12/1996	2714202	FR
NMXS-0142.01/FR	Utility - EPPAT	Abandoned	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/16/1994	94402912.3	8/21/1996	0660333	FR
NMXS-0143.00/FR	Utility - ORG	Abandoned	METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES	1/28/1994	9400951	5/31/1996	2716294	FR
NMXS-0144.00/FR	Utility - ORG	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/28/1994	9402556	5/31/1996	2716758	FR
NMXS-0144.01/FR	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/23/1995	95470006.8	10/16/1996	0669622	FR
NMXS-0145.00/FR	Utility - ORG	Lapsed	MEMORY REDUNDANCY CIRCUIT	2/28/1994	9402282	9/27/1996	2716743	FR
NMXS-0145.01/FR	Utility - EPPAT	Abandoned	MEMORY REDUNDANCY CIRCUIT	2/27/1995	95400420.6	6/19/1996	0669576	FR
NMXS-0146.00/FR	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/31/1994	9403844	5/24/1996	2718273	FR
NMXS-0146.01/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/20/1995	95400608.6	10/6/1999	0675503	FR
NMXS-0147.00/FR	Utility - ORG	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/31/1994	9401034	3/22/1996	2715782	FR
NMXS-0147.01/FR	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400190.5	10/16/1996	0666572	FR
NMXS-0148.00/FR	Utility - ORG	Abandoned	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/31/1994	9401035	3/22/1996	2715758	FR
NMXS-0148.01/FR	Utility - EPPAT	Abandoned	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400189.7	6/26/1996	0666573	FR
NMXS-0149.00/FR	Utility - ORG	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/31/1994	9401036	3/22/1996	2715759	FR
NMXS-0149.01/FR	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400188.9	6/26/1996	0666559	FR
NMXS-0150.00/FR	Utility - ORG	Abandoned	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/21/1994	9404983	6/28/1996	2719134	FR

PATENT
REEL: 030872 FRAME: 0178

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MEI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0150.01/FR	Utility - EPPAT	Abandoned	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/14/1995	95470014.2	9/18/1996	0678801	FR
NMXS-0151.00/FR	Utility - ORG	Abandoned	VOLTAGE BOOSTER CIRCUIT	4/21/1994	9404985	5/14/1996	2719148	FR
NMXS-0151.01/FR	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER CIRCUIT	4/14/1995	95470013.4	6/18/1997	0678868	FR
NMXS-0152.00/FR	Utility - ORG	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/13/1994	9404393	5/24/1996	2718867	FR
NMXS-0152.01/FR	Utility - EPPAT	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/6/1995	95400772.0	9/29/1999	0678875	FR
NMXS-0153.00/FR	Utility - ORG	Abandoned	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/23/1994	9402304	4/19/1996	2716566	FR
NMXS-0153.01/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/17/1995	95460007.8	1/22/1997	0674264	FR
NMXS-0154.00/FR	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/8/1994	9404565	6/7/1996	2718559	FR
NMXS-0154.01/FR	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/3/1995	95460015.1	8/21/1996	0676769	FR
NMXS-0155.00/FR	Utility - ORG	Abandoned	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	7/20/1994	9409202	9/6/1998	2722907	FR
NMXS-0155.01/FR	Utility - EPPAT	Abandoned	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	7/18/1995	95401708.1	12/18/1996	0696031	FR
NMXS-0156.00/FR	Utility - ORG	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/31/1994	9403845	5/24/1996	2718274	FR
NMXS-0156.01/FR	Utility - EPPAT	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/20/1995	95400607.8	6/2/1999	0675441	FR
NMXS-0157.00/FR	Utility - EPPAT	Abandoned	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/7/1994	94830276.5	3/7/2001	0686978	FR
NMXS-0158.00/FR	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY ELEMENT	3/31/1994	94830154.4	6/13/2001	0675501	FR
NMXS-0159.00/FR	Utility - EPPAT	Abandoned	SENSE AMPLIFIER WITH HYSTERESIS	5/3/1994	94830209.6	3/28/2001	0681293	FR
NMXS-0160.00/FR	Utility - EPPAT	Abandoned	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	4/12/1994	94830167.6	3/17/1999	0677869	FR
NMXS-0161.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/30/1994	94830591.7	3/26/2003	0720225	FR
NMXS-0162.00/FR	Utility - EPPAT	Abandoned	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	6/10/1994	94830283.1	3/7/2001	0686979	FR
NMXS-0163.00/FR	Utility - EPPAT	Abandoned	METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL	7/18/1994	94830363.1	10/14/1998	0696050	FR
NMXS-0164.00/FR	Utility - EPPAT	Abandoned	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	9/30/1994	94830471.2	12/1/1999	0704854	FR
NMXS-0168.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS	9/30/1994	94830468.8	12/15/1999	0704901	FR
NMXS-0170.00/FR	Utility - EPPAT	Abandoned	SYNCHRONIZATION DEVICE FOR OUTPUT STAGES, PARTICULARLY FOR ELECTRONIC MEMORIES	11/18/1994	94830538.8	1/9/2002	0713221	FR
NMXS-0171.00/FR	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING	4/4/1995	95830133.5	6/27/2001	0736876	FR
NMXS-0172.00/FR	Utility - EPPAT	Abandoned	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	5/19/1995	95830211.9	3/29/2000	0743648	FR
NMXS-0174.00/FR	Utility - EPPAT	Abandoned	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	1/26/1995	95830028.4	4/11/2001	0724267	FR
NMXS-0175.00/FR	Utility - EPPAT	Abandoned	TWIN-WELL MANUFACTURING PROCESS FOR AN EEPROM INTEGRATED DEVICE WITH REDUCED BODY EFFECT	11/24/1994	94830544.6	2/6/2002	0714133	FR
NMXS-0179.00/FR	Utility - EPPAT	Abandoned	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	5/5/1995	95830184.8	1/12/2000	0741387	FR
NMXS-0184.00/FR	Utility - EPPAT	Abandoned	CHARGE PUMP VOLTAGE MULTIPLIER CIRCUIT	12/5/1994	94830563.6	6/12/2002	0716368	FR
NMXS-0185.00/FR	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS	4/14/1995	95830153.3	9/13/2000	0737643	FR

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MtrDcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0186.00/FR	Utility - EPPAT	Abandoned	CURRENT DETECTING CIRCUIT	8/3/1995	95830354.7	1/26/2000	0757357	FR
NMXS-0187.00/FR	Utility - EPPAT	Abandoned	HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES	9/29/1995	95830405.7	4/4/2001	0768672	FR
NMXS-0189.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	12/2/1994	9430898L3	9/1/1999	0675489	FR
NMXS-0190.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	12/9/1994	94309218.9	3/24/1999	0675597	FR
NMXS-0194.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	5/24/1995	95303484.0	12/1/1999	0688851	FR
NMXS-0202.00/FR	Utility - EPPAT	Abandoned	CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES	10/27/1995	95307657.7	10/4/2001	0709853	FR
NMXS-0205.00/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	11/21/1995	95308348.2	2/2/2003	0717334	FR
NMXS-0207.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE	11/28/1995	95308569.2	6/27/2001	0718739	FR
NMXS-0208.00/FR	Utility - EPPAT	Abandoned	OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE	11/28/1995	95308561.0	2/20/2002	0718977	FR
NMXS-0209.00/FR	Utility - EPPAT	Abandoned	ADJUSTABLE CURRENT SOURCE	11/28/1995	95308562.8	10/31/2001	0718744	FR
NMXS-0210.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT	11/28/1995	95308543.8	3/15/2000	0718743	FR
NMXS-0211.00/FR	Utility - EPPAT	Abandoned	DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT	11/28/1995	95308568.6	8/30/2000	0718740	FR
NMXS-0214.00/FR	Utility - EPPAT	Abandoned	INTERNAL BUS CONTROL(FLASH MEMORY DEVICE TEST MODE TO DRIVE AN INTERNAL CONTROLBUS EXTERNALLY)	8/21/1995	95305818.7	11/10/1999	0698848	FR
NMXS-0215.00/FR	Utility - EPPAT	Abandoned	RESIDUAL CHARGE ELIMINATION FOR A MEMORY DEVICE	12/27/1995	95309478.6	6/5/2002	0721188	FR
NMXS-0216.00/FR	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/21/1994	9415430	1/31/1997	2728717	FR
NMXS-0216.01/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/14/1995	95402815.5	2/25/1998	0718850	FR
NMXS-0217.00/FR	Utility - ORG	Abandoned	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/12/1994	9410833	12/27/1996	2724483	FR
NMXS-0217.01/FR	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/11/1995	95402054.1	4/22/1998	0708584	FR
NMXS-0218.00/FR	Utility - ORG	Abandoned	CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM	5/19/1995	9506008	6/13/1997	2734390	FR
NMXS-0218.01/FR	Utility - EPPAT	Abandoned	CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM	5/15/1996	96401080.5	7/25/2001	0743650	FR
NMXS-0219.00/FR	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/20/1994	9415348	1/7/1997	2728380	FR
NMXS-0219.01/FR	Utility - EPPAT	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/14/1995	95402820.5	4/22/1998	0718849	FR
NMXS-0220.00/FR	Utility - ORG	Abandoned	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/21/1995	9507621	8/22/1997	2735922	FR
NMXS-0220.01/FR	Utility - EPPAT	Abandoned	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/17/1996	96470009.0	4/29/1998	0750244	FR
NMXS-0221.00/FR	Utility - ORG	Abandoned	RESISTANCE REFERENCE CIRCUIT	12/23/1994	9415553	2/7/1997	2728689	FR
NMXS-0221.01/FR	Utility - EPPAT	Abandoned	RESISTANCE REFERENCE CIRCUIT	12/21/1995	95402912.0	5/19/1999	0718887	FR
NMXS-0222.00/FR	Utility - ORG	Abandoned	DIGITAL RAMP GENERATOR	5/31/1995	9506498	7/18/1997	2734941	FR
NMXS-0222.01/FR	Utility - EPPAT	Abandoned	DIGITAL RAMP GENERATOR	5/29/1996	96401155.5	4/7/1999	0745996	FR
NMXS-0225.00/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR READING NON-VOLATILE MEMORIES	8/4/1995	95830357.0	3/28/2001	0757358	FR
NMXS-0226.00/FR	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT	3/23/1995	95830130.3	1/26/2000	0754024	FR
NMXS-0227.00/FR	Utility - EPPAT	Abandoned	READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE	4/28/1995	95830172.3	4/10/2002	0747903	FR
NMXS-0228.00/FR	Utility - EPPAT	Abandoned	MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS	7/28/1995	95830336.4	7/5/2000	0756285	FR

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MTI-DocketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0229.00/FR	Utility - EPPAT	Abandoned	THRESHOLD DETECTING DEVICE	8/4/1995	95830360.4	3/28/2001	0757352	FR
NMXS-0230.00/FR	Utility - EPPAT	Abandoned	CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES	7/28/1995	95830335.6	10/11/2000	0756220	FR
NMXS-0231.00/FR	Utility - EPPAT	Abandoned	FLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE	8/2/1995	95830351.3	5/23/2001	0758129	FR
NMXS-0232.00/FR	Utility - EPPAT	Abandoned	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/19/1995	95830253.1	1/26/2000	0750314	FR
NMXS-0233.00/FR	Utility - EPPAT	Abandoned	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	9/29/1995	95830406.5	1/26/2000	0766255	FR
NMXS-0234.00/FR	Utility - EPPAT	Abandoned	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	7/14/1995	95830302.6	1/26/2000	0753859	FR
NMXS-0235.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE	9/29/1995	95830407.3	12/1/1999	0766256	FR
NMXS-0236.00/FR	Utility - EPPAT	Abandoned	ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	3/29/1996	96830174.7	7/28/2004	0798735	FR
NMXS-0237.00/FR	Utility - EPPAT	Abandoned	DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY	6/20/1996	96830352.9	5/28/2003	0782149	FR
NMXS-0240.00/FR	Utility - EPPAT	Abandoned	UNBALANCED LATCH AND FUSE CIRCUIT INCLUDING THE SAME	7/28/1995	95830337.2	9/24/2003	0756379	FR
NMXS-0241.00/FR	Utility - EPPAT	Abandoned	REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS	3/29/1996	96830160.6	11/3/2004	0798729	FR
NMXS-0243.00/FR	Utility - EPPAT	Abandoned	PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD	7/31/1995	95830347.1	4/19/2000	0757355	FR
NMXS-0244.00/FR	Utility - EPPAT	Abandoned	SUPPLY VOLTAGES SWITCHES CIRCUIT	6/20/1996	96830353.7	4/24/2002	0782268	FR
NMXS-0247.00/FR	Utility - EPPAT	Abandoned	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	7/24/1995	95830317.4	1/26/2000	0756286	FR
NMXS-0248.00/FR	Utility - EPPAT	Abandoned	NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	10/31/1995	95830455.0	3/15/2000	0772282	FR
NMXS-0249.00/FR	Utility - EPPAT	Abandoned	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	11/3/1995	95830466.9			FR
NMXS-0250.00/FR	Utility - EPPAT	Issued	MEMORY DEVICE WITH IMPROVED YIELD AND RELIABILITY	9/29/1995	95830408.1	5/22/2002	0766174	FR
NMXS-0251.00/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR THE GENERATION OF A VOLTAGE AS A FUNCTION OF THE CONDUCTIVITY OF AN ELEMENTARY CELL OF A NON-VOLATILE MEMORY	3/29/1996	96830168.9	11/24/2004	0798743	FR
NMXS-0253.00/FR	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES	3/29/1996	96830167.1	11/7/2001	0798642	FR
NMXS-0254.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL	12/14/1995	95830520.3	9/13/2000	0779642	FR
NMXS-0257.00/FR	Utility - EPPAT	Lapsed	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURINGPROCESS	10/31/1995	95830459.4	10/12/2005	0772246	FR
NMXS-0259.00/FR	Utility - EPPAT	Abandoned	PROCESS OF FABRICATING TUNNEL-OXIDE NONVOLATILE MEMORY DEVICES	1/31/1996	96830038.2	11/26/2003	0788144	FR
NMXS-0260.00/FR	Utility - EPPAT	Abandoned	FABRICATION OF NATURAL TRANSISTORS IN A NONVOLATILE MEMORY PROCESS	1/22/1996	96830021.0	12/4/2002	0785570	FR
NMXS-0261.00/FR	Utility - EPPAT	Abandoned	MULTI-LEVEL MEMORY CIRCUITS AND CORRESPONDING READING AND WRITING METHODS	1/31/1996	96830044.2	8/24/2005	0788113	FR
NMXS-0262.00/FR	Utility - EPPAT	Abandoned	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	96937498.3	1/10/2001	0906622	FR
NMXS-0263.00/FR	Utility - EPPAT	Abandoned	CLOCK CIRCUIT FOR READING A MULTILEVEL NON VOLATILE MEMORY CELLS DEVICE	6/28/1996	96830371.9	3/19/2003	0817200	FR
NMXS-0264.00/FR	Utility - EPPAT	Abandoned	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	96937494.1	1/3/2001	0906623	FR
NMXS-0265.00/FR	Utility - EPPAT	Abandoned	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	3/22/1996	96830144.0	6/12/2002	0797145	FR
NMXS-0266.00/FR	Utility - EPPAT	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	5/9/1996	96830267.9	3/19/2003	0806773	FR
NMXS-0268.00/FR	Utility - EPPAT	Abandoned	ERASING METHOD FOR A NON-VOLATILE MEMORY	12/29/1995	95830554.2	5/10/2000	0782145	FR

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MtrDcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0270.00/FR	Utility - EPPAT	Abandoned	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	4/30/1996	96830245.5	2/26/2003	0782148	FR
NMXS-0271.00/FR	Utility - EPPAT	Abandoned	ERASE VOLTAGE CONTROL CIRCUIT FOR AN ELECTRICALLY ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830025.1	7/28/2004	0786779	FR
NMXS-0272.00/FR	Utility - EPPAT	Abandoned	METHOD FOR ERASING AN ELECTRICALLY PROGRAMMABLE AND ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830024.4	11/12/2003	0786778	FR
NMXS-0273.00/FR	Utility - EPPAT	Abandoned	PROGRAMMABLE DEVICE WITH BASIC MODULES ELECTRICALLY CONNECTED BY FLASH MEMORY CELLS	12/29/1995	95830552.6	5/23/2001	0782144	FR
NMXS-0274.00/FR	Utility - EPPAT	Abandoned	PAGE-MODE MEMORY DEVICE WITH MULTIPLE LEVEL MEMORY CELLS	6/5/1996	96830318.0	3/12/2003	0811986	FR
NMXS-0276.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE	1/31/1997	97830029.1	6/25/2003	0856886	FR
NMXS-0278.00/FR	Utility - EPPAT	Abandoned	CIRCUITS AND METHODS FOR READ-ENABLING MEMORY DEVICES SYNCHRONOUSLY WITH THE REACHING OF THE MINIMUM FUNCTIONALITY CONDITIONS OF THE MEMORY CELLS AND READING CIRCUITS, PARTICULARLY FOR NON-VOLATILE MEMORIES	4/29/1996	96830238.0	9/24/2003	0805452	FR
NMXS-0279.00/FR	Utility - EPPAT	Abandoned	COLUMN MULTIPLEXER	5/13/1996	96830275.2	11/12/2003	0810806	FR
NMXS-0284.00/FR	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE HAVING OPTIMIZED MANAGEMENT OF DATA TRANSMISSION LINES	8/20/1996	96830128.3	1/2/2003	0797208	FR
NMXS-0285.00/FR	Utility - EPPAT	Abandoned	PULSE GENERATION CIRCUIT AND METHOD FOR SYNCHRONIZED DATA LOADING IN AN OUTPUT PRE-BUFFER	3/29/1996	96830169.7	11/12/2003	0798730	FR
NMXS-0288.00/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS	5/8/1996	96830214.9	12/22/1999	0747800	FR
NMXS-0289.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE	12/20/1995	95309306.9	5/14/2003	0718741	FR
NMXS-0291.00/FR	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR BIASING BIT LINES	5/15/1996	96303448.3	2/5/2003	0747824	FR
NMXS-0314.00/FR	Utility - EPPAT	Lapsed	CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES	8/9/1996	96305856.5	11/28/2001	0760518	FR
NMXS-0316.00/FR	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/31/1995	9503863	5/30/1997	2732487	FR
NMXS-0316.01/FR	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/6/1996	96470004.1	6/23/1999	0735489	FR
NMXS-0317.00/FR	Utility - ORG	Abandoned	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OR NEGATIVE SUPPLY CIRCUIT	6/21/1995	9507618	8/22/1997	2735921	FR
NMXS-0317.01/FR	Utility - EPPAT	Abandoned	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OR NEGATIVE SUPPLY CIRCUIT	6/17/1996	96470011.6	5/20/1998	0757427	FR
NMXS-0318.00/FR	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	9/5/1995	9510577	10/19/1999	2738386	FR
NMXS-0318.01/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	9/2/1996	96460031.6	11/11/1998	0762428	FR
NMXS-0319.00/FR	Utility - ORG	Abandoned	HIGH VOLTAGE GENERATOR	12/26/1995	9515501	1/16/1998	2742942	FR
NMXS-0319.01/FR	Utility - EPPAT	Abandoned	HIGH VOLTAGE GENERATOR	12/24/1996	96402887.2	3/8/2000	0782243	FR
NMXS-0320.00/FR	Utility - ORG	Abandoned	METHODS AND APPARATUS FOR PROGRAMMING CONTENT-ADDRESSABLE MEMORIES USING FLOATING-GATE MEMORY CELLS	10/26/1995	9512662	12/5/1997	2740601	FR
NMXS-0321.00/FR	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/20/1996	9602300	4/17/1998	2745114	FR
NMXS-0321.01/FR	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/17/1997	97460009.0	6/9/1999	0791933	FR

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MIPDCktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0322.00/FR	Utility - ORG	Abandoned	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1/31/1996	9601378	3/27/1998	2744303	FR
NMXS-0322.01/FR	Utility - EPPAT	Abandoned	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1/24/1997	97460008.2	12/2/1998	0788233	FR
NMXS-0324.00/FR	Utility - EPPAT	Abandoned	DATA SENSING TIMING MODULATING CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/29/1996	96830165.5	11/12/2003	0798741	FR
NMXS-0330.00/FR	Utility - EPPAT	Abandoned	I/V CONVERTER FOR LOW SUPPLY NON VOLATILE MEMORY CELLS	6/18/1996	96830344.6	12/17/2003	0814480	FR
NMXS-0332.00/FR	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS	6/18/1996	96830346.1	8/27/2003	0814482	FR
NMXS-0334.00/FR	Utility - EPPAT	Abandoned	BIDIRECTIONAL CHARGE PUMP	8/2/1996	96830441.0	4/2/2003	0822556	FR
NMXS-0337.00/FR	Utility - EPPAT	Abandoned	OUTPUT STAGE FOR A MEMORY DEVICE AND FOR LOW VOLTAGE APPLICATIONS	7/24/1996	96830411.3	5/26/2004	0821362	FR
NMXS-0339.00/FR	Utility - EPPAT	Abandoned	HIGH VOLTAGE TOLERANCE OUTPUT STAGE	7/24/1996	96830413.9	10/9/2002	0821484	FR
NMXS-0343.00/FR	Utility - EPPAT	Abandoned	ADDRESS TRANSITION DETECTION CIRCUIT	3/6/1996	96830096.2	9/12/2001	0794618	FR
NMXS-0344.00/FR	Utility - EPPAT	Abandoned	METHOD FOR RECOVERING FAILED MEMORY	3/21/1996	96830136.6	7/3/2002	0797147	FR
NMXS-0346.00/FR	Utility - EPPAT	Abandoned	GAIN MODULATED SENSE AMPLIFIER, PARTICULARLY FOR MEMORY DEVICES	3/29/1996	96830164.8	2/5/2003	0798732	FR
NMXS-0348.00/FR	Utility - EPPAT	Abandoned	STANDBY VOLTAGE BOOSTING STAGE AND METHOD FOR A MEMORY DEVICE	3/29/1996	96830178.8	10/17/2001	0800259	FR
NMXS-0349.00/FR	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER FOR MEMORY DEVICES	3/29/1996	96830179.6	10/17/2001	0800260	FR
NMXS-0351.00/FR	Utility - EPPAT	Abandoned	AUTO-SAVING CIRCUIT FOR PROGRAMMING CONFIGURATION ELEMENTS IN NON-VOLATILE MEMORY DEVICES	4/5/1996	96830191.1	2/2/2005	0800178	FR
NMXS-0353.00/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR DETECTING THE COINCIDENCE BETWEEN A BINARY INFORMATION UNIT STORED THEREIN AND AN EXTERNAL DATUM	3/12/1996	96830143.2	8/14/2002	0797144	FR
NMXS-0354.00/FR	Utility - EPPAT	Abandoned	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	4/18/1996	96830216.6	3/12/2003	0802541	FR
NMXS-0356.00/FR	Utility - EPPAT	Abandoned	REDUNDANCY MEMORY REGISTER	4/18/1996	96830215.8	2/20/2002	0802482	FR
NMXS-0359.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH	6/6/1996	96830324.8	1/30/2002	0811918	FR
NMXS-0362.00/FR	Utility - EPPAT	Abandoned	READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE	6/18/1996	96830347.9	8/27/2003	0814483	FR
NMXS-0363.00/FR	Utility - EPPAT	Abandoned	MULTILEVEL NON VOLATILE MEMORY DEVICE	8/22/1996	96830455.0	4/9/2003	0825613	FR
NMXS-0364.00/FR	Utility - EPPAT	Abandoned	CHARGE INJECTION CIRCUIT FOR AN INSULATED GATE MOS TRANSISTOR AND COMPUTING DEVICES USING THE SAME	9/30/1996	96830492.3	2/25/2004	0833267	FR
NMXS-0366.00/FR	Utility - EPPAT	Abandoned	CONTROL CIRCUIT OF AN OUTPUT BUFFER	9/19/1996	96830475.8	8/19/2003	0831492	FR
NMXS-0372.00/FR	Utility - EPPAT	Abandoned	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	9/30/1996	96830494.9	4/2/2003	0833340	FR
NMXS-0383.00/FR	Utility - EPPAT	Abandoned	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	12/24/1996	96830649.8	5/23/2007	0851485	FR
NMXS-0385.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS	7/16/1997	97830359.2	3/23/2005	0892430	FR
NMXS-0386.00/FR	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH MULTIFUNCTIONAL TERMINALS	3/28/1997	97830151.3	7/28/2004	0867885	FR
NMXS-0387.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	12/5/1996	96830612.6	7/9/2003	0850348	FR
NMXS-0391.00/FR	Utility - EPPAT	Abandoned	VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARY FOR A NONVOLATILE MEMORY	2/28/1997	97830085.3	5/7/2003	0862183	FR
NMXS-0405.00/FR	Utility - ORG	Abandoned	DEVICE FOR READING CELLS OF A MEMORY	6/13/1996	9607374	9/25/1998	2749967	FR
NMXS-0406.00/FR	Utility - ORG	Abandoned	PARALLEL-ACCESS MEMORY AND METHOD	5/10/1996	9606123	7/10/1998	2748595	FR
NMXS-0407.00/FR	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY WITH INTERNAL REFRESH MEANS	10/25/1996	9613290	12/31/1998	2755287	FR
NMXS-0407.01/FR	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY WITH INTERNAL REFRESH MEANS	10/21/1997	97460043.9	8/4/1999	0838826	FR

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MTI-DckNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0408.00/FR	Utility - ORG	Abandoned	READ CIRCUIT FOR NON-VOLATILE MEMORY WORKING WITH A LOW SUPPLY VOLTAGE	9/24/1996	9611833	11/13/1998	2753879	FR
NMXS-0409.00/FR	Utility - ORG	Abandoned	DEVICE FOR THE PROTECTION OF STORED DATA	8/27/1996	9610588	10/30/1998	2752992	FR
NMXS-0410.00/FR	Utility - ORG	Abandoned	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	6/20/1996	9607705	3/27/1998	2744253	FR
NMXS-0410.01/FR	Utility - EPPAT	Abandoned	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	1/29/1997	97400209.9	10/7/1998	0788047	FR
NMXS-0411.00/FR	Utility - ORG	Abandoned	DEVICE FOR THE PROTECTION OF STORED DATA USING A TIME DELAY CIRCUIT	8/27/1996	9610589	12/4/1998	2752993	FR
NMXS-0412.00/FR	Utility - ORG	Abandoned	MEMORY WITH IMPROVED READING TIME	10/25/1996	9613080	1/22/1999	2755286	FR
NMXS-0412.01/FR	Utility - EPPAT	Abandoned	MEMORY WITH IMPROVED READING TIME	10/15/1997	97402429.1	12/11/2002	0838824	FR
NMXS-0413.00/FR	Utility - ORG	Abandoned	DEVICE AND METHOD FOR POWER-ON/POWER OFF CHECKING OF AN INTEGRATED CIRCUIT	12/19/1996	9615671	1/22/1999	2757712	FR
NMXS-0414.00/FR	Utility - ORG	Abandoned	OSCILLATOR AND SWITCH OVER CONTROL CIRCUIT FOR HIGH VOLTAGE GENERATOR	12/30/1996	9616355	2/19/1999	2758022	FR
NMXS-0415.00/FR	Utility - ORG	Abandoned	ELECTRICALLY ERASABLE FLOATING GRID MEMORY ORGANIZED IN WORDS	3/24/1998	9803786	5/26/2000	2776820	FR
NMXS-0416.00/FR	Utility - ORG	Abandoned	METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	12/17/1996	9615515	1/15/1999	2757306	FR
NMXS-0416.01/FR	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	11/21/1997	97402807.8	10/20/1999	0849740	FR
NMXS-0417.00/FR	Utility - ORG	Abandoned	METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY	12/17/1996	9615514	1/15/1999	2757305	FR
NMXS-0417.01/FR	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY	11/21/1997	97402806.0	10/20/1999	0849739	FR
NMXS-0418.00/FR	Utility - ORG	Abandoned	MEMORY WITH READ PROTECTED ZONES	12/24/1996	9615931	2/5/1999	2757654	FR
NMXS-0418.01/FR	Utility - EPPAT	Abandoned	MEMORY WITH READ PROTECTED ZONES	11/28/1997	97402869.8	6/9/1999	0851359	FR
NMXS-0419.00/FR	Utility - ORG	Abandoned	READ CIRCUIT FOR MEMORY ADAPTED TO THE MEASUREMENT OF LEAKAGE CURRENTS	3/11/1997	9703219	5/7/1999	2760888	FR
NMXS-0420.00/FR	Utility - ORG	Abandoned	LOAD PUMP TYPE OF VOLTAGE GENERATOR CIRCUIT	4/16/1997	9704928	5/28/1999	2762457	FR
NMXS-0421.00/FR	Utility - ORG	Abandoned	DIFFERENTIAL AMPLIFIER IN A MOS TRANSISTORS STRUCTURE	11/7/1997	9714018	12/24/1999	2770947	FR
NMXS-0422.00/FR	Utility - ORG	Abandoned	METHOD AND DEVICE FOR THE FILTERING OF A PULSE SIGNAL	5/30/1997	9706703	7/9/1999	2764135	FR
NMXS-0423.00/FR	Utility - ORG	Abandoned	RING OSCILLATOR USING CMOS TECHNOLOGY	1/13/1997	9700257	2/5/1999	2758422	FR
NMXS-0424.00/FR	Utility - ORG	Abandoned	PAGE-WRITE INDICATOR FOR NON-VOLATILE MEMORY	1/21/1997	9700710	4/9/1999	2758644	FR
NMXS-0425.00/FR	Utility - ORG	Abandoned	WORD ADDRESSABLE FLOATING-GATE MEMORY COMPRISING A REFERENCE VOLTAGE GENERATOR CIRCUIT FOR THE VERIFICATION OF THE CONTENTS OF A WORD	3/20/1997	9703578	6/25/1999	2761191	FR
NMXS-0426.00/FR	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR ERASURE OF A NON-VOLATILE AND ELECTRICALLY ERASABLE MEMORY	11/28/1996	9614777	12/31/1998	2756411	FR
NMXS-0427.00/FR	Utility - ORG	Abandoned	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	11/28/1996	9614776	1/15/1999	2756410	FR
NMXS-0427.01/FR	Utility - EPPAT	Abandoned	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	11/5/1997	97470027.0	8/4/1999	0845787	FR
NMXS-0428.00/FR	Utility - ORG	Abandoned	CIRCUIT FOR THE DETECTION OF CHANGES OF ADDRESS	2/4/1997	9701232	3/19/1999	2759195	FR
NMXS-0429.00/FR	Utility - ORG	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	4/8/1997	9704285	6/18/1999	2761802	FR
NMXS-0429.01/FR	Utility - EPPAT	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	3/20/1998	98400661.9	6/18/2003	0875899	FR
NMXS-0430.00/FR	Utility - ORG	Lapsed	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1997	9700642	12/14/2001	2758645	FR
NMXS-0430.01/FR	Utility - EPPAT	Lapsed	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1998	98903102.5	5/16/2001	0954865	FR
NMXS-0431.00/FR	Utility - ORG	Abandoned	VARIABLE FREQUENCY LOAD PUMP	7/18/1997	9709145	9/3/1999	2766303	FR
NMXS-0431.01/FR	Utility - EPPAT	Abandoned	VARIABLE FREQUENCY LOAD PUMP	7/17/1998	98401807.7	1/23/2002	0898356	FR
NMXS-0436.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLATILE MEMORY DEVICES	8/29/1997	97830435.0	11/12/2003	0899742	FR
NMXS-0446.00/FR	Utility - EPPAT	Issued	DECODER FOR ERASING A SINGLE ROW IN A FLASH MEMORY	11/26/1997	97830625.6	6/30/2010	0920023	FR
NMXS-0449.00/FR	Utility - EPPAT	Abandoned	INTERLEAVED ARCHITECTURE FOR PARALLEL PROGRAMMING OF FLASH DEVICES	10/28/1997	97830550.5	3/21/2007	0913835	FR
NMXS-0458.00/FR	Utility - EPPAT	Abandoned	SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF	12/22/1997	97830693.4	3/2/2005	0926687	FR
NMXS-0459.00/FR	Utility - EPPAT	Abandoned	COMPENSATED VOLTAGE REGULATOR	9/30/1997	97830484.8	7/23/2003	0905710	FR

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MTLDocNbr	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0461.00/FR	Utility - EPPAT	Lapsed	METHOD AND CIRCUIT FOR GENERATING AN ATD SIGNAL TO REGULATE THE ACCESS TO A NON-VOLATILE MEMORY	11/5/1997	97830576.1	3/17/2004	0915477	FR
NMXS-0462.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR REGULATING THE LENGTH OF AN ATD PULSE SIGNAL	11/5/1997	97830573.8	3/3/2004	0915476	FR
NMXS-0466.00/FR	Utility - EPPAT	Abandoned	HIGH VOLTAGE REGULATOR AND CORRESPONDING VOLTAGE REGULATION METHOD	11/5/1997	97830575.3	2/19/2003	0915408	FR
NMXS-0473.00/FR	Utility - EPPAT	Abandoned	ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS	7/28/1998	98114061.9	9/21/2005	0928003	FR
NMXS-0476.00/FR	Utility - EPPAT	Abandoned	MEMORY CELL INTEGRATED STRUCTURE AND CORRESPONDING BIASING DEVICE	4/22/1998	98830238.6	9/28/2005	0952615	FR
NMXS-0481.00/FR	Utility - EPPAT	Lapsed	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	99926682.8	4/10/2002	1097454	FR
NMXS-0484.00/FR	Utility - EPPAT	Abandoned	CONTROLLED ERASING FOR ANALOG & MULTILEVEL STORAGE IN FLASH EEPROM DEVICE	1/22/1998	98830024.0	6/9/2004	0932161	FR
NMXS-0485.00/FR	Utility - EPPAT	Abandoned	ESD PROTECTION NETWORK ON SEMICONDUCTOR CIRCUIT STRUCTURES	12/31/1997	97830741.1	9/20/2006	0932202	FR
NMXS-0487.00/FR	Utility - EPPAT	Abandoned	HIGH STORAGE CAPACITY NON-VOLATILE MEMORY	5/27/1998	98830324.4	11/26/2008	0961287	FR
NMXS-0488.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR THE FABRICATION OF A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	6/30/1998	98830388.9	11/14/2001	0971415	FR
NMXS-0504.00/FR	Utility - EPPAT	Lapsed	PIPELINED NON-BLOCKING LEVEL TWO CACHE SYSTEM WITH INHERENT TRANSACTION COLLISION-AVOIDANCE	12/1/1999	99309641.1	3/14/2007	1006448	FR
NMXS-0505.00/FR	Utility - ORG	Abandoned	NON VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING A READ AND/OR WRITE PROTECTABLE AREA AND ELECTRONIC SYSTEM INCLUDING IT	10/14/1997	9713359	1/14/2000	2770327	FR
NMXS-0505.01/FR	Utility - EPPAT	Abandoned	NON VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING A READ AND/OR WRITE PROTECTABLE AREA AND ELECTRONIC SYSTEM INCLUDING IT	10/13/1998	98402620.3	6/4/2003	0918336	FR
NMXS-0506.00/FR	Utility - ORG	Abandoned	METHOD AND WRITING IN AN EEPROM	10/28/1997	9713740	12/28/2001	2770326	FR
NMXS-0507.00/FR	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY	9/19/1997	9711912	12/24/1999	2768846	FR
NMXS-0507.01/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY	9/10/1998	98460086.1	11/15/2000	0903750	FR
NMXS-0508.00/FR	Utility - ORG	Abandoned	IMPROVEMENTS TO NON VOLATILE MEMORIES PROGRAMABLE WITH ""HOT CARRIER"" EFFECT AND ERASABLE BY TUNNEL EFFECT	10/15/1997	9712903	10/5/2001	2769747	FR
NMXS-0509.00/FR	Utility - ORG	Abandoned	NON VOLATILE ELECTRICALLY PROGRAMMABLE AND ERASABLE MEMORY	11/28/1997	9714982	1/28/2000	2771839	FR
NMXS-0510.00/FR	Utility - ORG	Abandoned	RADIO FREQUENCE SIGNAL DETECTOR FOR CONTACT-LESS SMARTCARD	9/23/1997	9711787	6/2/2000	2768875	FR
NMXS-0510.01/FR	Utility - EPPAT	Abandoned	RADIO FREQUENCE SIGNAL DETECTOR FOR CONTACT-LESS SMARTCARD	9/17/1998	98402303.6	5/24/2006	0903688	FR
NMXS-0511.00/FR	Utility - ORG	Abandoned	CIRCUIT FOR THE GENERATION OF VOLTAGE FOR THE PROGRAMMING OR ERASURE OF A MEMORY THAT USES FLOATING-GATE TRANSISTORS	10/29/1997	9713751	10/5/2001	2770325	FR
NMXS-0511.01/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR THE GENERATION OF VOLTAGE FOR THE PROGRAMMING OR ERASURE OF A MEMORY THAT USES FLOATING-GATE TRANSISTORS	10/12/1998	98470024.5	7/18/2001	0913836	FR
NMXS-0512.00/FR	Utility - ORG	Abandoned	SPSK DEMODULATION DEVICE	1/21/1998	9800584	3/3/2000	2773933	FR
NMXS-0512.01/FR	Utility - EPPAT	Abandoned	SPSK DEMODULATION DEVICE	1/20/1999	99400126.1	6/13/2001	0932283	FR
NMXS-0513.00/FR	Utility - ORG	Abandoned	PROCESS FOR SETTING THE FIRST PROGRAMMATION OF A MEMORY AND CORRESPONDING MEMORY	11/18/1997	9714686	2/4/2000	2771210	FR
NMXS-0514.00/FR	Utility - ORG	Abandoned	DEVICE AND METHOD FOR THE READING OF EEPROM CELLS	4/28/1998	9805330	9/28/2001	2778012	FR
NMXS-0516.00/FR	Utility - EPPAT	Abandoned	DIFFERENCIAL READING OF NONVOLATILE MEMORY CELLS WITHOUT USING A REFERENCE	5/29/1998	98830833.5	12/17/2003	0961285	FR
NMXS-0518.00/FR	Utility - EPPAT	Abandoned	SENSING ARRANGEMENT FOR A MULTILEVEL SEMICONDUCTOR MEMORY DEVICE	8/7/1998	98830491.1	11/2/2005	0978844	FR
NMXS-0522.00/FR	Utility - EPPAT	Abandoned	METHOD FOR READING A MULTI-LEVEL MEMORY CELL	3/27/1998	98830188.9	11/17/2004	0945869	FR

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MTI DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0523.00/FR	Utility EPPAT	Abandoned	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	9/30/1998	98830570.2	5/6/2004	0991075	FR
NMXS-0532.00/FR	Utility - EPPAT	Lapsed	A SIMPLIFIED PROCESS FOR DEFINING THE TUNNEL AREA IN SEMICONDUCTOR NON-VOLATILE NON-ALIGNED MEMORY CELLS	10/15/1998	98830614.8	2/25/2004	0994513	FR
NMXS-0533.00/FR	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE WITH ROW REDUNDANCY	5/12/1999	99830286.3	7/30/2003	1052572	FR
NMXS-0536.00/FR	Utility - EPPAT	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND I/V TRANSISTORS WITH SALICIDED JUNCTIONS	10/23/1998	98830645.2	5/19/2010	0986100	FR
NMXS-0538.00/FR	Utility - EPPAT	Abandoned	METHOD FOR CORRECTING ERRORS IN A MULTILEVEL MEMORY WITHOUT ADDITIONAL CELLS	2/25/1999	99830099.0	2/5/2003	1035473	FR
NMXS-0539.00/FR	Utility - EPPAT	Abandoned	MULTILEVEL NON VOLATILE MEMORY AND READING METHOD THEREFOR	2/10/1999	99830071.9	4/28/2004	1028433	FR
NMXS-0546.00/FR	Utility - EPPAT	Abandoned	LEVELS RESTORE IN ANALOG FLASH EEPROM	9/15/1998	98830536.3	2/9/2005	0987715	FR
NMXS-0557.00/FR	Utility - EPPAT	Abandoned	FLASH COMPATIBLE EEPROM	5/22/1999	99830390.3	2/2/2005	1067557	FR
NMXS-0558.00/FR	Utility - EPPAT	Abandoned	METHOD FOR READING A MEMORY, PARTICULARLY A NON-VOLATILE MEMORY	12/30/1998	98830801.1	7/18/2007	1017059	FR
NMXS-0565.00/FR	Utility - EPPAT	Abandoned	METHOD FOR AUTOALIGNING OVERLAPPED LINES OF CONDUCTOR MATERIAL PROVIDED IN INTEGRATED ELECTRONIC CIRCUITS	5/31/1999	99830336.6	8/17/2005	1058304	FR
NMXS-0566.00/FR	Utility - EPPAT	Abandoned	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/21/1999	99830235.0	8/9/2006	1047078	FR
NMXS-0568.00/FR	Utility - EPPAT	Abandoned	ESD PROTECTION DEVICE FOR SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURE	7/30/1999	99830491.9	5/26/2004	1073119	FR
NMXS-0569.00/FR	Utility - EPPAT	Abandoned	A SEMICONDUCTOR DEVICE WITH IMPROVED CHIP-LEADS INTERCONNECTIONS AND A PROCESS FOR MANUFACTURING THEREOF	2/11/1999	99830072.7	7/26/2006	1028464	FR
NMXS-0570.00/FR	Utility - EPPAT	Abandoned	READING METHOD FOR MULTILEVEL MEMORIES WITH SELECTIVE AMPLIFICATION OF CURRENT	2/26/1999	99830108.9	4/28/2004	1031991	FR
NMXS-0571.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATING FOR A CAPACITIVE LOAD	6/30/1999	99830418.2	11/12/2003	1065580	FR
NMXS-0584.00/FR	Utility - EPPAT	Lapsed	COMMUNICATIONS SYSTEM AND METHOD FOR REDUCING THE EFFECTS OF TRANSMITTER NON-LINEAR DISTORTION ON A RECEIVED SIGNAL	6/14/2000	00305020.0	1/31/2007	1061689	FR
NMXS-0585.00/FR	Utility - ORG	Abandoned	INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES	6/5/1998	9807200	8/4/2000	2779542	FR
NMXS-0585.01/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES	5/26/1999	99470014.4	11/22/2000	0962938	FR
NMXS-0586.00/FR	Utility - ORG	Abandoned	MULTILEVEL FLOATING GATE MEMORY	12/4/1998	9815461	11/29/2002	2786910	FR
NMXS-0587.00/FR	Utility - ORG	Abandoned	HIGH VOLTAGE GENERATION DEVICE	8/11/1998	9810308	9/15/2000	2782421	FR
NMXS-0588.00/FR	Utility - ORG	Abandoned	METHOD FOR VERIFYING THE MEMORY CIRCUIT INTEGRITY	12/11/1998	9815786	2/16/2001	2787233	FR
NMXS-0589.00/FR	Utility - ORG	Abandoned	SECURED EEPROM WITH UV ERASING DETECTION MEANS	12/3/1998	9815447			FR
NMXS-0589.01/FR	Utility - EPPAT	Abandoned	SECURED EEPROM WITH UV ERASING DETECTION MEANS	11/26/1999	99460065.8	1/21/2004	1006532	FR
NMXS-0590.00/FR	Utility - ORG	Abandoned	PROGRAMMING DEVICE FOR AN ELECTRICALLY PROGRAMMABLE NON VOLATILE MEMORY	4/21/1999	9905053	5/23/2008	2792761	FR
NMXS-0592.00/FR	Utility - EPPAT	Abandoned	READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATION VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	6/21/1999	99830382.0	3/5/2003	1063654	FR
NMXS-0593.00/FR	Utility - EPPAT	Abandoned	ERASING AND PARALLEL REWRITING CIRCUIT FOR MEMORY CELL BLOCKS, PARTICULARLY FOR ANALOG FLASH CELLS, AND RELATED OPERATING METHOD	6/21/1999	99830381.2	8/9/2006	1065668	FR
NMXS-0596.00/FR	Utility - EPPAT	Abandoned	GERARCHIC SECTOR BIASING FOR FLASH MEMORIES	6/24/1999	99830396.0	11/17/2004	1063653	FR
NMXS-0598.00/FR	Utility - EPPAT	Abandoned	A READING CIRCUIT FOR A SEMICONDUCTOR MEMORY	6/25/1999	99830408.4	11/23/2005	1071094	FR
NMXS-0599.00/FR	Utility - EPPAT	Abandoned	BIASING THE DRAIN OF A MEMORY CELL DURING READING	6/4/1999	99830848.1	3/21/2007	1058270	FR
NMXS-0603.00/FR	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING MULTILEVEL NON-VOLATILE MEMORIES BY APPLYING SEQUENCES OF PULSES WITHOUT VERIFY	8/3/1999	99830501.5	10/26/2005	1074995	FR
NMXS-0604.00/FR	Utility - EPPAT	Abandoned	ROW DECODER WITH REDUCED POWER CONSUMPTION DURING SWITCHING	6/4/1999	99830345.7	12/15/2004	1058271	FR
NMXS-0605.00/FR	Utility - EPPAT	Abandoned	ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE	6/17/1999	99830378.8	3/8/2006	1061525	FR

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MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0614.00/FR	Utility - EPPAT	Issued	MANUFACTURE OF AN HV-MOS TRANSISTOR WITH LOW MULTIPLICATION FACTOR IN A DUAL-GATE CMOS PROCESS	11/19/1999	99830717.7	5/26/2010	1102319	FR
NMXS-0615.00/FR	Utility - EPPAT	Abandoned	I/V CONVERTER WITH DECOUPLING MEANS FOR THE ARRAY INPUT/OUTPUT NODES	7/22/1999	99830469.5	9/24/2003	1071096	FR
NMXS-0632.00/FR	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY WITH SINGLE SUPPLY AND HIERARCHICAL ROW DECODING	7/28/1999	99830483.6	9/21/2005	1073060	FR
NMXS-0635.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY	9/18/2000	00830620.1	3/7/2007	1197968	FR
NMXS-0638.00/FR	Utility - EPPAT	Abandoned	LOW CONSUMPTION VOLTAGE BOOST DEVICE	12/30/1999	99830825.8	4/25/2007	1113450	FR
NMXS-0641.00/FR	Utility - EPPAT	Abandoned	VOLTAGE BOOSTING DEVICE, IN PARTICULAR FOR SPEEDING POWER-UP OF MULTILEVEL NONVOLATILE MEMORIES	2/8/2000	00830088.1	1/25/2006	1124313	FR
NMXS-0648.00/FR	Utility - EPPAT	Abandoned	LOGIC PARTITIONING OF A NONVOLATILE MEMORY ARRAY	3/28/2000	00830228.3	3/17/2004	1139210	FR
NMXS-0649.00/FR	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY MATRIX ARCHITECTURE	12/14/2000	00204838.7	9/6/2006	1170798	FR
NMXS-0665.00/FR	Utility - EPPAT	Issued	INTERLEAVED DATA PATH AND OUTPUT MANAGEMENT ARCHITECTURE FOR AN INTERLEAVED MEMORY AND LOAD PULSER CIRCUIT FOR OUTPUTTING THE READ DATA	4/17/2000	008302911	9/1/2010	1122735	FR
NMXS-0667.00/FR	Utility - EPPAT	Abandoned	REDUNDANCY ARCHITECTURE FOR AN INTERLEAVED MEMORY	3/2/2000	00830158.2	5/26/2004	1130517	FR
NMXS-0672.00/FR	Utility - ORG	Abandoned	CIRCUIT FOR THE PRODUCTION OF HIGHT VOLTAGE FOR THE PROGRAMMING OF A MEMORY	6/30/1999	9908663	8/31/2001	2795881	FR
NMXS-0672.01/FR	Utility - NSPCT	Abandoned	CIRCUIT FOR THE PRODUCTION OF HIGHT VOLTAGE FOR THE PROGRAMMING OF A MEMORY	6/26/2000	00946012.2	3/16/2005	1196926	FR
NMXS-0673.00/FR	Utility - ORG	Lapsed	NEW ARCHITECTURE FOR PAGE MODE IN A NON VOLATILE MEMORY	9/16/1999	9911601	12/14/2001	2798767	FR
NMXS-0673.01/FR	Utility - EPPAT	Abandoned	NEW ARCHITECTURE FOR PAGE MODE IN A NON VOLATILE MEMORY	9/15/2000	00402549.0	7/23/2008	1085520	FR
NMXS-0674.00/FR	Utility - ORG	Abandoned	MEMORY INCORPORATING COLUMN REGISTER AND METHOD OF WRITING IN SAID MEMORY	9/29/1999	9912149	12/14/2001	2799043	FR
NMXS-0675.00/FR	Utility - ORG	Lapsed	NEW ARCHITECTURE OF A NON VOLATILE MEMORY, WITH A COMMON DIFFUSED SOURCE FOR EACH WORD	9/16/1999	9911600	12/14/2001	2798768	FR
NMXS-0675.01/FR	Utility - EPPAT	Abandoned	NEW ARCHITECTURE OF A NON VOLATILE MEMORY, WITH A COMMON DIFFUSED SOURCE FOR EACH WORD	9/15/2000	00402548.2	4/10/2002	1085518	FR
NMXS-0676.00/FR	Utility - ORG	Abandoned	PROGRAMMING CIRCUIT FOR A MEMORY CELL	9/20/1999	9911858	3/12/2004	2798769	FR
NMXS-0677.00/FR	Utility - ORG	Abandoned	PAGE BY PAGE PROGRAMMABLE FLASH MEMORY	12/22/1999	9916445			FR
NMXS-0678.00/FR	Utility - ORG	Abandoned	METHOD FOR THE CORRECTION OF A BIT IN A STRING OF BITS	12/15/1999	9915816	4/26/2002	2802734	FR
NMXS-0691.00/FR	Utility - EPPAT	Abandoned	A LATERAL DMOS TRANSISTOR	9/21/2000	00830628.4	11/28/2007	1191601	FR
NMXS-0690.00/FR	Utility - EPPAT	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY	10/13/2000	00830671.4	10/6/2010	1199725	FR
NMXS-0704.00/FR	Utility - EPPAT	Abandoned	ANALOG-TO-DIGITAL CONVERSION METHOD AND DEVICE, IN HIGH-DENSITY MULTILEVEL NON-VOLATILE MEMORY DEVICES	11/23/2000	00127649.2	11/15/2006	1211812	FR
NMXS-0716.00/FR	Utility - EPPAT	Abandoned	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/13/2001	01129768.6	3/3/2004	1215679	FR
NMXS-0717.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL NONVOLATILE MEMORY CELL	1/15/2001	01830017.8	8/8/2007	1225595	FR
NMXS-0724.00/FR	Utility - EPPAT	Abandoned	NON-VOLATILE ELECTRICALLY ALTERABLE SEMICONDUCTOR MEMORY	1/24/2001	01830039.2	5/10/2006	1227499	FR
NMXS-0726.00/FR	Utility - EPPAT	Abandoned	METHOD FOR REFRESHING STORED DATA IN AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	2/19/2001	01830110.1	7/11/2007	1233421	FR
NMXS-0728.00/FR	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING DYNAMIC READING OF A MEMORY CELL WITH CONTROL OF THE INTEGRATION TIME	4/19/2001	01830266.1	8/15/2007	1251523	FR
NMXS-0740.00/FR	Utility - EPPAT	Abandoned	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/27/2001	01130836.8	3/3/2004	1220448	FR
NMXS-0747.00/FR	Utility - ORG	Abandoned	RAMP GENERATOR HAVING A LOW DROP-OUT	5/17/2000	0006262	8/15/2003	2809246	FR
NMXS-0748.00/FR	Utility - ORG	Abandoned	THRESHOLD AMPLIFIER	8/11/2000	0010554	10/11/2002	0010554	FR
NMXS-0749.00/FR	Utility - ORG	Abandoned	PAGE-ERASABLE FLASH MEMORY	11/15/2000	0014748			FR

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NMXS-0749.01/FR	Utility - NSPCT	Abandoned	PAGE-ERASABLE FLASH MEMORY	11/14/2001	01996861.9	4/6/2005	1342244	FR
NMXS-0750.00/FR	Utility - ORG	Abandoned	CIRCUIT FOR THE DETECTION OF A DEFECTIVE POWER SUPPLY CONNECTION	1/30/2001	0101255			FR
NMXS-0750.01/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR THE DETECTION OF A DEFECTIVE POWER SUPPLY CONNECTION	1/23/2002	02290165.6	4/14/2004	1227329	FR
NMXS-0751.00/FR	Utility - ORG	Abandoned	METHOD AND DEVICE FOR SEQUENTIAL READOUT OF A MEMORY WITH ADDRESS JUMP	2/23/2001	0102501			FR
NMXS-0752.00/FR	Utility - ORG	Abandoned	FLASH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL THRESHOLD VOLTAGES	11/15/2000	0014742	1/24/2003	2816750	FR
NMXS-0753.00/FR	Utility - ORG	Abandoned	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	3/13/2001	20010003401	6/27/2003	2822272	FR
NMXS-0753.01/FR	Utility - EPPAT	Abandoned	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	2/14/2002	02706857.6	5/11/2005	1368784	FR
NMXS-0754.00/FR	Utility - EPPAT	Abandoned	FLASH EEPROM AND EPROM ARRAYS WITH SELECT TRANSISTORS WITHIN THE BIT LINE PITCH	3/10/1995	95301607.8	8/14/2002	0673071	FR
NMXS-0756.00/FR	Utility - EPPAT	Abandoned	A MEMORY DEVICE	9/27/2002	02078984.8	9/6/2006	1306852	FR
NMXS-0757.00/FR	Utility - EPPAT	Abandoned	WORD LINE SELECTOR FOR A SEMICONDUCTOR MEMORY	2/20/2002	02425084.7	7/7/2004	1339069	FR
NMXS-0762.00/FR	Utility - EPPAT	Abandoned	MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS	9/28/2001	01830614.2	3/7/2007	1298670	FR
NMXS-0765.00/FR	Utility - EPPAT	Abandoned	SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON-VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD	8/5/2002	02019284.5	4/4/2007	1324344	FR
NMXS-0767.00/FR	Utility - EPPAT	Abandoned	FINITE STATE MACHINE INTERFACE HAS ARBITRATION STRUCTURE TO STORE COMMAND GENERATED BY INTERNAL CIRCUITS DURING EVALUATION PHASE OF STATE MACHINE FOR FLASH EEPROM DEVICE	12/4/2001	01830744.7	8/17/2005	1318440	FR
NMXS-0770.00/FR	Utility - EPPAT	Abandoned	ARCHITECTURE FOR A FLASH-EEPROM SIMULTANEOUSLY READABLE IN OTHER SECTORS WHILE ERASING AND/OR PROGRAMMING ONE OR MORE SECTORS	1/11/2002	02425009.4	3/30/2005	1327092	FR
NMXS-0771.00/FR	Utility - EPPAT	Lapsed	FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE	10/25/2001	01830671.2	10/3/2007	1308964	FR
NMXS-0782.00/FR	Utility - EPPAT	Abandoned	SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	2/20/2002	02425088.8	9/12/2007	1339103	FR
NMXS-0783.00/FR	Utility - EPPAT	Abandoned	CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS	2/20/2002	02425089.6	5/9/2007	1339111	FR
NMXS-0784.00/FR	Utility - EPPAT	Abandoned	BASIC STAGE FOR A CHARGE PUMP CIRCUIT	3/29/2002	02425199.3	11/9/2005	1349264	FR
NMXS-0788.00/FR	Utility - EPPAT	Abandoned	TEST STRUCTURE FOR THE MEASUREMENT OF CONTACT TO GATE DISTANCE IN NON-VOLATILE MEMORY DEVICES AND CORRESPONDING TEST METHOD	5/31/2002	02425360.1	8/3/2005	1367597	FR
NMXS-0800.00/FR	Utility - EPPAT	Abandoned	BUILT-IN TESTING METHODOLOGY IN FLASH MEMORY	2/27/2003	03425126.4	6/28/2006	1453062	FR
NMXS-0801.00/FR	Utility - EPPAT	Abandoned	SECTOR PROTECTION CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	7/31/2002	02255360.6	12/6/2006	1282135	FR
NMXS-0805.00/FR	Utility - ORG	Abandoned	CIRCUIT AND ASSOCIATED METHOD FOR THE ERASURE OR PROGRAMMING OF A MEMORY CELL	3/12/2001	0103284	5/23/2008	2821974	FR
NMXS-0806.00/FR	Utility - ORG	Abandoned	EEPROM MEMORY COMPRISING MEANS FOR SIMULTANEOUS READING OF SPECIAL BITS OF A FIRST AND SECOND TYPE	10/22/2001	0113635	1/30/2004	2831315	FR
NMXS-0807.00/FR	Utility - ORG	Abandoned	EEPROM WITH CONTROLLED PROGRAMMING CURRENT	6/25/2001	0108347			FR
NMXS-0808.00/FR	Utility - NSPCT	Abandoned	READ AMPLIFIER WITH A LOW CURRENT CONSUMPTION DIFFERENTIAL OUTPUT STAGE	11/20/2001	0114969	2/13/2004	2832566	FR
NMXS-0813.00/FR	Utility - EPPAT	Abandoned	REGULATION METHOD FOR THE SOURCE TERMINAL VOLTAGE IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	8/30/2002	02019433.8	3/14/2007	1331644	FR
NMXS-0814.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR FORMING TRENCHES WITH OBLIQUE PROFILE AND ROUNDED TOP CORNERS	6/28/2002	02425428.6	3/7/2007	1376683	FR
NMXS-0817.00/FR	Utility - EPPAT	Abandoned	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	10/8/2002	02425605.9	12/27/2006	1408550	FR

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MII Docket	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0818.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	10/8/2002	02425604.7	8/7/2007	1408549	FR
NMXS-0820.00/FR	Utility - EPPAT	Abandoned	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE, AND NONVOLATILE MEMORY DEVICE	4/26/2002	02425265.2	6/14/2006	1357559	FR
NMXS-0828.00/FR	Utility - EPPAT	Abandoned	SINGLE CELL ERASING METHOD FOR RECOVERING MEMORY CELLS UNDER PROGRAMMING DISTURBS IN NON VOLATILE SEMICONDUCTOR MEMORY DEVICES	11/28/2002	02425727.1	8/3/2005	1424700	FR
NMXS-0832.00/FR	Utility - EPPAT	Abandoned	VOLTAGE BOOST DEVICE AND MEMORY SYSTEM	7/4/2003	03425442.5	5/10/2006	1378913	FR
NMXS-0834.00/FR	Utility - EPPAT	Abandoned	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	12/16/2003	03104709.5	2/28/2007	1435574	FR
NMXS-0845.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING A MEMORY DEVICE HAVING SELECTOR TRANSISTORS FOR STORAGE ELEMENTS AND MEMORY DEVICE FABRICATED THEREBY	5/7/2003	03425292.4	7/19/2006	1475840	FR
NMXS-0853.00/FR	Utility - EPPAT	Abandoned	METHOD FOR DETECTING A RESISTIVE PATH OR A PREDETERMINED POTENTIAL IN NON-VOLATILE MEMORY ELECTRONIC DEVICES	9/30/2002	02425593.7	5/23/2007	1403880	FR
NMXS-0859.00/FR	Utility - EPPAT	Abandoned	METHOD FOR GENERATING A REFERENCE CURRENT FOR SENSE AMPLIFIERS AND CORRESPONDING GENERATOR	6/4/2003	03425353.4	8/16/2006	1484764	FR
NMXS-0869.00/FR	Utility - EPPAT	Issued	MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL-POLYSILICON LAYER TECHNOLOGY	12/23/2003	03104939.8	9/15/2010	1434257	FR
NMXS-0872.00/FR	Utility - EPPAT	Abandoned	METHOD FOR READING A NONVOLATILE MEMORY DEVICE AND NONVOLATILE MEMORY DEVICE IMPLEMENTING THE READING METHOD	4/10/2003	03425224.7	11/28/2007	1467377	FR
NMXS-0878.00/FR	Utility - EPPAT	Abandoned	GATE VOLTAGE REGULATION SYSTEM FOR A NON-VOLATILE MEMORY CELLS PROGRAMMING AND/OR SOFT PROGRAMMING PHASE	2/28/2003	03425134.8	10/12/2005	1453059	FR
NMXS-0883.00/FR	Utility - ORG	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING AN INTERNAL SUPPLY VOLTAGE MANAGEMENT DEVICE	4/23/2002	0205041			FR
NMXS-0883.01/FR	Utility - EPPAT	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING AN INTERNAL SUPPLY VOLTAGE MANAGEMENT DEVICE	4/17/2003	03358005.1	1/31/2007	1365418	FR
NMXS-0884.00/FR	Utility - ORG	Abandoned	PROGRAMMABLE POR CIRCUIT WITH TWO SWITCHING THRESHOLDS	8/16/2002	0210350	9/24/2004	2843660	FR
NMXS-0885.00/FR	Utility - ORG	Abandoned	EEPROM MEMORY COMPRISING A NON-VOLATILE REGISTER INTEGRATED INTO THE MEMORY ARRAY THEREOF	8/27/2002	0210611			FR
NMXS-0886.00/FR	Utility - ORG	Abandoned	DOUBLE READ STAGE SENSE AMPLIFIER	4/2/2003	0304077	7/15/2005	2853444	FR
NMXS-0887.00/FR	Utility - ORG	Abandoned	MANUFACTURING PROCESS FOR A FLASH MEMORY AND FLASH MEMORY THUS PRODUCED	1/22/2003	0300681	10/7/2005	2850205	FR
NMXS-0888.00/FR	Utility - ORG	Abandoned	FLASH MEMORY COMPRISING AN ERASE VERIFY ALGORITHM INTEGRATED INTO A PROGRAMMING ALGORITHM	2/27/2003	0302398	8/5/2005	2851843	FR
NMXS-0889.00/FR	Utility - ORG	Abandoned	NEGATIVE VOLTAGE WORD LINE DECODER, HAVING COMPACT TERMINATING ELEMENTS	1/21/2003	0300615			FR
NMXS-0890.00/FR	Utility - ORG	Abandoned	SECTORED FLASH MEMORY COMPRISING MEANS FOR CONTROLLING AND FOR REFRESHING MEMORY CELLS	2/10/2003	0301558	4/22/2005	2851074	FR
NMXS-0891.00/FR	Utility - ORG	Abandoned	METHOD FOR ERASING/PROGRAMMING A NON-VOLATILE ELECTRICALLY ERASABLE MEMORY	7/31/2003	0309456			FR
NMXS-0892.00/FR	Utility - ORG	Abandoned	WORD-PROGRAMMABLE FLASH MEMORY	6/12/2003	0307050			FR
NMXS-0892.01/FR	Utility - EPPAT	Abandoned	WORD-PROGRAMMABLE FLASH MEMORY	5/26/2004	04012393.7	4/9/2008	1486986	FR
NMXS-0893.00/FR	Utility - EPPAT	Abandoned	METHOD FOR MANUFACTURING DIFFERENTIAL ISOLATION STRUCTURES IN A SEMICONDUCTOR ELECTRONIC DEVICE AND CORRESPONDING STRUCTURE	7/11/2003	03425459.9	1/2/2008	1496548	FR
NMXS-0920.00/FR	Utility - EPPAT	Abandoned	REDUNDANCY BASED NAND FLASH MEMORY	7/14/2004	04103354.9	10/25/2006	1617438	FR
NMXS-0943.00/FR	Utility - EPPAT	Lapsed	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	6/14/2004	04425435.7	8/15/2007	1607984	FR
NMXS-0944.00/FR	Utility - EPPAT	Abandoned	ROW DECODER FOR NAND MEMORIES	8/11/2004	04425626.3	2/21/2007	1626413	FR

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NMXS-0948.00/FR	Utility - ORG	Abandoned	FLASH MEMORY COMPRISING MEANS FOR CHECKING AND REFRESHING MEMORY CELLS IN THE ERASED STATE	6/12/2003	0307052			FR
NMXS-0949.00/FR	Utility - ORG	Abandoned	MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD	8/18/2003	0309987			FR
NMXS-0949.01/FR	Utility - EPPAT	Abandoned	MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD	6/30/2004	04291653.6	8/15/2007	1508901	FR
NMXS-0950.00/FR	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	12/12/2003	0314521			FR
NMXS-0950.01/FR	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	12/8/2004	04029018.1	4/11/2007	1542130	FR
NMXS-0951.00/FR	Utility - EPPAT	Abandoned	METHOD FOR DESIGNING AN EXTENTED MEMORY ARRAY USING A PLURALITY OF SERIAL MEMORIES	12/12/2003	0314628			FR
NMXS-0952.00/FR	Utility - ORG	Abandoned	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION	12/12/2003	0314622			FR
NMXS-0952.01/FR	Utility - EPPAT	Abandoned	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION	12/8/2004	04029016.5	5/30/2007	1542233	FR
NMXS-0974.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	11/18/2005	05025286.5	10/3/2007	1670002	FR
NMXS-0991.00/FR	Utility - EPPAT	Abandoned	DEVICE FOR AUTOMATICALLY OPENING AND CLOSING CASH CONTAINER	1/28/2005	05100551.0	1/9/2008	1686591	FR
NMXS-1016.00/FR	Utility - EPPAT	Abandoned	SEQUENTIAL PROGRAM-VERIFY METHOD WITH RESULT BUFFERING	3/30/2004	04101301.2	8/1/2007	1583102	FR
NMXS-1037.00/FR	Utility - EPPAT	Lapsed	A COLUMN DECODING SYSTEM FOR SEMICONDUCTOR MEMORY DEVICES IMPLEMENTED WITH LOW VOLTAGE TRANSISTORS	4/12/2006	061125286	4/1/2009	1845532	FR
NMXS-1104.00/FR	Utility - ORG	Abandoned	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	10/23/1985	8515780	3/30/1590	2572217	FR
NMXS-1105.00/FR	Utility - EPPAT	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	10/9/1986	86830293.6	8/29/1990	0226549	FR
NMXS-1106.00/FR	Utility - EPPAT	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/29/1987	87830204.1	2/27/1991	0256993	FR
NMXS-1107.00/FR	Utility - EPPAT	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/12/1987	87830234.8	4/21/1993	0255489	FR
NMXS-1108.00/FR	Utility - EPPAT	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	5/4/1988	88107152.6	9/9/1992	0298215	FR
NMXS-1109.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/15/1988	88120977.9	5/12/1993	0322665	FR
NMXS-1110.00/FR	Utility - EPPAT	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	89100780.9	10/20/1993	0326004	FR
NMXS-1111.00/FR	Utility - EPPAT	Abandoned	CMOS VOLTAGE MULTIPLIER	6/16/1989	89830269.0	2/9/1994	0349495	FR
NMXS-1116.00/FR	Utility - EPPAT	Abandoned	PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	12/22/1989	89830569.3	7/19/1995	0376905	FR
NMXS-1117.00/FR	Utility - EPPAT	Abandoned	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/14/1990	90313667.9	11/8/1995	0435534	FR
NMXS-1118.00/FR	Utility - EPPAT	Abandoned	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	2/7/1991	91830037.7	5/10/1995	0445083	FR
NMXS-1119.00/FR	Utility - EPPAT	Abandoned	READING CIRCUIT FOR NONVOLATILEMEMORY CELL.	2/7/1991	91830036.9	1/3/1996	0443989	FR
NMXS-1120.00/FR	Utility - EPPAT	Abandoned	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	3/19/1991	91104217.4	9/13/1995	0450389	FR
NMXS-1121.00/FR	Utility - EPPAT	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	4/24/1991	91830167.2	11/25/1998	0454636	FR
NMXS-1122.00/FR	Utility - EPPAT	Abandoned	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	4/4/1991	91105323.9	12/29/1997	0455002	FR

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MG Docket No	Matter Type	Matter Status	Title	File Date	Serial No	Issue Date	Patent No	Country
NMXS-1123.00/FR	Utility - EPPAT	Abandoned	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	6/27/1991	91201641.7	5/28/1997	0464928	FR
NMXS-1125.00/FR	Utility - EPPAT	Abandoned	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	9/30/1991	91116659.3	8/13/1997	0479191	FR
NMXS-1126.00/FR	Utility - EPPAT	Abandoned	TWO PHASES SCAN PATH WITH SINGLECLOCK.	10/15/1991	91202668.9	7/8/1998	0482697	FR
NMXS-1127.00/FR	Utility - EPPAT	Abandoned	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	11/19/1990	90830529.5	2/19/1997	0487808	FR
NMXS-1128.00/FR	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/19/1990	90830530.3	5/8/1996	0486743	FR
NMXS-1129.00/FR	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/13/1990	90830583.2	5/1/1996	0491105	FR
NMXS-1130.00/FR	Utility - EPPAT	Abandoned	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/20/1991	91121952.5	4/2/1997	0492506	FR
NMXS-1131.00/FR	Utility - EPPAT	Abandoned	MEMORY CELL READING CIRCUIT	12/18/1991	91121675.2	3/12/1997	0492382	FR
NMXS-1132.00/FR	Utility - EPPAT	Abandoned	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	5/5/1992	92830205.8	7/29/1998	0514350	FR
NMXS-1133.00/FR	Utility - EPPAT	Abandoned	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	7/21/1992	92830400.5	10/15/1997	0526427	FR
NMXS-1134.00/FR	Utility - EPPAT	Abandoned	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	8/27/1992	92830458.3	7/2/1997	0530159	FR
NMXS-1135.00/FR	Utility - EPPAT	Abandoned	ROW DECODER FOR NAND-TYPE ROM	8/27/1992	92830457.5	3/4/1998	0534910	FR
NMXS-1136.00/FR	Utility - EPPAT	Abandoned	PLANARIZED CONTACT WITH A SANDWICH OF TUNGSTEN AND ALUMINIUM.	11/10/1992	92119191.2	9/22/1999	0543254	FR
NMXS-1137.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	11/2/1992	92118785.2	9/27/2000	0545082	FR
NMXS-1138.00/FR	Utility - EPPAT	Abandoned	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	9/24/1992	92830523.4	1/21/1998	0536095	FR
NMXS-1139.00/FR	Utility - EPPAT	Abandoned	METALLIZATION OVER TUNGSTEN PLUGS	5/27/1992	92830265.2	9/18/1996	0571691	FR
NMXS-1140.00/FR	Utility - EPPAT	Abandoned	LOW SWITCHING NOISE OUTPUT BUFFER	6/26/1992	92830335.3	10/31/2001	0585505	FR
NMXS-1141.00/FR	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	6/30/1992	92830339.5	9/13/1995	0576773	FR
NMXS-1142.00/FR	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	6/30/1992	92830340.3	9/15/1999	0576774	FR
NMXS-1143.00/FR	Utility - EPPAT	Abandoned	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	9/30/1992	92830541.6	12/2/1998	0591598	FR
NMXS-1144.00/FR	Utility - EPPAT	Abandoned	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	10/1/1992	92830552.3	5/27/1998	0575688	FR
NMXS-1145.00/FR	Utility - EPPAT	Abandoned	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	10/29/1992	92830589.5	7/28/1999	0594920	FR
NMXS-1146.00/FR	Utility - EPPAT	Abandoned	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	11/18/1992	92830625.7	5/28/1997	0598168	FR
NMXS-1147.00/FR	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	1/29/1993	93830031.6	5/6/1999	0608664	FR
NMXS-1148.00/FR	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS	1/29/1993	93830032.4	1/7/1998	0608665	FR
NMXS-1149.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS	2/11/1993	93830050.6	9/10/1997	0610643	FR
NMXS-1150.00/FR	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830057.1	7/30/1997	0613176	FR
NMXS-1151.00/FR	Utility - EPPAT	Abandoned	NONVOLATILE EPROM, EEPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830058.9	10/13/1999	0614223	FR
NMXS-1152.00/FR	Utility - EPPAT	Abandoned	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	3/18/1993	93830109.0	6/23/1999	0616332	FR
NMXS-1153.00/FR	Utility - EPPAT	Abandoned	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	3/18/1993	93830110.8	6/23/1999	0616333	FR
NMXS-1154.00/FR	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS	3/31/1993	93830128.0	7/22/1998	0618587	FR
NMXS-1155.00/FR	Utility - EPPAT	Abandoned	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	4/1/1993	93830134.8	7/28/1999	0595775	FR

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Matter Number	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1157.00/FR	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/11/1991	9112538	1/10/1997	2682522	FR
NMXS-1157.01/FR	Utility - NSPCT	Abandoned	METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/9/1992	92402777.4	3/4/1998	0537082	FR
NMXS-0001.00/GB	Utility - EPPAT	Abandoned	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/9/1988	88403140.2	4/10/1996	0321327	GB
NMXS-0002.00/GB	Utility - EPPAT	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/9/1988	88403141.0	1/13/1993	0323295	GB
NMXS-0003.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/26/1989	89401183.2	5/10/1993	0340107	GB
NMXS-0004.00/GB	Utility - EPPAT	Lapsed	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/19/1993	93401861.5	2/15/1995	0585150	GB
NMXS-0005.00/GB	Utility - EPPAT	Abandoned	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	7/15/1993	93401836.7	12/28/1994	0581639	GB
NMXS-0006.00/GB	Utility - EPPAT	Lapsed	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	9/14/1993	93402229.4	1/18/1995	0591022	GB
NMXS-0007.00/GB	Utility - EPPAT	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/14/1993	93403029.7	4/3/1996	0604270	GB
NMXS-0008.00/GB	Utility - EPPAT	Abandoned	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/19/1987	87401120.8	3/14/1990	0246965	GB
NMXS-0011.00/GB	Utility - EPPAT	Lapsed	CONTENT ADDRESSABLE MEMORY	5/23/1991	91304677.7	8/16/2000	0459703	GB
NMXS-0012.00/GB	Utility - EPPAT	Lapsed	REDUNDANCY FOR SERIAL MEMORY	12/21/1990	90314116.6	4/23/1997	0437081	GB
NMXS-0013.00/GB	Utility - EPPAT	Lapsed	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	3/25/1991	91302575.5	12/16/1998	0455839	GB
NMXS-0014.00/GB	Utility - EPPAT	Lapsed	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/19/1990	90313891.5	4/1/1998	0434381	GB
NMXS-0015.00/GB	Utility - EPPAT	Lapsed	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/16/1991	91309521.2	7/29/1998	0481751	GB
NMXS-0016.00/GB	Utility - EPPAT	Lapsed	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	6/29/1990	90307156.1	1/8/1997	0420388	GB
NMXS-0017.00/GB	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/12/1991	91307425.8	3/19/1997	0471543	GB
NMXS-0018.00/GB	Utility - EPPAT	Lapsed	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	5/31/1991	91304952.4	12/18/1996	0501057	GB
NMXS-0019.00/GB	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	5/31/1991	91304951.6	7/30/1997	0472266	GB
NMXS-0020.00/GB	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307423.3	3/19/1997	0471541	GB
NMXS-0021.00/GB	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307419.1	6/26/1996	0475588	GB
NMXS-0022.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308632.8	6/18/1997	0478251	GB
NMXS-0023.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308633.6	4/8/1998	0478252	GB
NMXS-0024.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	96117267.3	2/18/2004	0768676	GB
NMXS-0024.01/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	91307426.6	5/14/1997	0471544	GB
NMXS-0025.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/21/1991	91309721.8	1/7/1998	0482869	GB
NMXS-0026.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/23/1991	91308634.4	11/27/1996	0478253	GB

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NMXS-0027.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/23/1991	91308636.9	5/28/1997	0478254	GB
NMXS-0028.00/GB	Utility - EPPAT	Abandoned	ADDRESS BUFFER CIRCUIT HAVING LATCHING BASED ON TRANSITION	10/21/1991	91309720.0	1/7/1998	0482868	GB
NMXS-0029.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH PRECHARGED REDUNDANCY MULTIPLEXING	12/12/1991	91311569.7	9/11/1996	0491523	GB
NMXS-0030.00/GB	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH COLUMN DECODED BIT LINE EQUILIBRATE	12/11/1991	91311506.9	10/4/2000	0490650	GB
NMXS-0031.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/12/1991	91311570.5	9/24/1997	0490679	GB
NMXS-0032.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/12/1991	91311571.3	10/2/1996	0490680	GB
NMXS-0033.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	7/16/1992	92306526.2	3/4/1998	0523995	GB
NMXS-0034.00/GB	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	4/30/1992	92303960.6	10/20/1999	0514050	GB
NMXS-0035.00/GB	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR DUAL PORT MEMORY	4/30/1992	92303958.0	7/22/1998	0514049	GB
NMXS-0036.00/GB	Utility - EPPAT	Abandoned	CACHE TAG PARITY DETECT CIRCUIT	9/27/1992	92307736.1	10/8/2007	0506474	GB
NMXS-0037.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	7/16/1992	92306527.0	3/4/1998	0523996	GB
NMXS-0038.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT DUAL-PORT MEMORY DEVICE HAVING REDUCED CAPACITANCE	7/16/1992	92306528.8	5/20/1998	0523997	GB
NMXS-0039.00/GB	Utility - EPPAT	Abandoned	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	1/20/1993	93300397.2	7/8/1998	0552941	GB
NMXS-0040.00/GB	Utility - EPPAT	Abandoned	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	11/29/1993	93309496.3	6/13/2001	0600692	GB
NMXS-0041.00/GB	Utility - EPPAT	Abandoned	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	12/16/1992	92311510.9	3/3/1999	0547888	GB
NMXS-0042.00/GB	Utility - EPPAT	Abandoned	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/16/1992	92311511.7	4/14/1999	0547889	GB
NMXS-0045.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	12/16/1992	92311514.1	10/28/1998	0547892	GB
NMXS-0046.00/GB	Utility - EPPAT	Abandoned	REDUNDANCY DECODER	1/27/1993	93300560.5	7/22/1998	0554052	GB
NMXS-0049.00/GB	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR	4/29/1993	93303369.8	12/29/1999	0568373	GB
NMXS-0050.00/GB	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE	4/29/1993	93303370.6	10/20/1999	0568374	GB
NMXS-0051.00/GB	Utility - EPPAT	Abandoned	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	3/22/1993	93302156.0	6/20/2001	0564137	GB
NMXS-0052.00/GB	Utility - EPPAT	Abandoned	PARALLELIZED DIFFERENCE FLAG LOGIC	5/19/1993	93303874.7	2/23/2000	0574144	GB
NMXS-0053.00/GB	Utility - EPPAT	Abandoned	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/10/1993	93304489.3	12/20/2000	0579375	GB
NMXS-0059.00/GB	Utility - EPPAT	Lapsed	INTEGRATED CIRCUIT OUTPUT DRIVER	8/27/1993	93305835.5	3/26/1997	0586207	GB
NMXS-0062.00/GB	Utility - EPPAT	Abandoned	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/21/1993	93310384.8	3/3/1999	0604195	GB
NMXS-0064.00/GB	Utility - EPPAT	Abandoned	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/18/1994	94300188.2	5/10/2000	0612008	GB
NMXS-0065.00/GB	Utility - EPPAT	Abandoned	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/30/1993	93307776.0	3/3/1999	0590982	GB
NMXS-0066.00/GB	Utility - EPPAT	Abandoned	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/27/1993	93306836.3	10/29/1997	0586208	GB
NMXS-0067.00/GB	Utility - EPPAT	Abandoned	TEMPERATURE-COMPENSATED VOLTAGE LEVEL SENSE CIRCUIT	4/26/1994	94303005.6	4/3/2002	0626582	GB
NMXS-0068.00/GB	Utility - EPPAT	Abandoned	ADDRESS BUFFER	4/28/1994	94303082.5	9/22/1999	0622803	GB
NMXS-0069.00/GB	Utility - EPPAT	Abandoned	METHOD FOR STRESS TESTING DECODERS AND PERIPHERY CIRCUITS	4/28/1994	94303083.3	7/28/1999	0622809	GB
NMXS-0071.00/GB	Utility - EPPAT	Abandoned	OUTPUT DRIVER CIRCUIT	7/28/1993	93305947.9	2/24/1999	0581579	GB
NMXS-0072.00/GB	Utility - EPPAT	Lapsed	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	7/27/1994	94305553.3	11/10/1999	0637036	GB
NMXS-0073.00/GB	Utility - EPPAT	Abandoned	TEMPERATURE-STABLE CURRENT SOURCE	6/12/1995	95401363.7	4/8/1998	0687967	GB
NMXS-0074.00/GB	Utility - EPPAT	Lapsed	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	5/31/1993	93830243.7	12/15/2004	0627763	GB
NMXS-0075.00/GB	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/30/1993	93830403.7	12/1/1999	0646924	GB
NMXS-0076.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	9/10/1993	93830365.8	12/2/1998	0643418	GB
NMXS-0077.00/GB	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/30/1993	93830481.3	2/10/1999	0655742	GB
NMXS-0079.00/GB	Utility - EPPAT	Lapsed	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/24/1993	93830464.9	7/28/1999	0654791	GB
NMXS-0080.00/GB	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/7/1993	93830491.2	3/17/1999	0657814	GB

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NMXS-0081.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	11/30/1993	93830474.8	8/25/1999	0655743	GB
NMXS-0082.00/GB	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830063.9	7/8/1998	0668563	GB
NMXS-0083.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/9/1993	93830493.8	9/2/1998	0657811	GB
NMXS-0084.00/GB	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/29/1994	94830146.0	8/5/1998	0675440	GB
NMXS-0085.00/GB	Utility - EPPAT	Abandoned	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/21/1994	94830022.3	10/7/1998	0665485	GB
NMXS-0086.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE-MEMORY OUTPUT DATA	2/18/1994	94830069.4	7/7/1999	0678869	GB
NMXS-0087.00/GB	Utility - EPPAT	Abandoned	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/18/1994	94830070.2	5/17/2000	0668592	GB
NMXS-0088.00/GB	Utility - EPPAT	Abandoned	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/18/1994	94830071.0	6/7/2000	0678873	GB
NMXS-0089.00/GB	Utility - EPPAT	Abandoned	COUNT UNIT FOR NONVOLATILE MEMORIES	12/28/1993	93830527.3	7/7/1999	0662691	GB
NMXS-0090.00/GB	Utility - EPPAT	Abandoned	END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES	12/28/1993	93830526.5	3/31/1999	0661814	GB
NMXS-0091.00/GB	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	12/28/1993	93830525.7	7/16/1997	0661795	GB
NMXS-0092.00/GB	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1993	93830489.6	5/27/1998	0662690	GB
NMXS-0093.00/GB	Utility - EPPAT	Abandoned	READING CIRCUIT FOR AN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1994	94830124.7	5/31/2000	0678871	GB
NMXS-0094.00/GB	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/30/1993	93830478.9	9/1/1999	0655683	GB
NMXS-0095.00/GB	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/31/1994	94830032.2	5/23/2001	0665558	GB
NMXS-0096.00/GB	Utility - EPPAT	Abandoned	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/31/1994	94830156.9	7/11/2001	0675504	GB
NMXS-0098.00/GB	Utility - EPPAT	Lapsed	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	12/31/1993	93830537.2	6/9/1999	0661713	GB
NMXS-0099.00/GB	Utility - EPPAT	Abandoned	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1993	93830482.1	5/10/2000	0655669	GB
NMXS-0100.00/GB	Utility - EPPAT	Abandoned	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1994	94830077.7	9/26/2001	0668593	GB
NMXS-0101.00/GB	Utility - EPPAT	Abandoned	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830540.5	6/23/1999	0661714	GB
NMXS-0102.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	12/31/1993	93830545.5	3/29/2000	0661717	GB
NMXS-0103.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830542.2	6/9/1999	0661715	GB
NMXS-0104.00/GB	Utility - EPPAT	Abandoned	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/29/1993	93830528.1	9/23/1998	0661636	GB
NMXS-0105.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/18/1994	94830073.6	7/28/1999	0678870	GB
NMXS-0106.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/18/1994	94830074.4	10/20/1999	0668591	GB
NMXS-0107.00/GB	Utility - EPPAT	Abandoned	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH	4/19/1994	94830182.5	7/26/2000	0678874	GB
NMXS-0108.00/GB	Utility - EPPAT	Abandoned	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME	3/28/1994	94830144.5	10/4/2001	0676816	GB
NMXS-0109.00/GB	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830061.1	8/5/1998	0668562	GB
NMXS-0110.00/GB	Utility - EPPAT	Abandoned	REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS	3/28/1994	94830143.7	12/27/2000	0676768	GB
NMXS-0111.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	12/31/1993	93830543.0	7/21/1999	0661716	GB
NMXS-0112.00/GB	Utility - EPPAT	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	4/28/1994	94303084.1	4/7/1999	0627817	GB

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NMXS-0113.00/GB	Utility - EPPAT	Abandoned	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/10/1994	94302808.4	11/11/1998	0621537	GB
NMXS-0115.00/GB	Utility - EPPAT	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	6/27/1994	94304643.3	9/8/1999	0632594	GB
NMXS-0117.00/GB	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	6/27/1994	94304644.1	3/14/2001	0634751	GB
NMXS-0118.00/GB	Utility - EPPAT	Abandoned	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	6/27/1994	94304645.8	9/19/2001	0632460	GB
NMXS-0124.00/GB	Utility - EPPAT	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	7/27/1994	94305554.1	9/23/1998	0637134	GB
NMXS-0130.00/GB	Utility - EPPAT	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	9/28/1994	94307070.6	3/20/2002	0647028	GB
NMXS-0131.00/GB	Utility - EPPAT	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	99300541.2	3/6/2002	0952549	GB
NMXS-0131.01/GB	Utility - EPPAT	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	94307068.0	5/31/2000	0646926	GB
NMXS-0138.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/21/1994	94460043.6	5/29/1996	0654792	GB
NMXS-0139.00/GB	Utility - EPPAT	Abandoned	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	5/25/1994	94401162.6	10/4/2001	0626728	GB
NMXS-0140.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/26/1994	94460037.8	12/16/1998	0651394	GB
NMXS-0141.00/GB	Utility - EPPAT	Abandoned	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/21/1994	94470041.8	4/14/1999	0660331	GB
NMXS-0142.00/GB	Utility - EPPAT	Abandoned	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/16/1994	94402912.3	8/21/1996	0660333	GB
NMXS-0144.00/GB	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/23/1995	95470006.8	10/16/1996	0669622	GB
NMXS-0145.00/GB	Utility - EPPAT	Lapsed	MEMORY REDUNDANCY CIRCUIT	2/27/1995	95400420.6	6/19/1996	0669576	GB
NMXS-0146.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/20/1995	95400608.6	10/6/1999	0675503	GB
NMXS-0147.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400190.5	10/16/1996	0666572	GB
NMXS-0148.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400189.7	6/26/1996	0666576	GB
NMXS-0149.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400188.9	6/26/1996	0665559	GB
NMXS-0150.00/GB	Utility - EPPAT	Abandoned	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/14/1995	95470014.2	9/18/1996	0678801	GB
NMXS-0151.00/GB	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER CIRCUIT	4/14/1995	95470013.4	6/18/1997	0678868	GB
NMXS-0152.00/GB	Utility - EPPAT	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/6/1995	95400772.0	9/29/1999	0678875	GB
NMXS-0153.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/17/1995	95460007.8	1/22/1997	0674264	GB
NMXS-0154.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/3/1995	95460015.1	8/21/1996	0676769	GB
NMXS-0155.00/GB	Utility - EPPAT	Abandoned	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	7/18/1995	95401709.1	12/18/1996	0696031	GB
NMXS-0156.00/GB	Utility - EPPAT	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/20/1995	95400607.8	6/2/1999	0675441	GB
NMXS-0157.00/GB	Utility - EPPAT	Abandoned	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/7/1994	94830276.5	3/7/2001	0686978	GB
NMXS-0158.00/GB	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY ELEMENT	3/31/1994	94830154.4	6/13/2001	0675501	GB
NMXS-0159.00/GB	Utility - EPPAT	Abandoned	SENSE AMPLIFIER WITH HYSTERESIS	5/3/1994	94830209.6	3/28/2001	0681293	GB
NMXS-0160.00/GB	Utility - EPPAT	Abandoned	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	4/12/1994	94830167.6	3/17/1999	0677869	GB
NMXS-0161.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/30/1994	94830591.7	3/26/2003	0720223	GB
NMXS-0162.00/GB	Utility - EPPAT	Abandoned	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	6/10/1994	94830283.1	3/7/2001	0686979	GB
NMXS-0163.00/GB	Utility - EPPAT	Abandoned	METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL	7/18/1994	94830362.1	10/14/1998	0696050	GB

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NMXS-0164.00/GB	Utility - EPPAT	Abandoned	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	9/30/1994	94830471.2	12/1/1999	0704864	GB
NMXS-0166.00/GB	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	11/30/1994	94830554.5	10/23/2002	0715312	GB
NMXS-0168.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS	9/30/1994	94830468.8	12/15/1999	0704901	GB
NMXS-0170.00/GB	Utility - EPPAT	Abandoned	SYNCHRONIZATION DEVICE FOR OUTPUT STAGES, PARTICULARLY FOR ELECTRONIC MEMORIES	11/18/1994	94830538.8	1/9/2002	0713221	GB
NMXS-0171.00/GB	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING	4/4/1995	95830133.5	6/27/2001	0736876	GB
NMXS-0173.00/GB	Utility - EPPAT	Abandoned	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	5/19/1995	95830211.9	3/29/2000	0743648	GB
NMXS-0174.00/GB	Utility - EPPAT	Abandoned	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	1/26/1995	95830020.4	4/11/2001	0724267	GB
NMXS-0175.00/GB	Utility - EPPAT	Abandoned	TWIN-WELL MANUFACTURING PROCESS FOR AN EEPROM INTEGRATED DEVICE WITH REDUCED BODY EFFECT	11/24/1994	94830544.6	2/6/2002	0714133	GB
NMXS-0179.00/GB	Utility - EPPAT	Abandoned	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	5/5/1995	95830184.8	1/12/2000	0741387	GB
NMXS-0180.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	6/30/1995	95830281.2	11/27/2002	0751559	GB
NMXS-0181.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC	6/30/1995	95830282.0	11/27/2002	0751560	GB
NMXS-0183.00/GB	Utility - EPPAT	Abandoned	METHOD FOR IMPROVING THE PROFILE OF THE INTERMEDIATE DIELECTRIC, PARTICULARLY FOR NON VOLATILE MEMORIES	2/28/1996	96830086.3	12/10/2003	0793273	GB
NMXS-0184.00/GB	Utility - EPPAT	Abandoned	CHARGE PUMP VOLTAGE MULTIPLIER CIRCUIT	12/5/1994	94830583.6	6/12/2002	0716368	GB
NMXS-0185.00/GB	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS	4/14/1995	95830153.3	9/13/2000	0737643	GB
NMXS-0186.00/GB	Utility - EPPAT	Abandoned	CURRENT DETECTING CIRCUIT	8/3/1995	95830354.7	1/26/2000	0757357	GB
NMXS-0187.00/GB	Utility - EPPAT	Lapsed	HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES	9/29/1995	95830405.7	4/4/2001	0768672	GB
NMXS-0189.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	12/2/1994	94308981.3	9/1/1999	0675439	GB
NMXS-0190.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	12/9/1994	94309218.9	3/24/1999	0675597	GB
NMXS-0194.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	5/24/1995	95303484.0	12/1/1999	0685851	GB
NMXS-0202.00/GB	Utility - EPPAT	Abandoned	CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES	10/27/1995	95307657.7	10/4/2001	0709853	GB
NMXS-0205.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	11/21/1995	95308348.2	2/2/2003	0717334	GB
NMXS-0207.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE	11/28/1995	95308560.2	6/27/2001	0718739	GB
NMXS-0208.00/GB	Utility - EPPAT	Abandoned	OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE	11/28/1995	95308561.0	2/20/2002	0718977	GB
NMXS-0209.00/GB	Utility - EPPAT	Abandoned	ADJUSTABLE CURRENT SOURCE	11/28/1995	95308562.8	10/31/2001	0718744	GB
NMXS-0210.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT	11/28/1995	95308543.8	3/15/2000	0718743	GB
NMXS-0211.00/GB	Utility - EPPAT	Abandoned	DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT	11/28/1995	95308563.6	8/30/2000	0718740	GB
NMXS-0214.00/GB	Utility - ORG	Abandoned	INTERNAL BUS CONTROL(FLASH MEMORY DEVICE TEST MODE TO DRIVE AN INTERNAL CONTROLBUS EXTERNALLY]	8/26/1994	9417297.0			GB
NMXS-0214.01/GB	Utility - EPPAT	Abandoned	INTERNAL BUS CONTROL(FLASH MEMORY DEVICE TEST MODE TO DRIVE AN INTERNAL CONTROLBUS EXTERNALLY]	8/21/1995	95305818.7	11/10/1999	0698848	GB
NMXS-0215.00/GB	Utility - ORG	Abandoned	RESIDUAL CHARGE ELIMINATION FOR A MEMORY DEVICE	12/29/1994	9426337.3			GB
NMXS-0215.01/GB	Utility - EPPAT	Abandoned	RESIDUAL CHARGE ELIMINATION FOR A MEMORY DEVICE	12/27/1995	95309478.6	6/5/2002	0721188	GB

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NMXS-0216.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/14/1995	95402815.5	2/25/1998	0718850	GB
NMXS-0217.00/GB	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/11/1995	95402054.1	4/22/1998	0703584	GB
NMXS-0218.00/GB	Utility - EPPAT	Abandoned	CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM	5/15/1996	96401080.5	7/25/2001	0743650	GB
NMXS-0219.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/14/1995	95402820.5	4/22/1998	0718849	GB
NMXS-0220.00/GB	Utility - EPPAT	Abandoned	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/17/1996	96470009.0	4/29/1998	0750244	GB
NMXS-0221.00/GB	Utility - EPPAT	Abandoned	RESISTANCE REFERENCE CIRCUIT	12/21/1995	95402912.0	5/19/1999	0718887	GB
NMXS-0222.00/GB	Utility - EPPAT	Abandoned	DIGITAL RAMP GENERATOR	5/29/1996	96401155.5	4/7/1999	0745996	GB
NMXS-0225.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR READING NON-VOLATILE MEMORIES	8/4/1995	95830357.0	5/28/2001	0757358	GB
NMXS-0226.00/GB	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT	3/23/1995	95830110.3	1/26/2000	0734024	GB
NMXS-0227.00/GB	Utility - EPPAT	Abandoned	READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE	4/28/1995	95830172.3	4/10/2002	0747903	GB
NMXS-0228.00/GB	Utility - EPPAT	Abandoned	MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS	7/28/1995	95830336.4	7/5/2000	0756285	GB
NMXS-0229.00/GB	Utility - EPPAT	Abandoned	THRESHOLD DETECTING DEVICE	8/4/1995	95830360.4	3/28/2001	0757352	GB
NMXS-0230.00/GB	Utility - EPPAT	Abandoned	CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES	7/28/1995	95830335.6	10/11/2000	0756220	GB
NMXS-0231.00/GB	Utility - EPPAT	Abandoned	FLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE	8/2/1995	95830351.3	5/23/2001	0758129	GB
NMXS-0232.00/GB	Utility - EPPAT	Abandoned	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/19/1995	95830253.1	1/26/2000	0750314	GB
NMXS-0233.00/GB	Utility - EPPAT	Abandoned	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	9/29/1995	95830406.5	1/26/2000	0766255	GB
NMXS-0234.00/GB	Utility - EPPAT	Abandoned	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	7/14/1995	95830302.6	1/26/2000	0753859	GB
NMXS-0235.00/GB	Utility - EPPAT	Lapsed	VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE	9/29/1995	95830407.3	11/1/1999	0766256	GB
NMXS-0236.00/GB	Utility - EPPAT	Abandoned	ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	3/29/1996	96830174.7	7/28/2004	0798735	GB
NMXS-0237.00/GB	Utility - EPPAT	Abandoned	DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY	6/20/1996	96830352.9	5/28/2003	0782149	GB
NMXS-0238.00/GB	Utility - EPPAT	Abandoned	SYSTEM FOR DETERMINING THE PROGRAMMED/NON PROGRAMMED STATUS OF A MEMORY CELL	3/29/1996	96830163.0	11/12/2003	0798740	GB
NMXS-0239.00/GB	Utility - EPPAT	Abandoned	BOOST REGULATOR	1/24/1996	96830026.9	3/31/2004	0786777	GB
NMXS-0241.00/GB	Utility - EPPAT	Abandoned	REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS	3/29/1996	96830160.6	11/3/2004	0798729	GB
NMXS-0242.00/GB	Utility - EPPAT	Abandoned	TIME SHARING INTERNATIONAL BUS, PARTICULARLY FOR NON VOLATILE MEMORIES	3/20/1996	96830129.1	12/11/2002	0797209	GB
NMXS-0243.00/GB	Utility - EPPAT	Abandoned	PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD	7/31/1995	95830847.1	4/19/2000	0757355	GB
NMXS-0244.00/GB	Utility - EPPAT	Abandoned	SUPPLY VOLTAGES SWITCHES CIRCUIT	6/20/1996	96830353.7	4/24/2002	0782268	GB
NMXS-0246.00/GB	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS	10/31/1995	95830461.0	7/23/2003	0772200	GB
NMXS-0247.00/GB	Utility - EPPAT	Abandoned	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	7/24/1995	95830317.4	1/26/2000	0756286	GB

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NMXS-0248.00/GB	Utility - EPPAT	Abandoned	NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	10/31/1995	95830456.0	3/15/2000	0772282	GB
NMXS-0249.00/GB	Utility - EPPAT	Abandoned	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	11/3/1995	95830466.9			GB
NMXS-0250.00/GB	Utility - EPPAT	Issued	MEMORY DEVICE WITH IMPROVED YIELD AND RELIABILITY	9/29/1995	95830408.1	5/22/2002	0766174	GB
NMXS-0251.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR THE GENERATION OF A VOLTAGE AS A FUNCTION OF THE CONDUCTIVITY OF AN ELEMENTARY CELL OF A NON-VOLATILE MEMORY	3/29/1996	96830168.9	11/24/2004	0798743	GB
NMXS-0252.00/GB	Utility - EPPAT	Abandoned	ZERO CONSUMPTION POWER-ON-RESET	2/2/1996	96830046.7	11/13/2002	0788114	GB
NMXS-0253.00/GB	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES	3/29/1996	96830167.1	11/7/2001	0798642	GB
NMXS-0254.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL	12/14/1995	95830520.3	9/13/2000	0779642	GB
NMXS-0255.00/GB	Utility - EPPAT	Abandoned	HIGH-VOLTAGE-RESISTANT MOS TRANSISTOR, AND CORRESPONDING MANUFACTURING PROCESS	3/29/1996	96830175.4	12/3/2003	0798785	GB
NMXS-0257.00/GB	Utility - EPPAT	Lapsed	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURINGPROCESS	10/31/1995	95830459.4	10/12/2005	0772246	GB
NMXS-0260.00/GB	Utility - EPPAT	Abandoned	FABRICATION OF NATURAL TRANSISTORS IN A NONVOLATILE MEMORY PROCESS	1/22/1996	96830021.0	12/4/2002	0785570	GB
NMXS-0262.00/GB	Utility - EPPAT	Abandoned	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	96937493.3	1/10/2001	0906622	GB
NMXS-0263.00/GB	Utility - EPPAT	Abandoned	CLOCK CIRCUIT FOR READING A MULTILEVEL NON VOLATILE MEMORY CELLS DEVICE	6/28/1996	96830371.9	3/19/2003	0817200	GB
NMXS-0264.00/GB	Utility - EPPAT	Abandoned	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	96937494.1	1/3/2001	0906623	GB
NMXS-0265.00/GB	Utility - EPPAT	Abandoned	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	3/22/1996	96830144.0	6/12/2002	0797145	GB
NMXS-0266.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	5/9/1996	96830267.9	3/19/2003	0806773	GB
NMXS-0268.00/GB	Utility - EPPAT	Abandoned	ERASING METHOD FOR A NON-VOLATILE MEMORY	12/29/1995	95830554.2	5/10/2000	0782145	GB
NMXS-0269.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR GENERATING A SYNCHRONIZING ATD SIGNAL	11/27/1996	96830598.7	4/9/2003	0845784	GB
NMXS-0270.00/GB	Utility - EPPAT	Abandoned	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	4/30/1996	96830245.5	2/26/2003	0782148	GB
NMXS-0271.00/GB	Utility - EPPAT	Abandoned	ERASE VOLTAGE CONTROL CIRCUIT FOR AN ELECTRICALLY ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830025.1	7/28/2004	0786779	GB
NMXS-0272.00/GB	Utility - EPPAT	Abandoned	METHOD FOR ERASING AN ELECTRICALLY PROGRAMMABLE AND ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830024.4	11/12/2003	0786778	GB
NMXS-0273.00/GB	Utility - EPPAT	Abandoned	PROGRAMMABLE DEVICE WITH BASIC MODULES ELECTRICALLY CONNECTED BY FLASH MEMORY CELLS	12/29/1995	95830552.6	5/23/2001	0782144	GB
NMXS-0274.00/GB	Utility - EPPAT	Abandoned	PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS	6/5/1996	96830318.0	3/12/2003	0811986	GB
NMXS-0275.00/GB	Utility - EPPAT	Abandoned	HIGH VOLTAGES DETECTOR CIRCUIT AND INTEGRATED CIRCUIT USING SAME	1/31/1996	96830043.4	3/31/2004	0788231	GB
NMXS-0276.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE	1/31/1997	97830029.1	6/25/2003	0856886	GB
NMXS-0277.00/GB	Utility - EPPAT	Abandoned	MEMORY ARCHITECTURE FOR FLEXIBLE READING MANAGEMENT, PARTICULARLY FOR NON-VOLATILE MEMORIES, HAVING NOISE-IMMUNITY FEATURES, MATCHING DEVICE PERFORMANCE, AND HAVING OPTIMIZED THROUGHOUT	4/29/1996	96830239.8	1/2/2004	0805453	GB
NMXS-0278.00/GB	Utility - EPPAT	Abandoned	CIRCUITS AND METHODS FOR READ-ENABLING MEMORY DEVICES SYNCHRONOUSLY WITH THE REACHING OF THE MINIMUM FUNCTIONALITY CONDITIONS OF THE MEMORY CELLS AND READING CIRCUITS, PARTICULARLY FOR NON-VOLATILE MEMORIES	4/29/1996	96830238.0	9/24/2003	0805452	GB
NMXS-0279.00/GB	Utility - EPPAT	Abandoned	COLUMN MULTIPLEXER	5/13/1996	96830275.2	11/12/2003	0810606	GB

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Mat-DktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0280.00/GB	Utility - EPPAT	Abandoned	DRIVER DEVICE FOR SELECTION LINES FOR A MULTIPLEXER, TO BE USED IN A WIDE RANGE OF SUPPLY VOLTAGES, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/29/1996	96830166.3	11/12/2003	0798742	GB
NMXS-0281.00/GB	Utility - EPPAT	Abandoned	PROGRAMMING AND READING MANAGEMENT ARCHITECTURE FOR MEMORY DEVICES, PARTICULARLY FOR TEST PURPOSES	3/29/1996	96830161.4	1/7/2004	0798726	GB
NMXS-0283.00/GB	Utility - EPPAT	Abandoned	DATA READING PATH MANAGEMENT ARCHITECTURE FOR A MEMORY DEVICE, PARTICULARLY FOR NON VOLATILE MEMORIES	3/29/1996	96830162.2	5/26/2004	0798727	GB
NMXS-0284.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE HAVING OPTIMIZED MANAGEMENT OF DATA TRANSMISSION LINES	3/20/1996	96830128.3	1/2/2003	0797208	GB
NMXS-0285.00/GB	Utility - EPPAT	Abandoned	PULSE GENERATION CIRCUIT AND METHOD FOR SYNCHRONIZED DATA LOADING IN AN OUTPUT PRE-BUFFER	3/29/1996	96830169.7	11/12/2003	0798730	GB
NMXS-0288.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS	5/8/1996	96830214.9	12/22/1999	0747800	GB
NMXS-0289.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE	12/20/1995	95309306.9	5/14/2003	0718741	GB
NMXS-0291.00/GB	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR BIASING BIT LINES	5/15/1996	96303448.3	2/5/2003	0747824	GB
NMXS-0314.00/GB	Utility - EPPAT	Lapsed	CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES	8/9/1996	96305856.5	11/28/2001	0760518	GB
NMXS-0316.00/GB	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/6/1996	96470004.1	6/23/1999	0735489	GB
NMXS-0317.00/GB	Utility - EPPAT	Abandoned	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OR NEGATIVE SUPPLY CIRCUIT	6/17/1996	96470011.6	5/20/1998	0757427	GB
NMXS-0318.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	9/2/1996	96460031.6	11/11/1998	0762428	GB
NMXS-0319.00/GB	Utility - EPPAT	Abandoned	HIGH VOLTAGE GENERATOR	12/24/1996	96402887.2	3/8/2000	0782243	GB
NMXS-0321.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/17/1997	97460009.0	6/9/1999	0791933	GB
NMXS-0322.00/GB	Utility - EPPAT	Abandoned	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1/24/1997	97460008.2	12/2/1998	0788233	GB
NMXS-0323.00/GB	Utility - EPPAT	Abandoned	FLASH-EPROM WITH EMBEDDED EEPROM	4/15/1996	96830212.5	9/24/2003	0802569	GB
NMXS-0324.00/GB	Utility - EPPAT	Abandoned	DATA SENSING TIMING MODULATING CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/29/1996	96830165.5	11/12/2003	0798741	GB
NMXS-0326.00/GB	Utility - EPPAT	Abandoned	POWER ON RESET CIRCUIT WITH AUTO TURN OFF	4/30/1996	96830247.1	3/23/2005	0805556	GB
NMXS-0327.00/GB	Utility - EPPAT	Abandoned	UPROM CELL FOR LOW VOLTAGE SUPPLY	4/30/1996	96830243.0	2/18/2004	0805771	GB
NMXS-0328.00/GB	Utility - EPPAT	Abandoned	BIASING CIRCUIT FOR UPROM CELLS WITH LOW VOLTAGE SUPPLY	4/30/1996	96830242.2	2/11/2004	0805456	GB
NMXS-0329.00/GB	Utility - EPPAT	Abandoned	ROW DECODER FOR LOW POWER SUPPLY	5/24/1996	96830299.2	10/15/2003	0809254	GB
NMXS-0330.00/GB	Utility - EPPAT	Abandoned	I/V CONVERTER FOR LOW SUPPLY NON VOLATILE MEMORY CELLS	6/18/1996	96830344.6	12/17/2003	0814480	GB
NMXS-0331.00/GB	Utility - EPPAT	Abandoned	LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY DEVICE WITH VOLTAGE BOOSTING	6/18/1996	96830345.3	3/20/2002	0814481	GB
NMXS-0332.00/GB	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS	6/18/1996	96830346.1	8/27/2003	0814482	GB
NMXS-0333.00/GB	Utility - EPPAT	Abandoned	MOS CAPACITOR WITH WIDE VOLTAGE AND FREQUENCY OPERATING RANGES	7/30/1996	96830420.4	5/24/2006	0822601	GB
NMXS-0334.00/GB	Utility - EPPAT	Abandoned	BIDIRECTIONAL CHARGE PUMP	8/2/1996	96830441.0	4/2/2003	0822556	GB
NMXS-0339.00/GB	Utility - EPPAT	Abandoned	HIGH VOLTAGE TOLERANCE OUTPUT STAGE	7/24/1996	96830413.9	10/9/2002	0821484	GB
NMXS-0340.00/GB	Utility - EPPAT	Abandoned	SINGLE-CELL REFERENCE SIGNAL GENERATING CIRCUIT FOR READING NONVOLATILE MEMORY	6/18/1996	96830348.7	9/17/2003	0814484	GB
NMXS-0342.00/GB	Utility - EPPAT	Abandoned	NMOS NEGATIVE CHARGE PUMP	1/23/1997	97830014.3	6/22/2005	0855788	GB
NMXS-0343.00/GB	Utility - EPPAT	Abandoned	ADDRESS TRANSITION DETECTION CIRCUIT	3/6/1996	96830096.2	9/12/2001	0794618	GB
NMXS-0344.00/GB	Utility - EPPAT	Abandoned	METHOD FOR RECOVERING FAILED MEMORY	3/21/1996	96830136.6	7/3/2002	0797147	GB

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MII-PckNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0345.00/GB	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR GENERATING A POWER-ON RESET SIGNAL	3/29/1996	96830177.0	6/18/2003	0798728	GB
NMXS-0346.00/GB	Utility - EPPAT	Abandoned	GAIN MODULATED SENSE AMPLIFIER, PARTICULARLY FOR MEMORY DEVICES	3/29/1996	96830164.8	2/5/2003	0798732	GB
NMXS-0347.00/GB	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD TO ADJUST MEMORY TIMING	3/29/1996	96830175.2	12/3/2003	0798744	GB
NMXS-0348.00/GB	Utility - EPPAT	Abandoned	STANDBY VOLTAGE BOOSTING STAGE AND METHOD FOR A MEMORY DEVICE	3/29/1996	96830178.8	10/17/2001	0800259	GB
NMXS-0349.00/GB	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER FOR MEMORY DEVICES	3/29/1996	96830179.6	10/17/2001	0800260	GB
NMXS-0350.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR THE SWITCHING OF SUPPLY VOLTAGES IN ELECTRICALLY PROGRAMMABLE AND CANCELABLE NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	4/5/1996	96830193.7	3/3/2004	0800177	GB
NMXS-0351.00/GB	Utility - EPPAT	Abandoned	AUTO-SAVING CIRCUIT FOR PROGRAMMING CONFIGURATION ELEMENTS IN NON-VOLATILE MEMORY DEVICES	4/5/1996	96830191.1	2/2/2005	0800178	GB
NMXS-0352.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE MEMORY CELLS	4/5/1996	96830192.9	7/2/2003	0800176	GB
NMXS-0353.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR DETECTING THE COINCIDENCE BETWEEN A BINARY INFORMATION UNIT STORED THEREIN AND AN EXTERNAL DATUM	3/22/1996	96830143.2	8/14/2002	0797144	GB
NMXS-0354.00/GB	Utility - EPPAT	Abandoned	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	4/18/1996	96830216.6	3/12/2003	0802541	GB
NMXS-0355.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH ROW REDUNDANCY	4/18/1996	96830217.4	1/30/2002	0802483	GB
NMXS-0356.00/GB	Utility - EPPAT	Abandoned	REDUNDANCY MEMORY REGISTER	4/18/1996	96830215.8	2/20/2002	0802482	GB
NMXS-0357.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR TRANSFERRING REDUNDANCY DATA OF A REDUNDANCY CIRCUIT INSIDE A MEMORY DEVICE BY MEANS OF A TIME-SHARED APPROACH	6/6/1996	96830323.0	1/2/2002	0811917	GB
NMXS-0358.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH ROW AND COLUMN REDUNDANCY CIRCUITS AND A TIME-SHARED REDUNDANCY CIRCUIT TEST ARCHITECTURE.	6/6/1996	96830326.3	10/1/2003	0811988	GB
NMXS-0359.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH	6/6/1996	96830324.8	1/30/2002	0811918	GB
NMXS-0362.00/GB	Utility - EPPAT	Abandoned	READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE	6/18/1996	96830347.9	8/27/2003	0814483	GB
NMXS-0363.00/GB	Utility - EPPAT	Abandoned	MULTILEVEL NON VOLATILE MEMORY DEVICE	8/22/1996	96830455.0	4/9/2003	0825611	GB
NMXS-0364.00/GB	Utility - EPPAT	Abandoned	CHARGE INJECTION CIRCUIT FOR AN INSULATED GATE MOS TRANSISTOR AND COMPUTING DEVICES USING THE SAME	9/30/1996	96830492.3	2/25/2004	0833267	GB
NMXS-0366.00/GB	Utility - EPPAT	Abandoned	CONTROL CIRCUIT OF AN OUTPUT BUFFER	9/19/1996	96830475.8	3/19/2003	0831492	GB
NMXS-0367.00/GB	Utility - EPPAT	Abandoned	PROTECTION CIRCUIT FOR REDUNDANCY REGISTER SET-UP CELLS OF ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICES	10/30/1996	96830553.2	3/19/2003	0840327	GB
NMXS-0372.00/GB	Utility - EPPAT	Abandoned	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	9/30/1996	96830494.9	4/2/2003	0833340	GB
NMXS-0383.00/GB	Utility - EPPAT	Abandoned	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	12/24/1996	96830649.8	5/23/2007	0851485	GB
NMXS-0385.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS	7/16/1997	97830398.2	3/23/2005	0892430	GB
NMXS-0386.00/GB	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH MULTIFUNCTIONAL TERMINALS	3/28/1997	97830151.3	7/28/2004	0867885	GB
NMXS-0387.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	12/5/1996	96830612.6	7/9/2003	0833348	GB
NMXS-0388.00/GB	Utility - EPPAT	Abandoned	METHOD OF PRODUCING MOSFET TRANSISTORS BY MEANS OF TILTED IMPLANTS	4/21/1997	97830182.8	8/1/2007	0874389	GB
NMXS-0389.00/GB	Utility - EPPAT	Abandoned	METHOD FOR DATA SAVING IN CASE OF UNWANTED PROGRAMMING CYCLE INTERRUPTIONS OF A NON VOLATILE MEMORY AND NON VOLATILE MEMORY	4/30/1998	98830265.9	7/2/2003	0953984	GB
NMXS-0391.00/GB	Utility - EPPAT	Abandoned	VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARY FOR A NONVOLATILE MEMORY	2/28/1997	97830085.3	5/7/2003	0862183	GB
NMXS-0392.00/GB	Utility - EPPAT	Abandoned	METHOD FOR MANUFACTURING A NATIVE MOS P-CHANNEL TRANSISTOR WITH A PROCESS FOR MANUFACTURING NON-VOLATILE MEMORIES	8/27/1997	97830428.5	1/19/2005	0902466	GB
NMXS-0407.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY WITH INTERNAL REFRESH MEANS	10/21/1997	97460043.9	8/4/1999	0838826	GB
NMXS-0410.00/GB	Utility - EPPAT	Abandoned	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	1/29/1997	97400209.9	10/7/1998	0788047	GB

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MII-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0412.00/GB	Utility - EPPAT	Abandoned	MEMORY WITH IMPROVED READING TIME	10/15/1997	97402429.1	12/11/2002	0838824	GB
NMXS-0416.00/GB	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	11/21/1997	97402807.8	10/20/1999	0849740	GB
NMXS-0417.00/GB	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY	11/21/1997	97402806.0	10/20/1999	0849739	GB
NMXS-0418.00/GB	Utility - EPPAT	Abandoned	MEMORY WITH READ PROTECTED ZONES	11/28/1997	97402868.8	6/9/1999	0851359	GB
NMXS-0427.00/GB	Utility - EPPAT	Abandoned	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	11/5/1997	97470027.0	8/4/1999	0845787	GB
NMXS-0429.00/GB	Utility - EPPAT	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	3/20/1998	98400661.9	6/18/2003	0875899	GB
NMXS-0430.00/GB	Utility - EPPAT	Lapsed	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1998	98903102.6	5/16/2001	0954865	GB
NMXS-0433.00/GB	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH REDUCED POWER DISSIPATION	4/3/1997	97830100.4	7/2/2003	0869506	GB
NMXS-0436.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLAITLE MEMORY DEVICES	8/29/1997	97830435.0	11/12/2003	0899742	GB
NMXS-0439.00/GB	Utility - EPPAT	Abandoned	PARALLEL ANALOG PROGRAMMING OF FLASH DEVICES	5/9/1997	97830216.4	7/30/2003	0877386	GB
NMXS-0440.00/GB	Utility - EPPAT	Abandoned	MEMORY DEVICE GENERATOR FOR GENERATING MEMORY DEVICES WITH REDUNDANCY	10/20/1997	97830525.8	1/2/2004	0911747	GB
NMXS-0442.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR READING A NON-VOLATILE MEMORY	7/20/1998	98830438.2	12/3/2003	0974976	GB
NMXS-0443.00/GB	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR ANALOG PROGRAMMING OF FLASH EEPROM WITH AUTOVERIFY	9/29/1997	97830477.2	4/23/2003	0905712	GB
NMXS-0446.00/GB	Utility - EPPAT	Issued	DECODER FOR ERASING A SINGLE ROW IN A FLASH MEMORY	11/26/1997	97830625.6	6/30/2010	0920023	GB
NMXS-0456.00/GB	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	5/29/1998	98830332.7	5/19/2004	0961288	GB
NMXS-0460.00/GB	Utility - EPPAT	Lapsed	METHOD OF MULTI-LEVEL PROGRAMMING A NON VOLATILE MEMORY AND MULTI-LEVEL NONVOLATILE MEMORY	11/3/1997	97830566.2	7/23/2003	0913832	GB
NMXS-0461.00/GB	Utility - EPPAT	Lapsed	METHOD AND CIRCUIT FOR GENERATING AN ATD SIGNAL TO REGULATE THE ACCESS TO A NON-VOLATILE MEMORY	11/5/1997	97830576.1	3/17/2004	0915477	GB
NMXS-0462.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR REGULATING THE LENGTH OF AN ATD PULSE SIGNAL	11/5/1997	97830573.8	3/3/2004	0915476	GB
NMXS-0464.00/GB	Utility - EPPAT	Abandoned	IMPROVED OUTUPUT CIRCUIT FOR INTEGRATED CIRCUITS	10/24/1997	97830542.3	4/9/2003	0911974	GB
NMXS-0466.00/GB	Utility - EPPAT	Abandoned	HIGH VOLTAGE REGULATOR AND CORRESPONDING VOLTAGE REGULATION METHOD	11/5/1997	97830575.3	2/19/2003	0915408	GB
NMXS-0476.00/GB	Utility - EPPAT	Abandoned	MEMORY CELL INTEGRATED STRUCTURE AND CORRESPONDING BIASING DEVICE	4/22/1998	98830238.6	9/28/2005	0957515	GB
NMXS-0481.00/GB	Utility - EPPAT	Lapsed	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	99926682.8	4/10/2002	1097454	GB
NMXS-0484.00/GB	Utility - EPPAT	Abandoned	CONTROLLED ERASING FOR ANALOG & MULTILEVEL STORAGE IN FLASH EEPROM DEVICE	1/22/1998	98830024.0	6/9/2004	0932161	GB
NMXS-0487.00/GB	Utility - EPPAT	Abandoned	HIGH STORAGE CAPACITY NON-VOLATILE MEMORY	5/27/1998	98830324.4	11/26/2003	0961287	GB
NMXS-0488.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR THE FABRICATION OF A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	6/30/1998	98830388.9	11/14/2001	0971415	GB
NMXS-0500.00/GB	Utility - EPPAT	Abandoned	LOW VOLTAGE NON VOLATILE MEMORY SENSE AMPLIFIER	2/13/1998	98830064.6	10/20/2004	0936627	GB
NMXS-0504.00/GB	Utility - EPPAT	Lapsed	PIPELINED NON-BLOCKING LEVEL TWO CACHE SYSTEM WITH INHERENT TRANSACTION COLLISION-AVOIDANCE	12/1/1999	99309041.1	3/14/2007	1006448	GB
NMXS-0505.00/GB	Utility - EPPAT	Abandoned	NON VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING A READ AND/OR WRITE PROTECTABLE AREA AND ELECTRONIC SYSTEM INCLUDINT IT	10/21/1998	98402620.9	6/4/2003	0918336	GB
NMXS-0507.00/GB	Utility - EPPAT	Lapsed	METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY	9/10/1998	98460036.1	11/15/2000	0903750	GB
NMXS-0510.00/GB	Utility - EPPAT	Abandoned	RADIO FREQUENCE SIGNAL DETECTOR FOR CONTACT-LESS SMARTCARD	9/17/1998	98402303.6	5/24/2006	0903688	GB
NMXS-0511.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR THE GENERATION OF VOLTAGE FOR THE PROGRAMMING OR ERASURE OF A MEMORY THAT USES FLOATING-GATE TRANSISTORS	10/12/1998	98470024.5	7/18/2001	0913836	GB

PATENT
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MTI Docket No	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0516.00/GB	Utility - EPPAT	Abandoned	DIFFERENCIAL READING OF NONVOLATILE MEMORY CELLS WITHOUT USING A REFERENCE	5/29/1998	98830333.5	12/17/2003	0961285	GB
NMXS-0522.00/GB	Utility - EPPAT	Abandoned	METHOD FOR READING A MULTI-LEVEL MEMORY CELL	3/27/1998	98830188.3	11/17/2004	0945869	GB
NMXS-0523.00/GB	Utility - EPPAT	Abandoned	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	9/30/1998	98830570.2	5/6/2004	0991075	GB
NMXS-0525.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING MOS TRANSISTORS WITH SALICIZED JUNCTIONS AND NON-SALICIZED RESISTORS	7/22/1998	98830444.0	11/2/2005	0975021	GB
NMXS-0532.00/GB	Utility - EPPAT	Lapsed	A SIMPLIFIED PROCESS FOR DEFINING THE TUNNEL AREA IN SEMICONDUCTOR NON-VOLATILE NON-ALIGNED MEMORY CELLS	10/15/1998	98830614.8	2/25/2004	0994513	GB
NMXS-0533.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE WITH ROW REDUNDANCY	5/12/1999	99830286.3	7/30/2003	1052572	GB
NMXS-0536.00/GB	Utility - EPPAT	Issued	METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS	10/23/1998	98830645.2	5/19/2010	0986100	GB
NMXS-0537.00/GB	Utility - EPPAT	Abandoned	IMPROVED SELECTIVE SALICIZATION PROCESS FOR SEMICONDUCTOR SUBSTRATE INTEGRATED ELECTRONIC DEVICES	12/29/1998	98830793.0	10/26/2005	1017088	GB
NMXS-0538.00/GB	Utility - EPPAT	Abandoned	METHOD FOR CORRECTING ERRORS IN A MULTILEVEL MEMORY WITHOUT ADDITIONAL CELLS	2/25/1999	99830099.0	2/5/2003	1035473	GB
NMXS-0539.00/GB	Utility - EPPAT	Abandoned	MULTILEVEL NON VOLATILE MEMORY AND READING METHOD THEREFOR	2/10/1999	99830071.9	4/28/2004	1028433	GB
NMXS-0540.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT TO TEST THE VIRGIN CELLS IN A MULTILEVEL MEMORY	10/29/1998	98830654.4	8/10/2005	0997913	GB
NMXS-0541.00/GB	Utility - EPPAT	Lapsed	N-STAGE CONVERTER FOR READING/WRITING ANALOG FLASH CELLS	10/20/1998	98830625.2	1/11/2006	0997912	GB
NMXS-0557.00/GB	Utility - EPPAT	Abandoned	FLASH COMPATIBLE EEPROM	6/22/1999	99830390.3	2/2/2005	1067557	GB
NMXS-0558.00/GB	Utility - EPPAT	Abandoned	METHOD FOR READING A MEMORY, PARTICULARLY A NON-VOLATILE MEMORY	12/30/1998	98830801.1	7/18/2007	1017059	GB
NMXS-0561.00/GB	Utility - EPPAT	Abandoned	IMPROVED PROCESS FOR MANUFACTURING ELECTRONIC MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	2/26/1999	99830100.6	10/13/2004	1032035	GB
NMXS-0565.00/GB	Utility - EPPAT	Abandoned	METHOD FOR AUTOALIGNING OVERLAPPED LINES OF CONDUCTOR MATERIAL PROVIDED IN INTEGRATED ELECTRONIC CIRCUITS	5/31/1999	99830336.6	8/17/2005	1058304	GB
NMXS-0566.00/GB	Utility - EPPAT	Abandoned	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/21/1999	99830235.0	8/9/2006	1047078	GB
NMXS-0568.00/GB	Utility - EPPAT	Abandoned	ESD PROTECTION DEVICE FOR SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURE	7/30/1999	99830491.9	5/26/2004	1073119	GB
NMXS-0569.00/GB	Utility - EPPAT	Abandoned	A SEMICONDUCTOR DEVICE WITH IMPROVED CHIP-LEADS INTERCONNECTIONS AND A PROCESS FOR MANUFACTURING THEREOF	2/11/1999	99830072.7	7/26/2006	1028464	GB
NMXS-0570.00/GB	Utility - EPPAT	Abandoned	READING METHOD FOR MULTILEVEL MEMORIES WITH SELECTIVE AMPLIFICATION OF CURRENT	2/26/1999	99830108.9	4/28/2004	1031991	GB
NMXS-0571.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATING FOR A CAPACITIVE LOAD	5/30/1999	99830418.2	11/12/2003	1065580	GB
NMXS-0584.00/GB	Utility - EPPAT	Lapsed	COMMUNICATIONS SYSTEM AND METHOD FOR REDUCING THE EFFECTS OF TRANSMITTER NON-LINEAR DISTORTION ON A RECEIVED SIGNAL	6/14/2000	00305020.0	1/31/2007	1061689	GB
NMXS-0585.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES	5/26/1999	99470014.4	11/22/2000	0962938	GB
NMXS-0589.00/GB	Utility - EPPAT	Abandoned	SECURED EEPROM WITH UV ERASING DETECTION MEANS	11/26/1999	99460065.8	1/21/2004	1006532	GB
NMXS-0592.00/GB	Utility - EPPAT	Abandoned	READING METHOD FOR NON VOLATILE MEMORIES WITH SENSING RATION VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	6/21/1999	99830382.0	3/5/2003	1063654	GB
NMXS-0593.00/GB	Utility - EPPAT	Abandoned	ERASING AND PARALLEL REWRITING CIRCUIT FOR MEMORY CELL BLOCKS, PARTICULARLY FOR ANALOG FLASH CELLS, AND RELATED OPERATING METHOD	6/21/1999	99830381.2	8/9/2006	1065668	GB
NMXS-0596.00/GB	Utility - EPPAT	Abandoned	GERARCHIC SECTOR BIASING FOR FLASH MEMORIES	6/24/1999	99830396.0	11/17/2004	1063653	GB
NMXS-0597.00/GB	Utility - EPPAT	Abandoned	SYNCHRONOUS MULTILEVEL NON VOLATILE MEMORY AND RELATED READING METHOD	5/31/1999	99830331.7	3/29/2006	1058269	GB
NMXS-0598.00/GB	Utility - EPPAT	Abandoned	A READING CIRCUIT FOR A SEMICONDUCTOR MEMORY	6/25/1999	99830408.4	11/23/2005	1071094	GB
NMXS-0599.00/GB	Utility - EPPAT	Abandoned	BIASING THE DRAIN OF A MEMORY CELL DURING READING	6/4/1999	99830348.1	3/21/2007	1058270	GB

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MLD Ref No	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0603.00/GB	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING MULTILEVEL NON-VOLATILE MEMORIES BY APPLYING SEQUENCES OF PULSES WITHOUT VERIFY	8/3/1999	99830501.5	10/26/2005	1074995	GB
NMXS-0604.00/GB	Utility - EPPAT	Abandoned	ROW DECODER WITH REDUCED POWER CONSUMPTION DURING SWITCHING	6/4/1999	99830345.7	12/15/2004	1058271	GB
NMXS-0605.00/GB	Utility - EPPAT	Abandoned	ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE	6/17/1999	99830378.8	3/8/2006	1061525	GB
NMXS-0614.00/GB	Utility - EPPAT	Issued	MANUFACTURE OF AN HV-MOS TRANSISTOR WITH LOW MULTIPLICATION FACTOR IN A DUAL-GATE CMOS PROCESS	11/10/1999	99830717.7	5/26/2010	1102319	GB
NMXS-0615.00/GB	Utility - EPPAT	Abandoned	I/V CONVERTER WITH DECOUPLING MEANS FOR THE ARRAY INPUT/OUTPUT NODES	7/22/1999	99830469.5	9/24/2003	1071096	GB
NMXS-0619.00/GB	Utility - EPPAT	Lapsed	EMBEDDED STAGE FOR DETECTING SHORTCIRCUITS BETWEEN WORDLINES OF NON VOLATILE MEMORIES	9/10/1999	99830567.6	11/14/2007	1083575	GB
NMXS-0626.00/GB	Utility - EPPAT	Abandoned	COLUMN DECODER CIRCUIT FOR PAGE READING OF A SEMICONDUCTOR MEMORY	2/29/2000	00830149.1	1/26/2005	1130501	GB
NMXS-0632.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY WITH SINGLE SUPPLY AND HIERARCHICAL ROW DECODING	7/28/1999	99830483.6	9/21/2005	1073060	GB
NMXS-0635.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY	9/18/2000	00830620.1	3/7/2007	1179988	GB
NMXS-0638.00/GB	Utility - EPPAT	Abandoned	LOW CONSUMPTION VOLTAGE BOOST DEVICE	12/30/1999	99830825.8	4/25/2007	1113450	GB
NMXS-0639.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE WITH CONFIGURABLE ROW REDUNDANCY	2/14/2000	00830108.8	5/18/2005	1126372	GB
NMXS-0641.00/GB	Utility - EPPAT	Abandoned	VOLTAGE BOOSTING DEVICE, IN PARTICULAR FOR SPEEDING POWER-UP OF MULTILEVEL NONVOLATILE MEMORIES	2/8/2000	00830088.1	1/25/2006	1124313	GB
NMXS-0648.00/GB	Utility - EPPAT	Abandoned	LOGIC PARTITIONING OF A NONVOLATILE MEMORY ARRAY	3/28/2000	00830228.3	3/17/2004	1139210	GB
NMXS-0649.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY MATRIX ARCHITECTURE	12/14/2000	00204838.7	9/6/2006	1170798	GB
NMXS-0653.00/GB	Utility - EPPAT	Abandoned	CIRCUITAL STRUCTURE FOR PROGRAMMING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830391.7	7/23/2008	1160794	GB
NMXS-0654.00/GB	Utility - EPPAT	Abandoned	CIRCUITAL STRUCTURE FOR READING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830393.5	12/19/2007	1160795	GB
NMXS-0655.00/GB	Utility - EPPAT	Abandoned	INTEGRATED DEVICE WITH VOLTAGE SELECTOR	3/29/2000	00830239.0			GB
NMXS-0665.00/GB	Utility - EPPAT	Issued	INTERLEAVED DATA PATH AND OUTPUT MANAGEMENT ARCHITECTURE FOR AN INTERLEAVED MEMORY AND LOAD PULSER CIRCUIT FOR OUTPUTTING THE READ DATA	4/17/2000	008302911	9/1/2010	1122735	GB
NMXS-0667.00/GB	Utility - EPPAT	Abandoned	REDUNDANCY ARCHITECTURE FOR AN INTERLEAVED MEMORY	3/2/2000	00830158.2	5/26/2004	1130517	GB
NMXS-0670.00/GB	Utility - EPPAT	Abandoned	INTERLEAVED MEMORY DEVICE FOR BURST TYPE ACCESS IN SYNCHRONOUS READ MODE WITH THE TWO SEMI-ARRAYS INDEPENDENTLY READABLE IN RANDOM ACCESS ASYNCHRONOUS MODE	1/31/2000	00830068.3	3/30/2005	1122734	GB
NMXS-0671.00/GB	Utility - ORG	Abandoned	COLOR IMAGE RESTORATION WITH ANTI-ALIAS	11/3/1999	9925902.0			GB
NMXS-0672.00/GB	Utility - NSPCT	Abandoned	CIRCUIT FOR THE PRODUCTION OF HIGHT VOLTAGE FOR THE PROGRAMMING OF A MEMORY	6/26/2000	00946012.2	3/16/2005	1196926	GB
NMXS-0673.00/GB	Utility - EPPAT	Abandoned	NEW ARCHITECTURE FOR PAGE MODE IN A NON VOLATILE MEMORY	9/15/2000	00402549.0	7/23/2008	1085520	GB
NMXS-0675.00/GB	Utility - EPPAT	Lapsed	NEW ARCHITECTURE OF A NON VOLATILE MEMORY, WITH A COMMON DIFFUSED SOURCE FOR EACH WORD	9/15/2000	00402548.2	4/10/2002	1085518	GB
NMXS-0680.00/GB	Utility - EPPAT	Abandoned	CHARGE PUMP BOOSTER DEVICE WITH TRANSFER AND RECOVERY OF THE CHARGE	2/15/2000	00830105.3	5/3/2006	1158654	GB
NMXS-0699.00/GB	Utility - EPPAT	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY	10/13/2000	00830671.4	10/6/2010	1199725	GB
NMXS-0704.00/GB	Utility - EPPAT	Abandoned	ANALOG-TO-DIGITAL CONVERSION METHOD AND DEVICE, IN HIGH-DENSITY MULTILEVEL NON-VOLATILE MEMORY DEVICES	11/23/2000	00127649.2	11/15/2006	1211812	GB
NMXS-0716.00/GB	Utility - EPPAT	Abandoned	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/13/2001	01129768.6	3/3/2004	1215679	GB
NMXS-0717.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL NONVOLATILE MEMORY CELL	1/15/2001	01830017.8	8/8/2007	1225595	GB

PATENT
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MTI-DocketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0724.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE ELECTRICALLY ALTERABLE SEMICONDUCTOR MEMORY	1/24/2001	01830039.2	5/10/2006	1227499	GB
NMXS-0726.00/GB	Utility - EPPAT	Abandoned	METHOD FOR REFRESHING STORED DATA IN AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	2/19/2001	01830110.1	7/11/2007	1233421	GB
NMXS-0729.00/GB	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL AT LOW SUPPLY VOLTAGE AND WITH LOW OUTPUT DYNAMICS	2/14/2001	01830097.0	8/8/2007	1233420	GB
NMXS-0740.00/GB	Utility - EPPAT	Abandoned	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/27/2001	01130836.8	3/3/2004	1220448	GB
NMXS-0742.00/GB	Utility - EPPAT	Abandoned	CHARGE PUMP FOR A NONVOLATILE MEMORY WITH READ VOLTAGE REGULATION IN THE PRESENCE OF ADDRESS SKEW, AND NONVOLATILE MEMORY COMPRISING SUCH A CHARGE PUMP	2/6/2001	01830070.7			GB
NMXS-0749.00/GB	Utility - EPPAT	Abandoned	PAGE-ERASABLE FLASH MEMORY	11/14/2001	01956861.9	4/6/2005	1342244	GB
NMXS-0750.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR THE DETECTION OF A DEFECTIVE POWER SUPPLY CONNECTION	1/23/2002	02290165.6	4/14/2004	1227329	GB
NMXS-0753.00/GB	Utility - EPPAT	Abandoned	CONTROL SIGNAL-ADAPTIVE CONTACTLESS CHIP CARD	2/14/2002	02708857.6	5/11/2005	1368784	GB
NMXS-0754.00/GB	Utility - EPPAT	Abandoned	FLASH EEPROM AND EPROM ARRAYS WITH SELECT TRANSISTORS WITHIN THE BIT LINE PITCH	3/10/1995	95301607.8	8/14/2002	0673071	GB
NMXS-0756.00/GB	Utility - EPPAT	Abandoned	A MEMORY DEVICE	9/27/2002	02078984.8	9/6/2006	1306852	GB
NMXS-0757.00/GB	Utility - EPPAT	Abandoned	WORD LINE SELECTOR FOR A SEMICONDUCTOR MEMORY	2/20/2002	02425084.7	7/7/2004	1339069	GB
NMXS-0762.00/GB	Utility - EPPAT	Abandoned	MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS	9/28/2001	01830614.2	3/7/2007	1298670	GB
NMXS-0763.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY-PROGRAMMABLE NON-VOLATILE MEMORY CELL	2/20/2002	02425085.4	5/14/2008	1339068	GB
NMXS-0765.00/GB	Utility - EPPAT	Abandoned	SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD	8/5/2002	02019284.5	4/4/2007	1324344	GB
NMXS-0767.00/GB	Utility - EPPAT	Abandoned	FINITE STATE MACHINE INTERFACE HAS ARBITRATION STRUCTURE TO STORE COMMAND GENERATED BY INTERNAL CIRCUITS DURING EVALUATION PHASE OF STATE MACHINE FOR FLASH EEPROM DEVICE	12/4/2001	01830744.7	8/17/2005	1318440	GB
NMXS-0770.00/GB	Utility - EPPAT	Abandoned	ARCHITECTURE FOR A FLASH-EEPROM SIMULTANEOUSLY READABLE IN OTHER SECTORS WHILE ERASING AND/OR PROGRAMMING ONE OR MORE SECTORS	1/11/2002	02425009.4	3/30/2005	1327992	GB
NMXS-0771.00/GB	Utility - EPPAT	Lapsed	FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE	10/25/2001	01830571.2	10/3/2007	1308964	GB
NMXS-0775.00/GB	Utility - EPPAT	Abandoned	INTEGRATED RESISTIVE ELEMENT, PHASE-CHANGE MEMORY ELEMENT INCLUDING SAID RESISTIVE ELEMENT, AND METHOD OF MANUFACTURE THEREOF	1/17/2002	02425013.6	5/23/2007	1331675	GB
NMXS-0782.00/GB	Utility - EPPAT	Abandoned	SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	2/20/2002	02425088.8	9/12/2007	1339103	GB
NMXS-0783.00/GB	Utility - EPPAT	Abandoned	CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS	2/20/2002	02425089.6	5/9/2007	1339111	GB
NMXS-0784.00/GB	Utility - EPPAT	Abandoned	BASIC STAGE FOR A CHARGE PUMP CIRCUIT	3/29/2002	02425199.3	11/9/2005	1349264	GB
NMXS-0788.00/GB	Utility - EPPAT	Abandoned	TEST STRUCTURE FOR THE MEASUREMENT OF CONTACT TO GATE DISTANCE IN NON-VOLATILE MEMORY DEVICES AND CORRESPONDING TEST METHOD	5/31/2002	02425360.1	8/3/2005	1367597	GB
NMXS-0792.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR CONTROLLING A REFERENCE NODE IN A SENSE AMPLIFIER	12/28/2001	01830817.1	10/27/2004	1324347	GB
NMXS-0796.00/GB	Utility - EPPAT	Abandoned	MEMORY DEVICE OUTPUTTING READ DATA IN A TIME STARTING FROM A RISING EDGE OF AN EXTERNAL CLOCK THAT IS SHORTER THAN THAT OF KNOWN DEVICES	12/20/2001	01830782.7	2/27/2008	1324346	GB
NMXS-0799.00/GB	Utility - EPPAT	Lapsed	NONVOLATILE STORAGE DEVICE AND SELF-REDUNDANCY METHOD FOR THE SAME	8/13/2002	02425529.1	10/10/2007	1394810	GB
NMXS-0800.00/GB	Utility - EPPAT	Abandoned	BUILT-IN TESTING METHODOLOGY IN FLASH MEMORY	2/27/2003	03425126.4	6/28/2006	1453062	GB
NMXS-0801.00/GB	Utility - EPPAT	Abandoned	SECTOR PROTECTION CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	7/31/2002	02255360.6	12/6/2006	1282135	GB
NMXS-0811.00/GB	Utility - EPPAT	Abandoned	METHOD FOR REDUCING SPURIOUS ERASING DURING PROGRAMMING OF A NONVOLATILE NROM	4/30/2002	02425273.6	7/5/2006	1359591	GB

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MII Docno	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0813.00/GB	Utility - EPPAT	Abandoned	REGULATION METHOD FOR THE SOURCE TERMINAL VOLTAGE IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	8/30/2002	02019433.8	3/14/2007	1331644	GB
NMXS-0814.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR FORMING TRENCHES WITH OBLIQUE PROFILE AND ROUNDED TOP CORNERS	6/28/2002	02425428.6	3/7/2007	1376683	GB
NMXS-0817.00/GB	Utility - EPPAT	Abandoned	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	10/8/2002	02425605.9	12/27/2006	1408550	GB
NMXS-0818.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	10/8/2002	02425604.2	3/7/2007	1408549	GB
NMXS-0820.00/GB	Utility - EPPAT	Abandoned	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE, AND NONVOLATILE MEMORY DEVICE	4/26/2002	02425265.2	6/14/2006	1357559	GB
NMXS-0828.00/GB	Utility - EPPAT	Abandoned	SINGLE CELL ERASING METHOD FOR RECOVERING MEMORY CELLS UNDER PROGRAMMING DISTURBS IN NON VOLATILE SEMICONDUCTOR MEMORY DEVICES	11/26/2002	02425727.1	8/3/2005	1424700	GB
NMXS-0832.00/GB	Utility - EPPAT	Abandoned	VOLTAGE BOOST DEVICE AND MEMORY SYSTEM	7/4/2003	03425442.5	5/10/2006	1378913	GB
NMXS-0834.00/GB	Utility - EPPAT	Abandoned	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	12/16/2003	03104709.5	2/28/2007	1435574	GB
NMXS-0844.00/GB	Utility - EPPAT	Abandoned	STABILIZATION METHOD FOR DRAIN VOLTAGE IN NON-VOLATILE MULTI-LEVEL MEMORY CELLS AND RELATED MEMORY DEVICE					GB
NMXS-0846.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING A MEMORY DEVICE HAVING SELECTOR TRANSISTORS FOR STORAGE ELEMENTS AND MEMORY DEVICE FABRICATED THEREBY	5/7/2003	03425292.4	7/19/2006	1475840	GB
NMXS-0853.00/GB	Utility - EPPAT	Abandoned	METHOD FOR DETECTING A RESISTIVE PATH OR A PREDETERMINED POTENTIAL IN NON-VOLATILE MEMORY ELECTRONIC DEVICES	9/30/2002	02425598.7	5/23/2007	1408880	GB
NMXS-0859.00/GB	Utility - EPPAT	Abandoned	METHOD FOR GENERATING A REFERENCE CURRENT FOR SENSE AMPLIFIERS AND CORRESPONDING GENERATOR	6/4/2003	03425353.4	8/16/2006	1484764	GB
NMXS-0869.00/GB	Utility - EPPAT	Issued	MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL-POLYSILICON LAYER TECHNOLOGY	12/23/2003	03104939.8	9/15/2010	1434257	GB
NMXS-0872.00/GB	Utility - EPPAT	Abandoned	METHOD FOR READING A NONVOLATILE MEMORY DEVICE AND NONVOLATILE MEMORY DEVICE IMPLEMENTING THE READING METHOD	4/10/2003	03425224.7	11/28/2007	1467377	GB
NMXS-0877.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATION SYSTEM FOR A MULTIWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY	2/28/2003	3425133			GB
NMXS-0878.00/GB	Utility - EPPAT	Abandoned	GATE VOLTAGE REGULATION SYSTEM FOR A NON-VOLATILE MEMORY CELLS PROGRAMMING AND/OR SOFT PROGRAMMING PHASE	2/28/2003	03425134.8	10/12/2005	1453059	GB
NMXS-0882.00/GB	Utility - EPPAT	Abandoned	FAST PAGE PROGRAMMING ARCHITECTURE AND METHOD IN A NON-VOLATILE MEMORY DEVICE WITH AN SPI INTERFACE	12/30/2002	02425802.2	9/20/2006	1435624	GB
NMXS-0883.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING AN INTERNAL SUPPLY VOLTAGE MANAGEMENT DEVICE	4/17/2003	03358005.1	1/31/2007	1365418	GB
NMXS-0892.00/GB	Utility - EPPAT	Abandoned	WORD-PROGRAMMABLE FLASH MEMORY	5/26/2004	04012393.7	4/9/2008	1486986	GB
NMXS-0912.00/GB	Utility - EPPAT	Abandoned	AN IMPROVED PAGE BUFFER FOR A PROGRAMMABLE MEMORY DEVICE	6/24/2004	04102942.2	12/19/2007	1610343	GB
NMXS-0920.00/GB	Utility - EPPAT	Abandoned	REDUNDANCY BASED NAND FLASH MEMORY	7/14/2004	04103354.9	10/25/2006	1617438	GB
NMXS-0943.00/GB	Utility - EPPAT	Lapsed	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	6/14/2004	04425435.7	8/15/2007	1607964	GB
NMXS-0944.00/GB	Utility - EPPAT	Abandoned	ROW DECODER FOR NAND MEMORIES	8/11/2004	04425625.1	2/21/2007	1626413	GB
NMXS-0949.00/GB	Utility - EPPAT	Abandoned	MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD	6/30/2004	04291653.6	8/15/2007	1508901	GB
NMXS-0950.00/GB	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	12/8/2004	04029018.1	4/11/2007	1542130	GB

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NMXS-0952.00/GB	Utility - EPPAT	Abandoned	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION	12/8/2004	04029016.5	5/30/2007	1542233	GB
NMXS-0957.00/GB	Utility - EPPAT	Lapsed	MEMORY DEVICE	10/15/2004	04105094.9	9/19/2007	1647991	GB
NMXS-0961.00/GB	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2005	05425209.3	12/12/2007	1713084	GB
NMXS-0965.00/GB	Utility - EPPAT	Abandoned	MEMORY DEVICE AND METHOD OF OPERATING THE SAME WITH HIGH REJECTION OF THE NOISE ON THE HIGH-VOLTAGE SUPPLY LINE	10/8/2004	04425754.1	3/5/2008	1646051	GB
NMXS-0974.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	11/18/2005	05025286.5	10/3/2007	1670002	GB
NMXS-0983.00/GB	Utility - EPPAT	Abandoned	HIGH-VOLTAGE SWITCH WITH LOW OUTPUT RIPPLE FOR NON VOLATILE FLOATING-GATE MEMORIES	5/20/2005	05425347.1	7/8/2008	1724784	GB
NMXS-0991.00/GB	Utility - EPPAT	Abandoned	DEVICE FOR AUTOMATICALLY OPENING AND CLOSING CASH CONTAINER	1/28/2005	05100551.0	1/9/2008	1686591	GB
NMXS-0999.00/GB	Utility - EPPAT	Abandoned	NAND FLASH MEMORY WITH ERASE VERIFY BASED ON SHORTER DELAY BEFORE SENSING	7/28/2005	05106976.3	4/23/2008	1752989	GB
NMXS-1016.00/GB	Utility - EPPAT	Abandoned	SEQUENTIAL PROGRAM-VERIFY METHOD WITH RESULT BUFFERING	3/30/2004	04101301.2	8/1/2007	1583102	GB
NMXS-1037.00/GB	Utility - EPPAT	Lapsed	A COLUMN DECODING SYSTEM FOR SEMICONDUCTOR MEMORY DEVICES IMPLEMENTED WITH LOW VOLTAGE TRANSISTORS	4/12/2006	061125266	4/1/2009	1845532	GB
NMXS-1046.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH A PAGE BUFFER HAVING AN IMPROVED LAYOUT ARRANGEMENT	7/28/2005	05106973.0	5/14/2008	1748443	GB
NMXS-1104.00/GB	Utility - ORG	Abandoned	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	9/30/1985	8524041	11/9/1988	2165992	GB
NMXS-1105.00/GB	Utility - EPPAT	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	10/9/1986	86830293.6	8/29/1990	0226549	GB
NMXS-1106.00/GB	Utility - EPPAT	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/29/1987	87830204.1	2/27/1991	0256993	GB
NMXS-1107.00/GB	Utility - EPPAT	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/22/1987	87830234.8	4/21/1993	0255489	GB
NMXS-1108.00/GB	Utility - EPPAT	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	8/4/1988	88107152.6	9/9/1992	0298215	GB
NMXS-1109.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/15/1988	88120977.9	5/12/1993	0322665	GB
NMXS-1110.00/GB	Utility - EPPAT	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	89100780.9	10/20/1993	0326004	GB
NMXS-1111.00/GB	Utility - EPPAT	Abandoned	CMOS VOLTAGE MULTIPLIER	6/16/1989	89830269.0	2/9/1994	0349495	GB
NMXS-1116.00/GB	Utility - EPPAT	Abandoned	PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	12/22/1989	89830569.3	7/19/1995	0376905	GB
NMXS-1117.00/GB	Utility - EPPAT	Abandoned	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/14/1990	90313667.9	11/8/1995	0435534	GB
NMXS-1118.00/GB	Utility - EPPAT	Abandoned	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	2/7/1991	91830037.7	5/10/1995	0445083	GB
NMXS-1119.00/GB	Utility - EPPAT	Abandoned	READING CIRCUIT FOR NONVOLATILEMEMORY CELL.	2/7/1991	91830036.9	1/3/1996	0443989	GB
NMXS-1120.00/GB	Utility - EPPAT	Abandoned	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	3/19/1991	91104217.4	9/13/1995	0450389	GB
NMXS-1121.00/GB	Utility - EPPAT	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	4/24/1991	91830167.2	11/25/1998	0454636	GB
NMXS-1122.00/GB	Utility - EPPAT	Abandoned	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	4/4/1991	91105323.9	12/29/1997	0455002	GB
NMXS-1123.00/GB	Utility - EPPAT	Abandoned	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	5/27/1991	91201641.7	5/28/1997	0464928	GB
NMXS-1124.00/GB	Utility - EPPAT	Expired	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	10/1/1990	90830428.0	4/28/2004	0478871	GB

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MII-DocketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1125.00/GB	Utility - EPPAT	Abandoned	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	9/30/1991	91116659.3	8/13/1997	0479191	GB
NMXS-1126.00/GB	Utility - EPPAT	Abandoned	TWO PHASES SCAN PATH WITH SINGLECLOCK.	10/15/1991	91202668.9	7/8/1998	0482697	GB
NMXS-1127.00/GB	Utility - EPPAT	Abandoned	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	11/19/1990	90830529.5	2/19/1997	0487808	GB
NMXS-1128.00/GB	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/19/1990	90830530.3	5/8/1996	0486743	GB
NMXS-1129.00/GB	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/13/1990	90830583.2	5/1/1996	0491105	GB
NMXS-1130.00/GB	Utility - EPPAT	Abandoned	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/20/1991	91121052.5	4/2/1997	0492506	GB
NMXS-1131.00/GB	Utility - EPPAT	Abandoned	MEMORY CELL READING CIRCUIT	12/18/1991	91121675.2	3/12/1997	0492382	GB
NMXS-1132.00/GB	Utility - EPPAT	Abandoned	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	5/5/1992	92830205.8	7/29/1998	0514850	GB
NMXS-1133.00/GB	Utility - EPPAT	Abandoned	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	7/21/1992	92830400.5	10/15/1997	0526427	GB
NMXS-1134.00/GB	Utility - EPPAT	Abandoned	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	8/27/1992	92830458.3	7/2/1997	0530159	GB
NMXS-1135.00/GB	Utility - EPPAT	Abandoned	ROW DECODER FOR NAND-TYPE ROM	8/27/1992	92830457.5	3/4/1998	0534910	GB
NMXS-1136.00/GB	Utility - EPPAT	Abandoned	PLANARIZED CONTACT WITH A SANDWICH OF TUNGSTEN AND ALUMINIUM.	11/10/1992	92119191.2	9/22/1999	0543254	GB
NMXS-1137.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	11/2/1992	92118785.2	9/27/2000	0545082	GB
NMXS-1138.00/GB	Utility - EPPAT	Abandoned	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	9/24/1992	92830523.4	1/21/1998	0536095	GB
NMXS-1139.00/GB	Utility - EPPAT	Abandoned	METALLIZATION OVER TUNGSTEN PLUGS	5/27/1992	92830265.2	9/18/1996	0571691	GB
NMXS-1140.00/GB	Utility - EPPAT	Abandoned	LOW SWITCHING NOISE OUTPUT BUFFER	6/26/1992	92830335.3	10/31/2001	0585505	GB
NMXS-1141.00/GB	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	6/30/1992	92830339.5	9/13/1995	0576773	GB
NMXS-1142.00/GB	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	6/30/1992	92830340.3	9/15/1999	0576774	GB
NMXS-1143.00/GB	Utility - EPPAT	Abandoned	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	9/30/1992	92830541.6	12/2/1998	0591598	GB
NMXS-1144.00/GB	Utility - EPPAT	Abandoned	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	10/1/1992	92830552.3	5/27/1998	0575688	GB
NMXS-1145.00/GB	Utility - EPPAT	Abandoned	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	10/29/1992	92830589.5	7/28/1999	0594920	GB
NMXS-1146.00/GB	Utility - EPPAT	Abandoned	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	11/18/1992	92830625.7	5/28/1997	0598168	GB
NMXS-1147.00/GB	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	1/29/1993	93830031.6	5/6/1999	0608664	GB
NMXS-1148.00/GB	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS	1/29/1993	93830032.4	1/7/1998	0608665	GB
NMXS-1149.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS	2/11/1993	93830050.6	9/10/1997	0610643	GB
NMXS-1150.00/GB	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830057.1	7/30/1997	0613176	GB
NMXS-1151.00/GB	Utility - EPPAT	Abandoned	NONVOLATILE EPROM, EEPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830058.9	10/13/1999	0614223	GB
NMXS-1152.00/GB	Utility - EPPAT	Abandoned	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	3/18/1993	93830109.0	6/23/1999	0616332	GB
NMXS-1153.00/GB	Utility - EPPAT	Abandoned	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	3/18/1993	93830110.8	6/23/1999	0616333	GB
NMXS-1154.00/GB	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS	3/31/1993	93830128.0	7/22/1998	0618587	GB
NMXS-1155.00/GB	Utility - EPPAT	Abandoned	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	4/1/1993	93830134.8	7/28/1999	0595775	GB
NMXS-1157.00/GB	Utility - NSPCT	Abandoned	METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/9/1992	92402777.4	3/4/1998	0537082	GB
NMXS-1078.00/IN	Utility - NSPCT	Pending	PHASE CHANGE MEMORY DEVICE	7/26/2007	139/CHENP/2009			IN

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NMXS-0001.00/IT	Utility - EPPAT	Abandoned	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/9/1988	88403140.2	4/10/1996	0321327	IT
NMXS-0002.00/IT	Utility - EPPAT	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/9/1988	88403141.0	1/13/1993	0323295	IT
NMXS-0003.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/26/1989	89401183.2	5/10/1993	0340107	IT
NMXS-0004.00/IT	Utility - EPPAT	Lapsed	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/19/1993	93401861.5	2/15/1995	0585150	IT
NMXS-0005.00/IT	Utility - EPPAT	Abandoned	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	7/15/1993	93401836.7	12/28/1994	0581639	IT
NMXS-0006.00/IT	Utility - EPPAT	Lapsed	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	9/14/1993	93402229.4	1/18/1995	0591022	IT
NMXS-0007.00/IT	Utility - EPPAT	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/14/1993	93403029.7	4/3/1996	0604270	IT
NMXS-0008.00/IT	Utility - EPPAT	Abandoned	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/19/1987	87401120.8	3/14/1990	0246965	IT
NMXS-0009.00/IT	Utility - EPPAT	Lapsed	NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401991.0	10/27/1993	0302780	IT
NMXS-0010.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	7/29/1988	88401990.2	5/26/1993	0302779	IT
NMXS-0011.00/IT	Utility - EPPAT	Lapsed	CONTENT ADDRESSABLE MEMORY	5/23/1991	91304677.7	8/16/2000	0459703	IT
NMXS-0012.00/IT	Utility - EPPAT	Lapsed	REDUNDANCY FOR SERIAL MEMORY	12/21/1990	90314116.6	4/23/1997	0437081	IT
NMXS-0013.00/IT	Utility - EPPAT	Lapsed	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	3/25/1991	91302575.5	12/16/1998	0455339	IT
NMXS-0014.00/IT	Utility - EPPAT	Lapsed	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/19/1990	90313891.5	4/1/1998	0434381	IT
NMXS-0015.00/IT	Utility - EPPAT	Lapsed	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/16/1991	91309521.2	7/29/1998	0481751	IT
NMXS-0016.00/IT	Utility - EPPAT	Lapsed	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	6/29/1990	90307156.1	1/8/1997	0420388	IT
NMXS-0017.00/IT	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/12/1991	91307425.8	3/19/1997	0471543	IT
NMXS-0018.00/IT	Utility - EPPAT	Lapsed	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	5/31/1991	91304952.4	12/18/1996	0501057	IT
NMXS-0019.00/IT	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	5/31/1991	91304951.6	7/30/1997	0472266	IT
NMXS-0020.00/IT	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307423.3	3/19/1997	0471541	IT
NMXS-0021.00/IT	Utility - EPPAT	Lapsed	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/12/1991	91307419.1	6/26/1996	0475588	IT
NMXS-0022.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308632.8	6/18/1997	0478251	IT
NMXS-0023.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/23/1991	91308633.6	4/8/1998	0478252	IT
NMXS-0024.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/12/1991	91307426.6	5/14/1997	0471544	IT
NMXS-0025.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/21/1991	91309721.8	1/7/1998	0482869	IT
NMXS-0026.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/23/1991	91308634.4	11/27/1996	0478253	IT
NMXS-0027.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/23/1991	91308635.9	5/28/1997	0478254	IT
NMXS-0028.00/IT	Utility - EPPAT	Abandoned	ADDRESS BUFFER CIRCUIT HAVING LATCHING BASED ON TRANSITION	10/21/1991	91309720.0	1/7/1998	0482868	IT

PATENT
REEL: 030872 FRAME: 0208

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MII-DcknNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0029.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH PRECHARGED REDUNDANCY MULTIPLEXING	12/12/1991	91311569.7	9/11/1996	0491523	IT
NMXS-0031.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/12/1991	913115705	9/24/1997	0490679	IT
NMXS-0032.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/12/1991	91311571.3	10/2/1996	0490680	IT
NMXS-0033.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	7/16/1992	92306526.2	3/4/1998	0523995	IT
NMXS-0034.00/IT	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	4/30/1992	92303960.6	10/20/1999	0514050	IT
NMXS-0035.00/IT	Utility - EPPAT	Abandoned	CONTROL CIRCUIT FOR DUAL PORT MEMORY	4/30/1992	92303958.0	7/22/1998	0514049	IT
NMXS-0036.00/IT	Utility - EPPAT	Abandoned	CACHE TAG PARITY DETECT CIRCUIT	3/27/1992	92302736.1	10/8/1997	0506474	IT
NMXS-0037.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	7/16/1992	92306527.0	3/4/1998	0523996	IT
NMXS-0038.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT DUAL-PORT MEMORY DEVICE HAVING REDUCED CAPACITANCE	7/16/1992	92306528.8	5/20/1998	0523997	IT
NMXS-0039.00/IT	Utility - EPPAT	Abandoned	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	1/20/1993	93300397.2	7/8/1998	0552941	IT
NMXS-0041.00/IT	Utility - EPPAT	Abandoned	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	12/16/1992	92311510.9	3/3/1999	0547888	IT
NMXS-0042.00/IT	Utility - EPPAT	Abandoned	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/16/1992	92311511.7	4/14/1999	0547889	IT
NMXS-0045.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	12/16/1992	92311514.1	10/28/1998	0547892	IT
NMXS-0046.00/IT	Utility - EPPAT	Abandoned	REDUNDANCY DECODER	1/27/1993	93300560.5	7/22/1998	0554052	IT
NMXS-0049.00/IT	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR	4/29/1993	93303369.8	12/29/1999	0568373	IT
NMXS-0050.00/IT	Utility - EPPAT	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE	4/29/1993	93303370.6	10/20/1999	0568374	IT
NMXS-0052.00/IT	Utility - EPPAT	Abandoned	PARALLELIZED DIFFERENCE FLAG LOGIC	5/19/1993	93303874.7	2/23/2000	0574144	IT
NMXS-0053.00/IT	Utility - EPPAT	Abandoned	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/10/1993	93304489.3	12/20/2000	0579375	IT
NMXS-0059.00/IT	Utility - EPPAT	Lapsed	INTEGRATED CIRCUIT OUTPUT DRIVER	8/27/1993	93306835.5	3/26/1997	0586207	IT
NMXS-0062.00/IT	Utility - EPPAT	Abandoned	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/21/1993	93310384.8	3/3/1999	0604195	IT
NMXS-0064.00/IT	Utility - EPPAT	Abandoned	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/18/1994	94300188.2	5/10/2000	0612008	IT
NMXS-0065.00/IT	Utility - EPPAT	Abandoned	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/30/1993	93307776.0	3/3/1999	0590982	IT
NMXS-0066.00/IT	Utility - EPPAT	Abandoned	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/27/1993	93306836.3	10/29/1997	0586208	IT
NMXS-0068.00/IT	Utility - EPPAT	Abandoned	ADDRESS BUFFER	4/28/1994	94303082.5	9/22/1999	0622803	IT
NMXS-0071.00/IT	Utility - EPPAT	Abandoned	OUTPUT DRIVER CIRCUIT	7/28/1993	93305947.9	2/24/1999	0581579	IT
NMXS-0072.00/IT	Utility - EPPAT	Abandoned	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	7/27/1994	94305553.3	11/10/1999	0637036	IT
NMXS-0073.00/IT	Utility - EPPAT	Abandoned	TEMPERATURE-STABLE CURRENT SOURCE	6/12/1995	95401363.7	4/8/1998	0687967	IT
NMXS-0074.00/IT	Utility - EPPAT	Lapsed	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	5/31/1993	93830243.7	12/15/2004	0627763	IT
NMXS-0075.00/IT	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/30/1993	93830403.7	12/1/1999	0646924	IT
NMXS-0076.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	9/10/1993	93830365.8	12/2/1998	0643418	IT
NMXS-0077.00/IT	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/30/1993	93830481.3	2/10/1999	0655742	IT
NMXS-0079.00/IT	Utility - EPPAT	Lapsed	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/24/1993	93830464.9	7/28/1999	0654791	IT
NMXS-0080.00/IT	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/7/1993	93830491.2	3/17/1999	0657814	IT
NMXS-0081.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	11/30/1993	93830474.8	8/25/1999	0655743	IT
NMXS-0082.00/IT	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830062.9	7/8/1998	0668563	IT
NMXS-0083.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/9/1993	93830493.8	9/2/1998	0657811	IT
NMXS-0084.00/IT	Utility - EPPAT	Abandoned	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/29/1994	94830146.0	8/5/1998	0675440	IT

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MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0085.00/IT	Utility - EPPAT	Abandoned	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/21/1994	94830022.3	10/7/1998	0665485	IT
NMXS-0086.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE MEMORY OUTPUT DATA	2/18/1994	94830069.4	7/7/1999	0678869	IT
NMXS-0087.00/IT	Utility - EPPAT	Abandoned	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/18/1994	94830070.2	5/17/2000	0668592	IT
NMXS-0088.00/IT	Utility - EPPAT	Abandoned	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/18/1994	94830071.0	6/7/2000	0678873	IT
NMXS-0089.00/IT	Utility - EPPAT	Abandoned	COUNT UNIT FOR NONVOLATILE MEMORIES	12/28/1993	93830527.3	7/7/1999	0662691	IT
NMXS-0090.00/IT	Utility - EPPAT	Abandoned	END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES	12/28/1993	93830526.5	3/31/1999	0661814	IT
NMXS-0091.00/IT	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	12/28/1993	93830525.7	7/10/1997	0661795	IT
NMXS-0092.00/IT	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1993	93830489.6	5/27/1998	0662690	IT
NMXS-0093.00/IT	Utility - EPPAT	Abandoned	READING CIRCUIT FOR AN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1994	94830124.7	5/31/2000	0678871	IT
NMXS-0094.00/IT	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/30/1993	93830478.9	9/1/1999	0655683	IT
NMXS-0095.00/IT	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/31/1994	94830032.2	5/23/2001	0665558	IT
NMXS-0096.00/IT	Utility - EPPAT	Abandoned	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/31/1994	94830156.9	7/11/2001	0675504	IT
NMXS-0098.00/IT	Utility - EPPAT	Abandoned	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	12/31/1993	93830537.2	6/9/1999	0661713	IT
NMXS-0099.00/IT	Utility - EPPAT	Abandoned	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1993	93830482.1	5/10/2000	0655569	IT
NMXS-0100.00/IT	Utility - EPPAT	Abandoned	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1994	94830077.7	9/26/2001	0668593	IT
NMXS-0101.00/IT	Utility - EPPAT	Abandoned	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830540.6	6/23/1999	0661714	IT
NMXS-0102.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	12/31/1993	93830545.5	3/29/2000	0661717	IT
NMXS-0103.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/31/1993	93830542.2	6/9/1999	0661715	IT
NMXS-0104.00/IT	Utility - EPPAT	Abandoned	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/29/1993	93830528.1	9/23/1998	0661636	IT
NMXS-0105.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/18/1994	94830073.6	7/28/1999	0678870	IT
NMXS-0106.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/18/1994	94830074.4	10/20/1999	0668591	IT
NMXS-0107.00/IT	Utility - EPPAT	Abandoned	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH	4/19/1994	94830182.5	7/26/2000	0678874	IT
NMXS-0108.00/IT	Utility - EPPAT	Abandoned	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME	3/28/1994	94830144.5	10/4/2001	0676816	IT
NMXS-0109.00/IT	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY	2/17/1994	94830061.1	8/5/1998	0668562	IT
NMXS-0110.00/IT	Utility - EPPAT	Abandoned	REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS	3/28/1994	94830143.7	12/27/2000	0676768	IT
NMXS-0111.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	12/31/1993	93830543.0	7/21/1999	0661716	IT
NMXS-0112.00/IT	Utility - EPPAT	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	4/28/1994	94303084.1	4/7/1999	0627817	IT
NMXS-0113.00/IT	Utility - EPPAT	Abandoned	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/20/1994	94302808.4	11/11/1998	0621537	IT
NMXS-0115.00/IT	Utility - EPPAT	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	6/27/1994	94304543.3	9/8/1999	0632594	IT
NMXS-0124.00/IT	Utility - EPPAT	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	7/27/1994	94305554.1	9/23/1998	0637134	IT
NMXS-0131.00/IT	Utility - EPPAT	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/28/1994	94307068.0	5/31/2000	0646926	IT
NMXS-0138.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/21/1994	94460043.6	5/29/1996	0654792	IT
NMXS-0139.00/IT	Utility - EPPAT	Abandoned	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	5/25/1994	94401162.6	10/4/2001	0626728	IT

PATENT
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MTI-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0140.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/26/1994	94460037.8	12/16/1998	0651394	IT
NMXS-0141.00/IT	Utility - EPPAT	Abandoned	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/21/1994	94470041.8	4/14/1999	0660331	IT
NMXS-0142.00/IT	Utility - EPPAT	Abandoned	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/16/1994	94402912.3	8/21/1996	0660333	IT
NMXS-0144.00/IT	Utility - EPPAT	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/23/1995	95470006.8	10/16/1996	0669622	IT
NMXS-0145.00/IT	Utility - EPPAT	Abandoned	MEMORY REDUNDANCY CIRCUIT	2/27/1995	95400420.6	6/19/1996	0669576	IT
NMXS-0146.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/20/1995	95400608.6	10/6/1999	0675503	IT
NMXS-0147.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400190.5	10/16/1996	0666572	IT
NMXS-0148.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400189.7	6/26/1996	0666576	IT
NMXS-0149.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/27/1995	95400188.9	6/26/1996	0665559	IT
NMXS-0150.00/IT	Utility - EPPAT	Abandoned	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/14/1995	95470014.2	9/18/1996	0678801	IT
NMXS-0151.00/IT	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER CIRCUIT	4/14/1995	95470013.4	6/18/1997	0678868	IT
NMXS-0152.00/IT	Utility - EPPAT	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/6/1995	95400772.0	9/29/1999	0678875	IT
NMXS-0153.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/17/1995	95460007.8	1/22/1997	0674264	IT
NMXS-0154.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/3/1995	95460015.1	8/21/1996	0676769	IT
NMXS-0155.00/IT	Utility - EPPAT	Abandoned	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	7/18/1995	95401709.1	12/18/1996	0696031	IT
NMXS-0156.00/IT	Utility - EPPAT	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/20/1995	95400607.8	6/2/1999	0675441	IT
NMXS-0157.00/IT	Utility - EPPAT	Abandoned	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/7/1994	94830276.5	3/7/2001	0686978	IT
NMXS-0158.00/IT	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY ELEMENT	3/31/1994	94830154.4	6/13/2001	0675501	IT
NMXS-0159.00/IT	Utility - EPPAT	Abandoned	SENSE AMPLIFIER WITH HYSTERESIS	5/3/1994	94830209.6	3/28/2001	0681293	IT
NMXS-0160.00/IT	Utility - EPPAT	Abandoned	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	4/12/1994	94830167.6	8/17/1999	0677869	IT
NMXS-0161.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/30/1994	94830591.7	3/26/2003	0720223	IT
NMXS-0162.00/IT	Utility - EPPAT	Abandoned	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	6/10/1994	94830283.1	3/7/2001	0686979	IT
NMXS-0163.00/IT	Utility - EPPAT	Abandoned	METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL	7/18/1994	94830363.1	10/14/1998	0696050	IT
NMXS-0164.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	9/30/1994	94830471.2	12/1/1999	0704854	IT
NMXS-0165.00/IT	Utility - EPPAT	Abandoned	SENSE AMPLIFIER CIRCUIT FOR SEMICONDUCTOR MEMORY DEVICES	4/28/1995	95830166.5	12/12/2001	0740307	IT
NMXS-0166.00/IT	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	11/30/1994	94830554.5	10/23/2002	0715312	IT
NMXS-0168.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS	9/30/1994	94830468.8	12/15/1999	0704901	IT
NMXS-0170.00/IT	Utility - EPPAT	Abandoned	SYNCHRONIZATION DEVICE FOR OUTPUT STAGES, PARTICULARLY FOR ELECTRONIC MEMORIES	11/18/1994	94830538.8	1/9/2002	0713221	IT
NMXS-0171.00/IT	Utility - EPPAT	Abandoned	PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING	4/4/1995	95830133.5	6/27/2001	0736876	IT
NMXS-0173.00/IT	Utility - EPPAT	Abandoned	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	5/19/1995	95830211.9	3/29/2000	0743648	IT
NMXS-0174.00/IT	Utility - EPPAT	Abandoned	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	1/26/1995	95830020.4	4/11/2001	0724267	IT

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MTI DktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0175.00/IT	Utility - EPPAT	Abandoned	TWIN-WELL MANUFACTURING PROCESS FOR AN EEPROM INTEGRATED DEVICE WITH REDUCED BODY EFFECT	11/24/1994	94830544.6	7/6/2002	0714133	IT
NMXS-0177.00/IT	Utility - EPPAT	Abandoned	BYTE ERASABLE EEPROM FULLY COMPATIBLE WITH A SINGLE POWER SUPPLY FLASH-EPROM PROCESS	9/27/1994	94830459.7	11/28/2001	0704851	IT
NMXS-0179.00/IT	Utility - EPPAT	Abandoned	NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER	5/5/1995	95830184.8	1/12/2000	0741387	IT
NMXS-0180.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC	6/30/1995	95830281.2	11/27/2002	0751559	IT
NMXS-0181.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC	6/30/1995	95830282.0	11/27/2002	0751560	IT
NMXS-0183.00/IT	Utility - EPPAT	Abandoned	METHOD FOR IMPROVING THE PROFILE OF THE INTERMEDIATE DIELECTRIC, PARTICULARLY FOR NON VOLATILE MEMORIES	2/28/1996	96830086.3	12/10/2003	0793273	IT
NMXS-0184.00/IT	Utility - EPPAT	Abandoned	CHARGE PUMP VOLTAGE MULTIPLIER CIRCUIT	12/5/1994	94830563.6	6/12/2002	0716368	IT
NMXS-0185.00/IT	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS	4/14/1995	95830153.3	9/13/2000	0737643	IT
NMXS-0186.00/IT	Utility - EPPAT	Abandoned	CURRENT DETECTING CIRCUIT	8/3/1995	95830354.7	1/26/2000	0757357	IT
NMXS-0187.00/IT	Utility - EPPAT	Abandoned	HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES	9/29/1995	95830405.7	4/4/2001	0768672	IT
NMXS-0189.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	12/2/1994	94308981.3	9/1/1999	0675439	IT
NMXS-0190.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	12/9/1994	94309218.9	3/24/1999	0675597	IT
NMXS-0194.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	5/24/1995	95303484.0	12/1/1999	0688851	IT
NMXS-0210.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT	11/28/1995	95308543.8	3/15/2000	0718743	IT
NMXS-0211.00/IT	Utility - EPPAT	Abandoned	DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT	11/28/1995	95308563.6	8/30/2000	0718740	IT
NMXS-0214.00/IT	Utility - EPPAT	Abandoned	INTERNAL BUS CONTROL(FLASH MEMORY DEVICE TEST MODE TO DRIVE AN INTERNAL CONTROLBUS EXTERNALLY)	8/21/1995	95305818.7	11/10/1999	0688848	IT
NMXS-0216.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/14/1995	95402815.5	2/25/1998	0718850	IT
NMXS-0217.00/IT	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/11/1995	95402054.1	4/22/1998	0703584	IT
NMXS-0219.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/14/1995	95402820.5	4/22/1998	0718849	IT
NMXS-0220.00/IT	Utility - EPPAT	Abandoned	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/17/1996	96470008.0	4/29/1998	0750244	IT
NMXS-0221.00/IT	Utility - EPPAT	Abandoned	RESISTANCE REFERENCE CIRCUIT	12/13/1995	95402912.0	5/19/1999	0718887	IT
NMXS-0222.00/IT	Utility - EPPAT	Abandoned	DIGITAL RAMP GENERATOR	5/29/1996	96401155.5	4/7/1999	0745996	IT
NMXS-0223.00/IT	Utility - EPPAT	Abandoned	SERIAL DICHOTOMIC METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT IMPLEMENTING SUCH METHOD	1/27/1995	95830023.8	12/12/2001	0724266	IT
NMXS-0225.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR READING NON-VOLATILE MEMORIES	8/4/1995	95830357.0	3/28/2001	0757358	IT
NMXS-0226.00/IT	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT	3/23/1995	95830110.3	1/26/2000	0734024	IT
NMXS-0227.00/IT	Utility - EPPAT	Abandoned	READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE	4/28/1995	95830172.3	4/10/2002	0747903	IT
NMXS-0228.00/IT	Utility - EPPAT	Abandoned	MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS	7/28/1995	95830336.4	7/5/2000	0756285	IT
NMXS-0229.00/IT	Utility - EPPAT	Abandoned	THRESHOLD DETECTING DEVICE	8/4/1995	95830360.4	3/28/2001	0757352	IT
NMXS-0230.00/IT	Utility - EPPAT	Abandoned	CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES	7/28/1995	95830335.6	10/11/2000	0756220	IT

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NMXS 0231.00/IT	Utility - EPPAT	Abandoned	FLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE	8/2/1995	95830351.3	5/23/2001	0758129	IT
NMXS-0232.00/IT	Utility - EPPAT	Abandoned	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/19/1995	95830253.1	1/26/2000	0758314	IT
NMXS-0233.00/IT	Utility - EPPAT	Abandoned	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	9/29/1995	95830406.5	1/26/2000	0766255	IT
NMXS-0234.00/IT	Utility - EPPAT	Abandoned	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	7/14/1995	95830302.6	1/26/2000	0753859	IT
NMXS-0235.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE	9/29/1995	95830407.3	12/1/1999	0766256	IT
NMXS-0236.00/IT	Utility - EPPAT	Abandoned	ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD	3/29/1996	96830174.7	7/28/2004	0798735	IT
NMXS-0237.00/IT	Utility - EPPAT	Abandoned	DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY	6/20/1996	96830352.9	5/28/2003	0782149	IT
NMXS-0238.00/IT	Utility - EPPAT	Abandoned	SYSTEM FOR DETERMINING THE PROGRAMMED/NON PROGRAMMED STATUS OF A MEMORY CELL	3/29/1996	96830163.0	11/12/2003	0798740	IT
NMXS-0239.00/IT	Utility - EPPAT	Abandoned	BOOST REGULATOR	1/24/1996	96830026.9	3/31/2004	0786777	IT
NMXS-0240.00/IT	Utility - EPPAT	Abandoned	UNBALANCED LATCH AND FUSE CIRCUIT INCLUDING THE SAME	7/28/1995	95830337.2	9/24/2003	0756379	IT
NMXS-0241.00/IT	Utility - EPPAT	Abandoned	REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS	3/29/1996	96830160.6	11/3/2004	0798729	IT
NMXS-0242.00/IT	Utility - EPPAT	Abandoned	TIME SHARING INTERNATIONAL BUS, PARTICULARLY FOR NON VOLATILE MEMORIES	3/20/1996	96830129.1	12/11/2002	0797209	IT
NMXS-0243.00/IT	Utility - EPPAT	Abandoned	PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD	7/31/1995	95830347.1	4/19/2000	0757355	IT
NMXS-0244.00/IT	Utility - EPPAT	Abandoned	SUPPLY VOLTAGES SWITCHES CIRCUIT	6/20/1996	96830358.7	4/24/2002	0782268	IT
NMXS-0246.00/IT	Utility - EPPAT	Abandoned	VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS	10/31/1995	95830461.0	7/23/2003	0772200	IT
NMXS-0247.00/IT	Utility - EPPAT	Abandoned	FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR	7/24/1995	95830317.4	1/26/2000	0756286	IT
NMXS-0248.00/IT	Utility - EPPAT	Abandoned	NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	10/31/1995	95830456.0	3/15/2000	0772282	IT
NMXS-0249.00/IT	Utility - EPPAT	Abandoned	ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE	11/3/1995	95830466.9			IT
NMXS-0250.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH IMPROVED YIELD AND RELIABILITY	9/29/1995	95830408.1	5/22/2002	0766174	IT
NMXS-0251.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR THE GENERATION OF A VOLTAGE AS A FUNCTION OF THE CONDUCTIVITY OF AN ELEMENTARY CELL OF A NON-VOLATILE MEMORY	3/29/1996	96830168.9	11/24/2004	0798743	IT
NMXS-0252.00/IT	Utility - EPPAT	Abandoned	ZERO CONSUMPTION POWER-ON-RESET	2/2/1996	96830046.7	11/13/2002	0788114	IT
NMXS-0253.00/IT	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES	3/29/1996	96830167.1	11/7/2001	0798642	IT
NMXS-0254.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL	12/14/1995	95830520.3	9/13/2000	0779642	IT
NMXS-0255.00/IT	Utility - EPPAT	Abandoned	HIGH-VOLTAGE-RESISTANT MOS TRANSISTOR, AND CORRESPONDING MANUFACTURING PROCESS	3/29/1996	96830175.4	12/3/2003	0798785	IT
NMXS-0257.00/IT	Utility - EPPAT	Lapsed	HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURINGPROCESS	10/31/1995	95830459.4	10/12/2005	0772246	IT
NMXS-0260.00/IT	Utility - EPPAT	Abandoned	FABRICATION OF NATURAL TRANSISTORS IN A NONVOLATILE MEMORY PROCESS	1/22/1996	96830021.0	12/4/2002	0785570	IT
NMXS-0261.00/IT	Utility - EPPAT	Abandoned	MULTI-LEVEL MEMORY CIRCUITS AND CORRESPONDING READING AND WRITING METHODS	1/31/1996	96830044.2	8/24/2005	0788113	IT
NMXS-0262.00/IT	Utility - EPPAT	Lapsed	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	96937498.3	1/10/2001	0906622	IT

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NMXS-0263.00/IT	Utility - EPPAT	Abandoned	CLOCK CIRCUIT FOR READING A MULTILEVEL NON VOLATILE MEMORY CELLS DEVICE	5/28/1996	96830871.9	3/19/2003	0817200	IT
NMXS-0264.00/IT	Utility - EPPAT	Abandoned	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	96937494.1	1/3/2001	0906623	IT
NMXS-0265.00/IT	Utility - EPPAT	Abandoned	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	3/22/1996	96830144.0	6/12/2002	0797145	IT
NMXS-0266.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	5/9/1996	96830267.9	3/19/2003	0806773	IT
NMXS-0268.00/IT	Utility - EPPAT	Abandoned	ERASING METHOD FOR A NON-VOLATILE MEMORY	12/29/1995	95830554.2	5/10/2000	0782145	IT
NMXS-0269.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR GENERATING A SYNCHRONIZING ATD SIGNAL	11/27/1996	96830598.7	4/9/2003	0845784	IT
NMXS-0270.00/IT	Utility - EPPAT	Abandoned	METHOD TO PREVENT DISTURBS DURING THE PROGRAMMING AND ERASING PHASES IN A NON-VOLATILE MEMORY DEVICE	4/30/1996	96830245.5	2/26/2003	0782148	IT
NMXS-0271.00/IT	Utility - EPPAT	Abandoned	ERASE VOLTAGE CONTROL CIRCUIT FOR AN ELECTRICALLY ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830025.1	7/28/2004	0786779	IT
NMXS-0272.00/IT	Utility - EPPAT	Abandoned	METHOD FOR ERASING AN ELECTRICALLY PROGRAMMABLE AND ERASABLE NON-VOLATILE MEMORY CELL	1/24/1996	96830024.4	11/12/2003	0786778	IT
NMXS-0273.00/IT	Utility - EPPAT	Abandoned	PROGRAMMABLE DEVICE WITH BASIC MODULES ELECTRICALLY CONNECTED BY FLASH MEMORY CELLS	12/29/1995	95830552.6	5/23/2001	0782144	IT
NMXS-0274.00/IT	Utility - EPPAT	Abandoned	PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS	6/5/1996	96830318.0	3/12/2003	0811986	IT
NMXS-0275.00/IT	Utility - EPPAT	Abandoned	HIGH VOLTAGES DETECTOR CIRCUIT AND INTEGRATED CIRCUIT USING SAME	1/31/1996	96830043.4	3/31/2004	0788231	IT
NMXS-0276.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE	1/31/1997	97830029.1	6/25/2003	0856886	IT
NMXS-0277.00/IT	Utility - EPPAT	Abandoned	MEMORY ARCHITECTURE FOR FLEXIBLE READING MANAGEMENT, PARTICULARLY FOR NON-VOLATILE MEMORIES, HAVING NOISE IMMUNITY FEATURES, MATCHING DEVICE PERFORMANCE, AND HAVING OPTIMIZED THROUGHOUT	4/29/1996	96830239.8	1/2/2004	0805453	IT
NMXS-0278.00/IT	Utility - EPPAT	Abandoned	CIRCUITS AND METHODS FOR READ-ENABLING MEMORY DEVICES SYNCHRONOUSLY WITH THE REACHING OF THE MINIMUM FUNCTIONALITY CONDITIONS OF THE MEMORY CELLS AND READING CIRCUITS, PARTICULARLY FOR NON-VOLATILE MEMORIES	4/29/1996	96830238.0	9/24/2003	0805452	IT
NMXS-0279.00/IT	Utility - EPPAT	Abandoned	COLUMN MULTIPLEXER	5/13/1996	96830275.2	11/12/2003	0810606	IT
NMXS-0280.00/IT	Utility - EPPAT	Abandoned	DRIVER DEVICE FOR SELECTION LINES FOR A MULTIPLEXER, TO BE USED IN A WIDE RANGE OF SUPPLY VOLTAGES, PARTICULARLY FOR NON-VOLATILE MEMORIES	3/29/1996	96830166.3	11/12/2003	0798742	IT
NMXS-0281.00/IT	Utility - EPPAT	Abandoned	PROGRAMMING AND READING MANAGEMENT ARCHITECTURE FOR MEMORY DEVICES, PARTICULARLY FOR TEST PURPOSES	3/29/1996	96830161.4	1/7/2004	0798726	IT
NMXS-0283.00/IT	Utility - EPPAT	Abandoned	DATA READING PATH MANAGEMENT ARCHITECTURE FOR A MEMORY DEVICE, PARTICULARLY FOR NON VOLATILE MEMORIES	3/29/1996	96830162.2	5/26/2004	0798727	IT
NMXS-0284.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE HAVING OPTIMIZED MANAGEMENT OF DATA TRANSMISSION LINES	3/20/1996	96830128.3	1/2/2003	0797208	IT
NMXS-0288.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS	5/8/1996	96303214.9	12/22/1999	0747800	IT
NMXS-0316.00/IT	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/6/1996	96470004.1	6/23/1999	0735489	IT
NMXS-0317.00/IT	Utility - EPPAT	Abandoned	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OR NEGATIVE SUPPLY CIRCUIT	6/17/1996	96470011.6	5/20/1998	0757427	IT
NMXS-0318.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY	9/2/1996	96460031.6	11/11/1998	0762428	IT
NMXS-0319.00/IT	Utility - EPPAT	Abandoned	HIGH VOLTAGE GENERATOR	12/24/1996	96402887.2	3/8/2000	0782243	IT

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NMXS-0321.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES	2/17/1997	97460009.0	6/9/1999	0791933	IT
NMXS-0322.00/IT	Utility - EPPAT	Abandoned	DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED	1/24/1997	97460008.2	12/2/1998	0788233	IT
NMXS-0323.00/IT	Utility - EPPAT	Abandoned	FLASH-EPROM WITH EMBEDDED EEPROM	4/15/1996	96830212.5	9/24/2003	0802569	IT
NMXS-0326.00/IT	Utility - EPPAT	Abandoned	POWER ON RESET CIRCUIT WITH AUTO TURN OFF	4/30/1996	96830247.1	3/23/2005	0805556	IT
NMXS-0327.00/IT	Utility - EPPAT	Abandoned	UPROM CELL FOR LOW VOLTAGE SUPPLY	4/30/1996	96830243.0	2/18/2004	0806771	IT
NMXS-0328.00/IT	Utility - EPPAT	Abandoned	BIASING CIRCUIT FOR UPROM CELLS WITH LOW VOLTAGE SUPPLY	4/30/1996	96830242.2	2/11/2004	0805456	IT
NMXS-0329.00/IT	Utility - EPPAT	Abandoned	ROW DECODER FOR LOW POWER SUPPLY	5/24/1996	96830299.2	10/15/2003	0809254	IT
NMXS-0330.00/IT	Utility - EPPAT	Abandoned	I/V CONVERTER FOR LOW SUPPLY NON VOLATILE MEMORY CELLS	6/18/1996	96830344.6	12/17/2003	0814480	IT
NMXS-0331.00/IT	Utility - EPPAT	Abandoned	LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY DEVICE WITH VOLTAGE BOOSTING	6/18/1996	96830345.3	3/20/2002	0814481	IT
NMXS-0332.00/IT	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS	6/18/1996	96830346.1	8/27/2003	0814482	IT
NMXS-0333.00/IT	Utility - EPPAT	Abandoned	MOS CAPACITOR WITH WIDE VOLTAGE AND FREQUENCY OPERATING RANGES	7/30/1996	96830420.4	5/14/2006	0822601	IT
NMXS-0334.00/IT	Utility - EPPAT	Abandoned	BIDIRECTIONAL CHARGE PUMP	8/2/1996	96830441.0	4/2/2003	0822556	IT
NMXS-0335.00/IT	Utility - EPPAT	Abandoned	BICMOS NEGATIVE CHARGE PUMP	11/14/1996	96830581.3	2/27/2002	0843402	IT
NMXS-0336.00/IT	Utility - EPPAT	Abandoned	IMPROVED POSITIVE CHARGE PUMP	10/11/1996	96830521.9	2/6/2002	0836268	IT
NMXS-0337.00/IT	Utility - EPPAT	Abandoned	OUTPUT STAGE FOR A MEMORY DEVICE AND FOR LOW VOLTAGE APPLICATIONS	7/24/1996	96830411.8	5/26/2004	0821362	IT
NMXS-0339.00/IT	Utility - EPPAT	Abandoned	HIGH VOLTAGE TOLERANCE OUTPUT STAGE	7/24/1996	96830413.9	10/9/2002	0821484	IT
NMXS-0340.00/IT	Utility - EPPAT	Abandoned	SINGLE-CELL REFERENCE SIGNAL GENERATING CIRCUIT FOR READING NONVOLATILE MEMORY	6/18/1996	96830348.7	9/17/2003	0814484	IT
NMXS-0342.00/IT	Utility - EPPAT	Abandoned	NMOS NEGATIVE CHARGE PUMP	1/23/1997	97830014.3	6/22/2005	0855788	IT
NMXS-0343.00/IT	Utility - EPPAT	Abandoned	ADDRESS TRANSITION DETECTION CIRCUIT	3/6/1996	96830096.2	9/12/2001	0794618	IT
NMXS-0344.00/IT	Utility - EPPAT	Abandoned	METHOD FOR RECOVERING FAILED MEMORY	3/21/1996	96830136.6	7/3/2002	0797147	IT
NMXS-0345.00/IT	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD FOR GENERATING A POWER-ON RESET SIGNAL	3/29/1996	96830177.0	6/18/2003	0798728	IT
NMXS-0346.00/IT	Utility - EPPAT	Abandoned	GAIN MODULATED SENSE AMPLIFIER, PARTICULARLY FOR MEMORY DEVICES	3/29/1996	96830164.8	2/5/2003	0798732	IT
NMXS-0347.00/IT	Utility - EPPAT	Abandoned	CIRCUIT AND METHOD TO ADJUST MEMORY TIMING	3/29/1996	96830176.2	12/3/2003	0798744	IT
NMXS-0348.00/IT	Utility - EPPAT	Abandoned	STANDBY VOLTAGE BOOSTING STAGE AND METHOD FOR A MEMORY DEVICE	3/29/1996	96830178.8	10/17/2001	0800259	IT
NMXS-0349.00/IT	Utility - EPPAT	Abandoned	VOLTAGE BOOSTER FOR MEMORY DEVICES	3/29/1996	96830179.6	10/17/2001	0800260	IT
NMXS-0350.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR THE SWITCHING OF SUPPLY VOLTAGES IN ELECTRICALLY PROGRAMMABLE AND CANCELABLE NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	4/5/1996	96830193.7	3/3/2004	0800177	IT
NMXS-0351.00/IT	Utility - EPPAT	Abandoned	AUTO-SAVING CIRCUIT FOR PROGRAMMING CONFIGURATION ELEMENTS IN NON-VOLATILE MEMORY DEVICES	4/5/1996	96830191.1	2/2/2005	0800178	IT
NMXS-0352.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE MEMORY CELLS	4/5/1996	96830192.9	7/2/2003	0800176	IT
NMXS-0353.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR DETECTING THE COINCIDENCE BETWEEN A BINARY INFORMATION UNIT STORED THEREIN AND AN EXTERNAL DATUM	3/22/1996	96830143.2	8/14/2002	0797144	IT
NMXS-0354.00/IT	Utility - EPPAT	Abandoned	METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY	4/18/1996	96830216.6	3/12/2003	0802541	IT
NMXS-0355.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH ROW REDUNDANCY	4/18/1996	96830217.4	1/30/2002	0802483	IT
NMXS-0356.00/IT	Utility - EPPAT	Abandoned	REDUNDANCY MEMORY REGISTER	4/18/1996	96830215.8	2/20/2002	0802482	IT
NMXS-0357.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR TRANSFERRING REDUNDANCY DATA OF A REDUNDANCY CIRCUIT INSIDE A MEMORY DEVICE BY MEANS OF A TIME-SHARED APPROACH	6/6/1996	96830323.0	1/2/2002	0811917	IT
NMXS-0358.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH ROW AND COLUMN REDUNDANCY CIRCUITS AND A TIME-SHARED REDUNDANCY CIRCUIT TEST ARCHITECTURE.	6/6/1996	96830326.3	10/1/2003	0811988	IT
NMXS-0359.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH	6/6/1996	96830324.8	1/30/2002	0811918	IT

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MII DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0360.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY	6/6/1996	96830325.5	12/12/2001	0811919	IT
NMXS-0361.00/IT	Utility - EPPAT	Abandoned	PRE-CHARGE STEP DETERMINING CIRCUIT OF A GENERIC BIT LINE, PARTICULARLY FOR NON-VOLATILE MEMORIES	4/9/1996	96830197.8	3/10/2004	0801393	IT
NMXS-0362.00/IT	Utility - EPPAT	Abandoned	READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE	6/18/1996	96830347.9	8/27/2003	0814483	IT
NMXS-0363.00/IT	Utility - EPPAT	Abandoned	MULTILEVEL NON VOLATILE MEMORY DEVICE	8/22/1996	96830455.0	4/9/2003	0825611	IT
NMXS-0364.00/IT	Utility - EPPAT	Abandoned	CHARGE INJECTION CIRCUIT FOR AN INSULATED GATE MOS TRANSISTOR AND COMPUTING DEVICES USING THE SAME	9/30/1996	96830492.3	2/25/2004	0833267	IT
NMXS-0365.00/IT	Utility - ORG	Abandoned	ASYMMETRIC DELAY NETWORK AND PULSE GENERATOR	7/30/1996	MI96A01626	4/17/1998	1283363	IT
NMXS-0366.00/IT	Utility - EPPAT	Abandoned	CONTROL CIRCUIT OF AN OUTPUT BUFFER	9/19/1996	96830475.8	3/19/2003	0831492	IT
NMXS-0367.00/IT	Utility - EPPAT	Abandoned	PROTECTION CIRCUIT FOR REDUNDANCY REGISTER SET-UP CELLS OF ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICES	10/30/1996	96830553.2	3/19/2003	0840327	IT
NMXS-0372.00/IT	Utility - EPPAT	Abandoned	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	9/30/1996	96830494.9	4/2/2003	0833340	IT
NMXS-0375.00/IT	Utility - ORG	Abandoned	SELF-REGULATED EQUALIZER, PARTICULARLY FOR SENSE AMPLIFIERS	10/31/1996	MI96A02259	7/7/1998	1285072	IT
NMXS-0376.00/IT	Utility - ORG	Abandoned	INTEGRATED CIRCUIT FOR GENERATING INITIALIZATION SIGNALS FOR MEMORY CELL SENSING CIRCUITS	1/8/1997	MI97A00009	10/19/1998	1289863	IT
NMXS-0377.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR IMMUNIZING AN INTEGRATED CIRCUIT FROM NOISE AFFECTING ENABLE SIGNALS OF THE INTEGRATED CIRCUIT	12/31/1996	MI96A02762	10/15/1998	MI962762	IT
NMXS-0378.00/IT	Utility - ORG	Abandoned	MEMORY DEVICE WITH A MEMORY CELL MATRIX IN TRIPLE WELL TECHNOLOGY AND CORRESPONDING MANUFACTURING PROCESS	2/20/1997	MI97A00357	10/19/1998	1289933	IT
NMXS-0380.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR THE GENERATION AND RESET OF TIMING SIGNAL USED FOR READING A MEMORY DEVICE	1/8/1997	MI97A00010	10/19/1998	1289864	IT
NMXS-0381.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR SELECTIVELY ENABLING ONE AMONG A PLURALITY OF CIRCUIT ALTERNATIVES OF AN INTEGRATED CIRCUIT	10/25/1996	MI96A02210	7/7/1998	1286037	IT
NMXS-0383.00/IT	Utility - EPPAT	Abandoned	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	12/24/1996	96830649.8	5/23/2007	0851485	IT
NMXS-0385.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS	7/16/1997	97830359.2	3/23/2005	0892430	IT
NMXS-0386.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH MULTIFUNCTIONAL TERMINALS	3/28/1997	97830151.3	7/28/2004	0867885	IT
NMXS-0387.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	12/5/1996	96830612.6	7/9/2003	0833348	IT
NMXS-0388.00/IT	Utility - EPPAT	Abandoned	METHOD OF PRODUCING MOSFET TRANSISTORS BY MEANS OF TILTED IMPLANTS	4/21/1997	97830182.8	8/1/2007	0874389	IT
NMXS-0389.00/IT	Utility - EPPAT	Abandoned	METHOD FOR DATA SAVING IN CASE OF UNWANTED PROGRAMMING CYCLE INTERRUPTIONS OF A NON VOLATILE MEMORY AND NON VOLATILE MEMORY	4/30/1998	98830265.9	7/2/2003	0953984	IT
NMXS-0390.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR THE REPAIR OF FLOATING-GATE NON-VOLATILE MEMORIES DAMAGED BY PLASMA TREATMENT	12/16/1996	96830624.1	3/27/2002	0848422	IT
NMXS-0391.00/IT	Utility - EPPAT	Abandoned	VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARY FOR A NONVOLATILE MEMORY	2/28/1997	97830085.3	5/7/2003	0862183	IT
NMXS-0392.00/IT	Utility - EPPAT	Abandoned	METHOD FOR MANUFACTURING A NATIVE MOS P-CHANNEL TRANSISTOR WITH A PROCESS FOR MANUFACTURING NON-VOLATILE MEMORIES	8/27/1997	97830428.5	1/19/2005	0902466	IT
NMXS-0393.00/IT	Utility - ORG	Abandoned	DEPOSITION METHOD OF A DIELECTRIC STRUCTURE FOR PLANARIZING MEMORY DEVICES	7/16/1997	MI97A01682	3/8/1999	1293610	IT
NMXS-0407.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY WITH INTERNAL REFRESH MEANS	10/21/1997	97460043.9	8/4/1999	0838826	IT
NMXS-0410.00/IT	Utility - EPPAT	Abandoned	CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM	1/29/1997	97400209.9	10/7/1998	0788047	IT
NMXS-0412.00/IT	Utility - EPPAT	Abandoned	MEMORY WITH IMPROVED READING TIME	10/15/1997	97402429.1	12/11/2002	0838824	IT
NMXS-0416.00/IT	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY	11/21/1997	97402807.8	10/20/1999	0849740	IT
NMXS-0417.00/IT	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY	11/21/1997	97402806.0	10/20/1999	0849739	IT
NMXS-0418.00/IT	Utility - EPPAT	Abandoned	MEMORY WITH READ PROTECTED ZONES	11/28/1997	97402869.8	6/9/1999	0851359	IT

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MTI-DckNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0427.00/IT	Utility - EPPAT	Abandoned	DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY	11/5/1997	97470027.0	8/4/1999	0845787	IT
NMXS-0430.00/IT	Utility - EPPAT	Lapsed	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1998	98903102.6	5/16/2001	0954865	IT
NMXS-0433.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE WITH REDUCED POWER DISSIPATION	4/3/1997	97830160.4	7/2/2003	0869506	IT
NMXS-0434.00/IT	Utility - ORG	Abandoned	METHOD AND DEVICE FOR READING A NON VOLATILE MEMORY CELL	3/18/1997	TO97A00227	12/29/1998	1291209	IT
NMXS-0435.00/IT	Utility - ORG	Abandoned	SYNCRONIZED ATP	10/6/1998	TO98A00840			IT
NMXS-0436.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLAITLE MEMORY DEVICES	8/29/1997	97830435.0	11/12/2003	0899742	IT
NMXS-0437.00/IT	Utility - ORG	Abandoned	PROCESS FOR THE MANUFACTURING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE	8/7/1997	MI97A01902	3/24/1999	1294312	IT
NMXS-0439.00/IT	Utility - EPPAT	Abandoned	PARALLEL ANALOG PROGRAMMING OF FLASH DEVICES	5/9/1997	97830216.4	7/30/2003	0877386	IT
NMXS-0441.00/IT	Utility - ORG	Abandoned	CIRCUITRY SPACERS DEFINITION IN NON-VOLATILE MEMORIES FOR FORMING LDD IMPLANTS BY MEANS OF DIFFERENTIALLY ETCHING THE MATRIX FIELD OXXIDE WITHOUR OVERTCHING	12/29/1998	MI98A02843	3/7/2001	1304059	IT
NMXS-0442.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR READING A NON-VOLATILE MEMORY	7/20/1998	98830438.2	12/3/2003	0974976	IT
NMXS-0443.00/IT	Utility - EPPAT	Abandoned	METHOD AND DEVICE FOR ANALOG PROGRAMMING OF FLASH EEPROM WITH AUTOVERIFY	9/29/1997	97830477.2	4/23/2003	0905712	IT
NMXS-0444.00/IT	Utility - ORG	Abandoned	METHOD, PROCESS AND DEVICE FOR LOCATING POINT DEFECTS PRODUCING LEAKAGE CURRENTS IN A NON VOLATILE MEMORY DEVICE	5/21/1998	MI98A01123	6/6/2000	1301100	IT
NMXS-0445.00/IT	Utility - ORG	Abandoned	REVERSABLE CROSS REFERENCE SYSTEM	10/6/1998	TO98A00839			IT
NMXS-0447.00/IT	Utility - ORG	Abandoned	CIRCUIT AND METHOD OF READING CELLS OF AN ANALOG MEMORY ARRAY, IN PARTICULAR OF THE FLASH TYPE	7/25/1997	TO97A00667	3/8/1999	1293644	IT
NMXS-0448.00/IT	Utility - ORG	Abandoned	REDUCED CROSS-COUPLED DECODER	11/25/1999	MI99A02465	9/24/2002	1313847	IT
NMXS-0449.00/IT	Utility - EPPAT	Abandoned	INTERLEAVED ARCHITECTURE FOR PARALLEL PROGRAMMING OF FLASH DEVICES	10/28/1997	97830550.6	3/21/2007	0913835	IT
NMXS-0450.00/IT	Utility - ORG	Abandoned	A METHOD FOR MEASURING THE THICKNESS OF A SILICON LAYER DAMAGED BY PLASMA ETCHING	6/30/1998	MI98A01504	10/11/2001	1306911	IT
NMXS-0454.00/IT	Utility - EPPAT	Abandoned	DETERMINATION OF THICKNESS OF A DENUDED ZONE IN A SILICON WAFER	7/15/1997	97830354.3	9/12/2007	0898298	IT
NMXS-0456.00/IT	Utility - EPPAT	Abandoned	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	5/29/1998	98830332.7	5/19/2004	0961288	IT
NMXS-0458.00/IT	Utility - EPPAT	Abandoned	SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF	12/22/1997	97830693.4	3/2/2005	0926687	IT
NMXS-0459.00/IT	Utility - EPPAT	Abandoned	COMPENSATED VOLTAGE REGULATOR	9/30/1997	97830484.8	7/23/2003	0905710	IT
NMXS-0461.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR GENERATING AN ATD SIGNAL TO REGULATE THE ACCESS TO A NON-VOLATILE MEMORY	11/5/1997	97830576.1	3/17/2004	0915477	IT
NMXS-0462.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR REGULATING THE LENGTH OF AN ATD PULSE SIGNAL	11/5/1997	97830573.8	3/3/2004	0915476	IT
NMXS-0464.00/IT	Utility - EPPAT	Abandoned	IMPROVED OUTUPUT CIRCUIT FOR INTEGRATED CIRCUITS	10/24/1997	97830542.3	4/9/2003	0911974	IT
NMXS-0466.00/IT	Utility - EPPAT	Abandoned	HIGH VOLTAGE REGULATOR AND CORRESPONDING VOLTAGE REGULATION METHOD	11/5/1997	97830575.3	2/19/2003	0915408	IT
NMXS-0467.00/IT	Utility - ORG	Abandoned	HIGH VOLTAGE PUMP MANAGEMENT	1/30/1998	TO98A00077	6/9/2000	1301167	IT
NMXS-0468.00/IT	Utility - ORG	Abandoned	NEGATIVE VOLTAGE DISCHARGE	3/27/1998	MI98A00639	2/2/2000	1298817	IT
NMXS-0469.00/IT	Utility - ORG	Abandoned	NEGATIVE SWITCHES	3/27/1998	MI98A00641	2/2/2000	1298819	IT
NMXS-0471.00/IT	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR SINGLE-VOLTAGE MEMORY CIRCUITS, PARTICULARLY FLASH MEMORIES	11/21/1997	MI97A02594	6/25/1999	1296486	IT
NMXS-0472.00/IT	Utility - ORG	Abandoned	STABLE BIASING CIRCUIT FOR UPROM CELLS USED IN LOW POWER FLASH MEMORIES	12/19/1997	MI97A02811	8/2/1999	1296888	IT
NMXS-0473.00/IT	Utility - EPPAT	Abandoned	ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS	7/28/1998	98114051.9	9/21/2005	0928003	IT

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MTI DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0474.00/IT	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR CONTROLLING THE LENGTH OF AN ATD SIGNAL FOR TIMING THE ACCESS TO A NON-VOLATILE MEMORY	12/29/1997	MI97A002883	8/2/1999	1296908	IT
NMXS-0475.00/IT	Utility - ORG	Abandoned	DRIVER CIRCUIT WITH THREE OUTPUT LEVELS, ONE OF WHICH VOLTAGE BOOSTED	1/23/1998	MI98A000115	12/20/1999	1298186	IT
NMXS-0476.00/IT	Utility - EPPAT	Abandoned	MEMORY CELL INTEGRATED STRUCTURE AND CORRESPONDING BIASING DEVICE	4/22/1998	98830238.6	9/28/2005	0952615	IT
NMXS-0477.00/IT	Utility - ORG	Abandoned	ROW DECODER NMOS SOURCE DRIVER	3/27/1998	MI98A000638	2/2/2000	1298816	IT
NMXS-0479.00/IT	Utility - ORG	Abandoned	METHOD FOR EVALUATING AN INTEGRATED ELECTRONIC DEVICE	12/10/1997	T097A001073	7/14/1999	1296624	IT
NMXS-0481.00/IT	Utility - EPPAT	Lapsed	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	99926682.8	4/10/2002	1097454	IT
NMXS-0482.00/IT	Utility - ORG	Abandoned	NON-VOLATILE MEMORY CAPABLE OF AUTONOMOUSLY EXECUTING A PROGRAM	7/9/1998	MI98A001564	6/23/2000	1301555	IT
NMXS-0484.00/IT	Utility - EPPAT	Abandoned	CONTROLLED ERASING FOR ANALOG & MULTILEVEL STORAGE IN FLASH EEPROM DEVICE	1/22/1998	98830024.0	6/9/2004	0932161	IT
NMXS-0485.00/IT	Utility - EPPAT	Abandoned	ESD PROTECTION NETWORK ON SEMICONDUCTOR CIRCUIT STRUCTURES	12/31/1997	97830741.1	9/20/2006	0932202	IT
NMXS-0487.00/IT	Utility - EPPAT	Abandoned	HIGH STORAGE CAPACITY NON-VOLATILE MEMORY	5/27/1998	98830324.4	11/26/2003	0961287	IT
NMXS-0488.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR THE FABRICATION OF A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	6/30/1998	98830388.9	11/14/2001	0971415	IT
NMXS-0489.00/IT	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR PROGRAMMING A NON-VOLATILE MEMORY CELL WITH A SINGLE POWER SUPPLY	5/29/1998	MI98A01198	6/13/2000	1301398	IT
NMXS-0490.00/IT	Utility - ORG	Abandoned	ELECTRONIC COUNTER FOR NON-VOLATILE MEMORY DEVICES	3/6/1998	MI98A000454	1/12/2000	1298594	IT
NMXS-0494.00/IT	Utility - ORG	Abandoned	READ CIRCUIT FOR NON VOLATILE MEMORIES	10/31/1997	MI97A002458	5/28/1999	1295910	IT
NMXS-0496.00/IT	Utility - ORG	Abandoned	VERY STABLE TEMPERATURE CURRENT GENERATOR	2/5/1998	MI98A000219	1/12/2000	1298560	IT
NMXS-0497.00/IT	Utility - ORG	Abandoned	BITLINE BIASING CIRCUIT FOR EPROMS, EEPROMS AND FLASHEEPROMS APPLICATION	2/23/1998	MI98A000351	2/7/2000	1298938	IT
NMXS-0498.00/IT	Utility - ORG	Abandoned	FEEDBACK STATIC SENSE AMPLIFIER FOR EPROMS, EEPROMS AND FLASH EEPROMS APPLICATION	2/23/1998	MI98A000352	2/7/2000	1298939	IT
NMXS-0499.00/IT	Utility - ORG	Abandoned	UPROM MEMORY CELL FOR NON-VOLATILE MEMORY DEVICES	3/26/1998	MI98A000628	2/2/2000	1298807	IT
NMXS-0500.00/IT	Utility - EPPAT	Abandoned	LOW VOLTAGE NON VOLATILE MEMORY SENSE AMPLIFIER	2/13/1998	98830064.6	10/20/2004	0936627	IT
NMXS-0501.00/IT	Utility - ORG	Abandoned	BOOSTED DRIVER CIRCUIT HAVING LOW CONSUMPTION FOR A NON VOLATILE MEMORY	2/27/1998	T098A00165	7/20/2000	1302079	IT
NMXS-0502.00/IT	Utility - ORG	Abandoned	VOLTAGE PUMP CIRCUIT FOR GENERATING BOOSTED PHASES	2/27/1998	T098A00166	7/20/2000	1302080	IT
NMXS-0503.00/IT	Utility - ORG	Abandoned	VOLTAGE BOOSTING GENERATOR HAVING INCREASED DRIVE CAPABILITY	2/27/1998	T098A00167	7/20/2000	1302081	IT
NMXS-0505.00/IT	Utility - EPPAT	Abandoned	NON VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING A READ AND/OR WRITE PROTECTABLE AREA AND ELECTRONIC SYSTEM INCLUDINT IT	10/21/1998	98402620.3	6/4/2003	0918336	IT
NMXS-0507.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY	9/10/1998	98460036.1	11/15/2000	0903750	IT
NMXS-0510.00/IT	Utility - EPPAT	Abandoned	RADIO FREQUENCE SIGNAL DETECTOR FOR CONTACT-LESS SMARTCARD	9/17/1998	98402308.6	5/24/2006	0903688	IT
NMXS-0515.00/IT	Utility - ORG	Abandoned	LOW-SUPPLY ROW DECODER	6/5/1998	T098A00497	6/6/2000	1300989	IT
NMXS-0516.00/IT	Utility - EPPAT	Abandoned	DIFFERENCIAL READING OF NONVOLATILE MEMORY CELLS WITHOUT USING A REFERENCE	5/29/1998	98830338.5	12/17/2003	0961285	IT
NMXS-0518.00/IT	Utility - EPPAT	Abandoned	SENSING ARRANGEMENT FOR A MULTILEVEL SEMICONDUCTOR MEMORY DEVICE	8/7/1998	98830491.1	11/2/2005	0978844	IT
NMXS-0519.00/IT	Utility - ORG	Abandoned	NEGATIVE SWITCHES	3/27/1998	MI98A00640	2/2/2000	1298818	IT
NMXS-0520.00/IT	Utility - ORG	Abandoned	PROCESS FOR THE MANUFACTURE OF INTEGRATED DEVICES WITH GATE OXIDE PROTECTION FROM MANUFACTURING PROCESS DAMAGE, AND PROTECTION STRUCTURE THEREFOR	6/26/1998	T098A00556	6/6/2000	1301042	IT
NMXS-0521.00/IT	Utility - ORG	Abandoned	ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD	7/30/1998	MI98A01769	7/7/2000	1301880	IT
NMXS-0522.00/IT	Utility - EPPAT	Abandoned	METHOD FOR READING A MULTI-LEVEL MEMORY CELL	3/27/1998	98830188.3	11/17/2004	0945869	IT

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MII-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0523.00/IT	Utility - EPPAT	Abandoned	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	9/30/1998	98830570.2	5/6/2004	0991075	IT
NMXS-0525.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING MOS TRAMSISTORS WITH SALICIZED JUNCTIONS AND NON-SALICIZED RESISTORS	7/22/1998	98830444.0	11/2/2005	0975021	IT
NMXS-0527.00/IT	Utility - ORG	Abandoned	METHOD FOR ENHANCING SELECTIVITY BETWEEN A FILM OF A LIGHT-SENSITIVE MATERIAL AND A LAYER TO BE ETCHED IN ELECTRONIC SEMICONDUCTOR DEVICE FABRICATION PROCESSES	6/30/1998	MI98A01494	7/7/2000	1301840	IT
NMXS-0528.00/IT	Utility - ORG	Abandoned	MANUFACTURING METHOD OF SELECT TRANSISTORS OF NON VOLATILE MEMORIES WITH IMPROVED DRIVING CAPABILITY	6/12/1998	T098A00515	6/6/2000	1301007	IT
NMXS-0529.00/IT	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING N-CHANNEL AND -P-CHANNEL DV DRAIN EXTENSION TRANSISTORS BY A DIFFERENTIAL SPACER MASK IN A SALICIDE DUAL GATE	10/2/1998	MI98A02124	9/29/2000	1302589	IT
NMXS-0530.00/IT	Utility - ORG	Abandoned	FLOATING GATE MEMORIES WITH RAPID WRITING	6/26/1998	T098A00557	6/6/2000	1301043	IT
NMXS-0531.00/IT	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY WITH LOW SOURCE-LINE RESISTANCE	6/25/1998	MI98A01449	7/7/2000	1301799	IT
NMXS-0532.00/IT	Utility - EPPAT	Abandoned	A SIMPLIFIED PROCESS FOR DEFINING THE TUNNEL AREA IN SEMICONDUCTOR NON-VOLATILE NON-ALIGNED MEMORY CELLS	10/15/1998	98830614.8	2/25/2004	0994513	IT
NMXS-0533.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE WITH ROW REDUNDANCY	5/12/1999	99830286.3	7/30/2003	1052572	IT
NMXS-0537.00/IT	Utility - EPPAT	Abandoned	IMPROVED SELECTIVE SALICIZATION PROCESS FOR SEMICONDUCTOR SUBSTRATE INTEGRATED ELECTRONIC DEVICES	12/29/1998	98830793.0	10/26/2005	1017088	IT
NMXS-0538.00/IT	Utility - EPPAT	Abandoned	METHOD FOR CORRECTING ERRORS IN A MULTILEVEL MEMORY WITHOUT ADDITIONAL CELLS	2/25/1999	99830099.0	2/5/2003	1035473	IT
NMXS-0539.00/IT	Utility - EPPAT	Abandoned	MULTILEVEL NON VOLATILE MEMORY AND READING METHOD THEREFOR	2/10/1999	99830071.9	4/28/2004	1028433	IT
NMXS-0540.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT TO TEST THE VIRGIN CELLS IN A MULTILEVEL MEMORY	10/29/1998	98830654.4	8/10/2005	0997913	IT
NMXS-0541.00/IT	Utility - EPPAT	Lapsed	N-STAGE CONVERTER FOR READING/WRITING ANALOG FLASH CELLS	10/20/1998	98830626.2	1/11/2006	0997912	IT
NMXS-0542.00/IT	Utility - ORG	Abandoned	PROGRAMMING OF NON VOLATILE MEMORY CELLS WITH AUTOMATIC GENERATION OF THE PROGRAM VOLTAGE	11/13/1998	T098A00961	4/10/2001	1305181	IT
NMXS-0543.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR PARALLEL PROGRAMMING OF NONVOLATILE MEMORY CELLS WITH CONTROLLABLE PROGRAMMING SPEED	11/24/1998	T098A00990	10/30/2000	1303201	IT
NMXS-0544.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR ANALOG HIGH-PRECISION READING NON VOLATILE MEMORY CELLS	11/13/1998	T098A00962	4/10/2001	1305182	IT
NMXS-0546.00/IT	Utility - EPPAT	Abandoned	LEVELS RESTORE IN ANALOG FLASH EEPROM	9/15/1998	98830536.3	2/9/2005	0987715	IT
NMXS-0548.00/IT	Utility - ORG	Abandoned	USE OF FLASH CELLS IN REFERENCE VOLTAGE SOURCES FOR ANALOG SENSE AMPLIFIERS	10/23/1998	T098A00906	4/10/2001	1305138	IT
NMXS-0549.00/IT	Utility - ORG	Abandoned	CAPACITIVE BOOSTING CIRCUIT FOR ADJUSTING ROW READ VOLTAGE IN SEMICONDUCTOR NON VOLATILE MEMORY	1/19/1999	MI99A00081	10/11/2001	1305964	IT
NMXS-0550.00/IT	Utility - ORG	Abandoned	CAPACITIVE COMPENSATION CIRCUIT FOR ADJUSTING ROW READ VOLTAGE IN SEMICONDUCTOR NON VOLATILE MEMORY	1/19/1999	MI99A00080	10/11/2001	1305963	IT
NMXS-0553.00/IT	Utility - ORG	Abandoned	MULTIPLE LOADS VOLTAGE REGULATOR, PARTICULARLY FOR FLASH MEMORIES	12/22/1998	MI98A02787	3/7/2001	1304046	IT
NMXS-0555.00/IT	Utility - ORG	Abandoned	METHOD FOR HIGH-PRECISION PROGRAMMING OF NON VOLATILE MEMORY CELLS WITH OPTIMIZED PROGRAMMIMG SPEED	11/27/1998	T098A01003	10/30/2000	1303204	IT
NMXS-0557.00/IT	Utility - EPPAT	Abandoned	FLASH COMPATIBLE EEPROM	6/22/1999	99830390.3	2/2/2005	1057557	IT
NMXS-0559.00/IT	Utility - ORG	Abandoned	SYNCHRONOUS OUTPUT BUFFER	11/26/1999	MI99A02480	9/24/2002	1313853	IT
NMXS-0561.00/IT	Utility - EPPAT	Abandoned	IMPROVED PROCESS FOR MANUFACTURING ELECTRONIC MEMORY DEVICES WITH CELLS MATRIX HAVING VIRTUAL GROUND	2/26/1999	99830100.6	10/13/2004	1032035	IT
NMXS-0565.00/IT	Utility - EPPAT	Abandoned	METHOD FOR AUTOALIGNING OVERLAPPED LINES OF CONDUCTOR MATERIAL PROVIDED IN INTEGRATED ELECTRONIC CIRCUITS	5/31/1999	99830336.6	8/17/2005	1058304	IT
NMXS-0566.00/IT	Utility - EPPAT	Abandoned	METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE	4/21/1999	99830235.0	8/9/2006	1047078	IT

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NMXS-0568.00/IT	Utility - EPPAT	Abandoned	ESD PROTECTION DEVICE FOR SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURE	7/30/1998	98830491.9	5/26/2004	1073119	IT
NMXS-0569.00/IT	Utility - EPPAT	Abandoned	A SEMICONDUCTOR DEVICE WITH IMPROVED CHIP-LEADS INTERCONNECTIONS AND A PROCESS FOR MANUFACTURING THEREOF	2/11/1999	99830072.7	7/26/2006	1028464	IT
NMXS-0570.00/IT	Utility - EPPAT	Abandoned	READING METHOD FOR MULTILEVEL MEMORIES WITH SELECTIVE AMPLIFICATION OF CURRENT	2/26/1999	99830108.9	4/28/2004	1031991	IT
NMXS-0571.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATING FOR A CAPACITIVE LOAD	6/30/1999	99830418.2	11/12/2003	1065580	IT
NMXS-0580.00/IT	Utility - ORG	Abandoned	METHOD AND DEVICE FOR FAST ADDRESSING OF REDUNDANCY COLUMNS IN A NON VOLATILE MEMORY	4/13/1999	TO99A00289	11/14/2001	1307685	IT
NMXS-0581.00/IT	Utility - ORG	Abandoned	I/V CONVERTER IN A READING CIRCUIT, WITHOUT MAXIMUM POWER SUPPLY LIMITATION	4/13/1999	TO99A00290	11/14/2001	1307686	IT
NMXS-0582.00/IT	Utility - ORG	Abandoned	ADAPTATIVE EQUALIZATION CIRCUIT AND METHOD	4/13/1999	TO99A00291	11/14/2001	1307687	IT
NMXS-0585.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES	5/26/1999	99470014.4	11/22/2000	0962938	IT
NMXS-0591.00/IT	Utility - ORG	Abandoned	METHOD FOR ERASING AND REPROGRAMMING NON VOLATILE MEMORY CELLS IN PARTICULAR FLSH CELLS	4/23/1999	MI99A00859	4/9/2002	1312212	IT
NMXS-0592.00/IT	Utility - EPPAT	Abandoned	READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATION VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	6/21/1999	99830382.0	3/5/2003	1063654	IT
NMXS-0593.00/IT	Utility - EPPAT	Abandoned	ERASING AND PARALLEL REWRITING CIRCUIT FOR MEMORY CELL BLOCKS, PARTICULARLY FOR ANALOG FLASH CELLS, AND RELATED OPERATING METHOD	6/21/1999	99830381.2	8/9/2006	1065668	IT
NMXS-0595.00/IT	Utility - ORG	Abandoned	METHOD FOR THE READ VERIFY OF THE THRESHOLD VALUE IN NON-VOLATILE MEMORIES	5/11/1999	MI99A01017	4/17/2002	1312471	IT
NMXS-0596.00/IT	Utility - EPPAT	Abandoned	GERARCHIC SECTOR BIASING FOR FLASH MEMORIES	6/24/1999	99830396.0	11/17/2004	1063653	IT
NMXS-0597.00/IT	Utility - EPPAT	Abandoned	SYNCHRONOUS MULTILEVEL NON VOLATILE MEMORY AND RELATED READING METHOD	5/31/1999	99830331.7	3/29/2006	1058269	IT
NMXS-0598.00/IT	Utility - EPPAT	Abandoned	A READING CIRCUIT FOR A SEMICONDUCTOR MEMORY	6/25/1999	99830403.4	11/23/2005	1071094	IT
NMXS-0599.00/IT	Utility - EPPAT	Abandoned	BIASING THE DRAIN OF A MEMORY CELL DURING READING	6/4/1999	99830348.1	3/21/2007	1058270	IT
NMXS-0600.00/IT	Utility - ORG	Abandoned	DEVICE AND METHOD FOR MEASURING AN ANALOG VOLTAGE, PARTICULARLY FOR A NON VOLATILE MEMORY	7/2/1999	MI99A01474	6/17/2002	1313225	IT
NMXS-0601.00/IT	Utility - ORG	Abandoned	MEMORY ARCHITECTURE WITH LOW INTERNAL VOLTAGE REFERENCES SETTLING TIME, AND METHOD FOR GENERATING THE VOLTAGE REFERENCES	7/2/1999	MI99A01475	6/17/2002	1313226	IT
NMXS-0602.00/IT	Utility - ORG	Abandoned	LOW POWER CONSUPTION NON VOLATILE MEMORY DEVICE AND RELATED WRITING, READING AND ERASING METHODS	7/22/1999	MI99A01618	6/17/2002	1313199	IT
NMXS-0603.00/IT	Utility - EPPAT	Abandoned	METHOD FOR PROGRAMMING MULTILEVEL NON-VOLATILE MEMORIES BY APPLYING SEQUENCES OF PULSES WITHOUT VERIFY	8/3/1999	99830501.5	10/26/2006	1074995	IT
NMXS-0604.00/IT	Utility - EPPAT	Abandoned	ROW DECODER WITH REDUCED POWER CONSUMPTION DURING SWITCHING	6/4/1999	99830345.7	12/15/2004	1058271	IT
NMXS-0605.00/IT	Utility - EPPAT	Abandoned	ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE	6/17/1999	99830378.8	3/8/2006	1061525	IT
NMXS-0607.00/IT	Utility - ORG	Abandoned	SOFT PROGRAMMING METHOD FOR NON-VOLATILE MEMORY CELLS	12/14/1999	TO99A01088	3/12/2002	1311314	IT
NMXS-0609.00/IT	Utility - ORG	Abandoned	NON-VOLATILE MEMORY DEVICE AND MANUFACTURING PROCESS THEREOF	12/20/1999	MI99A02650	12/4/2002	1314142	IT
NMXS-0610.00/IT	Utility - ORG	Abandoned	BUFFER DEVICE WITH DUAL SUPPLY VOLTAGE FOR LOW SUPPLY VOLTAGE APPLICATIONS	12/13/1999	MI99A02576	12/4/2002	1314122	IT
NMXS-0613.00/IT	Utility - ORG	Abandoned	SOFT PROGRAMMING WITH CURRENT FLOW CONTROLLED BY THE BODY VOLTAGE	10/29/1999	TO99A00942			IT
NMXS-0615.00/IT	Utility - EPPAT	Abandoned	I/V CONVERTER WITH DECOUPLING MEANS FOR THE ARRAY INPUT/OUTPUT NODES	7/22/1999	99830469.5	9/24/2003	1071096	IT
NMXS-0616.00/IT	Utility - ORG	Abandoned	LOW RATE REMOVAL ETCH PROCESS IN THE MANUFACTURE OF SEMICONDUCTOR INTEGRATED DEVICES USING A DIELECTRIC FILM DEPOSITION CHAMBER	1/20/2000	MI00A00065	4/10/2003	1316286	IT

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NMXS-0618.00/IT	Utility - ORG	Abandoned	METHOD FOR REDUCING PLASMA DAMAGE	3/10/2000	TO00A00232			IT
NMXS-0620.00/IT	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR TIMING MULTI-LEVEL NON-VOLATILE MEMORIES	12/17/1999	MI99A002624	9/24/2002	1313878	IT
NMXS-0622.00/IT	Utility - ORG	Abandoned	STAIRCASE WAVEFORM GENERATOR FOR GATE VOLTAGE IN PROGRAM & VERIFY OPERATIONS	11/16/1999	TO99A00993	3/12/2002	1311440	IT
NMXS-0624.00/IT	Utility - ORG	Abandoned	SENSE AMPLIFIER WITH POSITIVE FEEDBACK AND SUBSEQUENT APPROXIMATIONS	10/29/1999	TO99A00943	1/11/2002	1308856	IT
NMXS-0625.00/IT	Utility - ORG	Abandoned	SENSE AMPLIFIER WITH CAPACITIVE SAMPLE AND HOLD	10/29/1999	TO99A00944	1/11/2002	1308857	IT
NMXS-0626.00/IT	Utility - EPPAT	Abandoned	COLUMN DECODER CIRCUIT FOR PAGE READING OF A SEMICONDUCTOR MEMORY	2/29/2000	00830149.1	1/26/2005	1130601	IT
NMXS-0627.00/IT	Utility - ORG	Abandoned	PROCESS FLOW FOR NON-VOLATILE MEMORY REALIZATION INCLUDING DIFFERENTIAL REMOVAL OF SACRIFICAL OXIDE	8/5/1999	MI99A01769	6/17/2002	1313155	IT
NMXS-0628.00/IT	Utility - ORG	Abandoned	ARCHITECTURE FOR MANAGING THE INTERNAL VOLTAGES OF A NON VOLATILE MEMORY DEVICE, ESPECIALLY FOR A DUAL WORK FLASH MEMORY WITH A SINGLE VOLTAGE SUPPLY	11/12/1999	MI99A02372	9/24/2002	1313873	IT
NMXS-0629.00/IT	Utility - ORG	Abandoned	CONTROL AND TIMING STRUCTURE FOR A MEMORY	10/6/2000	MI00A02163	9/19/2003	1318978	IT
NMXS-0632.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY WITH SINGLE SUPPLY AND HIERARCHICAL ROW DECODING	7/28/1999	99830483.6	9/21/2005	1073060	IT
NMXS-0634.00/IT	Utility - ORG	Abandoned	INTEGRATED MOS TRANSISTOR WITH A HIGH THRESHOLD VOLTAGE AND LOW MULTIPLICATION COEFFICIENT	12/17/1999	T099A01112	3/12/2002	1311325	IT
NMXS-0635.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY	9/18/2000	00830620.1	3/7/2007	1197968	IT
NMXS-0637.00/IT	Utility - ORG	Abandoned	PCH SWITCHING TRANSISTOR CONNECTED TO THE GATES OF NON-VOLATILE MEMORY CELLS	10/12/1999	TO99A00884	1/16/2002	1309102	IT
NMXS-0638.00/IT	Utility - EPPAT	Abandoned	LOW CONSUMPTION VOLTAGE BOOST DEVICE	12/30/1999	99830825.8	4/25/2007	1113450	IT
NMXS-0639.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY DEVICE WITH CONFIGURABLE ROW REDUNDANCY	2/14/2000	00830103.8	5/18/2005	1126372	IT
NMXS-0640.00/IT	Utility - ORG	Abandoned	INTEGRATED DEVICE WITH OPERATIVITY TESTING	3/3/2000	TO00A00207	11/12/2003	1319937	IT
NMXS-0641.00/IT	Utility - EPPAT	Abandoned	VOLTAGE BOOSTING DEVICE, IN PARTICULAR FOR SPEEDING POWER-UP OF MULTILEVEL NONVOLATILE MEMORIES	2/8/2000	00830088.1	1/25/2006	1124313	IT
NMXS-0642.00/IT	Utility - ORG	Abandoned	NON-VOLATILE HIGH-PERFORMANCE MEMORY DEVICE AND RELATIVE MANUFACTURING PROCESS	12/20/1999	MI99A02651	12/4/2002	1314143	IT
NMXS-0648.00/IT	Utility - EPPAT	Abandoned	LOGIC PARTITIONING OF A NONVOLATILE MEMORY ARRAY	3/28/2000	00830228.3	3/17/2004	1139210	IT
NMXS-0649.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY MATRIX ARCHITECTURE	12/14/2000	00204838.7	9/6/2006	1170798	IT
NMXS-0650.00/IT	Utility - ORG	Abandoned	RESISTIVE VOLTAGE DIVIDER FOR A STEPWISE VOLTAGE GENERATOR	11/16/1999	TO99A00994	3/12/2002	1311441	IT
NMXS-0652.00/IT	Utility - ORG	Abandoned	METHOD AND A DEVICE FOR TESTING ELECTRONIC MEMORY DEVICES	3/31/2000	MI00A00687	5/12/2003	1316870	IT
NMXS-0653.00/IT	Utility - EPPAT	Abandoned	CIRCUITAL STRUCTURE FOR PROGRAMMING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830392.7	7/25/2008	1160794	IT
NMXS-0654.00/IT	Utility - EPPAT	Abandoned	CIRCUITAL STRUCTURE FOR READING DATA IN A NON-VOLATILE MEMORY DEVICE	5/31/2000	00830393.5	12/19/2007	1160795	IT
NMXS-0655.00/IT	Utility - EPPAT	Abandoned	INTEGRATED DEVICE WITH VOLTAGE SELECTOR	3/29/2000	00830239.0			IT
NMXS-0657.00/IT	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY CELL WITH A FLOATING GATE REGION AUTOALIGNED TO THE ISOLATION AND WITH A HIGH COUPLING COEFFICIENT	7/11/2000	MI00A01567	7/23/2008	1318145	IT
NMXS-0658.00/IT	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY ARCHITECTURE	10/6/2000	MI00A02165	9/19/2003	1318979	IT
NMXS-0661.00/IT	Utility - ORG	Abandoned	CMOS TECHNOLOGY VOLTAGE BOOSTER	12/17/1999	MI99A02623	9/24/2002	1313877	IT
NMXS-0664.00/IT	Utility - ORG	Abandoned	ROW SELECTION CIRCUIT FOR FAST MEMORY DEVICES	12/21/1999	VA99A00037	7/23/2002	1313403	IT
NMXS-0666.00/IT	Utility - ORG	Abandoned	INTERLEAVED MEMORY DEVICE FOR SEQUENTIAL ACCESS SYNCHRONOUS READING WITH SIMPLIFIED ADDRESS COUNTERS	5/30/2000	VA00A00015	7/1/2004	1322978	IT
NMXS-0667.00/IT	Utility - EPPAT	Abandoned	REDUNDANCY ARCHITECTURE FOR AN INTERLEAVED MEMORY	3/2/2000	00830158.2	5/26/2004	1130517	IT

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NMXS-0670.00/IT	Utility - EPPAT	Abandoned	INTERLEAVED MEMORY DEVICE FOR BURST TYPE ACCESS IN SYNCHRONOUS READ MODE WITH THE TWO SEMI-ARRAYS INDEPENDENTLY READABLE IN RANDOM ACCESS ASYNCHRONOUS MODE	1/31/2000	00830068.3	3/30/2005	1122734	IT
NMXS-0679.00/IT	Utility - ORG	Abandoned	DISPOSITIVO SURVOLTORE BIDIREZIONALE AD ELEVATA EFFICIENZA	2/15/2000	TO00A00146	11/3/2003	1319841	IT
NMXS-0680.00/IT	Utility - EPPAT	Abandoned	CHARGE PUMP BOOSTER DEVICE WITH TRANSFER AND RECOVERY OF THE CHARGE	2/15/2000	00830105.3	5/3/2006	1158654	IT
NMXS-0683.00/IT	Utility - ORG	Abandoned	CONTROL CIRCUIT FOR A VARIABLE-VOLTAGE REGULATOR OF A NONVOLATILE MEMORY WITH HIERARCHICAL ROW DECODING	9/22/2000	TO00A00892	9/22/2003	1320666	IT
NMXS-0684.00/IT	Utility - ORG	Abandoned	CIRCUIT ARRANGEMENT FOR THE LOWERING OF THE THRESHOLD VOLTAGE OF A DIODE CONFIGURED TRANSISTOR	6/13/2000	MI00A01315	7/21/2003	1318013	IT
NMXS-0689.00/IT	Utility - ORG	Abandoned	READING CIRCUIT FOR SEMICONDUCTOR NON-VOLATILE MEMORIES	9/15/2000	MI00A02018	9/19/2003	1318892	IT
NMXS-0690.00/IT	Utility - ORG	Abandoned	MEMORIE TGRAM (THRESHOLD GAIN RANDOM ACCESS MEMORY)	11/30/2000	MI00A02593	10/20/2003	1319493	IT
NMXS-0693.00/IT	Utility - ORG	Abandoned	MULTIPURPOSE METHOD FOR CONSTRUCTING AN ERROR-CONTROL CODE FOR MULTILEVEL MEMORY CELLS OPERATING WITH A VARIABLE NUMBER OF STORAGE LEVELS, AND MULTIPURPOSE ERROR-CONTROL METHOD USING SAID ERROR-CONTROL CODE	11/7/2000	TO00A01049	12/30/2003	1321049	IT
NMXS-0694.00/IT	Utility - ORG	Abandoned	METHOD OF PULSE PROGRAMMING, IN PARTICULAR FOR HIGH-PARALLELISM MEMORY DEVICES, AND A MEMORY DEVICE IMPLEMENTING THE METHOD	10/31/2000	MI00A02367	9/23/2003	1319075	IT
NMXS-0697.00/IT	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR LOW-CONSUMPTION CIRCUITS	11/8/2000	RM00A00577	3/26/2003	1316002	IT
NMXS-0698.00/IT	Utility - ORG	Abandoned	SMALL SIZE, LOW CONSUMPTION, MULTILEVEL NONVOLATILE MEMORY	10/6/2000	TO00A00936	12/10/2003	1320699	IT
NMXS-0701.00/IT	Utility - ORG	Abandoned	CONTROL CIRCUIT FOR AN OUTPUT DRIVING STAGE OF AN INTEGRATED CIRCUIT	11/23/2000	MI00A02529	9/23/2003	1319130	IT
NMXS-0703.00/IT	Utility - ORG	Abandoned	HIERARCHIC DECODING CIRCUIT FOR SELECTING A ROW IN NON-VOLATILE MEMORY DEVICE	7/13/2000	MI00A01585	7/23/2003	1318158	IT
NMXS-0704.00/IT	Utility - EPPAT	Abandoned	ANALOG-TO-DIGITAL CONVERSION METHOD AND DEVICE, IN HIGH-DENSITY MULTILEVEL NON-VOLATILE MEMORY DEVICES	11/23/2000	00127649.2	11/15/2006	1211812	IT
NMXS-0705.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR READING NON-VOLATILE MEMORIES	10/27/2000	MI00A02337	9/23/2003	1319037	IT
NMXS-0707.00/IT	Utility - ORG	Abandoned	CONDUCTION LINE DECOUPLING CIRCUIT	7/27/2000	MI00A01729	7/28/2003	1318266	IT
NMXS-0709.00/IT	Utility - ORG	Abandoned	CAPACITANCE CURRENT TRANSDUCER FOR VERY PRECISE ON-CHIP CAPACITANCE MEASUREMENTS	12/19/2000	MI00A02755	10/20/2003	1319590	IT
NMXS-0711.00/IT	Utility - ORG	Abandoned	OUTPUT BUFFER FOR A NONVOLATILE MEMORY WITH OUTPUT SIGNAL SWITCHING NOISE REDUCTION, AND NONVOLATILE MEMORY COMPRISING THE SAME	6/1/2001	TO01A00530	12/13/2005	1331345	IT
NMXS-0712.00/IT	Utility - ORG	Abandoned	OUTPUT BUFFER FOR A NONVOLATILE MEMORY WITH OPTIMIZED SLEW-RATE CONTROL	6/1/2001	TO01A00531	12/13/2005	1331346	IT
NMXS-0713.00/IT	Utility - ORG	Abandoned	EEPROM FLASH MEMORY ERASABLE LINE BY LINE	8/30/2001	RM01A00525	9/28/2004	RM20010525	IT
NMXS-0714.00/IT	Utility - ORG	Abandoned	METHOD OF PROGRAMMING A PLURALITY OF MEMORY CELLS CONNECTED IN PARALLEL, AND A PROGRAMMING CIRCUIT THEREFOR	12/22/2000	MI00A02807	10/20/2003	1319614	IT
NMXS-0715.00/IT	Utility - ORG	Abandoned	COLUMN MULTIPLEXER FOR SEMICONDUCTOR MEMORIES	5/30/2001	MI01A01150	12/30/2004	1325839	IT
NMXS-0716.00/IT	Utility - EPPAT	Abandoned	PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL	12/13/2001	01129768.6	3/3/2004	1215679	IT
NMXS-0717.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL NONVOLATILE MEMORY CELL	1/15/2001	01830017.8	8/8/2007	1225595	IT
NMXS-0723.00/IT	Utility - ORG	Abandoned	HIGH-EFFICIENCY POWER CHARGE PUMP SUPPLYING HIGH DC OUTPUT CURRENTS	6/5/2001	TO01A00537	12/13/2005	1331350	IT
NMXS-0724.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE ELECTRICALLY ALTERABLE SEMICONDUCTOR MEMORY	1/24/2001	01830039.2	5/10/2006	1227499	IT
NMXS-0726.00/IT	Utility - EPPAT	Abandoned	METHOD FOR REFRESHING STORED DATA IN AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY	2/19/2001	01830110.1	7/11/2007	1233421	IT
NMXS-0727.00/IT	Utility - ORG	Abandoned	MEMORY WITH IMPROVED DIFFERENTIAL READING SYSTEM	6/21/2001	MI01A01311	12/30/2004	1325884	IT
NMXS-0728.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR TIMING DYNAMIC READING OF A MEMORY CELL WITH CONTROL OF THE INTEGRATION TIME	4/19/2001	01830266.1	8/15/2007	1251523	IT

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NMXS-0729.00/IT	Utility - EPPAT	Abandoned	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL AT LOW SUPPLY VOLTAGE AND WITH LOW OUTPUT DYNAMICS	2/14/2001	01830087.0	8/8/2007	1233420	IT
NMXS-0731.00/IT	Utility - ORG	Abandoned	METHOD FOR ERROR CONTROL IN MULTILEVEL CELLS WITH CONFIGURABLE NUMBER OF STORED BITS	6/1/2001	T001A00529	12/13/2005	1331344	IT
NMXS-0739.00/IT	Utility - ORG	Abandoned	OUTPUT BUFFER AND METHOD OF DRIVING	8/10/2000	IT2000VA00027	7/1/2004	VA20000027	IT
NMXS-0740.00/IT	Utility - EPPAT	Abandoned	GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD	12/27/2001	01130836.8	3/3/2004	1220448	IT
NMXS-0741.00/IT	Utility - ORG	Abandoned	BOOST DEVICE FOR NONVOLATILE MEMORIES WITH AN INTEGRATED STAND-BY CHARGE PUMP	2/16/2001	T001A00143	11/22/2005	1330501	IT
NMXS-0742.00/IT	Utility - EPPAT	Abandoned	CHARGE PUMP FOR A NONVOLATILE MEMORY WITH READ VOLTAGE REGULATION IN THE PRESENCE OF ADDRESS SKEW, AND NONVOLATILE MEMORY COMPRISING SUCH A CHARGE PUMP	2/6/2001	01830070.7			IT
NMXS-0743.00/IT	Utility - ORG	Abandoned	DEVICE AND METHOD FOR TIMING THE READING A NONVOLATILE MEMORY WITH REDUCED SWITCHING NOISE	2/20/2001	T001A00148	11/22/2005	1330504	IT
NMXS-0744.00/IT	Utility - ORG	Abandoned	DEVICE AND METHOD FOR AUTOMATICALLY GENERATING AN APPROPRIATE NUMBER OF WAIT CYCLES WHILE READING A NONVOLATILE MEMORY	4/6/2001	T001A00333	11/22/2005	1330602	IT
NMXS-0753.00/IT	Utility - EPPAT	Abandoned	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	2/14/2002	02706857.6	5/11/2005	1368784	IT
NMXS-0755.00/IT	Utility - ORG	Abandoned	METHOD OF RE-PROGRAMMING AN ARRAY OF NON-VOLATILE MEMORY CELLS, IN PARTICULAR OF THE NOR ARCHITECTURE FLASH TYPE, AFTER AN ERASE OPERATION, AND A CORRESPONDING MEMORY DEVICE	6/12/2001	MI01A01132	12/30/2004	1325852	IT
NMXS-0756.00/IT	Utility - EPPAT	Abandoned	A MEMORY DEVICE	9/27/2002	02078984.8	9/6/2006	1306852	IT
NMXS-0757.00/IT	Utility - EPPAT	Abandoned	WORD LINE SELECTOR FOR A SEMICONDUCTOR MEMORY	2/20/2002	02425084.7	7/7/2004	1339069	IT
NMXS-0760.00/IT	Utility - ORG	Abandoned	BINARY ENCODING CIRCUIT	12/24/2001	MI01A02795	7/20/2005	1328967	IT
NMXS-0762.00/IT	Utility - EPPAT	Abandoned	MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS	9/28/2001	01830614.2	3/7/2007	1298670	IT
NMXS-0763.00/IT	Utility - EPPAT	Abandoned	ELECTRICALLY-PROGRAMMABLE NON-VOLATILE MEMORY CELL	2/20/2002	02425085.4	5/14/2008	1339068	IT
NMXS-0764.00/IT	Utility - ORG	Abandoned	DECODING STRUCTURE FOR A MEMORY DEVICE WITH A CONTROL CODE	12/28/2001	MI01A02817	5/11/2005	1327316	IT
NMXS-0765.00/IT	Utility - EPPAT	Abandoned	SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON-VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD	8/5/2002	02019284.5	4/4/2007	1324344	IT
NMXS-0767.00/IT	Utility - EPPAT	Abandoned	FINITE STATE MACHINE INTERFACE HAS ARBITRATION STRUCTURE TO STORE COMMAND GENERATED BY INTERNAL CIRCUITS DURING EVALUATION PHASE OF STATE MACHINE FOR FLASH EEPROM DEVICE	12/4/2001	01830744.7	8/17/2005	1318440	IT
NMXS-0770.00/IT	Utility - EPPAT	Abandoned	ARCHITECTURE FOR A FLASH-EEPROM SIMULTANEOUSLY READABLE IN OTHER SECTORS WHILE ERASING AND/OR PROGRAMMING ONE OR MORE SECTORS	1/11/2002	02425009.4	3/30/2005	1327992	IT
NMXS-0771.00/IT	Utility - EPPAT	Lapsed	FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE	10/25/2001	01830671.2	10/3/2007	1308964	IT
NMXS-0773.00/IT	Utility - ORG	Abandoned	MEMORY SYSTEM COMPRISING A SEMICONDUCTOR MEMORY	12/12/2002	MI02A02629	9/6/2007	1340823	IT
NMXS-0781.00/IT	Utility - ORG	Abandoned	HIGH SPEED VOLTAGE REGULATOR FOR CAPACITIVE LOAD	7/9/2003	MI03A01403			IT
NMXS-0782.00/IT	Utility - EPPAT	Abandoned	SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF	2/20/2002	02425088.8	9/12/2007	1339103	IT
NMXS-0783.00/IT	Utility - EPPAT	Abandoned	CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS	2/20/2002	02425089.6	5/9/2007	1339111	IT
NMXS-0784.00/IT	Utility - EPPAT	Abandoned	BASIC STAGE FOR A CHARGE PUMP CIRCUIT	3/29/2002	02425199.3	11/9/2005	1349264	IT
NMXS-0787.00/IT	Utility - ORG	Abandoned	ADJUSTABLE FREQUENCY OSCILLATOR WITH PROGRAMMABLE CALIBRATING CIRCUIT AND RELATED SYSTEM AND METHOD	4/2/2002	T002A00288	1/25/2007	1337445	IT
NMXS-0788.00/IT	Utility - EPPAT	Abandoned	TEST STRUCTURE FOR THE MEASUREMENT OF CONTACT TO GATE DISTANCE IN NON-VOLATILE MEMORY DEVICES AND CORRESPONDING TEST METHOD	5/31/2002	02425360.1	8/3/2005	1367597	IT

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NMXS-0789.00/IT	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING ELECTRONIC CIRCUITS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE	5/2/2002	MI02A00931	4/11/2007	1339091	IT
NMXS-0792.00/IT	Utility - EPPAT	Abandoned	CIRCUIT FOR CONTROLLING A REFERENCE NODE IN A SENSE AMPLIFIER	12/28/2001	01830817.1	10/27/2004	1324347	IT
NMXS-0793.00/IT	Utility - ORG	Abandoned	NONVOLATILE MEMORY DEVICE WITH DOUBLE SERIAL/PARALLEL COMMUNICATION INTERFACE	10/16/2001	VA01A00035	11/22/2005	1330856	IT
NMXS-0795.00/IT	Utility - ORG	Abandoned	MEMORY DEVICE AND METHOD FOR READING SEQUENTIALLY GROUPS OF BITS FROM A MEMORY DEVICE	2/8/2002	VA02A00012			IT
NMXS-0796.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE OUTPUTTING READ DATA IN A TIME STARTING FROM A RISING EDGE OF AN EXTERNAL CLOCK THAT IS SHORTER THAN THAT OF KNOWN DEVICES	12/20/2001	01830782.7	2/27/2008	1324346	IT
NMXS-0797.00/IT	Utility - ORG	Abandoned	DEVICE INTEGRATING A NONVOLATILE MEMORY ARRAY AND A VOLATILE MEMORY ARRAY	2/8/2002	TO02A00118	1/16/2007	1337302	IT
NMXS-0798.00/IT	Utility - ORG	Abandoned	METHOD OF WRITING A GROUP OF DATA BYTES IN A MEMORY AND MEMORY DEVICE	2/21/2002	VA02A00016	10/11/2006	1335568	IT
NMXS-0799.00/IT	Utility - EPPAT	Lapsed	NONVOLATILE STORAGE DEVICE AND SELF-REDUNDANCY METHOD FOR THE SAME	8/13/2002	02425529.1	10/10/2007	1394810	IT
NMXS-0800.00/IT	Utility - EPPAT	Abandoned	BUILT-IN TESTING METHODOLOGY IN FLASH MEMORY	2/27/2003	03425126.4	6/28/2006	1453062	IT
NMXS-0810.00/IT	Utility - ORG	Abandoned	NON-VOLATILE LATCH CIRCUIT	5/10/2002	MI02A00984	4/20/2007	1339270	IT
NMXS-0811.00/IT	Utility - EPPAT	Abandoned	METHOD FOR REDUCING SPURIOUS ERASING DURING PROGRAMMING OF A NONVOLATILE NROM	4/30/2002	02425273.6	7/5/2006	1359591	IT
NMXS-0813.00/IT	Utility - EPPAT	Abandoned	REGULATION METHOD FOR THE SOURCE TERMINAL VOLTAGE IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT	8/30/2002	02019433.8	3/14/2007	1331644	IT
NMXS-0814.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR FORMING TRENCHES WITH OBLIQUE PROFILE AND ROUNDED TOP CORNERS	6/28/2002	02425428.6	3/7/2007	1376683	IT
NMXS-0816.00/IT	Utility - ORG	Abandoned	VOLTAGE REGULATOR WITH VERY QUICK RESPONSE	6/28/2002	TO02A00566	2/20/2007	1337891	IT
NMXS-0817.00/IT	Utility - EPPAT	Abandoned	ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF	10/8/2002	02425605.9	12/27/2006	1408550	IT
NMXS-0818.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS	10/8/2002	02425604.2	3/7/2007	1408549	IT
NMXS-0820.00/IT	Utility - EPPAT	Abandoned	SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE, AND NONVOLATILE MEMORY DEVICE	4/25/2002	02425265.2	6/14/2006	1357559	IT
NMXS-0823.00/IT	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING A BYTE SELECTION TRANSISTOR FOR A MATRIX OF NON VOLATILE MEMORY CELLS AND CORRESPONDING STRUCTURE	11/20/2002	MI02A02467	9/5/2007	1340698	IT
NMXS-0824.00/IT	Utility - ORG	Abandoned	ION-IMPLANTATION MACHINE, CONTROL METHOD THEREOF, AND PROCESS FOR MANUFACTURING INTEGRATED DEVICES	9/10/2002	TO02A00787	2/27/2007	1338111	IT
NMXS-0826.00/IT	Utility - ORG	Lapsed	METHOD OF PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	12/5/2002	MI02A02589	9/25/2007	1341313	IT
NMXS-0827.00/IT	Utility - ORG	Lapsed	A CIRCUIT FOR PROGRAMMING A NON-VOLATILE MEMORY DEVICE WITH ADAPTIVE PROGRAM LOAD CONTROL	11/12/2002	MI02A02387	9/5/2007	1340663	IT
NMXS-0828.00/IT	Utility - EPPAT	Abandoned	SINGLE CELL ERASING METHOD FOR RECOVERING MEMORY CELLS UNDER PROGRAMMING DISTURBS IN NON VOLATILE SEMICONDUCTOR MEMORY DEVICES	11/28/2002	02425727.1	8/3/2005	1424700	IT
NMXS-0831.00/IT	Utility - ORG	Abandoned	PROCESS FOR SELF ALIGNED MANUFACTURE OF INTEGRATED ELECTRONIC DEVICES	11/15/2002	TO02A00897	2/27/2007	1338236	IT
NMXS-0832.00/IT	Utility - ORG	Abandoned	VOLTAGE BOOST DEVICE AND MEMORY SYSTEM	7/5/2002	MI02A01486	5/22/2007	1339564	IT
NMXS-0832.01/IT	Utility - EPPAT	Abandoned	VOLTAGE BOOST DEVICE AND MEMORY SYSTEM	7/4/2003	03425442.5	5/10/2006	1378913	IT
NMXS-0834.00/IT	Utility - ORG	Lapsed	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	12/18/2002	MI02A02669	9/6/2008	1340858	IT

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NMXS-0834.01/IT	Utility - EPPAT	Abandoned	STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY	12/16/2003	03104709.5	2/28/2007	1435574	IT
NMXS-0838.00/IT	Utility - ORG	Abandoned	NON-VOLATILE MEMORY DEVICE WITH IMPROVED SEQUENTIAL PROGRAMMING SPEED	12/18/2002	MI02A02668	9/6/2007	1340857	IT
NMXS-0839.00/IT	Utility - ORG	Abandoned	MEMORY DEVICE COMPOSED OF A PLURALITY OF MEMORY CHIPS IN A SINGLE PACKAGE	12/4/2002	VA02A00067	10/11/2006	1335602	IT
NMXS-0840.00/IT	Utility - ORG	Abandoned	NONVOLATILE MEMORY DEVICE WITH SIMULTANEOUS READ/WRITE	11/29/2002	T002A01035	2/27/2007	1338265	IT
NMXS-0843.00/IT	Utility - ORG	Abandoned	PROGRAMMING METHOD FOR NON VOLATILE MULTILEVEL MEMORY CELLS AND CORRESPONDING PROGRAMMING CIRCUIT	11/28/2002	MI02A02531	9/6/2007	1340748	IT
NMXS-0846.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR MANUFACTURING A MEMORY DEVICE HAVING SELECTOR TRANSISTORS FOR STORAGE ELEMENTS AND MEMORY DEVICE FABRICATED THEREBY	5/7/2003	03425292.4	7/19/2006	1475840	IT
NMXS-0847.00/IT	Utility - ORG	Abandoned	DRIVING CIRCUIT FOR A MEMORY MATRIX LINE SELECTOR AND SYSTEM EMPLOYING THE CIRCUIT	4/30/2003	MI03A00886			IT
NMXS-0848.00/IT	Utility - ORG	Abandoned	PROCESS FOR THE FORMATION OF DIELECTRIC ISOLATION STRUCTURES IN SEMICONDUCTOR DEVICES	5/26/2003	RM03A00255	12/19/2007	1343457	IT
NMXS-0850.00/IT	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTOR SUBSTRATE	12/30/2002	MI02A02784	9/6/2007	1340941	IT
NMXS-0851.00/IT	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTOR SUBSTRATE	12/30/2002	MI02A02785	9/6/2007	1340942	IT
NMXS-0853.00/IT	Utility - EPPAT	Abandoned	METHOD FOR DETECTING A RESISTIVE PATH OR A PREDETERMINED POTENTIAL IN NON-VOLATILE MEMORY ELECTRONIC DEVICES	9/30/2002	02425593.7	5/23/2007	1403880	IT
NMXS-0855.00/IT	Utility - ORG	Lapsed	SEMICONDUCTOR MEMORY WITH EMBEDDED DRAM	11/20/2002	MI02A02464	9/5/2007	1340858	IT
NMXS-0856.00/IT	Utility - ORG	Abandoned	SEMICONDUCTOR INTEGRATED CIRCUIT	5/30/2003	MI03A01102			IT
NMXS-0859.00/IT	Utility - EPPAT	Abandoned	METHOD FOR GENERATING A REFERENCE CURRENT FOR SENSE AMPLIFIERS AND CORRESPONDING GENERATOR	6/4/2003	03425353.4	8/16/2006	1484764	IT
NMXS-0860.00/IT	Utility - ORG	Abandoned	METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY	12/5/2002	MI02A02570	9/25/2007	1341314	IT
NMXS-0862.00/IT	Utility - ORG	Abandoned	SENSE AMPLIFIER FOR LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS	2/18/2003	T003A00121	1/23/2008	0001343782	IT
NMXS-0863.00/IT	Utility - EPPAT	Abandoned	VOLTAGE SUPPLY DISTRIBUTION ARCHITECTURE FOR A PLURALITY OF MEMORY MODULES	12/30/2002	02425809.7	7/11/2007	1435621	IT
NMXS-0865.00/IT	Utility - ORG	Lapsed	PARALLEL SENSE AMPLIFIER WITH MIRRORING OF THE CURRENT BE MEASURED INTO EACH REFERENCE BRANCH	1/20/2003	MI03A00075			IT
NMXS-0866.00/IT	Utility - ORG	Abandoned	METHOD FOR THE FABRICATION OF ISOLATION STRUCTURES	8/1/2003	MI03A01591			IT
NMXS-0867.00/IT	Utility - ORG	Abandoned	ELEKTONENSPEKTROSKOP MIT EMISSION, DIE DURCH EINEN MONOCHROMATISCHEN ELEKTRONENSTRAHL INDUZIERT WIRD	10/7/2003	VA03A00037			IT
NMXS-0869.00/IT	Utility - ORG	Abandoned	MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL-POLYSILICON LAYER TECHNOLOGY	12/24/2002	T002A01119	2/27/2007	1338319	IT
NMXS-0870.00/IT	Utility - ORG	Abandoned	MOS DEVICE AND A PROCESS FOR MANUFACTURING MOS DEVICES USING A DUAL-POLYSILICON LAYER TECHNOLOGY WITH SIDE CONTACT	12/24/2002	T002A01118	2/27/2007	1338318	IT
NMXS-0872.00/IT	Utility - EPPAT	Abandoned	METHOD FOR READING A NONVOLATILE MEMORY DEVICE AND NONVOLATILE MEMORY DEVICE IMPLEMENTING THE READING METHOD	4/10/2003	03425224.7	11/28/2007	1467377	IT
NMXS-0874.00/IT	Utility - ORG	Abandoned	DEVICE AND METHOD FOR READING NON-VOLATILE MEMORIES HAVING AT LEAST ONE PSEUDO-PARALLEL COMMUNICATION INTERFACE	5/31/2002	MI02A01185	4/20/2007	1339350	IT
NMXS-0875.00/IT	Utility - ORG	Abandoned	AUTOMATIC DECODING METHOD FOR MAPPING AND SELECTING A NON-VOLATILE MEMORY DEVICE HAVING A LPC SERIAL COMMUNICATION INTERFACE IN THE AVAILABLE ADDRESSING AREA ON MOTHERBOARDS	7/18/2002	MI02A01583	5/22/2007	1339634	IT
NMXS-0876.00/IT	Utility - ORG	Lapsed	STRUCTURE FOR UPDATING A BLOCK OF MEMORY CELLS IN A FLASH MEMORY DEVICE WITH ERASE AND PROGRAM OPERATION REDUCTION	10/16/2002	MI02A02192			IT

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NMXS-0877.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATION SYSTEM FOR A MULTIWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY					IT
NMXS-0878.00/IT	Utility - EPPAT	Abandoned	GATE VOLTAGE REGULATION SYSTEM FOR A NON-VOLATILE MEMORY CELLS PROGRAMMING AND/OR SOFT PROGRAMMING PHASE	2/28/2003	03425134.8	10/12/2005	1453059	IT
NMXS-0879.00/IT	Utility - ORG	Abandoned	METHOD FOR SOFT-PROGRAMMING AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, AND AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE IMPLEMENTING THE SOFT-PROGRAMMING METHOD	2/17/2003	T003A000115	1/23/2008	0001318782	IT
NMXS-0880.00/IT	Utility - ORG	Abandoned	MEMORY DEVICE ACCESSIBLE WITH DIFFERENT COMMUNICATION PROTOCOLS	9/6/2002	VA02A00045	10/11/2006	1335586	IT
NMXS-0882.00/IT	Utility - EPPAT	Abandoned	FAST PAGE PROGRAMMING ARCHITECTURE AND METHOD IN A NON-VOLATILE MEMORY DEVICE WITH AN SPI INTERFACE	12/30/2002	02425802.2	9/20/2006	1435624	IT
NMXS-0892.00/IT	Utility - EPPAT	Abandoned	WORD-PROGRAMMABLE FLASH MEMORY	5/26/2004	04012393.7	4/9/2008	1486986	IT
NMXS-0894.00/IT	Utility - ORG	Abandoned	CHARGE PUMP CIRCUIT WITH A BRIEF SETTLING TIME AND HIGH OUTPUT VOLTAGE REGULATION PRECISION	11/5/2003	RM03A00512	1/23/2008	1343673	IT
NMXS-0896.00/IT	Utility - ORG	Lapsed	EXPLOITING A STATISTICAL DISTRIBUTION OF THE VALUES OF AN ELECTRICAL CHARACTERISTIC IN A POPULATION OF AUXILIARY MEMORY CELLS FOR OBTAINING REFERENCE CELLS	12/23/2004	MI04A02462			IT
NMXS-0897.00/IT	Utility - ORG	Lapsed	SENSE AMPLIFIER WITH EQUALIZER	8/6/2003	MI03A01619			IT
NMXS-0898.00/IT	Utility - ORG	Abandoned	METHOD FOR REDUCING DEFECTS AFTER A METAL ETCHING IN SEMICONDUCTOR DEVICES	12/12/2003	MI03A02444			IT
NMXS-0908.00/IT	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/28/2004	MI04A002533			IT
NMXS-0909.00/IT	Utility - ORG	Abandoned	PROCESS FOR DEFINING INTEGRATED CIRCUITS IN SEMICONDUCTOR ELECTRONIC DEVICES	11/17/2004	MI04A02206			IT
NMXS-0912.00/IT	Utility - EPPAT	Abandoned	AN IMPROVED PAGE BUFFER FOR A PROGRAMMABLE MEMORY DEVICE	6/24/2004	04102942.2	12/19/2007	1610343	IT
NMXS-0917.00/IT	Utility - ORG	Abandoned	READ/VERIFY CIRCUIT FOR MULTILEVEL MEMORY CELLS WITH RAMP READ VOLTAGE, AND READ/VERIFY METHOD THEREOF	7/8/2004	T004000470			IT
NMXS-0920.00/IT	Utility - EPPAT	Abandoned	REDUNDANCY BASED NAND FLASH MEMORY	7/14/2004	04103384.9	10/25/2006	1617438	IT
NMXS-0924.00/IT	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING ELECTRONIC NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE	12/28/2004	MI04A002532			IT
NMXS-0928.00/IT	Utility - ORG	Abandoned	INTEGRATED ELECTRONIC DEVICE HAVING A LOW VOLTAGE ELECTRIC SUPPLY	4/11/2005	MI05A000607			IT
NMXS-0939.00/IT	Utility - ORG	Abandoned	SENSE AMPLIFIER FOR READING A CELL OF A NON-VOLATILE MEMORY DEVICE	5/4/2004	VA04A00021			IT
NMXS-0940.00/IT	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR VERIFYING AND EVENTUALLY SUBSTITUTING DEFECTIVE REFERENCE CELLS OF A MEMORY	5/4/2004	VA04A00019			IT
NMXS-0941.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR SELECTING/DESELECTING A BITLINE OF A NON-VOLATILE MEMORY	5/4/2004	VA04A00020			IT
NMXS-0942.00/IT	Utility - ORG	Lapsed	FLASH MEMORY DEVICE WITH NAND ARCHITECTURE WITH REDUCED CAPACITIVE COUPLING EFFECT	6/5/2003	MI03A01126			IT
NMXS-0943.00/IT	Utility - EPPAT	Lapsed	METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE, AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD	6/14/2004	04425435.7	8/15/2007	1607984	IT
NMXS-0944.00/IT	Utility - EPPAT	Abandoned	ROW DECODER FOR NAND MEMORIES	8/11/2004	04425626.1	2/21/2007	1626413	IT
NMXS-0945.00/IT	Utility - ORG	Abandoned	METHOD OF GENERATING AN ENABLE SIGNAL OF A STANDARD MEMORY CORE AND RELATIVE MEMORY DEVICE	7/7/2003	VA03A00022			IT
NMXS-0946.00/IT	Utility - ORG	Lapsed	INTEGRATED MEMORY DEVICE WITH MULTI-SECTOR SELECTION COMMANDS	11/6/2003	MI03A02134			IT
NMXS-0947.00/IT	Utility - ORG	Lapsed	SYNCHRONOUS MEMORY DEVICE WITH REDUCED POWER CONSUMPTION	5/25/2004	MI04A01038			IT
NMXS-0949.00/IT	Utility - EPPAT	Abandoned	MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD	6/30/2004	04291653.6	8/15/2007	1508901	IT

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NMXS-0950.00/IT	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY	12/8/2004	04029018.1	4/11/2007	1542130	IT
NMXS-0952.00/IT	Utility - EPPAT	Abandoned	SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION	12/8/2004	04029016.5	5/30/2007	1542233	IT
NMXS-0954.00/IT	Utility - ORG	Abandoned	ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING A CNAND STRUCTURE AND BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2005	MI05A000608			IT
NMXS-0957.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE	10/15/2004	04105094.9	9/19/2007	1647991	IT
NMXS-0958.00/IT	Utility - ORG	Abandoned	CHARGE-PUMP DEVICE WITH INCREASED CURRENT OUTPUT	11/11/2004	TO04A00791			IT
NMXS-0959.00/IT	Utility - ORG	Pending	INTEGRATED ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING NAND STRUCTURE	4/11/2005	MI05A000609			IT
NMXS-0961.00/IT	Utility - EPPAT	Abandoned	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2005	05425209.3	12/12/2007	1713084	IT
NMXS-0963.00/IT	Utility - ORG	Abandoned	PROGRAMMING METHOD OF MULTILEVEL MEMORIES AND CORRESPONDING CIRCUIT	10/29/2004	MI04A02071			IT
NMXS-0964.00/IT	Utility - ORG	Lapsed	MEMORY DEVICE	10/15/2004	MI04A01957			IT
NMXS-0965.00/IT	Utility - EPPAT	Abandoned	MEMORY DEVICE AND METHOD OF OPERATING THE SAME WITH HIGH REJECTION OF THE NOISE ON THE HIGH-VOLTAGE SUPPLY LINE	10/8/2004	04425754.1	3/5/2008	1646051	IT
NMXS-0966.00/IT	Utility - ORG	Abandoned	ELECTRONIC MEMORY DEVICE HAVING HIGH DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE INTERFERENCE CELL-TO-CELL	12/14/2004	MI04A02373			IT
NMXS-0968.00/IT	Utility - ORG	Abandoned	ROW DECODER CIRCUIT AND RELATED SYSTEM AND METHOD	5/13/2005	MI05A000868			IT
NMXS-0969.00/IT	Utility - ORG	Abandoned	NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR	4/11/2005	MI05A000610			IT
NMXS-0972.00/IT	Utility - ORG	Abandoned	REMOVABLE DATA STORAGE DEVICE AND RELATED ASSEMBLING METHOD	1/31/2005	MI05A000139			IT
NMXS-0974.00/IT	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	11/19/2004	MI04A02241			IT
NMXS-0974.01/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL	11/18/2005	05025286.5	10/3/2007	1670002	IT
NMXS-0986.00/IT	Utility - ORG	Abandoned	ELECTRONIC MEMORY DEVICE HAVING HIGH INTEGRATION DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE COUPLING	12/14/2004	MI04A002374			IT
NMXS-0990.00/IT	Utility - ORG	Abandoned	CONTROL OF VOLTAGES DURING ERASE AND RE-PROGRAM OPERATIONS OF MEMORY CELLS	1/18/2005	VA05A000001			IT
NMXS-0991.00/IT	Utility - EPPAT	Abandoned	DEVICE FOR AUTOMATICALLY OPENING AND CLOSING CASH CONTAINER	1/28/2005	05100551.0	1/9/2008	1686591	IT
NMXS-0993.00/IT	Utility - ORG	Abandoned	DATA STORING METHOD FOR A NON-VOLATILE MEMORY CELL ARRAY HAVING AN ERROR CORRECTION CODE	4/29/2005	MI05A000780			IT
NMXS-0996.00/IT	Utility - ORG	Abandoned	METHOD OF MANAGING FAILS IN A NON-VOLATILE MEMORY DEVICE AND RELATIVE MEMORY DEVICE	11/8/2005	VA05A000061			IT
NMXS-0998.00/IT	Utility - ORG	Lapsed	FLASH MEMORY DEVICE WITH IMPROVED MANAGEMENT OF PROTECTION INFORMATION	5/11/2005	MI05A000838			IT
NMXS-0999.00/IT	Utility - EPPAT	Abandoned	NAND FLASH MEMORY WITH ERASE VERIFY BASED ON SHORTER DELAY BEFORE SENSING	7/28/2005	05105976.3	4/23/2008	1752989	IT
NMXS-1003.00/IT	Utility - ORG	Abandoned	NON VOLATILE MEMORY DEVICE ARCHITECTURE AND CORRESPONDING PROGRAMMING METHOD	3/31/2006	MI06A000627			IT
NMXS-1005.00/IT	Utility - ORG	Abandoned	MEMORY DEVICE AND RELATIVE CONTROL METHOD	2/22/2006	VA06A000011			IT
NMXS-1006.00/IT	Utility - ORG	Abandoned	RAMP GENERATOR AND RELATIVE ROW DECODER FOR FLASH MEMORY DEVICE	5/3/2005	VA05A000028			IT
NMXS-1007.00/IT	Utility - ORG	Lapsed	ROW SELECTOR WITH REDUCED AREA OCCUPATION FOR SEMICONDUCTOR MEMORY DEVICES	2/9/2006	MI06A000220			IT
NMXS-1011.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR GENERATING AN INTERNAL ENABLING SIGNAL FOR AN OUTPUT BUFFER OF A MEMORY	1/20/2005	VA05A00002			IT
NMXS-1014.00/IT	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR SIMULTANEOUSLY PROGRAMMING MEMORY CELLS	4/13/2005	VA05A000024			IT
NMXS-1016.00/IT	Utility - EPPAT	Abandoned	SEQUENTIAL PROGRAM-VERIFY METHOD WITH RESULT BUFFERING	3/30/2004	04101301.2	8/1/2007	1583102	IT

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MTI-DocketNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1020.00/IT	Utility - ORG	Abandoned	FLASH MEMORY DEVICE WITH A LOW PIN COUNT (LPC) COMMUNICATION INTERFACE	10/29/2004	MIMA02077			IT
NMXS-1025.00/IT	Utility - ORG	Abandoned	READING METHOD OF A NON-VOLATILE ELECTRONIC DEVICE AND CORRESPONDING DEVICE	5/26/2006	MI06A001037			IT
NMXS-1026.00/IT	Utility - ORG	Abandoned	MEMORY ARCHITECTURE	9/2/2005	MI05A001628			IT
NMXS-1027.00/IT	Utility - ORG	Abandoned	Unknown Title	9/13/2005	MI05A001679			IT
NMXS-1040.00/IT	Utility - ORG	Lapsed	READING CIRCUIT FOR SEMICONDUCTOR MEMORY	5/5/2006	MI06A000880			IT
NMXS-1042.00/IT	Utility - ORG	Lapsed	TEST CARTRIDGE WITH INTERNAL GENERATION OF THE TEST SIGNALS	12/22/2006	MI06A002467			IT
NMXS-1046.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY DEVICE WITH A PAGE BUFFER HAVING AN IMPROVED LAYOUT ARRANGEMENT	7/28/2005	05106973.0	5/14/2008	1748443	IT
NMXS-1048.00/IT	Utility - ORG	Abandoned	SYNCHONIZATION OF OPERATIONS IN DISTINCT MEMORY PARTITIONS	3/14/2006	VA06A000014			IT
NMXS-1050.00/IT	Utility - ORG	Abandoned	OPTIMIZED FLASH MEMORY ACCESS METHOD AND DEVICE	4/13/2006	MI06A000746			IT
NMXS-1052.00/IT	Utility - ORG	Abandoned	METHOD AND CIRCUITRY FOR PROGRAMMING A MEMORY CELL, IN PARTICULAR OF THE FLASH NOR TYPE	4/17/2007	MI07A000777			IT
NMXS-1055.00/IT	Utility - ORG	Lapsed	STRUCTURE AND METHOD TO OBTAIN A FAST PROGRAM NAND DEVICE	5/18/2007	MI07A001012			IT
NMXS-1058.00/IT	Utility - ORG	Abandoned	Process for manufacturing an electronic device integrated on semiconductor substrate comprising non volatile floating gate memories and an associated circuitry and corresponding electronic device	2/14/2007	MI07A000270			IT
NMXS-1065.00/IT	Utility - ORG	Abandoned	Process for manufacturing integrated circuits formed on a semiconductor substrate and comprising tungsten layers	3/6/2007	MI07A000446			IT
NMXS-1067.00/IT	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE	12/9/2005	MI05A002350			IT
NMXS-1072.00/IT	Utility - ORG	Issued	VOLTAGE REGULATOR MADE OF HIGH VOLTAGE TRANSISTORS	12/5/2006	VA06A000071	4/26/2010	1373831	IT
NMXS-1073.00/IT	Utility - ORG	Abandoned	Unknown Title	5/14/2007	MI07A000970			IT
NMXS-1075.00/IT	Utility - ORG	Abandoned	ELECTRONIC DEVICE COMPRISING NON VOLATILE MEMORY CELLS WITH OPTIMIZED PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD	3/28/2006	MI06A000585			IT
NMXS-1077.00/IT	Utility - ORG	Lapsed	PLASMA DEPOSITION PROCESS WITH VARIABLE PROCESS PARAMETERS	11/27/2006	MI06A002271			IT
NMXS-1089.00/IT	Utility - ORG	Pending	METHOD OF MANAGING A MULTILEVEL MEMORY DEVICE AND RELATED DEVICE	4/27/2007	VA07A000042			IT
NMXS-1090.00/IT	Utility - ORG	Issued	METHOD OF MANAGING A MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS	3/2/2007	IT2007VA000026	9/20/2010	VA20070026	IT
NMXS-1091.00/IT	Utility - ORG	Issued	MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS AND RELATED METHODS OF MANAGING	11/3/2006	IT2006VA000065	4/26/2010	VA20060065	IT
NMXS-1097.00/IT	Utility - ORG	Lapsed	NON-VOLATILE MEMORY CIRCUIT, SYSTEM, AND METHOD	4/17/2007	MI07A000787			IT
NMXS-1104.00/IT	Utility - ORG	Abandoned	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	10/23/1984	198423283	12/14/1989	1213230	IT
NMXS-1105.00/IT	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	12/20/1985	198523323	11/26/1987	1186485	IT
NMXS-1106.00/IT	Utility - ORG	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	6/3/1986	198683628	3/23/1988	1191561	IT
NMXS-1107.00/IT	Utility - ORG	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	7/10/1986	198683630	2/2/1989	1201834	IT
NMXS-1108.00/IT	Utility - ORG	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	5/7/1987	198720420	2/14/1990	1215403	IT
NMXS-1109.00/IT	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/21/1987	198723134	9/19/1990	1223571	IT
NMXS-1110.00/IT	Utility - ORG	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/29/1988	198819254	7/12/1990	1221780	IT
NMXS-1111.00/IT	Utility - ORG	Abandoned	CMOS VOLTAGE MULTIPLIER	6/28/1988	198883645	6/27/1990	1221261	IT
NMXS-1112.00/IT	Utility - ORG	Abandoned	CMOS LOGIC CIRCUIT FOR HIGH VOLTAGE OPERATION	7/6/1988	198883646	11/22/1990	1225607	IT
NMXS-1113.00/IT	Utility - ORG	Abandoned	FABRICATION OF CMOS DEVICES WITH REDUCED GATE LENGTH	7/29/1988	198883653	11/22/1990	1225612	IT
NMXS-1114.00/IT	Utility - ORG	Abandoned	FABRICATION OF CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTH AND LIGHTLY DOPED DRAIN	8/4/1988	198883655	11/22/1990	1225614	IT

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XTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS 1115.00/IT	Utility - ORG	Abandoned	GRIPPER FOR THE ADVANTAGEOUSLY ROBOTIZED HANDLING OF ONE OR MORE SILICON WAFERS AND/OR OF A SUPPORT FOR SUCH WAFERS	12/20/1988	198823081	5/28/1991	1228105	IT
NMXS-1116.00/IT	Utility - ORG	Abandoned	PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	12/28/1988	198883691	11/22/1990	1225638	IT
NMXS-1117.00/IT	Utility - ORG	Abandoned	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/14/1989	198922683	6/18/1993	01237894	IT
NMXS-1118.00/IT	Utility - ORG	Abandoned	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	2/16/1990	19900083604	11/17/1994	1246238	IT
NMXS-1119.00/IT	Utility - ORG	Abandoned	READING CIRCUIT FOR NONVOLATILEMEMORY CELL.	2/13/1990	19900083607	11/17/1994	1246241	IT
NMXS-1120.00/IT	Utility - ORG	Abandoned	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	3/30/1990	19900019903	10/27/1993	1239989	IT
NMXS-1121.00/IT	Utility - ORG	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	4/26/1990	19900083617	12/28/1994	1247640	IT
NMXS-1122.00/IT	Utility - ORG	Expired	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	4/27/1990	19900020157	11/27/1993	1240012	IT
NMXS-1123.00/IT	Utility - ORG	Abandoned	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	7/6/1990	19900020877	7/8/1994	1244293	IT
NMXS-1124.00/IT	Utility - EPPAT	Abandoned	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	10/1/1990	90830428.0	4/28/2001	0478871	IT
NMXS-1125.00/IT	Utility - ORG	Abandoned	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	10/2/1990	19900021626	6/28/1994	1243803	IT
NMXS-1126.00/IT	Utility - ORG	Abandoned	TWO PHASES SCAN PATH WITH SINGLECLOCK.	10/22/1990	19900021820	11/17/1994	1246301	IT
NMXS-1127.00/IT	Utility - EPPAT	Abandoned	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	11/19/1990	90830529.5	2/19/1997	0487808	IT
NMXS-1128.00/IT	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/19/1990	90830530.3	5/8/1996	0486743	IT
NMXS-1129.00/IT	Utility - EPPAT	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/13/1990	90830583.2	5/1/1996	0491105	IT
NMXS-1130.00/IT	Utility - ORG	Abandoned	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/28/1990	19900022569	11/26/1994	1246755	IT
NMXS-1131.00/IT	Utility - ORG	Abandoned	MEMORY CELL READING CIRCUIT	12/28/1990	19900022568	11/26/1994	1246754	IT
NMXS-1132.00/IT	Utility - ORG	Abandoned	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	5/10/1991	VA91A00012	3/28/1995	1249809	IT
NMXS-1133.00/IT	Utility - ORG	Abandoned	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	7/25/1991	VA91A00020	8/22/1995	1253676	IT
NMXS-1134.00/IT	Utility - ORG	Abandoned	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	8/30/1991	VA91A00026	8/22/1995	1253679	IT
NMXS-1135.00/IT	Utility - ORG	Abandoned	ROW DECODER FOR NAND-TYPE ROM	8/30/1991	VA91A00027	8/22/1995	1253680	IT
NMXS-1136.00/IT	Utility - ORG	Abandoned	PLANARIZED CONTACT WITH A SANDWICH OF TUNGSTEN AND ALUMINIUM.	11/22/1991	MI91A03121	5/29/1995	1252056	IT
NMXS-1137.00/IT	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	11/29/1991	TO91A00929	4/3/1995	1250233	IT
NMXS-1138.00/IT	Utility - ORG	Abandoned	DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER	11/29/1991	VA91A00042	8/22/1995	1253598	IT
NMXS-1139.00/IT	Utility - EPPAT	Abandoned	METALLIZATION OVER TUNGSTEN PLUGS	5/27/1992	92830265.2	9/18/1996	0571691	IT
NMXS-1140.00/IT	Utility - EPPAT	Abandoned	LOW SWITCHING NOISE OUTPUT BUFFER	6/26/1992	92830335.3	10/31/2001	0585505	IT
NMXS-1141.00/IT	Utility - EPPAT	Abandoned	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	6/30/1992	92830339.5	9/13/1995	0576773	IT
NMXS-1142.00/IT	Utility - EPPAT	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	6/30/1992	92830340.3	9/15/1999	0576774	IT
NMXS-1143.00/IT	Utility - EPPAT	Abandoned	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	9/30/1992	92830541.6	12/2/1998	0591598	IT
NMXS-1144.00/IT	Utility - EPPAT	Abandoned	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	10/1/1992	92830552.3	5/27/1998	0575688	IT
NMXS-1145.00/IT	Utility - EPPAT	Abandoned	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	10/29/1992	92830589.5	7/28/1999	0594920	IT

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MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-1146.00/IT	Utility - EPPAT	Abandoned	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	11/18/1992	92830625.7	5/28/1997	0598168	IT
NMXS-1147.00/IT	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	1/29/1993	93830031.6	5/5/1999	0608664	IT
NMXS-1148.00/IT	Utility - EPPAT	Abandoned	METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS	1/29/1993	93830032.4	1/7/1998	0608665	IT
NMXS-1149.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS	2/11/1993	93830050.6	9/10/1997	0610643	IT
NMXS-1150.00/IT	Utility - EPPAT	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830057.1	7/30/1997	0613176	IT
NMXS-1151.00/IT	Utility - EPPAT	Abandoned	NONVOLATILE EPROM, EEPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	2/17/1993	93830058.9	10/13/1999	0614223	IT
NMXS-1152.00/IT	Utility - EPPAT	Abandoned	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	3/18/1993	93830108.0	6/23/1999	0616332	IT
NMXS-1153.00/IT	Utility - EPPAT	Abandoned	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	3/18/1993	93830110.8	6/23/1999	0616333	IT
NMXS-1154.00/IT	Utility - EPPAT	Abandoned	SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS	3/31/1993	93830128.0	7/22/1998	0618587	IT
NMXS-1155.00/IT	Utility - EPPAT	Abandoned	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	4/1/1993	93830134.8	7/28/1999	0595775	IT
NMXS-1157.00/IT	Utility - NSPCT	Abandoned	METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/9/1992	92402777.4	3/4/1998	0537082	IT
NMXS-0001.00/JP	Utility - ORG	Expired	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/14/1988	19880316074	3/27/1998	2761501	JP
NMXS-0002.00/JP	Utility - ORG	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/22/1988	19880324766	5/28/1999	2931864	JP
NMXS-0003.00/JP	Utility - ORG	Expired	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/26/1989	19890107141	8/25/2000	3101697	JP
NMXS-0004.00/JP	Utility - ORG	Issued	INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE	7/26/1993	19930208599	2/21/2003	3398722	JP
NMXS-0005.00/JP	Utility - ORG	Abandoned	DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS	8/2/1993	19930209895			JP
NMXS-0006.00/JP	Utility - ORG	Abandoned	VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR	10/1/1993	19930269566			JP
NMXS-0007.00/JP	Utility - ORG	Abandoned	POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY CUTS FOR INTEGRATED CIRCUIT	12/22/1993	19930346107	2/6/2004	3520103	JP
NMXS-0008.00/JP	Utility - ORG	Abandoned	SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY	5/22/1987	19870125619			JP
NMXS-0009.00/JP	Utility - ORG	Abandoned	NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	8/3/1988	19880194287	9/19/1997	2696769	JP
NMXS-0010.00/JP	Utility - ORG	Abandoned	NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY	8/3/1988	19880194288	6/23/2000	3080624	JP
NMXS-0011.00/JP	Utility - ORG	Abandoned	CONTENT ADDRESSABLE MEMORY	5/31/1991	19910228111			JP
NMXS-0012.00/JP	Utility - ORG	Abandoned	REDUNDANCY FOR SERIAL MEMORY	1/10/1991	19910012378			JP
NMXS-0013.00/JP	Utility - ORG	Abandoned	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	4/25/1991	19910095055	5/12/2000	3064472	JP
NMXS-0014.00/JP	Utility - ORG	Abandoned	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	11/26/1990	19900318162	7/21/2000	3090330	JP
NMXS-0015.00/JP	Utility - ORG	Abandoned	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/17/1991	19910269786	6/1/2001	3195808	JP
NMXS-0016.00/JP	Utility - ORG	Abandoned	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	9/28/1990	19900022575	6/30/2000	3083145	JP

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Mtr-DktgNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0017.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/16/1991	19910206007	5/25/2001	3192173	JP
NMXS-0018.00/JP	Utility - ORG	Abandoned	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	7/11/1991	19910171385			JP
NMXS-0019.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	7/11/1991	19910170287			JP
NMXS-0020.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/16/1991	19910205847	3/9/2001	3167359	JP
NMXS-0020.01/JP	Utility - DIV	Expired	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	10/18/2000	2000-0317923	11/12/2004	3616564	JP
NMXS-0021.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/16/1991	19910205887	12/10/1999	3012710	JP
NMXS-0022.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/25/1991	19910245443			JP
NMXS-0023.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/25/1991	19910245446			JP
NMXS-0024.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/16/1991	19910205972	9/29/2000	3115036	JP
NMXS-0025.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/21/1991	19910272222			JP
NMXS-0026.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/25/1991	19910245454			JP
NMXS-0027.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/25/1991	19910245525			JP
NMXS-0028.00/JP	Utility - ORG	Expired	ADDRESS BUFFER CIRCUIT HAVING LATCHING BASED ON TRANSITION	10/21/1991	19910272191	11/29/2002	3375143	JP
NMXS-0029.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH PRECHARGED REDUNDANCY MULTIPLEXING	12/13/1991	19910330259	8/17/2001	3221900	JP
NMXS-0030.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH COLUMN DECODED BIT LINE EQUILIBRATE	12/11/1991	19910327250			JP
NMXS-0031.00/JP	Utility - ORG	Expired	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/13/1991	19910330242	10/22/2004	3609837	JP
NMXS-0032.00/JP	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/13/1991	19910330892			JP
NMXS-0033.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR	7/17/1992	19920189788			JP
NMXS-0034.00/JP	Utility - ORG	Abandoned	CONTROL CIRCUIT FOR RESETTING A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY	5/1/1992	19920112597			JP
NMXS-0035.00/JP	Utility - ORG	Abandoned	CONTROL CIRCUIT FOR DUAL PORT MEMORY	4/28/1992	19920110528			JP
NMXS-0036.00/JP	Utility - ORG	Abandoned	CACHE TAG PARITY DETECT CIRCUIT	3/27/1992	19920071734			JP
NMXS-0037.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS	7/17/1992	19920190414			JP
NMXS-0038.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT DUAL-PORT MEMORY DEVICE HAVING REDUCED CAPACITANCE	7/17/1992	19920190422			JP
NMXS-0039.00/JP	Utility - ORG	Abandoned	SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS	1/21/1993	19930008061			JP
NMXS-0040.00/JP	Utility - ORG	Abandoned	VIRTUAL GROUND READ ONLY MEMORY CIRCUIT	11/29/1993	19930298411			JP
NMXS-0041.00/JP	Utility - ORG	Abandoned	READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE	12/16/1992	19920336254			JP
NMXS-0042.00/JP	Utility - ORG	Abandoned	TRISTATABLE DRIVER FOR INTERNAL DATA BUS LINES	12/17/1992	19920336481			JP
NMXS-0043.00/JP	Utility - ORG	Abandoned	MULTIPLEXING SENSE AMPLIFIER	3/31/1994	19940063610			JP
NMXS-0045.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS	12/17/1992	19920336495			JP
NMXS-0046.00/JP	Utility - ORG	Issued	REDUNDANCY DECODER	2/1/1993	19930014481	9/17/2004	3598119	JP
NMXS-0047.00/JP	Utility - ORG	Abandoned	COLUMN REDUNDANCY ARCHITECTURE FOR A READ/WRITE MEMORY	2/1/1993	19930514568			JP
NMXS-0048.00/JP	Utility - ORG	Abandoned	SELECTIVE BULK WRITE OPERATION	4/7/1993	19930580761			JP
NMXS-0049.00/JP	Utility - ORG	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR	4/30/1993	19930104270	1/9/2004	3509894	JP
NMXS-0050.00/JP	Utility - ORG	Abandoned	PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE	4/30/1993	19930104305	1/23/2004	3515591	JP
NMXS-0051.00/JP	Utility - ORG	Abandoned	PARALLELIZED BORROW LOOK AHEAD SUBTRACTOR	3/31/1993	19930572683	8/1/2003	3457696	JP

PATENT
REEL: 030872 FRAME: 0231

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MU-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0052.00/JP	Utility - ORG	Abandoned	PARALLELIZED DIFFERENCE FLAG LOGIC	5/31/1993	19930127675			JP
NMXS-0053.00/JP	Utility - ORG	Abandoned	SERIALIZED DIFFERENCE FLAG CIRCUIT	6/21/1993	19930149514			JP
NMXS-0057.00/JP	Utility - ORG	Abandoned	INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS	11/2/1993	19930274564			JP
NMXS-0058.00/JP	Utility - ORG	Abandoned	STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE	11/12/1993	19930283673			JP
NMXS-0059.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT OUTPUT DRIVER	8/30/1993	19930214448			JP
NMXS-0062.00/JP	Utility - ORG	Abandoned	DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY	12/22/1993	19930325000			JP
NMXS-0064.00/JP	Utility - ORG	Abandoned	MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR	2/21/1994	19940622814	1/30/2004	3517442	JP
NMXS-0065.00/JP	Utility - ORG	Abandoned	STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS	9/22/1993	19930236648			JP
NMXS-0066.00/JP	Utility - ORG	Abandoned	SLEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY	8/30/1993	19930214463			JP
NMXS-0067.00/JP	Utility - ORG	Abandoned	TEMPERATURE-COMPENSATED VOLTAGE LEVEL SENSE CIRCUIT	4/28/1994	19940092055			JP
NMXS-0068.00/JP	Utility - ORG	Abandoned	ADDRESS BUFFER	4/28/1994	19940092353			JP
NMXS-0069.00/JP	Utility - ORG	Abandoned	METHOD FOR STRESS TESTING DECODERS AND PERIPHERY CIRCUITS	4/28/1994	19940092222			JP
NMXS-0072.00/JP	Utility - ORG	Abandoned	REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING SUBSTITUTION OF REDUNDANT ELEMENTS	8/1/1994	19940179913			JP
NMXS-0073.00/JP	Utility - ORG	Abandoned	TEMPERATURE-STABLE CURRENT SOURCE	6/13/1995	19950170389	12/3/1997	2684600	JP
NMXS-0074.00/JP	Utility - ORG	Abandoned	PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE	5/31/1994	19940139620			JP
NMXS-0075.00/JP	Utility - ORG	Abandoned	VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY	9/30/1994	19940238117			JP
NMXS-0076.00/JP	Utility - ORG	Abandoned	PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES	8/29/1994	19940203659			JP
NMXS-0077.00/JP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED STORAGE DEVICE	11/29/1994	19940294882	3/11/1997	2617095	JP
NMXS-0078.00/JP	Utility - ORG	Abandoned	CIRCUIT FOR COVERING INITIAL CONDITIONS WHEN STARTING-UP AN INTEGRATED CIRCUIT DEVICE	1/31/1995	19950714027	11/19/1999	3005169	JP
NMXS-0079.00/JP	Utility - ORG	Issued	METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE	11/21/1994	19940286349	11/14/1997	2718902	JP
NMXS-0080.00/JP	Utility - ORG	Abandoned	REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE	12/6/1994	19940302219	12/5/1996	2589458	JP
NMXS-0081.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER	11/29/1994	19940294881	6/12/1998	2791285	JP
NMXS-0082.00/JP	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING REDUNDANLY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND ROW REDUNDANCY INTEGRATED CIRCUITRY	2/17/1995	19950029439	6/12/1998	2791288	JP
NMXS-0083.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE	12/8/1994	19940304900	12/19/1996	2591922	JP
NMXS-0084.00/JP	Utility - ORG	Abandoned	REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE	3/28/1995	19950069258	1/9/1997	2599579	JP
NMXS-0085.00/JP	Utility - ORG	Issued	CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT	1/17/1995	19950020895	2/6/1998	2743853	JP
NMXS-0086.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE MEMORY OUTPUT DATA	2/20/1995	19950053776	8/8/1997	2682502	JP
NMXS-0087.00/JP	Utility - ORG	Abandoned	INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES	2/16/1995	19950050384	12/10/1999	3011042	JP
NMXS-0088.00/JP	Utility - ORG	Abandoned	LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES	2/15/1995	19950049302			JP
NMXS-0090.00/JP	Utility - ORG	Abandoned	END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES	12/28/1994	19940337494			JP
NMXS-0091.00/JP	Utility - ORG	Abandoned	VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT	12/28/1994	19940337463	4/25/1997	2638533	JP
NMXS-0092.00/JP	Utility - ORG	Abandoned	BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES	12/2/1994	19940323985	4/18/1997	2630284	JP
NMXS-0093.00/JP	Utility - ORG	Abandoned	READING CIRCUIT FOR AN INTEGRATED SEMICONDUCTOR MEMORY DEVICE	3/22/1995	19950062793	6/8/2001	3198027	JP
NMXS-0094.00/JP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX	11/30/1994	19940297004	12/5/1997	2726395	JP
NMXS-0095.00/JP	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY	1/27/1995	19950011663			JP

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MII DktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0096.00/JP	Utility - ORG	Abandoned	THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS	3/29/1995	19950071861			JP
NMXS-0097.00/JP	Utility - ORG	Abandoned	CIRCUIT FOR IDENTIFYING A MEMORY CELL HAVING ERRONEOUS DATA STORED THEREIN	8/31/1995	19950223517			JP
NMXS-0098.00/JP	Utility - ORG	Abandoned	DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE	1/4/1995	19950000117			JP
NMXS-0099.00/JP	Utility - ORG	Abandoned	STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT	11/30/1994	19940297646	5/30/1997	2656911	JP
NMXS-0100.00/JP	Utility - ORG	Abandoned	REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS	2/21/1995	19950056569	8/14/1998	2815819	JP
NMXS-0101.00/JP	Utility - ORG	Abandoned	CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	1/4/1995	19950000118	9/11/1997	2619615	JP
NMXS-0102.00/JP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS	1/4/1995	19950000119	10/16/1998	2839849	JP
NMXS-0103.00/JP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES	12/27/1994	19940325653	12/26/1997	2733029	JP
NMXS-0104.00/JP	Utility - ORG	Abandoned	INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY	12/27/1994	19940325112	7/8/1996	2540028	JP
NMXS-0105.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES	2/20/1995	19950053777	1/16/1998	2737686	JP
NMXS-0106.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES	2/14/1995	19950047962	7/18/1997	2674550	JP
NMXS-0107.00/JP	Utility - ORG	Abandoned	MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH	4/13/1995	19950088428	7/18/1997	2675277	JP
NMXS-0108.00/JP	Utility - ORG	Abandoned	FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME	3/28/1995	19950093229	10/31/1997	2713217	JP
NMXS-0109.00/JP	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY	2/15/1995	19950026642	12/5/1996	2588692	JP
NMXS-0110.00/JP	Utility - ORG	Abandoned	REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS	3/28/1995	19950069425	12/22/2000	3141102	JP
NMXS-0111.00/JP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES	12/27/1994	19940325654	12/26/1997	2733030	JP
NMXS-0112.00/JP	Utility - ORG	Abandoned	DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR	4/28/1994	19940092324			JP
NMXS-0113.00/JP	Utility - ORG	Abandoned	STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY	4/22/1994	19940084740			JP
NMXS-0114.00/JP	Utility - ORG	Abandoned	STRUCTURE FOR DESELECTIVE BROKEN SELECT LINES IN MEMORY ARRAYS	5/30/1994	19940116982			JP
NMXS-0115.00/JP	Utility - ORG	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	6/30/1994	19940149633			JP
NMXS-0117.00/JP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY	6/30/1994	19940149644			JP
NMXS-0118.00/JP	Utility - ORG	Abandoned	CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS	6/30/1994	19940149626			JP
NMXS-0124.00/JP	Utility - ORG	Abandoned	VARIABLE IMPEDANCE DELAY ELEMENTS	8/1/1994	19940179938			JP
NMXS-0128.00/JP	Utility - ORG	Abandoned	REDUNDANT LINE DECODER MASTER ENABLE	9/30/1994	19940236334			JP
NMXS-0129.00/JP	Utility - ORG	Abandoned	STRUCTURE TO UTILIZE A PARTIALLY FUNCTIONAL CACHE MEMORY BY INVALIDATION OF FAULTY CACHE MEMORY LOCATIONS	11/1/1994	19940268621			JP
NMXS-0130.00/JP	Utility - ORG	Abandoned	LATCH CONTROLLED OUTPUT DRIVER	9/30/1994	19940236207	2/27/2004	3526921	JP
NMXS-0131.00/JP	Utility - ORG	Abandoned	EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS	9/30/1994	19940236332			JP
NMXS-0132.00/JP	Utility - ORG	Abandoned	DATA COMPARING SENSE AMPLIFIER	12/22/1994	19940319683			JP
NMXS-0138.00/JP	Utility - ORG	Issued	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING	11/24/1994	1994-314029	11/21/1997	2720013	JP
NMXS-0139.00/JP	Utility - ORG	Abandoned	RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE	5/30/1994	19940139468			JP
NMXS-0140.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT	10/28/1994	19940289226			JP
NMXS-0141.00/JP	Utility - ORG	Abandoned	LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES	12/22/1994	19940336259			JP
NMXS-0142.00/JP	Utility - ORG	Issued	MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME	12/22/1994	19940336258	2/12/1999	2886472	JP

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NM-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0143.00/JP	Utility - ORG	Abandoned	METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES	1/30/1996	330201995			JP
NMXS-0144.00/JP	Utility - ORG	Abandoned	BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL	2/28/1995	647451995			JP
NMXS-0145.00/JP	Utility - ORG	Abandoned	MEMORY REDUNDANCY CIRCUIT	2/28/1995	647441995			JP
NMXS-0146.00/JP	Utility - ORG	Issued	INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT	3/31/1995	19950099561	4/23/1999	2919299	JP
NMXS-0147.00/JP	Utility - ORG	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT	1/31/1995	345311995			JP
NMXS-0148.00/JP	Utility - ORG	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT	1/31/1995	345301995			JP
NMXS-0149.00/JP	Utility - ORG	Abandoned	NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT	1/31/1995	345291995			JP
NMXS-0150.00/JP	Utility - ORG	Abandoned	SWITCHING REGULATOR WITH DYSSYMETRICAL DIFFERENTIAL INPUT STAGE	4/21/1995	19950139852			JP
NMXS-0151.00/JP	Utility - ORG	Abandoned	VOLTAGE BOOSTER CIRCUIT	4/21/1995	19950139854			JP
NMXS-0152.00/JP	Utility - ORG	Abandoned	METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF	4/13/1995	19950112348			JP
NMXS-0153.00/JP	Utility - ORG	Lapsed	CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT	2/23/1995	58726/95	10/2/1998	2833646	JP
NMXS-0154.00/JP	Utility - ORG	Abandoned	ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS	4/10/1995	19950109068	2/20/1998	2748335	JP
NMXS-0155.00/JP	Utility - ORG	Abandoned	PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS	7/20/1995	19950206516	10/23/1998	2843006	JP
NMXS-0156.00/JP	Utility - ORG	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	3/31/1995	19950099565			JP
NMXS-0156.01/JP	Utility - DIV	Abandoned	MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY	6/10/1998	19980161912			JP
NMXS-0157.00/JP	Utility - ORG	Abandoned	METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE	6/6/1995	19950139435			JP
NMXS-0158.00/JP	Utility - ORG	Abandoned	PROGRAMMABLE MEMORY ELEMENT	3/30/1995	19950773084			JP
NMXS-0159.00/JP	Utility - ORG	Abandoned	SENSE AMPLIFIER WITH HYSTERESIS	5/8/1995	19950135884			JP
NMXS-0160.00/JP	Utility - ORG	Abandoned	HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS	4/7/1995	19950082353			JP
NMXS-0161.00/JP	Utility - ORG	Abandoned	PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS	12/21/1995	19950333640			JP
NMXS-0162.00/JP	Utility - ORG	Issued	FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE	6/12/1995	19950145034	9/30/2005	3725581	JP
NMXS-0163.00/JP	Utility - ORG	Abandoned	METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL	7/12/1995	19950197943	1/21/2000	3024519	JP
NMXS-0164.00/JP	Utility - ORG	Issued	MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE	9/29/1995	254046/95	7/29/2005	3704184	JP
NMXS-0165.00/JP	Utility - ORG	Abandoned	SENSE AMPLIFIER CIRCUIT FOR SEMICONDUCTOR MEMORY DEVICES	4/23/1996	19960101177	7/21/2000	3091687	JP
NMXS-0166.00/JP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES	11/30/1995	19950312721			JP
NMXS-0169.00/JP	Utility - ORG	Abandoned	READING CIRCUIT FOR MEMORY CELLS	8/31/1995	19950223553			JP
NMXS-0170.00/JP	Utility - ORG	Abandoned	SYNCHRONIZATION DEVICE FOR OUTPUT STAGES, PARTICULARLY FOR ELECTRONIC MEMORIES	11/17/1995	19950299737			JP
NMXS-0173.00/JP	Utility - ORG	Abandoned	OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES	5/17/1996	19960123422			JP
NMXS-0174.00/JP	Utility - ORG	Abandoned	PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL	1/25/1996	19960831346			JP
NMXS-0177.00/JP	Utility - ORG	Abandoned	BYTE ERASABLE EEPROM FULLY COMPATIBLE WITH A SINGLE POWER SUPPLY FLASH-EPROM PROCESS	9/27/1995	19950274935			JP

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MIT-DCRNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0182.00/JP	Utility - ORG	Issued	A PROCESS FOR MANUFACTURING A MOS INTEGRATED CIRCUIT HAVINGCOMPONENTS WITH DIFFERENT DIELECTRICS	3/17/1996	19960054682	5/19/2000	3068454	JP
NMXS-0183.00/JP	Utility - ORG	Abandoned	METHOD FOR IMPROVING THE PROFILE OF THE INTERMEDIATE DIELECTRIC, PARTICULARLY FOR NON VOLATILE MEMORIES	2/13/1997	19970028874			JP
NMXS-0185.00/JP	Utility - ORG	Abandoned	VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS	4/12/1996	19960091312	8/6/1999	2963047	JP
NMXS-0188.00/JP	Utility - ORG	Abandoned	METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES	2/28/1995	19950040880			JP
NMXS-0189.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING	3/30/1995	19950072706			JP
NMXS-0190.00/JP	Utility - ORG	Issued	INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION	3/31/1995	19950074338	7/9/2004	3573372	JP
NMXS-0194.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS	5/31/1995	19950133243			JP
NMXS-0199.00/JP	Utility - ORG	Abandoned	PRE-CHARGED EXCLUSIONARY WIRED-CONNECTED PROGRAMMED REDUNDANT SELECT	9/29/1995	19950253509			JP
NMXS-0202.00/JP	Utility - ORG	Abandoned	CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES	10/31/1995	19950283572			JP
NMXS-0205.00/JP	Utility - ORG	Abandoned	CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE	12/14/1995	19950326060			JP
NMXS-0206.00/JP	Utility - ORG	Abandoned	OUTPUT DRIVER CIRCUITRY WITH LIMITED OUTPUT HIGH VOLTAGE	12/19/1995	19950330283			JP
NMXS-0207.00/JP	Utility - ORG	Issued	VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE	12/19/1995	19950330189	5/20/2005	3679178	JP
NMXS-0208.00/JP	Utility - ORG	Abandoned	OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE	12/20/1995	19950332286			JP
NMXS-0209.00/JP	Utility - ORG	Issued	ADJUSTABLE CURRENT SOURCE	12/20/1995	19950331983	9/17/2004	3596637	JP
NMXS-0214.00/JP	Utility - ORG	Issued	INTERNAL BUS CONTROL(FLASH MEMORY DEVICE TEST MODE TO DRIVE AN INTERNAL CONTROLBUS EXTERNALLY)	8/28/1995	19950218004	3/12/1999	2898230	JP
NMXS-0216.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM	12/21/1995	19950349885	1/29/1998	2880678	JP
NMXS-0217.00/JP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY	9/12/1995	19950259289	10/27/2000	3124713	JP
NMXS-0218.00/JP	Utility - ORG	Abandoned	CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM	5/9/1996	19960139400			JP
NMXS-0219.00/JP	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY	12/20/1995	19950354549	7/24/1998	2807203	JP
NMXS-0220.00/JP	Utility - ORG	Abandoned	CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD	6/6/1996	19960166739			JP
NMXS-0221.00/JP	Utility - ORG	Abandoned	RESISTANCE REFERENCE CIRCUIT	12/22/1995	19950354651	12/25/1998	2868716	JP
NMXS-0223.00/JP	Utility - ORG	Abandoned	SERIAL DICHOTOMIC METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT IMPLEMENTING SUCH METHOD	1/29/1996	19960013104			JP
NMXS-0224.00/JP	Utility - ORG	Abandoned	READING CIRCUIT FOR MULTILEVEL NON VOLATILE MEMORY CELL DEVICES	3/29/1996	19960076043			JP
NMXS-0226.00/JP	Utility - ORG	Issued	SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT	3/22/1996	19960066710	12/4/1998	2857649	JP
NMXS-0227.00/JP	Utility - ORG	Abandoned	READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE	4/30/1996	19960109179			JP
NMXS-0232.00/JP	Utility - ORG	Abandoned	NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES	6/19/1996	19960157779			JP
NMXS-0233.00/JP	Utility - ORG	Abandoned	PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT	9/30/1996	19960259923			JP
NMXS-0234.00/JP	Utility - ORG	Abandoned	METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL	7/12/1996	19960183432			JP
NMXS-0241.00/JP	Utility - ORG	Issued	REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS	3/27/1997	19970075469	12/8/2006	3889110	JP

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MH-DCKtNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0242.00/JP	Utility - ORG	Issued	TIME SHARING INTERNATIONAL BUS, PARTICULARLY FOR NON VOLATILE MEMORIES	3/13/1997	19970059519	3/16/2007	3930937	JP
NMXS-0261.00/JP	Utility - ORG	Issued	MULTI-LEVEL MEMORY CIRCUITS AND CORRESPONDING READING AND WRITING METHODS	1/31/1997	19970018819	12/22/2006	3894380	JP
NMXS-0262.00/JP	Utility - NSPCT	Issued	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	199805026367	9/7/2007	4007457	JP
NMXS-0263.00/JP	Utility - ORG	Issued	CLOCK CIRCUIT FOR READING A MULTILEVEL NON VOLATILE MEMORY CELLS DEVICE	6/27/1997	19970172303	9/29/2006	3859820	JP
NMXS-0264.00/JP	Utility - NSPCT	Issued	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	199805026377	6/15/2007	3958400	JP
NMXS-0265.00/JP	Utility - ORG	Issued	SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY	3/19/1997	19970086172	6/22/2007	3974680	JP
NMXS-0266.00/JP	Utility - ORG	Abandoned	ELECTRICALLY ERASABLE AND PROGRAMMABLE NON VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS	5/9/1997	19970119434			JP
NMXS-0269.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR GENERATING A SYNCHRONIZING ATD SIGNAL	11/27/1997	19970325809			JP
NMXS-0272.00/JP	Utility - ORG	Abandoned	METHOD FOR ERASING AN ELECTRICALLY PROGRAMMABLE AND ERASABLE NON-VOLATILE MEMORY CELL	1/21/1997	19970008449			JP
NMXS-0274.00/JP	Utility - ORG	Abandoned	PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS	6/2/1997	19970143880			JP
NMXS-0276.00/JP	Utility - ORG	Pending	PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE	1/30/1998	19980018490			JP
NMXS-0287.00/JP	Utility - ORG	Abandoned	CONSTANT CURRENT SOURCE WITH REDUCED SENSITIVITY TO SUPPLY VOLTAGE AND PROCESS VARIATION	3/8/1996	19960051914			JP
NMXS-0289.00/JP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE	4/1/1996	19960078703			JP
NMXS-0291.00/JP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR BIASING BIT LINES	5/28/1996	19960133360			JP
NMXS-0292.00/JP	Utility - ORG	Abandoned	REDUCED PIN COUNT STRESS TEST CIRCUIT FOR INTEGRATED MEMORY DEVICES AND METHOD THEREFOR	5/31/1996	19960138847			JP
NMXS-0293.00/JP	Utility - ORG	Issued	FAULT DETECTION FOR ENTIRE WAFER STRESS TEST	7/30/1996	19960200145	1/12/2007	3901246	JP
NMXS-0299.00/JP	Utility - ORG	Abandoned	REDUNDANCY ARCHITECTURE	12/27/1996	19960349572			JP
NMXS-0300.00/JP	Utility - ORG	Abandoned	TEST MODE ACTIVATION AND DATA OVERRIDE	1/16/1997	19970095455			JP
NMXS-0301.00/JP	Utility - ORG	Abandoned	PIPELINED CHIP ENABLE CONTROL CIRCUITRY AND METHODOLOGY	1/16/1997	19970095496			JP
NMXS-0302.00/JP	Utility - ORG	Abandoned	OUTPUT DRIVER CIRCUITRY HAVING A SINGLE SLEW RATE RESISTOR	1/16/1997	19970095528			JP
NMXS-0303.00/JP	Utility - ORG	Abandoned	REDUNDANCY CONTROL	12/27/1996	19960349643			JP
NMXS-0307.00/JP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR TRACKING THE START OF A WRITE TO A MEMORY CELL	1/17/1997	19970096024			JP
NMXS-0308.00/JP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL	1/17/1997	19970096236			JP
NMXS-0309.00/JP	Utility - ORG	Abandoned	CLOCKED SENSE AMPLIFIER WITH WORDLINE TRACKING	1/17/1997	19970096266			JP
NMXS-0311.00/JP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR SETTING THE TIME DURATION OF A WRITE TO A MEMORY CELL	1/17/1997	19970096721			JP
NMXS-0312.00/JP	Utility - ORG	Abandoned	LOW-POWER READ CIRCUIT AND METHOD FOR CONTROLLING A SENSE AMPLIFIER	1/17/1997	19970096800			JP
NMXS-0314.00/JP	Utility - ORG	Issued	CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES	8/23/1996	19960222282	1/12/2007	3901250	JP
NMXS-0315.00/JP	Utility - ORG	Abandoned	ENTIRE WAFER STRESS TEST METHOD FOR INTEGRATED MEMORY DEVICES AND CIRCUIT THEREFOR	8/21/1996	19960219954			JP
NMXS-0316.00/JP	Utility - ORG	Issued	METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES	3/29/1996	19960104190	12/12/1997	2727527	JP
NMXS-0317.00/JP	Utility - ORG	Abandoned	PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OR NEGATIVE SUPPLY CIRCUIT	5/23/1996	19960151655			JP
NMXS-0323.00/JP	Utility - ORG	Abandoned	FLASH-EPROM WITH EMBEDDED EEPROM	12/26/1996	19960348712			JP
NMXS-0330.00/JP	Utility - ORG	Abandoned	I/V CONVERTER FOR LOW SUPPLY NON VOLATILE MEMORY CELLS	6/18/1997	19970161556			JP

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MTI Dckt No	Matter Type	Matter Status	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0332.00/JP	Utility - ORG	Issued	CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS	6/18/1997	19970161557	6/8/2007	3958152	JP
NMXS-0335.00/JP	Utility - ORG	Abandoned	BICMOS NEGATIVE CHARGE PUMP	11/6/1997	19970304466			JP
NMXS-0363.00/JP	Utility - ORG	Abandoned	MULTILEVEL NON VOLATILE MEMORY DEVICE	8/22/1997	19970226524			JP
NMXS-0368.00/JP	Utility - ORG	Abandoned	PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES	12/16/1997	19970346843			JP
NMXS-0369.00/JP	Utility - ORG	Abandoned	METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC	9/30/1997	19970265934			JP
NMXS-0370.00/JP	Utility - ORG	Abandoned	PROCESS FOR DEPOSING A STRATIFIED DIELECTRIC STRUCTURE FOR ENHANCING THE PLANARITY OF SEMICONDUCTOR ELECTRONIC DEVICES	12/18/1997	19970348419			JP
NMXS-0371.00/JP	Utility - ORG	Abandoned	PROCESS FOR DEPOSING A MULTIPLE DIELECTRIC STRUCTURE FOR ENHANCING THE PLANARITY OF SEMICONDUCTOR ELECTRONIC DEVICES	12/18/1997	19970349003			JP
NMXS-0372.00/JP	Utility - ORG	Abandoned	READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS	9/29/1997	19970263781			JP
NMXS-0383.00/JP	Utility - ORG	Abandoned	AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES	12/18/1997	19970348835			JP
NMXS-0384.00/JP	Utility - ORG	Abandoned	MEMORY BLOCK FOR REALIZING SEMICONDUCTOR MEMORY DEVICES AND CORRESPONDING MANUFACTURING PROCESS	12/19/1997	19970351800			JP
NMXS-0387.00/JP	Utility - ORG	Issued	METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS	9/30/1997	19970266634	4/6/2007	3939830	JP
NMXS-0388.00/JP	Utility - ORG	Issued	METHOD OF PRODUCING MOSFET TRANSISTORS BY MEANS OF TILTED IMPLANTS	4/20/1998	19980109568	7/10/2009	4336804	JP
NMXS-0392.00/JP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING A NATIVE MOS P-CHANNEL TRANSISTOR WITH A PROCESS FOR MANUFACTURING NON-VOLATILE MEMORIES	8/27/1998	19980242119			JP
NMXS-0394.00/JP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED ELECTRONIC MEMORY DEVICES HAVING A VIRTUAL GROUND CELLS MATRIX	8/27/1998	19980242144			JP
NMXS-0395.00/JP	Utility - ORG	Abandoned	SWITCHING MASTER SLAVE CIRCUIT	1/16/1997	19970095400			JP
NMXS-0396.00/JP	Utility - ORG	Abandoned	MULTIPLE ACCESS MEMORY DEVICE	12/24/1997	19970354236			JP
NMXS-0398.00/JP	Utility - ORG	Abandoned	EXTERNAL WRITE PULSE CONTROL METHOD AND STRUCTURE	12/16/1997	19970345970			JP
NMXS-0399.00/JP	Utility - ORG	Issued	BURN-IN STRESS TEST MODE	12/16/1997	19970346027	1/23/2009	4249812	JP
NMXS-0401.00/JP	Utility - ORG	Abandoned	SENSE AMPLIFIER CONTROL OF A MEMORY DEVICE	4/27/1998	19980116723			JP
NMXS-0402.00/JP	Utility - ORG	Abandoned	CIRCUIT AND METHOD FOR SELECTING A SIGNAL	11/27/1997	19970325600			JP
NMXS-0404.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT THAT SUPPORTS AND METHOD FOR WAFER-LEVEL TESTING	9/17/1997	19970252106			JP
NMXS-0429.00/JP	Utility - ORG	Abandoned	SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT	4/8/1998	957391998			JP
NMXS-0430.00/JP	Utility - NSPCT	Abandoned	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1998	19980531671T			JP
NMXS-0433.00/JP	Utility - ORG	Abandoned	MEMORY DEVICE WITH REDUCED POWER DISSIPATION	3/27/1998	19980080939			JP
NMXS-0445.00/JP	Utility - ORG	Abandoned	DECODER FOR ERASING A SINGLE ROW IN A FLASH MEMORY	11/26/1998	19980335950			JP
NMXS-0455.00/JP	Utility - ORG	Abandoned	HIGH-VOLTAGE DRIVER CIRCUIT FOR THE DECODING PHASE IN MULTILEVEL NON-VOLATILE MEMORY DEVICES	12/28/1998	19980374857			JP
NMXS-0456.00/JP	Utility - ORG	Abandoned	MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	5/27/1999	19990148406			JP
NMXS-0457.00/JP	Utility - ORG	Abandoned	CONTROLLED HOT-ELECTRON PROGRAMMING OF NON VOLATILE MEMORY CELLS	10/9/1998	19980287743			JP
NMXS-0458.00/JP	Utility - ORG	Abandoned	SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF	12/21/1998	19980363349			JP
NMXS-0462.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR REGULATING THE LENGTH OF AN ATD PULSE SIGNAL	11/5/1998	19980315066			JP
NMXS-0464.00/JP	Utility - ORG	Abandoned	IMPROVED OUTUPUT CIRCUIT FOR INTEGRATED CIRCUITS	10/21/1998	19980299381			JP
NMXS-0470.00/JP	Utility - ORG	Issued	DATA PROTECTION METHOD FOR A SEMICONDUCTOR MEMORY AND CORRESPONDING PROTECTED MEMORY DEVICE	12/24/1998	19980367930	6/19/2009	4326054	JP

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MTI DocNum	Matter Type	MatterStatus	Title	FileDate	SerialNo	Issue Date	PatentNo	Country
NMXS-0473.00/JP	Utility ORG	Abandoned	ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS	12/28/1998	19980374358			JP
NMXS-0481.00/JP	Utility - NSPCT	Abandoned	MONOLITHICALLY INTEGRATED SELECTOR FOR MUETILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	20000557477T			JP
NMXS-0484.00/JP	Utility - ORG	Abandoned	CONTROLLED ERASING FOR ANALOG & MULTILEVEL STORAGE IN FLASH EEPROM DEVICE	1/22/1999	19990014078			JP
NMXS-0485.00/JP	Utility - ORG	Abandoned	ESD PROTECTION NETWORK ON SEMICONDUCTOR CIRCUIT STRUCTURES	12/28/1998	19980374718			JP
NMXS-0486.00/JP	Utility - ORG	Abandoned	METHOD AND A CIRCUIT FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	12/25/1998	10-370047			JP
NMXS-0486.01/JP	Utility - DIV	Pending	METHOD AND A CIRCUIT FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR	12/25/1998	2008-251327			JP
NMXS-0487.00/JP	Utility - ORG	Abandoned	HIGH STORAGE CAPACITY NON-VOLATILE MEMORY	5/21/1999	19990140917			JP
NMXS-0488.00/JP	Utility - ORG	Abandoned	PROCESS FOR THE FABRICATION OF A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI)	6/29/1999	19990182990			JP
NMXS-0505.00/JP	Utility - ORG	Abandoned	NON VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING A READ AND/OR WRITE PROTECTABLE AREA AND ELECTRONIC SYSTEM INCLUDINT IT	10/26/1998	19980304597			JP
NMXS-0510.00/JP	Utility - ORG	Issued	RADIO FREQUENCE SIGNAL DETECTOR FOR CONTACT-LESS SMARTCARD	9/24/1998	19980269355	5/12/2000	3065586	JP
NMXS-0516.00/JP	Utility - ORG	Issued	DIFFERENCIAL READING OF NONVOLATILE MEMORY CELLS WITHOUT USING A REFERENCE	5/31/1999	11-152232	3/11/2009	4237337	JP
NMXS-0522.00/JP	Utility ORG	Abandoned	METHOD FOR READING A MULTI-LEVEL MEMORY CELL	3/11/1999	19990064960			JP
NMXS-0523.00/JP	Utility - ORG	Issued	CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES	9/30/1999	19990280024	5/29/2009	4316743	JP
NMXS-0533.00/JP	Utility - ORG	Issued	NON-VOLATILE MEMORY DEVICE WITH ROW REDUNDANCY	5/12/2000	2000-139757	6/10/2011	4757978	JP
NMXS-0535.00/JP	Utility - ORG	Abandoned	PROCESS FOR DEFINITION OF OPENINGS IN A DIELECTRIC LAYER	9/16/1999	19990261939			JP
NMXS-0537.00/JP	Utility - ORG	Abandoned	IMPROVED SELECTIVE SALICIZATION PROCESS FOR SEMICONDUCTOR SUBSTRATE INTEGRATED ELECTRONIC DEVICES	12/28/1999	19990374714			JP
NMXS-0539.00/JP	Utility - ORG	Abandoned	MULTILEVEL NON VOLATILE MEMORY AND READING METHOD THEREFOR	2/10/2000	20000034209			JP
NMXS-0540.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT TO TEST THE VIRGIN CELLS IN A MULTILEVEL MEMORY	10/27/1999	19990304998			JP
NMXS-0545.00/JP	Utility - ORG	Allowed	PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH-PERFORMANCE LOGIC CIRCUITRY	11/25/1999	19990334205			JP
NMXS-0551.00/JP	Utility - ORG	Abandoned	CHIP OUTLINE BAND (COB) STRUCTURE FOR INTEGRATED CIRCUITS	1/14/2000	20000006540			JP
NMXS-0557.00/JP	Utility - ORG	Issued	FLASH COMPATIBLE EEPROM	6/21/2000	2000-186781	6/26/2009	4330057	JP
NMXS-0569.00/JP	Utility - ORG	Abandoned	A SEMICONDUCTOR DEVICE WITH IMPROVED CHIP-LEADS INTERCONNECTIONS AND A PROCESS FOR MANUFACTURING THEREOF	2/9/2000	20000031789			JP
NMXS-0570.00/JP	Utility - ORG	Abandoned	READING METHOD FOR MULTILEVEL MEMORIES WITH SELECTIVE AMPLIFICATION OF CURRENT	2/25/2000	2000-0049429			JP
NMXS-0571.00/JP	Utility - ORG	Abandoned	VOLTAGE REGULATING FOR A CAPACITIVE LOAD	6/30/2000	20000199353			JP
NMXS-0583.00/JP	Utility - ORG	Abandoned	MANUFACTURING PROCESS OF INTEGRATED SOI CIRCUIT STRUCUTRES	4/28/2000	20000130698			JP
NMXS-0592.00/JP	Utility - ORG	Abandoned	READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATION VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD	6/19/2000	20000182753			JP
NMXS-0596.00/JP	Utility - ORG	Abandoned	GERARCHIC SECTOR BIASING FOR FLASH MEMORIES	6/26/2000	20000196230			JP
NMXS-0599.00/JP	Utility - ORG	Abandoned	BIASING THE DRAIN OF A MEMORY CELL DURING READING	6/5/2000	20000171988			JP
NMXS-0603.00/JP	Utility - ORG	Issued	METHOD FOR PROGRAMMING MULTILEVEL NON-VOLATILE MEMORIES BY APPLYING SEQUENCES OF PULSES WITHOUT VERIFY	8/3/2000	2000-0236205	3/5/2010	4469475	JP
NMXS-0604.00/JP	Utility - ORG	Issued	ROW DECODER WITH REDUCED POWER CONSUMPTION DURING SWITCHING	6/5/2000	20000171999	8/12/2005	3707047	JP
NMXS-0605.00/JP	Utility - ORG	Abandoned	ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE	6/19/2000	2000-0187530			JP

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MTI-DocNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0612.00/JP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY WITH BURST AND PAGE READ CAPABILITY DURING ELECTRICAL ALTERATION SUSPEND	7/27/2000	20000227222			JP
NMXS-0615.00/JP	Utility - ORG	Issued	I/V CONVERTER WITH DECOUPLING MEANS FOR THE ARRAY INPUT/OUTPUT NODES	7/21/2000	20000253119	3/11/2005	3655538	JP
NMXS-0619.00/JP	Utility - ORG	Issued	EMBEDDED STAGE FOR DETECTING SHORTCIRCUITS BETWEEN WORDLINES OF NON VOLATILE MEMORIES	9/8/2000	20000272586	11/26/2004	3621334	JP
NMXS-0632.00/JP	Utility - ORG	Issued	NON-VOLATILE MEMORY WITH SINGLE SUPPLY AND HIERARCHICAL ROW DECODING	7/27/2000	20000227650	3/19/2010	4475762	JP
NMXS-0639.00/JP	Utility - ORG	Abandoned	NON-VOLATILE MEMORY DEVICE WITH CONFIGURABLE ROW REDUNDANCY	12/8/2000	20000374346			JP
NMXS-0670.00/JP	Utility - ORG	Issued	INTERLEAVED MEMORY DEVICE FOR BURST TYPE ACCESS IN SYNCHRONOUS READ MODE WITH THE TWO SEMI-ARRAYS INDEPENDENTLY READABLE IN RANDOM ACCESS ASYNCHRONOUS MODE	1/30/2001	20010022134	9/12/2003	3472556	JP
NMXS-0672.00/JP	Utility - NSPCT	Issued	VOLTAGE PRODUCTION CIRCUIT	6/26/2000	2001-508458	7/9/2010	4544802	JP
NMXS-0673.00/JP	Utility - ORG	Abandoned	NEW ARCHITECTURE FOR PAGE MODE IN A NON VOLATILE MEMORY	9/14/2000	20000281033			JP
NMXS-0682.00/JP	Utility - ORG	Abandoned	METHOD AND A CIRCUIT STRUCTURE FOR MODIFYING THE THRESHOLD VOLTAGES OF NON-VOLATILE MEMORY CELLS	7/9/2001	20010207874			JP
NMXS-0699.00/JP	Utility - ORG	Issued	METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY	10/15/2001	20010316940	12/28/2008	4237958	JP
NMXS-0700.00/JP	Utility - ORG	Abandoned	NONVOLATILE MEMORY DEVICE, HAVING PARTS WITH DIFFERENT ACCESS TIME, RELIABILITY, AND CAPACITY	9/20/2001	2001-287008			JP
NMXS-0706.00/JP	Utility - ORG	Abandoned	METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH PROGRAM AND VERIFY ALGORITHM USING A STAIRCASE VOLTAGE WITH VARYING STEP AMPLITUDE	4/10/2002	20020107937			JP
NMXS-0717.00/JP	Utility - ORG	Abandoned	METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL NONVOLATILE MEMORY CELL	1/15/2002	20020006591			JP
NMXS-0719.00/JP	Utility - ORG	Abandoned	METHOD AND DEVICE FOR REDUCING AVERAGE ACCESS TIME OF A NON-VOLATILE MEMORY DURING READING	12/28/2001	20010401897			JP
NMXS-0735.00/JP	Utility - ORG	Pending	LOW POWER CHARGE PUMP CIRCUIT	10/16/2002	20020302131			JP
NMXS-0749.00/JP	Utility - NSPCT	Abandoned	PAGE-ERASABLE FLASH MEMORY	11/14/2001	20010543444T			JP
NMXS-0751.00/JP	Utility - ORG	Issued	METHOD AND DEVICE FOR SEQUENTIAL READOUT OF A MEMORY WITH ADDRESS JUMP	2/22/2002	20020046868	11/21/2008	4217803	JP
NMXS-0762.00/JP	Utility - ORG	Abandoned	MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS	9/30/2002	20020287067			JP
NMXS-0769.00/JP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING MEMORY CELL	10/7/2002	20020294069			JP
NMXS-0774.00/JP	Utility - ORG	Abandoned	SELF-REPAIR METHOD FOR NON VOLATILE MEMORY DEVICE WITH ERASING/PROGRAMMING FAILURE DETECTION, AND NON VOLATILE MEMORY DEVICE THEREFOR	5/20/2003	2003-0142641			JP
NMXS-0774.01/JP	Utility - ORG	Pending	SELF-REPAIR METHOD FOR NON VOLATILE MEMORY DEVICE WITH ERASING/PROGRAMMING FAILURE DETECTION, AND NON VOLATILE MEMORY DEVICE THEREFOR	5/20/2003	2010-106014			JP
NMXS-0777.00/JP	Utility - ORG	Issued	SMALL AREA CONTACT REGION, HIGH EFFICIENCY PHASE CHANGE MEMORY CELL AND FABRICATION METHOD THEREOF	12/5/2002	20020353352	4/22/2011	4729236	JP
NMXS-0791.00/JP	Utility - ORG	Abandoned	REDUNDANCY CIRCUIT AND METHOD FOR SEMICONDUCTOR MEMORY DEVICES	6/2/2003	20030157166			JP
NMXS-0801.00/JP	Utility - ORG	Issued	SECTOR PROTECTION CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	8/1/2002	2002-0224398	9/11/2009	4373057	JP
NMXS-0802.00/JP	Utility - ORG	Abandoned	DUAL BANK FLASH MEMORY DEVICE AND METHOD	8/1/2002	20020224653			JP
NMXS-0803.00/JP	Utility - ORG	Abandoned	REDUNDANCY CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES	8/1/2002	20020225117			JP
NMXS-0804.00/JP	Utility - ORG	Abandoned	REDUNDANCY CIRCUIT AND METHOD FOR REPLACING DEFECTIVE MEMORY CELLS IN A FLASH MEMORY DEVICE	8/2/2002	20020225924			JP
NMXS-0830.00/JP	Utility - ORG	Allowed	MAGNITUDE CONTENT ADDRESSABLE MEMORY	10/21/2004	2004 307123			JP

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Matter No.	Matter Type	Matter Status	Title	File Date	Serial No.	Issue Date	Patent No.	Country
NMXS-0991.00/JP	Utility - ORG	Pending	MEMORY DEVICE WITH RAMP-LIKE VOLTAGE BIASING STRUCTURE BASED ON CURRENT GENERATOR	1/24/2006	20060015176			JP
NMXS-0997.00/JP	Utility - NSPCT	Pending	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/1/2006	2008-514105			JP
NMXS-1021.00/JP	Utility - ORG	Pending	METHOD AND DEVICE FOR IRREVERSIBLY PROGRAMMING AND READING NONVOLATILE MEMORY CELLS	10/3/2008	2008-260494			JP
NMXS-1041.00/JP	Utility - NSPCT	Pending	SEMICONDUCTOR FIELD-EFFECT TRANSISTOR, MEMORY CELL AND MEMORY DEVICE	3/20/2006	2009-0501022			JP
NMXS-1078.00/JP	Utility - NSPCT	Pending	PHASE CHANGE MEMORY DEVICE	7/26/2007	2009521273			JP
NMXS-1082.00/JP	Utility - ORG	Pending	PHASE CHANGE MEMORY DEVICE FOR MULTIBIT STORAGE	9/8/2008	2008-261125			JP
NMXS-1104.00/JP	Utility - ORG	Abandoned	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	10/22/1985	19850234661			JP
NMXS-1105.00/JP	Utility - ORG	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	12/12/1986	19860295058	8/9/1996	2080095	JP
NMXS-1106.00/JP	Utility - ORG	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/29/1987	19870132028	12/20/1996	2120910	JP
NMXS-1107.00/JP	Utility - ORG	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	7/10/1987	19870171373			JP
NMXS-1108.00/JP	Utility - ORG	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	5/6/1988	19880109969	12/5/1996	2588582	JP
NMXS-1109.00/JP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS	12/21/1988	19880324718	8/14/1998	2814092	JP
NMXS-1110.00/JP	Utility - ORG	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/27/1989	19890119374	5/22/1998	2784023	JP
NMXS-1111.00/JP	Utility - ORG	Abandoned	CMOS VOLTAGE MULTIPLIER	6/28/1989	19890166506			JP
NMXS-1112.00/JP	Utility - ORG	Abandoned	CMOS LOGIC CIRCUIT FOR HIGH VOLTAGE OPERATION	7/6/1989	19890175408			JP
NMXS-1113.00/JP	Utility - ORG	Abandoned	FABRICATION OF CMOS DEVICES WITH REDUCED GATE LENGTH	7/28/1989	19890196482			JP
NMXS-1114.00/JP	Utility - ORG	Abandoned	FABRICATION OF CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTH AND LIGHTLY DOPED DRAIN	8/3/1989	19890202260			JP
NMXS-1116.00/JP	Utility - ORG	Abandoned	PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS	12/28/1989	19890345077			JP
NMXS-1117.00/JP	Utility - ORG	Expired	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/11/1990	19900409654	6/15/2001	3199388	JP
NMXS-1118.00/JP	Utility - ORG	Abandoned	VOLTAGE-BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER	2/15/1991	19910344454			JP
NMXS-1119.00/JP	Utility - ORG	Abandoned	READING CIRCUIT FOR NONVOLATILEMEMORY CELL.	2/23/1991	19910050404	1/5/2001	3145722	JP
NMXS-1120.00/JP	Utility - ORG	Abandoned	METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE	3/27/1991	19910085967			JP
NMXS-1121.00/JP	Utility - ORG	Abandoned	METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS	4/26/1991	19910125538			JP
NMXS-1122.00/JP	Utility - ORG	Abandoned	DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE	4/26/1991	19910123019			JP
NMXS-1123.00/JP	Utility - ORG	Abandoned	READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS	7/4/1991	19910164266	5/11/2001	3184984	JP
NMXS-1124.00/JP	Utility - ORG	Abandoned	METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK	10/1/1991	19910280664			JP
NMXS-1125.00/JP	Utility - ORG	Abandoned	MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY	10/2/1991	19910255966			JP
NMXS-1126.00/JP	Utility - ORG	Abandoned	TWO PHASES SCAN PATH WITH SINGLECLOCK.	10/22/1991	19910273791	3/26/1999	2903441	JP
NMXS-1127.00/JP	Utility - ORG	Abandoned	COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES	11/19/1991	19910308540			JP

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NMXS-1128.00/JP	Utility - ORG	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/19/1991	19910308589	12/20/2007	3387860	JP
NMXS-1129.00/JP	Utility - ORG	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/12/1991	19910329074	9/21/2001	3233424	JP
NMXS-1130.00/JP	Utility - ORG	Abandoned	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/27/1991	19910346043			JP
NMXS-1131.00/JP	Utility - ORG	Abandoned	MEMORY CELL READING CIRCUIT	12/27/1991	19910346044	2/21/2003	3401024	JP
NMXS-1132.00/JP	Utility - ORG	Abandoned	CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES	5/11/1992	19920144910	5/17/2002	3307423	JP
NMXS-1133.00/JP	Utility - ORG	Abandoned	SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL	7/25/1992	19920218578			JP
NMXS-1134.00/JP	Utility - ORG	Abandoned	ZERO-CONSUMPTION POWER-ON RESET CIRCUIT	8/31/1992	19920255857			JP
NMXS-1135.00/JP	Utility - ORG	Abandoned	ROW DECODER FOR NAND-TYPE ROM	8/31/1992	19920255858			JP
NMXS-1136.00/JP	Utility - ORG	Abandoned	PLANARIZED CONTACT WITH A SANDWICH OF TUNGSTEN AND ALUMINIUM.	11/20/1992	19920311734			JP
NMXS-1137.00/JP	Utility - ORG	Abandoned	PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS	11/30/1992	19920320695			JP
NMXS-1139.00/JP	Utility - ORG	Abandoned	METALLIZATION OVER TUNGSTEN PLUGS	5/27/1993	19930151415			JP
NMXS-1140.00/JP	Utility - ORG	Abandoned	LOW SWITCHING NOISE OUTPUT BUFFER	6/28/1993	19930184492	7/11/2003	3449752	JP
NMXS-1141.00/JP	Utility - ORG	Abandoned	INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS	6/28/1993	19930157309	12/7/2001	3258770	JP
NMXS-1142.00/JP	Utility - ORG	Abandoned	VOLTAGE REGULATOR FOR MEMORY DEVICE	6/30/1993	19930162326			JP
NMXS-1143.00/JP	Utility - ORG	Abandoned	METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS	9/27/1993	19930240027			JP
NMXS-1144.00/JP	Utility - ORG	Abandoned	NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION	6/28/1993	19930184490			JP
NMXS-1145.00/JP	Utility - ORG	Abandoned	METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	10/29/1993	19930272484			JP
NMXS-1146.00/JP	Utility - ORG	Abandoned	METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES	11/17/1993	19930311209			JP
NMXS-1147.00/JP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS	1/28/1994	19940008653	6/21/2002	3320542	JP
NMXS-1148.00/JP	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS	1/27/1994	19940007807			JP
NMXS-1149.00/JP	Utility - ORG	Abandoned	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS	2/10/1994	19940016744			JP
NMXS-1150.00/JP	Utility - ORG	Issued	PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION	2/17/1994	19940020549	10/15/2004	3606596	JP
NMXS-1151.00/JP	Utility - ORG	Abandoned	NONVOLATILE EPROM, EEPROM OF FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION	2/17/1994	19940020548			JP
NMXS-1152.00/JP	Utility - ORG	Abandoned	NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS	3/17/1994	19940047208			JP
NMXS-1153.00/JP	Utility - ORG	Issued	METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS	3/17/1994	19940047209	5/14/2004	3553121	JP
NMXS-1154.00/JP	Utility - ORG	Issued	SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS	3/29/1994	19940058787	11/12/2004	3615561	JP
NMXS-1155.00/JP	Utility - ORG	Abandoned	METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES	10/29/1993	19930272485			JP
NMXS-0001.00/KR	Utility - ORG	Abandoned	METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINEDTHEREBY	12/12/1988	19880016607			KR
NMXS-0002.00/KR	Utility - ORG	Abandoned	METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT	12/20/1988	19880017186			KR
NMXS-0003.00/KR	Utility - ORG	Abandoned	ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL	4/25/1989	19890005514			KR
NMXS-0011.00/KR	Utility - ORG	Abandoned	CONTENT ADDRESSABLE MEMORY	5/30/1991	19910008893	11/1/1999	100228623B	KR
NMXS-0012.00/KR	Utility - ORG	Abandoned	REDUNDANCY FOR SERIAL MEMORY	1/12/1991	9100434			KR

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MII Docket	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNo	Country
NMXS-0013.00/KR	Utility - ORG	Abandoned	POLYCRYSTALLINE SILICON CONTACT STRUCTURE	4/30/1991	9106936			KR
NMXS-0014.00/KR	Utility - ORG	Abandoned	DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	12/21/1990	9021543			KR
NMXS-0015.00/KR	Utility - ORG	Abandoned	PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE	10/16/1991	9118205			KR
NMXS-0016.00/KR	Utility - ORG	Expired	TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL	8/24/1990	19900013107	10/15/1999	100223623B	KR
NMXS-0017.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY	8/17/1991	19910014249	7/1/1999	100206532B	KR
NMXS-0018.00/KR	Utility - ORG	Abandoned	DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY	7/22/1991	9112588			KR
NMXS-0019.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE	7/13/1991	9112074			KR
NMXS-0020.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/13/1991	19910014157	7/1/1999	100205445B	KR
NMXS-0021.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY	8/16/1991	19910014247	7/1/1999	100205449B	KR
NMXS-0022.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/20/1991	9116585			KR
NMXS-0023.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION	9/25/1991	9116651			KR
NMXS-0024.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY	8/16/1991	19910014248	7/1/1999	100205451B	KR
NMXS-0025.00/KR	Utility - ORG	Abandoned	INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK	10/12/1991	9118780			KR
NMXS-0026.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS	9/25/1991	9116845			KR
NMXS-0027.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS	9/19/1991	9116584			KR
NMXS-0028.00/KR	Utility - ORG	Abandoned	ADDRESS BUFFER CIRCUIT HAVING LATCHING BASED ON TRANSITION	10/16/1991	9118206			KR
NMXS-0029.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH PRECHARGED REDUNDANCY MULTIPLEXING	12/14/1991	19910023050	3/2/2000	100237583B	KR
NMXS-0030.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH COLUMN DECODED BIT LINE EQUILIBRATE	12/3/1991	9122168			KR
NMXS-0031.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS	12/14/1991	19910023049	11/1/1999	100228620B	KR
NMXS-0032.00/KR	Utility - ORG	Abandoned	SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY	12/14/1991	9123051			KR
NMXS-0036.00/KR	Utility - ORG	Abandoned	CACHE TAG PARITY DETECT CIRCUIT	3/28/1992	9205255			KR
NMXS-0997.00/KR	Utility - NSPCT	Pending	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	12/24/2007	2007-7030076			KR
NMXS-1021.00/KR	Utility - ORG	Pending	METHOD AND DEVICE FOR IRREVERSIBLY PROGRAMMING AND READING NONVOLATILE MEMORY CELLS	9/26/2008	10-2008-0094576			KR
NMXS-1041.00/KR	Utility - NSPCT	Abandoned	SEMICONDUCTOR FIELD-EFFECT TRANSISTOR, MEMORY CELL AND MEMORY DEVICE	3/20/2006	2008 7025440			KR
NMXS-1078.00/KR	Utility - NSPCT	Pending	PHASE CHANGE MEMORY DEVICE	7/26/2007	10-2009-7003416			KR
NMXS-1082.00/KR	Utility - ORG	Pending	PHASE CHANGE MEMORY DEVICE FOR MULTIBIT STORAGE	9/8/2008	1020080088362			KR
NMXS 1117.00/KR	Utility - ORG	Abandoned	METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS	12/12/1990	19900038410	5/20/1999	0179360B	KR
NMXS-1129.00/KR	Utility - ORG	Abandoned	SENSE CIRCUIT FOR STORAGE DEVICES SUCH A NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION	12/10/1991	9122529			KR
NMXS-1130.00/KR	Utility - ORG	Abandoned	FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES	12/27/1991	9124736			KR

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NMXS-1131.00/KR	Utility - ORG	Abandoned	MEMORY CELL READING CIRCUIT	12/28/1991	9125096			KR
NMXS-1104.00/NL	Utility - ORG	Abandoned	REDUCED-BEAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS	10/7/1985	8502733	8/3/1999	193393	NL
NMXS-1105.00/NL	Utility - EPPAT	Abandoned	METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING	10/9/1986	86830293.6	8/29/1990	0226549	NL
NMXS-1106.00/NL	Utility - EPPAT	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/29/1987	87830204.1	2/27/1991	0256993	NL
NMXS-1107.00/NL	Utility - EPPAT	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/22/1987	87830234.8	4/21/1993	0255489	NL
NMXS-1108.00/NL	Utility - EPPAT	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	5/4/1988	88107152.6	9/9/1992	0298215	NL
NMXS-1110.00/NL	Utility - EPPAT	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	89100780.9	10/20/1993	0326004	NL
NMXS-1111.00/NL	Utility - EPPAT	Abandoned	CMOS VOLTAGE MULTIPLIER	6/16/1989	89830269.0	2/9/1994	0349495	NL
NMXS-1106.00/SE	Utility - EPPAT	Abandoned	ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE	5/29/1987	87830204.1	2/27/1991	0246993	SE
NMXS-1107.00/SE	Utility - EPPAT	Abandoned	NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE	6/22/1987	87830234.8	4/21/1993	0255489	SE
NMXS-1108.00/SE	Utility - EPPAT	Abandoned	GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS	5/4/1988	88107152.6	9/9/1992	0298215	SE
NMXS-1110.00/SE	Utility - EPPAT	Abandoned	CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR	1/18/1989	89100780.9	10/20/1993	0326004	SE
NMXS-1111.00/SE	Utility - EPPAT	Abandoned	CMOS VOLTAGE MULTIPLIER	6/16/1989	89830269.0	2/9/1994	0349495	SE
NMXS-1021.00/SG	Utility - ORG	Issued	METHOD AND DEVICE FOR IRREVERSIBLY PROGRAMMING AND READING NONVOLATILE MEMORY CELLS	9/22/2008	200807017-9	9/15/2011	151220	SG
NMXS-0875.00/TW	Utility - ORG	Abandoned	AUTOMATIC DECODING METHOD FOR MAPPING AND SELECTING A NON-VOLATILE MEMORY DEVICE HAVING A LPC SERIAL COMMUNICATION INTERFACE IN THE AVAILABLE ADDRESSING AREA ON MOTHERBOARDS	6/25/2003	92117298			TW
NMXS-0880.00/TW	Utility - ORG	Abandoned	MEMORY DEVICE ACCESSIBLE WITH DIFFERENT COMMUNICATION PROTOCOLS	9/4/2003	92124462			TW
NMXS-1082.00/TW	Utility - ORG	Pending	PHASE CHANGE MEMORY DEVICE FOR MULTIBIT STORAGE	9/5/2008	97134288			TW
NMXS-1128.00/TW	Utility - ORG	Lapsed	SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH COMPENSATED OFFSET CURRENT	11/25/1991	81205632	9/11/1992	076142	TW
NMXS-0262.00/PC	Utility - ORG	Completed	MULTILEVER MEMORY CIRCUIT WITH REGULATED READING VOLTAGE	10/30/1996	PCT/IT96/000198			WO
NMXS-0264.00/PC	Utility - ORG	Abandoned	MULTILEVEL MEMORY CIRCUIT WITH REGULATED WRITINGVOLTAGE	10/30/1996	ITS600199			WO
NMXS-0430.00/PC	Utility - ORG	Completed	METHOD FOR PROGRAMMING A FLASH EPROM-TYPE FOR MEMORY	1/22/1998	PCT/FR98/00111			WO
NMXS-0481.00/PC	Utility - ORG	Completed	MONOLITHICALLY INTEGRATED SELECTOR FOR MULTILEVEL ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES	6/30/1999	PCT/I899/01225			WO
NMXS-0672.00/PC	Utility - ORG	Completed	CIRCUIT FOR THE PRODUCTION OF HIGHT VOLTAGE FOR THE PROGRAMMING OF A MEMORY	6/26/2000	PCT/FR00/01776			WO
NMXS-0749.00/PC	Utility - ORG	Abandoned	PAGE-ERASABLE FLASH MEMORY	11/14/2001	FR0103560			WO
NMXS-0753.00/PC	Utility - ORG	Abandoned	CONTACT LESS IC CARD WITH OPERATING SYSTEM USED IN CONTACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS	2/14/2002	PCT/FR02/00573			WO
NMXS-0867.00/PC	Utility - ORG	Abandoned	ELEKTONENSPEKTROSKOP MIT EMISSION, DIE DURCH EINEN MONOCHROMATISCHEN ELEKTRONENSTRAHL INDUZIERT WIRD	10/6/2004	PCT/IT04/00555			WO
NMXS-0885.00/PC	Utility - ORG	Abandoned	EEPROM MEMORY COMPRISING A NON-VOLATILE REGISTER INTEGRATED INTO THE MEMORY ARRAY THEREOF	8/21/2003	FR0302559			WO
NMXS-0997.00/PC	Utility - ORG	Completed	METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM	6/1/2006	PCT/EP06/062812			WO
NMXS-1029.00/PC	Utility - ORG	Abandoned	METHOD AND SYSTEM FOR DETECTING THE END POINT IN PLASMA ETCH	4/5/2005	IT0500187			WO
NMXS-1029.01/PC	Utility - ORG	Abandoned	METHOD AND SYSTEM FOR DETECTING THE END POINT IN PLASMA ETCH	4/4/2006	IT0600223			WO
NMXS-1041.00/PC	Utility - ORG	Completed	SEMICONDUCTOR FIELD-EFFECT TRANSISTOR, MEMORY CELL AND MEMORY DEVICE	3/20/2006	PCT/IT06/00170			WO
NMXS-1078.00/PC	Utility - ORG	Pending	PHASE CHANGE MEMORY DEVICE	7/26/2007	PCT/EP2007/057706			WO

Exhibit C - Foreign Applications and Patents

MD-DcktNo	MatterType	MatterStatus	Title	FileDate	SerialNo	IssueDate	PatentNO	Country
NMXS-1157.00/PC	Utility - ORG	Abandoned	METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY	10/9/1992	FR9200951			WO